

W. Eckstein

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Abstract

The Monte Carlo program TRIM.SP was applied to calculate sputtering yields, reflection coefficients and mean ranges. Tables of these values are produced in the energy range from 10 eV to 300 keV and for several angles of incidence. Li, Be, B, C, Mg, Al, Si, P, Ti, Fe, Ni, Cu, Ga, Ge, Nb, Mo, Ag, In, Cs, Sm, Ta, W, Pt, Au, Hg and U are chosen as one-component target materials, BeO, B₄C, B₂O₃, B(OH)₃, SiO₂, TiC, WO₃, WO₄, W_xO_y as more component targets. Some examples for layered structures are also given. //, H, D, T, ³He, ⁴He, C, N, O, Ne, Na, Mg, Al, P, Ar, K, Kr, Xe, Hg, Bi and Rn are selected as projectiles. Selfbombardment and an incident Maxwellian distribution is regarded for some cases, too.

0.1 Introduction

This report gives a collection of sputtering, reflection and range values calculated in the last decade (approximately), it is also an extension of an earlier report [1]. Whereas [1] only data for Be, C, and W targets are presented, this report gives data for other targets, too. In contrast to [1], the data in this report are given in exponential form to present more accurate values at low ion energies. Calculated sputtering yields from an earlier report are also included [2].

0.2 The model

The vectorized version of TRIM.SP [3, 4] and different versions of it were applied. The basis is a randomized target structure and the binary collision approximation. In most cases the KrC potential [5] is applied as interaction potential, but some examples are calculated with the Moliere [6], ZBL [8] and a special potential for Si [9]. The integration for getting the scattering angle is usually performed with the procedure 'magic' [7], but in a few cases also with the Gauss-Mehler procedure [10, 2]. For the inelastic energy loss an equipartition of the Lindhard-Scharff (LS) [11] and the Oen-Robinson (OR) [12] models is chosen mostly, but at high energies the Andersen-Ziegler (AZ) tables for H [13] and the Ziegler tables (Z) for He [14] are used. Further details can be found in [2]. As surface binding energy the heat of sublimation is used (see table 6.1 in [2]). For the hydrogen isotopes and nitrogen a binding energy $e_{sb} = -1$ eV is chosen for these projectiles which leads to an acceleration of the incoming species and to a decrease in the angle of incidence; it has further an influence on the backscattered species (deceleration and increase in exit angle) in the same way as the surface binding energy effects the sputtered atoms. The statistical errors in the sputtering yields and reflection coefficients are usually smaller than 3% (1 σ) for values larger than 10^{-5} and may reach 100% at the lowest values.

0.3 Data Representation

The calculated values are given in tables. The tables are arranged in such a way that lines give an angular dependence of sputtering yields at a fixed energy e_0 , and columns give an energy dependence at a fixed angle of incidence, α . In special cases this arrangement is changed. On top of the tables the input values are given:

z1	projectile (ion) atomic number
m1	projectile mass
z2	target atomic number
m2	target mass
c2	target atomic fraction
Eq	projectile energy (eV)
alpha	angle of incidence
nh	number of histories (= number of projectiles)
sbe	surface binding energy (eV) for target atoms
rlio	atomic target density (g/cm ³)
ef	cutoff energy (eV), to stop calculation
esb	projectile binding energy (eV)
ca	correction factor to the screening length in the potential
kkO	number of ring cylinders for weak simultaneous collisions (proj.)
kkOr	number of ring cylinders for weak simultaneous collisions (recoils)
kdeel	inelastic loss model for projectiles (1: LS, 2: OR, 3: (LS+OR)/2, 4: AZ for H, 5: Z for He)
kdee2	inelastic loss model for target atoms (1: LS, 2: OR, 3: (LS+OR)/2)
ipot	interaction potential for projectiles (1: KrC, 2: Moliere, 3: ZBL, 4: Si potential)
ipotr	interaction potential for target atoms (1: KrC, 2: Moliere, 3: ZBL, 4: Si potential)
program	this gives the version used for the calculation
ne	number of projectile energies in the table
na	number of incident angles in the table
dx	depth interval (Å)

For most projectile - target combinations five tables are produced: sputtering yields, sputtered energies, particle reflection coefficients, energy reflection coefficients, and average depths of implanted atoms. The definitions are: the sputter yield, Y , is the number of sputtered atoms per projectile, the sputtered energy, Y_e , is the mean energy taken away by sputtered atoms per projectile energy, the particle reflection coefficient, R_{jy} , is the fraction of backscattered projectiles (not implanted or transmitted), and the energy reflection coefficient, $/?\#$, is the fraction of the incident energy carried by the reflected projectiles. In a few cases also transmission has been investigated. T_n and T_e are the particle and energy transmission coefficients. YT and YTe are the forward sputtering yield and the forward sputtered energy, respectively.

Input values different from the usually chosen values are indicated by italic style. If the input values are the same, they are not repeated at the same page.

The data are stored at /afs/ipp/u/wge/reports/rep02. The data in the tables of the report are stored in the corresponding subdirectories; their names represent the target species. More data for other projectile-target combinations, but mostly for single energy and angle, can be found in /afs/ipp/m/wge/result/trim.

0.4 Data Use

The calculated values are valid for nearly flat surfaces.

The energy distribution of the sputtered atoms can be described in a first order approximation by a Thompson distribution:

$$f(E)dE = \frac{F}{\sqrt{C_y - j}} \frac{dE}{J} \quad (0.1)$$

Applying this distribution an energy E can be determined by a pseudorandom number r due to the formula

$$\frac{E}{E_s} = \frac{1}{(1 + 1/a)^{1/r} - 1} \quad (0.2)$$

where E_s is the surface binding energy and a the maximum transferable energy divided by the surface binding energy

$$a = \frac{4m_1 m_2}{(m_1 + m_2)^2} \frac{E_0}{E_s} \quad (0.3)$$

The mean energy $\langle E \rangle$ of sputtered atoms for a constant incident energy is given by

$$\langle E(E_0, \alpha) \rangle = E_0 \frac{Y_E(E_0, \alpha)}{Y(E_0, \alpha)} \quad (M)$$

For an incident Maxwellian distribution the mean energy is provided in the corresponding table.

The angular distribution of sputtered atoms can be approximated by a cosine distribution in a first approximation. An exit angle θ can again be determined by a random number r

$$\theta = \arcsin r \quad (0-5)$$

For backscattered atoms the situation is more difficult, because simple formulae for the energy and angular distributions do not exist. As for sputtered atoms the mean energy of reflected atoms can be determined for a constant incident energy by

$$\langle E(E_0, \alpha) \rangle = E_0 \frac{R_E(E_0, \alpha)}{t_i N(n_0, a)} \quad (0.6)$$

For rough surfaces the angular dependence of the sputtering yield and the reflection coefficients is less pronounced as given in the tables.

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The numbers in the table are the page numbers at which the corresponding data are presented. The lines of the table give the data for the same projectile (in italic style), the rows for the same target atom.

mono-atomic targets

	Li	Be	B	C	Al	Si	Ti	V	Fe	Ni	Cu	Ga	Ge	Zr	Nb
<i>P</i>		14		41		82			119						
<i>H</i>	7	16	37	44	76	83	104	111	114	120	138				165
<i>D</i>	10	20	47						114	121	139	152			
<i>T</i>									115			154			
<i>³He</i>		22								121					
<i>⁴He</i>	11	23		50	77	84	105		116	122	141				
<i>Li</i>	12														
<i>Be</i>		25		52											
<i>B</i>			39												
<i>C</i>				53		85									
<i>N</i>		30		62											
<i>O</i>		32	40	65											
<i>Ne</i>		33		66	78	85	106			124	143				
<i>Mg</i>						86								160	
<i>Al</i>					79	86								160	
<i>Si</i>						87								161	
<i>P</i>						100								161	
<i>Ar</i>	35			68	81	101	108			128	144			162	
<i>Ti</i>							109								
<i>V</i>								112							
<i>Fe</i>									118						
<i>Ni</i>										132					
<i>Cu</i>											146				
<i>Ga</i>												156			
<i>Kr</i>														164	
<i>Xe</i>				72		102				134	151				
<i>Hg</i>										136		159			
<i>Bi</i>						103							163		

	Mo	Pd	Ag	Tn	Cs	Sm	Ta	W	Pt	Au	Hg	U
<i>P</i>										242		
<i>H</i>	166			196			207	208				257
<i>D</i>	167		190	197				211		243		
<i>T</i>	170			199				214				
<i>⁴He</i>	172	188	191					217	239	246		258
<i>C</i>	175							219				
<i>N</i>								221				
<i>O</i>	175							224				
<i>Ne</i>	176							224	240	248		258
<i>Na</i>			192							249		
<i>Ar</i>	177		193					226		250		258
<i>K</i>			194							251		
<i>Kr</i>	180					205					255	259
<i>Mo</i>	181											
<i>In</i>				201								
<i>Xe</i>	185	189	195						241	252		260
<i>Cs</i>					203							
<i>W</i>								229				
<i>Au</i>										253		
<i>Hg</i>	186											
<i>Rn</i>	187											260
<i>U</i>												261

compound targets

	BeO	B ₂ C	B ₂ O ₃	B(OH) ₃	SiO ₂	TiC	WO ₃	WO ₄	W ₅ O ₁₅
<i>μ</i>					280				
<i>H</i>		266				281			
<i>D</i>		268							
<i>⁴He</i>		271							
<i>C</i>		274							
<i>o</i>	263	276	278	279			282	287	288
<i>Ne</i>		277					285		
<i>Kr</i>							286		

layered targets

	Li on Cu	Li on LiCu	B ₂ O ₃ on B	B ₂ O ₃ on B ₄ C	B(OH) ₃ on B	B(OH) ₃ on B ₄ C	O on WO ₃	WO ₃ on W
<i>D</i>		295						
<i>O</i>			301	303	305	307	310	311
<i>Ar</i>	291	299						

Mono-atomic targets

D -4 Li

Sputtering yield of Li by D

z1 = 1. m1 = 2.01, z2 = 3. m2 = 6.94, sbe = 1.67 eV, rho = 0.53 g/cm **3
 ef = 0.98 eV, esb = 1.00 eV. ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : testvmcx, IPP 9/82
 ne = 14, na = 2

E ₀ (eV)	0°	65°
10	3.81e-3	2.10e-2
15	9.88e-3	6.36e-2
20	1.58e-2	1.10e-1
30	2.38e-2	1.76e-1
50	3.30e-2	2.55e-1
70	3.87e-2	2.97e-1
100	4.22e-2	3.28e-1
200	4.45e-2	3.44e-1
300	4.10e-2	
500	3.41e-2	2.91e-1
1000	2.67e-2	2.06e-1
2000	1.81e-2	1.38e-1
5000	1.04e-2	7.08e-2
10000	6.93e-3	3.68e-2

Sputtered energy of Li by D

program : testvmcx
 ne = 13, na = 2

E ₀ (eV)	0°	65°
10	2.98e-4	3.21e-3
15	7.92e-4	9.43e-3
20	1.21e-3	1.50e-2
30	1.65e-3	2.11e-2
50	1.81e-3	2.39e-2
70	1.88e-3	2.41e-2
100	1.78e-3	2.21e-2
200	1.26e-3	1.65e-2
500	4.66e-4	9.04e-3
1000	2.50e-4	4.77e-3
2000	9.72e-5	1.97e-3
5000	3.33e-5	6.75e-4
10000	1.48e-5	2.31e-4

D -> Li

Particle reflection coefficient of D backscattered from Li
 z1 = 1. m1 = 2.01. z2 = 3. m2 = 6.94. sbe = 1.67 eV. rho=0.53 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipot=1 (KrC)
 program : testvmcx
 ne=13. na= 2

E ₀ (eV)	0°	65°
10	1.50e-1	5.48e-1
15	1.46e-1	5.31e-1
20	1.39e-1	5.09e-1
30	1.30e-1	4.70e-1
50	1.16e-1	4.24e-1
70	1.06e-1	4.02e-1
100	9.40e-2	3.80e-1
200	6.92e-2	3.36e-1
500	4.18e-2	2.83e-1
1000	2.28e-2	2.34e-1
2000	1.02e-2	1.86e-1
5000	3.28e-3	1.01e-1
10000	1.30e-3	4.92e-2

Energy reflection coefficient of D backscattered from Li
 program : testvmcx
 ne=13. na= 2

E ₀ (eV)	0°	65°
10	3.76e-2	3.07e-1
15	3.74e-2	3.03e-1
20	3.58e-2	2.87e-1
30	3.33e-2	2.56e-1
50	2.93e-2	2.23e-1
70	2.65e-2	2.06e-1
100	2.37e-2	1.88e-1
200	1.68e-2	1.61e-1
500	9.56e-3	1.25e-1
1000	4.86e-3	9.16e-2
2000	1.94e-3	6.21e-2
5000	5.52e-4	2.27e-2
10000	1.77e-4	8.20e-3

Average depth (mean range) in Å of D implanted in Li
 program : testvmcx
 ne=13. na= 2

E ₀ (eV)	0°	65°
10	1.25e+1	9.30e+0
15	1.70e+1	1.28e+1
20	2.13e+1	1.59e+1
30	2.94e+1	2.17e+1
50	4.49e+1	3.24e+1
70	6.01e+1	4.34e+1
100	8.24e+1	5.83e+1
200	1.58e+2	1.08e+2
500	3.90e+2	2.47e+2
1000	7.76e+2	4.61e+2
2000	1.52e+3	8.21e+2
5000	3.44e+3	1.66e+3
10000	5.99e+3	2.68e+3

D -> Li

Sputtering yield of Li by D
 z1= 1. m1= 2.01. z2= 3. m2= 6.94. sbe = eV. rho=0.53 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program : testvmx
 ne= 3. na= 2. n(sbe) = 4

sbe(eV)	1.60	1.90	2.20	2.50	2.20	2.50
Eo(eV)	0°	0°	0°	0°	65°	65°
30			5.90e-4	1.05e-4		
50	2.18e-2	1.29e-2	7.81e-3	4.50e-3	6.09e-3	3.23e-3
100	4.92e-2	3.57e-2	2.65e-2	2.05e-2		

Sputtered energy of Li by D
 ne= 3. na= 2. n(sbe) = 4

sbe(eV)	1.60	1.90	2.20	2.50	2.20	2.50
Eo(eV)	0°	0°	0°	0°	65°	65°
30			6.92e-6	8.83e-7		
50	4.75e-4	2.75e-4	1.58e-4	8.55e-5	1.30e-4	6.51e-5
100	9.74e-4	7.40e-4	5.51e-4	4.45e-4		

D ->Li

D on Li. Maxwellian velocity distribution, sheath potential 0 kT
 z1= 1. m1= 2.01. z2= 3. m2= 6.94. sbe = 1.67 eV. rho= 0.53 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program: testvmx
 ne=11

kT(eV)	Y	Ye	Esp	R _N	* _F	E _s	range
2	1.83e-3	6.58e-4	1.44e-f-0	2.04e-1	1.25e-1	2.45e+0	4.50e4-0
5	1.89e-2	4.33e-3	2.29e+0	3.04e-1	1.63e-1	5.36e+0	9.90e4-0
10	5.18e-2	8.25e-3	3.19e+0	3.24e-1	1.59e-1	9.84e+0	1.78eR1
20	9.83e-2	1.09e-2	4.42e+0	3.08e-1	1.44e-1	1.87e+1	3.22e+1
50	1.53e-1	9.92e-3	6.47e+0	2.70e-1	1.17e-1	4.33e+1	7.18e+1
100	1.74e-1	7.82e-3	8.93e-f-0	2.34e-1	9.77e-2	8.30e+1	1.34e+2
200	1.71e-1	4.95e-3	1.16e+1	2.00e-1	7.73e-2	1.54e+2	2.59e+2
500	1.39e-1	2.57e-3	1.84e+1	1.52e-1	5.27e-2	3.44e+2	6.03e+2
1000	1.05e-1	1.22e-3	2.32e+1	1.15e-1	3.40e-2	5.92e+2	1.12e+3
2000	7.19e-2	5.11e-4	2.83e+1	8.44e-2	2.12e-2	9.98e+2	1.97eR3
5000	3.93e-2	1.39e-4	3.54e+1	5.25e-2	1.00e-2	1.91e4-3	3.95e4-3

D on Li . Maxwellian velocity distribution , sheath potential 3 kT
 ne= 11

kT(eV)	Y	y _e	E _{sp}	R _{at}	R _{fi}	B _s	range
2	7.84e-3	1.02e-3	1.30e4-0	1.92e-1	6.17e-2	3.22e+0	1.17e+1
5	3.43e-2	3.09e-3	2.25e+0	1.74e-1	5.41e-2	7.75e4-0	2.37e+1
10	5.58e-2	3.72e-3	3.34e4-0	1.51e-1	4.62e-2	1.53e+1	4.21e+1
20	6.96e-2	3.28e-3	4.71e+0	1.25e-1	3.74e-2	2.99e+1	7.71e+1
50	7.10e-2	2.18e-3	7.67e+0	9.25e-2	2.66e-2	7.20e4-1	1.81e4-2
100	5.57e-2	1.13e-3	1.01e+1	6.27e-2	1.64e-2	1.31e+2	3.55e+2
200	4.40e-2	5.85e-4	1.33e+1	3.91e-2	9.19e-3	2.35eR2	7.05e+2
500	2.35e-2	1.70e-4	1.81e+1	1.52e-2	3.16e-3	5.19e+2	1.67e4-3
1000	1.60e-2	6.89e-5	2.15e+1	5.85e-3	1.03e-3	8.85e+2	3.06e+3
2000	9.17e-3	2.53e-5	2.76e-f-1	2.19e-3	3.31e-4	1.51e+3	5.29e+3
5000	4.43e-3	7.99e-6	4.51e+1	4.73e-4	7.77e-5	4.10e+3	1.01e+4

T -> Li

Sputtering yield of Li by T

z1 = 1, m1 = 3.01, z2 = 3, m2 = 6.94, sbe = 1.68, 1.67 eV, rho = 0.53 g/cm**3
 ef = 0.90, esb = 1.00, ca = 1.00, kk0 = kkOr = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: newtrim (Laszlo), IPP9/82
 ne = 13, na = 13

Bq (eV)	0°	20°	40°	50°	60°	65°	70°	75°	77°	80°	82°	85°	87°
10	2.52e-3					3.67e-2							
14	7.36e-3												
20	1.34e-2					1.50e-1							
30	2.04e-2												
50	3.00e-2					3.35e-1							
100	4.20e-2	5.44e-2	1.50e-1	2.25e-1	3.48e-1	4.30e-1	5.00e-1	5.74e-1		5.45e-1		2.51e-1	1.22e-1
200	4.71e-2					4.51e-1							
300	4.52e-2	6.40e-2	1.37e-1	2.16e-1			5.31e-1						
500	4.40e-2												
1000	3.66e-2					3.87e-1							
2000	2.67e-2					3.09e-1							
5000	1.64e-2					2.00e-1							
10000	1.10e-2					1.04e-1							
						6.11e-2							

Sputtered energy of Li by T

program: newtrim (Laszlo)
 ne = 10, na = 2

E ₀ (eV)	0°	65°
10		6.99e-3
20		2.42e-2
50	1.58e-3	3.54e-2
100	1.53e-3	3.24e-2
200	1.20e-3	2.43e-2
500	6.44e-4	1.38e-2
1000	3.47e-4	8.36e-3
2000	1.51e-4	3.48e-3
5000	6.03e-5	1.31e-3
10000	1.74e-5	4.90e-4

Particle reflection coefficient of T backscattered from Li

z1 = 1, m1 = 3.01, z2 = 3, m2 = 6.94, Es = 1.68 eV, rho = 0.53 g/cm**3
 ef = 0.90, esb = 1.00, ca = 1.00, kk0 = kkOr = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: newtrim (Laszlo)
 ne = 10, na = 2

E ₀ (eV)	0°	65°
10		4.75e-1
20		4.49e-1
50	6.62e-2	3.74e-1
100	5.39e-2	3.28e-1
200	3.96e-2	2.92e-1
500	2.29e-2	2.46e-1
1000	1.29e-2	2.04e-1
2000	5.75e-3	1.55e-1
5000	2.15e-3	9.41e-2
10000	7.45e-4	5.12e-2

Energy reflection coefficient of T backscattered from Li

ne = 10, na = 2

Bo (eV)	0°	65°
10		2.41e-1
20		2.33e-1
50	1.18e-2	1.80e-1
100	9.65e-3	1.50e-1
200	7.05e-3	1.29e-1
500	3.91e-3	1.03e-1
1000	2.11e-3	7.95e-2
2000	8.73e-4	5.10e-2
5000	2.96e-4	2.24e-2
10000	1.00e-4	8.83e-3

Average depth (mean range) in Å of T implanted in Li

ne = 10, na = 2

E ₀ (eV)	0°	65°
10		7.69e+0
20		1.35e+1
50	4.17e+1	2.79e+1
100	7.73e+1	5.08e+1
200	1.50e+2	9.47e+1
500	3.77e+2	2.28e+2
1000	7.77e+2	4.40e+2
2000	1.58e+3	8.34e+2
5000	3.76e+3	1.80e+3
10000	6.75e+3	3.03e+3

He -> Li

He on Li, Maxwellian velocity distribution, sheath potential 0 kT
 $z1 = 2$, $m1 = 4.00$, $z2 = 3$, $m2 = 6.94$, $sbe = 1.68$ eV, $\rho = 0.53$ g/cm**3
 $ef = 0.30$ eV, $esb = 0.00$ eV, $ca = 1.00$, $kk0 = kk0r = 2$, $kdee1 = kdee2 = 3$, $ipotr = ipotr = 1$ (KrC)
 program: newtrim (Laszlo)
 $n_e = 11$

kT(eV)	Y	Y _e	E _{sp}	R _{iv}	R _e	E _b	range
2	2.16e-3	1.07e-3	1.99e+0	5.37e-1	2.58e-1	1.92e+0	3.23e+0
5	2.83e-2	8.70e-3	3.08e+0	4.65e-1	2.16e-1	4.64e+0	6.54e+0
10	9.00e-2	1.84e-2	4.09e+0	3.95e-1	1.76e-1	8.90e+0	1.08e+1
20	1.88e-1	2.59e-2	5.50e+0	3.25e-1	1.38e-1	1.70e+1	1.77e+1
50	3.46e-1	2.85e-2	8.24e+0	2.49e-1	9.86e-2	3.96e+1	3.57e+1
100	4.37e-1	2.46e-2	1.12e+1	2.04e-1	7.84e-2	7.68e+1	6.43e+1
200	4.88e-1	1.90e-2	1.56e+1	1.67e-1	6.31e-2	1.51e+2	1.21e+2
500	4.71e-1	1.17e-2	2.46e+1	1.33e-1	4.87e-2	3.64e+2	2.88e+2
1000	4.25e-1	7.48e-3	3.49e+1	1.12e-1	3.83e-2	6.75e+2	5.58e+2
2000	3.45e-1	4.19e-3	4.84e+1	8.69e-2	2.62e-2	1.20e+3	1.08e+3
5000	2.34e-1	1.91e-3	8.15e+1	5.93e-2	1.58e-2	2.65e+3	2.38e+3

He on Li, Maxwellian velocity distribution, sheath potential 2 kT
 $n_e = 9$

kT(eV)	Y	Y _m	E _{sp}	R _{iv}	R _e	E _b	range
2	7.09e-3	1.78e-3	1.96e+0	2.30e-1	6.26e-2	2.13e+0	5.75e+0
5	5.41e-2	6.77e-3	2.50e+0	1.56e-1	3.60e-2	4.60e+0	1.12e+1
10	1.18e-1	1.09e-2	3.68e+0	1.18e-1	2.57e-2	8.69e+0	1.85e+1
20	1.78e-1	1.11e-2	4.95e+0	9.04e-2	2.00e-2	1.77e+1	3.20e+1
50	2.31e-1	9.16e-3	7.96e+0	6.56e-2	1.54e-2	4.69e+1	7.06e+1
100	2.41e-1	7.29e-3	1.21e+1	5.01e-2	1.12e-2	8.89e+1	1.31e+2
200	1.98e-1	3.90e-3	1.58e+1	3.51e-2	8.50e-3	1.94e+2	2.62e+2
500	1.54e-1	1.64e-3	2.12e+1	2.03e-2	4.53e-3	4.46e+2	6.51e+2
1000	1.03e-1	8.49e-4	3.31e+1	1.03e-2	2.04e-3	7.95e+2	1.29e+3

He on Li, Maxwellian velocity distribution, sheath potential 3 kT
 $n_e = 11$

kT(eV)	Y	Y _m	E _{sp}	R _{iv}	R _e	E _b	range
2	9.98e-3	1.76e-3	1.77e+0	1.89e-1	4.24e-2	2.25e+0	6.98e+0
5	5.89e-2	6.17e-3	2.62e+0	1.27e-1	2.52e-2	4.96e+0	1.35e+1
10	1.14e-1	8.36e-3	3.68e+0	9.61e-2	1.81e-2	9.43e+0	2.28e+1
20	1.65e-1	8.64e-3	5.24e+0	7.32e-2	1.39e-2	1.90e+1	3.96e+1
50	1.99e-1	6.63e-3	8.31e+0	5.04e-2	9.71e-3	4.81e+1	8.79e+1
100	1.96e-1	4.65e-3	1.19e+1	3.66e-2	6.95e-3	9.49e+1	1.69e+2
200	1.62e-1	2.68e-3	1.67e+1	2.43e-2	4.79e-3	1.97e+2	3.34e+2
500	1.19e-1	1.01e-3	2.13e+1	1.27e-2	2.24e-3	4.41e+2	8.42e+2
1000	8.36e-2	5.96e-4	3.57e+1	6.25e-3	8.84e-4	7.08e+2	1.66e+3
2000	5.46e-2	2.65e-4	4.83e+1	1.19e-3	1.91e-4	1.60e+3	3.09e+3
5000	1.78e-2	1.34e-4	1.34e+2				6.45e+3

He on Li, Maxwellian velocity distribution, sheath potential 9 kT
 $n_e = 11$

kT(eV)	Y	Y _e	E _{sp}	R _{iv}	R _e	E _b	range
2	9.98e-3	1.76e-3	1.77e+0	1.89e-1	4.24e-2	2.25e+0	6.98e+0
5	5.89e-2	6.17e-3	2.62e+0	1.27e-1	2.52e-2	4.96e+0	1.35e+1
10	1.14e-1	8.36e-3	3.68e+0	9.61e-2	1.81e-2	9.43e+0	2.28e+1
20	1.65e-1	8.64e-3	5.24e+0	7.32e-2	1.39e-2	1.90e+1	3.96e+1
50	1.99e-1	6.63e-3	8.31e+0	5.04e-2	9.71e-3	4.81e+1	8.79e+1
100	1.96e-1	4.65e-3	1.19e+1	3.66e-2	6.95e-3	9.49e+1	1.69e+2
200	1.62e-1	2.68e-3	1.67e+1	2.43e-2	4.79e-3	1.97e+2	3.34e+2
500	1.19e-1	1.01e-3	2.13e+1	1.27e-2	2.24e-3	4.41e+2	8.42e+2
1000	8.36e-2	5.96e-4	3.57e+1	6.25e-3	8.84e-4	7.08e+2	1.66e+3
2000	5.46e-2	2.65e-4	4.83e+1	1.19e-3	1.91e-4	1.60e+3	3.09e+3
5000	1.78e-2	1.34e-4	1.34e+2				6.45e+3

Li → Li

Sputtering yield of Li by Li

z1 = 3, m1 = 6.94, z2 = 3, m2 = 6.94, sbe = 1.68 eV, rho = 0.53 g/cm**3
 ef = 1.18 eV, esb = 1.68 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: newtrim (Laszlo), IPP 9/82
 ne = 9, na = 10

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	75°	80°	85°
20	5.42e-3							2.28e-1		
50	4.29e-2							5.96e-1		
100	9.48e-2	2.60e-1	5.19e-1		9.21e-1	1.05e-0	1.13e-0	1.07e-0	7.68e-1	3.21e-1
200	1.50e-1	3.43e-1	6.56e-1		1.18e-0	1.39e-0	1.58e-0	1.62e-0	1.36e-0	5.19e-1
500	1.91e-1							2.29e-0		
1000	2.07e-1	3.75e-1	6.57e-1	1.04e-0	1.33e-0		2.06e-0	2.49e-0	2.82e-0	2.16e-0
2000	1.87e-1							2.58e-0		
5000	1.44e-1							2.01e-0		
10000	1.19e-1							1.48e-0		

Sputtered energy of Li by Li

program: newtrim (Laszlo)
 ne = 9, na = 10

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	75°	80°	85°
20	2.62e-4							5.67e-2		
50	1.62e-3							1.02e-1		
100	2.72e-3	1.27e-2	3.41e-2		7.85e-2	9.78e-2	1.15e-1	1.22e-1	9.97e-2	5.00e-2
200	3.17e-3	1.23e-2	3.12e-2		7.17e-2	8.94e-2	1.10e-1	1.25e-1	1.16e-1	5.40e-2
500	2.61e-3							1.09e-1		
1000	2.08e-3	6.76e-3	1.61e-2	3.06e-2	4.15e-2		7.17e-2	8.97e-2	1.02e-1	8.26e-2
2000	1.29e-3								6.53e-2	
5000	5.98e-4								3.85e-2	
10000	3.46e-4								2.08e-2	

Particle reflection coefficient of Li backscattered from Li

z1 = 3, m1 = 6.94, z2 = 3, m2 = 6.94, sbe = 1.68 eV, rho = 0.53 g/cm**3
 ef = 1.18 eV, esb = 1.68 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: newtrim (Laszlo)
 ne = 9, na = 10

B _q (eV)	0°	30°	45°	55°	60°	65°	70°	75°	80°	85°
20	9.31e-4							5.18e-1		
50	3.80e-3							5.96e-1		
100	5.39e-3	2.39e-2	6.99e-2		1.93e-1	2.69e-1	3.72e-1	5.18e-1	7.21e-1	9.05e-1
200	5.10e-3	2.09e-2	5.93e-2		1.64e-1	2.27e-1	3.14e-1	4.33e-1	6.28e-1	8.89e-1
500	3.56e-3							3.52e-1		
1000	2.42e-3	1.11e-2	3.39e-2	7.57e-2	1.12e-1		2.24e-1	3.10e-1	4.50e-1	6.98e-1
2000	1.79e-3							2.89e-1		
5000	6.04e-4							2.45e-1		
10000								2.08e-1		

Energy reflection coefficient of Li backscattered from Li

ne = 9, na = 10

B _e (eV)	0°	30°	45°	55°	60°	65°	70°	75°	80°	85°
20	5.99e-5							2.56e-1		
50	2.25e-4							3.43e-1		
100	3.04e-4	2.92e-3	1.33e-2		6.05e-2	1.02e-1	1.70e-1	2.91e-1	4.98e-1	7.32e-1
200	2.79e-4	2.45e-3	1.07e-2		4.74e-2	7.96e-2	1.32e-1	2.26e-1	4.20e-1	7.49e-1
500	1.91e-4							1.67e-1		
1000	1.27e-4	1.20e-3	6.34e-3	1.77e-2	3.03e-2		8.35e-2	1.41e-1	2.53e-1	5.40e-1
2000	1.18e-4							1.25e-1		
5000	2.66e-5							1.01e-1		
10000								7.16e-2		

Average depth (mean range) in Å of Li implanted in Li

ne = 9, na = 10

E _a (eV)	0°	30°	45°	55°	60°	65°	70°	75°	80°	85°
20	1.01e4-1							3.62e-1-0		
50	1.94e-1-1							8.87e+0		
100	3.25e-1-1	2.85e-f-1	2.43e+1		1.95e+1	1.79e+1	1.66e+1	1.53e+1	1.40e+1	1.25e-1-1
200	5.63e-1-1	4.95e4-1	4.17e+1		3.35e-1-1	3.09e+1	2.85e+1	2.62e-f-1	2.43e+1	2.22e+1
500	1.24e+2							5.60e-1-1		
1000	2.39e+2	2.09e+2	1.74e+2	1.50e+2	1.38e-1-2		1.13e+2	1.04e+2	9.58e-f-1	8.93e-1-1
2000	4.79e+2							2.00e+2		
5000	1.23e-1-3							4.69e+2		
10000	2.45e+3							8.63e+2		

Li -4 Li

Li on Li, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 3, m1 = 6.94, z2 = 3, m2 = 6.94, sbe = 1.67 eV, rho = 0.53 g/cm**3
 ef = 1.62 eV, esb = 1.67 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx, newtrim(Laszlo)
 ne = 14

kT(eV)	Y	Y _e	E _{sp}	R _N	R _e	E _b	range
1.1	4.56e-4	3.04e-4	1.47e+0	1.10e-3	1.12e-3	2.24e+0	1.12e+0
1.4	1.24e-3	7.64e-4	1.73e+0	2.85e-3	2.74e-3	2.69e+0	1.36e+0
2	4.22e-3	2.37e-3	2.24e+0	9.29e-3	8.13e-3	3.50e+0	1.82e+0
3	1.41e-2	6.30e-3	2.68e+0	2.40e-2	1.80e-2	4.49e+0	2.51e+0
5	4.28e-2	1.44e-2	3.36e+0	5.70e-2	3.80e-2	6.67e+0	3.94e+0
10	1.26e-1	2.84e-2	4.53e+0	1.09e-1	6.07e-2	1.12e+1	6.83e+0
20	2.58e-1	3.90e-2	6.04e+0	1.43e-1	7.01e-2	1.96e+1	1.18e+1
50	4.88e-1	4.31e-2	8.87e+0	1.48e-1	6.39e-2	4.32e+1	2.43e+1
100	6.66e-1	4.10e-2	1.23e+1	1.34e-1	5.37e-2	8.01e+1	4.22e+1
200	7.95e-1	3.49e-2	1.74e+1	1.19e-1	4.60e-2	1.53e+2	7.64e+1
500	8.58e-1	2.39e-2	2.78e+1	9.74e-2	3.58e-2	3.66e+2	1.80e+2
1000	7.95e-1	1.62e-2	4.08e+1	7.90e-2	2.92e-2	7.39e+2	3.52e+2
2000	7.35e-1	1.12e-2	6.09e+1	7.05e-2	2.35e-2	1.33e+3	6.96e+2
5000				5.12e-2	1.82e-2	3.57e+3	1.69e+3

Li on Li, Maxwellian velocity distribution, sheath potential' 3 kT
 ne = 14

kT(eV)	Y	Y _e	E _{sp}	R _N	R _e	E _b	range
1.1	1.43e-3	3.71e-4	1.43e+0	1.56e-3	5.76e-4	2.03e+0	3.34e+0
1.4	3.47e-3	7.95e-4	1.61e+0	3.05e-3	1.04e-3	2.37e+0	4.02e+0
2	1.07e-2	2.00e-3	1.87e+0	6.82e-3	2.07e-3	3.03e+0	5.29e+0
3	2.71e-2	4.10e-3	2.27e+0	1.19e-2	3.06e-3	3.86e+0	7.15e+0
5	6.41e-2	7.17e-3	2.79e+0	1.71e-2	3.68e-3	5.39e+0	1.05e+1
10	1.36e-1	1.05e-2	3.84e+0	2.04e-2	3.51e-3	8.59e+0	1.74e+1
20	2.14e-1	1.16e-2	5.41e+0	1.92e-2	2.94e-3	1.53e+1	2.92e+1
50	3.19e-1	1.09e-2	8.58e+0	1.73e-2	2.65e-3	3.82e+1	6.10e+1
100	3.45e-1	8.13e-3	1.21e+1	1.28e-2	1.88e-3	7.31e+1	1.12e+2
200	3.24e-1	5.68e-3	1.76e+1	9.05e-3	1.43e-3	1.58e+2	2.15e+2
500	2.40e-1	2.46e-3	2.57e+1	4.72e-3	6.67e-4	3.53e+2	5.38e+2
1000	2.16e-1	1.54e-3	3.57e+1	2.99e-3	4.51e-4	7.57e+2	1.10e+3
2000	1.46e-1	8.98e-4	6.14e+1	7.58e-4	1.36e-4	1.80e+3	2.19e+3
5000	9.47e-2	3.04e-4	8.04e+1				5.07e+3

Li on Li, Maxwellian velocity distribution, sheath potential 9 kT
 ne = 14

kT(eV)	Y	Y _e	E _{sp}	R _N	R _e	E _b	range
1.1	5.18e-3	5.87e-4	1.37e+0	2.18e-3	3.64e-4	2.02e+0	6.58e+0
1.4	1.08e-2	1.04e-3	1.49e+0	3.38e-3	5.06e-4	2.31e+0	7.84e+0
2	2.37e-2	1.93e-3	1.79e+0	5.45e-3	7.29e-4	2.94e+0	1.01e+1
3	4.80e-2	3.25e-3	2.23e+0	7.61e-3	9.23e-4	4.00e+0	1.36e+1
5	8.93e-2	4.65e-3	2.86e+0	9.45e-3	9.90e-4	5.76e+0	1.99e+1
10	1.55e-1	6.03e-3	4.27e+0	1.01e-2	9.55e-4	1.04e+1	3.35e+1
20	2.15e-1	5.74e-3	5.87e+0	8.97e-3	8.33e-4	2.04e+1	5.84e+1
50	2.55e-1	4.50e-3	9.72e+0	6.58e-3	6.13e-4	5.12e+1	1.30e+2
100	2.49e-1	3.06e-3	1.35e+1	4.13e-3	3.27e-4	8.71e+1	2.52e+2
200	2.10e-1	1.82e-3	1.90e+1	2.23e-3	2.79e-4	2.75e+2	5.03e+2
500	1.43e-1	6.45e-4	2.49e+1	1.55e-3	1.37e-4	4.85e+2	1.29e+3
1000	1.20e-1	4.38e-4	4.01e+1	2.61e-4	1.90e-5	8.02e+2	2.57e+3
2000	8.47e-2	1.82e-4	4.71e+1	2.12e-4	8.83e-6	9.16e+2	4.88e+3
5000	4.98e-2	8.04e-5	8.89e+1				8.65e+3

H Be

Sputtering yield of Be by H

z1= 1, m1= 1.01, z2= 4, m2= 9.01, sbe=3.38 eV, rho=1.80 g/cm**3

ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)

program : trvmc

ne=17, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
15	2.39e-5	2.63e-5	2.85e-5	2.14e-5	1.21e-5	8.09e-6	4.43e-6			
17	1.80e-4	1.95e-4	2.08e-4	1.66e-4	1.05e-4	7.32e-5	4.48e-5	9.26e-6	3.26e-6	3.82e-6
20	8.03e-4	8.49e-4	9.25e-4	8.35e-4	6.15e-4	4.64e-4	3.12e-4	8.45e-5	3.29e-5	1.31e-5
22	1.45e-3	1.50e-3	1.68e-3	1.65e-3	1.32e-3		7.44e-4	2.31e-4	9.69e-5	3.89e-5
25	2.57e-3	2.75e-3	3.17e-3	3.36e-3	2.89e-3	2.50e-3	1.92e-3	7.73e-4	3.29e-4	1.38e-4
27	3.50e-3									
30	4.68e-3	4.98e-3	5.82e-3	6.88e-3	6.92e-3	6.37e-3	5.53e-3	2.68e-3	1.26e-3	4.78e-4
40	8.46e-3	9.19e-3	1.13e-2	1.43e-2	1.76e-2	1.87e-2	1.83e-2	1.10e-2	4.97e-3	1.39e-3
50	1.15e-2	1.24e-2	1.55e-2	2.20e-2	2.89e-2	3.24e-2	3.40e-2	2.38e-2	1.05e-2	2.46e-3
70	1.54e-2	1.69e-2	2.19e-2	3.35e-2	4.76e-2	5.61e-2	6.40e-2	5.41e-2	2.57e-2	4.28e-3
100	1.85e-2	2.04e-2	2.70e-2	4.38e-2	6.49e-2	7.81e-2	9.48e-2	9.73e-2	5.15e-2	6.63e-3
140	1.98e-2	2.24e-2	3.07e-2	5.05e-2	7.71e-2		1.18e-1	1.39e-1	8.57e-2	1.02e-2
200	2.02e-2	2.28e-2	3.27e-2	5.57e-2	8.43e-2	1.05e-1	1.33e-1	1.78e-1	1.33e-1	1.70e-2
300	1.93e-2	2.23e-2	3.27e-2	5.64e-2	8.66e-2		1.37e-1	2.07e-1	1.91e-1	3.41e-2
500	1.69e-2	1.98e-2	2.99e-2	5.13e-2	8.02e-2	1.00e-1	1.30e-1	2.15e-1	2.43e-1	8.09e-2
1000	1.26e-2	1.49e-2	2.26e-2	4.00e-2	6.28e-2	8.37e-2	1.04e-1	1.88e-1	2.51e-1	1.93e-1
2000						5.55e-2				

Sputtered energy of Be by H

ne=17, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
15	5.14e-7	6.20e-7	7.95e-7	6.37e-7	3.73e-7	2.51e-7	1.27e-7			
17	5.30e-6	6.12e-6	7.26e-6	6.29e-6	3.98e-6	2.79e-6	1.68e-6	3.59e-7	1.31e-7	2.07e-7
20	3.14e-5	3.45e-5	4.08e-5	3.99e-5	2.98e-5	2.25e-5	1.54e-5	4.24e-6	1.71e-6	7.12e-7
22	6.21e-5	6.65e-5	8.12e-5	8.74e-5	7.17e-5		4.08e-5	1.29e-5	5.50e-6	2.34e-6
25	1.22e-4	1.36e-4	1.68e-4	1.92e-4	1.73e-4	1.53e-4	1.19e-4	4.71e-5	2.15e-5	9.17e-6
27	1.74e-4									
30	2.42e-4	2.67e-4	3.31e-4	4.23e-4	4.46e-4	4.20e-4	3.77e-4	1.94e-4	9.45e-5	3.69e-5
40	4.61e-4	5.09e-4	6.62e-4	9.35e-4	1.17e-3	1.29e-3	1.33e-3	8.94e-4	4.35e-4	1.28e-4
50	6.19e-4	6.74e-4	8.89e-4	1.34e-3	1.87e-3	2.21e-3	2.45e-3	2.01e-3	9.77e-4	2.47e-4
70	7.72e-4	8.60e-4	1.14e-3	1.88e-3	2.88e-3	3.56e-3	4.33e-3	4.44e-3	2.38e-3	4.33e-4
100	8.25e-4	9.19e-4	1.24e-3	2.11e-3	3.33e-3	4.37e-3	5.66e-3	7.00e-3	4.30e-3	6.46e-4
140	7.78e-4	8.76e-4	1.21e-3	2.11e-3	3.44e-3		6.00e-3	8.66e-3	6.13e-3	8.86e-4
200	6.59e-4	7.45e-4	1.08e-3	1.99e-3	3.22e-3	4.34e-3	5.77e-3	8.99e-3	7.80e-3	1.27e-3
300	5.02e-4	5.80e-4	8.63e-4	1.66e-3	2.77e-3		4.77e-3	8.11e-3	8.64e-3	2.00e-3
500	3.13e-4	3.77e-4	5.91e-4	1.11e-3	1.99e-3	2.42e-3	3.33e-3	6.22e-3	7.74e-3	3.29e-3
1000	1.39e-4	1.66e-4	2.92e-4	5.88e-4	1.00e-3	1.27e-3	1.88e-3	3.66e-3	5.11e-3	4.57e-3
2000						6.26e-4				

H -4- Be

Particle reflection coefficient of H backscattered from Be
 z1 = 1, m1 = 1.01, z2 = 4, m2 = 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne=18, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	4.27e-1	4.51e-1	5.21e-1	6.43e-1	7.48e-1		8.56e-1	9.38e-1	9.61e-1	9.74e-1
15	3.79e-1	4.01e-1	4.65e-1	5.87e-1	7.02e-1	7.66e-1	8.32e-1	9.38e-1	9.69e-1	9.83e-1
17	3.66e-1	3.86e-1	4.48e-1	5.68e-1	6.85e-1	7.51e-1	8.20e-1	9.37e-1	9.70e-1	9.85e-1
20	3.49e-1	3.68e-1	4.28e-1	5.44e-1	6.61e-1	7.30e-1	8.04e-1	9.34e-1	9.71e-1	9.87e-1
22	3.40e-1	3.59e-1	4.16e-1	5.29e-1	6.46e-1		7.92e-1	9.31e-1	9.71e-1	9.88e-1
25	3.28e-1	3.46e-1	4.02e-1	5.10e-1	6.26e-1	6.97e-1	7.76e-1	9.26e-1	9.71e-1	9.89e-1
27	3.22e-1									
30	3.11e-1	3.28e-1	3.81e-1	4.85e-1	5.97e-1	6.69e-1	7.50e-1	9.17e-1	9.70e-1	9.91e-1
40	3.87e-1	3.03e-1	3.53e-1	4.48e-1	5.52e-1	6.21e-1	7.05e-1	8.97e-1	9.66e-1	9.93e-1
50	2.69e-1	2.85e-1	3.32e-1	4.22e-1	5.20e-1	5.87e-1	6.68e-1	8.75e-1	9.60e-1	9.93e-1
70	2.44e-1	2.58e-1	3.03e-1	3.88e-1	4.76e-1	5.35e-1	6.13e-1	8.33e-1	9.46e-1	9.94e-1
100	2.18e-1	2.32e-1	2.74e-1	3.53e-1	4.36e-1	4.90e-1	5.60e-1	7.77e-1	9.20e-1	9.93e-1
140	1.94e-1	2.08e-1	2.47e-1	3.23e-1	4.02e-1		5.17e-1	7.17e-1	8.82e-1	9.92e-1
200	1.68e-1	1.81e-1	2.19e-1	2.92e-1	3.69e-1	4.22e-1	4.77e-1	6.58e-1	8.28e-1	9.87e-1
300	1.39e-1	1.51e-1	1.87e-1	2.58e-1	3.31e-1		4.35e-1	6.00e-1	7.77e-1	9.74e-1
500	1.03e-1	1.14e-1	1.46e-1	2.13e-1	2.85e-1	3.36e-1	3.86e-1	5.39e-1	6.71e-1	9.37e-1
1000	5.91e-2	6.64e-2	9.28e-1	1.50e-1	2.17e-1		2.68e-1	3.18e-1	5.80e-1	8.28e-1
2000						1.91e-1				

Energy reflection coefficient of H backscattered from Be
 ne=18, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	1.96e-1	2.15e-1	2.73e-1	3.88e-1	5.01e-1		6.34e-1	7.58e-1	7.99e-1	8.24e-1
15	1.71e-1	1.87e-1	2.38e-1	3.50e-1	4.71e-1	5.45e-1	6.27e-1	7.85e-1	8.40e-1	8.70e-1
17	1.63e-1	1.78e-1	2.27e-1	3.35e-1	4.56e-1	5.33e-1	6.19e-1	7.89e-1	8.49e-1	8.81e-1
20	1.54e-1	1.68e-1	2.14e-1	3.16e-1	4.36e-1	5.14e-1	6.05e-1	7.92e-1	8.59e-1	8.93e-1
22	1.49e-1	1.62e-1	2.06e-1	3.04e-1	4.23e-1		5.95e-1	7.92e-1	8.63e-1	9.00e-1
25	1.42e-1	1.55e-1	1.96e-1	2.90e-1	4.04e-1	4.84e-1	5.79e-1	7.89e-1	8.68e-1	9.08e-1
27	1.39e-1									
30	1.33e-1	1.45e-1	1.83e-1	2.69e-1	3.78e-1	4.56e-1	5.54e-1	7.82e-1	8.73e-1	9.17e-1
40	1.20e-1	1.30e-1	1.65e-1	2.40e-1	3.37e-1	4.10e-1	5.06e-1	7.62e-1	8.74e-1	9.28e-1
50	1.11e-1	1.20e-1	1.52e-1	2.20e-1	3.08e-1	3.76e-1	4.68e-1	7.37e-1	8.70e-1	9.35e-1
70	9.79e-2	1.06e-1	1.34e-1	1.95e-1	2.70e-1	3.27e-1	4.10e-1	6.86e-1	8.54e-1	9.42e-1
100	8.46e-2	9.22e-2	1.17e-1	1.71e-1	2.36e-1	2.86e-1	3.56e-1	6.18e-1	8.21e-1	9.45e-1
140	7.29e-2	8.00e-2	1.02e-1	1.51e-1	2.09e-1		3.13e-1	5.45e-1	7.71e-1	9.45e-1
200	6.08e-2	6.72e-2	8.70e-2	1.31e-1	1.84e-1	2.25e-1	2.75e-1	4.73e-1	6.98e-1	9.40e-1
300	4.81e-2	5.30e-2	7.03e-2	1.09e-1	1.57e-1		2.37e-1	4.09e-1	6.03e-1	9.22e-1
500	3.29e-2	3.72e-2	5.11e-2	8.30e-2	1.24e-1	1.55e-1	1.94e-1	3.34e-1	4.90e-1	8.65e-1
1000	1.68e-2	1.92e-2	2.83e-2	5.06e-2	8.15e-2	1.07e-1	1.39e-1	2.55e-1	3.71e-1	7.02e-1
2000						6.27e-2				

Average depth (mean range) in Å of H implanted in Be
 ne=18, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	5.11e+0	5.06e+0	4.96e-f-0	4.79e+0	4.65e-f-0		4.49e+0	4.32e-j-0	4.24e-j-0	4.18e-j-0
15	6.88e+0	6.81e+0	6.64e+0	6.39e+0	6.20e-j-0	6.09e+0	5.98e+0	5.74e+0	5.58e-j-0	5.58e-f-0
17	7.55e-f-0	7.47e+0	7.27e+0	6.99e+0	6.77e+0	6.65e+0	6.54e+0	6.29e+0	6.17e+0	6.05e+0
20	8.52e-f-0	8.43e-j-0	8.20e+0	7.86e+0	7.61e+0	7.47e-j-0	7.34e-j-0	7.07e+0	6.93e+0	6.80e+0
22	9.15e-j-0	9.05e-j-0	8.80e-j-0	8.43e+0	8.15e-f-0		7.86e+0	7.57e-j-0	7.41e+0	7.27e+0
25	1.01e+1	1.00e+1	9.69e+0	9.25e+0	8.95e+0	8.79e-j-0	8.63e+0	8.30e+0	8.14e+0	7.98e+0
27	1.07e+1									
30	1.16e+1	1.15e-H	1.11e+1	1.06e-f-1	1.02e-j-1	1.01e+1	9.86e+0	9.49e+0	9.30e+0	9.13e+0
40	1.45e+1	1.44e-j-1	1.39e+1	1.32e+1	1.27e-j-1	1.25e+1	1.22e+1	1.18e+1	1.16e-j-1	1.13e+1
50	1.74e+1	1.71e+1	1.65e+1	1.57e-j-1	1.51e+1	1.47e+1	1.45e-j-1	1.39e+1	1.37e+1	1.34e+1
70	2.28e-j-1	2.25e+1	2.17e+1	2.05e-f-1	1.95e+1	1.91e+1	1.87e+1	1.80e+1	1.77e+1	1.74e+1
100	3.07e-j-1	3.03e-j-1	2.91e+1	2.73e+1	2.60e+1	2.54e+1	2.48e-j-1	2.38e+1	2.34e-j-1	2.31e+1
140	4.09e+1	4.03e+1	3.85e+1	3.60e+1	3.42e+1		3.24e-j-1	3.10e+1	3.05e+1	3.00e+1
200	5.58e+1	5.48e+1	5.23e+1	4.86e+1	4.58e-j-1	4.44e+1	4.33e+1	4.11e+1	4.05e-j-1	4.06e+1
300	8.00e-j-1	7.84e+1	7.44e+1	6.86e+1	6.41e+1		6.03e-j-1	5.67e+1	5.57e-p1	5.54e-j-1
500	1.26e-f-2	1.23e+2	1.17e+2	1.06e+2	9.82e+1	9.45e+1	9.10e+1	8.50e-j-1	8.28e+1	8.25e+1
1000	2.37e-f-2	2.31e+2	2.15e+1	1.91e+1	1.74e-j-2	1.65e+2	1.57e+2	1.43e+2	1.38e+2	1.36e+2
2000						2.80e-j-2				

D → Be

Sputtering yield of Be by D

zl= 1. ml = 2.01. z2= 4. m2= 9.01. sbe = 3.38 eV. rho = 1.80 g/cm**3
 ef=0.98 eV. esb = 1.00 eV. ca=1.00, kk0=kk0r=2. kdee1 = kdee2 = 3, ipot=ipotrl=1 (KrC)
 program : trvmc
 ne=21. na=12

Eq(eV)	0°	15°	30°	45°	55°	60°	65°	70°	75°	80°	85°	87°
10	4.13e-6	4.30e-6	4.56e-6									
11	2.61e-5	3.05e-5	3.15e-5	2.69e-5	1.86e-5		1.00e-5		3.67e-6	8.00e-7	5.00e-7	
12	9.29e-5	1.07e-4	1.25e-4	1.14e-4	8.71e-5	6.81e-5	5.37e-5		2.31e-5	1.39e-5	9.62e-6	
13	2.32e-4	2.67e-4	3.47e-4	3.16e-4	2.61e-4	2.10e-4	1.62e-4		7.67e-5	4.78e-5	3.18e-5	
14	4.65e-4	5.50e-4	6.90e-4	6.91e-4	5.92e-4		3.92e-4		1.91e-4	1.20e-4	7.85e-5	
15	8.10e-4	9.42e-4	1.21e-3	1.29e-3	1.12e-3	9.82e-4	7.97e-4		4.11e-4	2.57e-4	1.65e-4	
17	1.73e-3	2.02e-3	2.60e-3	3.03e-3	2.92e-3		2.29e-3		1.25e-3	7.67e-4	4.62e-4	
20	3.64e-3	4.19e-3	5.46e-3	7.03e-3	7.46e-3	7.12e-3	6.59e-3		3.76e-3	2.14e-3	1.16e-3	
25	7.30e-3	8.25e-3	1.11e-2	1.57e-2	1.87e-2	1.94e-2	1.85e-2		1.08e-2	5.51e-3	2.51e-3	
30	1.08e-2	1.22e-2	1.69e-2	2.54e-2	3.25e-2	3.58e-2	3.46e-2		2.07e-2	1.02e-2	3.82e-3	
40	1.68e-2	1.90e-2	2.64e-2	4.34e-2	6.08e-2		7.17e-2		4.54e-2	2.12e-2	5.91e-3	
50	2.09e-2	2.40e-2	3.45e-2	5.78e-2	8.53e-2	9.88e-2	1.07e-1		7.40e-2	3.23e-2	7.37e-3	
70	2.63e-2	3.04e-2	4.43e-2	7.94e-2	1.19e-1		1.60e-1		1.28e-1	5.90e-2	9.51e-3	
100	3.10e-2	3.59e-2	5.42e-2	9.78e-2	1.49e-1	1.80e-1	2.13e-1		2.00e-1	1.01e-1	1.27e-2	
140	3.32e-2	3.94e-2	6.11e-2	1.08e-1	1.68e-1		2.48e-1		2.71e-1	1.60e-1	1.82e-2	
200	3.51e-2	4.03e-2	6.32e-2	1.14e-1	1.77e-1	2.20e-1	2.68e-1		3.42e-1	2.43e-1	2.93e-2	
300	3.44e-2	4.20e-2	6.34e-2	1.12e-1	1.75e-1	2.12e-1	2.72e-1		3.91e-1	3.42e-1	5.71e-2	
500	3.24e-2	3.85e-2	5.82e-2	1.04e-1	1.50e-1	1.98e-1	2.57e-1		4.08e-1	4.39e-1	1.38e-1	
1000	2.53e-2	2.96e-2	4.37e-2	7.80e-2	1.25e-1	1.54e-1	2.06e-1		3.65e-1	4.59e-1	3.34e-1	
2000	1.76e-2											
3000	1.25e-2		2.02e-2	3.43e-2		7.29e-2		1.29e-1		2.89e-1	4.59e-1	3.18e-1

Sputtered energy of Be by D

ne=19. na=10

En (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	1.72e-7									
11	1.21e-6	1.56e-6	1.98e-6	1.99e-6	1.51e-6		9.34e-7	4.11e-7	1.24e-7	2.70e-8
12	4.88e-6	6.11e-6	8.54e-6	8.82e-6	7.18e-6	5.83e-6	5.05e-6	2.39e-6	1.49e-6	1.10e-6
13	1.30e-5	1.66e-5	2.54e-5	2.61e-5	2.35e-5	1.94e-5	1.55e-5	8.02e-6	5.16e-6	3.52e-6
14	2.79e-5	3.57e-5	5.17e-5	5.93e-5	5.50e-5		3.98e-5	2.08e-5	1.33e-5	8.92e-6
15	5.04e-5	6.24e-5	9.50e-5	1.14e-4	1.09e-4	9.93e-5	8.38e-5	4.72e-5	2.99e-5	1.98e-5
17	1.13e-4	1.43e-4	2.13e-4	2.87e-4	3.05e-4		2.57e-4	1.49e-4	9.47e-5	5.87e-5
20	2.51e-4	3.10e-4	4.62e-4	6.96e-4	8.14e-4	8.32e-4	7.90e-4	4.86e-4	2.91e-4	1.63e-4
25	5.28e-4	6.36e-4	9.66e-4	1.56e-3	2.09e-3	2.26e-3	2.32e-3	1.53e-3	8.29e-4	3.96e-4
30	7.87e-4	9.35e-4	1.44e-3	2.49e-3	3.56e-3	4.15e-3	4.36e-3	3.04e-3	1.59e-3	6.39e-4
40	1.20e-3	1.42e-3	2.12e-3	3.97e-3	6.30e-3		8.66e-3	6.66e-3	3.39e-3	1.01e-3
50	1.43e-3	1.68e-3	2.60e-3	4.94e-3	8.18e-3	1.02e-2	1.21e-2	1.04e-2	5.02e-3	1.26e-3
70	1.60e-3	1.88e-3	2.95e-3	5.87e-3	1.00e-2		1.59e-2	1.58e-2	8.45e-3	1.53e-3
100	1.63e-3	1.95e-3	3.04e-3	6.18e-3	1.07e-2	1.36e-2	1.78e-2	2.07e-2	1.22e-2	1.84e-3
140	1.48e-3	1.82e-3	2.94e-3	5.89e-3	1.02e-2		1.72e-2	2.30e-2	1.58e-2	2.26e-3
200	1.30e-3	1.48e-3	2.57e-3	5.21e-3	8.88e-3	1.21e-2	1.52e-2	2.31e-2	1.92e-2	3.03e-3
300	1.01e-3	1.24e-3	2.07e-3	4.14e-3	7.29e-3		1.22e-2	2.06e-2	2.03e-2	4.56e-3
500	6.64e-4	8.04e-4	1.42e-3	3.03e-3	4.99e-3	6.57e-3	8.91e-3	1.58e-2	1.85e-2	7.33e-3
1000	3.22e-4	3.90e-4	7.24e-4	1.47e-3	2.71e-3	3.50e-3	4.93e-3	9.33e-3	1.25e-2	1.04e-2

D → Be

Particle reflection coefficient of D backscattered from Be
 z1 = 1. m1 = 2.01. z2 = 4. m2 = 9.01. sbe = 3.38 eV. rho = 1.80 g/cm**3
 ef = 0.98 eV. esb = 1.00 eV. ca = 1.00, kk0 = kk0r = 2. kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrC)
 program : trvmc
 ne = 19. na = 10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	3.05e-1									
11	2.97e-1	3.23e-1	4.00e-1	5.45e-1	6.74e-1		8.12e-1	9.21e-1	9.52e-1	9.68e-1
12	2.89e-1	3.14e-1	3.90e-1	5.34e-1	6.66e-1	7.37e-1	8.08e-1	9.23e-1	9.55e-1	9.72e-1
13	2.82e-1	3.06e-1	3.81e-1	5.23e-1	6.57e-1	7.30e-1	8.04e-1	9.24e-1	9.58e-1	9.74e-1
14	2.76e-1	2.99e-1	3.72e-1	5.13e-1	6.48e-1		7.99e-1	9.24e-1	9.60e-1	9.77e-1
15	2.70e-1	2.92e-1	3.63e-1	5.03e-1	6.39e-1	7.15e-1	7.94e-1	9.24e-1	9.61e-1	9.78e-1
17	2.58e-1	2.80e-1	3.48e-1	4.84e-1	6.21e-1		7.83e-1	9.23e-1	9.63e-1	9.81e-1
20	2.45e-1	2.66e-1	3.29e-1	4.60e-1	5.95e-1	6.76e-1	7.64e-1	9.20e-1	9.65e-1	9.84e-1
25	2.27e-1	2.46e-1	3.05e-1	4.26e-1	5.58e-1	6.41e-1	7.34e-1	9.12e-1	9.66e-1	9.87e-1
30	2.14e-1	2.32e-1	2.88e-1	4.01e-1	5.27e-1	6.11e-1	7.06e-1	9.02e-1	9.64e-1	9.89e-1
40	2.95e-1	2.10e-1	2.61e-1	3.64e-1	4.81e-1		6.56e-1	8.80e-1	9.60e-1	9.91e-1
50	1.81e-1	1.96e-1	2.44e-1	3.41e-1	4.49e-1	5.22e-1	6.17e-1	8.56e-1	9.53e-1	9.92e-1
70	1.63e-1	1.76e-1	2.19e-1	3.07e-1	4.05e-1		5.58e-1	8.09e-1	9.38e-1	9.93e-1
100	1.43e-1	1.58e-1	2.00e-1	2.77e-1	3.65e-1	4.24e-1	5.03e-1	7.48e-1	9.10e-1	9.93e-1
140	1.29e-1	1.41e-1	1.85e-1	2.53e-1	3.35e-1		4.61e-1	6.85e-1	8.68e-1	9.91e-1
200	1.12e-1	1.22e-1	1.59e-1	2.30e-1	3.09e-1	3.58e-1	4.24e-1	6.22e-1	8.10e-1	9.86e-1
300	9.35e-2	1.04e-1	1.37e-1	2.05e-1	2.81e-1		3.90e-1	5.64e-1	7.35e-1	9.72e-1
500	7.20e-2	8.05e-2	1.10e-1	1.72e-1	2.46e-1	2.87e-1	3.47e-1	5.09e-1	6.49e-1	9.32e-1
1000	4.38e-2	5.04e-2	7.37e-2	1.27e-1	1.92e-1	2.39e-1	2.94e-1	4.45e-1	5.66e-1	8.23e-1

Energy reflection coefficient of D backscattered from Be
 ne = 19. na = 10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	9.79e-2									
11	9.60e-2	1.11e-1	1.62e-1	2.73e-1	3.92e-1		5.42e-1	6.93e-1	7.47e-1	7.79e-1
12	9.40e-2	1.09e-1	1.58e-1	2.69e-1	3.89e-1	4.63e-1	5.45e-1	7.04e-1	7.61e-1	7.95e-1
13	9.19e-2	1.06e-1	1.54e-1	2.63e-1	3.86e-1	4.61e-1	5.46e-1	7.13e-1	7.73e-1	8.08e-1
14	9.00e-2	1.04e-1	1.50e-1	2.58e-1	3.81e-1		5.46e-1	7.20e-1	7.84e-1	8.20e-1
15	8.80e-2	1.01e-1	1.47e-1	2.53e-1	3.76e-1	4.55e-1	5.45e-1	7.26e-1	7.92e-1	8.30e-1
17	8.43e-2	9.67e-2	1.40e-1	2.42e-1	3.65e-1		5.40e-1	7.34e-1	8.07e-1	8.47e-1
20	7.96e-2	9.11e-2	1.31e-1	2.27e-1	3.48e-1	4.30e-1	5.29e-1	7.41e-1	8.22e-1	8.66e-1
25	7.33e-2	8.34e-2	1.19e-1	2.06e-1	3.21e-1	4.04e-1	5.07e-1	7.44e-1	8.38e-1	8.88e-1
30	6.84e-2	7.79e-2	1.11e-1	1.90e-1	2.97e-1	3.79e-1	4.83e-1	7.40e-1	8.46e-1	9.03e-1
40	6.14e-2	6.94e-2	9.80e-2	1.67e-1	2.62e-1		4.39e-1	7.22e-1	8.52e-1	9.20e-1
50	5.66e-2	6.39e-2	8.97e-2	1.52e-1	2.38e-1	3.04e-1	4.02e-1	6.98e-1	8.51e-1	9.30e-1
70	5.01e-2	5.65e-2	7.90e-2	1.33e-1	2.06e-1		3.48e-1	6.47e-1	8.37e-1	9.41e-1
100	4.35e-2	4.94e-2	7.06e-2	1.16e-1	1.78e-1	2.27e-1	2.98e-1	5.78e-1	8.04e-1	9.47e-1
140	3.86e-2	4.35e-2	6.14e-2	1.04e-1	1.58e-1		2.62e-1	5.07e-1	7.52e-1	9.48e-1
200	3.27e-2	3.73e-2	5.42e-2	9.20e-2	1.41e-1	1.77e-1	2.31e-1	4.36e-1	6.78e-1	9.43e-1
300	2.66e-2	3.06e-2	4.47e-2	7.88e-2	1.24e-1		2.04e-1	3.73e-1	5.84e-1	9.24e-1
500	1.96e-2	2.28e-2	3.43e-2	6.32e-2	1.02e-1	1.31e-1	1.71e-1	3.15e-1	4.76e-1	8.67e-1
1000	1.10e-2	1.30e-2	2.10e-2	4.24e-2	7.19e-2	9.78e-2	1.31e-1	2.49e-1	3.71e-1	7.08e-1

Average depth (mean range) in Å of D implanted in Be
 ne = 19. na = 10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	4.20e+0									
11	4.53e-10	4.47e+0	4.31e+0	4.06e+0	3.87e+0		3.63e-40	3.37e-10	3.24e-j-0	3.12e-j-0
12	4.85e-10	4.78e+0	4.61e+0	4.35e+0	4.14e-f-0	4.01e+0	3.89e+0	3.62e+0	3.48e+0	3.38e+0
13	5.16e-10	5.08e+0	4.90e-10	4.62e+0	4.40e+0	4.26e+0	4.14e+0	3.86e+0	3.72e+0	3.60e+0
14	5.47e+0	5.39e+0	5.19e+0	4.88e-f-0	4.66e-f-0		4.39e+0	4.09e-f-0	3.95e-f-0	3.82e-j-0
15	5.77e+0	5.68e+0	5.47e-10	5.15e+0	4.90e+0	4.75e+0	4.62e-f-0	4.32e-f-0	4.17e+0	4.04e+0
17	6.36e+0	6.26e-10	6.02e-10	5.66e-j-0	5.39e+0		5.08e-10	4.76e-10	4.59e+0	4.44e-10
20	7.21e+0	7.10e-10	6.82e-10	6.39e-10	6.08e-10	5.91e+0	5.74e-10	5.39e+0	5.21e+0	5.02e-10
25	8.61e+0	8.48e+0	8.11e-10	7.59e-10	7.20e-10	6.99e+0	6.79e-10	6.37e+0	6.17e+0	5.96e-10
30	9.95e+0	9.79e+0	9.36e+0	8.74e+0	8.29e-10	8.11e+0	7.81e+0	7.36e+0	7.09e+0	6.84e+0
40	1.26e-1	1.24e+1	1.18e+1	1.10e+1	1.04e+1		9.78e+0	9.19e-f-0	8.86e+0	8.59e-f-0
50	1.52e-1	1.49e-1	1.42e-H	1.31e+1	1.24e+1	1.20e+1	1.17e+1	1.10e+1	1.06e-1	1.02e+1
70	2.02e+1	1.98e+1	1.89e-H	1.74e-f-1	1.63e-1		1.54e-J-1	1.45e+1	1.41e-j-1	1.34e+1
100	2.76e+1	2.71e-f-1	2.57e-f-1	2.37e+1	2.21e-f-1	2.15e+1	2.07e+1	1.94e+1	1.88e+1	1.85e+1
140	3.75e+1	3.69e+1	3.47e+1	3.18e-f-1	2.97e+1		2.77e-j-1	2.60e-f-1	2.52e+1	2.42e-f-1
200	5.22e+1	5.12e-f-1	4.82e+1	4.41e+1	4.08e-1	3.91e-j-1	3.79e-1	3.52e+1	3.43e+1	3.33e+1
300	7.68e+1	7.51e+1	7.07e+1	6.40e+1	5.88e+1		5.44e-1	5.03e+1	4.90e-1	4.85e+1
500	1.26e+2	1.24e-1	1.15e+2	1.03e+2	9.47e-H	9.06e+1	8.66e+1	7.94e+1	7.69e+1	7.60e+1
1000	2.51e+2	2.45e+2	2.26e+2	1.99e+2	1.81e+2	1.69e+2	1.61e+2	1.45e+2	1.39e-j-2	1.37e+2

D → Be

D on Be. Maxwellian velocity distribution, sheath potential 3 kT
 z1= 1, m1 = 2.01, z2= 4, m2= 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : testvmcx
 ne=12

kT(eV)	Y	Y _p	E _{sp}	R _N	R _{gj}	E _b	range
2	2.64e-4	4.14e-5	1.57e+0	3.82e-1	1.52e-1	3.98e+0	3.98e+0
2.5	1.00e-3	1.40e-4	1.75e+0	3.61e-1	1.44e-1	4.98e4-0	4.75e+0
3	2.19e-3	2.74e-4	1.87e+0	3.42e-1	1.35e-1	5.94e-f-0	5.48e+0
4	6.45e-3	7.50e-4	2.32e+0	3.11e-1	1.21e-1	7.80e4-0	6.87e+0
5	1.15e-2	1.22e-3	2.64e+0	2.87e-1	1.10e-1	9.60e-)-0	8.17e4-0
7	2.10e-2	1.92e-3	3.21e+0	2.57e-1	9.63e-2	1.31e4-1	1.07e+1
10	3.19e-2	2.47e-3	3.86e+0	2.32e-1	8.55e-2	1.84e+1	1.43e+1
20	4.78e-2	2.80e-3	5.86e+0	1.85e-1	6.44e-2	3.49e+1	2.60e+1
50	5.65e-2	1.96e-3	8.69e+0	1.35e-1	4.48e-2	8.29e+1	6.05e+1
100	5.14e-2	1.22e-3	1.19e+1	1.01e-1	3.11e-2	1.55e+2	1.18e+2
200	3.96e-2	6.26e-4	1.58e+1	6.67e-2	1.90e-2	2.85e+2	2.31e+2
500	2.35e-2	1.87e-4	1.98e4-1	3.00e-2	6.91e-3	5.75e+2	5.48e4-2
1000	1.45e-2	7.95e-5	2.74e+1	1.29e-2	2.69e-3	1.04e+3	1.03e+3
2000	8.34e-3	3.34e-5	4.00e+1	4.38e-3	8.29e-4	1.89e4-3	1.82e+3

D -> Be

D on Be, Maxwellian, energy distribution, sheath potential 0 kT, a=0°
 z1 = 1, m1 = 2.01, z2 = 4, m2 = 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 program : testvmcx
 ne=11

kT(eV)	Y	Y _B	E _{sp}	R _N	R _s	R _b	range
5	4.73e-4	1.10e-4	1.74e-J-0	2.29e-1	8.30e-2	2.72e+0	2.86e+0
7	1.36e-3	2.67e-4	2.06e+0	2.43e-1	8.13e-2	3.52e+0	3.93e+0
10	3.08e-3	5.18e-4	2.52e4-0	2.45e-1	7.61e-2	4.66e+0	5.42e4-0
20	9.32e-3	1.08e-3	3.45e4-0	2.27e-1	6.28e-2	8.26e+0	9.86e+0
30	1.41e-2	1.29e-3	4.12e+0	2.07e-1	5.45e-2	1.19e+1	1.40e+1
40	1.81e-2	1.33e-3	4.41e+0	1.91e-1	4.85e-2	1.52e+1	1.80e+1
50	2.05e-2	1.34e-3	4.91e+0	1.81e-1	4.43e-2	1.84e+1	2.20e+1
100	2.73e-2	1.22e-3	6.69e+0	1.47e-1	3.31e-2	3.38e-H	4.12e+1
200	3.12e-2	8.30e-4	8.03e+0	1.15e-1	2.30e-2	6.04e+1	8.02e+1
500	2.75e-2	3.96e-4	1.08e+1	7.25e-2	1.21e-2	1.26e+2	1.94e+2
1000	2.37e-2	1.92e-4	1.22e4-1	4.82e-2	6.35e-3	1.98e+2	3.75e4-2

D on Be, Maxwellian energy distribution, sheath potential 0 kT, a=60°
 ne=10

kT(eV)	Y	Y _s	R _{sp}	R _{??}	R-b	R _{fc}	range
5	1.22e-3	5.06e-4	3.12e-J-0	5.78e-1	4.08e-1	5.29e+0	1.71e+0
7	4.08e-3	1.41e-3	3.62e+0	6.17e-1	4.11e-1	6.99e-(-0	2.67e4-0
10	1.08e-2	2.94e-3	4.07e+0	6.31e-1	3.93e-1	9.32e+0	4.12e+0
20	4.07e-2	7.48e-3	5.50e+0	6.11e-1	3.34e-1	1.63e4-1	8.45e4-0
30	6.91e-2	1.00e-2	6.54e+0	5.66e-1	2.86e-1	2.28e+1	1.22e+1
50	1.13e-1	1.16e-2	7.74e+0	5.14e-1	2.39e-1	3.49e+1	1.86e4-1
100	1.61e-1	1.03e-2	9.62e4-0	4.36e-1	1.84e-1	6.35e-f-1	3.33e+1
200	1.89e-1	7.79e-3	1.23e+1	3.69e-1	1.47e-1	1.19e-f-2	5.98e4-1
500	1.77e-1	3.94e-3	1.68e+1	2.94e-1	9.81e-2	2.52e+2	1.35e4-2
1000	1.45e-1	2.23e-3	2.32e4-1	2.36e-1	6.47e-2	4.14e+2	2.46e4-2

D on Be, Maxwellian energy distribution, sheath potential 3 kT, a=0°
 z1 = 1, m1 = 2.01, z2 = 4, m2 = 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 program : testvmcx
 ne=10

kT(eV)	Y	Y _f	@sp	Rat	R _b	E _b	range
5	5.49e-3	4.59e-4	1.88e+0	2.39e-1	7.59e-2	7.14e+0	7.92e4-0
7	1.14e-2	9.23e-4	2.54e+0	2.14e-1	6.67e-2	9.82e+0	1.04e+1
10	1.85e-2	1.37e-3	3.34e+0	1.89e-1	5.86e-2	1.39e+1	1.39e-H
20	2.96e-2	1.60e-3	4.85e+0	1.52e-1	4.52e-2	2.67e+1	2.53e+1
30	3.21e-2	1.47e-3	6.19e-(-0	1.32e-1	3.87e-2	3.95e4-1	3.64e+1
50	3.53e-2	1.18e-3	7.49e+0	1.09e-1	3.09e-2	6.38e+1	5.88e+1
100	3.31e-2	6.96e-4	9.46e+0	7.95e-2	2.13e-2	1.20e+2	1.14e+2
200	2.78e-2	3.69e-4	1.19e-(-1	4.87e-2	1.18e-2	2.18e+2	2.26e+2
500	1.70e-2	1.18e-4	1.57e+1	1.96e-2	4.12e-3	4.74e+2	5.52e+2
1000	1.14e-2	4.52e-5	1.79e+1	8.58e-3	1.65e-3	8.66e+2	1.04e+3

D on Be, Maxwellian energy distribution, sheath potential 3 kT, a=60°
 ne=11

kT(eV)	Y	Y _b	E _{sp}	r _b	R _b	•R _b	range
5	9.48e-3	1.07e-3	2.53e-f-0	3.11e-1	1.24e-1	9.01e+0	7.38e-(-0
7	1.84e-2	1.86e-3	3.17e+0	2.77e-1	1.08e-1	1.23e-H	9.67e+0
10	3.10e-2	2.61e-3	3.78e-f-0	2.47e-1	9.39e-2	1.71e+1	1.29e+1
15	4.26e-2	3.03e-3	4.80e+0	2.19e-1	8.08e-2	2.49e+1	1.82e4-1
20	4.96e-2	3.09e-3	5.59e+0	2.01e-1	7.34e-2	3.28e-f-1	2.33e+1
30	6.06e-2	3.01e-3	6.73e+0	1.78e-1	6.33e-2	4.82e+1	3.33e-(-1
50	6.00e-2	2.29e-3	8.60e+0	1.49e-1	5.15e-2	7.79e-(-1	5.34e+1
100	5.74e-2	1.60e-3	1.26e+1	1.14e-1	3.70e-2	1.47e+2	1.03e+2
200	4.54e-2	7.30e-4	1.45e+1	7.68e-2	2.23e-2	2.62e+2	2.02e4-2
500	2.74e-2	2.44e-4	2.01e+1	3.79e-2	9.15e-3	5.44e+2	4.86e-(-2
1000	1.66e-2	1.08e-4	2.92e+1	1.61e-2	3.47e-3	9.71e+2	9.08e+2

T -> Be

Sputtering yield of Be by T

z1 = 1, m1 = 3.02, z2 = 4, m2 = 9.01, sbe = 3.38 eV, rho = 1.80 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trvmc
 ne = 15, na = 10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	1.78e-5	2.56e-5	3.89e-5	4.74e-5	4.98e-5	4.92e-5	4.55e-5	3.43e-5	2.76e-5	2.12e-5
11	7.08e-5	1.00e-4	1.49e-4	1.81e-4	1.96e-4		1.82e-4	1.32e-4	1.05e-4	7.89e-5
12	1.77e-4	2.44e-4	3.77e-4	4.92e-4	5.30e-4	5.47e-4	5.05e-4	3.65e-4	2.66e-4	2.00e-4
13	3.49e-4	4.72e-4	7.42e-4	1.02e-3	1.15e-3		1.09e-3	7.68e-4	5.68e-4	4.10e-4
15	9.03e-4	1.20e-3	1.98e-3	2.92e-3	3.46e-3	3.58e-3	3.43e-3	2.37e-3	1.61e-3	1.07e-3
17	1.74e-3	2.28e-3	3.71e-3	6.05e-3	7.30e-3		7.59e-3	4.98e-3	3.16e-3	1.95e-3
20	3.43e-3	4.39e-3	7.28e-3	1.24e-2	1.60e-2	1.72e-2	1.70e-2	1.06e-2	6.07e-3	3.28e-3
25	6.83e-3	8.60e-3	1.42e-2	2.54e-2	3.52e-2	3.84e-2	3.87e-2	2.31e-2	1.19e-2	5.34e-3
30	1.03e-2	1.29e-2	2.12e-2	3.96e-2	5.62e-2		6.36e-2	3.85e-2	1.88e-2	7.22e-3
50	2.11e-2	2.56e-2	4.26e-2	8.41e-2	1.28e-1		1.61e-1	1.10e-1	4.78e-2	1.09e-2
100	3.27e-2	4.02e-2	6.88e-2	1.33e-1	2.10e-1		2.98e-1	2.73e-1	1.36e-1	1.72e-2
200	4.00e-2	4.94e-2	8.17e-2	1.55e-1	2.44e-1	3.25e-1	3.73e-1	4.63e-1	3.24e-1	3.82e-2
300	4.14e-2	5.06e-2	8.22e-2	1.55e-1	2.38e-1		3.78e-1	5.30e-1	4.67e-1	7.57e-2
500	4.05e-2	4.85e-2	7.70e-2	1.41e-1	2.22e-1	2.66e-1	3.56e-1	5.61e-1	5.99e-1	1.83e-1
1000	3.38e-2	3.94e-2	6.09e-2	1.12e-1	1.73e-1	2.13e-1	2.88e-1	5.01e-1	6.42e-1	4.52e-1

Sputtered energy of Be by T

ne = 15, na = 10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	1.09e-6	1.86e-6	3.57e-6	5.18e-6	5.82e-6	6.06e-6	5.83e-6	4.72e-6	3.89e-6	3.07e-6
11	4.65e-6	7.58e-6	1.40e-5	2.04e-5	2.40e-5		2.44e-5	1.90e-5	1.52e-5	1.17e-5
12	1.22e-5	1.92e-5	3.63e-5	5.67e-5	6.75e-5	7.26e-5	7.05e-5	5.40e-5	4.03e-5	3.08e-5
13	2.51e-5	3.82e-5	7.37e-5	1.19e-4	1.53e-4		1.58e-4	1.17e-4	8.86e-5	6.52e-5
15	6.76e-5	1.01e-4	2.02e-4	3.59e-4	4.73e-4	5.17e-4	5.21e-4	3.86e-4	2.74e-4	1.82e-4
17	1.33e-4	1.93e-4	3.85e-4	7.52e-4	1.03e-3		1.19e-3	8.54e-4	5.66e-4	3.58e-4
20	2.64e-4	3.73e-4	7.46e-4	1.56e-3	2.29e-3	2.62e-3	2.75e-3	1.93e-3	1.16e-3	6.54e-4
25	5.19e-4	7.19e-4	1.40e-3	3.09e-3	4.93e-3	5.86e-3	6.30e-3	4.40e-3	2.45e-3	1.14e-3
30	7.78e-4	1.04e-3	2.03e-3	4.60e-3	7.58e-3		1.02e-2	7.44e-3	3.92e-3	1.58e-3
50	1.42e-3	1.84e-3	3.38e-3	8.04e-3	1.45e-2		2.20e-2	1.89e-2	9.22e-3	2.30e-3
100	1.69e-3	2.13e-3	4.07e-3	9.35e-3	1.69e-2		2.86e-2	3.29e-2	1.94e-2	2.88e-3
200	1.42e-3	1.83e-3	3.48e-3	7.97e-3	1.39e-2		2.42e-2	3.61e-2	2.93e-2	4.46e-3
300	1.16e-3	1.50e-3	2.84e-3	6.41e-3	1.10e-2		1.95e-2	3.19e-2	3.19e-2	6.81e-3
500	8.22e-4	1.04e-3	2.02e-3	4.49e-3	7.99e-3		1.41e-2	2.48e-2	2.93e-2	1.11e-2
1000	4.28e-4	5.57e-4	1.08e-3	2.42e-3	4.34e-3		8.14e-3	1.53e-2	2.05e-2	1.59e-2

T -> Be

Particle reflection coefficient of T backscattered from Be
 z1 = 1. m1 = 3.02. z2 = 4. m2 = 9.01) sbe=3.38 eV. rho = 1.80 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00, kk0=kk0r=2. kdecl = kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne=15. na=10

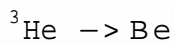
B ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	2.06e-1	2.33e-1	3.15e-1	4.70e-1	6.12e-1	6.89e-1	7.66e-1	8.90e-1	9.28e-1	9.48e-1
11	2.04e-1	2.30e-1	3.10e-1	4.65e-1	6.09e-1		7.67e-1	8.97e-1	9.36e-1	9.56e-1
12	2.01e-1	2.26e-1	3.04e-1	4.58e-1	6.04e-1	6.85e-1	7.67e-1	9.02e-1	9.42e-1	9.62e-1
13	1.98e-1	2.22e-1	2.98e-1	4.51e-1	5.98e-1		7.65e-1	9.05e-1	9.46e-1	9.66e-1
15	1.90e-1	2.12e-1	2.85e-1	4.34e-1	5.83e-1	6.68e-1	7.58e-1	9.08e-1	9.52e-1	9.73e-1
17	1.82e-1	2.04e-1	2.73e-1	4.17e-1	5.66e-1		7.47e-1	9.09e-1	9.56e-1	9.77e-1
20	1.72e-1	1.92e-1	2.57e-1	3.94e-1	5.42e-1	6.33e-1	7.31e-1	9.08e-1	9.59e-1	9.81e-1
25	1.59e-1	1.77e-1	2.37e-1	3.63e-1	5.05e-1	5.96e-1	7.01e-1	9.00e-1	9.60e-1	9.86e-1
30	1.49e-1	1.65e-1	2.20e-1	3.38e-1	4.74e-1		6.71e-1	8.90e-1	9.59e-1	9.88e-1
50	1.23e-1	1.37e-1	1.83e-1	2.79e-1	3.93e-1		5.76e-1	8.41e-1	9.49e-1	9.92e-1
100	9.57e-2	1.07e-1	1.44e-1	2.24e-1	3.12e-1		4.59e-1	7.26e-1	9.01e-1	9.92e-1
200	7.27e-2	8.20e-2	1.14e-1	1.83e-1	2.59e-1		3.78e-1	5.91e-1	7.96e-1	9.85e-1
300	6.04e-2	6.85e-2	9.85e-2	1.61e-1	2.35e-1		3.46e-1	5.32e-1	7.16e-1	9.71e-1
500	4.62e-2	5.27e-2	7.92e-2	1.36e-1	2.05e-1		3.09e-1	4.78e-1	6.27e-1	9.29e-1
1000	2.86e-2	3.39e-2	5.47e-2	1.03e-1	1.65e-1		2.63e-1	4.22e-1	5.45e-1	8.14e-1

Energy reflection coefficient of T backscattered from Be
 ne=15. na=10

B ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	4.43e-2	5.68e-2	9.98e-2	1.99e-1	3.11e-1	3.80e-1	4.56e-1	6.08e-1	6.64e-1	6.98e-1
11	4.48e-2	5.69e-2	9.91e-2	1.99e-1	3.13e-1		4.65e-1	6.26e-1	6.87e-1	7.23e-1
12	4.49e-2	5.66e-2	9.77e-2	1.97e-1	3.13e-1	3.88e-1	4.71e-1	6.41e-1	7.06e-1	7.44e-1
13	4.47e-2	5.59e-2	9.58e-2	1.94e-1	3.12e-1		4.75e-1	6.54e-1	7.21e-1	7.62e-1
15	4.38e-2	5.41e-2	9.19e-2	1.87e-1	3.06e-1	3.86e-1	4.78e-1	6.72e-1	7.47e-1	7.90e-1
17	4.25e-2	5.22e-2	8.77e-2	1.80e-1	2.98e-1		4.76e-1	6.84e-1	7.65e-1	8.12e-1
20	4.05e-2	4.93e-2	8.21e-2	1.68e-1	2.85e-1	3.68e-1	4.69e-1	6.96e-1	7.86e-1	8.37e-1
25	3.75e-2	4.53e-2	7.45e-2	1.52e-1	2.62e-1	3.44e-1	4.50e-1	7.02e-1	7.07e-1	8.66e-1
30	3.51e-2	4.23e-2	6.86e-2	1.39e-1	2.42e-1		4.29e-1	7.01e-1	8.19e-1	8.85e-1
50	2.87e-2	3.43e-2	5.49e-2	1.08e-1	1.88e-1		3.52e-1	6.63e-1	8.30e-1	9.21e-1
100	2.21e-2	2.62e-2	4.15e-2	8.14e-2	1.37e-1		2.55e-1	5.44e-1	7.84e-1	9.43e-1
200	1.65e-2	1.98e-2	3.24e-2	6.42e-2	1.07e-1		1.93e-1	4.02e-1	6.57e-1	9.41e-1
300	1.37e-2	1.63e-2	2.75e-2	5.53e-2	9.51e-2		1.70e-1	3.42e-1	5.61e-1	9.23e-1
500	1.01e-2	1.23e-2	2.15e-2	4.52e-2	8.00e-2		1.45e-1	2.89e-1	4.55e-1	8.63e-1
1000	5.95e-3	7.51e-3	1.39e-2	3.18e-2	5.96e-2		1.14e-1	2.35e-1	3.58e-1	7.04e-1

Average depth (mean range) in Å of T implanted in Be
 ne=15. na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	3.73e-10	3.66e-f-0	3.47e+0	3.18e-10	2.94e-f-0	2.77e+0	2.64e-10	2.29e-10	2.12e+0	1.99e-10
11	4.04e-10	3.96e+0	3.77e+0	3.46e+0	3.21e+0		2.90e-10	2.54e-10	2.36e+0	2.22e-f-0
12	4.34e-10	4.26e+0	4.05e-10	3.72e-10	3.46e-10	3.29e+0	3.14e-10	2.77e+0	2.59e-10	2.44e-f-0
13	4.63e-10	4.54e+0	4.32e+0	3.97e-10	3.70e+0		3.37e+0	3.00e+0	2.81e+0	2.65e+0
15	5.19e+0	5.10e+0	4.84e+0	4.46e-j-0	4.16e+0	3.98e+0	3.81e+0	3.42e-10	3.21e+0	3.04e+0
17	5.74e+0	5.63e+0	5.34e-10	4.92e-10	4.60e+0		4.24e+0	3.82e-10	3.59e+0	3.40e+0
20	6.53e-10	6.41e-f-0	6.08e-f-0	5.59e-10	5.22e-10	5.01e-10	4.81e+0	4.38e+0	4.16e+0	3.93e+0
25	7.82e-10	7.66e+0	7.24e+0	6.65e-10	6.20e+0	5.98e-10	5.74e-10	5.24e+0	4.97e+0	4.73e+0
30	9.07e+0	8.88e+0	8.39e-f-0	7.68e+0	7.16e-10		6.63e-f-0	6.07e-f-0	5.75e+0	5.47e+0
50	1.39e+1	1.36e+1	1.28e-f-1	1.16e-H	1.08e+1		1.00e-f-1	9.15e-10	8.75e+0	8.26e+0
100	2.55e+1	2.50e+1	2.34e+1	2.11e+1	1.94e+1		1.78e+1	1.64e-11	1.57e+1	1.47e-H
200	4.88e-11	4.76e+1	4.44e+1	3.97e+1	3.63e-11		3.31e+1	3.03e-11	2.93e+1	2.83e-f-1
300	7.25e+1	7.07e-f-1	6.58e-11	5.86e-11	5.32e+1		4.82e-11	4.40e-11	4.23e+1	4.09e-11
500	1.22e+2	1.18e-f-2	1.10e+2	9.68e+1	8.74e-11		7.85e-f-1	7.10e+1	6.81e+1	6.59e-11
1000	2.49e-4-2	2.42e+2	2.22e+2	1.94e-1-2	1.73e+2		1.53e+2	1.36e+2	1.29e+2	1.25e+2



Sputtering yield of Be by ${}^3\text{He}$

z1= 2, m1= 3.02, z2= 4, m2= 9.01, sbe=3.38 eV, rho=1.80 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne= 7, na= 1

E ₀ (eV)	0°
20	3.29e-3
30	1.61e-2
50	4.07e-2
100	7.04e-2
200	9.38e-2
500	9.87e-2
1000	9.56e-2

Sputtered energy of Be by ${}^3\text{He}$

ne= 7, na= 1

E ₀ (eV)	0°
20	2.49e-4
30	1.19e-3
50	2.72e-3
100	3.71e-3
200	3.40e-3
500	2.07e-3
1000	1.29e-3

Particle reflection coefficient of ${}^3\text{He}$ backscattered from Be

z1= 2, m1= 3.02, z2= 4, m2= 9.01, sbe=3.38 eV, rho=1.80 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne= 7, na= 1

E ₀ (eV)	0°
20	2.74e-1
30	2.20e-1
50	1.72e-1
100	1.26e-1
200	9.36e-2
500	6.55e-2
1000	4.21e-2

Energy reflection coefficient of ${}^3\text{He}$ backscattered from Be

ne= 7, na= 1

E ₀ (eV)	0°
20	6.57e-2
30	5.25e-2
50	4.00e-2
100	2.82e-2
200	2.02e-2
500	1.40e-2
1000	8.52e-3

Average depth (mean range) in Å of ${}^3\text{He}$ implanted in Be

ne= 7, na= 1

E ₀ (eV)	0°
20	4.25e+0
30	5.76e+0
50	8.52e+0
100	1.49e+1
200	2.70e+1
500	6.20e+1
1000	1.21e+2

⁴He Be

Sputtering yield of Be by ⁴He

z1= 2. m1= 4.00. z2= 4. m2= 9.01. sbe=3.38 eV. rho=1.80 g/cm**3
 ef=0.50 eV. esb=0.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program : trvmc
 ne=23, na= 9

EO(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	3.34e-6	8.39e-6	1.97e-5	2.03e-5	1.82e-5	1.92e-5	8.86e-6	2.04e-6	
11	1.59e-5	3.46e-5	6.56e-5	7.58e-5	8.52e-5	9.01e-5	3.65e-5	7.69e-6	
12	4.18e-5	7.72e-5	1.42e-4	1.95e-4	2.57e-4	2.88e-4	1.09e-4	2.18e-5	
13	8.92e-5	1.51e-4	2.81e-4	4.58e-4	6.51e-4	6.89e-4	2.39e-4	4.23e-5	1.00e-6
15	3.08e-4	4.80e-4	8.95e-4	1.70e-3	2.48e-3	2.44e-3	7.39e-4	1.27e-4	
17	8.21e-4	1.21e-3	2.32e-3	4.43e-3	6.16e-3	5.82e-3	1.64e-3	2.58e-4	2.33e-6
20	2.27e-3	3.25e-3	6.23e-3	1.20e-2	1.59e-2	1.40e-2	3.68e-3	5.39e-4	4.80e-6
25	6.28e-3	8.90e-3	1.68e-2	3.19e-2	4.16e-2	3.50e-2	8.72e-3	1.28e-3	8.40e-6
30	1.16e-2	1.57e-2	3.02e-2	5.75e-2	7.30e-2	6.24e-2	1.72e-2	2.35e-3	2.00e-5
40	2.35e-2	3.11e-2	5.76e-2	1.10e-1	1.41e-1	1.27e-1	3.68e-2	5.16e-3	3.31e-5
50	3.42e-2	4.47e-2	8.12e-2	1.56e-1	2.05e-1	1.94e-1	6.22e-2	9.25e-3	5.43e-5
70	5.03e-2	6.53e-2	1.17e-1	2.24e-1	3.04e-1	3.16e-1	1.25e-1	2.12e-2	1.05e-4
100	6.76e-2	8.77e-2	1.54e-1	2.90e-1	4.05e-1	4.66e-1	2.35e-1	4.84e-2	2.49e-4
140	8.31e-2	1.04e-1	1.82e-1	3.39e-1	4.85e-1	5.98e-1	3.88e-1	1.04e-1	5.83e-4
200	9.60e-2	1.20e-1	2.01e-1	3.71e-1	5.48e-1	7.23e-1	5.99e-1	2.11e-1	1.69e-3
300	1.06e-1	1.30e-1	2.14e-1	3.89e-1	5.83e-1	8.21e-1	8.40e-1	4.34e-1	6.74e-3
400	1.09e-1	1.34e-1	2.13e-1	3.93e-1	5.90e-1	8.56e-1	9.94e-1	6.39e-1	1.68e-2
500	1.10e-1	1.36e-1	2.12e-1	3.88e-1	5.86e-1	8.64e-1	1.09e-0	8.12e-1	3.60e-2
700	1.09e-1	1.30e-1	2.06e-1	3.66e-1	5.61e-1	8.49e-1	1.18e-0	1.06e-0	1.06e-1
1000	1.04e-1	1.25e-1	1.89e-1	3.37e-1	5.21e-1	8.18e-1	1.21e-0	1.24e-0	2.77e-1
2000	8.70e-2	1.00e-1	1.48e-1	2.62e-1	4.03e-1	6.67e-1	1.10e-0	1.36e-0	9.00e-1
5000	5.93e-2	6.60e-2	9.39e-2	1.58e-1	2.38e-1	4.08e-1	7.66e-1	1.09e-0	1.37e-0
10000	4.08e-2	4.52e-2	6.05e-2	9.41e-2	1.42e-1	2.38e-1	4.87e-1	7.53e-1	1.23e-0

Sputtered energy of Be by ⁴He

ne=23, na= 9

B _n (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	1.61e-7	4.95e-7	1.63e-6	2.12e-6	2.20e-6	2.72e-6	1.40e-6	3.30e-7	
11	8.90e-7	2.37e-6	5.87e-6	8.26e-6	1.09e-5	1.29e-5	5.78e-6	1.24e-6	
12	2.60e-6	5.76e-6	1.35e-5	2.27e-5	3.45e-5	4.23e-5	1.80e-5	3.81e-6	
13	5.89e-6	1.19e-5	2.78e-5	5.59e-5	9.05e-5	1.07e-4	4.26e-5	7.71e-6	1.57e-7
15	2.21e-5	4.04e-5	9.59e-5	2.24e-4	3.67e-4	4.05e-4	1.38e-4	2.48e-5	
17	6.21e-5	1.06e-4	2.57e-4	6.06e-4	9.63e-4	1.03e-3	3.28e-4	5.44e-5	4.45e-7
20	1.75e-4	2.92e-4	7.08e-4	1.69e-3	2.60e-3	2.62e-3	7.86e-4	1.21e-4	1.09e-6
25	4.72e-4	7.73e-4	1.87e-3	4.49e-3	6.94e-3	6.81e-3	1.98e-3	3.04e-4	1.70e-6
30	8.45e-4	1.31e-3	3.21e-3	7.87e-3	1.19e-2	1.22e-2	3.75e-3	5.73e-4	
40	1.60e-3	2.38e-3	5.46e-3	1.36e-2	2.14e-2	2.36e-2	8.37e-3	1.25e-3	6.64e-6
50	2.17e-3	3.11e-3	7.01e-3	1.75e-2	2.83e-2	3.34e-2	1.35e-2	2.12e-3	9.91e-6
70	2.82e-3	3.98e-3	8.65e-3	2.15e-2	3.57e-2	4.66e-2	2.38e-2	4.48e-3	1.91e-5
100	3.22e-3	4.52e-3	9.56e-3	2.30e-2	3.89e-2	5.54e-2	3.69e-2	8.80e-3	3.89e-5
140	3.39e-3	4.55e-3	9.58e-3	2.28e-2	3.84e-2	5.70e-2	4.90e-2	1.58e-2	8.24e-5
200	3.19e-3	4.41e-3	8.88e-3	2.07e-2	3.55e-2	5.53e-2	5.89e-2	2.53e-2	2.22e-4
300	2.83e-3	3.79e-3	7.67e-3	1.76e-2	3.03e-2	4.95e-2	6.25e-2	3.85e-2	7.26e-4
400	2.46e-3	3.43e-3	6.71e-3	1.55e-2	2.67e-2	4.40e-2	6.01e-2	4.58e-2	1.55e-3
500	2.27e-3	3.09e-3	5.95e-3	1.36e-2	2.35e-2	3.98e-2	5.82e-2	4.99e-2	2.90e-3
700	1.80e-3	2.41e-3	4.90e-3	1.10e-2	1.91e-2	3.25e-2	5.14e-2	5.13e-2	6.64e-3
1000	1.39e-3	1.94e-3	3.72e-3	8.61e-3	1.50e-2	2.67e-2	4.35e-2	4.75e-2	1.35e-2
2000	7.58e-4	1.02e-3	2.03e-3	4.74e-3	8.54e-3	1.61e-2	2.84e-2	3.53e-2	2.48e-2
5000	2.80e-4	3.74e-4	7.54e-4	1.79e-3	3.26e-3	6.47e-3	1.30e-2	1.88e-2	2.08e-2
10000	1.18e-4	1.59e-4	3.28e-4	7.12e-4	1.32e-3	2.53e-3	6.01e-3	9.39e-3	1.28e-2

${}^4\text{He} \rightarrow \text{Be}$

Particle reflection coefficient of ${}^4\text{He}$ backscattered from Be
 $z1 = 2, m1 = 4.00, z2 = 4, m2 = 9.01, sbe = 3.38 \text{ eV}, \rho = 1.80 \text{ g/cm}^3$
 $ef = 0.50 \text{ eV}, esb = 0.00 \text{ eV}, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 \text{ (KrC)}$
 program : trvmc
 $ne = 23, na = 9$

E_0 (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	3.15E-1	3.55E-1	4.62E-1	6.44E-1	7.88E-1	9.20E-1	9.90E-1	9.99E-1	1.00E-J-0
11	3.05E-1	3.44E-1	4.49E-1	6.32E-1	7.79E-1	9.16E-1	9.90E-1	9.99E-1	1.00E4-0
12	2.94E-1	3.32E-1	4.36E-1	6.20E-1	7.70E-1	9.12E-1	9.89E-1	9.99E-1	1.00E+0
13	2.84E-1	3.20E-1	4.24E-1	6.08E-1	7.61E-1	9.08E-1	9.89E-1	9.99E-1	1.00E4-0
15	2.64E-1	2.98E-1	3.99E-1	5.85E-1	7.42E-1	8.99E-1	9.88E-1	9.99E-1	1.00E+0
17	2.47E-1	2.79E-1	3.76E-1	5.61E-1	7.23E-1	8.90E-1	9.87E-1	9.99E-1	1.00E+0
20	2.25B-1	2.54E-1	3.47E-1	5.29E-1	6.96E-1	8.74E-1	9.85E-1	9.99E-1	1.00E4-0
25	1.97E-1	2.23E-1	3.08E-1	4.82E-1	6.52E-1	8.47E-1	9.81E-1	9.98E-1	1.00E+0
30	1.77E-1	2.00E-1	2.77E-1	4.41E-1	6.12E-1	8.21E-1	9.76E-1	9.98E-1	1.00E+0
40	1.50E-1	1.69E-1	2.36E-1	3.81E-1	5.48E-1	7.69E-1	9.65E-1	9.97E-1	1.00E+0
50	1.32E-1	1.50E-1	2.08E-1	3.40E-1	4.98E-1	7.21E-1	9.52E-1	9.96E-1	1.00E-J-0
70	1.10E-1	1.25E-1	1.75E-1	2.85E-1	4.25E-1	6.42E-1	9.21E-1	9.92E-1	1.00E+0
100	9.22E-2	1.05E-1	1.48E-1	2.44E-1	3.59E-1	5.58E-1	8.68E-1	9.82E-1	1.00E+0
140	7.91E-2	8.69E-2	1.26E-1	2.10E-1	3.08E-1	4.87E-1	8.00E-1	9.64E-1	1.00E+0
200	6.61E-2	7.43E-2	1.09E-1	1.82E-1	2.74E-1	4.19E-1	7.13E-1	9.27E-1	1.00E+0
300	5.40E-2	6.34E-2	9.14E-2	1.58E-1	2.37E-1	3.68E-1	6.21E-1	8.57E-1	9.99E-1
400	4.63E-2	5.55E-2	8.12E-2	1.42E-1	2.18E-1	3.37E-1	5.62E-1	7.93E-1	9.97E-1
500	4.17E-2	4.99E-2	7.43E-2	1.34E-1	2.05E-1	3.20E-1	5.26E-1	7.41E-1	9.93E-1
700	3.43E-2	4.10E-2	6.39E-2	1.17E-1	1.85E-1	2.95B-1	4.81E-1	6.63E-1	9.79E-1
1000	2.79E-2	3.31E-2	5.39E-2	1.03B-1	1.68E-1	2.71E-1	4.43E-1	6.00E-1	9.42E-1
2000	1.67E-2	2.05E-2	3.54E-2	7.54E-2	1.31E-1	2.26E-1	3.86E-1	5.15E-1	8.05E-1
5000	6.59E-3	8.27E-3	1.62E-2	4.10E-2	8.21E-2	1.66E-1	3.20E-1	4.40E-1	6.43E-1
10000	2.86E-3	3.54E-3	6.96E-3	2.06E-2	4.80E-2	1.14E-1	2.63E-1	3.85E-1	5.69E-1

Energy reflection coefficient of ${}^4\text{He}$ backscattered from Be
 $ne = 23, na = 9$

E_0 (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	4.87E-2	6.66E-2	1.24E-1	2.50E-1	3.91E-1	5.85E-1	7.99E-1	8.86E-1	9.48E-1
11	4.76E-2	6.47E-2	1.21E-1	2.47E-1	3.88E-1	5.86E-1	8.03E-1	8.90E-1	9.52E-1
12	4.64E-2	6.27E-2	1.17E-1	2.43E-1	3.85E-1	5.86E-1	8.06B-1	8.94E-1	9.55E-1
13	4.51E-2	6.08E-2	1.14E-1	2.39E-1	3.82E-1	5.85E-1	8.09E-1	8.98E-1	9.58E-1
15	4.26E-2	5.70E-2	1.08E-1	2.30E-1	3.74E-1	5.81E-1	8.13E-1	9.03E-1	9.62E-1
17	4.02B-2	5.34E-2	1.01E-1	2.21E-1	3.66E-1	5.76E-1	8.15E-1	9.07E-1	9.65E-1
20	3.70E-2	4.88E-2	9.29E-2	2.07E-1	3.51E-1	5.66E-1	8.17E-1	9.11E-1	9.68E-1
25	3.28E-2	4.28E-2	8.12E-2	1.86E-1	3.27E-1	5.48E-1	8.16E-1	9.16E-1	9.72E-1
30	2.97E-2	3.85E-2	7.21E-2	1.68E-1	3.04E-1	5.28E-1	8.12E-1	9.18E-1	9.78E-1
40	2.53E-2	3.21E-2	5.98E-2	1.40E-1	2.64E-1	4.88E-1	7.99E-1	9.20E-1	9.77E-1
50	2.21E-2	2.83E-2	5.18E-2	1.21E-1	2.33E-1	4.49E-1	7.83E-1	9.18E-1	9.78E-1
70	1.85E-2	2.33E-2	4.23E-2	9.73E-2	1.90E-1	3.85E-1	7.46E-1	9.11E-1	9.79E-1
100	1.55E-2	1.94E-2	3.47E-2	7.91E-2	1.51E-1	3.16E-1	6.85E-1	8.94E-1	9.79E-1
140	1.30E-2	1.60E-2	2.92E-2	6.62E-2	1.24E-1	2.60E-1	6.10E-1	8.64E-1	9.79E-1
200	1.10B-2	1.38E-2	2.50E-2	5.56E-2	1.05E-1	2.11E-1	5.16E-1	8.13B-1	9.77E-1
300	9.04E-3	1.16E-2	2.05E-2	4.75E-2	8.75E-2	1.75E-1	4.20E-1	7.22E-1	9.73E-1
400	7.68E-3	1.00E-2	1.85E-2	4.15E-2	7.82E-2	1.55E-1	3.62E-1	6.43E-1	9.67E-1
500	6.94E-3	9.10E-3	1.67E-2	3.86E-2	7.29E-2	1.43E-1	3.24E-1	5.79E-1	9.59E-1
700	5.67E-3	7.40E-3	1.43E-2	3.35E-2	6.45E-2	1.29E-1	2.81E-1	4.88E-1	9.34E-1
1000	4.58E-3	5.91E-3	1.17E-2	2.93E-2	5.70E-2	1.14B-1	2.48E-1	4.16E-1	8.78E-1
2000	2.62E-3	3.49E-3	7.42E-3	1.99E-2	4.14E-2	8.85E-2	2.00B-1	3.21E-1	6.84E-1
5000	9.27E-4	1.28E-3	2.96E-3	9.22E-3	2.20E-2	5.48E-2	1.41B-1	2.36E-1	4.60E-1
10000	3.74E-4	4.89E-4	1.13E-3	3.92E-3	1.03E-2	3.01E-2	9.46E-2	1.74E-1	3.50E-1

Average depth (mean range) in Å of ${}^4\text{He}$ in Be
 $ne = 23, na = 9$

B_0 (°V)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	2.40E+0	2.30E+0	2.20E-J-0	2.10E4-0	1.90E+0	1.70E4-0	1.30E+0	1.10B+0	6.00E-1
11	2.60B+0	2.50B+0	2.40E+0	2.20E+0	2.00E4-0	1.80E4-0	1.50B+0	1.20E+0	7.00E-1
12	2.80B-J-0	2.70E+0	2.60E+0	2.40E4-0	2.20E+0	1.90E+0	1.60E+0	1.30E+0	8.00E-1
13	2.90E+0	2.90E+0	2.70B+0	2.50E+0	2.30E-J-0	2.10E4-0	1.70E+0	1.40E+0	9.00E-1
15	3.30E+0	3.20E+0	3.10E+0	2.80E4-0	2.60E+0	2.30E+0	1.90E+0	1.60E+0	1.10E+0
17	3.60E+0	3.50E+0	3.40E4-0	3.10E4-0	2.90E4-0	2.50E-J-0	2.10E+0	1.80E4-0	1.30B+0
20	4.10E+0	4.00E-J-0	3.80E+0	3.50E+0	3.20E+0	2.90E+0	2.40E-J-0	2.10E4-0	1.60E-J-0
25	4.80E+0	4.70E4-0	4.40E+0	4.10E4-0	3.80E+0	3.40E+0	2.90E+0	2.60E+0	2.10E4-0
30	5.50E+0	5.40E+0	5.10E4-0	4.60E4-0	4.30E+0	3.90E+0	3.40E+0	3.00E+0	2.50E-I-0
40	6.80E-J-0	6.70E+0	6.30E4-0	5.70E4-0	5.30E-J-0	4.80E+0	4.20E+0	3.80E+0	3.20B+0
50	8.10E4-0	7.90E4-0	7.50E+0	6.70E+0	6.20E+0	5.70E+0	5.00E4-0	4.50E4-0	3.90E4-0
70	1.06E+1	1.04E+1	9.70E4-0	8.70E4-0	8.00E+0	7.30E+0	6.50E+0	6.00E+0	4.60E4-0
100	1.42E+1	1.39E4-1	1.29E+1	1.16E+1	1.06E-J-1	9.60E+0	8.70E+0	8.00E+0	6.50E4-0
140	1.89E+1	1.84E+1	1.71E+1	1.53E+1	1.39E+1	1.26E+1	1.13E+1	1.06E+1	9.00E4-0
200	2.58E+1	2.51E+1	2.33E+1	2.07E+1	1.88E+1	1.69E4-1	1.52E+1	1.43E+1	1.18E+1
300	3.72E+1	3.61E+1	3.35E+1	2.95E+1	2.67E4-1	2.39E-J-1	2.15E+1	2.04E-J-1	1.82E4-1
400	4.84E+1	4.71B-J-1	4.38E+1	3.84E+1	3.46E+1	3.09E+1	2.77E+1	2.64E-J-1	2.39E+1
500	6.00E+1	5.82E+1	5.38E+1	4.71E+1	4.25E+1	3.77E-J-1	3.37E+1	3.23E+1	2.97E+1
700	8.29E+1	8.07E+1	7.41E4-1	6.49E+1	5.81E+1	5.12E4-1	4.56E+1	4.33E4-1	4.19E+1
1000	1.18E+2	1.15E+2	1.05E+2	9.16E+1	8.12E4-1	7.14E+1	6.33E+1	6.02E+1	5.84E+1
2000	2.38E+2	2.30E+2	2.10E-J-2	1.80E+2	1.58E+2	1.37E+2	1.19E4-2	1.12B+2	1.08E+2
5000	5.97E+2	5.77E+2	5.22E+2	4.38E+2	3.75E+2	3.15E4-2	2.63E+2	2.43E+2	2.30E+2
10000	1.15E+3	1.11E+3	1.00E4-3	8.29E4-2	6.95E+2	5.62E+2	5.00E+2	4.08E+2	3.78E+2

Be -> Be

Sputtering yield of Be by Be

z1= 4, m1= 9.01, z2= 4, m2= 9.01, sbe = 3.38 eV, rho = 1.80 g/cm**3
 ef=3.33 eV, esb= 3.38 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trvnc
 ne=24, na=15

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
5				3.05e-6	7.10e-6	9.83e-6	1.05e-5	1.02e-5	1.03e-5
6			3.17e-6	2.32e-5	3.87e-5	4.62e-5	4.62e-5	4.64e-5	4.61e-5
7			1.36e-5	6.54e-5	9.76e-5	1.18e-4	1.30e-4	1.34e-4	1.38e-4
8		3.35e-6	3.53e-5	1.35e-4	1.96e-4	2.71e-4	3.47e-4	3.80e-4	4.01e-4
9		9.66e-6	7.48e-5	2.48e-4	3.92e-4	6.31e-4	8.84e-4	9.58e-4	1.01e-3
10		2.12e-5	1.33e-4	4.22e-4	7.84e-4	1.37e-3	1.89e-3	2.04e-3	2.17e-3
11	6.78e-6	4.03e-5	2.21e-4	7.39e-4	1.51e-3	2.62e-3	3.47e-3	3.77e-3	3.74e-3
12	1.26e-5	6.63e-5	3.47e-4	1.22e-3	2.74e-3	4.67e-3	5.88e-3	6.00e-3	6.04e-3
13	2.14e-5	1.01e-4	5.39e-4	2.07e-3	4.48e-3	7.29e-3	8.69e-3	8.73e-3	8.84e-3
15	5.23e-5	2.17e-4	1.22e-3	4.95e-3	9.90e-3	1.48e-2	1.61e-2	1.57e-2	1.51e-2
17	1.15e-4	4.40e-4	2.39e-3	9.79e-3	1.79e-2	2.48e-2	2.50e-2	2.35e-2	2.22e-2
20	3.05e-4	1.09e-3	5.63e-3	2.08e-2	3.47e-2	4.38e-2	4.04e-2	3.65e-2	3.33e-2
25	1.09e-3	3.32e-3	1.54e-2	4.77e-2	7.14e-2	8.21e-2	6.87e-2	5.85e-2	5.09e-2
30	2.68e-3	7.27e-3	2.95e-2	8.18e-2	1.16e-1	1.25e-1	9.74e-2	7.92e-2	6.58e-2
40	8.41e-3	1.93e-2	6.54e-2	1.58e-1	2.12e-1	2.15e-1	1.50e-1	1.12e-1	8.65e-2
50	1.68e-2	3.45e-2	1.03e-1	2.33e-1	3.06e-1	3.04e-1	1.99e-1	1.37e-1	9.65e-2
70	3.77e-2	6.72e-2	1.73e-1	3.59e-1	4.70e-1	4.71e-1	2.87e-1	1.73e-1	1.03e-1
100	7.00e-2	1.11e-1	2.49e-1	4.93e-1	6.63e-1	6.94e-1	4.21e-1	2.29e-1	1.06e-1
200	1.43e-1	1.98e-1	3.77e-1	7.18e-1	1.02e-0	1.21e-0	8.77e-1	4.38e-1	1.16e-1
300	1.86e-1	2.46e-1	4.37e-1	8.19e-1	1.19e-0	1.52e-0	1.30e-0	6.90e-1	1.37e-1
500	2.33e-1	2.93e-1	4.94e-1	9.03e-1	1.34e-0	1.85e-0	1.92e-0	1.23e-0	2.08e-1
700	2.57e-1	3.16e-1	5.11e-1	9.30e-1	1.40e-0	2.00e-0	2.31e-0	1.72e-0	3.09e-1
1000	2.74e-1	3.31e-1	5.19e-1	9.31e-1	1.41e-0	2.09e-0	2.65e-0	2.27e-0	5.10e-1
2000	2.53e-1								
3000	2.63e-1						2.99e-0	3.38e-0	2.20e-0
5000	2.27e-1								

E ₀ (eV)	0°	20°	40°	50°	60°	70°	75°	77.5°	80°	85°
1000	2.65e-1	3.64e-1	7.25e-1	1.11e-0	1.67e-0	2.41e-0	2.63e-0		2.27e-0	5.02e-1
3000	2.63e-1	3.25e-1	6.02e-1	9.12e-1	1.46e-0	2.35e-0	2.99e-0	3.20e-0	3.38e-0	2.20e-0

Sputtering energy of Be by Be

ne=24, na=15

Bq(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
5				3.14e-7	8.46e-7	1.38e-6	1.62e-6	1.63e-6	1.71e-6
6			2.59e-7	2.61e-6	5.18e-6	7.07e-6	7.93e-6	8.26e-6	8.46e-6
7			1.17e-6	7.76e-6	1.39e-5	1.96e-5	2.41e-5	2.56e-5	2.71e-5
8		2.15e-7	3.18e-6	1.64e-5	2.93e-5	4.74e-5	6.86e-5	7.69e-5	8.28e-5
9		6.65e-7	6.91e-6	3.11e-5	6.10e-5	1.16e-4	1.82e-4	2.02e-4	2.18e-4
10		1.56e-6	1.25e-5	5.47e-5	1.28e-4	2.62e-4	4.01e-4	4.50e-4	4.87e-4
11	3.57e-7	2.98e-6	2.14e-5	1.01e-4	2.58e-4	5.22e-4	7.69e-4	8.63e-4	8.62e-4
12	6.92e-7	4.94e-6	3.46e-5	1.73e-4	4.79e-4	9.61e-4	1.34e-3	1.42e-3	1.45e-3
13	1.18e-6	7.66e-6	5.51e-5	3.05e-4	8.07e-4	1.54e-3	2.03e-3	2.10e-3	2.18e-3
15	2.97e-6	1.66e-5	1.33e-4	7.60e-4	1.85e-3	3.22e-3	3.91e-3	3.94e-3	3.87e-3
17	6.75e-6	3.49e-5	2.70e-4	1.56e-3	3.44e-3	5.56e-3	6.23e-3	6.08e-3	5.87e-3
20	1.84e-5	8.91e-5	6.56e-4	3.39e-3	6.76e-3	1.01e-2	1.04e-2	9.68e-3	9.00e-3
25	6.59e-5	2.69e-4	1.77e-3	7.72e-3	1.40e-2	1.90e-2	1.79e-2	1.57e-2	1.39e-2
30	1.53e-4	5.54e-4	3.25e-3	1.29e-2	2.23e-2	2.87e-2	2.53e-2	2.12e-2	1.79e-2
40	4.26e-4	1.30e-3	6.53e-3	2.31e-2	3.80e-2	4.69e-2	3.79e-2	2.93e-2	2.27e-2
50	7.62e-4	2.09e-3	9.24e-3	3.09e-2	5.09e-2	6.20e-2	4.77e-2	3.43e-2	2.43e-2
70	1.47e-3	3.45e-3	1.33e-2	4.03e-2	6.67e-2	8.36e-2	6.18e-2	3.97e-2	2.37e-2
100	2.37e-3	4.85e-3	1.61e-2	4.58e-2	7.73e-2	1.01e-1	7.68e-2	4.54e-2	2.12e-2
200	3.69e-3	6.38e-3	1.73e-2	4.58e-2	7.90e-2	1.15e-1	1.07e-1	6.12e-2	1.66e-2
300	4.03e-3	6.49e-3	1.64e-2	4.21e-2	7.23e-2	1.12e-1	1.22e-1	7.56e-2	1.61e-2
500	3.96e-3	6.07e-3	1.44e-2	3.56e-2	6.24e-2	1.01e-1	1.28e-1	9.56e-2	1.84e-2
700	3.68e-3	5.51e-3	1.27e-2	3.11e-2	5.55e-2	9.18e-2	1.24e-1	1.07e-1	2.31e-2
1000	3.25e-3	4.82e-3	1.08e-2	2.64e-2	4.81e-2	8.10e-2	1.17e-1	1.12e-1	3.07e-2
3000	1.87e-3						7.86e-2	9.04e-2	5.93e-2

E ₀ (eV)	0°	20°	40°	50°	60°	70°	75°	77.5°	80°	85°
1000	3.13e-3	5.83e-3	1.88e-2	3.42e-2	6.07e-2	9.75e-2	1.16e-1		1.12e-1	3.08e-2
3000	1.87e-3	3.02e-3	9.30e-3	1.90e-2	3.44e-2	6.14e-2	7.86e-2	8.59e-2	9.04e-2	5.93e-2

Be -> Be

Particle reflection coefficient of Be backscattered from Be

z1 = 4, m1 = 9.01, z2 = 4, m2 = 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=3.33 eV, esb=3.38 eV, ca=1.00, kk0=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne = 24, na=16

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
5							2.61e-8	1.04e-7	1.79e-7
6				1.86e-8	1.75e-7	5.41e-6	2.48e-5	4.10e-5	5.53e-5
7				3.86e-7	1.37e-5	1.13e-4	4.21e-4	6.15e-4	7.63e-4
8				7.09e-6	1.20e-4	7.28e-4	2.15e-3	2.93e-3	3.51e-3
9			4.43e-7	6.14e-5	5.57e-4	2.63e-3	6.71e-3	8.81e-3	1.04e-2
10			6.21e-6	2.91e-4	1.80e-3	6.80e-3	1.55e-2	1.97e-2	2.28e-2
11		1.23e-7	3.32e-5	8.97e-4	4.43e-3	1.40e-2	2.89e-2	3.59e-2	4.06e-2
12		8.83e-7	1.03e-4	2.15e-3	8.66e-3	2.46e-2	4.72e-2	5.72e-2	6.40e-2
13	3.54e-8	4.31e-6	2.64e-4	4.10e-3	1.49e-2	3.81e-2	6.91e-2	8.23e-2	9.10e-2
15	9.31e-7	3.54e-5	1.00e-3	1.07e-2	3.25e-2	7.24e-2	1.21e-1	1.41e-1	1.55e-1
17	7.28e-6	1.30e-4	2.37e-3	2.00e-2	5.47e-2	1.13e-1	1.81e-1	2.08e-1	2.26e-1
20	4.31e-5	4.34e-4	5.59e-3	3.70e-2	9.22e-2	1.77e-1	2.73e-1	3.11e-1	3.35e-1
25	1.90e-4	1.28e-3	1.19e-2	6.57e-2	1.52e-1	2.78e-1	4.17e-1	4.71e-1	5.05e-1
30	4.20e-4	2.31e-3	1.77e-2	8.98e-2	1.99e-1	3.58e-1	5.33e-1	6.01e-1	6.40e-1
40	1.02e-3	4.22e-3	2.65e-2	1.18e-1	2.54e-1	4.56e-1	6.79e-1	7.60e-1	8.07e-1
50	1.63e-3	5.73e-3	3.17e-2	1.28e-1	2.72e-1	4.95e-1	7.46e-1	8.35e-1	8.84e-1
70	2.72e-3	7.80e-3	3.48e-2	1.28e-1	2.70e-1	5.03e-1	7.82e-1	8.88e-1	9.41e-1
100	3.91e-3	9.09e-3	3.47e-2	1.17e-1	2.44e-1	4.68e-1	7.78e-1	9.03e-1	9.65e-1
200	5.32e-3	9.73e-3	2.92e-2	8.92e-2	1.81e-1	3.64e-1	6.94e-1	8.82e-1	9.79e-1
300	5.18e-3	8.94e-3	2.57e-2	7.52e-2	1.54e-1	3.05e-1	6.16e-1	8.41e-1	9.80e-1
500	4.65e-3	7.66e-3	2.12e-2	6.12e-2	1.26e-1	2.51e-1	5.09e-1	7.55e-1	9.74e-1
700	4.04e-3	6.53e-3	1.83e-2	5.38e-2	1.11e-1	2.23e-1	4.56e-1	6.84e-1	9.62e-1
1000	3.42e-3	5.54e-3	1.53e-2	4.69e-2	9.92e-2	2.00e-1	4.05e-1	6.12e-1	9.39e-1

E ₀ (eV)	0°	20°	40°	50°	60°	70°	75°	77.5°	80°	82.5°	85°
1000	3.62e-3	6.70e-3	3.33e-2	6.57e-2	1.44e-1	2.79e-1	4.03e-1	3.75e-1	6.07e-1		9.40e-1
3000	1.30e-3	3.30e-3	1.98e-2	4.40e-2	1.09e-1	2.13e-1	3.15e-1	3.75e-1	4.54e-1	5.66e-1	7.71e-1

Energy reflection coefficient of Be backscattered from Be

ne=24, na=16

Bo (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
5							3.22e-9	1.42e-8	2.48e-8
6				2.21e-9	2.12e-8	7.74e-7	3.92e-6	6.78e-6	9.38e-6
7				4.45e-8	2.09e-6	2.03e-5	8.56e-5	1.31e-4	1.67e-4
8				9.31e-7	2.10e-5	1.50e-4	5.03e-4	7.16e-4	8.79e-4
9			4.36e-8	8.72e-6	1.03e-4	5.90e-4	1.70e-3	2.33e-3	2.82e-3
10			6.66e-7	4.45e-5	3.51e-4	1.61e-3	4.19e-3	5.60e-3	6.62e-3
11		9.90e-9	4.06e-6	1.47e-4	9.07e-4	3.48e-3	8.34e-3	1.08e-2	1.26e-2
12		7.44e-8	1.34e-5	3.73e-4	1.85e-3	6.43e-3	1.44e-2	1.83e-2	2.11e-2
13	2.07e-9	3.70e-7	3.49e-5	7.50e-4	3.35e-3	1.04e-2	2.21e-2	2.77e-2	3.15e-2
15	6.56e-8	3.40e-6	1.41e-4	2.11e-3	7.88e-3	2.14e-2	4.19e-2	5.17e-2	5.84e-2
17	5.27e-7	1.35e-5	3.50e-4	4.15e-3	1.41e-2	3.56e-2	6.66e-2	8.09e-2	9.08e-2
20	3.24e-6	4.71e-5	8.71e-4	8.23e-3	2.54e-2	5.96e-2	8.23e-2	1.30e-1	1.45e-1
25	1.44e-5	1.40e-4	1.90e-3	1.55e-2	4.51e-2	1.01e-1	1.81e-1	2.16e-1	2.40e-1
30	3.07e-5	2.49e-4	2.86e-3	2.18e-2	6.16e-2	1.39e-1	2.46e-1	2.96e-1	3.28e-1
40	7.07e-5	4.30e-4	4.24e-3	2.92e-2	8.29e-2	1.90e-1	3.47e-1	4.18e-1	4.65e-1
50	1.08e-4	5.54e-4	4.88e-3	3.15e-2	9.08e-2	2.16e-1	4.09e-1	5.00e-1	5.59e-1
70	1.67e-4	6.85e-4	5.10e-3	3.07e-2	9.04e-2	2.29e-1	4.68e-1	5.91e-1	6.70e-1
100	2.20e-4	7.46e-4	4.68e-3	2.67e-2	7.93e-2	2.15e-1	4.92e-1	6.48e-1	7.53e-1
200	2.83e-4	7.30e-4	3.60e-3	1.81e-2	5.23e-2	1.55e-1	4.46e-1	6.76e-1	8.49e-1
300	2.68e-4	6.46e-4	3.03e-3	1.43e-2	4.19e-2	1.21e-1	3.81e-1	6.45e-1	8.76e-1
500	2.50e-4	5.51e-4	2.43e-3	1.13e-2	3.20e-2	9.16e-2	2.94e-1	5.61e-1	8.85e-1
700	2.21e-4	4.76e-4	2.10e-3	9.68e-3	2.76e-2	7.79e-2	2.49e-1	4.88e-1	8.75e-1
1000	1.89e-4	4.12e-4	1.78e-3	8.41e-3	2.44e-2	6.79e-2	2.09e-1	4.15e-1	8.48e-1

E ₀ (eV)	0°	20°	40°	50°	60°	70°	75°	77.5°	80°	82.5°	85°
1000	1.86e-4	5.43e-4	5.39e-3	1.40e-2	4.05e-2	1.14e-1	2.05e-1	1.91e-1	4.10e-1		8.49e-1
3000	7.79e-5	3.43e-4	3.09e-3	9.18e-3	3.03e-2	8.05e-2	1.41e-1	1.91e-1	2.61e-1	3.79e-1	6.30e-1

Be -> Be

Average depth (mean range) in Å of Be implanted in Be
 z1= 4. m1= 9.01. z2= 4. m2= 9.01. sbe=3.38 eV. rho=1.80 g/cm**3
 ef=3.33 eV. esb= 3.38 eV. kk0=kk0r=2. kdee1=kdee2 = 3. ipot=ipotr=1 (KrC), ca=1.00
 program : trvmc
 ne= 24, na=10

Bo (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
5	6.00E-1	5.00E-1	5.00E-1	4.00E-1	4.00E-1	3.00E-1	3.00E-1	3.00E-1	3.00E-1
6	8.00E-1	7.00E-1	6.00E-1	5.00E-1	4.00E-1	4.00E-1	3.00E-1	3.00E-1	3.00E-1
7	9.00E-1	9.00E-1	8.00E-1	6.00E-1	5.00E-1	4.00E-1	3.00E-1	3.00E-1	3.00E-1
8	1.10E+0	1.00E+0	9.00E-1	7.00E-1	5.00E-1	4.00E-1	3.00E-1	3.00E-1	3.00E-1
9	1.20E+0	1.10E+0	1.00E+0	7.00E-1	6.00E-1	4.00E-1	3.00E-1	3.00E-1	3.00E-1
10	1.30E+0	1.20E+0	1.00E+0	8.00E-1	6.00E-1	5.00E-1	3.00E-1	3.00E-1	3.00E-1
11	1.40E+0	1.30E+0	1.10E+0	9.00E-1	7.00E-1	5.00E-1	4.00E-1	3.00E-1	3.00E-1
12	1.50E+0	1.40E+0	1.20E+0	9.00E-1	7.00E-1	5.00E-1	4.00E-1	3.00E-1	3.00E-1
13	1.70E+0	1.60E+0	1.30E+0	1.00E+0	8.00E-1	5.00E-1	4.00E-1	3.00E-1	3.00E-1
15	1.90E+0	1.80E+0	1.50E+0	1.10E+0	8.00E-1	6.00E-1	4.00E-1	3.00E-1	3.00E-1
17	2.10E+0	2.00E+0	1.70E+0	1.30E+0	9.00E-1	7.00E-1	4.00E-1	4.00E-1	3.00E-1
20	2.40E+0	2.30E+0	2.00E+0	1.50E+0	1.10E+0	8.00E-1	5.00E-1	4.00E-1	4.00E-1
25	2.90E+0	2.80E+0	2.40E+0	1.80E+0	1.40E+0	1.00E+0	6.00E-1	5.00E-1	4.00E-1
30	3.40E+0	3.20E+0	2.80E+0	2.20E+0	1.70E+0	1.20E+0	8.00E-1	6.00E-1	5.00E-1
40	4.20E+0	4.10E+0	3.60E+0	2.90E+0	2.30E+0	1.80E+0	1.20E+0	9.00E-1	8.00E-1
50	5.00E+0	4.80E+0	4.30E+0	3.50E+0	3.00E+0	2.40E+0	1.70E+0	1.30E+0	1.10E+0
70	6.60E+0	6.40E+0	5.70E+0	4.80E+0	4.00E+0	3.30E+0	2.60E+0	2.10E+0	1.80E+0
100	8.70E+0	8.40E+0	7.50E+0	6.40E+0	5.50E+0	4.70E+0	3.70E+0	3.20E+0	2.70E+0
200	1.48E+1	1.43E+1	1.29E+1	1.10E+1	9.50E+0	8.10E+0	6.70E+0	6.00E+0	5.00E+0
300	2.06E+1	1.99E+1	1.80E+1	1.52E+1	1.31E+1	1.12E+1	9.40E+0	8.50E+0	7.40E+0
500	3.15E+1	3.05E+1	2.76E+1	2.33E+1	2.01E+1	1.70E+1	1.44E+1	1.32E+1	1.17E+1
700	4.23E+1	4.10E+1	3.70E+1	3.12E+1	2.69E+1	2.27E+1	1.91E+1	1.76E+1	1.58E+1
1000	5.84E+1	5.65E+1	5.11E+1	4.30E+1	3.68E+1	3.08E+1	2.59E+1	2.38E+1	2.18E+1

Be -> Be

Sputtering yield of Be by Be

z1 = 4, m1= 9.01, z2= 4, m2= 9.01, sbe=2.00 eV, rho = 1.85 g/cm**3
 ef=1.98 eV, esb=2.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvln
 ne= 8, na= 5

E ₀ (eV)	20°	35°	45°	60°	75°
20					8.10e-2
50			5.25e-1		2.46e-1
100			9.49e-1		5.30e-1
200	5.38e-1	9.38e-1	1.32e-0		1.20e-0
500	6.28e-1	1.06e-0	1.50e-0		1.85e-0
1000	5.95e-1	9.84e-1	1.40e-0		3.94e-0
2000	5.69e-1		1.23e-0	2.30e-0	
5000			9.30e-1	1.85e-0	3.89e-0

Sputtered energy of Be by Be

ne= 8, na= 5

E ₀ (eV)	20°	35°	45°	60°	75°
20					1.90e-2
50			5.62e-2		4.66e-2
100			6.65e-2		7.48e-2
200	1.23e-2	3.24e-2	5.71e-2		1.12e-1
500	9.13e-3	2.32e-2	3.97e-2		1.38e-1
1000	6.40e-3	1.58e-2	2.69e-2		1.19e-1
2000	4.15e-3		1.71e-2	4.31e-2	
5000			1.05e-2	2.64e-2	6.26e-2

Particle reflection coefficient of Be backscattered from Be

z1 = 4, m1= 9.01, z2= 4, m2= 9.01, sbe=2.00 eV, rho = 1.85 g/cm**3
 ef=1.98 eV, esb=2.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvln
 ne=10, na= 6

Eq (eV)	20°	35°	45°	60°	70°	75°
15				5.67e-2		1.38e-1
20			3.98e-2	1.43e-1		6.58e-1
30				2.90e-1		
50			1.70e-1	3.91e-1		8.70e-1
100			1.36e-1	3.56e-1		8.46e-1
200	1.22e-2	4.50e-2	9.23e-2	2.56e-1	5.16e-1	7.43e-1
500	9.40e-3	2.93e-2	5.46e-2	1.68e-1	3.53e-1	5.29e-1
1000	8.13e-3	2.20e-2	4.52e-2	1.34e-1	2.74e-1	4.03e-1
2000	5.10e-3	1.56e-2	3.10e-2	1.10e-1		
5000			2.29e-2	8.38e-2		2.83e-1

Energy reflection coefficient of Be backscattered from Be

ne=10, na= 6

Eq (eV)	20°	35°	45°	60°	70°	75°
15				1.47e-2		4.68e-2
20			8.19e-3	4.25e-2		3.05e-1
30				9.84e-2		
50			4.25e-2	1.49e-1		5.44e-1
100			3.27e-2	1.39e-1		5.69e-1
200	9.81e-4	6.34e-3	2.05e-2	9.31e-2	2.75e-1	4.93e-1
500	7.60e-4	4.28e-3	1.05e-2	5.20e-2	1.64e-1	3.12e-1
1000	6.91e-4	2.98e-3	8.41e-3	3.88e-2	1.13e-1	2.11e-1
2000	4.40e-4	2.26e-3	5.72e-3	3.15e-2		
5000			4.26e-3	2.27e-2		1.24e-1

Average depth (mean range) in Å of Be implanted in Be

ne=10, na= 8

E ₀ (eV)	20°	35°	45°	60°	70°	75°	80°	85°
15				5.70e-1		3.40e-1	2.90e-1	
20			1.12e+0	7.30e-1		4.05e-1	3.40e-1	3.10e-1
30				1.16e+0		6.40e-1	5.10e-1	4.30e-1
50			2.89e+0	2.14e+0		1.42e+0	1.08e+0	8.80e-1
100			5.32e+0	4.16e+0		3.02e+0	2.53e+0	2.09e+0
200	1.23e+1	1.07e+1	9.55e+0	7.51e+0	6.33e+0	5.67e+0	5.12e+0	4.39e+0
500	2.72e+1	2.38e+1	2.12e+1	1.66e+1	1.39e+1	1.27e+1	1.17e+1	9.81e+0
1000	5.11e+1	4.49e+1	4.00e+1	3.08e+1	2.60e+1	2.37e+1	2.18e+1	1.92e+1
2000	1.01e+2	8.81e+1	7.78e+1	6.09e+1		4.51e+1	4.15e+1	3.77e+1
5000			1.95e+2	1.49e+2	1.08e+2	1.09e+2	9.89e+1	9.00e+1

Be -> Be

Be on Be, Maxwellian velocity distribution, sheath potential 0 kT
 z1= 4, m1= 9.01, z2= 4, m2= 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=3.33 eV, esb=3.38 eV, ca=1.00, kk0=kk0r=2, kdec1=kdec2=3, ipot=ipotrl=1 (KrC)
 program : testvmcx
 ne= 14

kT(eV)	Y	Y _E	E _{sp}	R _N	B _s	E _b	range
2.4	4.40e-4	2.86e-4	3.12e+0	1.69e-3	1.69e-3	4.81e+0	2.40e-1
3	1.13e-3	6.80e-4	3.62e+0	4.20e-3	4.02e-3	5.73e+0	3.36e-1
4	3.24e-3	1.74e-3	4.30e-j-0	1.11e-2	9.65e-3	6.95e-j-0	4.89e-1
5	6.74e-3	3.25e-3	4.82e+0	2.11e-2	1.69e-2	8.04e-j-0	6.41e-1
7	1.79e-2	7.16e-3	5.61e+0	4.36e-2	3.23e-2	1.04e-H	9.20e-1
10	4.10e-2	1.39e-2	6.80e+0	7.92e-2	5.42e-2	1.38e+1	1.34e-f-0
20	1.33e-1	2.97e-2	8.94e+0	1.53e-1	9.01e-2	2.35e+1	2.69e+0
50	3.60e-1	4.57e-2	1.27e+1	1.99e-1	9.82e-2	4.94e-j-1	6.30e+0
100	5.82e-1	4.76e-2	1.64e+1	1.96e-1	8.89e-2	9.11e-H	1.13e+1
200	7.89e-1	4.38e-2	2.21e+1	1.70e-1	7.34e-2	1.72e+2	2.00e+1
500	1.00e-0	3.43e-2	3.41e+1	1.27e-1	4.82e-2	3.79e-j-2	4.40e-j-1
1000	1.05e-0	2.60e-2	4.98e+1	1.07e-1	4.12e-2	7.69e-j-2	8.57e+1
2000	9.84e-1	1.76e-2	7.06e+1	8.87e-2	3.19e-2	1.42e+3	1.66e+2
5000	7.67e-1	8.68e-3	1.14e+2	6.66e-2	2.27e-2	3.43e+3	4.14e+2

Be on Be, Maxwellian velocity distribution, sheath potential 3 kT
 ne=12

kT(eV)	Y	Y _E	E _{sp}	* γ _v	R _N	E _b	range
1.4	1.43e-4	3.82e-5	1.87e+0	1.63e-4	7.18e-5	3.08e-j-0	6.63e-1
2	7.05e-4	1.82e-4	2.58e+0	1.10e-3	4.52e-4	4.12e-f-0	1.03e+0
3	4.10e-3	9.43e-4	3.45e+0	4.89e-3	1.75e-3	5.38e-j-0	1.54e-j-0
5	2.13e-2	3.83e-3	4.50e+0	1.51e-2	4.57e-3	7.59e+0	2.47e+0
10	9.07e-2	1.02e-2	5.64e+0	2.69e-2	6.22e-3	1.16e-j-1	4.43e+0
20	2.02e-1	1.45e-2	7.18e-f-0	2.76e-2	5.13e-3	1.86e+1	7.65e+0
50	3.39e-1	1.45e-2	1.07e+1	2.23e-2	3.43e-3	3.84e+1	1.59e-j-1
100	4.05e-1	1.22e-2	1.50e+1	1.72e-2	2.54e-3	7.37e+1	2.83e+1
200	4.38e-1	9.26e-3	2.12e-f-1	1.32e-2	1.94e-3	1.47e+2	5.27e-j-1
500	4.10e-1	5.46e-3	3.33e+1	8.17e-3	1.19e-3	3.65e+2	1.26e+2
1000	3.29e-1	3.12e-3	4.74e+1	4.71e-3	7.19e-4	7.64e+2	2.52e+2
2000	2.52e-1	1.59e-3	6.32e+1	2.67e-3	4.12e-4	1.54e-f-3	5.14e-j-2

Be on Be, Maxwellian velocity distribution, sheath potential 9 kT
 ne=14

kT(eV)	Y	Y _E	E _{sp}	R _N	B _E	E _b	range
1.4	8.07e-4	1.11e-4	2.12e+0	6.22e-4	1.28e-4	3.18e+0	1.77e+0
1.5	1.15e-3	1.59e-4	2.27e+0	8.40e-4	1.72e-4	3.38e-f-0	1.88e+0
2	4.13e-3	5.16e-4	2.75e-j-0	2.47e-3	4.67e-4	4.16e+0	2.42e+0
3	1.67e-2	1.64e-3	3.25e-f-0	5.86e-3	9.56e-4	5.39e+0	3.41e+0
5	5.34e-2	3.86e-3	3.97e+0	1.01e-2	1.33e-3	7.27e+0	5.14e+0
10	1.36e-1	6.49e-3	5.24e-j-0	1.22e-2	1.31e-3	1.19e+1	8.83e+0
20	2.24e-1	7.71e-3	7.58e+0	1.23e-2	1.16e-3	2.07e+1	1.52e+1
50	3.18e-1	6.61e-3	1.14e+1	8.60e-3	7.35e-4	4.70e+1	3.26e+1
100	3.39e-1	5.06e-3	1.64e+1	6.57e-3	5.88e-4	9.84e+1	6.09e+1
200	3.28e-1	3.50e-3	2.35e+1	4.11e-3	3.91e-4	2.09e+2	1.18e+2
500	2.63e-1	1.78e-3	3.72e-f-1	2.01e-3	2.18e-4	5.97e+2	2.99e+2
1000	2.00e-1	9.36e-4	5.15e+1	6.76e-4	6.79e-5	1.11e-j-3	6.06e+2
2000	1.47e-1	4.98e-4	7.48e+1	6.57e-4	6.40e-5	2.14e-j-3	1.21e+3
5000	9.14e-2	1.67e-4	1.00e+2				2.80e-f-3

N -> Be

Sputtering yield of Be by N

z1= 7, m1 = 14.01, z2= 4, m2= 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.95 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdecl = kdec2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne=16, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10			6.00E-6	4.36E-5	6.72E-5	1.22E-4	1.72E-4	1.65E-4	1.43E-4
12		8.67E-7	3.97E-5	1.75E-4	4.81E-4	9.51E-4	1.04E-3	8.36E-4	6.57E-4
15	1.13E-6	1.16E-5	1.72E-4	1.26E-3	3.59E-3	5.69E-3	4.37E-3	3.01E-3	2.07E-3
20	1.30E-5	1.26E-4	1.42E-3	9.69E-3	2.04E-2	2.37E-2	1.36E-2	8.05E-3	4.73E-3
25	1.32E-4	6.48E-4	5.96E-3	2.95E-2	5.03E-2	5.10E-2	2.53E-2	1.33E-2	6.72E-3
27	2.23E-4	1.08E-3	9.07E-3	4.01E-2	6.49E-2	6.37E-2	3.04E-2	1.55E-2	7.40E-3
30	4.97E-4	2.10E-3	1.51E-2	5.89E-2	8.96E-2	8.43E-2	3.88E-2	1.84E-2	8.20E-3
40	2.72E-3	8.91E-3	4.55E-2	1.36E-1	1.84E-1	1.63E-1	6.78E-2	2.81E-2	9.70E-3
50	7.94E-3	2.07E-2	8.48E-2	2.20E-1	2.86E-1	2.48E-1	9.91E-2	3.73E-2	1.03E-2
70	2.53E-2	5.31E-2	1.66E-1	3.79E-1	4.82E-1	4.24E-1	1.67E-1	5.58E-2	1.06E-2
100	6.02E-2	1.05E-1	2.71E-1	5.69E-1	7.39E-1	6.80E-1	2.82E-1	8.75E-2	1.14E-2
140	1.08E-1	1.69E-1	3.79E-1	7.53E-1	1.00E+0	9.94E-1	4.54E-1	1.38E-1	1.23E-2
200	1.72E-1	2.45E-1	4.86E-1	9.37E-1	1.29E+0	1.40E+0	7.38E-1	2.33E-1	1.53E-2
300	2.47E-1	3.29E-1	5.97E-1	1.12E+0	1.59E+0	1.89E+0	1.23E+0	4.34E-1	2.22E-2
500	3.38E-1	4.27E-1	7.15E-1	1.31E+0	1.90E+0	2.49E+0	2.12E+0	9.55E-1	4.64E-2
1000	4.48E-1	5.36E-1	8.32E-1	1.46E+0	2.18E+0	3.11E+0	3.51E+0	2.38E+0	1.83E-1

Sputtered energy of Be by N

ne=16, na= 9

B ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10			6.00E-6	4.36E-5	6.72E-5	1.22E-4	1.72E-4	1.65E-4	1.43E-4
12		8.67E-7	3.97E-5	1.75E-4	4.81E-4	9.51E-4	1.04E-3	8.36E-4	6.57E-4
15	1.13E-6	1.16E-5	1.72E-4	1.26E-3	3.59E-3	5.69E-3	4.37E-3	3.01E-3	2.07E-3
20	1.30E-5	1.26E-4	1.42E-3	9.69E-3	2.04E-2	2.37E-2	1.36E-2	8.05E-3	4.73E-3
25	1.32E-4	6.48E-4	5.96E-3	2.95E-2	5.03E-2	5.10E-2	2.53E-2	1.33E-2	6.72E-3
27	2.23E-4	1.08E-3	9.07E-3	4.01E-2	6.49E-2	6.37E-2	3.04E-2	1.55E-2	7.40E-3
30	4.97E-4	2.10E-3	1.51E-2	5.89E-2	8.96E-2	8.43E-2	3.88E-2	1.84E-2	8.20E-3
40	2.72E-3	8.91E-3	4.55E-2	1.36E-1	1.84E-1	1.63E-1	6.78E-2	2.81E-2	9.70E-3
50	7.94E-3	2.07E-2	8.48E-2	2.20E-1	2.86E-1	2.48E-1	9.91E-2	3.73E-2	1.03E-2
70	2.53E-2	5.31E-2	1.66E-1	3.79E-1	4.82E-1	4.24E-1	1.67E-1	5.58E-2	1.06E-2
100	6.02E-2	1.05E-1	2.71E-1	5.69E-1	7.39E-1	6.80E-1	2.82E-1	8.75E-2	1.14E-2
140	1.08E-1	1.69E-1	3.79E-1	7.53E-1	1.00E+0	9.94E-1	4.54E-1	1.38E-1	1.23E-2
200	1.72E-1	2.45E-1	4.86E-1	9.37E-1	1.29E+0	1.40E+0	7.38E-1	2.33E-1	1.53E-2
300	2.47E-1	3.29E-1	5.97E-1	1.12E+0	1.59E+0	1.89E+0	1.23E+0	4.34E-1	2.22E-2
500	3.38E-1	4.27E-1	7.15E-1	1.31E+0	1.90E+0	2.49E+0	2.12E+0	9.55E-1	4.64E-2
1000	4.48E-1	5.36E-1	8.32E-1	1.46E+0	2.18E+0	3.11E+0	3.51E+0	2.38E+0	1.83E-1

N -> Be

Particle reflection coefficient of N backscattered from Be
 z1= 7, m1= 14.01, z2= 4, m2= 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2= 3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne=16, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10		2.50E-7	1.77E-4	9.43E-3	5.26E-2	1.64E-1	3.19E-1	3.83E-1	4.23E-1
12		3.87E-6	1.01E-3	2.36E-2	9.69E-2	2.58E-1	4.60E-1	5.38E-1	5.84E-1
15		4.59E-5	3.58E-3	5.11E-2	1.69E-1	3.84E-1	6.26E-1	7.13E-1	7.59E-1
20	8.00E-6	3.66E-4	9.76E-3	9.50E-2	2.63E-1	5.26E-1	7.87E-1	8.67E-1	9.07E-1
25	4.03E-5	8.48E-4	1.56E-2	1.25E-1	3.20E-1	6.00E-1	8.57E-1	9.30E-1	9.62E-1
27	5.88E-5	1.04E-3	1.73E-2	1.33E-1	3.33E-1	6.17E-1	8.74E-1	9.42E-1	9.72E-1
30	9.43E-5	1.28E-3	1.93E-2	1.42E-1	3.48E-1	6.35E-1	8.89E-1	9.55E-1	9.81E-1
40	1.76E-4	1.83E-3	2.28E-2	1.52E-1	3.64E-1	6.57E-1	9.12E-1	9.73E-1	9.93E-1
50	2.22E-4	2.05E-3	2.32E-2	1.48E-1	3.56E-1	6.53E-1	9.18E-1	9.78E-1	9.96E-1
70	2.92E-4	2.13E-3	2.10E-2	1.31E-1	3.24E-1	6.23E-1	9.15E-1	9.82E-1	9.98E-1
100	2.98E-4	2.00E-3	1.81E-2	1.07E-1	2.75E-1	5.67E-1	8.98E-1	9.81E-1	9.99E-1
140	3.75E-4	1.82E-3	1.50E-2	8.61E-2	2.26E-1	4.99E-1	8.67E-1	9.77E-1	9.99E-1
200	3.33E-4	1.52E-3	1.25E-2	6.77E-2	1.80E-1	4.20E-1	8.16E-1	9.66E-1	9.99E-1
300	4.12E-4	1.51E-3	9.97E-3	5.23E-2	1.39E-1	3.37E-1	7.32E-1	9.40E-1	9.99E-1
500	3.35E-4	1.29E-3	7.62E-3	3.89E-2	1.04E-1	2.54E-1	6.01E-1	8.72E-1	9.98E-1
1000	4.00E-4	9.30E-4	5.28E-3	2.71E-2	7.38E-2	1.85E-1	4.43E-1	7.11E-1	9.90E-1

Energy reflection coefficient of N backscattered from Be
 ne=16, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10		1.99E-8	1.71E-5	1.47E-3	1.15E-2	4.78E-2	1.16E-1	1.52E-1	1.76E-1
12		2.77E-7	1.07E-4	3.83E-3	2.17E-2	7.87E-2	1.79E-1	2.29E-1	2.62E-1
15		3.22E-6	4.04E-4	8.78E-3	3.95E-2	1.24E-1	2.65E-1	3.34E-1	3.78E-1
20	2.63E-7	2.63E-5	1.10E-3	1.71E-2	6.54E-2	1.83E-1	3.73E-1	4.62E-1	5.19E-1
25	1.77E-6	6.02E-5	1.74E-3	2.29E-2	8.27E-2	2.21E-1	4.42E-1	5.45E-1	6.11E-1
27	2.53E-6	7.19E-5	1.93E-3	2.45E-2	8.74E-2	2.32E-1	4.62E-1	5.70E-1	6.39E-1
30	4.05E-6	8.60E-5	2.11E-3	2.61E-2	9.27E-2	2.44E-1	4.87E-1	6.01E-1	6.74E-1
40	6.55E-6	1.11E-4	2.38E-3	2.79E-2	9.95E-2	2.65E-1	5.37E-1	6.68E-1	7.52E-1
50	7.43E-6	1.12E-4	2.27E-3	2.66E-2	9.79E-2	2.70E-1	5.62E-1	7.07E-1	7.99E-1
70	7.99E-6	1.00E-4	1.86E-3	2.25E-2	8.80E-2	2.61E-1	5.81E-1	7.48E-1	8.52E-1
100	6.73E-6	7.96E-5	1.42E-3	1.72E-2	7.19E-2	2.36E-1	5.79E-1	7.71E-1	8.91E-1
140	7.97E-6	6.54E-5	1.08E-3	1.27E-2	5.58E-2	2.02E-1	5.58E-1	7.78E-1	9.15E-1
200	5.84E-6	4.99E-5	8.10E-4	9.22E-3	4.13E-2	1.62E-1	5.16E-1	7.70E-1	9.32E-1
300	8.36E-6	5.08E-5	6.00E-4	6.55E-3	2.91E-2	1.19E-1	4.47E-1	7.40E-1	9.42E-1
500	5.38E-6	4.18E-5	4.50E-4	4.47E-3	1.97E-2	8.04E-2	3.40E-1	6.62E-1	9.44E-1
1000	9.43E-6	3.43E-5	3.20E-4	3.03E-3	1.27E-2	5.16E-2	2.18E-1	4.93E-1	9.25E-1

Average depth (mean range) in Å of N implanted in Be
 ne=16, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	9.00E-1	9.00E-1	7.00E-1	5.00E-1	4.00E-1	2.00E-1	1.00E-1	1.00E-1	1.00E-1
12	1.10E+0	1.00E+0	9.00E-1	6.00E-1	4.00E-1	3.00E-1	1.00E-1	1.00E-1	1.00E-1
15	1.40E+0	1.30E+0	1.10E+0	8.00E-1	6.00E-1	3.00E-1	2.00E-1	1.00E-1	1.00E-1
20	1.90E+0	1.80E+0	1.50E+0	1.10E+0	8.00E-1	5.00E-1	3.00E-1	2.00E-1	1.00E-1
25	2.30E+0	2.20E+0	1.80E+0	1.40E+0	1.10E+0	7.00E-1	4.00E-1	3.00E-1	2.00E-1
27	2.40E+0	2.30E+0	2.00E+0	1.50E+0	1.20E+0	8.00E-1	5.00E-1	3.00E-1	2.00E-1
30	2.70E+0	2.50E+0	2.20E+0	1.60E+0	1.30E+0	9.00E-1	6.00E-1	4.00E-1	3.00E-1
40	3.40E+0	3.20E+0	2.80E+0	2.20E+0	1.80E+0	1.30E+0	9.00E-1	6.00E-1	4.00E-1
50	4.10E+0	3.90E+0	3.40E+0	2.70E+0	2.20E+0	1.70E+0	1.20E+0	9.00E-1	6.00E-1
70	5.30E+0	5.00E+0	4.40E+0	3.50E+0	3.00E+0	2.40E+0	1.70E+0	1.30E+0	9.00E-1
100	6.90E+0	6.60E+0	5.80E+0	4.70E+0	4.00E+0	3.20E+0	2.40E+0	1.90E+0	1.30E+0
140	8.40E+0	9.00E+0	7.50E+0	6.10E+0	5.20E+0	4.20E+0	3.30E+0	2.70E+0	1.90E+0
200	1.14E+1	1.09E+1	9.70E+0	8.00E+0	6.70E+0	5.60E+0	4.40E+0	3.70E+0	2.80E+0
300	1.53E+1	1.47E+1	1.31E+1	1.08E+1	9.10E+0	7.60E+0	6.10E+0	5.30E+0	4.20E+0
500	2.25E+1	2.16E+1	1.94E+1	1.60E+1	1.35E+1	1.11E+1	9.10E+0	8.10E+0	6.50E+0
1000	3.89E+1	3.75E+1	3.36E+1	2.77E+1	2.33E+1	1.91E+1	1.54E+1	1.40E+1	1.17E+1

O → Be

Sputtering yield of Be by O

z1 = 8, m1 = 16.00, z2 = 4, m2 = 9.01, sbe=3.38 eV, rho=1.80 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kkO=kkOr=2, kdeel = kdec2=3, ipot=ipotr = 1 (KrC)
 program : trvmc
 only low fluence!
 ne=19, na= 1

E _q (eV)	0°
18	4.89e-6
20	1.36e-5
22	3.03e-5
25	9.18e-5
30	3.71e-4
40	2.16e-3
45	4.03e-3
50	6.41e-3
60	1.34e-2
70	2.22e-2
100	6.06e-2
140	1.02e-1
200	1.65e-1
300	2.35e-1
500	3.50e-1
1000	4.97e-1
2000	5.81e-1
5000	6.10e-1
10000	5.24e-1

Sputtered energy of Be by O
 ne=10, na= 1

E ₀ (eV)	0°
18	1.71e-7
20	4.99e-7
22	1.19e-6
25	3.72e-6
30	1.54e-5
40	8.78e-5
45	1.60e-4
50	2.46e-4
60	4.80e-4
70	7.55e-4

Particle reflection coefficient of O backscattered from Be
 z1 = 8, m1 = 16.00, z2 = 4, m2 = 9.01, sbe=3.38 eV, rho = 1.80 g/cm**3
 ef=0.95 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdec2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 only low fluence!
 ne=10, na= 1

E ₀ (eV)	0°
18	4.20e-8
20	2.24e-7
22	1.12e-6
25	3.40e-6
30	1.05e-5
40	2.57e-5
45	3.85e-5
50	5.60e-5
60	5.80e-5
70	3.00e-5

Energy reflection coefficient of O backscattered from Be
 ne=10, na= 1

E ₀ (eV)	0°
18	1.70e-9
20	8.69e-9
22	4.52e-8
25	1.34e-7
30	3.68e-7
40	9.16e-7
45	1.18e-6
50	1.64e-6
60	1.30e-6
70	1.41e-6

Average depth (mean range) in Å of O implanted in Be
 ne = 10, na= 1

E ₀ (eV)	0°
18	1.62e+0
20	1.80e+0
22	1.97e+0
25	2.22e+0
30	2.60e+0
40	3.32e+0
45	3.65e+0
50	3.96e+0
60	4.57e+0
70	5.13e+0

Ne -> Be

Sputtering yield of Be by Ne

z1=10, m1= 20.18, z2= 4, m2= 9.01, sbe=3.38 eV, rho=1.80 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel=kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc
 ne=26, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10			4.40e-7			9.78e-6	6.67e-6	2.08e-6	
11			3.38e-6	3.66e-5	4.64e-5	4.27e-5	2.45e-5	7.14e-6	1.33e-7
12		5.59e-8	1.18e-5	8.78e-5	1.10e-4	1.26e-4	7.28e-5	2.15e-5	9.00e-7
13	7.45e-9	3.13e-7	2.83e-5	1.62e-4	2.33e-4	3.24e-4	1.81e-4	4.81e-5	4.00e-7
14	3.91e-8	1.07e-6	5.68e-5	2.68e-4	4.62e-4	7.00e-4	3.57e-4	9.21e-5	2.50e-6
15	1.20e-7	2.14e-6	9.76e-5	4.38e-4	8.77e-4	1.36e-3	6.33e-4	1.56e-4	3.52e-6
17	8.18e-7	1.14e-5	2.38e-4	1.07e-3	2.61e-3	3.69e-3	1.47e-3	3.45e-4	9.40e-6
20	5.80e-6	4.91e-5	6.31e-4	3.59e-3	8.54e-3	1.04e-2	3.59e-3	8.33e-4	2.13e-5
22	1.54e-5	1.07e-4	1.14e-3	6.69e-3	1.49e-2	1.67e-2	5.51e-3	1.20e-3	3.43e-5
25	4.73e-5	2.66e-4	2.53e-3	1.41e-2	2.79e-2	2.88e-2	8.96e-3	1.99e-3	5.78e-5
30	1.99e-4	8.77e-4	7.12e-3	3.32e-2	5.81e-2	5.47e-2	1.63e-2	3.52e-3	1.03e-4
35	5.66e-4	2.16e-3	1.47e-2	6.01e-2	9.45e-2	8.59e-2	2.59e-2	5.42e-3	1.61e-4
40	1.28e-3	4.28e-3	2.55e-2	9.16e-2	1.38e-1	1.23e-1	3.64e-2	7.64e-3	2.23e-4
45	2.44e-3	7.47e-3	3.91e-2	1.28e-1	1.81e-1	1.62e-1	4.91e-2	1.00e-2	2.82e-4
50	4.08e-3	1.16e-2	5.44e-2	1.64e-1	2.32e-1	2.03e-1	6.09e-2	1.27e-2	3.49e-4
60	9.11e-3	2.24e-1	8.93e-2	2.44e-1	3.34e-1	2.90e-1	9.01e-2	1.85e-2	4.86e-4
70	1.63e-2	3.61e-2	1.26e-1	3.18e-1	4.35e-1	3.82e-1	1.23e-1	2.53e-2	6.19e-4
80	2.75e-2								
100	4.51e-2	8.23e-2	2.26e-1	5.12e-1	7.02e-1	6.51e-1	2.25e-1	4.84e-2	1.09e-3
150	9.80e-2	1.55e-1	3.57e-1	7.56e-1	1.06e-0	1.07e-0	4.41e-1	1.03e-1	2.13e-3
200	1.50e-1	2.20e-1	4.58e-1	9.36e-1	1.33e-0	1.43e-0	6.80e-1	1.71e-1	3.33e-3
300	2.40e-1	3.27e-1	6.10e-1	1.18e-0	1.71e-0	2.03e-0	1.19e-0	3.50e-1	7.10e-3
500	3.72e-1	4.72e-1	7.98e-1	1.47e-0	2.17e-0	2.83e-0	2.18e-0	8.37e-1	2.11e-2
700	4.58e-1	5.67e-1	9.13e-1	1.64e-0	2.44e-0	3.33e-0	3.04e-0	1.43e-0	4.59e-2
1000	5.44e-1	6.56e-1	1.02e-0	1.80e-0	2.68e-0	3.81e-0	4.00e-0	2.33e-0	1.12e-1
3000	7.00e-1								

Sputtered energy of Be by Ne
 ne=24, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10			1.19e-8			1.10e-6	1.01e-6	3.08e-7	
11			1.27e-7	2.37e-6	4.08e-6	5.07e-6	3.67e-6	1.12e-6	1.96e-8
12		1.52e-9	4.90e-7	6.11e-6	1.05e-5	1.58e-5	1.11e-5	3.49e-6	1.49e-7
13	1.4e-10	8.29e-9	1.26e-6	1.21e-5	2.39e-5	4.26e-5	2.82e-5	7.95e-6	5.45e-8
14	9.3e-10	2.71e-8	2.73e-6	2.11e-5	4.96e-5	9.50e-5	5.78e-5	1.56e-5	4.46e-7
15	2.47e-9	7.18e-8	4.86e-6	3.64e-5	9.81e-5	1.91e-4	1.05e-4	2.73e-5	5.54e-7
17	2.32e-8	3.97e-7	1.30e-5	9.73e-5	3.19e-4	5.61e-4	2.64e-4	6.26e-5	1.46e-6
20	1.78e-7	1.89e-6	3.83e-5	3.67e-4	1.14e-3	1.73e-3	6.77e-4	1.58e-4	3.26e-6
22	4.86e-7	4.33e-6	7.41e-5	7.17e-4	2.08e-3	2.87e-3	1.08e-3	2.35e-4	5.25e-6
25	1.54e-6	1.17e-5	1.75e-4	1.59e-3	4.05e-3	5.11e-3	1.80e-3	3.99e-4	8.90e-6
30	7.04e-6	4.04e-5	5.35e-4	3.91e-3	8.69e-3	1.01e-2	3.37e-3	6.97e-4	1.52e-5
35	2.01e-5	1.04e-4	1.13e-3	7.13e-3	1.43e-2	1.60e-2	5.35e-3	1.06e-3	2.26e-5
40	4.63e-5	2.08e-4	1.96e-3	1.09e-2	2.09e-2	2.28e-2	7.57e-3	1.48e-3	2.96e-5
45	8.74e-5	3.61e-4	2.98e-3	1.51e-2	2.73e-2	3.00e-2	9.96e-3	1.87e-3	3.63e-5
50	1.44e-4	5.52e-4	4.08e-3	1.88e-2	3.43e-2	3.72e-2	1.22e-2	2.35e-3	4.27e-5
60	3.10e-4	1.03e-3	6.37e-3	2.69e-2	4.74e-2	5.10e-2	1.75e-2	3.30e-3	5.48e-5
70	5.29e-4	1.58e-3	8.64e-3	3.35e-2	5.88e-2	6.47e-2	2.30e-2	4.29e-3	6.36e-5
100	1.32e-3	3.17e-3	1.35e-2	4.65e-2	8.23e-2	9.57e-2	3.81e-2	7.22e-3	9.03e-5
150	2.53e-3	5.16e-3	1.78e-2	5.56e-2	9.96e-2	1.28e-1	6.43e-2	1.35e-2	1.34e-4
200	3.47e-3	6.48e-3	1.97e-2	5.86e-2	1.04e-1	1.44e-1	8.68e-2	2.04e-2	1.86e-4
300	4.67e-3	7.95e-3	2.15e-2	5.88e-2	1.05e-1	1.58e-1	1.23e-1	3.66e-2	3.37e-4
500	5.69e-3	8.89e-3	2.18e-2	5.56e-2	9.89e-2	1.60e-1	1.63e-1	7.05e-2	9.18e-4
700	5.96e-3	9.06e-3	2.11e-2	5.23e-2	9.31e-2	1.53e-1	1.82e-1	9.99e-2	1.96e-3
1000	5.97e-3	8.85e-3	2.00e-2	4.86e-2	8.65e-2	1.45e-1	1.90e-1	1.33e-1	4.85e-3

Ar -> Be

Sputtering yield of Be by Ar
 z1=18, m1= 39.95, z2= 4, m2= 9.01, sbe=3.38 eV, rho=1.80 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0-kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program : trvmc
 ne=25, na= 9

Eo(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
13				2.60e-7	8.90e-7	8.35e-7	1.07e-6	4.80e-7	
14				2.39e-6	4.69e-6	4.33e-6	5.37e-6	1.91e-6	
15			7.83e-7	2.25e-5	3.14e-5	2.60e-5	1.66e-5	4.82e-6	
16			3.14e-6	4.89e-5	6.85e-5	6.80e-5	4.39e-5	1.23e-5	
17			8.57e-6	8.55e-5	1.25e-4	1.48e-4	9.74e-5	2.85e-5	
18			1.71e-5	1.36e-4	2.12e-4	2.87e-4	1.93e-4	5.23e-5	1.80e-6
20		1.14e-6	4.85e-5	2.93e-4	5.25e-4	8.85e-4	5.55e-4	1.40e-4	3.98e-6
22		4.14e-6	1.15e-4	5.51e-4	1.23e-3	2.25e-3	1.21e-3	3.03e-4	8.70e-6
25	9.80e-7	1.64e-5	2.73e-4	1.40e-3	3.45e-3	6.31e-3	3.02e-3	6.97e-4	2.05e-5
30	1.18e-5	7.63e-5	8.35e-4	5.09e-3	1.25e-2	1.91e-2	8.09e-3	1.84e-3	5.23e-5
35	5.22e-5	2.46e-4	2.24e-3	1.26e-2	2.91e-2	3.99e-2	1.59e-2	3.50e-3	1.05e-4
40	1.48e-4	6.29e-4	4.94e-3	2.48e-2	5.33e-2	6.71e-2	2.63e-2	5.89e-3	1.76e-4
45	3.43e-4	1.30e-3	8.96e-3	4.12e-2	8.22e-2	1.01e-1	3.83e-2	8.57e-3	2.66e-4
50	6.98e-4	2.36e-3	1.44e-2	6.12e-2	1.18e-1	1.38e-1	5.28e-2	1.18e-2	3.50e-4
60	2.02e-3	5.80e-3	2.99e-2	1.10e-1	1.95e-1	2.25e-1	8.65e-2	1.90e-2	5.71e-4
70	4.36e-3	1.13e-2	4.99e-2	1.64e-1	2.82e-1	3.22e-1	1.24e-1	2.82e-2	8.30e-4
100	1.83e-2	3.79e-2	1.24e-1	3.29e-1	5.44e-1	6.30e-1	2.59e-1	5.83e-2	1.72e-3
150	5.72e-2	9.76e-2	2.45e-1	5.65e-1	9.13e-1	1.12e-0	5.23e-1	1.28e-1	3.62e-3
200	1.01e-1	1.59e-1	3.51e-1	7.56e-1	1.20e-0	1.54e-0	8.81e-1	2.15e-1	6.01e-3
300	1.91e-1	2.69e-1	5.28e-1	1.05e-0	1.64e-0	2.22e-0	1.40e-0	4.23e-1	1.23e-2
500	3.49e-1	4.49e-1	7.86e-1	1.46e-0	2.24e-0	3.21e-0	2.58e-0	9.51e-1	3.31e-2
700	4.71e-1	5.87e-1	9.68e-1	1.74e-0	2.65e-0	3.93e-0	3.65e-0	1.60e-0	6.52e-2
1000	6.07e-1	7.36e-1	1.16e-0	2.03e-0	3.07e-0	4.65e-0	5.01e-0	2.64e-0	1.36e-1
3000	9.00e-1								
5000	1.06e-0								

Sputtered energy of Be by Ar
 ne=23, na= 9

Eo(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
13				9.75e-9	4.49e-8	6.19e-8	9.51e-8	4.58e-8	
14				8.70e-8	2.38e-7	3.27e-7	4.68e-7	1.76e-7	
15			1.72e-8	9.43e-7	1.76e-6	2.05e-6	1.67e-6	5.09e-7	
16			8.72e-8	2.17e-6	4.05e-6	5.52e-6	4.45e-6	1.34e-6	
17			2.28e-7	3.98e-6	7.77e-6	1.24e-5	1.00e-5	3.19e-6	
18			4.90e-7	6.61e-6	1.41e-5	2.48e-5	2.03e-5	5.75e-6	1.56e-7
20		2.53e-8	1.55e-6	1.54e-5	3.70e-5	8.09e-5	6.12e-5	1.61e-5	3.80e-7
22		9.68e-8	3.93e-6	3.07e-5	9.34e-5	2.17e-4	1.39e-4	3.60e-5	8.76e-7
25	1.89e-8	4.14e-7	1.03e-5	8.67e-5	3.03e-4	6.52e-4	3.69e-4	8.62e-5	2.10e-6
30	2.75e-7	2.11e-6	3.58e-5	3.56e-4	1.14e-3	2.12e-3	1.06e-3	2.38e-4	5.40e-6
35	1.23e-6	7.52e-6	1.05e-4	9.40e-4	2.76e-3	4.66e-3	2.13e-3	4.62e-4	1.07e-5
40	3.64e-6	2.02e-5	2.45e-4	1.93e-3	5.18e-3	8.02e-3	3.60e-3	7.69e-4	1.76e-5
45	8.67e-6	4.36e-5	4.61e-4	3.23e-3	8.07e-3	1.22e-2	5.21e-3	1.12e-3	2.58e-5
*50	1.78e-5	7.94e-5	7.52e-4	4.83e-3	1.15e-2	1.67e-2	7.21e-3	1.51e-3	3.31e-5
60	5.17e-5	1.99e-4	1.56e-3	8.63e-3	1.90e-2	2.71e-2	1.17e-2	2.42e-3	5.04e-5
70	1.11e-4	3.83e-4	2.55e-3	1.25e-2	2.69e-2	3.81e-2	1.65e-2	3.47e-3	6.78e-5
100	4.26e-4	1.17e-3	5.80e-3	2.29e-2	4.74e-2	6.89e-2	3.24e-2	6.58e-3	1.15e-4
150	1.19e-3	2.68e-3	1.00e-2	3.38e-2	6.83e-2	1.05e-1	5.84e-2	1.27e-2	1.88e-4
200	1.92e-3	3.91e-3	1.28e-2	3.96e-2	7.79e-2	1.27e-1	8.12e-2	1.96e-2	2.62e-4
300	3.09e-3	5.49e-3	1.59e-2	4.48e-2	8.48e-2	1.46e-1	1.18e-1	3.42e-2	4.24e-4
500	4.48e-3	7.27e-3	1.82e-2	4.71e-2	8.64e-2	1.54e-1	1.67e-1	6.55e-2	9.72e-4
700	5.21e-3	7.94e-3	1.90e-2	4.71e-2	8.50e-2	1.53e-1	1.92e-1	9.60e-2	1.80e-3
1000	5.58e-3	8.31e-3	1.91e-2	4.61e-2	8.24e-2	1.48e-1	2.09e-1	1.31e-1	3.89e-3

D ++ B

D on B. Maxwellian velocity distribution, sheath potential 3 kT
 z1= 1. m1= 2.00. z2= 5. m2= 10.81. sbe=5.73 eV. rho=2.35 g/cm**3 ef=0.98 eV. esb=1.00 eV. ca=1.00. kk0=kk0r=2.
 kdee1 = kdee2=3. ipot=ipotr= 1 (KrC)
 program : testvmcx
 ne=12

kT(eV)	Y	Ye	Esp	R _N	Re	Eb	range
3	6.34e-5	8.86e-6	2.10e+0	4.15e-1	1.82e-1	6.58e+0	4.85e+0
4	3.81e-4	4.76e-5	2.50e4-0	3.78e-1	1.64e-1	8.64e+0	6.02e+0
5	1.21e-3	1.36e-4	2.81e+0	3.51e-1	1.49e-1	1.06e+1	7.14e+0
10	9.12e-3	8.30e-4	4.55e+0	2.82e-1	1.13e-1	2.01e+1	1.23e4-1
20	2.14e-2	1.47e-3	6.86e4-0	2.27e-1	8.70e-2	3.83e+1	2.19e+1
30	2.64e-2	1.58e-3	8.98e4-0	2.05e-1	7.69e-2	5.64e+1	3.14e+1
50	3.10e-2	1.44e-3	1.16e+1	1.74e-1	6.30e-2	9.04eH-1	4.95e+1
100	3.12e-2	9.72e-4	1.56e+1	1.34e-1	4.52e-2	1.69e+2	9.48e+1
200	2.63e-2	5.84e-4	2.22e+1	9.36e-2	2.88e-2	3.08e+2	1.83e+2
500	1.64e-2	1.69e-4	2.57e+1	4.44e-2	1.15e-2	6.50e+2	4.36e+2
1000	1.10e-2	7.26e-5	3.31e+1	2.09e-2	4.67e-3	1.12e+3	8.19e+2
2000	6.35e-3	3.02e-5	4.75e4-1	7.85e-3	1.61e-3	2.05e+3	1.47e+3

B -> B

Sputtering yield of B by B

z1 = 5, m1 = 10.81, z2 = 5, m2 = 10.81, sbe=5.73 eV, rho=2.35 g/cm**3
 ef=5.68, esb=5.73, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl (KrC)
 program: testvmcx, trspvmc, TPP 9/82
 ne= 9, na=13

E ₀ (eV)	0°	15°	20°	30°	40°	45°	50°	60°	65°	70°	75°	80°	85°
50	2.56e-3												
70	7.84e-3												
100	2.10e-2												
200	7.44e-2												
500	1.52e-1												
1000	2.12e-1	2.80e-1		4.56e-1		8.27e-1		1.50e-0	1.79e-0	2.04e-0	2.09e-0	1.55e-0	3.41e-1
2000	2.50e-1		3.44e-1		6.75e-1		1.02e-0	1.54e-0		2.29e-0		2.51e-0	8.19e-1
5000	2.13e-1												
10000	2.10e-1												

Sputtered energy of B by B

program: testvmcx, trspvmc
 ne= 9, na=13

E ₀ (eV)	0°	15°	20°	30°	40°	45°	50°	60°	65°	70°	75°	80°	85°
50	1.29e-4												
70	3.74e-4												
100	8.40e-4												
200	2.40e-3												
500	3.39e-3												
1000	3.51e-3	5.56e-3		1.28e-2		3.14e-2		7.18e-2	9.02e-2	1.11e-1	1.26e-1	1.09e-1	2.95e-2
2000	2.82e-3		5.23e-3		1.70e-2		3.04e-2	5.34e-2		8.90e-2		1.11e-1	4.47e-2
5000	1.53e-3												
10000	9.83e-4												

Particle reflection coefficient of B backscattered from B

z1 = 5, m1 = 10.81, z2 = 5, m2 = 10.81, sbe=5.73 eV, rho=2.35 g/cm**3
 ef=5.68, esb=5.73, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl (KrC)
 program: testvmcx, trspvmc
 ne= 9, na=13

E ₀ (eV)	0°	15°	20°	30°	40°	45°	50°	60°	65°	70°	75°	80°	85°
50	4.45e-4												
70	8.65e-4												
100	1.88e-3												
200	3.90e-3												
500	5.17e-3												
1000	4.45e-3	7.30e-3		2.41e-2		5.72e-2		1.59e-1	2.20e-1	3.17e-1	4.54e-1	6.82e-1	9.51e-1
2000	2.85e-3		6.20e-3		3.03e-2		6.48e-2	1.29e-1		2.64e-1		5.57e-1	8.93e-1
5000	2.00e-3												
10000	7.00e-4												

Energy reflection coefficient of B backscattered from B

ne= 9, na=13

E ₀ (eV)	0°	15°	20°	30°	40°	45°	50°	60°	65°	70°	75°	80°	85°
50	3.05e-5												
70	5.38e-5												
100	1.23e-4												
200	1.98e-4												
500	2.55e-4												
1000	2.60e-4	5.38e-4		2.61e-3		1.04e-2		4.49e-2	7.82e-2	1.34e-1	2.43e-1	4.82e-1	8.52e-1
2000	1.57e-4		5.40e-4		4.16e-3		1.29e-2	3.52e-2		1.06e-1		3.56e-1	7.85e-1
5000	1.07e-4												
10000	5.68e-5												

Average depth (mean range) in Å of B implanted in B

ne= 9, na=13

E ₀ (eV)	0°	15°	20°	30°	40°	45°	50°	60°	65°	70°	75°	80°	85°
50	3.67e+0												
70	4.77e+0												
100	6.25e+0												
200	1.05e+1												
500	2.33e+1												
1000	4.13e+1	3.76e+1		3.38e+1		2.88e+1		2.29e+1	2.09e+1	1.92e+1	1.76e+1	1.62e+1	1.44e+1
2000	7.26e+1		6.84e+1		5.69e+1		4.97e+1	4.21e+1		3.54e+1		2.87e+1	2.76e+1
5000	1.76e+2												
10000	3.56e+2												

B B

B on B, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 5, m1 = 10.81, z2 = 5, m2 = 10.81, sbe=5.73 eV, rho=2.35 g/cm**3
 ef=5.68 eV, esb=5.73 eV, ca=1.00, kk0=kk0r=2, kdeel=kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=12

kT(eV)	Y	Y _{JS}	E _{sp}	R _A r	R _e	E _{fc}	range
4	4.51e-4	2.92e-4	5.18e+0	1.58e-3	1.61e-3	8.15e+0	3.29e-1
5	1.12e-3	6.88e-4	6.11e+0	3.89e-3	3.67e-3	9.41e+0	4.34e-1
7	4.07e-3	2.16e-3	7.31e+0	1.19e-2	1.04e-2	1.22e+1	6.35e-1
10	1.18e-2	5.21e-3	8.87e+0	2.93e-2	2.30e-2	1.57e+1	9.17e-1
20	5.67e-2	1.74e-2	1.23e+1	9.08e-2	5.91e-2	2.60e+1	1.80e+0
50	2.12e-1	3.70e-2	1.74e+1	1.70e-1	9.17e-2	5.38e+1	4.27e+0
100	3.90e-1	4.50e-2	2.31e+1	1.87e-1	8.90e-2	9.57e+1	7.76e+0
200	6.02e-1	4.67e-2	3.10e+1	1.75e-1	7.72e-2	1.76e+2	1.37e+1
500	8.52e-1	3.84e-2	4.55e+1	1.42e-1	5.74e-2	4.09e+2	2.98e+1
1000	9.66e-1	3.25e-2	6.66e+1	1.15e-1	4.44e-2	7.64e+2	5.45e+1
2000	9.76e-1	2.35e-2	9.68e+1	1.03e-1	3.80e-2	1.48e+3	1.06e+2
5000	8.49e-1	1.30e-2	1.52e+2	7.89e-2	2.69e-2	3.40e+3	2.55e+2

B on B, Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 5, m1 = 10.81, z2 = 5, m2 = 10.81, sbe=5.73 eV, rho=2.35 g/cm**3
 ef=5.68 eV, esb=5.73 eV, ca=1.00, kk0=kk0r=2, kdeel=kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=10

kT(eV)	Y	Y _b	E _{sp}	R/v	R _b	E _g	range
3	4.69e-4	1.32e-4	4.21e+0	6.34e-4	2.63e-4	6.22e+0	1.07e+0
5	3.97e-3	9.51e-4	5.99e+0	4.59e-3	1.60e-3	8.69e+0	1.74e+0
10	2.99e-2	4.70e-3	7.85e+0	1.71e-2	4.81e-3	1.41e+1	3.17e+0
20	1.03e-1	1.04e-2	1.01e+1	2.50e-2	5.30e-3	2.12e+1	5.51e+0
50	2.38e-1	1.35e-2	1.42e+1	2.24e-2	3.72e-3	4.16e+1	1.13e+1
100	3.30e-1	1.32e-2	2.00e+1	2.30e-2	3.47e-3	7.52e+1	1.96e+1
200	3.81e-1	1.07e-2	2.81e+1	1.29e-2	1.97e-3	1.52e+2	3.50e+1
500	4.03e-1	7.22e-3	4.48e+1	1.11e-2	1.60e-3	3.60e+2	8.04e+1
1000	3.55e-1	4.50e-3	6.32e+1	7.18e-3	9.66e-4	6.73e+2	1.58e+2
2000	2.88e-1	2.58e-3	8.98e+1	3.99e-3	5.72e-4	1.44e+3	3.17e+2

B on B, Maxwellian velocity distribution, sheath potential 9 kT
 z1 = 5, m1 = 10.81, z2 = 5, m2 = 10.81, sbe=5.73 eV, rho=2.35 g/cm**3
 ef=5.68 eV, esb=5.73 eV, ca=1.00, kk0=kk0r=2, kdeel=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=11

kT(eV)	Y	Y _m	E _{sp}	R ₇₇	R _e	E _{fc}	range
2	2.89e-4	4.40e-5	3.35e+0	2.33e-4	5.28e-5	4.99e+0	1.75e+0
5	1.36e-2	1.37e-3	5.54e+0	4.57e-3	7.31e-4	8.80e+0	3.74e+0
10	5.97e-2	3.95e-3	7.28e+0	9.30e-3	1.20e-3	1.42e+1	6.39e+0
20	1.33e-1	6.10e-3	1.01e+1	1.16e-2	1.16e-3	2.21e+1	1.09e+1
50	2.34e-1	6.89e-3	1.62e+1	9.38e-3	8.83e-4	5.18e+1	2.25e+1
100	2.85e-1	6.06e-3	2.34e+1	7.68e-3	6.51e-4	9.33e+1	4.04e+1
200	2.99e-1	4.34e-3	3.19e+1	5.60e-3	5.22e-4	2.05e+2	7.59e+1
500	3.06e-1	5.15e-3	3.71e+1	7.50e-3	8.96e-4	2.64e+2	7.58e+1
1000	2.33e-1	1.50e-3	7.07e+1	8.38e-4	1.03e-4	1.35e+3	3.73e+2
2000	1.78e-1	8.35e-4	1.03e+2	5.54e-4	2.77e-5	1.10e+3	7.52e+2
5000	1.13e-1	3.04e-4	1.48e+2				1.80e+3

O → B

Sputtering yield of B by O
 z1 = 8, m1 = 16.00, z2 = 5, m2 = 10.81, sbe=5.90 eV, rho=2.35 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdeel=kdee2=3, ipot=ipotr=1 (KrC)
 program: IPP 9/82
 only low fluence!
 ne = 5, na=1

E ₀ (eV)	0 ^o
150	3.75e-2
300	1.14e-1
1000	2.77e-1
3000	3.87e-1
6000	4.16e-1

H → C

Sputtering yield of C by H

z1 = 1, m1 = 1.00, z2 = 6, m2 = 12.01, sbe = 7.41 eV, rho = 2.20 g/cm**3
 ef = 1.80 eV, esb = 2.26 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 alpha = 0.00
 program : trspvnc
 ne = 5, na = 1, n(dx) = 8

E ₀ (eV)	dx = 10 Å	50 A	100 A	300 A	500 A	1000 A	2000 A	5000 A
1000	1.45e-3	3.12e-3	5.49e-3	5.31e-3	5.34e-3	6.50e-3		6.50e-3
5000	1.65e-3	2.16e-3	1.80e-3		2.66e-3	2.19e-3	2.55e-3	
10000	1.20e-3	1.51e-3	1.33e-3		1.61e-3	1.72e-3		
20000	8.75e-4	8.44e-4	1.16e-3		1.16e-3	1.38e-3		
40000	5.17e-4	6.99e-4	5.91e-4					

Sputtered energy of C by H

ne = 5, na = 1, n(dx) = 8

E ₀ (eV)	dx=10 Å	50 A	100 Å	300 Å	500 Å	1000 Å	2000 A	5000 Å
1000	1.87e-5	5.34e-5	1.11e-4	8.97e-5	1.09e-4	1.18e-4		1.18e-4
5000	6.15e-6	8.11e-6	5.89e-6		1.01e-5	1.07e-5	1.18e-5	
10000	3.22e-6	3.30e-6	4.36e-6		6.17e-6	4.24e-6		
20000	1.34e-6	1.14e-6	1.46e-6		1.80e-6	2.84e-6		
40000	4.71e-7	7.37e-7	5.02e-7					

Particle reflection coefficient of H backscattered from C

ne = 5, na = 1, n(dx) = 8

E ₀ (eV)	dx=10 Å	50 A	100 A	300 A	500 A	1000 A	2000 A	5000 A
1000	4.21e-3	3.31e-2	7.32e-2	1.03e-1	1.01e-1	9.80e-2		9.80e-2
5000	2.64e-4	1.24e-3	3.05e-3		1.66e-2	1.74e-2	1.66e-2	
10000	5.96e-5	3.68e-4	6.52e-4		4.99e-3	6.33e-3		
20000	1.67e-5	9.27e-5	1.48e-4		1.09e-3	2.28e-3		
40000	4.38e-6	1.50e-5	4.85e-5					

Energy reflection coefficient of H backscattered from C

ne = 5, na = 1, n(dx) = 8

E ₀ (eV)	dx=10 A	50 A	100 A	300 A	500 A	1000 A	2000 A	5000 A
1000	3.05e-3	1.70e-2	2.72e-2	3.33e-2	3.27e-2	3.20e-2		3.20e-2
5000	2.02e-4	7.71e-4	1.67e-3		4.10e-3	4.47e-3	4.24e-3	
10000	4.55e-5	2.51e-4	3.75e-4		1.44e-3	1.58e-3		
20000	1.32e-5	6.74e-5	9.98e-5		3.89e-4	5.85e-4		
40000	3.48e-6	1.14e-5	2.84e-5					

Average depth (mean range) in Å of H implanted in C

ne = 4, na = 1, n(dx) = 7

E ₀ (eV)	dx = 50 A	100 A	300 A	500 A	1000 A	2000 A	5000 A
1000	6.88e+0	4.49e+1	1.68e+2	1.98e+2	1.96e+2		1.96e-f-2
5000		6.85e-1		2.62e+2	6.99e-)-2	7.99e-f-2	
10000				1.93e+2	6.24e+2		
20000				4.54e+1	4.27e+2		

H → C

Transmission sputtering yield of C by H

z1 = 1, m1 = 1.00, z2 = 6, m2 = 12.01, sbe = 7.41 eV, rho = 2.20 g/cm**3
 ef = 1.80 eV, esb = 2.26 eV, ca = 1.00, kko = kkor = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 alpha = 0.00
 program : trspvmc
 ne = 5, na = 1, n(dx) = 6

EO(eV)	dx=10 Å	50 A	100 Å	300 A	500 A	1000 A
1000	2.20e-2	2.99e-2	3.38e-2	6.03e-3	3.38e-2	
5000	6.40e-3	1.02e-2	1.20e-2		1.94e-2	1.19e-2
10000	3.39e-3	5.46e-3	6.55e-3		9.93e-3	1.64e-2
20000	1.78e-3	2.71e-3	3.35e-3		4.20e-3	7.07e-3
40000	8.79e-4	1.36e-3	1.71e-3			

Transmission sputtered energy of C by H

ne = 5, na = 1, n(dx) = 6

Bo (eV)	dx=10 A	50 A	100 A	300 A	500 A	1000 A
1000	1.07e-3	1.22e-3	1.18e-3	9.09e-5	1.18e-3	
5000	1.37e-4	2.16e-4	2.66e-4		2.47e-4	5.16e-5
10000	4.83e-5	1.02e-4	9.98e-5		1.47e-4	1.23e-4
20000	1.53e-5	3.49e-5	4.81e-5		6.22e-5	6.25e-5
40000	4.76e-6	1.07e-5	2.23e-5			

Particle transmission coefficient of H transmitted through C

ne = 5, na = 1, n(dx) = 6

EO(eV)	dx = 10 A	50 A	100 A	300 A	500 A	1000 A
1000	9.95e-1	9.64e-1	8.91e-1	1.65e-1	5.04e-5	
5000	9.99e-1	9.98e-1	9.96e-1		9.27e-1	2.70e-1
10000	1.00e-0	9.99e-1	9.99e-1		9.91e-1	9.29e-1
20000	1.00e-0	1.00e-0	9.99e-1		9.98e-1	9.93e-1
40000	1.00e-0	1.00e-0	1.00e-0			

Energy transmission coefficient of H transmitted through C

ne = 5, na = 1, n(dx) = 6

Eo (eV)	dx = 10 A	50 A	100 A	300 A	500 A	1000 A
1000	9.66e-1	8.14e-1	6.01e-1	3.05e-2	1.93e-6	
5000	9.88e-1	9.40e-1	8.81e-1		4.23e-1	2.60e-2
10000	9.92e-1	9.59e-1	9.19e-1		6.20e-1	2.92e-1
20000	9.94e-1	9.72e-1	9.44e-1		7.33e-1	5.01e-1
40000	9.96e-1	9.80e-1	9.60e-1			

D → C

Sputtering yield of C by D

z1 = 1, m1 = 2.01, z2 = 6, m2 = 12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot=1 (KrC) program : trvmc
 ne=12, na= 9

E _a (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
30	8.58E-5	1.12E-4	1.78E-4	2.30E-4	2.08E-4	1.12E-4	2.55E-5	8.60E-6	2.56E-6
33	2.16E-4					3.29E-4			
40	7.35E-4	9.15E-4	1.26E-3	1.72E-3	2.21E-3	1.80E-3	7.60E-4	3.12E-4	9.35E-5
50	1.96E-3	2.33E-3	3.09E-3	4.58E-3	5.87E-3	5.95E-3	4.15E-3	1.76E-3	4.45E-4
70	4.79E-3	5.19E-3	7.01E-3	1.13E-2	1.57E-2	2.14E-2	1.78E-2	8.60E-3	1.57E-3
100	8.18E-3	8.77E-3	1.21E-2	1.96E-2	3.08E-2	4.59E-2	4.78E-2	2.72E-2	4.04E-3
140	1.10E-2	1.21E-2	1.68E-2	2.88E-2	4.40E-2	7.03E-2	8.63E-2	5.73E-2	8.17E-3
200	1.32E-2	1.48E-2	2.41E-2	3.56E-2	5.93E-2	9.10E-2	1.21E-1	9.76E-2	1.41E-2
300	1.47E-2	1.66E-2	2.40E-2	4.33E-2	6.81E-2	1.13E-1	1.63E-1	1.51E-1	2.94E-2
500	1.44E-2	1.72E-2	2.72E-2	4.58E-2	7.39E-2	1.20E-1	1.89E-1	2.12E-1	7.29E-2
1000	1.30E-2	1.49E-2	2.36E-2	4.18E-2	6.49E-2	1.08E-1	1.90E-1	2.35E-1	1.72E-1
2000	1.02E-2			3.45E-2			1.88E-1	2.22E-1	2.45E-1

Sputtered energy of C by D

ne=12, na= 9

E _a (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
30	3.32E-6	4.76E-6	8.71E-6	1.27E-5	1.21E-5	6.80E-6	1.71E-6	6.29E-7	2.24E-7
33	9.15E-6					2.31E-5			
40	3.58E-5	5.17E-5	8.06E-5	1.26E-4	1.81E-4	1.54E-4	6.87E-5	2.90E-5	8.69E-6
50	1.18E-4	1.50E-4	2.19E-4	3.60E-4	5.08E-4	5.70E-4	4.41E-4	1.95E-4	5.31E-5
70	3.26E-4	3.50E-4	5.33E-4	9.23E-4	1.38E-3	2.05E-3	2.04E-3	1.10E-3	2.26E-4
100	5.27E-4	5.96E-4	8.80E-4	1.50E-3	2.56E-3	4.29E-3	5.49E-3	3.55E-3	5.71E-4
140	6.77E-4	7.50E-4	1.09E-3	2.03E-3	3.31E-3	5.93E-3	8.75E-3	6.73E-3	1.14E-3
200	7.12E-4	8.00E-4	1.18E-3	2.19E-3	3.99E-3	6.60E-3	1.04E-2	9.95E-3	1.73E-3
300	6.56E-4	7.50E-4	1.12E-3	2.23E-3	3.84E-3	7.15E-3	1.15E-2	1.19E-2	3.08E-3
500	5.02E-4	5.80E-4	1.03E-3	1.87E-3	3.19E-3	5.90E-3	1.01E-2	1.26E-2	5.40E-3
1000	2.94E-4	3.70E-4	5.70E-4	1.17E-3	2.01E-3	3.61E-3	6.82E-3	9.28E-3	7.69E-3
2000	1.39E-4			6.56E-4			4.66E-3	5.72E-3	6.93E-3

D → C

Particle reflection coefficient of D backscattered from C

z1 = 1, m1= 2.01, z2= 6, m2 = 12.01, sbe = 7.41 eV, rho = 1.85 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trvmc
 ne = 14, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	3.74E-1	3.99E-1	4.70E-1	6.00E-1	7.09E-1	8.29E-1	9.23E-1	9.51E-1	9.66E-1
20	3.13E-1	3.32E-1	3.92E-1	5.10E-1	6.29E-1	7.79E-1	9.21E-1	9.64E-1	9.84E-1
30	2.81E-1	2.99E-1	3.52E-1	4.57E-1	5.70E-1	7.27E-1	9.03E-1	9.63E-1	9.89E-1
33	2.75E-1					7.13E-1			
40	2.62E-1	2.77E-1	3.28E-1	4.23E-1	5.29E-1	6.83E-1	8.82E-1	9.59E-1	9.91E-1
50	2.48E-1	2.62E-1	3.09E-1	4.01E-1	4.99E-1	6.49E-1	8.60E-1	9.52E-1	9.92E-1
70	2.27E-1	2.41E-1	2.86E-1	3.71E-1	4.59E-1	5.99E-1	8.20E-1	9.37E-1	9.92E-1
100	2.07E-1	2.19E-1	2.62E-1	3.39E-1	4.26E-1	5.48E-1	7.65E-1	9.10E-1	9.91E-1
140	1.88E-1	2.00E-1	2.41E-1	3.17E-1	3.97E-1	5.11E-1	7.10E-1	8.69E-1	9.90E-1
200	1.69E-1	1.80E-1	2.19E-1	2.96E-1	3.66E-1	4.75E-1	6.56E-1	8.24E-1	9.84E-1
300	1.48E-1	1.57E-1	1.95E-1	2.64E-1	3.40E-1	4.38E-1	6.04E-1	7.53E-1	9.71E-1
500	1.20E-1	1.28E-1	1.63E-1	2.27E-1	3.01E-1	3.98E-1	5.48E-1	6.79E-1	9.32E-1
1000	8.00E-2	8.85E-2	1.20E-1	1.82E-1	2.51E-1	3.52E-1	4.96E-1	6.03E-1	8.31E-1
2000	4.53E-2			1.31E-1			4.19E-1	5.59E-1	7.53E-1

Energy reflection coefficient of D backscattered from C
 ne = 14, na = 9

B _q (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	1.47E-1	1.64E-1	2.18E-1	3.29E-1	4.39E-1	5.76E-1	7.11E-1	7.60E-1	7.89E-1
20	1.21E-1	1.34E-1	1.76E-1	2.73E-1	3.89E-1	5.59E-1	7.58E-1	8.34E-1	8.78E-1
30	1.06E-1	1.17E-1	1.53E-1	2.35E-1	3.40E-1	5.13E-1	7.51E-1	8.53E-1	9.08E-1
33	1.03E-1					5.00E-1			
40	9.73E-2	1.07E-1	1.39E-1	2.11E-1	3.06E-1	4.72E-1	7.32E-1	8.56E-1	9.23E-1
50	9.10E-2	9.92E-2	1.29E-1	1.96E-1	2.81E-1	4.38E-1	7.09E-1	8.53E-1	9.32E-1
70	8.20E-2	8.97E-2	1.17E-1	1.76E-1	2.49E-1	3.89E-1	6.62E-1	8.38E-1	9.41E-1
100	7.33E-2	8.02E-2	1.04E-1	1.56E-1	2.22E-1	3.40E-1	5.99E-1	8.06E-1	9.46E-1
140	6.55E-2	7.18E-2	9.43E-2	1.43E-1	2.01E-1	3.04E-1	5.35E-1	7.54E-1	9.47E-1
200	5.73E-2	6.34E-2	8.42E-2	1.30E-1	1.81E-1	2.74E-1	4.75E-1	6.93E-1	9.41E-1
300	4.95E-2	5.36E-2	7.22E-2	1.13E-1	1.63E-1	2.43E-1	4.15E-1	6.05E-1	9.22E-1
500	3.83E-2	4.22E-2	5.79E-2	9.24E-2	1.37E-1	2.10E-1	3.54E-1	5.10E-1	8.67E-1
1000	2.37E-2	2.70E-2	3.95E-2	6.77E-2	1.06E-1	1.71E-1	2.96E-1	4.18E-1	7.23E-1
2000	1.22E-2			4.29E-2			2.26E-1	3.53E-1	6.08E-1

Average depth (mean range) in Å of D implanted in C
 ne = 13, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	5.20E+0	5.20E+0	5.00E+0	4.80E+0	4.60E+0	4.40E+0	4.20E+0	4.10E+0	4.00E+0
20	8.60E+0	8.50E+0	8.20E+0	7.90E+0	7.60E+0	7.30E+0	6.90E+0	6.70E+0	6.60E+0
33	1.25E+1					1.03E+1			
40	1.45E+1	1.43E+1	1.38E+1	1.30E+1	1.25E+1	1.19E+1	1.14E+1	1.10E+1	1.07E+1
50	1.72E+1	1.70E+1	1.64E+1	1.54E+1	1.48E+1	1.41E+1	1.34E+1	1.30E+1	1.27E+1
70	2.26E+1	2.22E+1	2.14E+1	2.01E+1	1.90E+1	1.82E+1	1.73E+1	1.69E+1	1.63E+1
100	3.02E+1	2.97E+1	2.84E+1	2.67E+1	2.53E+1	2.39E+1	2.30E+1	2.24E+1	2.16E+1
140	4.01E+1	3.95E+1	3.77E+1	3.52E+1	3.33E+1	3.16E+1	3.01E+1	2.96E+1	2.88E+1
200	5.48E+1	5.39E+1	5.13E+1	4.76E+1	4.49E+1	4.26E+1	4.04E+1	3.94E+1	3.87E+1
300	7.88E+1	7.74E+1	7.36E+1	6.79E+1	6.38E+1	5.95E+1	5.65E+1	5.55E+1	5.47E+1
500	1.26E+2	1.24E+2	1.16E+2	1.07E+2	1.00E+2	9.34E+1	8.72E+1	8.55E+1	8.28E+1
1000	2.45E+2	2.39E+2	2.24E+2	2.02E+2	1.86E+2	1.70E+2	1.57E+2	1.52E+2	1.51E+2
2000	3.91E+2			3.11E+2			2.13E+2	2.20E+2	2.14E+2

D → C

D on C. Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1, m1 = 2.01, z2=6, m2= 12.01, sbe=7.42 eV, rho=2.26 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 10

kT(eV)	Y	Y _e	E _{sp}	R _{Nr}	R _e	B _{fe}	range
8	2.22e-4	5.85e-5	4.23e+0	5.92e-1	3.53e-1	9.53e4-0	5.31e4-0
10	5.87e-4	1.45e-4	4.95e+0	5.82e-1	3.41e-1	1.17e+0	6.45e+0
14	1.81e-3	3.82e-4	5.90e+0	5.61e-1	3.19e-1	1.60e+1	8.52e+0
20	4.43e-3	8.30e-4	7.48e-f-0	5.31e-1	2.94e-1	2.21e+1	1.12e+1
30	1.07e-2	1.66e-3	9.28e+0	4.93e-1	2.63e-1	3.21e+1	1.56e+1
50	2.18e-2	2.68e-3	1.23e+1	4.44e-1	2.28e-1	5.14e4-1	2.34e+1
100	3.99e-2	3.04e-3	1.52e+1	3.81e-1	1.85e-1	9.72e+1	4.15e+1
200	5.32e-2	2.88e-3	2.16e+1	3.23e-1	1.48e-1	1.82e+2	7.62e4-1
500	5.86e-2	1.79e-3	3.07e+1	2.52e-1	1.04e-1	4.14e4-2	1.73e+2
1000	5.40e-2	1.05e-3	3.92e+1	2.02e-1	7.32e-2	7.30e+2	3.22e+2

D on C. Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1, m1 = 2.01, z2=6, m2= 12.01, sbe=7.42 eV, rho=2.26 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr=1(KrC)
 program: testvmcx
 ne= 16

kT(eV)	Y	Y _e	E _{sp}	R _N	R _e	E _h	range
5	2.27e-4	2.70e-5	2.97e-0	3.72e-1	1.64e-1	1.10e+1	7.91e+0
5	2.36e-4	2.79e-5	2.96e-0	3.71e-1	1.64e-1	1.10e+1	7.92e+0
7	1.17e-3	1.19e-4	3.56e-0	3.37e-1	1.45e-1	1.51e+1	1.09e+1
10	3.67e-3	3.61e-4	4.91e-0	3.06e-1	1.28e-1	2.10e+1	1.34e+1
10	3.72e-3	3.47e-4	4.66e-0	3.05e-1	1.28e-1	2.09e- -1	1.34e-f-1
14	7.36e-3	6.46e-4	6.15e-0	2.78e-1	1.14e-1	2.87e- -1	1.75e- -1
20	1.19e-2	8.93e-4	7.50e-0	2.54e-1	1.01e-1	4.00e- -1	2.35e+1
20	1.25e-2	9.47e-4	7.59e-0	2.54e-1	1.02e-1	4.00e+1	2.35e-H
30	1.70e-2	1.11e-3	9.66e-0	2.26e-1	8.80e-2	5.83e- -1	3.30e+1
40	2.15e-2	1.27e-3	1.18e+1	2.08e-1	7.97e-2	7.65e+1	4.25e+1
50	1.99e-2	1.01e-3	1.27e+1	1.95e-1	7.74e-2	9.43e+1	5.16e+1
50	2.23e-2	1.18e-3	1.32e+1	1.95e-1	7.32e-2	9.41e+1	5.19e+1
100	2.35e-2	8.68e-4	1.85e+1	1.56e-1	5.53e-2	1.78e+2	9.78e- -1
200	2.17e-2	4.91e-4	2.27e- -1	1.12e-1	3.65e-2	3.26e4-2	1.87e+2
500	1.48e-2	2.10e-4	3.54e+1	5.76e-2	1.55e-2	6.73e+2	4.42e-f-2
1000	9.49e-3	7.33e-5	3.86e+1	2.81e-2	6.54e-3	1.17e+3	8.31e4-2

D on C. Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1, m1= 2.01, z2=6, m2= 12.01, sbe=4-4 rho=1.85 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr = 1(KrC)
 program: trspvmc
 ne=12

kT(eV)	Y	Y _e	E _{sp}	R ₇₇	R _e	E _h	range
2	1.77e-5		1.20e+0	4.46e-1		4.56e4-0	4.37e+0
3	3.38e-4		1.71e-f-0	4.01e-1		6.77e+0	5.96e- -0
4	1.33e-3		2.16e- -0	3.69e-1		8.88e- -0	7.42e+0
5	2.95e-3		2.55e- -0	3.46e-1		1.09e+1	8.81e+0
7	7.69e-3		3.26e+0	3.15e-1		1.50e-f-1	1.15e- -1
10	1.48e-2		4.15e+0	2.87e-1		2.06e-f-1	1.53e-t-1
14	2.26e-2		5.13e- -0	2.64e-1		2.87e+1	2.02e+1
20	2.98e-2		6.30e+0	2.42e-1		4.02e+1	2.73e+1
50	4.03e-2		1.00e+1	1.89e-1		9.49e+1	6.15e-f-1
100	3.96e-2		1.36e- -1	1.49e-1		1.79e+2	1.17e- -2
200	3.30e-2		1.77e+1	1.09e-1		3.27e- -2	2.25e+2
500	2.20e-2		2.44e-f-1	5.66e-2		6.83e- -2	5.34e+2

D on C. Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1, m1= 2.01, z2=6, m2= 12.01, sbe=7.40, rho=2.00 g/cm**3
 ef=0.95 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr = 1(KrC)
 program: testvmcx
 ne= 2

kT(eV)	Y	Y _e	E _{sp}	R ₇₇	R _e	E _h	range
1000	8.85e-3	7.47e-5	4.22e-H	2.80e-2	6.63e-3	1.19e4-3	9.32e+2
2000	5.54e-3	3.08e-5	5.57e+1	1.12e-2	2.34e-3	2.08e+3	1.69e+3

T → C

Sputtering yield of C by T

z1 = 1, m1 = 2.01, z2 = 6, m2 = 12.01, sbe = 7.41 eV, rho = 1.85 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdeel = kdec2 = 3, ipot = ipotr = 1 (KrC)
 program : trvmc
 ne = 12, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
20			6.00E-6	7.80E-6					
25	4.70E-5	7.40E-5	1.43E-4	2.15E-4	1.82E-4	1.25E-4	4.14E-5	1.80E-5	7.00E-6
30	2.44E-4	3.25E-4	6.09E-4	9.78E-4	1.06E-3	9.45E-4	4.38E-4	2.30E-4	9.49E-5
40	1.23E-3	1.50E-3	2.56E-3	4.41E-3	6.15E-3	6.65E-3	4.37E-3	2.14E-3	6.37E-4
50	2.76E-3	3.50E-3	5.36E-3	9.16E-3	1.36E-2	1.77E-2	1.32E-2	6.16E-3	1.48E-3
70	6.05E-3	6.87E-3	1.03E-2	1.97E-2	3.02E-2	4.49E-2	3.92E-2	1.98E-2	3.57E-3
100	9.44E-3	1.14E-2	1.71E-2	3.20E-2	5.24E-2	7.87E-2	8.63E-2	4.77E-2	6.94E-3
140	1.28E-2	1.39E-2	2.25E-2	4.44E-2	6.92E-2	1.11E-1	1.38E-1	8.51E-2	1.17E-2
200	1.54E-2	1.76E-2	2.96E-2	5.58E-2	8.79E-2	1.41E-1	1.91E-1	1.45E-1	2.02E-2
300	1.75E-2	2.06E-2	3.29E-2	6.32E-2	1.02E-1	1.67E-1	2.35E-1	2.16E-1	4.29E-2
500	1.87E-2	2.23E-2	3.60E-2	6.58E-2	1.05E-1	1.73E-1	2.64E-1	2.92E-1	9.97E-2
1000	1.68E-2	2.02E-2	3.32E-2	5.98E-2	9.56E-2	1.61E-1	2.70E-1	3.40E-1	2.36E-1

Sputtered energy of C by T

ne = 12, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
20			2.08e-7	5.59e-7					
25	2.26E-6	4.13E-6	9.81E-6	1.69E-5	1.57E-5	1.19E-5	4.67E-6	1.98E-6	9.39E-7
30	1.41E-5	2.14E-5	4.68E-5	8.94E-5	1.07E-4	1.03E-4	5.25E-5	2.85E-5	1.22E-5
40	8.27E-5	1.10E-4	2.18E-4	4.34E-4	6.94E-4	8.32E-4	6.24E-4	3.26E-4	1.02E-4
50	1.96E-4	2.70E-4	4.72E-4	9.44E-4	1.57E-3	2.29E-3	2.02E-3	1.07E-3	2.71E-4
70	4.54E-4	5.56E-4	8.91E-4	1.93E-3	3.24E-3	5.71E-3	6.29E-3	3.55E-3	6.91E-4
100	6.68E-4	8.18E-4	1.39E-3	2.88E-3	5.26E-3	9.12E-3	1.24E-2	7.74E-3	1.36E-3
140	8.37E-4	9.27E-4	1.58E-3	3.49E-3	6.22E-3	1.14E-2	1.72E-2	1.25E-2	2.16E-3
200	8.51E-4	1.07E-3	1.83E-3	3.86E-3	6.77E-3	1.27E-2	2.00E-2	1.75E-2	3.16E-3
300	8.36E-4	1.02E-3	1.73E-3	3.66E-3	6.79E-3	1.21E-2	1.98E-2	2.09E-2	5.34E-3
500	6.78E-4	8.14E-4	1.42E-3	3.03E-3	5.23E-3	9.51E-3	1.69E-2	2.09E-2	8.60E-3
1000	3.92E-4	5.01E-4	9.10E-4	1.98E-3	3.55E-3	6.45E-3	1.18E-2	1.52E-2	1.25E-2

T - * C

Particle reflection coefficient of T backscattered from C
 z1 = 1. m1 = 2.01. z2 = 6. m2 = 12.01. sbe=7.41 eV. rho=1.85 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00. kkO=kkOr=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program : trvmc
 ne=13. na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	2.89E-1	3.13E-1	3.90E-1	5.32E-1	6.58E-1	7.92E-1	9.04E-1	9.38E-1	9.56E-1
20	2.41E-1	2.61E-1	3.24E-1	4.50E-1	5.82E-1	7.49E-1	9.10E-1	9.59E-1	9.81E-1
25	2.26E-1	2.44E-1	3.03E-1	4.20E-1	5.48E-1	7.21E-1	9.01E-1	9.59E-1	9.85E-1
30	2.14E-1	2.32E-1	2.86E-1	3.98E-1	5.20E-1	6.94E-1	8.91E-1	9.58E-1	9.87E-1
40	1.97E-1	2.13E-1	2.63E-1	3.66E-1	4.78E-1	6.49E-1	8.69E-1	9.53E-1	9.89E-1
50	1.85E-1	1.99E-1	2.47E-1	3.42E-1	4.48E-1	6.10E-1	8.46E-1	9.47E-1	9.91E-1
70	1.67E-1	1.82E-1	2.25E-1	3.11E-1	4.08E-1	5.60E-1	8.01E-1	9.30E-1	9.91E-1
100	1.52E-1	1.62E-1	2.05E-1	2.85E-1	3.73E-1	5.09E-1	7.43E-1	9.03E-1	9.90E-1
140	1.37E-1	1.49E-1	1.87E-1	2.64E-1	3.44E-1	4.69E-1	6.86E-1	8.60E-1	9.88E-1
200	1.21E-1	1.32E-1	1.68E-1	2.44E-1	3.19E-1	4.36E-1	6.27E-1	8.07E-1	9.83E-1
300	1.05E-1	1.16E-1	1.52E-1	2.22E-1	2.95E-1	4.04E-1	5.74E-1	7.35E-1	9.67E-1
500	8.46E-2	9.52E-2	1.27E-1	1.93E-1	2.63E-1	3.63E-1	5.21E-1	6.60E-1	9.27E-1
1000	5.77E-2	6.59E-2	9.38E-2	1.55E-1	2.20E-1	3.18E-1	4.69E-1	5.83E-1	8.24E-1

Energy reflection coefficient of T backscattered from C
 ne=13. na= 9

Bq(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	8.56E-2	9.98E-2	1.48E-1	2.53E-1	3.64E-1	5.05E-1	6.50E-1	7.05E-1	7.38E-1
20	7.31E-2	8.38E-2	1.21E-1	2.12E-1	3.27E-1	5.02E-1	7.17E-1	8.03E-1	8.53E-1
25	6.81E-2	7.77E-2	1.12E-1	1.94E-1	3.04E-1	4.82E-1	7.19E-1	8.20E-1	8.77E-1
30	6.42E-2	7.31E-2	1.04E-1	1.80E-1	2.83E-1	4.61E-1	7.15E-1	8.29E-1	8.93E-1
40	5.83E-2	6.62E-2	9.40E-2	1.61E-1	2.52E-1	4.22E-1	6.98E-1	8.35E-1	9.22E-1
50	5.41E-2	6.14E-2	8.68E-2	1.47E-1	2.30E-1	3.87E-1	6.77E-1	8.34E-1	9.24E-1
70	4.87E-2	5.53E-2	7.74E-2	1.30E-1	2.01E-1	3.42E-1	6.27E-1	8.19E-1	9.36E-1
100	4.37E-2	4.85E-2	6.92E-2	1.16E-1	1.78E-1	2.97E-1	5.64E-1	7.88E-1	9.42E-1
140	3.87E-2	4.40E-2	6.23E-2	1.05E-1	1.61E-1	2.63E-1	5.02E-1	7.37E-1	9.44E-1
200	3.42E-2	3.86E-2	5.56E-2	9.60E-2	1.44E-1	2.36E-1	4.38E-1	6.70E-1	9.38E-1
300	2.90E-2	3.39E-2	4.96E-2	8.59E-2	1.31E-1	2.12E-1	3.84E-1	5.83E-1	9.18E-1
500	2.30E-2	2.68E-2	4.05E-2	7.19E-2	1.14E-1	1.82E-1	3.30E-1	4.91E-1	8.61E-1
1000	1.46E-2	1.78E-2	2.81E-2	5.47E-2	8.88E-2	1.52E-1	2.78E-1	3.99E-1	7.20E-1

Average depth (mean range) in Å of T implanted in C
 ne=13. na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	4.60E+0	4.50E+0	4.40E+0	4.10E+0	3.90E+0	3.60E+0	3.30E+0	3.20E+0	3.00E+0
20	7.70E+0	7.60E+0	7.30E+0	6.80E+0	6.50E+0	6.10E+0	5.70E+0	5.50E+0	5.30E+0
25	9.20E+0	9.00E+0	8.60E+0	8.10E+0	7.60E+0	7.20E+0	6.70E+0	6.50E+0	6.20E+0
30	1.05E+1	1.04E+1	9.90E+0	9.20E+0	8.70E+0	8.20E+0	7.70E+0	7.40E+0	7.10E+0
40	1.32E+1	1.29E+1	1.23E+1	1.15E+1	1.08E+1	1.02E+1	9.50E+0	9.20E+0	8.80E+0
50	1.57E+1	1.54E+1	1.47E+1	1.36E+1	1.28E+1	1.21E+1	1.13E+1	1.09E+1	1.05E+1
70	2.06E+1	2.02E+1	1.92E+1	1.77E+1	1.66E+1	1.57E+1	1.47E+1	1.42E+1	1.34E+1
100	2.77E+1	2.72E+1	2.58E+1	2.38E+1	2.22E+1	2.09E+1	1.95E+1	1.89E+1	1.79E+1
140	3.71E+1	3.63E+1	3.44E+1	3.16E+1	2.96E+1	2.74E+1	2.59E+1	2.50E+1	2.43E+1
200	5.08E+1	5.02E+1	4.72E+1	4.31E+1	4.01E+1	3.73E+1	3.47E+1	3.43E+1	3.28E+1
300	7.41E+1	7.26E+1	6.83E+1	6.24E+1	5.75E+1	5.27E+1	4.96E+1	4.81E+1	4.60E+1
500	1.21E+2	1.18E+2	1.11E+2	1.00E+2	9.22E+1	8.47E+1	7.82E+1	7.66E+1	7.44E+1
1000	2.42E+2	2.35E+2	2.19E+2	1.95E+2	1.76E+2	1.62E+2	1.47E+2	1.43E+2	1.39E+2

T -> C

T on C, Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1, m1 = 3.02, z2 = 6, m2 = 12.01, sbe=7.42 eV, rho=2.26 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne = 9

kT(eV)	Y	Y _E	E _{sp}	R/V	R _{fi}	E _b	range
7	2.13e-3	2.79e-4	4.51e+0	2.72e-1	9.87e-2	1.27e+1	9.11e+0
10	6.00e-3	6.80e-4	5.66e+0	2.42e-1	8.51e-2	1.76e+1	1.20e+1
14	1.15e-2	1.12e-3	6.79e+0	2.19e-1	7.62e-2	2.43e+1	1.58e+1
20	1.76e-2	1.46e-3	8.32e+0	1.98e-1	6.67e-2	3.37e+1	2.13e+1
30	2.33e-2	1.69e-3	1.08e+1	1.75e-1	5.88e-2	5.03e+1	3.03e+1
50	2.95e-2	1.73e-3	1.47e+1	1.50e-1	4.97e-2	8.28e+1	4.80e+1
100	3.23e-2	1.34e-3	2.07e+1	1.19e-1	3.77e-2	1.58e+2	9.29e+1
200	3.05e-2	7.91e-4	2.60e+1	8.55e-2	2.60e-2	3.04e+2	1.84e+2
500	1.96e-2	3.21e-4	4.10e+1	4.71e-2	1.20e-2	6.36e+2	4.57e+2

T on C, Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1, m1 = 3.02, z2 = 6, m2 = 12.01, sbe=4-4° rho=1.85 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1(KrC)
 program: trspvmc
 ne = 9

kT(eV)	Y	Y _E	E _{sp}	R _N	R _B	R _b	range
2	7.83e-5		1.75e4-0	3.63e-1		3.77e+0	3.74e+0
3	7.40e-4		2.27e+0	3.29e-1		5.65e4-0	5.22e+0
5	5.04e-3		3.12e+0	2.79e-1		9.22e+0	7.81e+0
7	1.19e-2		3.81e+0	2.51e-1		1.26e+1	1.02e+1
10	2.13e-2		4.68e-J-0	2.24e-1		1.77e+1	1.37e+1
15	3.27e-2		5.88e+0	2.00e-1		2.61e+1	1.93e+1
20	3.98e-2		6.90e4-0	1.84e-1		3.44e+1	2.48e+1
30	4.76e-2		8.37e+0	1.65e-1		5.08e+1	3.55e+1
50	5.28e-2		1.07e+1	1.43e-1		8.31e+1	5.71e+1

He C

Sputtering yield of G by He

z1 = 2, m1 = 4.00, z2 = 6, m2 = 12.01, sbe = 7.41 eV, rho = 1.85 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trvmc
 ne = 22, na = 9

Eo(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
20	2.42E-6	7.10E-6	2.05E-5	2.04E-5	1.09E-5	3.84E-6	8.64E-7	4.00E-7	
25	4.20E-5	7.14E-5	1.51E-4	1.95E-4	1.68E-4	1.23E-4	3.83E-5	6.98E-6	
27	1.00E-4	1.51E-4	2.98E-4	4.29E-4	4.34E-4	3.45E-4	1.18E-4	1.97E-5	
30	2.40E-4	3.68E-4	7.02E-4	1.10E-3	1.25E-3	1.12E-3	3.84E-4	6.08E-5	
35	7.20E-4	9.99E-4	1.97E-3	3.33E-3	4.17E-3	4.04E-3	1.39E-3	2.13E-4	
40	1.50E-3	2.03E-3	3.86E-3	7.20E-3	9.33E-3	9.26E-3	3.22E-3	4.72E-4	2.18E-6
50	3.83E-3	5.03E-3	9.12E-3	1.75E-2	2.45E-2	2.59E-2	9.71E-3	1.53E-3	6.43E-6
60	6.84E-3	8.61E-3	1.50E-2	2.94E-2	4.31E-2	4.73E-2	1.95E-2	3.40E-3	1.38E-5
70	1.01E-2	1.22E-2	2.07E-2	4.13E-2	6.23E-2	7.14E-2	3.30E-2	6.27E-3	2.35E-5
100	1.83E-2	2.23E-2	3.70E-2	7.36E-2	1.13E-1	1.44E-1	8.37E-2	2.02E-2	8.40E-5
140	2.63E-2	3.22E-2	5.31E-2	1.02E-1	1.61E-1	2.19E-1	1.58E-1	4.81E-2	2.64E-4
200	3.45E-2	4.23E-2	7.04E-2	1.35E-1	2.07E-1	2.95E-1	2.65E-1	1.04E-1	9.49E-4
300	4.28E-2	5.36E-2	8.65E-2	1.64E-1	2.50E-1	3.68E-1	3.90E-1	2.13E-1	4.03E-3
400	4.75E-2	5.80E-2	9.45E-2	1.76E-1	2.71E-1	4.05E-1	4.79E-1	3.19E-1	1.09E-2
500	5.05E-2	6.12E-2	9.96E-2	1.83E-1	2.81E-1	4.24E-1	5.33E-1	4.12E-1	2.25E-2
700	5.17E-2	6.30E-2	1.03E-1	1.87E-1	2.90E-1	4.38E-1	5.99E-1	5.41E-1	6.42E-2
1000	5.19E-2	6.28E-2	1.00E-1	1.86E-1	2.84E-1	4.36E-1	6.38E-1	6.58E-1	1.59E-1
2000	4.69E-2	5.63E-2	8.84E-2	1.56E-1	2.44E-1	3.93E-1	6.38E-1	7.58E-1	4.93E-1
3000	4.24E-2	4.91E-2	7.56E-2	1.36E-1	2.11E-1	3.45E-1	5.91E-1	7.49E-1	6.73E-1
5000	3.40E-2	4.00E-2	5.79E-2	1.07E-1	1.66E-1	2.74E-1	4.98E-1	6.83E-1	7.92E-1
10000	2.43E-2	2.76E-2	4.04E-2	6.84E-2	1.05E-1	1.81E-1	3.50E-1	5.23E-1	7.67E-1
20000	1.66E-2	1.85E-2	2.65E-2	4.13E-2	6.32E-2	1.07E-1	2.23E-1	3.48E-1	6.10E-1

Sputtered energy of 0 by He

ne = 22, na = 9

Bo(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
20	1.01e-7	3.72e-7	1.39e-6	1.79e-6	1.08e-6	4.62e-7	1.30e-7	6.71e-8	
25	2.34E-6	4.64E-6	1.26E-5	1.96E-5	1.95E-5	1.55E-5	5.29E-6	1.01E-6	
27	1.00E-5	1.03E-5	2.54E-5	4.41E-5	5.02E-5	4.51E-5	1.68E-5	2.93E-6	
30	2.00E-5	2.64E-5	6.29E-5	1.20E-4	1.55E-4	1.56E-4	5.88E-5	9.52E-6	
35	5.00E-5	7.71E-5	1.87E-4	3.85E-4	5.51E-4	6.02E-4	2.40E-4	3.96E-5	
40	1.10E-4	1.62E-4	3.78E-4	8.55E-4	1.27E-3	1.49E-3	6.06E-4	9.43E-5	4.38E-7
50	2.80E-4	4.09E-4	8.88E-4	2.11E-3	3.44E-3	4.31E-3	1.96E-3	3.36E-4	1.43E-6
60	5.00E-4	7.04E-4	1.46E-3	3.44E-3	5.95E-3	7.81E-3	4.01E-3	7.58E-4	3.12E-6
70	7.40E-4	9.74E-4	1.92E-3	4.71E-3	8.36E-3	1.15E-2	6.75E-3	1.41E-3	5.35E-6
100	1.29E-3	1.66E-3	3.09E-3	7.41E-3	1.35E-2	2.11E-2	1.56E-2	4.41E-3	1.85E-5
140	1.68E-3	2.14E-3	4.10E-3	9.20E-3	1.68E-2	2.77E-2	2.57E-2	9.23E-3	5.45E-5
200	1.95E-3	2.48E-3	4.58E-3	1.05E-2	1.85E-2	3.12E-2	3.55E-2	1.67E-2	1.74E-4
300	2.01E-3	2.61E-3	4.74E-3	1.04E-2	1.86E-2	3.12E-2	4.04E-2	2.64E-2	6.41E-4
400	1.93E-3	2.46E-3	4.69E-3	9.93E-3	1.74E-2	2.97E-2	4.17E-2	3.26E-2	1.49E-3
500	1.85E-3	2.24E-3	4.24E-3	9.43E-3	1.63E-2	2.77E-2	4.09E-2	3.61E-2	2.66E-3
700	1.55E-3	2.00E-3	3.72E-3	8.13E-3	1.41E-2	2.44E-2	3.74E-2	3.82E-2	6.07E-3
1000	1.26E-3	1.65E-3	3.16E-3	6.94E-3	1.22E-2	1.99E-2	3.29E-2	3.68E-2	1.11E-2
2000	7.40E-4	9.80E-4	1.89E-3	4.03E-3	7.17E-3	1.29E-2	2.30E-2	2.88E-2	2.07E-2
3000	5.30E-4	6.60E-4	1.28E-3	2.96E-3	5.17E-3	9.62E-3	1.77E-2	2.27E-2	2.10E-2
5000	2.90E-4	3.90E-4	7.30E-4	1.72E-3	3.14E-3	6.01E-3	1.18E-2	1.62E-2	1.81E-2
10000	1.20E-4	1.70E-4	3.30E-4	7.60E-4	1.36E-3	2.80E-3	6.03E-3	9.09E-3	1.19E-2
20000	5.00E-5	8.00E-5	1.60E-4	3.10E-4	5.90E-4	1.10E-3	2.77E-3	4.37E-3	6.88E-3

Be → C

Sputtering yield of C by Be

z1= 4, m1= 9.01, z2= 6, m2= 12.01, sbe = 7.41 eV, rho = 2.26 g/cm**3
 ef=7.35 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program : trvmc95
 only low fluence!
 ne = 8, na= 1

E ₀ (eV)	Ō ³
30	1.20e-5
40	2.11e-4
50	9.28e-4
70	4.48e-3
100	1.25e-2
200	4.42e-2
500	1.07e-1
1000	1.40e-1

Sputtered energy of C by Be
 ne= 8, na= 1

E ₀ (eV)	0°
30	6.72e-7
40	1.41e-5
50	6.08e-5
70	2.65e-4
100	6.41e-4
200	1.74e-3
500	2.83e-3
1000	2.64e-3

Particle reflection coefficient of Be backscattered from C

z1= 4, m1= 9.01, z2= 6, m2= 12.01, sbe = 7.41 eV, rho = 2.26 g/cm**3
 ef=7.35 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program : trvmc95
 only low fluence!
 ne = 8, na= 1

E _p (eV)	(F
30	2.86e-2
40	2.48e-2
50	2.46e-2
70	2.64e-2
100	2.68e-2
200	2.60e-2
500	2.02e-2
1000	1.39e-2

Energy reflection coefficient of Be backscattered from C
 ne= 8, na= 1

E ₀ (eV)	0°
30	1.92e-3
40	2.44e-3
50	2.85e-3
70	3.27e-3
100	3.01e-3
200	2.56e-3
500	1.76e-3
1000	1.23e-3

Average depth (mean range) in Å Be implanted in C
 ne= 8, na= 1

E ₀ (eV)	0°
30	2.58e-10
40	3.40e+0
50	4.16e+0
70	5.53e+0
100	7.28e+0
200	1.26e+1
500	2.64e+1
1000	4.77e+1

C → C

Sputtering yield of C by C

z1= 6, m1= 12.01, z2= 6, m2= 12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=7.35 eV, esb=7.41 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc, testvmcx
 ne=19, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
8						5.00e-6	7.69e-6	8.99e-6	9.65e-6
10			5.00e-7	6.50e-6	2.07e-5	2.60e-5	3.81e-5	3.87e-5	3.78e-5
12			3.21e-6	2.36e-5	5.03e-5	7.39e-5	8.42e-5	8.64e-5	8.58e-5
15			1.10e-5	8.90e-5	1.47e-4	2.00e-4	2.36e-4	2.60e-4	2.64e-4
17						3.95e-4			
20		1.00e-5	8.10e-5	3.60e-4	6.74e-4	1.18e-3	1.73e-3	1.95e-3	2.05e-3
25	5.00e-6	3.10e-5	2.76e-4	1.28e-3	2.90e-3	5.02e-3	6.61e-3	7.13e-3	7.12e-3
30	1.83e-5	1.00e-4	8.15e-4	3.95e-3	8.02e-3	1.31e-2	1.55e-2	1.55e-2	1.60e-2
40	1.35e-4	5.96e-4	3.73e-3	1.56e-2	2.85e-2	4.06e-2	4.16e-2	3.40e-2	3.85e-2
45	2.74e-4								
50	5.21e-4	1.89e-3	1.04e-2	3.58e-2	5.81e-2	7.50e-2	7.57e-2	7.03e-2	6.37e-2
70	2.57e-3	7.31e-3	3.01e-2	8.40e-2	1.34e-1	1.63e-1	1.51e-1	1.28e-1	1.10e-1
100	8.84e-3	1.96e-2	6.53e-2	1.66e-1	2.45e-1	2.89e-1	2.45e-1	1.99e-1	1.54e-1
140	2.13e-2	3.95e-2	1.11e-1	2.52e-1	3.74e-1	4.43e-1	3.65e-1	2.60e-1	1.83e-1
200	4.14e-2	6.76e-2	1.63e-1	3.49e-1	5.16e-1	6.33e-1	5.14e-1	3.53e-1	2.11e-1
300	7.16e-2	1.06e-1	2.27e-1	4.60e-1	6.83e-1	8.63e-1	7.42e-1	4.94e-1	2.42e-1
500	1.16e-1	1.61e-1	3.05e-1	5.98e-1	8.91e-1	1.18e-0	1.15e-0	7.92e-1	3.01e-1
1000	1.78e-1	2.28e-1	3.93e-1	7.38e-1	1.10e-0	1.55e-0	1.77e-0	1.45e-0	4.92e-1
1200	2.13E-1								

Sputtered energy of C by C

ne=19, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
8						6.25e-7	1.04e-6	1.27e-6	1.37e-6
10				5.76E-7	2.69E-6	3.92E-6	5.96E-6	6.31E-6	6.45E-6
12			2.79E-7	2.62E-6	6.69E-6	1.14E-5	1.47E-5	1.55E-5	1.59E-5
15			1.05E-6	1.07E-5	2.19E-5	3.46E-5	4.39E-5	5.10E-5	5.40E-5
17						7.13e-5			
20		7.29E-7	6.84E-6	4.83E-5	1.10E-4	2.30E-4	3.77E-4	4.42E-4	4.79E-4
25	2.49E-7	2.49E-6	2.94E-5	1.92E-4	5.19E-4	1.06E-3	1.61E-3	1.74E-3	1.80E-3
30	1.09E-6	7.99E-6	9.28E-5	6.15E-4	1.57E-3	2.94E-3	3.89E-3	4.07E-3	4.32E-3
40	8.28E-6	4.85E-5	4.35E-4	2.52E-3	5.71E-3	9.61E-3	1.12E-2	1.12E-2	1.10E-2
45	1.63e-5								
50	2.98E-5	1.49E-4	1.17E-3	5.77E-3	1.15E-2	1.80E-2	2.08E-2	2.00E-2	1.81E-2
70	1.32E-4	5.06E-4	3.08E-3	1.26E-2	2.47E-2	3.68E-2	4.01E-2	3.52E-2	3.10E-2
100	4.06E-4	1.21E-3	6.00E-3	2.19E-2	4.06E-2	5.90E-2	6.04E-2	5.14E-2	4.06E-2
140	8.92E-4	2.16E-3	8.86E-3	2.89E-2	5.32E-2	7.71E-2	7.89E-2	6.06E-2	4.48E-2
200	1.57E-3	3.26E-3	1.13E-2	3.40E-2	6.18E-2	9.29E-2	9.35E-2	7.18E-2	4.66E-2
300	2.35E-3	4.40E-3	1.32E-2	3.67E-2	6.56E-2	1.01E-1	1.09E-1	8.23E-2	4.48E-2
500	3.12E-3	5.29E-3	1.39E-2	3.70E-2	6.52E-2	1.02E-1	1.25E-1	1.00E-1	4.32E-2
1000	3.48E-3	5.41E-3	1.30E-2	3.27E-2	5.68E-2	9.42E-2	1.26E-1	1.18E-1	4.88E-2
1200	3.72E-3								

C → C

Particle reflection coefficient of C backscattered from C
 z1= 6, m1= 12.01, z2= 6, m2= 12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=7.35 eV, esb=7.41 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 program : trvmc, testvmcx
 ne=18, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10						6.67E-7		8.00E-8	1.20E-7
12					4.00E-8	7.91E-7	5.67E-6	9.98E-6	1.30E-5
15				5.00E-6	1.69E-5	1.07E-4	3.66E-4	5.13E-4	6.53E-4
17						6.76E-4			
20			7.00E-6	2.20E-4	1.14E-3	3.69E-3	8.11E-3	1.02E-2	1.17E-2
25		4.00E-6	1.38E-4	1.99E-3	7.19E-3	1.78E-2	3.26E-2	3.94E-2	4.35E-2
30	2.02E-6	3.46E-5	6.64E-4	6.27E-3	1.98E-2	4.43E-2	7.30E-2	8.64E-2	9.39E-2
40	2.82E-5	2.58E-4	3.16E-3	2.16E-2	5.60E-2	1.12E-1	1.75E-1	2.03E-1	2.20E-1
45	6.23E-5								
50	1.11E-4	7.41E-4	6.47E-3	3.74E-2	9.15E-2	1.81E-1	2.82E-1	3.25E-1	3.56E-1
70	4.23E-4	1.97E-3	1.30E-2	6.25E-2	1.43E-1	2.80E-1	4.51E-1	5.30E-1	5.76E-1
100	1.11E-3	3.76E-3	1.96E-2	7.98E-2	1.78E-1	3.51E-1	5.88E-1	6.89E-1	7.58E-1
140	2.14E-3	5.52E-3	2.34E-2	8.52E-2	1.83E-1	3.70E-1	6.34E-1	7.67E-1	8.53E-1
200	3.38E-3	7.28E-3	2.61E-2	8.48E-2	1.77E-1	3.50E-1	6.39E-1	7.91E-1	8.92E-1
300	4.36E-3	8.44E-3	2.53E-2	8.10E-2	1.62E-1	3.23E-1	6.08E-1	7.88E-1	9.18E-1
500	5.32E-3	8.91E-3	2.45E-2	7.09E-2	1.39E-1	2.73E-1	5.36E-1	7.40E-1	9.28E-1
1000	4.84E-3	7.34E-3	2.05E-2	5.91E-2	1.17E-1	2.24E-1	4.46E-1	6.36E-1	9.09E-1
1200	3.70E-3								

Energy reflection coefficient of C backscattered from C
 ne=18, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10						1.03E-7		1.50E-8	1.89E-8
12					6.97E-9	1.37E-7	1.11E-6	1.99E-6	2.57E-6
15				8.57E-7	2.73E-6	1.95E-5	7.67E-5	1.11E-4	1.45E-4
17						1.36E-4			
20			8.15E-7	3.51E-5	2.19E-4	8.51E-4	2.11E-3	2.78E-3	3.29E-3
25		1.95E-7	1.86E-5	3.63E-4	1.61E-3	4.77E-3	9.99E-3	1.28E-2	1.45E-2
30	1.34E-6	3.44E-6	9.73E-5	1.25E-3	4.93E-3	1.32E-2	2.49E-2	3.12E-2	3.48E-2
40	1.93E-6	2.59E-5	4.84E-4	4.83E-3	1.56E-2	3.79E-2	6.82E-2	8.34E-2	9.36E-2
45	1.08E-5								
50	7.52E-6	7.29E-5	9.88E-4	8.69E-3	2.69E-2	6.52E-2	1.18E-1	1.45E-1	1.64E-1
70	2.79E-5	1.89E-4	1.99E-3	1.46E-2	4.45E-2	1.09E-1	2.10E-1	2.62E-1	2.97E-1
100	6.78E-5	3.37E-4	2.82E-3	1.84E-2	5.61E-2	1.44E-1	3.00E-1	3.81E-1	4.43E-1
140	1.26E-4	4.75E-4	3.19E-3	1.91E-2	5.63E-2	1.55E-1	3.49E-1	4.70E-1	5.57E-1
200	1.98E-4	5.92E-4	3.44E-3	1.81E-2	5.19E-2	1.46E-1	3.69E-1	5.19E-1	6.41E-1
300	2.55E-4	6.40E-4	3.11E-3	1.60E-2	4.60E-2	1.31E-1	3.56E-1	5.43E-1	7.12E-1
500	2.94E-4	6.46E-4	2.90E-3	1.32E-2	3.58E-2	1.03E-1	3.02E-1	5.16E-1	7.63E-1
1000	2.72E-4	5.21E-4	2.30E-3	1.05E-2	2.84E-2	7.58E-2	2.33E-1	4.27E-1	7.75E-1
1200	1.98E-4								

Average depth (mean range) in Å of C implanted in C
 ne=19, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
8						5.02E-1	4.24E-1	3.97E-1	3.79E-1
10	1.28E+0	1.23E+0	1.10E-j-O	9.28E-1	8.03E-1	6.90E-1	6.03E-1	5.72E-1	5.54E-1
12			1.23E+0	9.95E-1	8.08E-1	6.28E-1	4.83E-1	4.33E-1	4.02E-1
15	1.81E+0	1.73E-J-0	1.54E+0	1.24E+0	9.36E-1	6.99E-1	5.13E-1	4.51E-1	4.11E-1
17						7.46E-1			
20	2.31E+0	2.21E+0	1.95E+0	1.48E+0	1.14E+0	8.16E-1	5.71E-1	4.89E-1	4.38E-1
25	2.77E+0	2.65E+0	2.30E+0	1.75E+0	1.33E+0	9.44E-1	6.36E-1	5.36E-1	4.74E-1
30	3.19E+0	3.05E+0	2.66E-J-0	2.03E+0	1.50E+0	1.10E+0	7.00E-1	6.00E-1	5.00E-1
40	3.97E+0	3.80E-J-0	3.32E-J-0	2.60E+0	2.00E+0	1.40E+0	9.00E-1	8.00E-1	6.00E-1
45	4.34E+0								
50	4.69E+0	4.49E+0	3.90E+0	3.10E+0	2.40E+0	1.80E+0	1.10E-J-0	9.00E-1	8.00E-1
70	5.99E+0	5.75E+0	5.10E-J-0	4.10E+0	3.30E+0	2.50E+0	1.70E+0	1.40E+0	1.20E+0
100	7.74E+0	7.40E+0	6.70E+0	5.50E+0	4.60E+0	3.80E+0	2.80E-J-0	2.30E+0	1.90E+0
140	9.84E+0	9.50E+0	8.50E+0	7.20E+0	6.20E+0	5.20E+0	4.00E+0	3.50E+0	3.00E+0
200	1.27E+1	1.23E+1	1.11E+1	9.40E+0	8.20E+0	6.90E+0	5.70E+0	5.00E+0	4.20E+0
300	1.71E+1	1.65E+1	1.50E+1	1.27E+1	1.10E+1	9.40E+0	7.90E+0	7.10E+0	6.00E+0
500	2.51E+1	2.43E-J-1	2.20E+1	1.87E+1	1.63E+1	1.38E+1	1.17E+1	1.07E+1	9.50E+0
1000	4.34E+1	4.20E+1	3.80E+1	3.22E+1	2.78E+1	2.38E+1	2.03E+1	1.85E+1	1.71E+1
1200	4.14E+1								

C → C

Sputtering yield of C by C

z1 = 6, m1 = 12.01, z2 = 6, m2 = 12.01, sbe=7.42 eV, rho = 2.26 g/cm**3
 ef=7.37 eV, esb = 7.42 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : testvmcx, trspvlcn, trvmc95, trvmc
 ne=36, na= 7

Bo(eV)	0°	30°	45°	50°	70°	75°	85°
8					2.63e-6		
10					1.83e-5		
12					5.49e-5		
14					1.14e-4		
15					1.72e-4		
20					1.32e-3		
25	5.72e-6				5.72e-3		
28	1.15e-5						
30	1.94E-5				1.40e-2		
35	5.53e-5						
40	1.44e-4				4.16e-2		
45	2.97e-4						
50	5.33E-4				7.77e-2		
50	5.75e-4						
70	2.72E-3				1.55e-1		
100	9.31E-3				2.64e-1		
100	1.01e-2						
150	2.65e-2						
200	4.51e-2				5.98e-1		
200	4.60e-2						
500	1.27E-1				1.27e-0		
500	1.30e-1						
1000	1.92E-1				1.81e-0		
1000	1.85e-1						
1200	2.13e-1						
2000	2.26e-1				2.16e-0		
2000	2.24e-1						
3000		4.59e-1	8.23e-1			2.68e-0	1.23e-0
3000			8.27e-1	1.03e-0			
5000	2.54e-1				2.35e-0		
5000	2.34e-1						
10000	2.25E-1				2.06e-0		
10000	2.12e-1			7.67e-1			
30000	1.60E-1				1.13e-0		
30000	1.56e-1						
100000	8.58e-2				4.39e-1		

Sputtered energy of C by C

ne=36, na= 7

E ₀ (eV)	0°	30°	45°	50°	70°	75°	85°
8					3.50e-7		
10					2.67e-6		
12					8.99e-6		
14					2.04e-5		
15					3.07e-5		
20					2.69e-4		
25	6.76e-7				1.27e-3		
28	7.46e-7						
30	1.23E-6				3.30e-3		
35	3.69e-6						
40	8.84e-6				1.04e-2		
45	1.88e-5						
50	3.16E-5				1.97e-2		
50	3.43e-5						
70	1.42E-4				3.82e-2		
100	4.30E-4				6.00e-2		
100	4.89e-4						
150	1.04e-3						
200	1.62e-3				9.82e-2		
200	1.60e-3						
500	3.26E-3				1.22e-1		
500	3.19e-3						
1000	3.56E-3				1.13e-1		
1000	3.27e-3						
1200	3.73e-3						
2000	3.07e-3				9.71e-2		
2000	2.86e-3						
3000		9.06e-3	2.27e-2			1.07e-1	6.04e-2
3000			2.15e-2	2.92e-2			
5000	2.15e-3				7.36e-2		
5000	1.96e-3						
10000	1.32E-3				5.13e-2		
10000	1.24e-3			1.36e-2			
30000	4.66E-4				1.68e-2		
30000	5.03e-4						
100000	1.08e-4				2.34e-3		

C → C

Particle reflection coefficient of C backscattered from C
 z1 = 6. m1 = 12.01. z2 = 6. m2 = 12.01. sbe=7.42 eV. rho = 2.26 g/cm**3
 ef=7.37 eV. esb=7.42 eV. ca=1.00, kk0=kk0r=2. kdee1=kdee2=3. ipot=ipot = 1 (KrC)
 program : testvmcx, trspvlen. trvmc95. trvmc
 ne = 34, na = 7

E ₀ (eV)	0°	30°	45°	50°	70°	75°	85°
12					2.82e-6		
14					5.91e-5		
15					1.86e-4		
20					5.44e-3		
25	1.41e-7				2.61e-2		
28	4.65e-7						
30	1.45E-6				6.32e-2		
35	8.15e-6						
40	2.88e-5				1.58e-1		
45	6.58e-5						
50	1.14E-4				2.59e-1		
50	1.10e-4						
70	5.03E-4				4.13e-1		
100	1.25E-3				5.28e-1		
100	1.33e-3						
150	2.46e-3						
200	3.45e-3				5.42e-1		
200	3.03e-3						
500	5.29E-3				4.05e-1		
500	3.84e-3						
1000	5.04E-3				3.37e-1		
1000	4.04e-3						
1200	3.70e-3						
2000	3.95e-3				2.91e-1		
2000	3.56e-3						
3000		1.30e-2	4.01e-2			3.56e-1	8.28e-1
3000			4.19e-2	6.01e-2			
5000	1.60e-3				2.28e-1		
5000	1.82e-3						
10000	1.10E-3				1.88e-1		
10000	1.16e-3			3.75e-2			
30000	4.67E-4				1.46e-1		
30000	4.20e-4						
100000	5.79e-5				7.52e-2		

Energy reflection coefficient of C backscattered from C
 ne=34, na= 7

E ₀ (eV)	0°	30°	45°	50°	70°	75°	85°
12					1.47e-6		
14					1.16e-5		
15					3.82e-5		
20					1.31e-3		
25	3.63e-7				7.34e-3		
28	2.09e-7						
30	1.02E-7				1.99e-2		
35	6.11e-7						
40	2.05e-6				5.69e-2		
45	4.74e-6						
50	8.44E-6				1.01e-1		
50	1.22e-5						
70	3.40E-5				1.78e-1		
100	7.89E-5				2.48e-1		
100	8.64e-5						
150	1.51e-4						
200	2.08e-4				2.77e-1		
200	1.83e-4						
500	2.88E-4				1.94e-1		
500	2.02e-4						
1000	2.99E-4				1.44e-1		
1000	2.29e-4						
1200	1.09e-4						
2000	2.28e-4				1.14e-1		
2000	2.20e-4						
3000		1.44e-3	6.86e-3			1.63e-1	7.05e-1
3000			7.31e-3	1.22e-2			
5000	8.71e-5				8.49e-2		
5000	1.08e-4						
10000	6.68E-5				6.84e-2		
10000	5.59e-5			7.28e-3			
30000	1.27E-5				4.50e-2		
30000	2.22e-5						
100000	2.47e-6				1.54e-2		

C → C

Average depth (mean range) in Å of C implanted in C
 z1 = 6. m1 = 12.01. z2 = 6. m2 = 12.01. sbe = 7.42 eV. rho = 2.26 g/cm**3
 ef = 7.37 eV. esb = 7.42 eV. ca = 1.00. kk0 = kk0r = 2 ; kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : testvmcx. trspvln. trvmc95. trvmc
 ne = 37. na = 7

E ₀ (eV)	0°	30°	45°	50°	70°	75°	85°
8					2.59e-1		
10					3.16e-1		
12					3.46e-1		
14					3.67e-1		
15					3.76e-1		
20	1.46e+0				4.33e-1		
25	2.10e+0				4.98e-1		
28	2.31e+0						
30	2.45E+0				5.74e-1		
30	2.03e+0						
35	2.78e+0						
40	3.09e+0				7.59e-1		
45	3.39e+0						
50	3.68E+0				9.81e-1		
50	3.07e+0						
70	4.74E+0				1.53e+0		
100	6.17E+0				2.48e+0		
100	5.30e+0						
150	8.30e+0						
200	1.02e+1				4.95e+0		
200	9.08e+0						
500	2.04E4-1				1.02e+1		
500	1.89e+1						
1000	3.54E+1				1.81e+1		
1000	3.37e+1						
1200	4.11e4-1						
2000	6.41e+1				3.14e+1		
2000	6.18e+1						
3000		8.05e+1	6.74e+1			4.08e+1	3.49e+1
3000			6.76e+1	6.29e+1			
5000	1.49e+2				6.97e+1		
5000	1.46e+2						
10000	2.94E+2				1.34e4-2		
10000	2.91e+2			1.96e4-2			
30000	8.82E+2				3.69e+2		
30000	8.77e+2						
100000	2.72e+3				1.02e+3		

C → C

Sputtering yield of C by C

z1 = 6, m1 = 12.01, z2 = 6, m2 = 12.01, sbe = 7.40 eV, rho = 2.00 g/cm**3
 ef = 7.35, 6.90 eV, esb = 7.40 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : testvmcx, newtrim (Laszlo), trspvmc
 ne = 22, na = 7

E ₀ (eV)	0°	30°	45°	60°	65°	70°	80°
17					3.83e-4		
18					5.37e-4		
18					3.06e-4		
19					8.09e-4		
19					5.21e-4		
20					1.23e-3		
20					8.65e-4		
25					5.22e-3		
25					4.62e-3		
30					1.26e-2		
45	2.59e-4						
50	5.05E-4				8.12e-2		
53	7.48e-4						
55	8.66e-4						
70	2.62E-3				1.73e-1		
100	9.49E-3				3.12e-1	2.83e-1	
150						4.57e-1	
300	7.36e-2				8.97e-1		
300	8.05e-2	2.33e-1	4.85e-1	8.16e-1		8.49e-1	4.66e-1
1000	1.79e-1	4.23e-1	7.37e-1	1.38e-0		1.73e-0	1.39e-0
3000	2.49e-1			1.50e-0		2.25e-0	2.68e-0
6000						2.26e-0	

Sputtered energy of C by C

B ₀ (eV)	0°	30°	45°	60°	65°	70°	80°
17					6.68e-5		
18					9.62e-5		
18					5.66e-5		
19					1.53e-4		
19					9.95e-5		
20					2.35e-4		
20					1.71e-4		
25					1.10e-3		
25					1.01e-3		
30					2.89e-3		
45	1.63e-5						
50	3.05E-5				1.92e-2		
53	4.28e-5						
55	5.05e-5						
70	1.37E-4				3.90e-2		
100	4.36E-4				6.35e-2	6.37e-2	
150					9.96e-2	8.66e-2	
300	2.24e-3						
300	2.41e-3	1.30e-2	3.85e-2	8.21e-2		1.08e-1	7.84e-2
1000	3.54e-3	1.36e-2	2.99e-2	7.40e-2		1.14e-1	1.11e-1
3000	2.80e-3			4.91e-2		9.20e-2	1.12e-1
6000						6.34e-2	

C → C

Particle reflection coefficient of C backscattered from C
 z1= 6, m1= 12.01, z2= 6, m2= 12.01, sbe=7.40 eV, rho=2.00 g/cm**3
 ef=7.35, 6.90 eV, esb=7.40 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : testvmcx, newtrim (Laszlo), trspvmc
 ne=22, na= 7

E ₀ (eV)	0°	30°	45°	60°	65°	70°	80°
17					6.42e-4		
18					1.30e-3		
18					1.27e-3		
19					2.24e-3		
19					2.21e-3		
20					3.77e-3		
20					3.60e-3		
25					1.87e-2		
25					1.86e-2		
30					4.49e-2		
45	6.93e-5						
50	1.13E-4				1.90e-1		
53	1.53e-4						
55	1.79e-4						
70	3.98E-4				2.96e-1		
100	1.30E-3				3.68e-1	4.84e-1	
150						5.19e-1	
300	4.27e-3				3.40e-1		
300	4.47e-3	2.54e-2	8.19e-2	2.47e-1		4.73e-1	8.06e-1
1000	4.46e-3	1.76e-2	5.98e-2	1.54e-1		3.40e-1	6.56e-1
3000	3.98e-3			1.34e-1		2.44e-1	4.93e-1
6000						2.42e-1	

Energy reflection coefficient of C backscattered from C
 ne=22, na= 7

E ₀ (eV)	0°	30°	45°	60°	65°	70°	80°
17					1.37e-4		
18					2.75e-4		
18					2.65e-4		
19					4.90e-4		
19					4.81e-4		
20					8.47e-4		
20					8.15e-4		
25					4.94e-3		
25					4.81e-3		
30					1.32e-2		
45	4.84e-6						
50	7.50E-6				6.87e-2		
53	9.82e-6						
55	1.13e-5						
70	2.73E-5				1.16e-1		
100	8.89E-5				1.52e-1	2.25e-1	
150						2.55e-1	
300	2.31e-4				1.38e-1		
300	2.54e-4	3.23e-3	1.66e-2	8.64e-2		2.32e-1	5.63e-1
1000	2.13e-4	1.70e-3	1.03e-2	4.55e-2		1.40e-1	4.52e-1
3000	1.31e-4			3.69e-2		9.34e-2	2.91e-1
6000						8.17e-2	

Average depth- (mean range) in Å of C implanted in C
 ne=22, na= 7

E ₀ (eV)	0°	30°	45°	60°	65°	70°	80°
17					6.36e-1		
18					6.57e-1		
18					3.12e-1		
19					6.77e-1		
19					5.73e-1		
20					6.97e-1		
20					6.87e-1		
25					8.07e-1		
25					8.05e-1		
30					9.36e-1		
45	3.51e+0						
50	3.86E+0				1.53e+0		
53	4.08e+0						
55	4.21e+0						
70	5.12E+0				2.33e+0		
100	7.09E+0				3.40e-1-0	2.94e-0	
150						4.49e-0	
300	1.57e+1				8.64e+0		
300	1.57e+1	1.39e-H	1.18e+1	9.29e-0		8.22e-0	6.46e-0
1000	4.00e+1	3.50e+1	3.09e-f-1	2.39e+1		1.98e+1	1.70e+1
3000	1.03e+2			5.99e+1		5.13e+1	4.15e+1
6000						9.50e+1	

C → C

C on C, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 6, m1 = 12.01, z2 = 6, m2 = 12.01, sbe = 7.42 eV, rho = 2.26 g/cm**3
 ef = 7.37, esb = 7.42 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx
 ne = 11

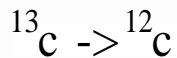
kT(eV)	Y	Ye	E _{sp}	R _w	Re	E _b	range
5	4.24e-4	2.85e-4	6.71e+0	1.27e-3	1.28e-3	1.01e+1	4.93e-1
7	1.63e-3	9.62e-4	8.23e+0	4.78e-3	4.51e-3	1.32e+1	6.95e-1
10	5.88e-3	3.00e-3	1.02e+1	1.44e-2	1.19e-2	1.66e+1	9.77e-1
20	3.35e-2	1.22e-2	1.46e+1	5.89e-2	4.11e-2	2.80e+1	1.82e+0
50	1.54e-1	3.22e-2	2.09e+1	1.40e-1	7.71e-2	5.54e+1	4.10e+0
100	3.15e-1	4.28e-2	2.78e+1	1.70e-1	8.35e-2	9.85e+1	7.39e+0
200	5.06e-1	4.60e-2	3.64e+1	1.72e-1	7.55e-2	1.75e+2	1.27e+1
500	7.67e-1	4.21e-2	5.49e+1	1.46e-1	5.87e-2	4.02e+2	2.67e+1
1000	9.08e-1	3.54e-2	7.75e+1	1.22e-1	4.77e-2	7.75e+2	4.79e+1
2000	9.94e-1	2.72e-2	1.09e+2	1.02e-1	3.72e-2	1.46e+3	9.01e+1
5000	9.16e-1	1.58e-2	1.73e+2	8.36e-2	2.93e-2	3.52e+3	2.16e+2

C on C, Maxwellian velocity distribution, sheath potential 3 kT
 ne = 13

kT(eV)	Y	Ye	E _{sp}	R _w	Re	E _b	range
3.5	2.87e-4	7.74e-5	4.72e+0	3.71e-4	1.61e-4	7.58e+0	1.29e-0
5	1.45e-3	3.68e-4	6.36e-j-0	1.75e-3	6.70e-4	9.57e+0	1.78e+0
7	5.25e-3	1.19e-3	7.91e+0	5.15e-3	1.76e-3	1.19e+1	2.37e+0
10	1.58e-2	2.81e-3	8.92e+0	1.03e-2	3.12e-3	1.51e+1	3.17e+0
14	3.44e-2	5.08e-3	1.03e+1	1.52e-2	3.99e-3	1.84e+1	4.14e+0
20	6.52e-2	7.68e-3	1.18e+1	2.02e-2	4.53e-3	2.25e+1	5.44e+0
30	1.14e-1	1.05e-2	1.37e+1	2.22e-2	4.58e-3	3.09e+1	7.36e+0
50	1.82e-1	1.25e-2	1.72e+1	2.33e-2	4.04e-3	4.34e+1	1.08e+1
100	2.77e-1	1.31e-2	2.36e-f-1	2.14e-2	3.33e-3	7.78e+1	1.84e+1
200	3.56e-1	1.18e-2	3.31e+1	1.79e-2	2.54e-3	1.42e+2	3.19e+1
500	4.05e-1	8.48e-3	5.24e+1	1.25e-2	1.76e-3	3.52e+2	7.03e+1
1000	3.86e-1	5.88e-3	7.62e+1	9.26e-3	1.35e-3	7.30e+2	1.33e+2
2000	3.37e-1	3.70e-3	1.09e+2	4.60e-3	6.80e-4	1.46e+3	2.61e+2

C on C, Maxwellian velocity distribution, sheath potential 9 kT
 ne = 15

kT(eV)	Y	Ye	E _{sp}	R _w	Re	E _b	range
2	8.57e-5	1.32e-5	3.39e+0	6.90e-5	1.48e-5	4.72e+0	2.13e-j-0
3	7.70e-4	1.05e-4	4.52e-j-0	5.20e-4	1.10e-4	6.82e-j-0	2.48e+0
5	6.07e-3	6.76e-4	6.13e+0	2.78e-3	4.83e-4	9.55e-j-0	3.72e+0
7	1.68e-2	1.55e-3	7.09e+0	4.92e-3	7.25e-4	1.13e-j-1	4.80e+0
10	3.69e-2	2.82e-3	8.41e+0	7.52e-3	1.01e-3	1.48e+1	6.28e+0
14	6.35e-2	4.00e-3	9.71e+0	9.15e-3	1.09e-3	1.83e+1	8.04e+0
20	9.93e-2	5.22e-3	1.16e-j-1	1.07e-2	1.20e-3	2.47e+1	1.05e+1
30	1.47e-1	6.34e-3	1.43e+1	1.09e-2	1.12e-3	3.39e+1	1.42e+1
50	2.02e-1	6.84e-3	1.87e+1	1.06e-2	9.51e-4	4.95e-H	2.09e+1
100	2.68e-1	6.39e-3	2.63e-f-1	9.12e-3	8.05e-4	9.70e+1	3.66e+1
200	3.06e-1	5.17e-3	3.71e-f-1	6.74e-3	6.01e-4	1.96e+2	6.66e-j-1
500	3.01e-1	3.28e-3	6.01e+1	4.43e-3	4.39e-4	5.45e+2	1.55e+2
1000	2.52e-1	1.97e-3	8.60e-j-1	2.65e-3	1.81e-4	7.51e+2	3.50e+2
2000	2.01e-1	1.19e-3	1.30e+2	7.32e-4	3.52e-5	1.06e+3	6.93e-j-2
5000	1.33e-1	3.78e-4	1.57e+2				1.70e+3



Particle reflection coefficient of ^{13}C backscattered from ^{12}C
 $z1 = 6, m1 = 13.00, z2 = 6, m2 = 12.00, sbe = 7.41 \text{ eV}, \rho = 2.26 \text{ g/cm}^3$
 $ef = 0.50 \text{ eV}, esb = 7.41 \text{ eV}, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 \quad (\text{KrC})$
 $\alpha = 0.00$
 program : trvmc95
 $ne = 10, na = 1$

B_0 (eV)	0°	comment
22	3.03e-2	ef=7.35 eV, esb=0.00 eV
22	4.51e-2	esb=0.00 eV
47	2.00e-5	
72	1.50e-4	
92	3.30e-4	
122	6.60e-4	
222	1.95e-3	
472	3.33e-3	
692	3.34e-3	
1000	3.32e-3	

Particle reflection coefficient of ^{13}C backscattered from ^{12}C
 $ne = 10, na = 1$

E_0 (eV)	0°	comment
22	7.19e-5	ef=7.35 eV, esb=0.00 eV
22	8.57e-4	esb=0.00 eV
47	1.53e-6	
72	8.01e-6	
92	1.97e-5	
122	3.07e-5	
222	9.47e-5	
472	1.58e-4	
692	1.64e-4	
1000	1.48e-4	

Moments of depth distribution in \AA of ^{13}C implanted in ^{12}C
 $z1 = 6, m1 = 13.00, z2 = 6, m2 = 12.00, sbe = 7.41 \text{ eV}, \rho = 2.26 \text{ g/cm}^3$
 $ef = 0.50 \text{ eV}, esb = 7.41 \text{ eV}, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 \quad (\text{KrC})$
 $\alpha = 0.00$
 program : trvmc95
 $ne = 10, na = 1$

E_0 (eV)	range	sigma	skewness	kurtosis	comment
10	1.46e+0	9.74e-1	3.61e-1	2.51e+0	
22	1.39e+0	8.18e-1	2.98e-1	2.28e+0	ef=7.35 eV, esb=0.00 eV
22	1.88e-j-0	1.16e+0	2.88e-1	2.50e+0	ef=7.35 eV, esb=7.41 eV
22	2.38e+0	1.34e-j-0	2.18e-1	2.53e-j-0	
22	2.40e-d-0	1.37e-j-0	2.27e-1	2.54e+0	kdee1=kdee2=2
22	2.32e+0	1.30e+0	2.05e-1	2.54e+0	kdee1=kdee2=1
22	2.55e+0	1.44e-j-0	2.48e-1	2.59e+0	kkO=kkOr=1
22	2.29e+0	1.30e+0	2.09e-1	2.53e+0	kk0=kk0r=3
22	2.59e+0	1.47e+0	2.64e-1	2.59e+0	ipot=ipotr=3
22	2.39e-j-0	1.36e+0	2.26e-1	2.54e-f-0	ck=0.50
22	2.42e+0	1.39e+0	2.33e-1	2.54e+0	ck=0.00
22	3.41e-j-0	1.95e-j-0	3.04e-1	2.67e+0	kkO=kkOr=0
22	1.91e+0	1.05e+0	3.15e-1	2.52e+0	esb=0.00 eV
32	3.00e+0	1.61e+0	2.03e-1	2.58e+0	
47	3.87e+0	1.99e+0	2.11e-1	2.62e+0	
72	5.15e+0	2.59e+0	2.53e-1	2.68e-j-0	
92	6.08e+0	3.04e+0	2.82e-1	2.69e+0	
122	7.39e+0	3.67e+0	3.11e-1	2.73e+0	
222	1.13e+1	5.56e+0	3.88e-1	2.86e+0	
472	1.95e-H	9.62e+0	4.35e-1	2.94e+0	
692	2.63e+1	1.28e+1	4.29e-1	2.91e-j-0	
1000	3.54e+1	1.70e-j-1	4.06e-1	2.88e+0	

N C

Sputtering yield of C by N
 z1 = 7, m1 = 14.01, z2 = 6, m2 = 12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl=1 (KrC)
 program: trvmc
 ne=14, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
15				7.93E-6	1.68E-5		1.28E-5	5.29E-6	3.00E-6	2.15E-6
20			1.31E-5	9.85E-5	1.41E-4		1.57E-4	1.31E-4	9.04E-5	5.71E-5
25		3.60E-6	7.67E-5	3.70E-4	8.16E-4		1.36E-3	9.78E-4	5.75E-4	2.91E-4
30	1.12E-6	1.78E-5	2.39E-4	1.40E-3	3.41E-3		5.10E-3	3.15E-3	1.58E-3	6.70E-4
40	1.81E-5	1.55E-4	1.70E-3	9.34E-3	1.85E-2		2.20E-2	1.10E-2	4.46E-3	1.46E-3
50	1.23E-4	7.40E-4	6.03E-3	2.68E-2	4.57E-2		4.89E-2	2.25E-2	8.25E-3	2.06E-3
70	1.11E-3	4.30E-3	2.38E-2	7.85E-2	1.19E-1		1.22E-1	5.45E-2	1.77E-2	2.89E-3
100	5.53E-3	1.50E-2	5.98E-2	1.64E-1	2.42E-1		2.52E-1	1.14E-1	3.47E-2	3.66E-3
140	1.63E-2	3.47E-2	1.08E-1	2.62E-1	3.84E-1		4.19E-1	2.05E-1	6.24E-2	4.54E-3
200	3.68E-2	6.42E-2	1.67E-1	3.75E-1	5.52E-1		6.31E-1	3.57E-1	1.16E-1	6.18E-3
300	6.94E-2	1.06E-1	2.39E-1	5.06E-1	7.46E-1		9.08E-1	6.20E-1	2.27E-1	1.03E-2
500	1.21E-1	1.68E-1	3.30E-1	6.55E-1	9.78E-1		1.27E+0	1.10E+0	5.16E-1	2.45E-2
1000	1.96E-1	2.53E-1	4.40E-1	8.31E-1	1.24E+0		1.74E+0	1.90E+0	1.29E+0	1.08E-1
15000						1.15e-0				

Sputtered energy of C by N
 ne=14, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
15				5.85e-7	1.62e-6		1.63e-6	8.24e-7	5.39e-7	4.74e-7
20			8.14e-7	9.36E-6	1.81E-5		2.53E-5	2.41E-5	1.75E-5	1.21E-5
25		1.79e-7	5.56E-6	4.12E-5	1.19E-4		2.44E-4	2.04E-4	1.26E-4	6.56E-5
30	4.60e-8	9.61e-7	2.01E-5	1.77E-4	5.65E-4		1.03E-3	7.42E-4	3.88E-4	1.70E-4
40	7.69e-7	9.64E-6	1.65E-4	1.38E-3	3.42E-3		5.00E-3	2.90E-3	1.22E-3	4.08E-4
50	5.63E-6	4.88E-5	6.15E-4	4.11E-3	8.78E-3		1.16E-2	6.26E-3	2.34E-3	5.70E-4
70	5.03E-5	2.78E-4	2.33E-3	1.16E-2	2.25E-2		2.87E-2	1.52E-2	5.08E-3	7.77E-4
100	2.35E-4	8.73E-4	5.28E-3	2.18E-2	4.11E-2		5.40E-2	3.00E-2	9.43E-3	8.90E-4
140	6.37E-4	1.81E-3	8.44E-3	3.02E-2	5.63E-2		7.81E-2	4.85E-2	1.55E-2	9.68E-4
200	1.31E-3	2.97E-3	1.13E-2	3.64E-2	6.76E-2		9.75E-2	7.19E-2	2.53E-2	1.12E-3
300	2.20E-3	4.21E-3	1.36E-2	4.02E-2	7.26E-2		1.10E-1	9.84E-2	4.16E-2	1.59E-3
500	3.13E-3	5.39E-3	1.49E-2	4.05E-2	7.23E-2		1.14E-1	1.26E-1	7.07E-2	3.07E-3
1000	3.74E-3	5.89E-3	1.44E-2	3.67E-2	6.45E-2		1.06E-1	1.40E-1	1.12E-1	1.08E-2
15000						2.18e-2				-E

N → C

Particle reflection coefficient of N backscattered from C
 z1 = 7, m1= 14.01, z2= 6, m2= 12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=0.95 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trvmc
 ne=16, na=10

Eo(eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	2.78e-6	3.02E-4	7.13E-3	5.63E-2	1.54E-1		3.21E-1	5.10E-1	5.80E-1	6.20E-1
12	3.84E-5	9.46E-4	1.48E-2	9.34E-2	2.23E-1		4.28E-1	6.38E-1	7.12E-1	7.55E-1
15	2.85E-4	2.71E-3	2.76E-2	1.43E-1	3.07E-1		5.40E-1	7.65E-1	8.37E-1	8.76E-1
20	1.06E-3	6.20E-3	4.57E-2	1.98E-1	3.90E-1		6.40E-1	8.61E-1	9.23E-1	9.54E-1
25	1.91E-3	8.99E-3	5.65E-2	2.24E-1	4.28E-1		6.83E-1	8.96E-1	9.53E-1	9.78E-1
30	2.62E-3	1.08E-2	6.18E-2	2.34E-1	4.41E-1		6.97E-1	9.11E-1	9.65E-1	9.87E-1
40	3.62E-3	1.27E-2	6.46E-2	2.34E-1	4.39E-1		7.00E-1	9.21E-1	9.75E-1	9.94E-1
50	4.27E-3	1.34E-2	6.31E-2	2.23E-1	4.24E-1		6.87E-1	9.23E-1	9.79E-1	9.96E-1
70	4.93E-3	1.36E-2	5.76E-2	1.97E-1	3.85E-1		6.53E-1	9.16E-1	9.81E-1	9.98E-1
100	5.57E-3	1.32E-2	5.01E-2	1.66E-1	3.32E-1		5.98E-1	8.96E-1	9.79E-1	9.99E-1
140	5.53E-3	1.23E-2	4.25E-2	1.38E-1	2.81E-1		5.32E-1	8.65E-1	9.73E-1	9.99E-1
200	5.43E-3	1.11E-2	3.66E-2	1.14E-1	2.36E-1		4.59E-1	8.15E-1	9.61E-1	9.99E-1
300	4.94E-3	9.64E-3	3.00E-2	9.41E-2	1.92E-1		3.82E-1	7.38E-1	9.34E-1	9.99E-1
500	4.45E-3	7.91E-3	2.36E-2	7.36E-2	1.50E-1		3.04E-1	6.20E-1	8.68E-1	9.98E-1
1000	3.28E-3	5.77E-3	1.70E-2	5.49E-2	1.16E-1		2.34E-1	4.79E-1	7.23E-1	9.87E-1
15000						6.88e-2				

Energy reflection coefficient of N backscattered from C
 ne=16, na=10

Eo(eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	1.53e-7	2.59E-5	9.18E-4	1.06E-2	3.86E-2		1.05E-1	2.06E-1	2.52E-1	2.82E-1
12	2.25e-6	8.41E-5	2.00E-3	1.85E-2	5.82E-2		1.47E-1	2.76E-1	3.34E-1	3.73E-1
15	1.78E-5	2.40E-4	3.86E-3	2.96E-2	8.44E-2		1.98E-1	3.61E-1	4.34E-1	4.81E-1
20	6.53E-5	5.58E-4	6.39E-3	4.29E-2	1.14E-1		2.54E-1	4.54E-1	5.42E-1	6.00E-1
25	1.12E-4	7.84E-4	7.82E-3	4.97E-2	1.30E-1		2.85E-1	5.08E-1	6.09E-1	6.74E-1
30	1.44E-4	9.01E-4	8.39E-3	5.24E-2	1.38E-1		3.02E-1	5.42E-1	6.53E-1	7.24E-1
40	1.79E-4	9.73E-4	8.37E-3	5.21E-2	1.41E-1		3.15E-1	5.80E-1	7.07E-1	7.88E-1
50	1.93E-4	9.53E-4	7.79E-3	4.89E-2	1.36E-1		3.15E-1	5.98E-1	7.38E-1	8.27E-1
70	2.00E-4	8.59E-4	6.55E-3	4.14E-2	1.22E-1		3.01E-1	6.09E-1	7.69E-1	8.71E-1
100	1.97E-4	7.55E-4	5.20E-3	3.30E-2	1.01E-1		2.72E-1	6.01E-1	7.86E-1	9.03E-1
140	1.82E-4	6.53E-4	4.11E-3	2.55E-2	8.07E-2		2.35E-1	5.77E-1	7.88E-1	9.23E-1
200	1.73E-4	5.49E-4	3.34E-3	1.98E-2	6.29E-2		1.92E-1	5.33E-1	7.76E-1	9.36E-1
300	1.52E-4	4.60E-4	2.59E-3	1.52E-2	4.73E-2		1.49E-1	4.65E-1	7.43E-1	9.44E-1
500	1.44E-4	3.77E-4	1.95E-3	1.11E-2	3.39E-2		1.07E-1	3.65E-1	6.66E-1	9.44E-1
1000	1.15E-4	2.80E-4	1.43E-3	7.86E-3	2.43E-2		7.36E-2	2.49E-1	5.10E-1	9.21E-1
15000						1.60e-2				

Average depth (mean range) in A of N implanted in C
 ne=16, na=10

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	80°	85°
10	1.20E+0	1.10E+0	9.00E-1	6.00E-1	5.00E-1		3.00E-1	2.00E-1	1.00E-1	1.00E-1
12	1.40E+0	1.30E+0	1.10E+0	8.00E-1	6.00E-1		4.00E-1	2.00E-1	2.00E-1	1.00E-1
15	1.70E+0	1.60E+0	1.30E+0	1.00E+0	8.00E-1		5.00E-1	3.00E-1	2.00E-1	2.00E-1
20	2.20E+0	2.00E+0	1.80E+0	1.40E+0	1.10E+0		8.00E-1	5.00E-1	4.00E-1	3.00E-1
25	2.60E+0	2.50E+0	2.20E+0	1.70E+0	1.30E+0		1.00E+0	5.00E-1	3.00E-1	2.00E-1
30	3.10E+0	2.90E+0	2.50E+0	2.10E+0	1.70E+0		1.20E+0	8.00E-1	7.00E-1	5.00E-1
40	3.80E+0	3.60E+0	3.20E+0	2.60E+0	2.30E+0		1.80E+0	1.20E+0	9.00E-1	6.00E-1
50	4.50E+0	4.30E+0	3.60E+0	3.20E+0	2.70E+0		2.20E+0	1.50E+0	1.10E+0	9.00E-1
70	5.70E+0	5.50E+0	4.60E+0	4.20E+0	3.60E+0		3.00E+0	2.10E+0	1.60E+0	1.10E+0
100	7.40E+0	7.10E+0	6.00E+0	5.40E+0	4.70E+0		4.00E+0	3.00E+0	2.40E+0	1.60E+0
140	9.40E+0	9.00E+0	8.20E+0	6.90E+0	6.00E+0		5.10E+0	4.00E+0	3.30E+0	2.20E+0
200	1.20E+1	1.16E+1	1.05E+1	8.90E+0	7.70E+0		6.60E+0	5.40E+0	4.60E+0	3.20E+0
300	1.60E+1	1.55E+1	1.40E+1	1.18E+1	1.02E+1		8.70E+0	7.30E+0	6.40E+0	4.80E+0
500	2.32E+H	2.24E+1	2.02E+1	1.71E+1	1.48E+1		1.26E+1	1.06E+1	9.50E+0	7.60E+0
1000	3.94E+1	3.80E+1	3.44E+1	2.89E+1	2.50E+1		2.10E+1	1.76E+1	1.62E+1	1.39E+1
15000						2.48e+2				

N → C

Sputtering yield of C by N

z1= 7, m1= 14.01, z2= 6, m2= 12.01, sbe=7.41 eV, rho = 2.26 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program: trvmc
 ne= 2, na=12

B ₀ (eV)	0°	10°	20°	30°	40°	50°	60°	70°	75°	80°	85°	87°
15000	2.64e-1	2.79e-1	3.25e-1	4.11e-1	5.54e-1	8.02e-1	1.28e-0	2.24e-0	2.99e-0	3.87e-0	4.04e-0	2.05e-0
30000	2.15e-1	2.23e-1	2.54e-1	3.07e-1	3.95e-1	5.43e-1	8.37e-1	1.53e-0	2.21e-0	3.22e-0	4.29e-0	

Sputtered energy of C by N

ne= 2, na=12

B ₀ (eV)	0°	10°	20°	30°	40°	50°	60°	70°	75°	80°	85°	87°
15000	1.21e-3	1.44e-3	2.15e-3	3.74e-3	6.70e-3	1.23e-2	2.40e-2	4.68e-2	6.32e-2	7.90e-2	7.72e-2	4.05e-2
30000	6.40e-4	7.57e-4	1.14e-3	1.92e-3	3.34e-3	5.90e-3	1.10e-2	2.30e-2	3.47e-2	4.93e-2	5.72e-2	

Particle reflection coefficient of N backscattered from C

z1= 7, m1= 14.01, z2= 6, m2= 12.01, sbe = 7.41 eV, rho=2.26 g/cm**3
 ef=0.95 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr = 1 (KrC)
 program: trvmc
 ne= 2, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	50°	60°	70°	75°	80°	85°	87°
15000	3.93e-4	5.85e-4	1.27e-3	3.41e-3	9.43e-3	2.65e-2	7.02e-2	1.70e-1	2.60e-1	3.85e-1	6.07e-1	8.38e-1
30000	1.50e-4	2.68e-4	5.20e-4	1.69e-3	5.19e-3	1.63e-2	4.96e-2	1.39e-1	2.22e-1	3.44e-1	5.43e-1	

Energy reflection coefficient of N backscattered from C

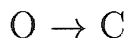
ne= 2, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	50°	60°	70°	75°	80°	85°	87°
15000	1.80e-5	3.33e-5	9.01e-5	3.36e-4	1.21e-3	4.58e-3	1.63e-2	5.61e-2	1.05e-1	1.96e-1	4.27e-1	7.34e-1
30000	6.75e-6	1.28e-5	3.71e-5	1.57e-4	6.28e-4	2.62e-3	1.08e-2	4.23e-2	8.25e-2	1.62e-1	3.48e-1	

Average depth (mean range) in Å of N implanted in C

ne= 2, na=12

B ₀ (eV)	0°	10°	20°	30°	40°	50°	60°	70°	75°	80°	85°	87°
15000	3.76e- -2	3.70e+2	3.54e+2	3.26e+2	2.90e+2	2.48e+2	2.04e+2	1.62e+2	1.45e+2	1.30e+2	1.20e+2	1.18e+2
30000	7.52e-f-2	7.43e+2	7.08e+2	6.53e- -2	5.80e- -2	4.92e+2	3.98e+2	3.11e+2	2.73e+2	2.43e+2	2.20e+2	



Sputtering yield of C by O

z1= 8, m1 = 16.00, z2= 6, m2= 12.01, sbe=7.41 eV, rho=1.85, 2.00 g/cm**3
 ef=0.95, 2.10 eV, esb=1.00, 2.60 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: trvmc95, newtrim
 only low fluence!
 ne=11, na=1

E ₀ (eV)	0°
38	4.60e-6
40	7.98e-6
42	1.30e-5
45	2.56e-5
50	6.56e-5
60	2.87e-4
70	7.79e-4
100	4.59e-3
150	1.80e-2
300	6.85e-2
1000	2.15e-1
3000	3.23e-1
6000	3.40e-1

Sputtered energj of C by O

only low fluence!
 ne= 7, na=1

E ₀ (eV)	0°
38	1.78e-7
40	3.17e-7
42	5.33e-7
45	1.09e-6
150	6.75e-4
300	2.06e-3
1000	4.15e-3
3000	3.34e-3
6000	2.67e-3

Particle reflection coefficient of O backscattered from C

z1= 8, m1 = 16.00, z2= 6, m2= 12.01, sbe=7.40 eV, 1.85, 2.00 g/cm**3
 ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: newtrim, trvmc95
 only low fluence!
 ne= 7, na=1

Eq (eV)	0°
38	9.90e-4
40	1.06e-3
42	1.12e-3
45	1.21e-3
150	9.89e-4
300	1.44e-3
1000	6.39e-4
3000	3.21e-4
6000	4.18e-4

Energy reflection coefficient of O backscattered from C

only low fluence!
 ne= 7, na=1

EO(eV)	0°
38	4.34e-5
40	4.53e-5
42	4.70e-5
45	4.92e-5
150	2.78e-5
300	3.60e-5
1000	2.42e-5
3000	1.60e-6
6000	5.00e-6

Average depth (mean range) in Å of O implanted in C

only low fluence!
 ne= 7, na=1

B ₀ (eV)	0°
38	3.54e+0
40	3.68e+0
42	3.82e+0
45	4.02e+0
150	8.68e+0
300	1.40e+1
1000	3.37e+1
3000	8.34e+1
6000	1.55e+2

Ne → C

Sputtering yield of C by Ne

z1=10, ml= 20.18, z2= 6, m2= 12.01, sbe=7.41, rho=1.85 g/cm**3

ef=0.05 eV, esb=0.00 eV, ca=1.00, kkO= kkOr=2, kdee1= kdee2= 3, ipot=ipotr=1 (KrC)

program : trvnic

ne=24, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
15					9.51e-7	7.53e-7			
16				1.17e-6	3.45e-6	2.15e-6			
17				3.60e-6	7.68e-6	5.34e-6	1.38e-6		
18				8.20e-6	1.40e-5	1.04e-5	3.60e-6	1.09e-6	
20			1.23e-6	4.15e-5	6.95e-5	5.65e-5	2.28e-5	5.44e-6	
22			2.86e-6	4.71e-5	7.73e-5	1.05e-4	6.48e-5	1.67e-5	6.67e-7
25		1.20e-7	2.32e-5	2.03e-4	3.48e-4	5.24e-4	2.64e-4	5.71e-5	1.05e-6
30		2.76e-6	1.03e-4	6.70e-4	1.64e-3	2.63e-3	1.09e-3	2.27e-4	3.53e-6
35	6.40e-7	9.52e-6	2.02e-4	1.86e-3	5.55e-3	7.95e-3	2.89e-3	5.45e-4	8.66e-6
40	3.74e-6	4.61e-5	6.93e-4	5.10e-3	1.19e-2	1.53e-2	5.10e-3	9.67e-4	1.62e-5
45	1.07e-5	9.47e-5	1.38e-3	1.03e-2	2.26e-2	2.68e-2	8.92e-3	1.64e-3	2.29e-5
50	3.41e-5	2.53e-4	2.99e-3	1.72e-2	3.35e-2	3.65e-2	1.21e-2	2.38e-3	3.57e-5
60	1.48e-4	8.44e-4	7.70e-3	3.81e-2	6.81e-2	7.16e-2	2.40e-2	4.43e-3	6.18e-5
70	4.59e-4	2.12e-3	1.47e-2	6.09e-2	9.95e-2	1.05e-1	3.80e-2	6.73e-3	9.62e-5
100	3.25e-3	9.87e-3	4.63e-2	1.47e-1	2.27e-1	2.36e-1	8.83e-2	1.73e-2	2.20e-4
140	1.18e-2	2.69e-2	9.44e-2	2.56e-1	3.93e-1	4.21e-1	1.75e-1	3.81e-2	4.74e-4
200	3.03e-2	5.61e-2	1.60e-1	3.87e-1	5.91e-1	6.63e-1	3.26e-1	8.21e-2	1.04e-3
300	6.50e-2	1.03e-1	2.46e-1	5.46e-1	8.32e-1	9.92e-1	6.04e-1	1.80e-1	2.72e-3
500	1.26e-1	1.80e-1	3.61e-1	7.43e-1	1.13e-0	1.47e-0	1.15e-0	4.59e-1	9.91e-3
1000	2.32e-1	2.99e-1	5.24e-1	9.98e-1	1.51e-0	2.09e-0	2.17e-0	1.31e-0	6.38e-2
2000	3.36e-1	4.09e-1	6.49e-1	1.18e-0	1.79e-0	2.63e-0	3.25e-0	2.69e-0	3.79e-1
5000	4.16e-1	4.90e-1	7.30e-1	1.25e-0	1.92e-0	2.99e-0	4.28e-0	4.54e-0	2.19e-0
10000	4.21e-1	4.84e-1	6.88e-1	1.13e-0	1.73e-0	2.82e-0	4.55e-0	5.31e-0	4.28e-0
20000	3.81e-1	4.28e-1	5.76e-1	8.83e-1	1.31e-0	2.19e-0	4.09e-0	5.32e-0	5.70e-0

Sputtered energy of C by Ne

ne=24, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
15					5.96e-8	7.77e-8			
16				6.16e-8	2.46e-7	2.17e-7			
17				1.87e-7	6.08e-7	6.25e-7	2.08e-7		
18				4.97e-7	1.25e-6	1.25e-6	5.86e-7	1.75e-7	
20			4.97e-8	3.04e-6	7.13e-6	8.10e-6	3.80e-6	8.81e-7	
22			1.36e-7	3.67e-6	8.39e-6	1.46e-5	1.06e-5	2.93e-6	1.55e-7
25		4.47e-9	1.20e-6	1.80e-5	4.22e-5	8.02e-5	4.83e-5	1.08e-5	1.99e-7
30		9.65e-8	6.20e-6	6.60e-5	2.29e-4	4.54e-4	2.21e-4	4.91e-5	6.28e-7
35	1.87e-8	4.36e-7	1.39e-5	2.16e-4	8.56e-4	1.55e-3	6.66e-4	1.28e-4	1.88e-6
40	1.31e-7	2.13e-6	5.38e-5	6.38e-4	1.96e-3	3.13e-3	1.18e-3	2.30e-4	3.31e-6
45	4.11e-7	4.81e-6	1.14e-4	1.36e-3	3.86e-3	5.73e-3	2.24e-3	4.11e-4	4.64e-6
50	1.29e-6	1.34e-5	2.59e-4	2.30e-3	5.81e-3	7.89e-3	3.05e-3	5.99e-4	6.96e-6
60	6.14e-6	4.69e-5	6.79e-4	5.26e-3	1.20e-2	1.60e-2	6.23e-3	1.13e-3	1.20e-5
70	1.90e-5	1.16e-4	1.30e-3	8.34e-3	1.74e-2	2.32e-2	9.82e-3	1.72e-3	1.76e-5
100	1.27e-4	5.28e-4	3.81e-3	1.85e-2	3.70e-2	4.85e-2	2.19e-2	4.25e-3	3.61e-5
140	4.34e-4	1.34e-3	6.98e-3	2.84e-2	5.59e-2	7.65e-2	4.02e-2	8.49e-3	6.73e-5
200	1.02e-3	2.46e-3	1.04e-2	3.66e-2	7.11e-2	1.01e-1	6.45e-2	1.66e-2	1.32e-4
300	1.95e-3	3.96e-3	1.35e-2	4.23e-2	7.96e-2	1.20e-1	9.74e-2	3.13e-2	2.86e-4
500	3.12e-3	5.51e-3	1.58e-2	4.54e-2	8.23e-2	1.31e-1	1.35e-1	6.33e-2	9.19e-4
1000	4.24e-3	6.71e-3	1.66e-2	4.33e-2	7.79e-2	1.27e-1	1.64e-1	1.18e-1	5.53e-3
2000	4.41e-3	6.52e-3	1.48e-2	3.66e-2	6.56e-2	1.12e-1	1.62e-1	1.53e-1	2.62e-2
5000	3.53e-3	5.13e-3	1.11e-2	2.76e-2	4.98e-2	8.85e-2	1.40e-1	1.54e-1	8.59e-2
10000	2.53e-3	3.62e-3	7.82e-3	1.92e-2	3.63e-2	6.70e-2	1.14e-1	1.34e-1	1.11e-1
20000	1.56e-3	2.21e-3	4.71e-3	1.14e-2	2.11e-2	4.12e-2	8.11e-2	1.03e-1	1.04e-1

Ar → C

Sputtering yield of C by Ar

z1=18, m1=39.95, z2=6, m2=12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=0.05 eV, esb=0.00 eV, ca=1.00, kk0=2, k0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: trvmc
 ne=11, na=9

E0(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
25			1.60e-7	1.88e-5	4.80e-5	4.12e-5	1.62e-5	4.00e-6	9.00e-8
30			4.44e-6	9.87e-5	1.94e-4	2.29e-4	1.32e-4	3.73e-5	7.10e-7
40	1.80e-7	2.52e-6	7.96e-5	6.71e-4	1.75e-3	3.40e-3	1.77e-3	3.74e-4	7.38e-6
50	2.46e-6	2.31e-5	4.18e-4	3.20e-3	8.55e-3	1.47e-2	6.49e-3	1.33e-3	2.33e-5
70	6.64e-5	3.67e-4	3.54e-3	2.00e-2	4.57e-2	6.11e-2	2.65e-2	5.31e-3	9.35e-5
100	8.27e-4	2.98e-3	1.76e-2	7.25e-2	1.40e-1	1.78e-1	7.67e-2	1.60e-2	2.73e-4
140	4.62e-3	1.18e-2	4.90e-2	1.63e-1	2.99e-1	3.76e-1	1.72e-1	3.94e-2	6.61e-4
200	1.66e-2	3.34e-2	1.05e-1	2.94e-1	5.21e-1	6.75e-1	3.46e-1	8.68e-2	1.53e-3
300	4.54e-2	7.57e-2	1.93e-1	4.70e-1	8.13e-1	1.10e-0	6.73e-1	1.96e-1	3.94e-3
500	1.09e-1	1.60e-1	3.34e-1	7.22e-1	1.19e-0	1.73e-0	1.34e-0	4.96e-1	1.31e-2
1000	2.47e-1	3.21e-1	5.68e-1	1.09e-0	1.72e-0	2.62e-0	2.75e-0	1.46e-0	6.94e-2

Sputtered energy of C by Ar

ne=11, na=9

E0 (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
25			4.77e-9	8.41e-7	3.12e-6	3.78e-6	1.94e-6	5.16e-7	1.06e-8
30			1.33e-7	5.68E-6	1.51E-5	2.36E-5	1.71E-5	5.05E-6	8.74E-8
40	3.51e-9	8.05e-8	3.44e-6	4.90E-5	1.74E-4	4.25E-4	2.68E-4	5.91E-5	9.55E-7
50	6.13e-8	7.95e-7	2.21E-5	2.75E-4	9.65E-4	2.08E-3	1.11E-3	2.30E-4	3.24E-6
70	1.97e-6	1.49E-5	2.21E-4	1.95E-3	5.58E-3	9.49E-3	4.83E-3	9.66E-4	1.27E-5
100	2.58E-5	1.26E-4	1.13E-3	6.98E-3	1.69E-2	2.73E-2	1.42E-2	2.86E-3	3.44E-5
140	1.37E-4	4.83E-4	2.99E-3	1.44E-2	3.33E-2	5.37E-2	3.01E-2	6.72E-3	7.14E-5
200	4.66E-4	1.25E-3	5.80E-3	2.30E-2	5.05E-2	8.38E-2	5.51E-2	1.38E-2	1.45E-4
300	1.15E-3	2.49E-3	9.21E-3	3.11E-2	6.54E-2	1.12E-1	9.01E-2	2.77E-2	3.09E-4
500	2.32E-3	4.28E-3	1.28E-2	3.77E-2	7.42E-2	1.31E-1	1.36E-1	5.75E-2	8.75E-4
1000	3.91E-3	6.30E-3	1.57E-2	4.13E-2	7.60E-2	1.35E-1	1.83E-1	1.17E-1	4.28E-3

Ar-» C

Particle reflection coefficient of Ar backscattered from C
 z1= 18, m1 = 39.95, z2= 6, m2= 12.01, sbe=7.41 eV, rho=1.85 g/cm**3
 ef=0.20 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: trvmc
 ne=14, na=8

E ₀ (eV)	15°	30°	45°	55°	65°	75°	80°	85°
10	2.76E-4	8.67E-3	1.14E-1	3.69E-1	7.42E-1	9.70E-1	9.97E-1	1.00E4-0
15	5.26E-5	5.43E-3	1.01E-1	3.56E-1	7.40E-1	9.73E-1	9.98E-1	1.00E+0
20	3.00E-5	4.27E-3	9.36E-2	3.48E-1	7.37E-1	9.73E-1	9.98E-1	1.00E+0
25	3.15E-5	3.75E-3	8.82E-2	3.38E-1	7.30E-1	9.74E-1	9.98E-1	1.00E-f-O
30	3.22E-5	3.41E-3	8.30E-2	3.27E-1	7.22E-1	9.73E-1	9.98E-1	1.00E+0
40	2.76E-5	2.84E-3	7.32E-2	3.05E-1	7.01E-1	9.71E-1	9.98E-1	1.00E+0
50	2.49E-5	2.35E-3	6.44E-2	2.82E-1	6.79E-1	9.67E-1	9.98E-1	1.00E-f-O
70	1.94E-5	1.66E-3	5.01E-2	2.42E-1	6.34E-1	9.58E-1	9.97E-1	1.00E-f-O
100	1.46E-5	1.11E-3	3.61E-2	1.94E-1	5.71E-1	9.43E-1	9.96E-1	1.00E-f-O
140	9.93E-6	8.47E-4	2.56E-2	1.49E-1	5.00E-1	9.19E-1	9.93E-1	1.00E-f-O
200	5.95E-6	5.96E-4	1.78E-2	1.09E-1	4.13E-1	8.77E-1	9.88E-1	1.00E-f-O
300	5.98E-6	4.49E-4	1.28E-2	7.68E-2	3.21E-1	8.09E-1	9.76E-1	1.00E-f-O
500	5.20E-6	3.45E-4	8.91E-3	5.10E-2	2.24E-1	6.88E-1	9.38E-1	1.00E-f-O
1000		2.61E-4	5.86E-3	3.15E-2	1.42E-1	4.97E-1	8.22E-1	9.98E-1

Energy reflection coefficient of Ar backscattered from C
 ne=14, na=8

E ₀ (eV)	15°	30°	45°	55°	65°	75°	80°	85°
10	8.53e-8	5.74E-5	4.06E-3	3.25E-2	1.52E-1	4.33E-1	6.15E-1	7.95E-1
15	2.32e-7	7.96E-5	4.74E-3	3.65E-2	1.67E-1	4.64E-1	6.49E-1	8.25E-1
20	3.17e-7	8.79E-5	4.97E-3	3.85E-2	1.75E-1	4.83E-1	6.72E-1	8.45E-1
25	3.71e-7	8.70E-5	4.99E-3	3.90E-2	1.79E-1	4.97E-1	6.88E-1	8.58E-1
30	3.86e-7	8.21E-5	4.85E-3	3.88E-2	1.81E-1	5.06E-1	7.01E-1	8.68E-1
40	3.01e-7	6.83E-5	4.39E-3	3.73E-2	1.80E-1	5.17E-1	7.18E-1	8.83E-1
50	2.51e-7	5.46E-5	3.87E-3	3.50E-2	1.78E-1	5.23E-1	7.29E-1	8.94E-1
70	1.69e-7	3.51E-5	2.94E-3	3.00E-2	1.68E-1	5.25E-1	7.42E-1	9.08E-1
100	1.01e-7	2.01E-5	1.97E-3	2.35E-2	1.50E-1	5.18E-1	7.49E-1	9.20E-1
140	6.53e-8	1.27E-5	1.26E-3	1.71E-2	1.30E-1	5.01E-1	7.49E-1	9.28E-1
200	2.95e-8	7.88E-6	7.44E-4	1.17E-2	1.03E-1	4.69E-1	7.42E-1	9.34E-1
300	2.92e-8	5.17E-6	4.61E-4	7.09E-3	7.39E-2	4.18E-1	7.19E-1	9.38E-1
500	1.39e-8	3.60E-6	2.78E-4	3.86E-3	4.49E-2	3.32E-1	6.64E-1	9.37E-1
1000		2.68e-6	1.59E-4	1.91E-3	2.25E-2	2.08E-1	5.35E-1	9.25E-1

Average depth (mean range of Ar implanted in C)
 ne=14, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	1.30E+0	1.30E4-0	1.10E-f-0	9.00E-1	8.00E-1	6.00E-1	5.00E-1	4.00E-1	2.00E-1
15	2.00E4-0	1.90E-J-0	1.70E4-0	1.30E+0	1.10E-f-0	8.00E-1	6.00E-1	5.00E-1	3.00E-1
20	2.60E-J-0	2.50E-J-0	2.10E+0	1.60E+0	1.30E-J-0	1.00E-f-O	8.00E-1	6.00E-1	5.00E-1
25	3.10E+0	3.00E+0	2.60E+0	2.00E+0	1.60E+0	1.20E-J-0	9.00E-1	7.00E-1	5.00E-1
30	3.60E4-0	3.50E+0	3.00E+0	2.20E+0	1.80E4-0	1.40E4-0	1.10E-f-0	9.00E-1	6.00E-1
40	4.50E-J-0	4.30E+0	3.70E4-0	2.80E+0	2.20E4-0	1.70E+0	1.30E+0	1.10E+0	8.00E-1
50	5.20E+0	5.00E4-0	4.30E+0	3.30E+0	2.60E4-0	2.00E+0	1.60E-J-0	1.30E4-0	9.00E-1
70	6.50E+0	6.20E-J-0	5.40E-J-0	4.10E+0	3.30E+0	2.60E+0	2.00E4-0	1.70E4-0	1.10E+0
100	8.10E+0	7.80E+0	6.80E+0	5.20E4-0	4.20E-J-0	3.30E-J-0	2.50E-J-0	2.20E4-0	1.70E+0
140	1.00E-f-1	9.60E+0	8.40E+0	6.50E4-0	5.20E+0	4.10E+0	3.20E+0	2.70E4-0	2.30E4-0
200	1.23E+1	1.18E4-1	1.04E+1	8.20E-J-0	6.50E4-0	5.10E+0	4.00E+0	3.40E+0	2.80E-I-0
300	1.56E+1	1.50E-J-1	1.32E-J-1	1.05E4-1	8.40E+0	6.60E4-0	5.20E+0	4.50E4-0	3.50E+0
500	2.10E+1	2.02E-J-1	1.79E-f-1	1.43E+1	1.15E+1	9.00E+0	7.00E+0	6.20E+0	5.40E4-0
1000	3.16E4-1	3.05E-J-1	2.72E4-1	2.19E+1	1.78E-J-1	1.38E+1	1.06E+1	9.40E4-0	7.20E+0

Ar → C

Sputtering yield of C by Ar

z1 = 18, m1 = 39.95, z2 = 6, m2 = 12.01, sbe = 7.40, 7.42 eV, rho = 2.26 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trspvmcx
 ne = 9, na = 1

E ₀ (eV)	0°
100	8.51E-4
100	8.60e-4
200	1.80e-2
300	4.96E-2
500	1.23E-1
500	1.20e-1
1000	2.64E-1
1000	2.67e-1
4000	6.32E-1

Sputtered energy of C by Ar

ne = 9, na = 1

E ₀ (eV)	0°
100	2.65E-5
100	2.67e-5
200	4.92e-4
300	1.24E-3
500	2.55E-3
500	2.49e-3
1000	4.09E-3
1000	4.07e-3
4000	4.95E-3

Average depth (mean range) in Å of Ar implanted in C

z1 = 18, m1 = 39.95, z2 = 6, m2 = 12.01, sbe = 7.40, 7.42 eV, rho = 2.26 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trspvmcx
 ne = 7, na = 1

E ₀ (eV)	0°
50	3.82e+0
100	6.20E+0
200	9.61e4-0
300	1.23E+1
500	1.67E+1
1000	2.55E4-1
4000	6.28E+1

Ar → C

Sputtering yield of C by Ar

z1=18, m1 = 39.95, z2= 6, m2= 12.01, sbe=7.40, rho=2.26 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot
 alpha=0.00
 program : trspvmcx
 ne= 4, n(ipot) = 3

B ₀ (eV)	KrC	Moliere	ZBL	comment
5000	6.83B-1	7.58e-1	6.70e-1	
5000	1.12e-0			sbe=4.40 eV
5000	1.04e-0			sbe=4.40 eV, rho=1.85 g/cm**3
5000	6.24e-1			rho=1.85 g/cm**3

Sputtered energy of C by Ar

ne= 4, n(ipot)= 3

Bo (eV)	KrC	Moliere	ZBL	comment
5000	4.98B-3	4.57e-3	5.26e-3	
5000	5.68e-3			sbe=4.40 eV
5000	5.69e-3			sbe=4.40 eV, rho = 1.85 g/cm**3
5000	4.66e-3			rho=1.85 g/cm**3

Average depth (mean range) in Å of Ar implanted in C

ne= 4, n(ipot)= 3

B ₀ (eV)	KrC	Moliere	ZBL	comment
5000	7.41E+1	6.00e4-1	7.51e+1	
5000	7.37e+1			sbe=4.40 eV
5000	9.05e+1			sbe=4.40 eV, rho=1.85 g/cm**3
5000	9.10e+1			rho = 1.85 g/cm**3

Xe -> C

Sputtering yield of C by Xe
 z1=54, m1 = 131.30, z2= 6, m2= 12.01, sbe=7.42, 7.40 eV, rho=2.26 g/cm**3
 ef=0.50, esb= 0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx, trspvmcx
 ne=45, na=11

E ₀ (eV)	0°	15°	30°	45°	60°	65°	70°	75°	77.5°	80°	85°
53								2.97e-6			
55				4.38e-6						2.34e-6	
56								1.01e-5			
59										1.00e-5	
60				1.71e-5				4.08e-5			
61										1.60e-5	
63										2.72e-5	
65				4.06e-5				1.25e-4		4.49e-5	
70			3.19e-6	8.01e-5				3.65e-4		1.23e-4	
75			7.66e-6	1.48e-4				8.80e-4		2.85e-4	
77								1.24e-3			
80			1.60e-5	2.18e-4				1.84e-3		5.67e-4	
85			3.35e-5								
90		2.12e-6	5.10e-5	5.44e-4				5.63e-3		1.61e-3	
95			7.92e-5								
100		6.33e-6	1.29e-4	1.15e-3				1.22e-2		3.42e-3	
105		1.00e-5									
110	1.86e-6	1.76e-5	2.68e-4							6.16e-3	
120	5.62e-6	3.88e-5	5.37e-4	4.26e-3	2.20e-2	3.47e-2	4.57e-2	3.70e-2		1.07e-2	
130	1.22e-5	7.48e-5	8.54e-4							1.52e-2	
135			1.19e-3								
140	2.22e-5	1.36e-4	1.49e-3	1.06e-2							
150	4.50e-5	2.33e-4	2.40e-3	1.55e-2	6.74e-2	1.04e-1	1.29e-1	1.02e-1		2.86e-2	
160		3.82e-4									
170	1.24e-4		5.04e-3	2.79e-2				1.62e-1		4.69e-2	
180	1.89e-4	8.74e-4									
190		1.20e-3									
200	4.15e-4	1.62e-3	1.04e-2	5.21e-2	1.89e-1	2.66e-1	3.33e-1	2.74e-1	1.80e-1	8.12e-2	
220	8.08e-4	2.64e-3									
230	1.11e-3										
250	1.70e-3	5.30e-3	2.60e-2	1.06e-1				5.02e-1		1.54e-1	
300	4.24e-3	1.07e-2	4.56e-2	1.63e-1				7.67e-1		2.46e-1	
300	3.89e-3										
500	2.76e-2	5.31e-2	1.52e-1	3.99e-1	1.00e-0		1.83e-0	1.82e-0		6.97e-1	
500	3.00e-2										
700	6.71e-2										
1000	1.27e-1	1.86e-1	3.93e-1	8.39e-1	1.79e-0		3.23e-0	3.82e-0		2.07e-0	
1000	1.28e-1										
2000	3.25e-1										
3000	4.66e-1	6.00e-1	9.81e-1	1.77e-0	3.43e-0		5.92e-0	7.98e-0		7.42e-0	
4000	5.99e-1										
7000	8.50e-1										
10000	1.02e-0	1.19e-0	1.80e-0	3.04e-0	5.47e-0			1.25e+1		1.62e+1	6.77e-0
30000	1.46e-0	1.73e-0	2.43e-0	3.88e-0				1.60e-1		2.28e+1	
100000	1.69e-0	1.89e-0	2.53e-0	3.73e-0				1.50e-1		2.45e+1	

Xe → C

Sputtered energy of C by Xe

z1=54, m1 = 131.30, z2= 6, m2= 12.01, sbe=7.42 eV, rho=2.26 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kk0=kk0r=2, kdeel=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=44, na=11

Eo(eV)	0°	15°	30°	45°	60°	65°	70°	75°	77.5°	80°	85°
53								1.43e-7			
55				8.12e-8						1.30e-7	
56								4.88e-7			
59										5.64e-7	
60				3.33e-7				1.93e-6			
61										9.02e-7	
63										1.41e-6	
65				8.63e-7				6.25e-6		2.32e-6	
70			1.40e-7	1.80e-6				1.78e-5		6.69e-6	
75			2.22e-7	3.52e-6				4.68e-5		1.57e-5	
77								6.66e-5			
80			2.76e-7	6.47e-6				9.94e-5		3.18e-5	
85			6.40e-7								
90		1.05e-7	9.27e-7	1.54e-5				3.22e-4		9.78e-5	
95			1.47e-6								
100		2.68e-7	2.47e-6	3.43e-5				7.32e-4		2.25e-4	
105		5.28e-7									
110	1.50e-7	3.33e-7	5.54e-6							3.95e-4	
120	2.12e-7	9.82e-7	1.18e-5	1.62e-4	1.09e-3	1.84e-3	2.67e-3	2.40e-3		7.29e-4	
130	2.48e-7	1.80e-6	1.94e-5							1.05e-3	
135			2.61e-5								
140	6.15e-7	2.29e-6	3.58e-5	3.88e-4							
150	1.27e-6	4.03e-6	5.97e-5	5.73e-4	3.42e-3	5.73e-3	7.81e-3	6.91e-3		2.01e-3	
160		6.92e-6									
170	1.72e-6		1.29e-4	1.06e-3				1.10e-2		3.32e-3	
180	2.80e-6	1.55e-5									
190		2.09e-5									
200	5.65e-6	2.88e-5	2.76e-4	1.98e-3	9.74e-3	1.48e-2	2.03e-2	1.89e-2	1.30e-2	5.84e-3	
220	1.09e-5	4.56e-5									
230	1.50e-5										
250	2.28e-5	9.45e-5	6.93e-4	3.95e-3				3.36e-2		1.11e-2	
300	5.51e-5	1.88e-4	1.15e-3	5.90e-3				5.07e-2		1.72e-2	
300	5.21e-5										
500	3.36e-4	8.22e-4	3.40e-3	1.23e-2	4.01e-2		8.76e-2	1.01e-1		4.41e-2	
500	3.47e-4										
700	7.23e-4										
1000	1.20e-3	2.23e-3	6.86e-3	2.00e-2	5.48e-2		1.13e-1	1.54e-1		1.03e-1	
2000	2.36e-3										
3000	2.91e-3	4.22e-3	1.02e-2	2.58e-2	6.31e-2		1.22e-1	1.77e-1		2.03e-1	
4000	3.10e-3										
7000	3.48e-3										
10000	3.43e-3	5.09e-3	1.14e-2	2.75e-2	6.44e-2			1.67e-1		2.30e-1	1.24e-1
30000	3.05e-3	4.94e-3	1.04e-2	2.54e-2				1.56e-1		2.16e-1	
100000	2.19e-3	2.99e-3	7.14e-3	1.71e-2				1.21e-1		1.82e-1	

Xe -> C

Particle reflection coefficient of Xe backscattered from C
 z1=54, IX11=131.30, z2= 6, m2= 12.01, sbe=7.42 eV, rho=2.26 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 program: testvmcx
 ne=38, na=11

E ₀ (eV)	0°	15°	30°	45°	60°	65°	70°	75°	77.5°	80°	85°
53								9.13e-1			
55				1.90e-5						9.97e-1	
56								9.11e-1			
59										9.97e-1	
60				1.90e-5				9.09e-1			
61										9.97e-1	
63										9.97e-1	
65				1.91e-5				9.05e-1		9.97e-1	
70				1.89e-5				9.02e-1		9.96e-1	
75				1.83e-5				8.98e-1		9.96e-1	
77								8.97e-1			
80			9.40e-6	1.95e-5				8.94e-1		9.96e-1	
85			8.18e-6								
90		8.91e-6	7.17e-6	1.80e-5				8.87e-1		9.96e-1	
95			7.55e-6								
100		8.43e-6	7.63e-6	1.75e-5				8.79e-1		9.95e-1	
105		8.95e-6									
110	8.72e-6	8.22e-6	1.00e-5							9.95e-1	
120	7.67e-6	8.33e-6	8.67e-6	2.00e-5	2.36e-2	1.43e-1	4.79e-1	8.64e-1		9.94e-1	
130	7.95e-6	7.20e-6	7.33e-6							9.94e-1	
135			7.00e-6								
140	6.91e-6	7.80e-6	8.00e-6	1.50e-5							
150	1.04e-5	9.40e-6	1.69e-5	2.00e-5	1.90e-2	1.21e-1	4.33e-1	8.41e-1		9.93e-1	
160		1.00e-5									
170	9.50e-6							8.24e-1		9.91e-1	
180	8.88e-6	8.00e-6									
190		4.00e-6									
200	7.50e-6	7.00e-6		3.00e-5	1.31e-2	9.55e-2	3.70e-1	7.98e-1	9.34e-1	9.90e-1	
220	6.67e-6										
230	6.00e-6										
250	7.00e-6							7.58e-1		9.86e-1	
300	6.00e-6			3.00e-5				7.23e-1		9.80e-1	
500					5.90e-3		1.86e-1	5.85e-1		9.54e-1	
1000					4.60e-3		9.86e-2	3.73e-1		8.62e-1	
3000					2.90e-3		4.56e-2	1.65e-1		5.52e-1	
10000					8.00e-4			8.80e-2		2.79e-1	8.35e-1
30000								5.84e-2		1.84e-1	
100000								4.12e-2		1.32e-1	

Energy reflection coefficient of Xe backscattered from C
 ne=38, na=11

E ₀ (eV)	0°	15°	30°	45°	60°	65°	70°	75°	77.5°	80°	85°
53								2.90e-1			
55				3.65e-6						5.72e-1	
56								2.91e-1			
59										5.75e-1	
60				7.12e-6				2.91e-1			
61										5.77e-1	
63										5.78e-1	
65				4.02e-6				2.92e-1		5.80e-1	
70			1.12e-5	2.89e-6				2.92e-1		5.83e-1	
75			2.91e-6	2.02e-6				2.92e-1		5.85e-1	
77								2.91e-1			
80			2.28e-6	3.06e-6				2.91e-1		5.88e-1	
85			4.10e-6								
90		1.89e-6	1.87e-6	1.81e-6				2.90e-1		5.92e-1	
95			1.48e-6								
100		1.68e-6	1.17e-6	8.03e-7				2.88e-1		5.95e-1	
105		1.57e-6									
110	3.97e-5	1.43e-6	9.10e-7							5.97e-1	
120	1.56e-6	1.62e-6	1.50e-6	6.82e-7	9.38e-4	1.13e-2	7.71e-2	2.85e-1		5.99e-1	
130	4.76e-6	1.07e-6	8.06e-6							6.00e-1	
135			6.46e-7								
140	1.17e-6	9.65e-7	6.08e-7	5.91e-7							
150	6.42e-6	6.33e-6	3.29e-6	4.26e-6	6.77e-4	9.15e-3	6.91e-2	2.75e-1		6.02e-1	
160		2.24e-6									
170	2.54e-6							2.70e-1		6.03e-1	
180	4.36e-6	1.54e-6									
190		9.00e-7									
200	1.40e-6	9.07e-7		5.42e-6	4.15e-4	6.93e-3	5.79e-2	2.60e-1	4.25e-1	6.02e-1	
220	1.24e-6										
230	2.84e-6										
250	7.98e-7							2.43e-1		5.98e-1	
300	1.99e-6			2.14e-7				2.27e-1		5.93e-1	
500					9.16e-5		2.41e-2	1.73e-1		5.59e-1	
1000					6.43e-5		8.45e-3	9.15e-2		4.67e-1	
3000					2.77e-5		2.00e-3	2.28e-2		2.32e-1	
10000					1.50e-6			7.71e-3		7.39e-2	6.11e-1
30000								4.67e-3		3.35e-2	
100000								3.32e-3		2.35e-2	

Xe -> C

Average depth (mean range) of Xe implanted in C
 z1= 54, m1= 131.30, z2= 6, m2= 12.01, sbe=7.42 eV, rho= 2.26 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kk0=kk0r=2, kdec1=kdec2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 43, na=11

Bq (eV)	0°	15°	30°	45°	60°	65°	70°	75°	77.5°	80°	85°
50	1.20e+1										
53								2.48e+0			
55				8.24e+0						2.12e+0	
56								2.55e+0			
59										2.21e+0	
60				8.57e+0				2.65e4-0			
61										2.25e+0	
63										2.29e4-0	
65				8.89e-f-0				2.76e+0		2.35e+0	
70			1.18e+1	9.19e+0				2.87e+0		2.44e+0	
75			1.21e4-1	9.47e+0				2.98e+0		2.52e+0	
77											
80			1.25e+1	9.75e+0				3.08e+0		2.61e+0	
85			1.28e4-1								
90		1.49e+1	1.31e+1	1.03e+1				3.28e4-0		2.82e+0	
95			1.34e+1								
100	1.62e+1	1.55e+1	1.37e+1	1.07e+1				3.45e+0		3.01e+0	
105											
110	1.68e+1	1.62e+1								3.10e+0	
120	1.74e+1	1.68e+1	1.48e+1	1.16e+1	7.21e+0	5.70e+0	4.54e4-0	3.76e+0		3.30e+0	
130	1.80e+1	1.73e+1	1.53e+1							3.29e+0	
135			1.56e+1								
140	1.86e4-1	1.79e+1	1.58e+1	1.24e+1							
150	1.91e+1	1.84e+1		1.28e+1	8.03e-J-0	6.36e4-0	5.05e+0	4.16e+0		3.53e+0	
160		1.89e+1									
170	2.01e+1		1.71e+1	1.35e+1				4.44e+0		3.86e4-0	
180	2.06e+1	1.98e+1									
190		2.03e+1									
200	2.15e-f-1	2.07e+1	1.84e4-1	1.45e+1	9.20e+0	7.27e+0	5.80e+0	4.80e+0	4.42e+0	4.20e+0	
220		2.15e+1									
230	2.28e+1										
250	2.36e+1	2.27e+1	2.01e+1	1.59e+1				5.28e+0		4.54e+0	
300	2.54e+1	2.45e+1	2.17e+1	1.73e4-1				5.75e+0		4.98e+0	
500	3.14e+1	3.02e+1	2.69e+1	2.14e+1	1.41e-H		8.97e+0	7.25e4-0		6.29e+0	
700	3.61e4-1										
1000	4.20e+1	4.05e+1	3.61e+1	2.91e+1	1.95e+1		1.26e+1	1.01e+1		8.26e4-0	
2000	5.69e+1										
3000	6.84e+1	6.62e+1	5.90e+1	4.79e+1	3.30e+1		2.21e+1	1.73e+1		1.41e+1	
4000	7.85e+1										
7000	1.03e+2										
10000	1.24e+2	1.20e+2	1.08e+2	8.80e+1	6.12e+1			3.34e+1		2.56e+1	2.09e+1
30000	2.33e+2	2.24e+2	2.01e+2	1.64e+2				6.23e+1		4.77e+1	
100000	5.17e+2	5.05e+2	4.51e+2	3.68e+2				1.39e+2		1.06e+2	

D -4 Al

Sputtering yield of Al by D

z1 = 1, m1 = 2.01, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx
 ne = 5, na = 1

Ep(eV)	0°
40	7.55e-3
300	4.15e-2
1000	3.91e-2
3000	2.87e-2
10000	1.33e-2

Sputtered energy of Al by D
 ne = 5, na = 1

E ₀ (eV)	0°
40	3.33e-4
300	1.07e-3
1000	4.64e-4
3000	1.63e-4
10000	2.46e-5

Particle reflection coefficient of D backscattered from Al

z1 = 1, m1 = 2.01, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx
 ne = 5, na = 1

Eq(eV)	0°
40	4.24e-1
300	2.96e-1
1000	2.04e-1
3000	1.08e-1
10000	3.06e-2

Energy reflection coefficient of D backscattered from Al
 ne = 5, na = 1

E ₀ (eV)	0°
40	2.14e-1
300	1.32e-1
1000	8.23e-2
3000	3.67e-2
10000	8.39e-3

Average depth (mean range) in Å of D implanted in Al
 ne = 5, na = 1

E ₀ (eV)	0°
40	2.17e+1
300	9.32e+1
1000	2.52e+2
3000	6.66e+2
10000	1.95e+3

He -> Al

Sputtering yield of Al by He

z1 = 2, m1 = 4.00, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
program: trspvmcx, TPP 9/82
ne = 13, na = 1

E ₀ (eV)	0°
15	1.83e-4
20	2.83e-3
30	1.46e-2
40	2.97e-2
50	4.20e-2
70	6.24e-2
100	8.64e-2
300	1.49e-1
500	1.62e-1
1000	1.63e-1
5000	1.10e-1
10000	7.62e-2
30000	3.47e-2

Sputtered energy of Al by He

program: trspvmcx
ne = 13, na = 1

B ₀ (eV)	0°
15	7.37e-6
20	1.50e-4
30	9.58e-4
40	1.98e-3
50	2.74e-3
70	3.77e-3
100	4.38e-3
300	4.42e-3
500	3.48e-3
1000	2.45e-3
5000	5.37e-4
10000	1.95e-4
30000	3.63e-5

He → Al

Particle reflection coefficient He backscattered from Al
 z1 = 2, m1 = 4.00, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trspvmcx
 ne = 13, na = 1

E ₀ (eV)	0°
15	4.86e-1
20	4.51e-1
30	4.04e-1
40	3.73e-1
50	3.59e-1
70	3.33e-1
100	3.12e-1
300	2.44e-1
500	2.17e-1
1000	1.79e-1
5000	8.30e-2
10000	4.94e-2
30000	1.38e-2

Energy reflection coefficient of He backscattered from Al
 ne = 13, na = 1

E ₀ (eV)	0°
15	2.15e-1
20	1.95e-1
30	1.69e-1
40	1.53e-1
50	1.45e-1
70	1.31e-1
100	1.21e-1
300	9.05e-2
500	7.82e-2
1000	6.10e-2
5000	2.46e-2
10000	1.36e-2
30000	3.16e-3

Average depth (mean range) in Å of He implanted in Al
 ne = 13, na = 1

B ₀ (eV)	0°
15	6.59e+0
20	7.83e+0
30	1.01e4-1
40	1.21e+1
50	1.39e+1
70	1.73e+1
100	2.20e+1
300	4.85e+1
500	7.18e+1
1000	1.26e+2
5000	5.35e+2
10000	1.01e+3
30000	2.72e+3

Ne → Al

Sputtering yield of Al by Ne
 z1 = 10, m1 = 20.18, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: IPP 9/82
 ne = 14, na = 1

E ₀ (eV)	0°
20	2.40e-4
30	4.46e-3
50	3.90e-2
100	1.74e-1
200	3.85e-1
500	6.92e-1
1000	9.17e-1
2000	1.06e-0
5000	1.13e-0
10000	1.09e-0
20000	9.71e-1
50000	7.64e-1
100000	5.53e-1
200000	4.12e-1

Al -4- Al

Sputtering yield of Al by Al

z1=13, m1= 26.98, z2=13, m2= 26.98, sbe=3.36 eV, rho=2.70 g/cm**3
 ef=3.30 eV, esb=3.36 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipottr=1 (KrC)
 program: trspvmcx
 ne= 6, na=1

MeV)	0°
40	1.16e-2
80	8.75e-2
200	3.46e-1
500	7.22e-1
50000	1.04e-0
100000	7.92e-1

Sputtered energy of Al by Al

ne= 6, na=1

E ₀ (eV)	0°
40	6.10e-4
80	3.31e-3
200	9.10e-3
500	1.15e-2
50000	1.43e-3
100000	6.57e-4

Particle reflection coefficient of Al backscattered from Al

z1=13, m1= 26.98, z2=13, m2= 26.98, sbe=3.36 eV, rho=2.70 g/cm**3
 ef=3.30 eV, esb=3.36 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipottr=1 (KrC)
 program: trspvmcx
 ne= 6, na=1

E ₀ (eV)	0°
40	1.28e-3
80	5.60e-3
200	9.40e-3
500	1.54e-2
50000	1.50e-3
100000	5.00e-4

Energy reflection coefficient of Al backscattered from Al

ne= 6, na=1

E ₀ (eV)	0°
40	9.42e-5
80	3.39e-4
200	4.41e-4
500	6.12e-4
50000	8.67e-5

Average depth (mean range) in Å of Al implanted in Al

ne= 6, na=1

E ₀ (eV)	0°
40	4.04e+0
80	6.34e+0
200	1.12e+1
500	1.98e+1
50000	7.33e+2
100000	1.46e+3

Al -> Al

Sputtering yield of Al by Al

z1 = 13, m1 = 26.98, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
 ef = 3.30 eV, esb = 3.36 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 2 (Moliere)
 program: trspvmex
 ne = 11, na = 1

E ₀ (eV)	0°
40	1.61e-2
60	6.88e-2
80	1.43e-1
200	5.88e-1
500	1.16e-0
1000	1.56e-0
5000	1.91e-0
10000	1.76e-0
20000	1.55e-0
50000	1.14e-0
100000	9.67e-1

Sputtered energy of Al by Al

ne=11, na=1

Ep(eV)	$\bar{\epsilon}^{75}$
40	9.29e-4
60	3.42e-3
80	6.39e-3
200	1.55e-2
500	1.81e-2
1000	1.56e-2
5000	7.29e-3
10000	4.75e-3
20000	2.81e-3
50000	1.27e-3
100000	6.13e-4

Particle reflection coefficient of Al backscattered from Al

z1 = 13, m1 = 26.98, z2 = 13, m2 = 26.98, sbe = 3.36 eV, rho = 2.70 g/cm**3
 ef = 3.30 eV, esb = 3.36 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 2 (Moliere)
 program: trspvmex
 ne = 11, na = 1

E ₀ (eV)	0°
40	1.03e-3
60	3.35e-3
80	6.70e-3
200	1.45e-2
500	1.44e-2
1000	1.20e-2
5000	7.00e-3
10000	3.33e-3
20000	2.00e-3
50000	8.00e-4

Energy reflection coefficient of Al backscattered from Al

ne=11, na=1

E ₀ (eV)	0°
40	7.51e-5
60	2.47e-4
80	4.33e-4
200	7.47e-4
500	5.34e-4
1000	5.39e-4
5000	3.29e-4
10000	1.88e-4
20000	1.50e-4
50000	3.51e-5

Average depth (mean range) in Å of Al implanted in Al

ne=11, na=1

E ₀ (eV)	0°
40	2.33e+0
60	3.21e+0
80	4.03e+0
200	7.52e+0
500	1.43e+1
1000	2.28e+1
5000	8.26e+1
10000	1.51e+2
20000	2.89e+2
50000	7.09e+2
100000	1.43e+3

Ar → Al

Sputtering yield of Al by Ar

z1 = 18, m1 = 39.95, z2 = 13, m2 = 26.98, sbe=3.36 eV, rho=2.70 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: TPP 9/82, trslc, trvmc95c
 ne=18, na=4

E ₀ (eV)	0°	30°	60°	85°
30	5.10e-4			
50	1.09e-2			
100	9.72e-2			
100	1.17e-1	3.78e-1	6.67e-1	1.93e-3
200	3.10e-1			
500	7.38e-1			
500	9.10e-1	1.58e-0	2.99e-0	3.71e-2
1000	1.08e-0			
1000	1.37e-0	2.21e-0	4.57e-0	1.43e-1
1000	1.10e-0			
2000	1.40e-0			
5000	1.73e-0			
10000	1.87e-0			
10000	2.39e-0	3.54e-0	9.08e-0	6.53e-0
20000	1.87e-0			
50000	1.69e-0			
100000	1.45e-0			
200000	1.18e-0			

Sputtered energy of Al by Ar

program: trslc, trvmc95c
 ne = 5, na=4

E ₀ (eV)	0°	30°	60°	85°
100	3.67e-3	2.48e-2	9.43e-2	1.45e-4
500	1.33e-2	3.97e-2	1.61e-1	1.10e-3
1000	1.38e-2	3.67e-2	1.54e-1	3.74e-3
1000	1.16e-2			
10000	7.29e-3	1.86e-2	9.11e-2	1.07e-1

Particle reflection coefficient of Ar backscattered from Al

z1 = 18, m1 = 39.95, z2 = 13, m2 = 26.98, sbe=3.36 eV, rho=2.70 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: trslc, trvmc95c
 ne = 5, na=4

Bo (eV)	0°	30°	60°	85°
100	3.14e-3	5.72e-2	5.67e-1	1.00e-0
500	2.32e-3	2.52e-2	3.01e-1	1.00e-0
1000	2.18e-3	1.84e-2	2.24e-1	9.99e-1
1000	2.80e-3			
10000	9.20e-4	7.47e-3	1.07e-1	8.01e-1

Energy reflection coefficient of Ar backscattered from Al

ne = 5, na=4

Ro (eV)	0°	30°	60°	85°
100	6.99e-5	4.38e-3	1.88e-1	9.42e-1
500	3.83e-5	1.38e-3	8.07e-2	9.53e-1
1000	3.62e-5	9.37e-4	5.17e-2	9.43e-1
1000	1.33e-5			
10000	2.10e-5	4.47e-4	2.06e-2	6.39e-1

Average depth (mean range) in Å of Ar implanted in Al

ne = 5, na=4

Ro (eV)	0°	30°	60°	85°
100	5.32e-j-0	4.55e+0	3.07e+0	1.20e+0
500	1.42e+1	1.23e+1	8.36e+0	4.42e+0
1000	2.16e+1	1.88e+1	1.26e+1	6.84e+0
1000	2.90e+1			
10000	1.05e+2	9.11e+1	5.89e+1	3.71e+1

H -> Si

Sputtering yield of Si by H

z1= 1, m1= 1.01, z2= 14, m2= 28.09, sbe=4.70, rho=2.33 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc95, IPP 9/82
 ne=11, na= 1

Eo (eV)	0°
50	5.23e-5
60	3.60e-4
70	8.90e-4
100	2.40e-3
200	7.60e-3
300	9.57e-3
500	1.10e-2
1000	1.05e-2
2000	9.00e-3
5000	5.50e-3
10000	3.60e-3

Sputtered energy of Si by H

program : trvmc95
 ne= 2, na= 1

Ep(eV)	(T)
50	5.16e-7
300	2.01e-4

Particle reflection coefficient of H backscattered from Si

z1= 1, m1= 1.01, z2= 14, m2= 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc95
 ne= 2, na= 1

Eo(eV)	" 0°
50	4.65e-1
300	3.35e-1

Energy reflection coefficient of H backscattered from Si

ne= 2, na= 1

Eo (eV)	0°
50	2.53e-1
300	1.58e-1

Average depth (mean range) in Å of H implanted in Si

ne= 2, na= 1

B _a (eV)	0°
50	3.33e+1
300	1.12e+2

D -> Si

Sputtering yield of Si by D

z1= 1, m1= 2.01, z2= 14, m2= 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program : trvmc95, trspvmcx. IPP 9/82
 ne=10, na= 9

EO(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
25	1.90e-6	8.25e-3	1.11e-2	1.57e-2	1.87e-2	1.85e-2	1.08e-2	5.51e-3	2.51e-3
27	2.82e-5								
30	1.52e-4	1.22e-2	1.69e-2	2.54e-2	3.25e-2	3.46e-2	2.07e-2	1.02e-2	3.82e-3
50	3.09e-3	2.40e-2	3.45e-2	5.78e-2	8.53e-2	1.07e-1	7.40e-2	3.23e-2	7.37e-3
100	1.15e-2	3.59e-2	5.42e-2	9.78e-2	1.49e-1	2.13e-1	2.00e-1	1.01e-1	1.27e-2
200	2.03e-2	4.03e-2	6.32e-2	1.14e-1	1.77e-1	2.68e-1	3.42e-1	2.43e-1	2.93e-2
500	2.48e-2	3.85e-2	5.82e-2	1.04e-1	1.59e-1	2.57e-1	4.08e-1	4.39e-1	1.38e-1
1000	2.36e-2	2.96e-2	4.37e-2	7.80e-2	1.25e-1	2.06e-1	3.65e-1	4.59e-1	3.34e-1
2000	1.96e-2								
5000	1.22e-2								

Sputtered energy of Si by D

program : trvmc95
 ne= 2, na= 1

MeV)	O ^s
25	1.67e-8
27	3.28e-7

Particle reflection coefficient of D backscattered from Si

z1= 1, m1= 2.01, z2= 14, m2= 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trvmc95
 ne= 3, na= 1

E ₀ (eV)	0°
20	4.64e-1
25	4.51e-1
27	4.47e-1

Energy reflection coefficient of D backscattered from Si

ne= 3, na= 1

E ₀ (eV)	0°
20	2.44e-1
25	2.34e-1
27	2.31e-1

Average depth (mean range) in Å of D implanted in Si

ne= 3, na= 1

EO(eV)	0°
20	1.67e-(-1)
25	1.93e+1
27	2.02e+1

D on Si, Maxwellian velocity distribution, sheath potential 3 kT

z1= 1, m1= 2.01, z2= 14, m2= 28.09, sbe=4.70 eV, rho= 2.32 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1(KrC)
 program: trvmc95
 ne=11

kT(eV)	Y	Y _E	E _{sp}	R _N	RB	E _b	range
5	2.47e-4	1.56e-5	1.58e-f-0	4.99e-1	2.77e-1	1.39e+1	1.89e4-1
7	1.19e-3	7.04e-5	2.07e-}-0	4.74e-1	2.57e-1	1.90e+1	2.33e+1
10	4.05e-3	2.26e-4	2.79e+0	4.52e-1	2.41e-1	2.66e+1	2.94e+1
20	1.47e-2	7.06e-4	4.79e+0	4.12e-1	2.11e-1	5.12e+1	4.72e+1
30	2.20e-2	9.09e-4	6.19e4-0	3.89e-1	1.95e-1	7.51e4-1	6.29e+1
50	2.97e-2	9.85e-4	8.30e-}-0	3.55e-1	1.73e-1	1.22e+2	9.20e-}-1
100	3.54e-2	7.88e-4	1.11e +1	3.06e-1	1.41e-1	2.31e-f-2	1.58e+2
200	3.62e-2	5.55e-4	1.53e4-1	2.52e-1	1.08e-1	4.31e-J-2	2.81e+2
300	3.39e-2	3.82e-4	1.69e+1	2.14e-1	8.66e-2	6.08e+2	3.96e-}-2
500	2.76e-2	2.33e-4	2.12e+1	1.71e-1	6.30e-2	9.23e+2	6.17e+2
1000	2.03e-2	9.66e-5	2.38e+1	1.08e-1	3.47e-2	1.61e4-3	1.13e+3

He Si

Sputtering yield of Si by He

z1= 2, m1= 4.00, z2=14, m2= 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvmcx, IPP 9/82
 ne= 6, na= 1

E ₀ (eV)	0°
50	1.64e-2
100	4.43e-2
300	8.77e-2
500	1.01e-1
1000	1.04e-1
4000	8.08e-2

Sputtered energy of Si by He

program : trspvmcx
 ne= 6, na= 1

E ₀ (eV)	0°
50	1.08e-3
100	2.61e-3
300	3.37e-3
500	2.88e-3
1000	1.99e-3
4000	6.47e-4

Particle reflection coefficient of He backscattered from Si

z1= 2, m1= 4.00, z2= 14, m2= 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvmcx
 ne= 6, na= 1

E ₀ (eV)	0°
50	3.60e-1
100	3.16e-1
300	2.57e-1
500	2.27e-1
1000	1.88e-1
4000	1.06e-1

Energy reflection coefficient of He backscattered from Si

ne= 6, na= 1

E ₀ (eV)	0°
50	1.47e-1
100	1.24e-1
300	9.54e-2
500	8.37e-2
1000	6.68e-2
4000	3.32e-2

Average depth (mean range) in Å of He implanted in Si

ne= 6, na= 1

E ₀ (eV)	0°
50	1.69e+1
100	2.66e+1
300	5.75e+1
500	8.46e+1
1000	1.48e+2
4000	5.04e+2

C → Si

C on Si, Maxwellian velocity distribution, sheath potential 9 kT
 z1 = 6, m1 = 12.01, z2 = 14, m2 = 28.09, sbe = 4.70 eV, rho = 2.32 g/cm**3
 ef = 4.65 eV, esb = 4.70 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvmc
 ne = 5

kT(eV)	Y	Ye	E _{sp}	■R-n	Rje?	E _k	range
5	5.27e-2	4.74e-3	4.94e+0	1.42e-1	2.72e-2	1.05e+1	7.91e+0
10	1.46e-1	9.82e-3	7.41e+0	1.50e-1	2.95e-2	2.15e+1	1.24e+1
20	2.75e-1	1.30e-2	1.04e+1	1.40e-1	2.72e-2	4.26e+1	1.92e+1
40	4.10e-1	1.35e-2	1.45e+1	1.24e-1	2.35e-2	8.37e+1	3.04e+1
50	5.57e-1	1.31e-2	1.58e+1	1.17e-1	2.14e-2	1.01e+2	3.54e+1

C on Si, Maxwellian velocity distribution, sheath potential 9 kT
 z1 = 6, m1 = 12.01, z2 = 14, m2 = 28.09, sbe = 4.70 eV, rho = 2.32 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvmc
 ne = 4

kT(eV)	Y	Ye	E _{sp}	■R/V	R _e	E _k	range
5	4.79e-2	4.27e-3	4.90e+0	2.27e-1	4.62e-2	1.12e+1	8.29e+0
10	1.42e-1	9.32e-3	7.24e+0	1.90e-1	3.69e-2	2.14e+1	1.26e+1
20	2.71e-1	1.30e-2	1.05e+1	1.57e-1	2.94e-2	4.13e+1	1.94e+1
40	4.10e-1	1.34e-2	1.43e+1	1.34e-1	2.48e-2	8.15e+1	3.05e+1

Ne -4- Si

Sputtering yield of Si by Ne
 z1 = 10, m1 = 20.18, z2 = 14, m2 = 28.09, sbe = 4.70, rho = 2.32 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : IPP 9/82
 ne = 12, na = 1

Bo(eV)	0°
30	7.60e-4
40	4.50e-3
50	1.15e-2
70	3.60e-2
100	8.00e-2
300	3.00e-1
1000	6.20e-1
3000	7.70e-1
10000	7.90e-1
30000	6.80e-1
100000	4.10e-1
300000	2.70e-1

Mg -4- Si

Particle reflection coefficient of Mg backscattered from Si
z1 = 12, miss 24.00, z2 = 14, m2 = 28.09, rho = 2.33 g/cm**3
ef = 1.00 eV, esb = 1.00 eV, ca = 1.00, kk0 = 2, kdeel = 3, ipot = 1 (KrC)
program: trrange3
only low fluence!
ne = 2, na = 1

E ₀ (eV)	0°
100000	1.55e-3
200000	6.10e-4

Energy reflection coefficient of Mg backscattered from Si
only low fluence!
ne = 2, na = 1

E ₀ (eV)	0°
100000	1.03e-4
200000	3.36e-5

Average depth (mean range) in Å of Mg implanted in Si
only low fluence!
ne = 2, na = 1

B ₀ (eV)	0°
100000	1.78e+3
200000	3.47e+3

Al → Si

Particle reflection coefficient of Al backscattered from Si
z1 = 13, miss 27.00; z2 = 14, m2 = 28.09, rho = 2.33 g/cm**3
ef = 1.00 eV, esb = 1.00 eV, ca = 1.00, kk0 = 2, kdeel = 3, ipot = 1 (KrC)
program: trrange3
only low fluence!
ne = 2, na = 1

E ₀ (eV)	0°
100000	9.17e-4
200000	3.65e-4

Energy reflection coefficient of Al backscattered from Si
only low fluence!
ne = 2, na = 1

B ₀ (eV)	0°
100000	4.86e-5
200000	1.73e-5

Average depth (mean range) in Å of Al implanted in Si
only low fluence!
ne = 2, na = 1

E ₀ (eV)	0°
100000	1.65e+3
200000	3.22e+3

Si Si

Sputtering yield of Si by Si

z1 = 14, m1 = 28.09, z2 = 14, m2 = 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.65 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program : trvmc, trvmc95, IPP 9/82
 ne=18, na= 9

Bo (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
30	4.70e-4								
40	2.00e-3								
50	1.40e-2								
70	3.80e-2								
100	6.20e-2								
300	3.00e-1								
500	4.40e-1	5.38e-1	8.43e-1	1.35e-0	1.76e-0	2.03e-0	1.69e-0	1.07e-0	3.50e-1
1000	7.00e-1								
1000	4.60e-1								
2000	8.96e-1	1.02e-0	1.47e-0	2.32e-0	3.12e-0	3.97e-0	4.24e-0	3.52e-0	1.26e-0
3000	9.60e-1								
10000	1.20e-0								
25000	1.13e-0								
30000	1.02e-0								
50000	1.09e-0								
75000	9.13e-1								
100000	7.36e-1								
100000	7.90e-1								

Sputtered energy of Si by Si

program : trvmc95
 ne= 2, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
500	9.04e-3	1.33e-2	2.87e-2	6.38e-2	1.01e-1	1.44e-1	1.54e-1	1.12e-1	
2000	9.22e-3	1.23e-2	2.46e-2	5.24e-2	8.53e-2	1.29e-1	1.69e-1	1.60e-1	6.76e-2

Particle reflection coefficient of Si backscattered from Si

z1 = 14, m1= 28.09, z2 = 14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.65 eV, esb= 4.70 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program : trvmc95
 ne= 2, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
500	1.20e-2	1.87e-2	4.32e-2	1.06e-1	1.91e-1	3.38e-1	6.05e-1	8.01e-1	
2000	1.08e-2	1.52e-2	3.13e-2	8.07e-2	1.42e-1	2.51e-1	4.44e-1	6.14e-1	9.00e-1

Energy reflection coefficient of Si backscattered from Si

ne= 2, na= 9

B ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
500	5.55e-4	1.16e-3	4.46e-3	1.86e-2	4.77e-2	1.24e-1	3.39e-1	5.58e-1	
2000	4.51e-4	8.81e-4	3.00e-3	1.24e-2	3.06e-2	7.76e-2	2.09e-1	3.80e-1	7.57e-1

Average depth (mean range) in Å of Si implanted in Si

ne= 2, na= 9

B ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
500	2.28e+1	2.21e-f-1	2.02e+1	1.75e4-1	1.55e-)-1	1.35e+1	1.16e+1	1.06e-)-1	
2000	5.55e-)-1	5.39e+1	4.91e+1	4.23e-f-1	3.71e+1	3.21e-j-1	2.77e+1	2.57e-)-1	2.37e+1

Si → Si

Sputtering yield of Si by Si

z1=14. m1= 28.09. z2=14. m2= 28.09. sbe=4.70 eV. rho=2.32 g/cm**3
 ef=4.60 eV. esb=4.70 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. KrC potential
 program : testsi. Gauss-Mehler integration (nn-n=16)
 ne=12. na=15

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.64e-4											
30	5.42e-4											
40	2.79e-3											
50	7.93e-3											
70	2.72e-2											
100	6.81e-2											
200	2.13e-1	2.46e-1	3.40e-1	5.07e-1	7.06e-1	9.34e-1	1.03e-0	1.08e-0	1.06e-0	9.66e-1	7.47e-1	4.63e-1
500	5.08e-1											
1000	7.52e-1											
2000	9.72e-1											
5000	1.19e-0											
10000	1.24e-0											

E ₀ (eV)	85°	87°	88°	89°
200	2.44e-1	1.89e-1	1.70e-1	1.64e-1

Sputtered energy of Si by Si

ne=12. na=15

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	9.07e-6											
30	3.17e-5											
40	1.60e-4											
50	4.21e-4											
70	1.28e-3											
100	2.78e-3											
200	6.40e-3	8.36e-3	1.46e-2	2.82e-2	4.99e-2	8.33e-2	1.04e-1	1.21e-1	1.33e-1	1.36e-1	1.18e-1	7.73e-2
500	1.00e-2											
1000	1.05e-2											
2000	9.64e-3											
5000	7.41e-3											
10000	5.48e-3											

E ₀ (eV)	85°	87°	88°	89°
200	3.97e-2	2.91e-2	2.64e-2	2.54e-2

Si -> Si

Particle reflection coefficient of Si backscattered from Si
 z1 = 14, m1 = 28.09, z2 = 14, m2 = 28.09, sbe = 4.70 eV, rho = 2.32 g/cm**3
 ef = 4.60 eV, esb = 4.70 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, KrC potential
 program : testsi, Gauss-Mehler integration (nnn=16)
 ne=12, na=15

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	5.38e-6											
30	2.91e-5											
40	1.83e-4											
50	4.77e-4											
70	1.57e-3											
100	3.11e-3											
200	7.34e-3	1.02e-2	2.09e-2	4.50e-2	8.87e-2	1.77e-1	2.41e-1	3.27e-1	4.40e-1	5.71e-1	7.23e-1	8.67e-1
500	1.15e-2											
1000	1.11e-2											
2000	9.77e-3											
5000	6.89e-3											
10000	5.02e-3											

E ₀ (eV)	85°	87°	88°	89°
200	9.48e-1	9.68e-1	9.71e-1	9.74e-1

Energy reflection coefficient of Si backscattered from Si
 ne=12, na=15

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	3.04e-7											
30	1.98e-6											
40	1.27e-5											
50	3.20e-5											
70	8.79e-5											
100	1.69e-4											
200	3.41e-4	6.05e-4	1.75e-3	5.17e-3	1.49e-2	4.14e-2	6.80e-2	1.10e-1	1.78e-1	2.74e-1	4.11e-1	5.78e-1
500	5.06e-4											
1000	4.59e-4											
2000	4.39e-4											
5000	3.29e-4											
10000	2.40e-4											

Bq(eV)	85°	87°	88°	89°
200	7.15e-1	7.52e-1	7.62e-1	7.68e-1

Average depth (mean range) in Å of Si implanted in Si
 ne=12, na=15

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	2.81e+0											
30	3.21e+0											
40	3.93e+0											
50	4.56e+0											
70	5.71e+0											
100	7.16e+0											
200	1.11e+1	1.09e+1	1.05e+1	9.79e+0	8.96e+0	7.86e+0	7.43e+0	6.91e+0	6.26e+0	5.76e+0	5.25e+0	4.29e+0
500	1.97e+1											
1000	3.08e+1											
2000	4.93e+1											
5000	9.70e+1											
10000	1.70e+2											

E ₀ (eV)	85°	87°	88°	89°
200	3.55e+0	3.19e+0	3.28e+0	2.88e+0

Si → Si

Sputtering yield of Si by Si

z1 = 14, m1 = 28.09, z2=14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipot=2 (Moliere potential)
 program : testsi, Gauss-Mehler integration (nnn=16)
 ne=12, na=16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.86e-4											
30	5.83e-4											
40	3.16e-3											
50	9.53e-3											
70	3.48e-2											
100	8.76e-2											
200	2.86e-1	3.19e-1	4.37e-1	6.16e-1	8.25e-1	1.03e-0	1.11e-0	1.12e-0	1.05e-0	9.12e-1	6.87e-1	4.18e-1
500	6.75e-1											
1000	9.64e-1											
2000	1.18e-0											
5000	1.27e-0											
10000	1.25e-0											

E ₀ (eV)	85°	87°	88°	89°
200	2.08e-1	1.64e-1	1.53e-1	1.40e-1

Sputtered energy of Si by Si

ne=12, na=16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.01e-5											
30	3.36e-5											
40	1.86e-4											
50	5.28e-4											
70	1.74e-3											
100	3.69e-3											
200	8.63e-3	1.08e-2	1.89e-2	3.43e-2	5.85e-2	9.36e-2	1.14e-1	1.27e-1	1.35e-1	1.30e-1	1.06e-1	6.67e-2
500	1.29e-2											
1000	1.26e-2											
2000	1.05e-2											
5000	7.01e-3											
10000	4.67e-3											

Bo(eV)	85°	87°	88°	89°
200	3.09e-2	2.26e-2	2.11e-2	1.87e-2

Si Si

Particle reflection coefficient of Si backscattered from Si
 z1=14, m1= 28.09, z2= 14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdee2=3, ipot=ipot=2 (Moliere potential)
 program : testsi, Gauss-Mehler integration (nnn = 16)
 ne=12, na=16

Bo(eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	2.13e-6											
30	2.78e-5											
40	1.93e-4											
50	6.27e-4											
70	1.67e-3											
100	4.03e-3											
200	9.50e-3	1.27e-2	2.56e-2	5.34e-2	1.13e-1	2.13e-1	2.86e-1	3.77e-1	4.96e-1	6.36e-1	7.71e-1	8.97e-1
500	1.23e-2											
1000	1.11e-2											
2000	8.58e-3											
5000	6.04e-3											
10000	4.03e-3											

E ₀ (eV)	85°	87°	88°	89°
200	9.67e-1	9.78e-1	9.80e-1	9.83e-1

Energy reflection coefficient of Si backscattered from Si
 ne=12, na=16

Bo (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.91e-7											
30	1.95e-6											
40	1.40e-5											
50	4.14e-5											
70	1.06e-4											
100	2.27e-4											
200	4.65e-4	7.71e-4	2.14e-3	6.34e-3	1.99e-2	5.16e-2	8.39e-2	1.32e-1	2.05e-1	3.16e-1	4.52e-1	6.07e-1
500	5.43e-4											
1000	4.69e-4											
2000	3.86e-4											
5000	2.91e-4											
10000	2.10e-4											

E ₀ (eV)	85°	87°	88°	89°
200	7.38e-1	7.69e-1	7.75e-1	7.84e-1

Average depth (mean range) in Å of Si implanted in Si
 ne=12, na=16

B ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	2.26e+0											
30	2.59e+0											
40	3.19e+0											
50	3.72e+0											
70	4.67e+0											
100	5.88e+0											
200	9.17e+0	9.04e+0	8.65e+0	8.06e+0	7.38e+0	6.56e+0	6.06e+0	5.71e+0	5.24e+0	4.69e+0	4.24e+0	3.54e+0
500	1.65e+1											
1000	2.65e+1											
2000	4.38e+1											
5000	9.16e+1											
10000	1.67e+2											

E ₀ (eV)	85°	87°	88°	89°
200	2.66e+0	2.36e+0	2.25e+0	2.35e+0

Si -> Si

Sputtering yield of Si by Si

z1 = 14, m1 = 28.09, z2 = 14, m2 = 28.09, sbe=4.70 eV, rho=2.33 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=0.65, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=2 (Moliere potential)
 program : testsi, Gauss-Mehler integration (nnn = 16)
 ne = 4, na = 1

Eq(eV)	0°
50	4.06e-3
70	1.38e-2
100	3.77e-2
200	1.37e-1

Sputtered energy of Si by Si

ne = 4, na = 1

Bq(eV)	0°
50	1.99e-4
70	6.24e-4
100	1.62e-3
200	4.60e-3

Particle reflection coefficient of Si backscattered from Si

z1 = 14, m1 = 28.09, z2 = 14, m2 = 28.09, sbe=4.70 eV, rho=2.33 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=0.65, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=2 (Moliere potential)
 program : testsi, Gauss-Mehler integration (nnn = 16)
 ne = 4, na = 1

Eo(eV)	O ³
50	3.35e-4
70	1.16e-3
100	2.97e-3
200	7.31e-3

Energy reflection coefficient of Si backscattered from Si

ne = 4, na = 1

Ep(eV)	0°
50	1.82e-5
70	6.87e-5
100	1.69e-4
200	3.86e-4

Average depth (mean range) in Å of Si implanted in Si

ne = 4, na = 1

B ₀ (eV)	0°
50	9.47e+0
70	1.13e+1
100	1.35e+1
200	1.94e+1

Si Si

Sputtering yield of Si by Si

z1=14, m1= 28.09, z2=14, m2 = 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=4 (Si-Si potential (with attractive part))
 program : testsi, Gauss-Mehler integration (nnn=16)
 ne=12, na=16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.29e-4											
30	3.84e-4											
40	1.77e-3											
50	5.16e-3											
70	1.83e-2											
100	4.74e-2											
200	1.70e-1	1.86e-1	2.54e-1	3.74e-1	5.30e-1	7.13e-1	8.00e-1	8.71e-1	9.09e-1	8.99e-1	8.24e-1	7.25e-1
500	4.11e-1											
1000	6.61e-1											
2000	9.50e-1											
5000	1.24e-0											
10000	1.29e-0											

B ₀ (eV)	85°	87°	88°	89°
200	5.87e-1	5.44e-1	5.40e-1	5.37e-1

Sputtered energy of Si by Si

ne=12, na=16

B ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	7.26e-6											
30	2.17e-5											
40	9.58e-5											
50	2.73e-4											
70	8.55e-4											
100	1.92e-3											
200	5.39e-3	6.49e-3	1.08e-2	2.01e-2	3.61e-2	6.05e-2	7.56e-2	9.22e-2	1.08e-1	1.19e-1	1.18e-1	1.13e-1
500	8.61e-3											
1000	1.00e-2											
2000	1.03e-2											
5000	8.36e-3											
10000	6.03e-3											

E ₀ (eV)	85°	87°	88°	89°
200	9.71e-2	9.11e-2	9.01e-2	9.05e-2

Si -> Si

Particle reflection coefficient of Si backscattered from Si
 z1= 14, m1= 28.09, z2= 14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdec1 = kdec2 = 3, ipot=ipotr=4 (Si-Si potential (with attractive part))
 program : testsi, Gauss-Mehler integration (nnn = 16)
 ne=12, na=16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.38e-6											
30	9.13e-6											
40	7.08e-5											
50	1.99e-4											
70	6.20e-4											
100	1.83e-3											
200	5.10e-3	7.25e-3	1.28e-2	2.78e-2	5.67e-2	1.16e-1	1.63e-1	2.19e-1	2.95e-1	3.83e-1	4.96e-1	5.98e-1
500	9.35e-3											
1000	1.12e-2											
2000	1.03e-2											
5000	7.89e-3											
10000	5.32e-3											

E ₀ (eV)	85°	87°	88°	89°
200	6.97e-1	7.22e-1	7.28e-1	7.32e-1

Energy reflection coefficient of Si backscattered from Si
 ne=12, na=16

B ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	9.83e-8											
30	7.67e-7											
40	4.46e-6											
50	1.12e-5											
70	3.07e-5											
100	9.83e-5											
200	2.37e-4	4.21e-4	1.01e-3	2.75e-3	8.18e-3	2.34e-2	3.84e-2	6.08e-2	9.63e-2	1.47e-1	2.17e-1	3.02e-1
500	4.18e-4											
1000	4.93e-4											
2000	4.73e-4											
5000	3.80e-4											
10000	2.64e-4											

B ₀ (eV)	85°	87°	88°	89°
200	3.87e-1	4.13e-1	4.15e-1	4.19e-1

Average depth (mean range) in Å of Si implanted in Si
 ne=12, na=16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	3.20e+0											
30	3.65e+0											
40	4.43e+0											
50	5.12e+0											
70	6.35e+0											
100	7.96e+0											
200	1.22e+1	1.21e+1	1.16e+1	1.07e+1	9.87e+0	8.73e+0	8.18e+0	7.67e+0	7.13e+0	6.56e+0	6.04e+0	5.44e+0
500	2.13e+1											
1000	3.22e+1											
2000	4.98e+1											
5000	9.66e+1											
10000	1.70e+2											

E ₀ (eV)	85°	87°	88°	89°
200	5.00e+0	4.85e+0	4.85e+0	4.85e+0

Si → Si

Sputtering yield of Si by Si

z1 = 14, m1 = 28.09, z2 = 14, m2 = 28.09, sbe = 4.70 eV, rho = 2.32 g/cm**3
 ef = 4.60 eV, esb = 4.70 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 3 (ZBL potential)
 program : testsi, Gauss-Mehler integration (nnn = 16)
 ne = 12, na = 16

Eq (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	1.27e-4											
30	4.29e-4											
40	2.21e-3											
50	6.15e-3											
70	2.12e-2											
100	5.28e-2											
200	1.73e-1	1.99e-1	2.82e-1	4.33e-1	6.28e-1	8.43e-1	9.52e-1	1.03e-0	1.03e-0	9.81e-1	8.02e-1	5.18e-1
500	4.18e-1											
1000	6.26e-1											
2000	8.37e-1											
5000	1.06e-0											
10000	1.12e-0											

E ₀ (eV)	85°	87°	88°	89°
200	2.77e-1	2.14e-1	1.97e-1	1.87e-1

Sputtered energy of Si by Si

ne = 12, na = 16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	7.06e-6											
30	2.44e-5											
40	1.20e-4											
50	3.14e-4											
70	9.70e-4											
100	2.06e-3											
200	5.30e-3	6.84e-3	1.23e-2	2.40e-2	4.48e-2	7.46e-2	9.47e-2	1.15e-1	1.28e-1	1.38e-1	1.26e-1	8.94e-2
500	8.58e-3											
1000	9.25e-3											
2000	8.83e-3											
5000	7.10e-3											
10000	5.34e-3											

E ₀ (eV)	85°	87°	88°	89°
200	4.77e-2	3.72e-2	3.26e-2	3.04e-2

Si -> Si

Particle reflection coefficient of Si backscattered from Si
 z1 = 14, m1 = 28.09, z2 = 14, m2 = 28.09, sbe = 4.70 eV, rho = 2.32 g/cm³
 cf = 4.60 eV, esb = 4.70 eV, ca = 1.00, kk0 = kk0r = 2, kdec1 = kdec2 = 3, ipot = ipotr = 3 (ZBL potential)
 program : testsi, Gauss-Mehler integration (nnn = 16)
 ne = 12, na = 16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	3.50e-6											
30	2.38e-5											
40	1.45e-4											
50	3.83e-4											
70	1.14e-3											
100	2.45e-3											
200	7.06e-3	9.40e-3	1.94e-2	3.89e-2	8.17e-2	1.61e-1	2.22e-1	2.97e-1	4.03e-1	5.19e-1	6.71e-1	8.30e-1
500	1.05e-2											
1000	1.08e-2											
2000	9.57e-3											
5000	7.58e-3											
10000	5.53e-3											

E ₀ (eV)	85°	87°	88°	89°
200	9.36e-1	9.54e-1	9.61e-1	9.63e-1

Energy reflection coefficient of Si backscattered from Si
 ne = 12, na = 16

Bo (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	2.33e-7											
30	1.47e-6											
40	8.95e-6											
50	2.21e-5											
70	6.02e-5											
100	1.33e-4											
200	3.46e-4	5.44e-4	1.61e-3	4.36e-3	1.29e-2	3.63e-2	5.98e-2	9.47e-2	1.56e-1	2.40e-1	3.67e-1	5.38e-1
500	4.80e-4											
1000	4.60e-4											
2000	4.31e-4											
5000	3.54e-4											
10000	2.87e-4											

E ₀ (eV)	85°	87°	88°	89°
200	6.84e-1	7.21e-1	7.32e-1	7.41e-1

Average depth (mean range) in Å of Si implanted in Si
 ne = 12, na = 16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
25	3.33e+0											
30	3.79e+0											
40	4.60e+0											
50	5.32e+0											
70	6.59e+0											
100	8.22e+0											
200	1.26e+1	1.24e+1	1.19e+1	1.11e+1	1.01e+1	8.92e+0	8.30e+0	7.76e+0	7.20e+0	6.49e+0	5.84e+0	5.05e+0
500	2.22e+1											
1000	3.45e+1											
2000	5.48e+1											
5000	1.06e+2											
10000	1.84e+2											

E ₀ (eV)	85°	87°	88°	89°
200	4.16e+0	3.82e+0	3.76e+0	3.90e+0

Si → Si

Sputtering yield of Si by Si

z1=14, m1= 28.09, z2=14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC potential)
 program : testsi, Gauss-Mehler integration (nnn=number of pivots)
 ne=1, n(nnn)=4

Bo(eV)	2	4	8	16
100	6.20e-2	6.61e-2	6.82e-2	6.79e-2

Sputtered energy of Si by Si

ne=1, np(nnn)=4

E ₀ (eV)	2	4	8	16
100	2.48e-3	2.65e-3	2.73e-3	2.77e-3

Particle reflection coefficient of Si backscattered from Si

z1=14, m1= 28.09, z2=14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.60 eV, esb=4.70 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC potential)
 program : testsi, Gauss-Mehler integration (nnn=number of pivots)
 ne=1, n(nnn)=4

B ₀ (eV)	2	4	8	16
100	3.07e-3	3.38e-3	3.17e-3	3.03e-3

Energy reflection coefficient of Si backscattered from Si

ne=1, n(nnn)=4

E ₀ (eV)	2	4	8	16
100	1.61e-4	1.90e-4	1.73e-4	1.64e-4

Average depth (mean range) in Å of Si implanted in Si

ne=1, h'(nnn)=4

B ₀ (eV)	2	4	8	16
100	8.15e4-0	7.39e+0	7.19e+0	7.15e+0

Si -> Si

Sputtering yield of Si by Si

z1=14, m1= 28.09, z2= 14, m2= 28.09, sbe=4.70 eV, rho= 2.33 g/cm**3
 ef=4.65 eV, esb=4.70 eV, ca=1.00, kk0=kk0r, kdeel = kdee2=3, KrC potential
 e0= 100 eV, alpha=0.0
 program : testsi, Gauss-Mehler integration (nnn=16)
 ne=1, n(kk0)=4

Potential	kk0=0	1	2	3
KrC	7.53e-2	6.35e-2	6.81e-2	7.13e-2
Mol	1.01e-1	8.20e-2	8.76e-2	9.39e-2
ZBL	5.82e-2	5.01e-2	5.28e-2	5.76e-2
Si-Si	7.45e-2	7.12e-2	4.74e-2	3.36e-2

Sputtered energy of Si by Si

ne=1, n(kk0)=4

Potential	kk0=0	1	2	3
KrC	2.99e-3	2.62e-3	2.78e-3	2.87e-3
Mol	4.10e-3	3.41e-3	3.69e-3	3.89e-3
ZBL	2.29e-3	2.00e-3	2.06e-3	2.22e-3
Si-Si	3.17e-3	3.04e-3	1.92e-3	1.39e-3

Particle reflection coefficient of Si backscattered from Si

z1=14, m1= 28.09, z2= 14, m2= 28.09, sbe=4.70 eV, rho=2.33 g/cm**3
 ef=4.65 eV, esb=4.70 eV, ca=1.00, kk0=kk0r, kdeel = kdee2=3, KrC potential
 e0= 100 eV, alpha=0.0
 program : testsi, Gauss-Mehler integration (nnn=16)
 ne=1, n(kk0)=4

Potential	kk0=0	1	2	3
KrC	2.59e-3	2.69e-3	3.11e-3	3.33e-3
Mol	3.06e-3	3.44e-3	4.03e-3	3.96e-3
ZBL	2.45e-3	2.29e-3	2.45e-3	2.78e-3
Si-Si	3.05e-3	3.05e-3	1.83e-3	1.15e-3

Energy reflection coefficient of Si backscattered from Si

ne=1, n(kk0)=4

Potential	kk0=0	1	2	3
KrC	1.25e-4	1.48e-4	1.69e-4	1.97e-4
Mol	1.43e-4	1.92e-4	2.27e-4	2.21e-4
ZBL	1.21e-4	1.23e-4	1.33e-4	1.39e-4
Si-Si	1.63e-4	1.47e-4	9.83e-5	6.52e-5

Average depth (mean range) in Å of Si implanted in Si

ne=1, n(kk0)=4

Potential	kk0=0	1	2	3
KrC	7.83e+0	7.21e-0	7.16e-f-0	7.14e+0
Mol	6.53e+0	5.93e+0	5.88e-f-0	5.89e-f-0
ZBL	8.84e+0	8.32e+0	8.22e+0	8.24e+0
Si-Si	8.36e+0	8.13e-f-0	7.96e-J-0	7.75e+0

Si -4 Si

Sputtering yield of Si by Si

z1 = 14, m1 = 28.09, z2=14, m2= 28.09, sbe=4.70 eV, rho = 2.32 g/cm**3
 ef=4.65 eV, esb = 4.70 eV, kk0=kk0r=2, kdee1=kdee2=3
 program : trspvmcx
 ne=1; alpha=0.

E ₀ (eV)	Pot. = KrC ca=1.00	Mol 1.00	ZBL 1.00	Mol 0.62
200	1.73e-1	2.84e-1	1.78e-1	1.26e-1

Sputtered energy of Si by Si

ne=1; alpha=0.

E ₀ (eV)	Pot.=KrC ca=1.00	Mol 1.00	ZBL 1.00	Mol 0.62
200	5.34e-3	8.63e-3	5.55e-3	4.39e-3

Particle reflection coefficient of Si backscattered from Si

z1 = 14, m1 = 28.09, z2 = 14, m2= 28.09, sbe=4.70 eV, rho=2.32 g/cm**3
 ef=4.65 eV, esb = 4.70 eV, kk0=kk0r=2, kdee1=kdee2=3
 program : trspvmcx
 ne=1; alpha=0.

B ₀ (eV)	Pot. = KrC ca=1.00	Mol 1.00	ZBL 1.00	Mol 0.62
200	8.46e-3	1.11e-2	7.28e-3	6.54e-3

Energy reflection coefficient of Si backscattered from Si

ne=1; alpha=0.

E ₀ (eV)	Pot. = KrC ca=1.00	Mol 1.00	ZBL 1.00	Mol 0.62
200	4.54e-4	5.77e-4	3.59e-4	3.49e-4

Average depth (mean range) in Å of Si implanted in Si

ne=1; alpha=0.

E ₀ (eV)	Pot. = KrC ca=1.00	Mol 1.00	ZBL 1.00	Mol 0.62
200	1.31e+1	9.03e+0	1.24e+1	2.07e+1

P -> Si

Particle reflection coefficient of P backscattered from Si
z1 = 15, m1 = 31.00, z2 = 14, m2 = 28.09, rho = 2.33 g/cm**3
ef = 1.00 eV, esb = 1.00 eV, ca = 1.00, kk0 = 2, kdeel = 3, ipot = 1 (KrC)
program: trrange3
only low fluence!
ne = 2, na = 1

Eo(eV)	0°
100000	5.50e-4
200000	2.25e-4

Energy reflection coefficient of P backscattered from Si
only low fluence!
ne = 2, na = 1

Bo(eV)	0°
100000	2.56e-5
200000	9.26e-6

Average depth (mean range) in Å of P implanted in Si
only low fluence!
ne = 2, na = 1

Eo(eV)	0°
100000	1.43e+3
200000	2.81e+3

Ar → Si

Sputtering yield of Si by Ar

z1= 18, m1= 39.95, z2= 14, m2= 28.09; sbe=4.70, rho=2.32 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1= kdee2=3, ipot=ipotr =1 (KrC)
 program : trspvmcx, TPP 9/82
 ne=15, na= 1

Bp (eV)	0°
50	1.79e-3
50	1.60e-3
100	3.08e-2
100	3.20e-2
300	2.33e-1
300	2.30e-1
500	3.96e-1
500	3.50e-1
1000	6.64e-1
1000	6.20e-1
3000	9.50e-1
4000	1.19e-0
10000	1.20e-0
30000	1.25e-0
100000	1.20e-0

Sputtered energy of Si by Ar

program : trspvmcx
 ne= 6, na= 1

Eq (eV)	0°
50	1.79e-3
50	1.60e-3
100	3.08e-2
100	3.20e-2
300	2.33e-1
300	2.30e-1
500	3.96e-1
500	3.50e-1
1000	6.64e-1
1000	6.20e-1
3000	9.50e-1
4000	1.19e-0
10000	1.20e-0
30000	1.25e-0
100000	1.20e-0

Particle reflection coefficient of Ar backscattered from Si

z1= 18, m1= 39.95, z2= 14, m2= 28.09; sbe=4.70, rho=2.32 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kkO= kkO=2, kdee1= kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvmcx
 ne= 6, na= 1

Ep (eV)	0°
50	7.83e-3
100	4.01e-3
300	3.93e-3
500	3.55e-3
1000	3.40e-3
4000	1.29e-3

Energy reflection coefficient of Ar backscattered from Si

ne= 6, na= 1

Bp (eV)	0°
50	1.04e-4
100	7.12e-5
300	8.09e-5
500	6.04e-5
1000	7.64e-5
4000	1.68e-5

Average depth (mean range) in Å of Ar implanted in Si

ne= 6, na= 1

Bp (eV)	0°
50	6.27e+0
100	9.36e+0
300	1.73e+1
500	2.30e+1
1000	3.44e+1
4000	8.24e+1

Xe Si

Sputtering yield of Si by Xe

z1=54, m1 = 131.30, z2=14, m2= 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotrl=1 (KrC)
 program : trspvmcx, TPP 9/82
 ne=18, na= 1

E ₀ (eV)	0°
50	3.54e-5
50	4.00e-5
100	3.84e-3
100	3.65e-3
200	4.83e-2
300	1.14e-1
500	2.56e-1
500	2.74e-1
1000	5.53e-1
1000	5.84e-1
2000	9.76e-1
4000	1.48e-0
5000	1.54e-0
10000	2.09e-0
20000	2.51e-0
50000	2.99e-0
100000	3.13e-0
200000	3.10e-0

Sputtered energy of Si by Xe

program : trspvmcx
 ne= 6, na= 1

E ₀ (eV)	0°
50	8.90e-7
100	9.24e-5
300	2.09e-3
500	3.87e-3
1000	5.98e-3
4000	7.87e-3

Particle reflection coefficient of Xe backscattered from Si

z1=54, m1=131.30, z2=14, m2 = 28.09, sbe=4.70, rho=2.32 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotrl=1 (KrC)
 program : trspvmcx
 ne= 1, na= 1

Bo (eV)	0°
50	6.13e-6

Energy reflection coefficient of Xe backscattered from Si

ne= 1, na= 1

E ₀ (eV)	0°
50	1.44e-6

Average depth (mean range) in Å of Xe implanted in Si

ne= 6, na= 1

E ₀ (eV)	0°
50	1.24e+1
100	1.72e+1
300	2.79e+1
500	3.48e+1
1000	4.72e+1
4000	8.91e+1

Bi -> Si

Average depth (mean range) in Å of Bi implanted in Si
z1=83, m1 = 209.00, z2= 14, m2= 28.09, rho= 2.33 g/cm**3
ef=1.00 eV, esb=1.00 eV, ca=1.00, kk0=2, kdeel=3, ipot = 1 (KrC)
program: trrange3
only low fluence.
ne= 2, na= 1

E ₀ (eV)	0°
200000	8.94e4-2
400000	1.48e+3

D → Ti

Sputtering yield of Ti by D

z1= 1, m1= 2.01, z2= 22, m2= 47.90, sbe=4.89 eV, rho= 4.52 g/cm**3
 ef=0.98, esb= 1.00, ca=1.00, kk0=kk0r=2, kdee1 = 4,kdee2 = 3, ipot=ipotr= 1 (KrC)
 program: testvmcx, IPP 9/82
 ne= 8, na=1

Bo (eV)	0°
50	3.64e-4
70	2.49e-3
100	6.53e-3
300	2.14e-2
1000	2.72e-2
3000	2.17e-2
10000	1.13e-2
30000	5.00e-3

Sputtered energy of Ti by D

program: testvmcx
 ne= 8, na=1

E ₀ (eV)	0°
50	5.69e-6
70	6.59e-5
100	1.92e-4
300	5.04e-4
1000	3.56e-4
3000	1.36e-4
10000	3.13e-5
30000	3.70e-6

Particle reflection coefficient of D backscattered from Ti

z1= 1, m1= 2.01, z2= 22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=0.98, esb= 1.00, ca=1.00, kk0=kk0r=2, kdee1 = 4,kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 8, na=1

B ₀ (eV)	0°
50	5.13e-1
70	4.95e-1
100	4.73e-1
300	4.01e-1
1000	3.09e-1
3000	1.89e-1
10000	7.85e-2
30000	1.95e-2

Energy reflection coefficient of D backscattered from Ti

ne= 8, na=1

B ₀ (eV)	0°
50	2.94e-1
70	2.78e-1
100	2.61e-1
300	2.08e-1
1000	1.46e-1
3000	7.62e-2
10000	2.55e-2
30000	5.22e-3

Average depth (mean range) in Å of D implanted in Ti

ne= 8, na=1

E ₀ (eV)	0°
50	2.78e4-1
70	3.42e+ 1
100	4.29e+1
300	9.04e+1
1000	2.23e+ 2
3000	5.48e+ 2
10000	1.53e+3
30000	3.93e+ 3

He -> Ti

Sputtering yield of Ti by He

z1= 2, m1= 4.00, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx, TPP 9/82
 ne= 8, na=1

E ₀ (eV)	0°
40	3.31e-3
60	1.50e-2
100	3.58e-2
300	8.09e-2
1000	1.13e-1
3000	1.07e-1
10000	6.63e-2
30000	3.40e-2

Sputtered energy of Ti by He

program: testvmcx
 ne= 8, na=1

Bp (eV)	0°
40	1.30e-4
60	7.34e-4
100	1.72e-3
300	2.62e-3
1000	1.82e-3
3000	8.56e-4
10000	2.07e-4
30000	4.89e-5

Particle reflection coefficient of He backscattered from Ti

z1= 2, m1= 4.00, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 8, na=1

E ₀ (eV)	0°
40	4.93e-1
60	4.58e-1
100	4.27e-1
300	3.62e-1
1000	2.87e-1
3000	2.06e-1
10000	1.09e-1
30000	3.95e-2

Energy reflection coefficient of He backscattered from Ti

ne= 8, na=1

E ₀ (eV)	0°
40	2.53e-1
60	2.28e-1
100	2.06e-1
300	1.66e-1
1000	1.23e-1
3000	8.11e-2
10000	3.59e-2
30000	1.10e-2

Average depth (mean range) in Å of He implanted in Ti

ne= 8, na=1

E ₀ (eV)	0°
40	1.38e+1
60	1.76e+1
100	2.39e+1
300	4.89e+1
1000	1.17e+2
3000	2.83e+2
10000	7.96e+2
30000	2.12e+3

Ne -> Ti

Sputtering yield of Ti by Ne

z1 = 10, m1 = 20.18, z2=22, m2= 47.90, sbe=4.89 eV, rho = 4.51 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrr=1 (KrC)
 program: testvmcx, TPP 9/82
 ne=15, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
38	1.02e-2	1.12e-2	1.43e-2	1.98e-2	2.75e-2	3.24e-2	3.71e-2	3.79e-2	2.34e-2	1.04e-2	2.10e-3	2.00e-5
50	3.00e-2											
100	1.45e-1											
200	3.23e-1											
380	5.33e-1	5.62e-1	6.58e-1	8.17e-1	1.03e-0	1.13e-0	1.24e-0	1.37e-0	1.18e-0	8.51e-1	3.46e-1	1.25e-2
500	6.14e-1											
1000	8.20e-1											
2000	9.98e-1											
3800	1.08e-0	1.15e-0	1.27e-0	1.61e-0	2.00e-0	2.32e-0	2.65e-0	3.47e-0	4.22e-0	4.30e-0	3.81e-0	1.38e-0
5000	1.09e-0											
10000	1.08e-0											
20000	9.40e-1											
50000	7.32e-1											
100000	5.51e-1											
200000	4.14e-1											

Sputtered energy of Ti by Ne

program: testvmcx, IPP 9/82
 ne=15, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
38	8.60e-4	1.04e-3	1.44e-3	2.39e-3	3.72e-3	4.67e-3	5.83e-3	6.97e-3	4.73e-3	2.26e-3	4.66e-4	7.46e-6
50	2.30e-3											
100	9.00e-3											
200	1.34e-2											
380	1.57e-2	1.70e-2	2.24e-2	3.12e-2	4.74e-2	5.60e-2	6.85e-2	9.23e-2	9.99e-2	8.31e-2	3.77e-2	8.54e-4
500	1.55e-2											
1000	1.41e-2											
2000	1.17e-2											
3798	8.92e-3	9.86e-3	1.24e-2	1.78e-2	2.62e-2	3.27e-2	4.01e-2	6.08e-2	8.71e-2	9.82e-2	9.83e-2	4.30e-2
5000	7.83e-3											
10000	5.21e-3											
20000	3.13e-3											
50000	1.43e-3											
100000	6.29e-4											
200000	3.03e-4											

Ne -> Ti

Particle reflection coefficient of Ne backscattered from Ti
 z1 = 10, m1 = 20.18, z2=22; m2= 47.90, sbe=4.89 eV, rho=4.51 g/cm**3
 ef=0.50, esb=0.00, ca=1.00, kkO=kkOr=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=15, na=12

Eo(eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
38	3.27e-1	3.49e-1	3.95e-1	4.60e-1	5.60e-1	6.14e-1	6.79e-1	8.17e-1	9.43e-1	9.83e-1	9.98e-1	1.00e-0
50	3.07e-1											
100	2.34e-1											
200	1.81e-1											
380	1.50e-1	1.58e-1	1.79e-1	2.11e-1	2.67e-1	3.00e-1	3.49e-1	4.67e-1	6.71e-1	8.07e-1	9.47e-1	1.00e-0
500	1.40e-1											
1000	1.15e-1											
2000	9.90e-2											
3798	8.05e-2	8.54e-2	9.52e-2	1.23e-1	1.60e-1	1.82e-1	2.14e-1	2.96e-1	4.24e-1	5.10e-1	6.40e-1	9.02e-1
5000	7.45e-2											
10000	5.89e-2											
20000	4.35e-2											
50000	2.39e-2											
100000	1.42e-2											
200000	7.56e-3											

Energy reflection coefficient of Ne backscattered from Ti
 ne=15, na=12

Eo (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
38	5.58e-2	6.46e-2	8.59e-2	1.23e-1	1.88e-1	2.34e-1	2.90e-1	4.43e-1	6.56e-1	7.81e-1	8.92e-1	9.68e-1
50	5.21e-2											
100	3.98e-2											
200	2.97e-2											
380	2.48e-2	2.74e-2	3.41e-2	4.70e-2	7.24e-2	9.00e-2	1.18e-1	2.04e-1	3.97e-1	5.64e-1	7.93e-1	9.68e-1
500	2.32e-2											
1000	1.85e-2											
2000	1.60e-2											
3798	1.32e-2	1.46e-2	1.76e-2	2.63e-2	4.04e-2	4.95e-2	6.41e-2	1.09e-1	2.01e-1	2.80e-1	4.27e-1	7.95e-1
5000	1.24e-2											
10000	9.68e-3											
20000	7.12e-3											
50000	3.89e-3											
100000	2.07e-3											
200000	1.10e-3											

Average depth (mean range) in Å of Ne implanted in Ti
 ne=15, na=12

Eo (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
38	6.91e+0	6.86e+0	6.76e+0	6.65e+0	6.49e+0	6.42e+0	6.35e+0	6.07e+0	5.70e+0	5.50e+0	5.19e+0	
50	7.58e+0											
100	9.90e+0											
200	1.35e+1											
380	1.87e+1	1.86e+1	1.82e+1	1.76e+1	1.67e+1	1.63e+1	1.58e+1	1.49e+1	1.40e+1	1.35e+1	1.27e+1	1.26e+1
500	2.17e+1											
1000	3.27e+1											
2000	5.51e+1											
3798	7.99e+1	7.91e+1	7.67e+1	7.31e+1	6.85e+1	6.58e+1	6.32e+1	5.75e+1	5.26e+1	5.13e+1	4.88e+1	4.65e+1
5000	9.84e+1											
10000	1.70e+2											
20000	3.09e+2											
50000	7.12e+2											
100000	1.37e+3											
200000	2.60e+3											

Ar -> Ti

Sputtering yield of Ti by Ar

z1= 18, m1 = 39.95, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=0.20, 0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 =kdee2 = 3, ipot=ipot= 1 (KrC)
 program : trvmc95
 ne= 5, na= 5

E ₀ (eV)	0°	20°	45°	50°	60°
640					2.29e-0
1000	1.04e-0				
1040		1.15e-0	2.14e-0		3.15e-0
1440					3.84e-0
5000				4.62e-0	

Sputtered energy of Ti by Ar

ne= 5, na= 5

E ₀ (eV)	0°	20°	45°	50°	60°
640					1.34e-1
1000	1.52e-2				
1040		2.22e-2	7.00e-2		1.33e-1
1440					1.34e-1
5000				6.66e-2	

Particle reflection coefficient of Ar backscattered from Ti

z1= 18, m1 = 39.95, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=0.20, 0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 =kdee2 = 3, ipot=ipot= 1 (KrC)
 program : trvmc95
 ne= 5, na= 5

E ₀ (eV)	0°	20°	45°	50°	60°
640					3.28e-1
1000	3.76e-2				
1040		6.04e-2	1.49e-1		3.08e-1
1440					2.88e-1
5000				1.33e-1	

Energy reflection coefficient of Ar backscattered from Ti

ne= 5, na= 5

E ₀ (eV)	0°	20°	45°	50°	60°
640					9.65e-2
1000	2.06e-3				
1040		4.33e-3	2.47e-2		9.13e-2
1440					8.45e-2
5000				2.59e-2	

Average depth (mean range) in Å of Ar implanted in Ti

ne= 5, na= 5

E ₀ (eV)	0°	20°	45°	50°	60°
640					1.33e+1
1000	2.40e+1				
1040		2.54e+1	2.10e+1		1.65e+1
1440					2.04e+1
5000				4.85e+1	

Ti -> Ti

Sputtering yield of Ti by Ti
 z1=22, m1 = 47.90, z2=22, m2= 47.90, sbe=4.89 eV, rho = 4.52 g/cm**3
 ef=4.85, esb=4.89, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx, IPP 9/82
 ne=13, na=1

E ₀ (eV)	0°
60	7.14e-3
80	1.96e-2
100	6.62e-2
100	3.62e-2
200	2.39e-1
300	2.41e-1
1000	1.04e-0
1000	7.16e-1
10000	2.14e-0
10000	1.73e-0
50000	1.62e-0
100000	1.71e-0
100000	1.39e-0

Sputtered energy of Ti by Ti
 program: testvmcx
 ne= 5, na=1

E ₀ (eV)	0°
100	2.73e-3
200	7.43e-3
1000	1.45e-2
10000	8.88e-3
100000	2.10e-3

Particle reflection coefficient of Ti backscattered from Ti
 z1=22, m1 = 47.90, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=4.85, esb=4.89, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 5, na=1

E ₀ (eV)	0°
100	4.19e-3
200	1.08e-2
1000	1.65e-2
10000	7.70e-3
100000	2.00e-3

Energy reflection coefficient of Ti backscattered from Ti
 ne= 5, na=1

E ₀ (eV)	0°
100	2.36e-4
200	5.31e-4
1000	6.48e-4
10000	4.30e-4
100000	1.55e-4

Average depth (mean range) in Å of Ti implanted in Ti
 ne= 5, na=1

E ₀ (eV)	0°
100	6.04e-1
200	9.03e+0
1000	2.23e+1
10000	9.72e+1
100000	6.60e+2

Ti → Ti

Sputtering yield of Ti by Ti

z1=22, m1 = 47.90, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=4.85, esb=4.89, ca=0.75, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl=1 (KrC)
 program: testvmcx
 ne= 8, na=1

E ₀ (eV)	0°
60	7.14e-3
80	1.96e-2
100	3.62e-2
300	2.41e-1
1000	7.16e-1
10000	1.73e-0
50000	1.62e-0
100000	1.39e-0

Sputtered energy of Ti by Ti

program: testvmcx
 ne= 8, na=1

E ₀ (eV)	0°
60	3.29e-4
80	8.63e-4
100	1.49e-3
300	6.66e-3
1000	1.12e-2
10000	8.54e-3
50000	3.22e-3
100000	1.87e-3

Particle reflection coefficient of Ti backscattered from Ti

z1=22, m1= 47.90, z2=22, m2= 47.90, sbe=4.89 eV, rho=4.52 g/cm**3
 ef=4.85, esb=4.89, ca=0.75, kk0=kk0r=2, kdee1 = kdee2=3, ipots=ipotrl=1 (KrC)
 program: testvmcx
 ne= 8, nas=1

E ₀ (eV)	0°
60	7.96e-4
80	1.75e-3
100	2.91e-3
300	1.08e-2
1000	1.46e-2
10000	9.50e-3
50000	4.50e-3
100000	2.43e-3

Energy reflection coefficient of Ti backscattered from Ti
 ne= 8, na=1

E ₀ (eV)	0°
60	4.19e-5
80	9.48e-5
100	1.61e-4
300	5.39e-4
1000	6.40e-4
10000	3.43e-4
50000	2.08e-4
100000	1.14e-4

Average depth (mean range) in Å of Ti implanted in Ti
 ne= 8, na=1

E ₀ (eV)	0°
60	8.23e+0
80	9.56e+0
100	1.07e+1
300	1.86e+1
1000	3.49e+1
10000	1.36e+2
50000	4.59e+2
100000	8.27e+2

D -> V

Sputtering yield of V by T)

z1= 1, m1= 2.01, z2=23, m2= 50.94, sbe=5.33 eV, rho = 6.10 g/cm**3
 ef=0.95 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 4,kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=11, na=1

EO(eV)	0°
50	7.42e-5
60	5.72e-4
70	1.49e-3
80	2.72e-3
100	5.27e-3
200	1.56e-2
500	2.60e-2
1000	2.68e-2
2000	2.49e-2
5000	1.84e-2
10000	1.30e-2

Sputtered energy of V by D
 ne=11, na=1

E ₀ (eV)	0°
50	6.86e-7
60	9.59e-6
70	3.12e-5
80	6.52e-5
100	1.36e-4
200	4.08e-4
500	5.15e-4
1000	3.53e-4
2000	2.09e-4
5000	7.78e-5
10000	3.00e-5

Particle reflection coefficient of D backscattered from V

z1= 1, m1= 2.01, z2=23, m2= 50.94, sbe=5.33 eV, rho=6.10 g/cm**3
 ef=0.95 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 4,kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=11, na=1

Bo(eV)	0°
50	5.32e-1
60	5.20e-1
70	5.10e-1
80	5.00e-1
100	4.86e-1
200	4.42e-1
500	3.75e-1
1000	3.17e-1
2000	2.50e-1
5000	1.52e-1
10000	8.55e-2

Energy reflection coefficient of D backscattered from V
 ne=11, na=1

Bo(eV)	0°
50	3.12e-1
60	3.02e-1
70	2.93e-1
80	2.86e-1
100	2.74e-1
200	2.39e-1
500	1.90e-1
1000	1.51e-1
2000	1.09e-1
5000	5.61e-2
10000	2.74e-2

Average depth (mean range) in Å of D implanted in V
 ne=11, na=1

E ₀ (eV)	0°
50	2.18e+1
60	2.44e+1
70	2.70e+1
80	2.93e+1
100	3.38e+1
200	5.35e+1
500	1.03e+2
1000	1.73e+2
2000	3.03e+2
5000	6.53e+2
10000	1.19e+3

$$V \rightarrow V$$

Sputtering yield of V by V

z1 = 23, m1 = 50.94, z2=23, m2= 50.94, sbe=5.33 eV, rho = 6.10 g/cm**3
 ef=5.28 eV, esb=5.33 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotrl (KrC)
 program: testvmcx
 ne=13, na=1

E ₀ (eV)	0°
30	2.15e-4
40	1.18e-3
50	4.07e-3
60	9.75e-3
70	1.85e-2
80	3.04e-2
100	6.05e-2
200	2.48e-1
500	7.13e-1
1000	1.17e-0
2000	1.66e-0
5000	2.23e-0
10000	2.56e-0

Sputtered energy of V by V

ne=13, na=1

MeV)	0°
30	1.16e-5
40	6.67e-5
50	2.32e-4
60	5.35e-4
70	9.56e-4
80	1.48e-3
100	2.70e-3
200	8.11e-3
500	1.51e-2
1000	1.71e-2
2000	1.67e-2
5000	1.36e-2
10000	1.08e-2

$$V \rightarrow V$$

Particle reflection coefficient of V backscattered from V
 z1=23, m1 = 50.94, z2=23, m2= 50.94, sbe=5.33 eV, rho=6.10 g/cm**3
 ef=5.28 eV, esb=5.33 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 program: testvmx
 ne=13, na=1

Bq (eV)	0°
30	4.37e-6
40	1.06e-4
50	4.65e-4
60	1.05e-3
70	1.75e-3
80	2.61e-3
100	4.23e-3
200	1.07e-2
500	1.57e-2
1000	1.69e-2
2000	1.65e-2
5000	1.27e-2
10000	1.01e-2

Energy reflection coefficient of V backscattered from V
 ne=13, na=1

E0 (eV)	0°
30	2.91e-7
40	7.69e-6
50	3.36e-5
60	7.39e-5
70	1.18e-4
80	1.79e-4
100	2.67e-4
200	5.59e-4
500	7.29e-4
1000	7.20e-4
2000	6.45e-4
5000	5.35e-4
10000	4.48e-4

Average depth (mean range) in Å of V implanted in V
 ne=13, na=1

B0 (eV)	0°
30	1.90e-J-0
40	2.36e+0
50	2.77e+0
60	3.14e+0
70	3.47e+0
80	3.79e+0
100	4.36e+0
200	6.65e-J-0
500	1.13e+1
1000	1.70e+1
2000	2.55e+1
5000	4.55e+1
10000	7.32e+1

H → Fe

Particle reflection coefficient of H backscattered from Fe
 z1 = 1, m1 = 1.01, z2 = 26, m2 = 55.85, sbe = 4.34 eV, rho = 7.87 g/cm**3
 ef = 100.00 eV, esb = 1.00 eV, ca = -1.00, kko = 0, kk0r = 2, kdee1 = 4, kdee2 = 3, ipot = ipotr = 1 (KrC)
 dx = 50000.00 A
 program: trvmc95
 ne = 1, na = 4

Ro (eV)	83°	86°	88°	89°
3000000	5.19e-2	1.81e-1	3.83e-1	5.52e-1

Energy reflection coefficient of H backscattered from Fe
 ne = 1, na = 4

E ₀ (eV)	83°	86°	88°	89°
3000000	1.91e-2	8.16e-2	2.32e-1	4.05e-1

Average depth (mean range) in Å of H implanted in Fe
 ne = 1, na = 4

E ₀ (eV)	83°	86°	88°	89°
3000000	3.06e+4	2.54e4-4	2.23e-f-4	2.13e+4

Particle transmission coefficient of IT transmitted through Fe
 ne = 1, na = 4

E ₀ (eV)	83°	86°	88°	89°
3000000	3.99e-1	1.53e-1	6.71e-2	4.08e-2

Energy transmission coefficient of H transmitted through Fe
 ne = 1, na = 4

E ₀ (eV)	83°	86°	88°	89°
3000000	1.18e-1	3.60e-2	1.48e-2	9.05e-3

D → Fe

D on Fe, Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1, m1 = 2.01, z2 = 26, m2 = 55.85, sbe = 4.34 eV, rho = 7.87 g/cm**3
 ef = 0.95 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvmc95
 ne = 11

kT(eV)	Y	Y _#	E _{sp}	Rat	Re	Efe	range
7	1.57e-4	5.87e-6	1.31e-0	6.20e-1	4.02e-1	2.27e+1	1.44e+1
8	3.56e-4	1.27e-5	1.43e+0	6.09e-1	3.91e-1	2.57e+1	1.56e+1
9	7.04e-4	2.44e-5	1.56e+0	5.99e-1	3.81e-1	2.86e+1	1.67e+1
10	1.20e-3	4.06e-5	1.70e+0	5.91e-1	3.73e-1	3.16e+1	1.78eR1
14	4.42e-3	1.39e-4	2.20e+0	5.67e-1	3.50e-1	4.32e+1	2.20e+1
20	1.10e-2	3.25e-4	2.95e+0	5.42e-1	3.27e-1	6.04e+1	2.75e+1
50	3.41e-2	7.66e-4	5.63e+0	4.84e-1	2.75e-1	1.42e+2	5.03e+1
100	4.50e-2	7.22e-4	8.02e+0	4.29e-1	2.33e-1	2.71e+2	8.21e+1
200	4.99e-2	5.44e-4	1.09e+1	3.75e-1	1.91e-1	5.11e+2	1.37e+2
500	4.55e-2	2.66e-4	1.46e+1	2.88e-1	1.31e-1	1.14e+3	2.82e+2
1000	3.63e-2	1.29e-4	1.77e+1	2.13e-1	8.51e-2	2.00e+3	4.96e+2

T → Fe

Particle reflection coefficient of T backscattered from Fe
 z1= 1, m1= 3.02, z2=26, m2= 55.85, sbe=4.34 eV, rho= 7.87 g/cm**3
 ef=100.00 eV, esb= 1.00 eV, ca=1.00, kko=0, kkor=2, kdel=4, kdee2= 3, ipot=ipotrl=1 (KrC)
 dx= 15000.00 A
 program: trvmc95
 ne= 1, na= 4

Eo(eV)	79°	83°	86°	88°	89°
1000000	4.06e-2	1.35e-1	3.03e-1	4.94e-1	6.37e-1

Energy reflection coefficient of T backscattered from Fe
 ne= 1, na= 4

Eo(eV)	79°	83°	86°	88°	89°
1000000	5.60e-3	2.01e-2	7.24e-2	2.02e-1	3.68e-1

Average depth (mean range) in Å of T implanted in Fe
 ne= 1, na= 4

Eo (eV)	79°	83°	86°	88°	89°
1000000	8.63e-13	6.77e-13	5.57e+3	5.04e+3	4.90e+3

Particle transmission coefficient of T transmitted through Fe
 ne= 1, na= 4

Eo (eV)	79°	83°	86°	88°	89°
1000000	1.33e-1	3.73e-2	1.41e-2	7.72e-3	5.24e-3

Energy transmission coefficient of T transmitted through Fe
 ne= 1, na= 4

Eo (eV)	79°	83°	86°	88°	89°
1000000	6.63e-3	1.91e-3	8.99e-4	5.86e-4	4.35e-4

He → Fe

Sputtering yield of Fe by He
z1 = 2, m1 = 4.00, z2 = 26, m2 = 55.85, sbe = 4.34 eV, rho = 7.87 g/cm**3
ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
program: trspvmcx, TPP 9/82
ne = 10, na = 1

E ₀ (eV)	0°
40	5.02e-3
50	1.26e-2
70	3.04e-2
100	5.52e-2
300	1.24e-1
1000	1.66e-1
1000	1.72e-1
5000	1.42e-1
10000	1.06e-1
30000	5.15e-2

Sputtered energy of Fe by He
program: testvmcx, trspvmcx
ne = 11, na = 1

E ₀ (eV)	0°
40	1.79e-4
50	5.15e-4
70	1.31e-3
100	2.30e-3
300	3.48e-3
1000	2.38e-3
1000	2.36e-3
3000	1.03e-3
5000	6.37e-4
10000	2.77e-4
30000	5.50e-5

He → Fe

Particle reflection coefficient of He backscattered from Fe
 $z1 = 2$, $m1 = 4.00$, $z2=26$, $m2= 55.85$; $sbe=4.34$ eV, $\rho= 7.87$ g/cm**3
 $ef=0.50$ eV, $esb=0.00$ eV, $ca=1.00$, $kk0=kk0r=2$, $kdee1=kdee2=3$, $ipot=ipotr=1$ (KrC)
 5.5 MeV : $kkO=0$, $kdee1=5$, $ef=100$ eV, $esb=1.00$ eV, $dx=7000$ nm
 program: testvmcx, trvmc95
 $ne=11$, $na=5$

Bo (eV)	0°	83°	86°	88°	89°
40	5.62e-1				
50	5.38e-1				
70	5.05e-1				
100	4.75e-1				
300	3.99e-1				
1000	3.19e-1				
3000	2.40e-1				
5000	1.93e-1				
10000	1.33e-1				
30000	5.34e-2				
5500000		1.38e-2	8.17e-2	2.76e-1	4.72e-1

Energy reflection coefficient of He backscattered from Fe
 $ne=11$, $na=5$

E ₀ (eV)	0°	83°	86°	88°	89°
40	3.11e-1				
50	2.92e-1				
70	2.67e-1				
100	2.45e-1				
300	1.94e-1				
1000	1.43e-1				
3000	1.01e-1				
5000	7.59e-2				
10000	4.52e-2				
30000	1.51e-2				
5500000		3.67e-3	1.86e-2	9.78e-2	2.51e-1

Average depth (mean range) in Å of He implanted in Fe
 program: testvmcx, trspvmcx
 $ne=10$, $na=1$

E ₀ (eV)	0°
40	9.20e+0
50	1.05e+1
70	1.28e+1
100	1.59e+1
300	3.21e+1
1000	7.55e+1
3000	1.79e+2
5000	2.72e+2
10000	4.92e+2
30000	1.30e+3

Fe -> Fe

Sputtering yield of Fe by Fe

z1 = 26, m1 = 55.85, z2=26, m2 = 55.85, sbe=4.34 eV, rho = 7.87 g/cm**3
 ef=4.29 eV, esb = 4.34 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: testvmcx, TPP 9/82
 ne=11, na= 1

E ₀ (eV)	0°
50	9.84e-3
70	4.00e-2
100	1.18e-1
200	4.10e-1
500	1.12e-0
1000	1.80e-0
2000	2.47e-0
5000	3.19e-0
10000	3.91e-0
30000	3.88e-0
100000	3.38e-0

Sputtered energy of Fe by Fe

program: testvmcx
 ne=11, na= 1

E ₀ (eV)	0°
50	5.35e-4
70	2.05e-3
100	4.90e-3
200	1.29e-2
500	2.12e-2
1000	2.24e-2
2000	2.03e-2
5000	1.58e-2
10000	1.32e-2
30000	7.94e-3
100000	3.10e-3

Particle reflection coefficient of Fe backscattered from Fe

z1 = 26, m1 = 55.85, z2=26, m2 = 55.85, sbe=4.34 eV, rho = 7.87 g/cm**3
 ef=4.29 eV, esb=4.34 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: testvmcx
 ne=11, na= 1

E ₀ (eV)	0°
50	9.25e-4
70	3.06e-3
100	5.95e-3
200	1.38e-2
500	1.98e-2
1000	2.34e-2
2000	1.88e-2
5000	1.24e-2
10000	1.30e-2
30000	6.67e-3
100000	4.00e-3

Energy reflection coefficient of Fe backscattered from Fe

ne=11, na= 1

E ₀ (eV)	0°
50	6.52e-5
70	2.10e-4
100	3.79e-4
200	6.23e-4
500	8.52e-4
1000	9.52e-4
2000	7.11e-4
5000	4.40e-4
10000	4.76e-4
30000	3.61e-4
100000	2.29e-4

Average depth (mean range) in Å of Fe implanted in Fe

ne=11, na= 1

E ₀ (eV)	0°
50	2.06e+0
70	2.63e+0
100	3.36e+0
200	5.21e+0
500	8.82e+0
1000	1.31e+1
2000	1.98e+1
5000	3.57e+1
10000	5.52e+1
30000	1.26e+2
100000	3.39e+2

$\mu \rightarrow \text{Ni}$

Particle reflection coefficient of μ backscattered from Ni
 $z1 = 1, m1 = 0.11, z2=28, m2= 58.71, sbe=4.46 \text{ eV}, \rho = 8.90 \text{ g/cm}^3$
 $ef=0.50 \text{ eV}, esb=0.00 \text{ eV}, ca=1.00, kk0=kk0r=2, kdee2=3, ipot=ipotr=1 \text{ (KrC)}$
 $10 - 1000 \text{ eV} : kdee1 = 3, 1000 - 20000 \text{ eV} : kdee1 = 4$
 program: trvmc
 $ne= 8, na= 1$

B_0 (eV)	0°
10	7.08e-1
100	4.25e-1
500	2.64e-1
1000	2.01e-1
1000	1.78e-1
5000	5.99e-2
10000	3.05e-2
20000	1.29e-2

Energy reflection coefficient of p backscattered from Ni
 $ne= 8, na= 1$

E_0 (eV)	0°
10	4.39e-1
100	2.04e-1
500	1.04e-1
1000	7.05e-2
1000	6.25e-2
5000	1.81e-2
10000	8.96e-3
20000	4.63e-3

Average depth (mean range) in \AA of p implanted in Ni
 $ne= 8, na= 1$

E_0 (eV)	0°
10	5.53e+0
100	1.80e+1
500	4.61e+1
1000	7.19e+1
1000	6.60e+1
5000	2.13e+2
10000	3.76e+2
20000	7.21e+2

H -> Ni

Sputtering yield of Ni by H

z1= 1, m1= 1.01, z2=28, m2= 58.71, sbe=4.46 eV, rho= 8.90 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program: TESTVMCX, TPP 9/82
 ne=13, na=16

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	65°	70°	75°	80°
150	2.00e-3	2.10e-3	2.05e-3	2.20e-3	2.35e-3	2.35e-3	2.25e-3	2.05e-3	1.80e-3	1.20e-3	6.40e-4	
200	4.50e-3	4.50e-3	4.80e-3	5.40e-3	5.50e-3	6.20e-3	5.90e-3	6.10e-3	5.80e-3	4.70e-3	3.03e-3	1.05e-3
400	1.16e-2	1.25e-2	1.35e-2	1.45e-2	1.60e-2	1.90e-2		2.40e-2	2.65e-2	2.80e-2	3.05e-2	2.50e-2
500	1.44e-2											
700	1.52e-2											
1000	1.52e-2	1.40e-2	1.70e-2	1.95e-2	2.40e-2	3.30e-2		4.80e-2		7.10e-2	9.30e-2	9.80e-1
2000	1.42e-2											
3000	1.20e-2											
5000	1.10e-2											
10000	8.20e-3											
20000	4.50e-3											
50000	2.70e-3		2.55e-3		4.09e-3			9.68e-3				4.42e-2
100000	1.20e-3											

E ₀ (eV)	85°	87°	88°	89°
1000	3.80e-2	3.60e-4		
50000	8.97e-2	1.54e-1	1.72e-1	7.68e-2

Sputtered energy of Ni by H

program: TESTVMCX
 ne= 1, na= 3

E ₀ (eV)	87°	88°	89°
50000	1.12e-4	1.39e-4	7.97e-5

Particle reflection coefficient of H backscattered from Ni

z1= 1, m1= 1.01, z2=28, m2= 58.71, sbe=4.46 eV, rho= 8.90 g/cm**3
 ef=0.98 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program: TESTVMCX
 ne= 1, na= 3

Bp (eV)	87°	88°	89°
50000	6.69e-1	7.46e-1	9.26e-1

Energy reflection coefficient of H backscattered from Ni

ne= 1, na= 3

E ₀ (eV)	87°	88°	89°
50000	4.20e-1	5.34e-1	8.55e-1

Average depth (mean range) in Å of H implanted in Ni

ne= 1, na= 3

E ₀ (eV)	87°	88°	89°
50000	9.38e+2	9.41e+2	9.35e+2

D Ni

Sputtering yield of Ni by D
 z1= 1, m1= 2.01, z2=28, m2= 58.71, sbe=4.46 eV, rho= 8.90 g/cm**3
 ef=0.98 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: TPP 9/82
 ne=14, na= 1

Ro (eV)	0°
75	3.10e-3
100	7.90e-3
150	1.84e-2
200	2.52e-2
300	3.27e-2
500	4.13e-2
700	3.86e-2
1000	4.03e-2
2000	3.72e-2
3000	3.26e-2
5000	2.64e-2
10000	1.85e-2
50000	6.00e-3
100000	4.00e-3

³He Ni

Sputtering yield of Ni by ³He
 z1= 2, m1 = 3.02, z2=28, m2= 58.71, sbe=4.46 eV, rho=8.90 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: TPP 9/82
 ne=13, na= 1

EO (eV)	0°
40	7.60e-4
50	3.70e-3
70	1.35e-2
100	3.50e-2
200	8.00e-2
300	1.00e-1
750	1.30e-1
1500	1.40e-1
2000	1.40e-1
5000	1.20e-1
20000	5.50e-2
30000	6.47e-2
50000	3.18e-2

He -> Ni

Sputtering yield of Ni by He

z1 = 2, m1 = 4.00, z2 = 28, m2 = 58.71, sbe = 4.46 eV, rho = 8.90 g/cm**3

ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: TESTVMCX, TRSPVICS, TRSPVIC, IPP 9/82

ne = 30, na = 9

E ₀ (eV)	0°	30°	60°	75°	80°	85°	87°	88°	89°
26	4.28e-6								
28	5.49e-5								
30	2.06e-4								
35	1.27e-3								
40	3.27e-3								
50	1.00e-2								
70	2.83e-2								
100	5.38e-2								
150	8.20e-2								
150	7.14e-2								
200	1.02e-1								
200	9.64e-2								
300	1.29e-1								
300	1.20e-1								
500	1.54e-1								
500	1.40e-1								
700	1.54e-1								
1000	1.75e-1								
1000	1.63e-1								
1500	1.68e-1								
2000	1.58e-1								
3000	1.77e-1								
3000	1.48e-1								
5000	1.35e-1								
10000	1.19e-1								
10000	1.03e-1								
20000	6.97e-2								
30000	6.47e-2								
50000	3.64e-2								
100000	2.23e-2	3.28e-2	8.44e-2	2.34e-1	3.27e-1	7.50e-1	9.37e-1	9.98e-1	4.12e-1

Sputtered energy of Ni by He

program: TESTVMCX, TRSPVICS, TRSPVIC

ne = 17, na = 6

E _q (eV)	0°	75°	85°	87°	88°	89°
26	6.35e-8					
28	1.42e-6					
30	3.60e-6					
35	3.37e-5					
40	1.04e-4					
50	3.95e-4					
70	1.18e-3					
100	2.20e-3					
150	3.06e-3					
200	3.41e-3					
300	3.56e-3					
500	3.19e-3					
1000	2.38e-3					
3000	1.15e-3					
10000	3.38e-4					
30000	6.86e-5					
100000		1.99e-4	8.59e-4	9.78e-4	1.08e-3	5.17e-4

He -4- Ni

Particle reflection coefficient of He backscattered from Ni
 z1 = 2. m1 = 4.00, z2=28, m2= 58.71. sbe=4.46 eV, rho = 8.90 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: TESTVMCX, TRSPV1CS, TRSPV1C
 ne=17, na= 6

Ro (eV)	0°	75°	85°	87°	88°	89°
26	6.37e-1					
28	6.27e-1					
30	6.18e-1					
35	5.98e-1					
40	5.81e-1					
50	5.58e-1					
70	5.23e-1					
100	4.91e-1					
150	4.61e-1					
200	4.37e-1					
300	4.13e-1					
500	3.81e-1					
1000	3.30e-1					
3000	2.50e-1					
10000	1.46e-1					
30000	6.06e-2					
100000		3.04e-1	5.76e-1	6.76e-1	7.37e-1	9.26e-1

Energy reflection coefficient of He backscattered from Ni
 ne=17, na= 6

Ro (eV)	0°	75°	85°	87°	88°	89°
26	3.72e-1					
28	3.64e-1					
30	3.57e-1					
35	3.41e-1					
40	3.28e-1					
50	3.09e-1					
70	2.83e-1					
100	2.58e-1					
150	2.37e-1					
200	2.22e-1					
300	2.05e-1					
500	1.83e-1					
1000	1.54e-1					
3000	1.05e-1					
10000	5.32e-2					
30000	1.82e-2					
100000		9.81e-2	3.15e-1	4.43e-1	5.37e-1	8.55e-1

Average depth (mean range) in Å of He implanted in Ni
 ne=17, na= 6

E ₀ (eV)	0°	75°	85°	87°	88°	89°
26	6.79e+0					
28	7.06e+0					
30	7.33e+0					
35	7.98e+0					
40	8.60e+0					
50	9.77e+0					
70	1.19e+1					
100	1.47e+1					
150	1.90e+1					
200	2.27e+1					
300	2.95e+1					
500	4.18e+1					
1000	6.78e+1					
3000	1.60e+2					
10000	4.43e+2					
30000	1.15e+3					
100000		1.24e+3	1.08e+3	1.07e+3	1.08e+3	1.03e+3

Ne -> Ni

Sputtering yield of Ni by Ne

z1 = 10, m1 = 20.18, z2 = 28, m2 = 58.71, sbe = 4.46 eV, rho = 8.90 g/cm**3

ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee2 = 3, ipot = ipotr = 1 (KrC)

program: TESTVMCX, TPP 9/82

ne = 49, na = 18

E ₀ (eV)	0°	5°	10°	15°	20°	25°	30°	40°	45°	50°	55°	60°
18	2.61e-6											
19	1.05e-5											
20	3.01e-5											
22	1.22e-4											
23	2.18e-4											
25	5.44e-4											
25	5.40e-4											
27	1.12e-3											
27	1.11e-3											
28	1.52e-3											
30	2.50e-3											
30	2.00e-3											
35	7.38e-3											
40	1.51e-2											
40	1.30e-2											
50	3.91e-2											
50	3.90e-2											
70	1.08e-1											
70	1.11e-1											
100	2.23e-1											
100	2.38e-1											
150	3.90e-1											
150	4.17e-1											
200	5.32e-1											
200	5.66e-1											
300	7.53e-1											
300	8.05e-1											
500	1.03e-0											
500	1.09e-0											
700	1.29e-0											
1000	1.41e-0											
1000	1.47e-0	1.45e-0	1.52e-0	1.57e-0	1.68e-0	1.80e-0	1.95e-0	2.29e-0	2.50e-0	2.63e-0	2.76e-0	2.82e-0
1500	1.62e-0											
2000	1.75e-0											
3000	1.85e-0											
3000	1.78e-0											
5000	1.90e-0											
7000	1.79e-0											
10000	1.86e-0											
10000	1.81e-0											
15000	1.67e-0											
20000	1.56e-0											
30000	1.48e-0											
30000	1.39e-0											
50000	1.18e-0											
100000	9.33e-1											
100000	8.89e-1											
200000	6.94e-1											
300000	5.00e-1											

E ₀ (eV)	65°	70°	75°	80°	82.5°	89°
1000	2.77e-0	2.44e-0	1.81e-0	7.62e-1	2.93e-1	3.23e-2

Ne → Ni

Sputtered energy of Ni by Ne
 program: TRSTVMCX
 ne = 26, na = 18

R ₀ (eV)	0°	5°	10°	15°	20°	25°	30°	40°	45°	50°	55°	60°
18	1.15e-6											
19	2.88e-6											
20	2.29e-6											
22	9.66e-6											
23	2.10e-5											
25	4.22e-5											
25	4.14e-5											
27	9.91e-5											
27	8.54e-5											
28	1.20e-4											
30	2.00e-4											
35	6.21e-4											
40	1.28e-3											
50	3.24e-3											
70	8.17e-3											
100	1.45e-2											
150	2.03e-2											
200	2.34e-2											
300	2.57e-2											
500	2.56e-2											
1000	2.26e-2											
1000	2.27e-2	2.17e-2	2.38e-2	2.59e-2	2.88e-2	3.25e-2	3.81e-2	5.12e-2	6.15e-2	7.29e-2	8.13e-2	9.37e-2
3000	1.52e-2											
10000	7.18e-3											
30000	3.12e-3											
100000	7.92e-4											

R ₀ (eV)	65°	70°	75°	80°	82.5°	89°
1000	1.02e-1	1.03e-1	8.78e-2	4.19e-2	1.50e-2	9.96e-4

Ne -> Ni

Particle reflection coefficient of Ne backscattered from Ni
 z1 = 10. m1 = 20.18. z2 = 28. m2 = 58.71. sbe = 4.46 eV. rho = 8.90 g/cm**3
 ef = 0.50 eV. esb = 0.00 eV. ca = 1.00. kk0 = kk0r = 2. kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrC)
 program: TESTVMCX
 ne = 25. na = 18

E ₀ (eV)	0°	5°	10°	15°	20°	25°	30°	40°	45°	50°	55°	60°
18	5.48e-1											
19	5.47e-1											
20	5.45e-1											
22	5.41e-1											
25	5.33e-1											
25	5.51e-1											
27	5.28e-1											
27	5.54e-1											
28	5.40e-1											
30	5.16e-1											
35	5.01e-1											
40	4.86e-1											
50	4.56e-1											
70	4.08e-1											
100	3.57e-1											
150	3.12e-1											
200	2.83e-1											
300	2.48e-1											
500	2.13e-1											
1000	1.79e-1											
1000	1.59e-1	1.68e-1	1.70e-1	1.79e-1	1.90e-1	2.01e-1	2.15e-1	2.66e-1	3.08e-1	3.37e-1	3.97e-1	4.55e-1
3000	1.31e-1											
10000	8.58e-2											
30000	5.52e-2											
100000	2.60e-2											

Bq (eV)	65°	70°	75°	80°	82.5°	89°
1000	5.37e-1	6.46e-1	7.79e-1	9.35e-1	9.83e-1	1.00e-0

Energy reflection coefficient of Ne backscattered from Ni
 ne = 25. na = 18

E ₀ (eV)	0°	5°	10°	15°	20°	25°	30°	40°	45°	50°	55°	60°
18	1.08e-1											
19	1.09e-1											
20	1.09e-1											
22	1.10e-1											
25	1.10e-1											
25	1.10e-1											
27	1.10e-1											
27	1.10e-1											
28	1.09e-1											
30	1.08e-1											
35	1.07e-1											
40	1.05e-1											
50	9.94e-2											
70	9.03e-2											
100	7.97e-2											
150	6.87e-2											
200	6.15e-2											
300	5.35e-2											
500	4.48e-2											
1000	3.66e-2											
1000	3.35e-2	3.52e-2	3.61e-2	3.93e-2	4.26e-2	4.91e-2	5.58e-2	8.05e-2	1.02e-1	1.23e-1	1.62e-1	2.08e-1
3000	2.65e-2											
10000	1.71e-2											
30000	1.06e-2											
100000	4.54e-3											

E ₀ (eV)	65°	70°	75°	80°	82.5°	89°
1000	2.78e-1	3.89e-1	5.57e-1	7.93e-1	9.02e-1	9.70e-1

Ne → Ni

Average depth (mean range) in Å of Ne implanted in Ni
 21= 10, m1= 20.18, z2=28, m2= 58.71, sbe=4.46 eV, rho = 8.90 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 program: TESTVMCX
 ne=25, na= 18

E ₀ (eV)	0°	5°	10°	15°	20°	25°	30°	40°	45°	50°	55°	60°
18	1.73e+0											
19	1.80e+0											
20	1.87e+0											
22	1.99e+0											
25	2.16e+0											
25	2.21e+0											
27	2.26e+0											
27	2.31e+0											
28	2.36e+0											
30	2.41e+0											
35	2.64e+0											
40	2.84e+0											
50	3.22e+0											
70	3.87e-f-0											
100	4.69e+0											
150	5.90e+0											
200	6.93e+0											
300	8.76e+0											
500	1.19e+1											
1000	1.83e+1											
1000	1.94e+1	1.94e+1	1.91e+1	1.91e+1	1.88e+1	1.85e+1	1.81e+1	1.72e+1	1.70e+1	1.64e+1	1.59e+1	1.55e+1
3000	3.81e+1											
10000	9.50e+1											
30000	2.47e+2											
100000	7.48e+2											

E ₀ (eV)	65°	70°	75°	80°	82.5°	89°
1000	1.50e+1	1.48e+1	1.41e+1	1.35e+1	1.40e+1	8.58e+0

Ar → Ni

Sputtering yield of Ni by Ar

z1 = 18, m1 = 39.95, z2 = 28, m2 = 58.71, sbe = 4.46 eV, rho = 8.90 g/cm**3
 ef = 0.20 (0.5) eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: TRS1C, TESTVMCX, TRVMC, TRSPV1C, TPP 9/82, newtrspd, trsplcn
 ne = 42, na = 8

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°	80°
18	3.92e-6							
19	1.45e-5							
20	2.02e-5		9.43e-4				6.41e-4	
22	7.61e-5							
25	1.51e-4		4.47e-3				2.17e-3	
27	3.44e-4							
30	5.39e-4		1.27e-2				4.37e-3	
32	9.48e-4							
35	1.54e-3							
40	3.43e-3		4.35e-2				1.13e-2	
50	1.30e-2		8.87e-2				2.05e-2	
50	1.16e-2							
60	2.92e-2							
70	5.21e-2		2.03e-1				4.34e-2	
70	5.35e-2							
100	1.49e-1		3.87e-1				8.27e-2	
100	1.60e-1							
150	3.52e-1							
200	4.93e-1		9.25e-1				2.53e-1	
200	5.32e-1							
290	7.65e-1	1.09e-0	1.32e-0	1.33e-0	1.29e-0	1.19e-0	4.30e-1	
300	7.78e-1	1.12e-0	1.35e-0	1.38e-0	1.35e-0	1.25e-0	4.49e-1	1.32e-1
300	8.51e-1							
500	1.19e-0		2.02e-0				8.71e-1	
500	1.29e-0							
700	1.61e-0							
1000	1.80e-0		3.15e-0				1.95e-0	
1000	1.90e-0							
1000	1.97e-0	2.70e-0	3.32e-0			3.62e-0	2.05e-0	
2000	2.49e-0							
3000	2.69e-0							
3000	2.70e-0							
10000	3.25e-0							
10000	3.13e-0							
20000	2.88e-0							
30000	3.06e-0							
30000	2.92e-0							
50000	2.81e-0							
100000	2.48e-0							
100000	2.24e-0							
200000	1.82e-0							
300000	1.64e-0							

Ar → Ni

Sputtered energy of Ni by Ar
 z1= 18. m1= 39.95. z2=28. m2= 58.71. sbe=4.46 eV. rho=8.90 g/cm**3
 efs=0.20 (0.5) eV. esb=0.00 eV. ca=1.00. kk0=kk0r=2. kdee1=kdee2 = 3. ipot=ipot=1 (KrC)
 program: TRS1C. TESTVMCX. TRVMC. TRSPVIC. newtrspd. trsplcn
 ne=24. na= 8

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°	80°
18	3.92e-6							
19	1.45e-5							
20	2.02e-5		9.43e-4				6.41e-4	
22	7.61e-5							
25	1.51e-4		4.47e-3				2.17e-3	
27	3.44e-4							
30	5.39e-4		1.27e-2				4.37e-3	
32	9.48e-4							
35	1.54e-3							
40	3.43e-3		4.35e-2				1.13e-2	
50	1.30e-2		8.87e-2				2.05e-2	
50	1.16e-2							
60	2.92e-2							
70	5.21e-2		2.03e-1				4.34e-2	
70	5.35e-2							
100	1.49e-1		3.87e-1				8.27e-2	
100	1.60e-1							
150	3.52e-1							
200	4.93e-1		9.25e-1				2.53e-1	
200	5.32e-1							
290	7.65e-1	1.09e-0	1.32e-0	1.33e-0	1.29e-0	1.19e-0	4.30e-1	
300	7.78e-1	1.12e-0	1.35e-0	1.38e-0	1.35e-0	1.25e-0	4.49e-1	1.32e-1
300	8.51e-1							
500	1.19e-0		2.02e-0				8.71e-1	
500	1.29e-0							
700	1.61e-0							
1000	1.80e-0		3.15e-0				1.95e-0	
1000	1.90e-0							
1000	1.97e-0	2.70e-0	3.32e-0			3.62e-0	2.05e-0	
2000	2.49e-0							
3000	2.69e-0							
3000	2.70e-0							
10000	3.25e-0							
10000	3.13e-0							
20000	2.88e-0							
30000	3.06e-0							
30000	2.92e-0							
50000	2.81e-0							
100000	2.48e-0							
100000	2.24e-0							
200000	1.82e-0							
300000	1.64e-0							

Ar → Ni

Particle reflection coefficient of Ar backscattered from Ni
 z1=18, m1=39.95, z2=28, m2=58.71, sbe=4.46 eV, rho=8.90 g/cm**3
 ef=0.20 (0.5) eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel=kdee2=3, ipot=ipot=1 (KrC)
 program: TRS1C, TESTVMCX, TRVMC, TRSPV1C newtrspd, trsplcn
 ne=24, na=8

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°	80°
18	2.61e-1							
19	2.55e-1							
20	2.51e-1		6.15e-1				9.85e-1	
22	2.43e-1							
25	2.34e-1		6.07e-1				9.85e-1	
27	2.29e-1							
30	2.24e-1		5.97e-1				9.85e-1	
32	2.21e-1							
35	2.18e-1							
40	2.12e-1		5.82e-1				9.84e-1	
50	2.05e-1		5.68e-1				9.83e-1	
60	2.00e-1							
70	1.97e-1		5.41e-1				9.81e-1	
100	1.83e-1		5.02e-1				9.77e-1	
200	1.52e-1		4.20e-1				9.59e-1	
290	1.35e-1	2.23e-1	3.64e-1	4.35e-1	5.27e-1	6.17e-1	9.42e-1	
300	1.37e-1	2.23e-1	3.62e-1	4.31e-1	5.16e-1	6.09e-1	9.38e-1	9.92e-1
500	1.13e-1		3.02e-1				8.95e-1	
1000	8.44e-2		2.41e-1				7.97e-1	
1000	7.71e-2	1.31e-1	2.21e-1			4.11e-1	8.00e-1	
3000	5.77e-2							
10000	3.65e-2							
30000	2.43e-2							
100000	1.01e-2							

Energy reflection coefficient of Ar backscattered from Ni
 ne=24, na=8

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°	80°
18	1.09e-2							
19	1.12e-2							
20	1.14e-2		1.49e-1				6.78e-1	
22	1.19e-2							
25	1.25e-2		1.53e-1				6.91e-1	
27	1.27e-2							
30	1.31e-2		1.56e-1				6.98e-1	
32	1.34e-2							
35	1.37e-2							
40	1.40e-2		1.59e-1				7.09e-1	
50	1.43e-2		1.59e-1				7.15e-1	
60	1.44e-2							
70	1.42e-2		1.53e-1				7.20e-1	
100	1.34e-2		1.42e-1				7.20e-1	
200	1.13e-2		1.14e-1				6.99e-1	
290	9.74e-3	3.38e-2	9.44e-2	1.34e-1	1.95e-1	2.69e-1	6.73e-1	
300	9.82e-3	3.34e-2	9.31e-2	1.31e-1	1.87e-1	2.62e-1	6.74e-1	8.49e-1
500	8.48e-3		7.14e-2				6.26e-1	
1000	6.22e-3		5.29e-2				5.26e-1	
1000	5.79e-3	1.84e-2	4.94e-2			1.52e-1	5.28e-1	
3000	4.27e-3							
10000	3.04e-3							
30000	2.11e-3							
100000	8.23e-4							

Average depth (mean range) in Å of Ar implanted in Ni
 ne=24, na=8

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°	80°
18	1.11e+0							
19	1.15e+0							
20	1.19e+0		1.02e+0				5.29e-1	
22	1.27e+0							
25	1.39e+0		1.20e+0				6.05e-1	
27	1.47e+0							
30	1.58e+0		1.36e+0				6.93e-1	
32	1.65e+0							
35	1.76e+0							
40	1.93e+0		1.66e+0				8.80e-1	
50	2.24e+0		1.93e+0				1.03e+0	
60	2.54e+0							
70	2.80e+0		2.40e+0				1.36e+0	
100	3.51e+0		3.00e+0				1.81e+0	
200	5.30e+0		4.50e+0				3.01e+0	
290	6.57e+0	6.04e+0	5.47e+0	5.30e+0	5.07e+0	4.83e+0	3.86e+0	
300	6.69e+0	6.18e+0	5.57e+0	5.39e+0	5.16e+0	4.91e+0	3.96e+0	3.29e+0
500	8.93e+0		7.38e+0				5.38e+0	
1000	1.33e+1		1.08e+1				8.12e+0	
1000	1.20e+1	1.09e+1	1.21e+1			1.08e+1	9.39e+0	
3000	2.63e+1							
10000	6.03e+1							
30000	1.42e+2							
100000	4.23e+2							

Ar -> Ni

Sputtering yield of Ni by Ar

z1=18, m1=39.95, z2=28, m2=58.71, sbe=4.46 eV, rho=8.90 g/cm**3
 ef=0.20, esb=0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=3 (ZBL)
 program: TRVMC
 ne=7, na=7

Bo (eV)	0°	30°	45°	50°	55°	60°	75°
50	1.10e-2		6.83e-2				
70	4.61e-2		1.62e-1				
100	1.38e-1		3.31e-1				
200	5.06e-1		8.55e-1				
290	7.80e-1	1.06e-0	1.26e-0	1.25e-0	1.22e-0	1.10e-0	3.88e-1
500	1.32e-0		1.99e-0				
1000	2.04e-0		3.21e-0				

Sputtered energy of Ni by Ar

ne=7, na=7

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°
50	7.04e-4		9.70e-3				
70	2.95e-3		2.20e-2				
100	7.95e-3		4.07e-2				
200	2.13e-2		7.90e-2				
290	2.57e-2	5.47e-2	9.43e-2	1.06e-1	1.13e-1	1.16e-1	4.94e-2
500	3.02e-2		1.03e-1				
1000	2.97e-2		1.00e-1				

Particle reflection coefficient of Ar backscattered from Ni

z1=18, m1=39.95, z2=28, m2=58.71, sbe=4.46 eV, rho=8.90 g/cm**3
 ef=0.20, esb=0.00, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=3 (ZBL)
 program: TRVMC
 ne=7, na=7

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°
50	0.41		5.82e-1				
70	0.22		5.61e-1				
100	0.11		5.20e-1				
200	0.07		4.33e-1				
290	0.06	2.32e-1	3.69e-1	4.48e-1	5.33e-1	6.35e-1	9.44e-1
500	0.05		3.04e-1				
1000	0.04		2.27e-1				

Energy reflection coefficient of Ar backscattered from Ni

ne=7, na=7

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°
50	1.29e-2		1.47e-1				
70	1.32e-2		1.48e-1				
100	1.35e-2		1.39e-1				
200	1.22e-2		1.15e-1				
290	9.96e-3	3.52e-2	9.26e-2	1.35e-1	1.90e-1	2.69e-1	6.68e-1
500	8.53e-3		7.27e-2				
1000	6.56e-3		5.15e-2				

Average depth (mean range) in Å of Ar implanted in Ni

ne=7, na=7

E ₀ (eV)	0°	30°	45°	50°	55°	60°	75°
50	1.58e+0		1.33e+0				
70	2.08e+0		1.73e+0				
100	2.71e+0		2.27e+0				
200	4.36e+0		3.64e+0				
290	5.55e+0	5.12e+0	4.49e+0	4.42e+0	4.13e+0	3.92e+0	3.09e+0
500	7.76e+0		6.30e+0				
1000	1.19e+1		9.62e+0				

Ni → Ni

Sputtering yield of Ni by Ni

z1=28, m1 = 58.71, z2=28, m2= 58.71, sbe=4.46 eV, rho=8.90 g/cm**3

ef=4.41 eV, esb=4.46 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: TESTVMCX, TRSPV1C, TRSPV1CS, IPP 9/82

ne=26, na=13

E ₀ (eV)	0°	15°	30°	45°	50°	55°	60°	65°	70°	75°	80°	85°	87°
14										1.20e-3			
15	2.49e-6												
16										2.93e-3			
18	1.51e-5												
20	3.72e-5									8.86e-3			
25	1.79e-4									2.00e-2			
30	5.33e-4									3.28e-2			
40	2.63e-3									6.01e-2			
50	8.72e-3									1.13e-1			
60													
70	3.63e-2												
80										1.56e-1			
100	1.08e-1									1.98e-1			
100	1.24e-1									2.90e-1			
200	4.08e-1									4.04e-1			
500	1.16e-0									1.07e-0			
1000	1.89e-0									2.18e-0			
1000	2.03e-0									2.30e-0			
2000	2.81e-0									4.24e-0			
2500	2.90e-0	3.22e-0								5.19e-0			
3000	3.06e-0												
5000	3.63e-0									8.72e-0			
10000	4.11e-0									1.29e+1			
30000	4.40e-0									2.02e+1			
100000	4.20e-0									2.41e+1			
300000	3.05e-0												

Sputtered energy of Ni by Ni

program: TESTVMCX, TRSPV1C, TRSPV1CS

ne=23, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	85°
14								4.09e-4	
15	9.94e-6								
16								6.05e-4	
18	4.18e-6								
20	4.61e-6							1.92e-3	
25	1.17e-5							4.36e-3	
30	2.92e-5							7.41e-3	
40	1.53e-4							1.33e-2	
50	4.80e-4								
60								2.35e-2	
70	1.86e-3								
80								3.07e-2	
100	4.81e-3							3.65e-2	
200	1.31e-2							5.72e-2	
500	2.26e-2							9.95e-2	
1000	2.42e-2							1.38e-1	
2000								1.75e-1	
2500	2.14e-2	2.73e-2						1.81e-1	1.31e-2
3000	2.10e-2								
5000								1.93e-1	
10000	1.43e-2							1.87e-1	
30000	8.56e-3							1.53e-1	
100000	4.24e-3							1.07e-1	

Ni -4- Ni

Particle reflection coefficient of Ni backscattered from Ni
 z1=28, m1 = 58.71, z2=28, m2= 58.71, sbe=4.46 eV, rho = 8.90 g/cm**3
 ef=4.41 eV, esb = 4.46 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: TESTVMCX, TRSPVIC, TRSPVICS
 ne=23, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	85°
14								1.42e-2	
15	1.45e-7							3.16e-2	
16									
18	7.47e-7							8.73e-2	
20	5.50e-7							1.87e-1	
25								2.99e-1	
30	2.75e-6							5.02e-1	
40	1.24e-4								
50	5.72e-4								
60								7.39e-1	
70	2.69e-3								
80								8.31e-1	
100	6.13e-3							8.65e-1	
200	1.39e-2							8.98e-1	
500	2.16e-2							8.59e-1	
1000	2.15e-2							7.81e-1	
2000								6.75e-1	
2500	1.90e-2	2.62e-2	5.30e-2	1.20e-1	2.09e-1	2.71e-1	3.62e-1	6.32e-1	9.93e-1
3000	1.76e-2								
5000								5.24e-1	
10000	1.23e-2							4.37e-1	
30000	8.27e-3							3.82e-1	
100000	4.00e-3							3.16e-1	

Energy reflection coefficient of Ni backscattered from Ni
 ne=23, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	85°
14								3.87e-3	
15	6.08e-6							9.38e-3	
16									
18	1.63e-6							2.85e-2	
20	1.62e-6							6.63e-2	
25								1.13e-1	
30	1.50e-7							2.08e-1	
40	7.34e-6								
50	4.27e-5								
60								3.50e-1	
70	1.89e-4								
80								4.34e-1	
100	3.98e-4							4.79e-1	
200	7.14e-4							5.56e-1	
500	8.74e-4							5.48e-1	
1000	8.32e-4							4.84e-1	
2000								3.88e-1	
2500	7.22e-4	1.39e-3	4.85e-3	1.88e-2	4.85e-2	7.60e-2	1.26e-1	3.55e-1	9.12e-1
3000	6.28e-4								
5000								2.64e-1	
10000	4.57e-4							2.09e-1	
30000	4.46e-4							1.66e-1	
100000	1.86e-4							1.33e-1	

Average depth (mean range) in Å of Ni implanted in Ni
 ne=23, na= 9

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	75°	85°
15	4.63e-1								
18	6.47e-1								
20	7.44e-1								
25	9.41e-1								
30	1.12e+0								
40	1.47e+0							2.40e-2	
50	1.76e+0								
60								2.77e-1	
70	2.27e+0								
80								5.74e-1	
100	2.91e+0							8.09e-1	
200	4.52e+0							1.79e+0	
500	7.84e+0							3.83e+0	
1000	1.16e+1							6.00e+0	
2000								9.11e+0	
2500	1.99e+1	1.94e+1	1.77e+1	1.54e+1	1.37e+1	1.29e+1	1.21e+1	1.04e+1	8.13e+0
3000	2.24e+1								
5000								1.59e+1	
10000	4.79e+1							2.41e+1	
30000	1.05e+2							5.00e+1	
100000	2.85e+2							1.26e+2	

Kr → Ni

Sputtering yield of Ni by Kr

zl=36. ml = 83.80. z2=28. m2= 58.71. sbe=4.46 eV. rho=8.90 g/cm**3
 ef=0.50 eV. esb=0.00 eV. ca=1.00. kk0=kk0r=2. kdec1 = kdec2=3. ipot=ipotrl=1 (KrC)
 program: TESTVMCX, IPP 9/82
 ne= 20, na= 2

E ₀ (eV)	0°	75°
20		8.09e-4
22	5.93e-6	
25	2.19e-5	
30	1.08e-4	6.12e-3
40	8.67e-4	1.54e-2
50	3.02e-3	2.77e-2
70	1.65e-2	5.96e-2
100	6.46e-2	1.14e-1
100	6.36e-2	
150	1.80e-1	
200	3.07e-1	3.32e-1
300	6.34e-1	
500	1.01e-0	1.07e-0
1000	1.93e-0	2.23e-0
2000		4.49e-0
3000	3.26e-0	
5000		9.48e-0
10000	4.43e-0	1.50e+1
30000	5.06e-0	2.36e+1
100000	4.99e-0	

Sputtered energy of Ni by Kr

program: TESTVMCX

ne=16, na= 2

E ₀ (eV)	0°	75°
20		1.53e-4
22	3.32e-6	
25	1.48e-6	
30	4.16e-6	1.24e-3
40	3.88e-5	3.05e-3
50	1.28e-4	5.44e-3
70	6.78e-4	1.08e-2
100	2.41e-3	1.87e-2
150	5.81e-3	
200	8.96e-3	4.36e-2
500	1.81e-2	9.66e-2
1000		1.42e-1
2000		1.89e-1
5000		2.16e-1
10000		2.16e-1
30000		1.83e-1

Kr → Ni

Particle reflection coefficient of Kr backscattered from Ni
 z1=36, m1= 83.80, z2=28, m2= 58.71. sbe=4.46 eV, rho = 8.90 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: TESTVMCX
 ne=16, na= 2

E ₀ (eV)	0°	75°
20		9.77e-1
22	1.86e-1	
25	1.60e-1	
30	1.28e-1	9.78e-1
40	8.98e-2	9.77e-1
50	6.78e-2	9.76e-1
70	4.42e-2	9.73e-1
100	2.79e-2	9.69e-1
150	1.56e-2	
200	1.05e-2	9.50e-1
500	5.00e-3	8.91e-1
1000		8.07e-1
2000		6.83e-1
5000		5.29e-1
10000		4.31e-1
30000		3.57e-1

Energy reflection coefficient of Kr backscattered from Ni
 ne=16, na= 2

E ₀ (eV)	0°	75°
20		5.58e-1
22	6.62e-5	
25	7.65e-5	
30	1.04e-4	5.82e-1
40	1.33e-4	5.94e-1
50	1.45e-4	6.02e-1
70	1.58e-4	6.11e-1
100	1.50e-4	6.14e-1
150	1.28e-4	
200	1.09e-4	6.02e-1
500	7.86e-5	5.46e-1
1000		4.70e-1
2000		3.66e-1
5000		2.50e-1
10000		1.75e-1
30000		1.34e-1

Average depth (mean range) in Å of Kr implanted in Ni
 ne=16, na= 2

E ₀ (eV)	0°	75°
20		4.33e-1
22	1.17e+0	
25	1.27e+0	
30	1.45e+0	5.39e-1
40	1.79e+0	6.37e-1
50	2.08e+0	7.38e-1
70	2.60e+0	9.34e-1
100	3.27e+0	1.23e+0
150	4.17e+0	
200	4.94e+0	2.03e+0
500	8.26e+0	3.80e+0
1000		5.75e+0
2000		8.54e+0
5000		1.39e+1
10000		2.11e+1
30000		4.14e+1

Xe -4- Ni

Sputtering yield of Ni by Xe

z1=54, m1 = 131.30, z2=28, m2= 58.71, sbe=4.46 eV, rho= 8.90 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kkO= kkOr=2; kdee1 = kdee2 = 3, ipot=ipotr=:1 (KrC)
 program: TESTVMCX, IPP 9/82 '
 ne=38, na= 2

E ₀ (eV)	0°	60°
15		7.78e-6
18		1.52e-4
20		5.87e-4
25	6.23e-6	4.38e-3
30	3.83e-5	1.34e-2
40	3.53e-4	4.56e-2
50	1.36e-3	9.03e-2
70	8.28e-3	2.00e-1
70	6.40e-3	
100	3.66e-2	3.90e-1
100	3.47e-2	
150	1.22e-1	
200	2.19e-1	9.61e-1
200	2.39e-1	
300	4.25e-1	
300	4.88e-1	
500	8.13e-1	2.34e-0
500	9.68e-1	
1000	1.60e-0	4.16e-0
1000	1.77e-0	
1500	2.40e-0	
2000	2.60e-0	6.81e-0
2000	2.82e-0	
3000	3.44e-0	
5000	3.98e-0	1.17e+1
5000	4.18e-0	
7000	4.78e-0	
10000	5.20e-0	1.55e+1
10000	4.95e-0	
15000	5.67e-0	
20000	5.98e-0	1.94e+1
20000	5.90e-0	
30000	6.53e-0	
50000	7.06e-0	2.38e+1
50000	6.63e-0	
100000	7.18e-0	2.41e+1
100000	6.76e-0	
200000	6.79e-0	

Sputtered energy of Ni by Xe

program: TESTVMCX

ne=19, na= 2

E ₀ (eV)	0°	60°
15		7.19e-6
18		1.83e-5
20		7.12e-5
25	1.92e-6	7.52e-4
30	3.64e-6	1.86e-3
40	1.38e-5	6.73e-3
50	4.75e-5	1.34e-2
70	2.95e-4	2.92e-2
100	1.24e-3	5.36e-2
200	5.76e-3	1.04e-1
300	8.98e-3	
500	1.38e-2	1.58e-1
1000	1.85e-2	1.79e-1
2000	1.96e-2	1.77e-1
5000	1.76e-2	1.59e-1
10000	1.57e-2	1.45e-1
20000	1.25e-2	1.24e-1
50000	9.31e-2	1.03e-1
100000	6.41e-2	8.22e-2

Xe -> Ni

Particle reflection coefficient of Xe backscattered from Ni
 z1=54, l1l1= 131.30, z2=28, m2 = 58.71, sbe = 4.46 eV, rho=8.90 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 program: TESTVMCX
 ne=18, na= 2

E ₀ (eV)	0°	60°
15		6.67e-1
18		6.60e-1
20		6.56e-1
25	1.20e-1	6.48e-1
30	8.73e-2	6.38e-1
40	4.86e-2	6.31e-1
50	2.87e-2	6.18e-1
70	1.17e-2	5.99e-1
100	3.34e-3	5.70e-1
200	1.00e-4	4.98e-1
500		3.67e-1
1000		2.63e-1
2000		2.04e-1
5000		1.31e-1
10000		1.10e-1
20000		8.46e-2
50000		7.20e-2
100000		4.96e-3

Energy reflection coefficient of Xe backscattered from Ni
 ne=18, na= 2

E ₀ (eV)	0°	60°
15		1.18e-1
18		1.22e-1
20		1.25e-1
25	1.43e-6	1.29e-1
30	4.90e-7	1.33e-1
40	1.94e-6	1.39e-1
50	1.67e-6	1.39e-1
70	1.52e-6	1.39e-1
100	1.03e-6	1.36e-1
200	1.16e-6	1.19e-1
500		8.11e-2
1000		5.13e-2
2000		3.33e-2
5000		1.68e-2
10000		1.39e-2
20000		1.03e-2
50000		8.15e-3
100000		5.77e-3

Average depth (mean range) in Å of Xe implanted in Ni
 ne=19, na= 2

E ₀ (eV)	0°	60°
15		5.83e-1
18		6.44e-1
20		6.84e-1
25	1.47e+0	7.79e-1
30	1.69e+0	8.71e-1
40	2.10e+0	1.05e+0
50	2.46e+0	1.23e+0
70	3.10e+0	1.54e+0
100	3.91e+0	1.97e+0
200	5.93e+0	3.08e+0
300	7.37e+0	
500	9.64e+0	5.18e+0
1000	1.36e+1	7.44e+0
2000	1.92e+1	1.05e+1
5000	3.08e+1	1.67e+1
10000	4.50e+1	2.46e+1
20000	6.65e+1	3.65e+1
50000	1.19e+2	6.32e+1
100000	1.93e+2	1.02e+2

H -> Cu

Sputtering yield of Cu by H

z1= 1, m1 = 1.01, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.98 eV, esb =1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 3, 4, kdee2=3, ipot=ipotr=1 (KrC)
 program: TESTVMCX, TPP 9/82
 ne=16, na=10

E ₀ (eV)	0°	30°	50°	70°	78°	80°	85°	87°	88°	89°
80	1.57e-4									
100	1.01e-3									
150	4.82e-3									
200	8.89e-3									
300	1.39e-2									
500	2.10e-2									
1000	1.95e-2									
2000	1.80e-2									
5000	1.40e-2									
10000	9.68e-3									
20000	3.20e-3									
26700	5.10e-3									
40000	2.80e-3									
50000	3.01e-3	3.87e-3	7.02e-3	2.27e-2	3.87e-2	6.02e-2	1.22e-1	1.75e-1	1.97e-1	9.74e-2
80000	2.30e-3									
100000	2.20e-3									

Sputtered energy of Cu by H

program: TESTVMCX
 ne= 9, na= 6

E ₀ (eV)	0°	80°	85°	87°	88°	89°
80	9.12e-7					
100	8.93e-6					
150	5.37e-5					
200	1.03e-4					
300	1.55e-4					
1000	1.34e-4					
2000	7.86e-5					
10000	9.70e-6					
50000		3.58e-5	7.65e-5	1.13e-4	1.35e-4	8.36e-5

Particle reflection coefficient of H backscattered from Cu

z1= 1, m1 = 1.01, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.98 eV, esb =1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 3, 4, kdee2=3, ipot=ipotr=1 (KrC)
 program: TESTVMCX
 ne= 9, na= 6

B ₀ (eV)	0°	80°	85°	87°	88°	89°
80	5.62e-1					
100	5.46e-1					
150	5.14e-1					
200	4.94e-1					
300	4.62e-1					
1000	3.48e-1					
2000	2.74e-1					
10000	9.79e-2					
50000		4.13e-1	5.78e-1	6.71e-1	7.45e-1	9.17e-1

Energy reflection coefficient of H backscattered from Cu

ne= 9, na= 6

E ₀ (eV)	0°	80°	85°	87°	88°	89°
80	3.41e-1					
100	3.26e-1					
150	2.98e-1					
200	2.80e-1					
300	2.54e-1					
1000	1.69e-1					
2000	1.20e-1					
10000	3.14e-2					
50000		1.62e-1	3.08e-1	4.26e-1	5.37e-1	8.40e-1

Average depth (mean range) in Å of H implanted in Cu

ne= 9, na= 6

E ₀ (eV)	0°	80°	85°	87°	88°	89°
80	2.58e+1					
100	2.94e+1					
150	3.75e+1					
200	4.47e+1					
300	5.76e+1					
1000	1.29e+2					
2000	2.15e+2					
10000	7.61e+2					
50000		1.06e+3	9.98e+2	9.85e+2	9.79e+2	1.01e+3

D -> Cu

Sputtering yield of Cu by D

z1 = 1, m1 = 2.01, z2 = 29, m2 = 63.54, sbe = 3.52 eV, rho = 8.95 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx, IPP 9/82, newtrim
 ne = 28, na = 11

E ₀ (eV)	0°	30°	45°	60°	65°	70°	75°	77.5°	80°	85°	87°
37	2.80e-5										
40	1.43e-4		1.10e-4								
42	2.89e-4										
45	5.69e-4		4.68e-4								
47	8.71e-4		7.56e-4								
50	1.47e-3		1.26e-3	7.31e-4	5.60e-4	3.10e-4	1.31e-4		3.85e-5		
53					8.95e-4						
55			2.27e-3								
60	3.56e-3										
70	6.24e-3						1.34e-3				
75	8.80e-3								6.39e-4		
80	9.39e-3										
100	1.64e-2	1.81e-2	1.84e-2	1.71e-2	1.49e-2		8.95e-3		3.60e-3		
120	2.17e-2										
150	2.59e-2										
200	3.50e-2						6.57e-2				
250	4.06e-2										
300	4.34e-2	5.52e-2	6.39e-2	9.37e-2	1.05e-1		1.24e-1	1.09e-1	8.55e-2		
500	4.62e-2										
1000	5.39e-2	6.93e-2	9.19e-2	1.44e-1	1.75e-1		2.50e-1		2.58e-1	1.00e-1	
2000	5.16e-2				1.85e-1						
2000	4.83e-2										
3000	3.93e-2		8.51e-2	1.39e-1	1.62e-1		2.70e-1		3.34e-1	3.04e-1	
10000	2.47e-2		5.45e-2		1.13e-1		1.92e-1		2.85e-1	4.16e-1	3.47e-1
30000	9.31e-3										
53000	6.10e-3										
80000	6.20e-3										
160000	2.90e-3										

Sputtered energy of Cu by D

program: testvmcx, newtrim
 ne = 15, na = 8

E ₀ (eV)	0°	30°	45°	60°	65°	75°	77.5°	80°
40			9.90e-7					
45			6.20e-6					
47			1.09e-5					
50				1.16e-5		1.94e-6		5.60e-7
53					1.51e-5			
55			4.17e-5					
70						2.83e-5		
75								1.36e-5
100		4.19e-4		4.13e-4				
200	7.16e-4					1.62e-3		
300	7.60e-4	9.23e-4		1.74e-3			2.53e-3	
500	6.15e-4							
1000	4.75e-4		8.33e-4	1.45e-3		2.99e-3		
2000	2.63e-4				1.24e-3			
3000	1.69e-4		3.78e-4	7.05e-4		1.47e-3		

D -> Cu

Particle reflection coefficient of D backscattered from Cu
 $z1 = 1$, $m1 = 2.01$, $z2 = 29$, $m2 = 63.54$, $sbe = 3.52$ eV, $\rho = 8.95$ g/cm³
 $ef = 0.98$ eV, $esb = 1.00$ eV, $ca = 1.00$, $kk0 = kk0r = 2$, $kdee1 = kdee2 = 3$, $ipotr = ipotr = 1$ (KrC)
 program: testvmcx, newtrim
 $ne = 15$, $na = 8$

B ₀ (eV)	0°	30°	45°	60°	65°	75°	77.5°	80°
40			7.09e-1					
45			6.99e-1					
47			6.95e-1					
50				7.98e-1		9.48e-1		9.83e-1
53					8.40e-1			
55			6.81e-1					
70						9.32e-1		
75								9.77e-1
100		5.74e-1		7.35e-1				
200	4.87e-1					8.44e-1		
300	4.53e-1	5.00e-1		6.49e-1			8.50e-1	
500	4.21e-1							
1000	3.59e-1		4.75e-1	5.65e-1		7.01e-1		
2000	2.91e-1				5.49e-1			
3000	2.45e-1		3.67e-1	4.71e-1		6.19e-1		

Energy reflection coefficient of D backscattered from Cu
 $ne = 15$, $na = 8$

B ₀ (eV)	0°	30°	45°	60°	65°	75°	77.5°	80°
40			5.09e-1					
45			4.97e-1					
47			3.92e-1					
50				6.32e-1		8.67e-1		9.35e-1
53					6.22e-1			
55			4.70e-1					
70						8.43e-1		
75								8.18e-1
100		3.55e-1		5.50e-1				
200	2.76e-1					7.17e-1		
300	2.50e-1	2.90e-1		4.48e-1			7.28e-1	
500	2.25e-1							
1000	1.81e-1		2.72e-1	3.60e-1		5.24e-1		
2000	1.34e-1				3.45e-1			
3000	1.08e-1		1.85e-1	2.67e-1		4.21e-1		

Average depth (mean range) in A of D implanted in Cu
 $ne = 15$, $na = 8$

B ₀ (eV)	0°	30°	45°	60°	65°	75°	77.5°	80°
40			1.60e+1					
45			1.71e+1					
47			1.61e+1					
50				1.79e+1		1.75e+1		1.74e+1
53					1.80e+1			
55			1.89e+1					
70						2.14e+1		
75								2.19e+1
100		2.79e+1		2.71e+1				
200	4.47e+1					4.11e+1		
300	5.84e+1	5.69e+1		5.45e+1			5.31e+1	
500	8.33e+1							
1000	1.39e+2		1.31e+2	1.24e+2		1.20e+2		
2000	2.37e+2				2.03e+2			
3000	3.28e+2		2.99e+2	2.78e+2		2.70e+2		

D on Cu, Maxwellian velocity distribution, sheath potential 3 kT
 $z1 = 1$, $m1 = 2.01$, $z2 = 29$, $m2 = 63.54$, $sbe = 3.52$ eV, $\rho = 8.95$ g/cm³
 $ef = 0.98$ eV, $esb = 1.00$ eV, $ca = 1.00$, $kk0 = kk0r = 2$, $kdee1 = kdee2 = 3$, $ipotr = ipotr = 1$ (KrC)
 program: testvmcx
 $ne = 4$

kT (eV)	Y	r_F	$B_{z,p}$	R/V	R _{fi}	B_x	range
15	8.64e-3	2.37e-4	2.06e+0	5.85e-1	3.67e-1	4.71e+1	2.35e+1
20	1.64e-2	4.25e-4	2.59e+0	5.65e-1	3.49e-1	6.17e+1	2.82e+1
25	2.35e-2	5.78e-4	3.08e+0	5.50e-1	3.35e-1	7.60e+1	3.23e+1
1000	4.55e-2	1.39e-4	1.52e+1	2.33e-1	9.75e-2	2.10e+1	4.79e+2

He -> Cu

Sputtering yield of Cu by He
 z1 = 2. m1 = 4.00. z2 = 29j m2 = 63.54. sbe = 3.52 eV. rho = 8.95 g/cm**3
 ef = 0.50 eV. esb = 0.00 eV. ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrC)
 program: trspvmcx. IPP 9/82
 ne = 15; na = 1

Bo (eV)	0°
50	2.04e-2
50	1.93e-2
70	4.58e-2
100	7.86e-2
100	7.77e-2
200	1.33e-1
300	1.60e-1
500	1.90e-1
500	1.91e-1
1000	2.17e-1
1000	2.13e-1
2000	2.16e-1
4000	1.92e-1
5000	1.74e-1
10000	1.31e-1

Sputtered energy of Cu by He
 program: trspvmcx
 ne = 14. na = 1

E ₀ (eV)	0°
50	8.02e-4
50	7.59e-4
70	1.84e-3
100	2.87e-3
100	2.92e-3
200	3.84e-3
300	3.88e-3
500	3.49e-3
500	3.53e-3
1000	2.48e-3
2000	1.65e-3
4000	8.52e-4
5000	5.99e-4
10000	2.96e-4

He -4 Cu

Particle reflection coefficient of He backscattered from Cu
 z1= 2, miss 4.00, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0rs=2, kdee= kdee2=3, ipot=sipot=1 (KrC)
 program: trspvmex
 ne=14, na= 1

E ₀ (eV)	0°
50	5.62e-1
50	5.63e-1
70	5.29e-1
100	5.00e-1
200	4.54e-1
300	4.20e-1
500	3.91e-1
500	3.93e-1
1000	3.49e-1
1000	3.50e-1
2000	2.92e-1
4000	2.33e-1
5000	2.20e-1
10000	1.50e-1

Energy reflection coefficient of He backscattered from Cu
 ne=13, nass 1

E ₀ (eV)	0°
50	3.17e-1
70	2.89e-1
100	2.68e-1
200	2.33e-1
300	2.11e-1
500	1.90e-1
500	1.91e-1
1000	1.64e-1
1000	1.66e-1
2000	1.32e-1
4000	9.66e-2
5000	8.78e-2
10000	5.45e-2

Average depth (mean range) in Å of He implanted in Cu
 ne=14, na= 1

B ₀ (eV)	0°
50	1.08e+1
70	1.31e+1
100	1.61e+1
100	1.60e+1
200	2.47e+1
300	3.21e+1
500	4.55e+1
500	4.58e+1
1000	7.33e+1
1000	7.34e+1
2000	1.25e+2
4000	2.15e+2
5000	2.63e+2
10000	4.70e+2

Ne -> Cu

Sputtering yield of Cu by Ne

z1=10, m1= 20.18, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 7, na= 1

E _a (eV)	O'
50	8.36e-2
100	3.33e-1
200	7.10e-1
500	1.30e-0
1000	1.72e-0
2000	2.08e-0
4000	2.26e-0

Sputtered energy of Cu by Ne

ne= 7, na= 1

E ₀ (eV)	0°
50	6.64e-3
100	1.98e-2
200	2.80e-2
500	2.85e-2
1000	2.44e-2
2000	1.93e-2
4000	1.36e-2

Particle reflection coefficient of Ne backscattered from Cu

z1=10, m1= 20.18, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 7, na= 1

E _p (eV)	o'
50	4.65e-1
100	3.67e-1
200	2.91e-1
500	2.28e-1
1000	1.86e-1
2000	1.60e-1
4000	1.32e-1

Energy reflection coefficient of Ne backscattered from Cu

ne= 7, na= 1

E _p (eV)	0°
50	1.13e-1
100	8.89e-2
200	6.90e-2
500	5.13e-2
1000	4.13e-2
2000	3.40e-2
4000	2.89e-2

Average depth (mean range) in Å of Ne implanted in Cu

ne= 7, na= 1

E ₀ (eV)	0°
50	3.58e4-0
100	5.17e+0
200	7.57e+0
500	1.30e+1
1000	1.98e+1
2000	3.14e+1
4000	5.07e+1

Ar → Cu

Sputtering yield of Cu by Ar

z1 = 18, m1 = 39.95, z2 = 29, m2 = 63.54, sbe = 3.52 eV, rho = 8.95 g/cm**3

ef = 0.50 eV, esb = 0.00 eV, cas = 1.00, kk0 = kk0rs = 2, kdeels = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: testvmcx, trspvmcx, trspvles

ne = 20, na = 12

E ₀ (eV)	0°	15°	30°	45°	50°	55°	60°	65°	70°	75°	80°	85°
10								4.63e-6			1.14e-6	
11				3.65e-6								
12			3.16e-6	2.10e-5				1.06e-4			1.45e-5	
13		2.49e-6										
14	1.84e-6	9.58e-6	5.61e-5	2.17e-4		4.71e-4	5.66e-4	6.10e-4	4.65e-4	2.56e-4	5.73e-5	
15						9.79e-4	1.20e-3	1.10e-3	8.64e-4			
16	2.12e-5	6.31e-5	2.41e-4	9.23e-4		1.60e-3	1.86e-3	1.78e-3	1.29e-3	6.58e-4	1.43e-4	
18	7.78e-5	1.86e-4	6.09e-4	2.34e-3		3.96e-3		3.99e-3				
20	1.80e-4	4.00e-4	1.44e-3	4.77e-3		7.79e-3	7.98e-3	6.80e-3	4.82e-3	2.03e-3	4.80e-4	
25	8.40e-4	1.72e-3	5.36e-3	1.57e-2		2.25e-2		1.78e-2			1.16e-3	
30	3.12e-3	5.52e-3	1.46e-2	3.34e-2	4.05e-2	4.33e-2	4.08e-2	3.33e-2	2.08e-2	9.09e-3	2.06e-3	
40	1.54e-2	2.38e-2	4.85e-2	8.92e-2		9.89e-2		6.94e-2			4.46e-3	
50	3.96e-2	5.54e-2	9.91e-2	1.55e-1	1.65e-1	1.61e-1		1.13e-1	7.14e-2	3.21e-2	7.62e-3	
100	2.65e-1											
300	1.05e-0	1.15e-0	1.41e-0	1.66e-0	1.65e-0	1.64e-0	1.52e-0	1.28e-0	9.67e-1	5.76e-1	1.83e-1	7.76e-3
500	1.55e-0											
1000	2.27e-0											
2000	3.10e-0											
3000	3.48e-0											
4000	3.50e-0											

Sputtered energy of Cu by Ar

ne = 21, na = 12

E ₀ (eV)	0°	15°	30°	45°	50°	55°	60°	65°	70°	75°	80°	85°
10				2.20e-6				1.03e-6			3.44e-7	
11				3.61e-6								
12			1.54e-6					1.63e-5			2.70e-6	
13		2.60e-6										
14	1.89e-6	1.99e-6	6.55e-6	2.83e-5		6.90e-5	8.63e-5	9.70e-5	7.92e-5	4.66e-5	1.08e-5	
15						1.46e-4	1.85e-4	1.91e-4	1.61e-4			
16	3.65e-6	5.32e-6	2.31e-5	1.23e-4		2.49e-4	3.02e-4	3.03e-4	2.32e-4	1.28e-4	2.77e-5	
18	6.24e-6	1.36e-5	6.12e-5	3.10e-4		6.00e-4		7.09e-4				
20	1.21e-5											
25	1.09e-5	2.93e-5	1.58e-4	7.01e-4		1.23e-3	1.36e-3	1.23e-3	9.29e-4	4.03e-4	9.47e-5	
30	5.57e-5	1.39e-4	5.73e-4	2.21e-3		3.66e-3		3.35e-3			2.58e-4	
40	2.16e-4	4.65e-4	1.60e-3	4.70e-3	6.17e-3	7.21e-3	7.31e-3	6.35e-3	4.26e-3	1.84e-3	3.99e-4	
50	1.10e-3	2.04e-3	5.23e-3	1.23e-2		1.65e-2		1.34e-2			8.27e-4	
100	2.72e-3	4.43e-3	1.03e-2	2.08e-2	2.40e-2	2.60e-2		2.10e-2	1.38e-2	6.12e-3	1.31e-3	
300	1.34e-2											
500	2.87e-2	3.55e-2	5.98e-2	9.99e-2	1.12e-1	1.23e-1	1.28e-1	1.20e-1	9.62e-2	5.95e-2	1.57e-2	3.19e-4
1000	3.03e-2											
2000	2.85e-2											
3000	2.68e-2											
4000	2.32e-2											
4000	1.85e-2											

Ar -> Cu

Particle reflection coefficient of Ar backscattered from Cu
 z1= 18, m1= 39.95, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kkO=kkOr=2, kdee1= kdee2=3, ipot=ipot=1 (KrC)
 program: testvmcXj trspvmcx. trspvlcs
 ne=22, na=12

Ro (eV)	0°	15°	30°	45°	50°	55°	60°	65°	70°	75°	80°	85°
5	4.86e-1											
10	3.42e-1											
11				6.44e-1				9.08e-1			9.97e-1	
12			4.57e-1	6.40e-1							9.98e-1	
13		3.39e-1						9.08e-1				
14	2.93e-1	3.33e-1	4.45e-1	6.34e-1		7.75e-1	8.46e-1	9.07e-1	9.54e-1	9.85e-1	9.98e-1	
15						7.74e-1	8.45e-1	9.07e-1	9.55e-1			
16	2.81e-1	3.23e-1	4.37e-1	6.28e-1		7.73e-1	8.43e-1	9.06e-1	9.55e-1	9.85e-1	9.98e-1	
18	2.73e-1	3.16e-1	4.31e-1	6.24e-1		7.70e-1		9.06e-1				
20	2.67e-1	3.11e-1	4.15e-1	6.20e-1		7.67e-1	8.40e-1	9.05e-1	9.54e-1	9.86e-1	9.98e-1	
25	2.57e-1	3.01e-1	4.17e-1	6.12e-1		7.59e-1		9.01e-1			9.98e-1	
30	2.52e-1	2.95e-1	4.08e-1	6.04e-1	6.76e-1	7.53e-1	8.29e-1	8.98e-1	9.52e-1	9.85e-1	9.98e-1	
40	2.44e-1	2.85e-1	3.98e-1	5.88e-1		7.38e-1		8.90e-1			9.98e-1	
50	2.38e-1	2.77e-1	3.85e-1	5.74e-1	6.47e-1	7.27e-1		8.82e-1	9.45e-1	9.83e-1	9.98e-1	
100	2.14e-1											
300	1.51e-1	1.75e-1	2.36e-1	3.63e-1	4.36e-1	5.08e-1	6.05e-1	7.21e-1	8.31e-1	9.32e-1	9.91e-1	1.00e-0
500	1.25e-1											
1000	9.64e-2											
1000	1.01e-1											
2000	8.42e-2											
3000	7.03e-2											
4000	6.26e-2											

Energy reflection coefficient of Ar backscattered from Cu
 ne=22, na=12

Ro (eV)	0°	15°	30°	45°	50°	55°	60°	65°	70°	75°	80°	85°
5	3.27e-3											
10	1.18e-2							4.34e-1			7.67e-1	
11				1.49e-1								
12			6.29e-2	1.51e-1				4.43e-1			7.81e-1	
13		2.74e-2										
14	1.46e-2	2.82e-2	6.63e-2	1.56e-1		2.72e-1	3.53e-1	4.50e-1	5.60e-1	6.77e-1	7.91e-1	
15						2.74e-1	3.55e-1	4.52e-1	5.64e-1			
16	1.55e-2	2.95e-2	6.89e-2	1.60e-1		2.77e-1	3.57e-1	4.55e-1	5.67e-1	6.85e-1	7.99e-1	
18	1.63e-2	3.04e-2	7.08e-2	1.63e-1		2.79e-1		4.59e-1				
20	1.71e-2	3.11e-2	7.22e-2	1.66e-1		2.82e-1	3.64e-1	4.62e-1	5.77e-1	6.96e-1	8.12e-1	
25	1.82e-2	3.21e-2	7.45e-2	1.69e-1		2.86e-1		4.68e-1			8.23e-1	
30	1.90e-2	3.25e-2	7.53e-2	1.72e-1	2.23e-1	2.90e-1	3.71e-1	4.72e-1	5.89e-1	7.13e-1	8.31e-1	
40	1.99e-2	3.23e-2	7.47e-2	1.73e-1		2.91e-1		4.75e-1			8.42e-1	
50	1.99e-2	3.18e-2	7.27e-2	1.71e-1	2.23e-1	2.90e-1		4.74e-1	5.95e-1	7.26e-1	8.49e-1	
100	1.85e-2											
300	1.31e-2	1.79e-2	3.87e-2	9.61e-2	1.37e-1	1.87e-1	2.64e-1	3.69e-1	5.07e-1	6.70e-1	8.49e-1	9.68e-1
500	1.11e-2											
1000	8.26e-3											
1000	8.72e-3											
2000	7.59e-3											
3000	6.63e-3											
4000	5.01e-3											

Average depth (mean range) in Å of Ar implanted in Cu
 ne=21, na=11

Ro (eV)	0°	15°	30°	45°	50°	55°	60°	65°	70°	75°	80°
5	5.43e-1										
10	8.65e-1							5.60e-1			3.30e-1
11				7.70e-1							
12			8.51e-1	8.16e-1				6.21e-1			3.53e-1
13		9.54e-1									
14	1.06e+0	1.00e+0	9.49e-1	9.04e-1		8.14e-1	7.54e-1	6.83e-1	5.96e-1	4.95e-1	3.79e-1
15						8.53e-1	7.88e-1	7.10e-1	6.23e-1		
16	1.16e+0	1.11e+0	1.05e+0	9.90e-1		8.87e-1	8.20e-1	7.41e-1	6.48e-1	5.33e-1	4.01e-1
18	1.26e+0	1.21e+0	1.14e+0	1.08e+0		9.66e-1		8.01e-1			
20	1.35e+0	1.30e+0	1.23e+0	1.16e+0		1.04e+0	9.60e-1	8.68e-1	7.51e-1	6.17e-1	4.63e-1
25	1.58e+0	1.53e+0	1.45e+0	1.35e+0		1.22e+0		1.01e+0			5.34e-1
30	1.79e+0	1.74e+0	1.66e+0	1.54e+0	1.47e+0	1.39e+0	1.27e+0	1.16e+0	9.94e-1	8.44e-1	5.88e-1
40	2.17e+0	2.12e+0	2.02e+0	1.87e+0		1.69e+0		1.42e+0			8.14e-1
50	2.53e-f-0	2.47e+0	2.36e+0	2.17e+0	2.08e+0	1.97e+0		1.68e-1-0	1.47e+0	1.24e+0	9.14e-1
100	3.90e+0										
300	7.25e+0	7.10e+0	6.64e+0	6.05e+0-0	5.86e-1-0	5.68e+0	5.34e+0	5.14e+0	4.82e+0	4.53e+0-0	4.00e+0
500	9.61e+0										
1000	1.45e+1-1										
2000	2.22e+1										
3000	2.89e+1										
4000	3.39e-f-1										

Ar → Cu

Sputtering yield of Cu by Ar

z1=18, m1=39.95, z2=29, m2=63.54, sbe=3.52 eV, rho=8.95 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot
 alpha=0.
 program: trspvmex
 ne=1, na=1

Eo(eV)	Y	Y _m	H _N	R ₀	range	potential
100	2.65e-1	1.34e-2	2.14e-1	1.85e-2	3.90e+0	KrC
100	2.52e-1	1.53e-2	2.88e-1	2.34e-2	2.43e+0	Moliere
100	2.41e-1	1.36e-2	2.35e-1	1.92e-2	3.01e+0	ZRL

Cu → Cu

Sputtering yield of Cu by Cu

z1=29, m1=63.54, z2=29, m2=63.54, sbe=3.52 eV, rho=8.95 g/cm**3
 ef=3.45 eV, esb=3.52 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=rl (KrC)
 program: IPP 9/82
 ne=24, na=10

Eo(eV)	0°	15°	30°	45°	55°	65°	70°	75°	80°	85°
14	1.00e-5									
16	4.00e-5									
18	1.00e-4									
20	1.90e-4	6.10e-4	2.54e-3	9.63e-3	1.71e-2	2.13e-2		2.06e-2	1.82e-2	1.58e-2
23	4.60e-4									
25	7.50e-4									
28	1.39e-3									
30	1.98e-3									
32	2.70e-3									
50	2.45e-2	4.28e-2	1.02e-1	1.83e-1	2.06e-1	1.83e-1		1.14e-1	8.45e-2	6.04e-2
60	4.84e-2									
70	7.93e-2									
80	1.16e-1									
100	1.87e-1	2.55e-1	4.19e-1	5.60e-1	5.69e-1	4.60e-1		2.42e-1	1.44e-1	8.22e-2
200	5.85e-1									
300	9.47e-1	1.07e-0	1.40e-0	1.71e-0	1.71e-0	1.43e-0		7.64e-1	3.72e-1	1.07e-1
500	1.50e-0									
1000	2.40e-0	2.59e-0	3.30e-0	4.06e-0	4.42e-0	4.14e-0	3.56e-0		1.35e-0	2.54e-1
2000	3.35e-0									
3000	3.80e-0	4.21e-0	5.33e-0	6.96e-0		8.86e-0	8.46e-0		4.38e-0	8.84e-1
5000	4.51e-0									
10000	5.14e-0	5.84e-0	7.24e-0	1.02e+1	1.26e+1	1.53e+1	1.57e+1	1.56e+1	1.26e+1	4.25e-0
30000	5.57e-0									
100000	4.66e-0	5.35e-0	6.71e-0	9.45e-0		1.95e+1			3.03e+1	1.85e+1

Cu -> Cu

Sputtered energy of Cu by Cu
 z1 = 29. m1 = 63.54. z2 = 29. m2 = 63.54. sbe=3.52 eV. rho=8.95 g/cm**3
 ef=3.47 eV. esb = 3.52 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmx
 ne=43, na=14

E ₀ (eV)	0°	15°	25°	30°	35°	40°	45°	55°	60°	65°	70°	75°
7										7.19e-6		
7.5										2.12e-6		
8				2.51e-6			2.20e-6			4.48e-6		
9				2.36e-6			4.36e-6			1.83e-5		
10		3.00e-6		5.25e-6			1.21e-5			5.59e-5		
11		2.55e-6		9.23e-6			1.12e-4					
11.8										2.34e-4		
12	4.09e-6	2.56e-6	2.06e-5	1.51e-5	2.39e-5	3.66e-5	5.89e-5	1.42e-4		2.71e-4		3.80e-4
13				2.56e-5						5.07e-4		
14	3.91e-6	6.11e-6		3.86e-5			1.82e-4			7.74e-4		
15				5.98e-5								
16	3.26e-6	1.35e-5		8.14e-5			4.24e-4	9.62e-4		1.55e-3		1.88e-3
17				1.17e-4						2.25e-3		
18	1.28e-5	2.66e-5		1.56e-4			8.26e-4					
20	9.71e-6	4.10e-5		2.69e-4			1.44e-3	3.02e-3		4.22e-3		
22		6.71e-5										
23	2.31e-5	8.70e-5		5.73e-4			2.68e-3					
25	6.85e-5			8.35e-4								
27		2.24e-4										
28	7.23e-5											
30	1.06e-4	3.64e-4		1.92e-3			6.82e-3	1.18e-2		1.39e-2	1.31e-2	
32	1.46e-4											
35		7.24e-4		3.43e-3								
40	4.96e-4	1.38e-3		5.47e-3			1.55e-2			2.46e-2		
50	1.30e-3	2.97e-3		1.01e-2			2.50e-2	3.44e-2				2.34e-2
60	2.43e-3											
70	3.77e-3	7.27e-3		1.98e-2			4.26e-2			5.25e-2		
95							6.00e-2					
100	8.00e-3	1.35e-2		3.20e-2			6.32e-2	7.76e-2		7.16e-2		3.99e-2
120							7.30e-2					
200	1.74e-2	2.55e-2		5.22e-2			9.52e-2			1.15e-1		
300	2.27e-2	3.09e-2		5.91e-2			1.10e-1	1.38e-1		1.41e-1		8.03e-2
500	2.58e-2						1.15e-1			1.70e-1		
1000	2.78e-2	3.39e-2		6.10e-2			1.11e-1	1.53e-1		1.88e-1	1.84e-1	
2000										1.90e-1		
3000	2.17e-2	2.75e-2		4.69e-2			8.81e-2		1.61e-1	1.82e-1	1.98e-1	
5000	1.96e-2									1.68e-1		
10000	1.46e-2	1.92e-2		3.33e-2			6.51e-2	9.96e-2		1.50e-1	1.68e-1	1.87e-1
30000	9.30e-3	1.11e-2		2.08e-2			4.48e-2			1.10e-1		
100000	3.32e-3	5.67e-3		9.98e-3			2.02e-2			6.34e-2		

E ₀ (eV)	80°	85°
6.5	1.61e-6	
7	2.98e-6	
7.4	4.40e-6	
8	1.14e-5	
9	3.83e-5	4.15e-5
10	1.04e-4	1.11e-4
11	2.27e-4	
12	4.16e-4	4.19e-4
14	1.02e-3	1.02e-3
15		1.42e-3
16	1.85e-3	1.86e-3
18	2.89e-3	
20	4.04e-3	3.66e-3
30	9.53e-3	8.10e-3
40	1.36e-2	1.03e-2
50	1.64e-2	1.17e-2
70	1.96e-2	
100	2.21e-2	1.16e-2
200	2.83e-2	
300	3.39e-2	7.35e-3
500	4.76e-2	
1000	7.27e-2	7.63e-3
3000	1.32e-1	1.80e-2
10000	1.76e-1	6.68e-2
30000	1.75e-1	1.15e-1
100000	1.30e-1	1.18e-1
300000		9.87e-2

Cu -4 Cu

Particle reflection coefficient of Cu backscattered from Cu
 z1=29, m1 = 63.54, z2=29, m2 = 63.54, sbe=3.52 eV, rho=8.95 g/cm**3
 ef=3.47 eV, esb=3.52 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=43, na=14

E ₀ (eV)	0°	15°	25°	30°	35°	40°	45°	55°	60°	65°	70°	75°
7										8.29e-6		
7.5										4.60e-5		
8				5.05e-8			5.25e-7			1.38e-4		
9				5.00e-8			6.70e-6			7.32e-4		
10		2.02e-8		1.50e-7			3.64e-5			2.38e-3		
11				3.33e-7			1.29e-4					
11.8										9.07e-3		
12	2.22e-8	2.00e-7	4.29e-7	2.00e-6	1.03e-5	8.04e-5	3.09e-4	2.50e-3		1.02e-2		2.33e-2
13				7.00e-6						1.64e-2		
14	1.75e-7			1.98e-5			1.18e-3			2.46e-2		
15				6.10e-5								
16		1.33e-6		1.33e-4			3.21e-3	1.54e-2		4.61e-2		9.13e-2
17				2.61e-4						5.89e-2		
18	1.00e-6	9.00e-6		4.41e-4			6.95e-3					
20	7.50e-7	3.70e-5		1.08e-3			1.26e-2	4.29e-2		1.06e-1		
22		9.40e-5										
23	1.14e-6	1.49e-4		3.04e-3			2.47e-2					
25	4.00e-6			5.13e-3								
27		4.48e-4										
28	2.60e-5											
30	4.87e-5	8.78e-4		1.16e-2			6.47e-2	1.49e-1		2.92e-1	3.78e-1	
32	9.71e-5											
35		2.25e-3		2.03e-2								
40	5.15e-4	3.71e-3		2.96e-2			1.26e-1			4.42e-1		
50	1.92e-3	7.71e-3		4.77e-2			1.74e-1	3.30e-1				7.62e-1
60	3.18e-3											
70	4.53e-3	1.63e-2		7.30e-2			2.35e-1			6.40e-1		
95							2.63e-1					
100	9.78e-3	2.47e-2		9.45e-2			2.64e-1	4.55e-1		6.84e-1		8.89e-1
120							2.70e-1					
200	1.83e-2	3.67e-2		1.03e-1			2.62e-1			6.67e-1		
300	2.08e-2	3.83e-2		1.01e-1			2.35e-1	4.08e-1		6.25e-1		8.88e-1
500	2.28e-2						2.07e-1			5.55e-1		
1000	2.18e-2	3.13e-2		7.03e-2			1.67e-1	2.79e-1		4.64e-1	6.01e-1	
2000										3.72e-1		
3000	2.44e-2	2.76e-2		5.46e-2			1.14e-1		2.70e-1	3.35e-1	4.44e-1	
5000	1.62e-2									2.96e-1		
10000	1.44e-2	1.30e-2		4.33e-2			7.97e-2	1.50e-1		2.53e-1	3.36e-1	4.54e-1
30000	9.67e-3	1.00e-2		2.70e-2			5.40e-2			2.13e-1		
100000	3.00e-3	4.67e-3		1.36e-2			4.10e-2			1.80e-1		

E ₀ (eV)	80°	85°
6.5	1.84e-5	
7	8.86e-5	
7.4	2.26e-4	
8	7.76e-4	
9	3.48e-3	4.24e-3
10	8.85e-3	1.04e-2
11	1.74e-2	
12	2.96e-2	3.35e-2
14	6.42e-2	7.35e-2
15		9.68e-2
16	1.11e-1	1.25e-1
18	1.68e-1	
20	2.29e-1	2.54e-1
30	5.26e-1	5.70e-1
40	7.29e-1	7.76e-1
50	8.36e-1	8.78e-1
70	9.19e-1	
100	9.51e-1	9.79e-1
200	9.70e-1	
300	9.70e-1	9.97e-1
500	9.61e-1	
1000	9.30e-1	9.98e-1
3000	8.05e-1	9.88e-1
10000	6.14e-1	9.13e-1
30000	5.09e-1	7.58e-1
100000	4.70e-1	6.17e-1

Cu Cu

Energy reflection coefficient of Cu backscattered from Cu
 z1=29. m1 = 63.54. z2=29. m2= 63.54. sbe=3.52 eV. rho=8.95 g/cm**3
 ef=3.47 eV. esb=3.52 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipottr=1 (KrC)
 program: testvmcx
 ne=43. na=14

E ₀ (eV)	0°	15°	25°	30°	35°	40°	45°	55°	60°	65°	70°	75°
7										2.24e-6		
7.5										6.90e-6		
8				5.06e-7			1.98e-7			2.18e-5		
9				7.35e-6			1.05e-6			1.35e-4		
10		6.78e-7		3.77e-7			5.24e-6			5.01e-4		
11				5.51e-7			2.09e-5					
11.8										2.24e-3		
12	2.64e-8	9.95e-8	8.71e-8	8.68e-7	1.68e-6	1.15e-5	5.21e-5	5.19e-4		2.55e-3		6.66e-3
13				6.42e-7						4.35e-3		
14	4.76e-7			2.04e-6			2.07e-4			6.73e-3		
15				6.53e-6								
16		2.53e-7		1.57e-5			5.77e-4	3.61e-3		1.32e-2		2.99e-2
17				3.00e-5						1.70e-2		
18	2.44e-6	3.29e-6		5.45e-5			1.27e-3					
20	2.93e-7	1.11e-5		1.44e-4			2.37e-3	1.04e-2		3.22e-2		
22		9.40e-6										
23	7.58e-7	1.51e-5		4.26e-4			4.78e-3					
25	2.80e-7			7.45e-4								
27		4.71e-5										
28	1.49e-6											
30	2.91e-6	9.15e-5		1.73e-3			1.34e-2	3.92e-2		9.81e-2	1.40e-1	
32	6.25e-6											
35		2.28e-4		3.11e-3								
40	3.30e-5	3.67e-4		4.52e-3			2.76e-2			1.59e-1		
50	1.37e-4	8.10e-4		7.45e-3			3.95e-2	9.69e-2				3.67e-1
60	2.02e-4											
70	3.10e-4	1.61e-3		1.11e-2			5.53e-2			2.62e-1		
95							6.27e-2					
100	6.02e-4	2.23e-3		1.39e-2			6.28e-2	1.47e-1		2.98e-1		5.17e-1
120							6.40e-2					
200	9.33e-4	2.84e-3		1.34e-2			6.04e-2			3.02e-1		
300	1.15e-3	2.62e-3		1.22e-2			5.01e-2	1.28e-1		2.82e-1		5.6Be-1
500	9.76e-4						4.10e-2			2.41e-1		
1000	8.42e-4	1.61e-3		7.18e-3			2.96e-2	7.48e-2		1.84e-1	2.99e-1	
2000										1.31e-1		
3000	9.87e-4	1.28e-3		4.57e-3			1.58e-2		7.24e-2	1.11e-1	1.83e-1	
5000	5.77e-4									9.18e-2		
10000	5.02e-4	8.13e-4		3.44e-3			1.14e-2	3.20e-2		7.66e-2	1.25e-1	2.04e-1
30000	4.25e-4	5.81e-4		2.87e-3			7.83e-3			6.66e-2		
100000	7.11e-5	3.04e-4		1.09e-3			5.56e-3			5.46e-2		

E ₀ (eV)	80°	85°
6.5	3.16e-6	
7	1.42e-5	
7.4	3.98e-5	
8	1.48e-4	
9	7.91e-4	9.91e-4
10	2.27e-3	2.75e-3
11	4.87e-3	
12	8.83e-3	1.02e-2
14	2.08e-2	2.45e-2
15		3.33e-2
16	3.82e-2	4.41e-2
18	6.02e-2	
20	8.54e-2	9.81e-2
30	2.27e-1	2.56e-1
40	3.50e-1	3.93e-1
50	4.39e-1	4.89e-1
70	5.48e-1	
100	6.28e-1	7.07e-1
200	7.18e-1	
300	7.38e-1	8.69e-1
500	7.39e-1	
1000	7.05e-1	9.18e-1
3000	5.70e-1	9.01e-1
10000	3.74e-1	7.82e-1
30000	2.69e-1	5.88e-1
100000	2.44e-1	4.25e-1
300000		4.28e-1

C11-4- Cu

Average depth (mean range) in Å of Cu implanted in Cu
 z1=29, m1= 63.54, z2=29, m2= 63.54, sbe=3.52 eV, rho=8.95 g/cm**3
 ef=3.47 eV, esb=3.52 eV, ca=1.00, kkO=kkOr=2, kdee1=kdee2=3, ipot=ipotr = 1 (KrC)
 program: testvmcx
 ne=38, na=14

E _a (eV)	0°	15°	25°	30°	35°	40°	45°	55°	60°	65°	70°	75°
8				5.15e-3								
9				6.78e-2			1.59e-2					
10		1.83e-1		1.35e-1			5.78e-2					
11		2.69e-1		2.02e-1			9.87e-2					
12	3.84e-1	3.52e-1	3.01e-1	2.67e-1	2.28e-1	1.85e-1	1.38e-1	3.00e-2				
13				3.27e-1								
14	5.45e-1	5.00e-1		3.82e-1			2.08e-1					
15				4.33e-1								
16	6.75e-1	6.18e-1		4.79e-1			2.69e-1	1.13e-1				
17				5.20e-1								
18	7.81e-1	7.19e-1		5.60e-1			3.24e-1					
20	8.73e-1	8.07e-1		6.35e-1			3.75e-1	1.87e-1				
22		8.89e-1								9.19e-3		
23	1.00e-0	9.32e-1		7.38e-1			4.49e-1					
25	1.09e-0			8.06e-1								
27		1.09e-0										
28	1.21e-0											
30	1.30e-0	1.20e-0		9.69e-1			6.36e-1	3.94e-1		1.57e-1	5.39e-2	
32	1.37e-0											
35		1.38e-0		1.13e-0								
40	1.66e-0	1.56e-0		1.28e-0			9.00e-1			3.49e-1		
50	1.97e-0	1.85e-0		1.57e-0			1.17e-0	8.87e-1				2.74e-1
60	2.26e-0											
70	2.51e-0	2.39e-0		2.09e-0			1.67e-0			1.02e-0		
95							2.21e-0					
100	3.21e-0	3.06e-0		2.75e-0			2.30e-0	1.99e-0		1.56e-0		9.91e-1
120							2.66e-0					
200	4.94e-0	4.79e-0		4.39e-0			3.83e-0			2.90e-0		
300	6.25e-0	6.06e-0		5.65e-0			4.92e-0	4.38e-0		3.72e-0		2.88e-0
500	8.36e-0						6.57e-0			5.10e-0		
1000	1.24e+1	1.21e+1		1.11e+1			9.87e-0	8.73e-0		7.72e-0	7.25e-0	
2000										1.12e+1		
3000	2.34e+1	2.30e+1		2.09e+1			1.85e+1		1.52e+1	1.42e+1	1.31e+1	
5000	3.16e+1									1.91e+1		
10000	5.02e+1	4.74e+1		4.46e+1			3.86e+1	3.37e+1		2.86e+1	2.78e+1	2.54e-f-1
30000	1.07e+2	1.06e+2		9.73e+1			8.50e+1			5.96e+1		
100000	3.00e-f-2	2.81e+2		2.54e+2			2.19e-f-2			1.59e+2		

Bo (eV)	80°	85°
50	1.32e-1	3.05e-2
70	3.87e-1	
100	7.71e-1	4.52e-1
200	1.54e-0	
300	2.36e-0	1.46e-0
500	3.67e-0	
1000	5.55e-0	4.57e-0
3000	1.12e+1	9.26e-0
10000	2.44e+1	2.28e+1
30000	4.83e+1	4.52e-f-1
100000	1.30e+2	1.06e+2
300000		1.78e+2

Cu on Cu, Maxwellian velocity distribution, sheath potential 3 kT
 z1=29, m1= 63.54, z2=29, m2= 63.54, sbe=3.52, rho=8.95 g/cm**3
 ef=3.50 eV, esb=3.52 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 3

kT(eV)	Y	Y _R	E _{sp}	R ₇₇	Re	E _b	range
15	5.67e-1	2.60e-2	7.57e-f-0	4.39e-2	4.37e-3	1.64e-f-1	4.20e4-0
20	8.15e-1	3.19e-2	8.64e+0	4.13e-2	4.00e-3	2.13e+1	5.05e4-0
25	1.01e-0	3.41e-2	9.32e+0	4.05e-2	3.40e-3	2.31e+1	5.71e+0

iX.6 — CII

Sputtering yield of Cu by Xe

z1=54, m1 = 131.30, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvmx, trspvlcs
 ne= 8, na= 1

MeV	0°
50	6.48e-3
100	8.69e-2
300	6.50e-1
500	1.17e-0
1000	2.13e-0
2000	3.30e-0
3000	4.09e-0
4000	4.51e-0

Sputtering yield of Cu by Xe

ne= 8, na= 1

MeV	(P)
50	2.35e-4
100	2.79e-3
300	1.32e-2
500	1.80e-2
1000	2.19e-2
2000	2.32e-2
3000	2.23e-2
4000	1.97e-2

Particle reflection coefficient of Xe backscattered from Cu

z1=54, m1 = 131.30, z2=29, m2= 63.54, sbe=3.52 eV, rho= 8.95 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvmx, trspvlcs
 ne= 7, na= 1

Bq (eV)	0°
50	2.77e-2
100	4.26e-3
300	2.20e-4
500	1.00e-4
2000	2.80e-4
3000	3.07e-4
4000	6.00e-4

Energy reflection coefficient of Xe backscattered from Cu

ne= 7, na= 1

Eo (eV)	cP ⁵
50	2.40e-6
100	2.86e-6
300	1.54e-6
500	1.21e-6
2000	1.91e-6
3000	2.45e-6
4000	8.91e-7

Average depth (mean range) in Å of Xe implanted in Cu

ne= 8, na= 1

B _a (eV)	0°
50	2.66e+0
100	4.17e+0
300	7.73e+0
500	1.01e+1
1000	1.42e+1
2000	2.03e+1
3000	2.49e+1
4000	2.86e+1

D → Ga

Sputtering yield of Ga by D

z1= 1, m1= 2.01, z2=31, m2= 69.72, sbe=2.82 eV, rho=5.91 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kkOr=2, kdeel = kd.ee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx, IPP 9/82
 ne=10, na= 2

E ₀ (eV)	0°	65°
30	1.58e-6	8.75e-7
50	2.54e-3	1.63e-3
70	7.80e-3	7.06e-3
100	1.55e-2	2.08e-2
200	3.13e-2	6.90e-2
500	4.45e-2	1.37e-1
1000	4.92e-2	1.65e-1
2000	4.52e-2	1.64e-1
5000	3.48e-2	1.38e-1
10000	2.38e-2	1.05e-1

Sputtered energy of Ga by D

program: testvmcx
 ne=10, na= 2

E ₀ (eV)	0°	65°
30	2.28e-9	3.45e-9
50	4.39e-5	2.95e-5
70	1.64e-4	1.63e-4
100	3.48e-4	4.75e-4
200	5.99e-4	1.40e-3
500	5.60e-4	1.84e-3
1000	4.08e-4	1.52e-3
2000	2.37e-4	9.67e-4
5000	8.52e-5	4.60e-4
10000	3.41e-5	2.22e-4

Particle reflection coefficient of D backscattered from Ga

z1= 1, m1= 2.01, z2=31, m2= 69.72, sbe=2.82 eV, rho=5.91 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne=10, na= 2

E ₀ (eV)	0°	65°
30	5.93e-1	8.32e-1
50	5.68e-1	7.95e-1
70	5.48e-1	7.69e-1
100	5.29e-1	7.47e-1
200	4.91e-1	7.04e-1
500	4.27e-1	6.48e-1
1000	3.71e-1	6.03e-1
2000	3.04e-1	5.57e-1
5000	2.03e-1	4.76e-1
10000	1.27e-1	4.03e-1

Energy reflection coefficient of D backscattered from Ga

ne=10, na= 2

B ₀ (eV)	0°	65°
30	3.72e-1	6.80e-1
50	3.47e-1	6.30e-1
70	3.29e-1	5.96e-1
100	3.11e-1	5.63e-1
200	2.79e-1	5.10e-1
500	2.29e-1	4.46e-1
1000	1.88e-1	3.98e-1
2000	1.43e-1	3.49e-1
5000	8.20e-2	2.68e-1
10000	4.44e-2	2.00e-1

Average depth (mean range) in Å of D implanted in Ga

ne=10, na= 2

E ₀ (eV)	0°	65°
30	2.42e4-1	2.31e+1
50	3.25e+1	3.09e+1
70	3.96e+1	3.74e+1
100	4.89e+1	4.64e+1
200	7.54e+1	7.04e+1
500	1.38e+2	1.26e+2
1000	2.27e+2	2.03e+2
2000	3.85e+2	3.33e+2
5000	7.98e+2	6.50e+2
10000	1.43e+3	1.08e+3

D -+ Ga

D on Ga, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1, m1 = 2.01, z2=31, m2 = 69.72, sbe=2.82 eV, rho= 5.91 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmx
 ne=10

kT(eV)	Y	Y _m	E _{sp}	R ₁₇	R _m	B _j	range
10	2.71e-4	1.76e-5	1.30e+0	7.53e-1	5.49e-1	1.46e+1	1.86e+1
20	3.00e-3	1.53e-4	2.04e+0	7.21e-1	5.03e-1	2.79e+1	2.79e+1
30	7.39e-3	3.13e-4	2.55e+0	6.99e-1	4.77e-1	4.10e+1	3.54e+1
50	1.83e-2	6.09e-4	3.32e+0	6.69e-1	4.42e-1	6.60e+1	4.76e+1
100	4.07e-2	9.38e-4	4.60e+0	6.34e-1	4.03e-1	1.27e+2	7.25e+1
200	6.73e-2	1.04e-3	6.16e+0	5.87e-1	3.57e-1	2.43e+2	1.15e+2
500	9.35e-2	8.54e-4	9.15e+0	5.24e-1	2.94e-1	5.62e+2	2.19e+2
1000	1.03e-1	5.86e-4	1.14e+1	4.67e-1	2.42e-1	1.04e+3	3.67e+2
2000	9.78e-2	3.32e-4	1.35e+1	3.98e-1	1.86e-1	1.87e+3	6.21e+2
5000	8.22e-2	1.43e-4	1.74e+1	3.06e-1	1.19e-1	3.88e+3	1.27e+3

D on Ga, Maxwellian velocity distribution, sheath potential 3 kT
 ne=11

kT(eV)	Y	Y _m	E _{sp}	R _v	R _b	B _b	range
5	6.50e-5	2.23e-6	8.56e-1	6.39e-1	4.43e-1	1.66e+1	2.15e+1
7	6.93e-4	1.94e-5	9.81e-1	6.20e-1	4.02e-1	2.27e+1	2.60e+1
10	3.35e-3	9.02e-5	1.35e+0	6.00e-1	3.82e-1	3.19e+1	3.18e+1
20	1.63e-2	3.95e-4	2.43e+0	5.64e-1	3.45e-1	6.12e+1	4.81e+1
50	4.01e-2	7.06e-4	4.40e+0	5.10e-1	2.97e-1	1.46e+2	8.48e+1
100	5.30e-2	6.79e-4	6.41e+0	4.64e-1	2.58e-1	2.78e+2	1.35e+2
200	5.90e-2	4.94e-4	8.39e+0	4.07e-1	2.16e-1	5.30e+2	2.21e+2
500	5.36e-2	2.28e-4	1.07e+1	3.20e-1	1.50e-1	1.18e+3	4.41e+2
1000	4.28e-2	1.14e-4	1.34e+1	2.47e-1	1.04e-1	2.11e+3	7.65e+2
2000	3.40e-2	5.40e-5	1.59e+1	1.65e-1	5.98e-2	3.62e+3	1.34e+3
5000	1.72e-2	1.08e-5	1.57e+1	7.35e-2	2.07e-2	7.07e+3	2.87e+3

T → Ga

Sputtering yield of Ga by T

z1= 1, m1= 3.01, z2=31, m2= 69.72, sbe=2.97 eV, rho=5.91 g/cm**3
 ef=0.90 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 program: newtrim (Laszlo), TPP 9/82
 ne= 8, na= 2

E ₀ (eV)	0°	65°
50	8.73e-3	7.60e-3
100	2.85e-2	4.97e-2
200	5.00e-2	1.24e-1
500	6.84e-2	2.11e-1
1000	7.15e-2	2.46e-1
2000	6.81e-2	2.54e-1
5000	5.24e-2	2.00e-1
10000	3.56e-2	

Sputtered energy of Ga by T

program: newtrim (Laszlo)
 ne= 8, na= 2

E ₀ (eV)	0°	65°
50	2.62e-4	2.48e-4
100	8.73e-4	1.60e-3
200	1.23e-3	3.29e-3
500	1.05e-3	3.64e-3
1000	7.22e-4	2.84e-3
2000	4.07e-4	1.84e-3
5000	1.76e-4	8.14e-4
10000	6.22e-5	

Particle reflection coefficient of T backscattered from Ga

z1= 1, m1= 3.01, z2=31, m2= 69.72, sbe=2.97 eV, rho=5.91 g/cm**3
 ef=0.90 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 program: newtrim (Laszlo)
 ne= 8, na= 2

E ₀ (eV)	0°	65°
50	5.36e-1	7.81e-1
100	5.02e-1	7.30e-1
200	4.65e-1	6.88e-1
500	4.11e-1	6.31e-1
1000	3.61e-1	5.98e-1
2000	3.00e-1	5.44e-1
5000	2.08e-1	4.74e-1
10000	1.37e-1	

Energy reflection coefficient of T backscattered from Ga

ne= 8, na= 2

E ₀ (eV)	0°	65°
50	3.14e-1	6.08e-1
100	2.85e-1	5.43e-1
200	2.56e-1	4.90e-1
500	2.17e-1	4.32e-1
1000	1.82e-1	3.95e-1
2000	1.42e-1	3.43e-1
5000	8.66e-2	2.79e-1
10000	4.90e-2	

Average depth (mean range) in Å of T implanted in Ga

ne= 8, na= 2

E ₀ (eV)	0°	65°
50	3.02e+1	2.84e+1
100	4.60e+1	4.29e+1
200	7.17e+1	6.61e+1
500	1.35e+2	1.23e+2
1000	2.26e+2	2.01e+2
2000	3.92e+2	3.39e+2
5000	8.45e+2	6.97e+2
10000	1.55e+3	

T → Ga

T on Ga, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1, m1 = 3.01, z2=31, m2= 69.72, she=2.97 eV, rho= 5.91 g/cm**3
 ef=0.90 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: newtrim(Laszlo)
 ne= 9

kT(eV)	Y	Y _#	E _{gp}	R _{?sr}	Re	E _{fe}	range
10	1.11e-3	9.34e-5	1.69e4-0	7.29e-1	5.17e-1	1.42e+1	1.69e+1
20	7.80e-3	5.20e-4	2.67e+0	6.98e-1	4.76e-1	2.73e+1	2.57e+1
50	3.46e-2	1.54e-3	4.34eR0	6.48e-1	4.22e-1	6.50e+1	4.47e+1
100	7.13e-2	2.03e-3	5.72e+0	6.07e-1	3.81e-1	1.26e+2	6.97eR1
200	1.08e-1	2.13e-3	7.88e4-0	5.73e-1	3.45e-1	2.41eR2	1.11e+2
500	1.42e-1	1.53e-3	1.08e+1	5.11e-1	2.88e-1	5.66e+2	2.20e+2
1000	1.58e-1	1.15e-3	1.46e+1	4.66e-1	2.44e-1	1.05e+3	3.75e4-2
2000	1.39e-1	6.18e-4	1.77e+1	4.04e-1	1.96e-1	1.92e+3	6.54e+2
5000	1.18e-1	2.56e-4	2.16e+1	3.14e-1	1.29e-1	4.07e+3	1.38e+3

T on Ga, Maxwellian velocity distribution, sheath potential 3 kT
 ne= 9

kT(eV)	Y	Y _e	E _{sp}	R _{jV}	Re	E _s	range
10	9.56e-3	3.68e-4	1.93e+0	5.70e-1	3.49e-1	3.06e+1	2.97e+1
20	3.07e-2	9.94e-4	3.23e+0	5.39e-1	3.21e-1	5.94e+1	4.49eR1
50	6.50e-2	1.46e-3	5.60e+0	4.84e-1	2.76e-1	1.43e+2	8.05e+1
100	8.10e-2	1.24e-3	7.63e+0	4.46e-1	2.45e-1	2.76eR2	1.33e+2
200	8.47e-2	8.85e-4	1.04e+1	3.99e-1	2.12e-1	5.30e+2	2.22e+2
500	7.77e-2	3.98e-4	1.28e+1	3.18e-1	1.56e-1	1.23e+3	4.55e+2
1000	6.48e-2	2.17e-4	1.67e+1	2.49e-1	1.07e-1	2.16eR3	8.12e4-2
2000	4.91e-2	9.75e-5	1.99e+1	1.76e-1	6.65e-2	3.79e+3	1.46e+3
5000	3.06e-2	2.81e-5	2.30e+1	8.45e-2	2.56e-2	7.58eR3	3.19e+3

T on Ga, Maxwellian velocity distribution, sheath potential 9 kT
 ne= 5

kT(eV)	Y	Y _e	E _{sp}	R _w	Re	E _s	range
10	3.18e-2	9.61e-4	3.33e+0	5.15e-1	2.97e-1	6.35e+1	4.85eR1
20	5.52e-2	1.34e-3	5.32e+0	4.75e-1	2.66e-1	1.23e+2	7.54e+1
50	7.79e-2	1.17e-3	8.28e4-0	4.19e-1	2.25e-1	2.95e+2	1.43e+2
100	8.25e-2	7.50e-4	1.00e+1	3.69e-1	1.87e-1	5.58e4-2	2.40e+2
200	7.11e-2	4.15e-4	1.29e+1	3.16e-1	1.52e-1	1.06e+3	4.18eR2

Gei-y Gei

Sputtering yield of Ga by Ga

z1=31, m1 = 69.72, z2=31, m2= 69.72, sbe=2.97 eV, rho=5.91 g/cm**3
 ef=2.47 eV, esb=2.97 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot = 1 (KrC)
 program: newtrim (Laszlo), TPP 9/82
 ne=12, na= 8

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	5.56e-4				4.94e-2			
50	4.60e-2				3.48e-1			
100	2.37e-1	5.25e-1	7.57e-1	8.28e-1	8.03e-1		6.18e-1	2.84e-1
150	4.43e-1	8.22e-1	1.12e-0	1.22e-0	1.19e-0		9.18e-1	
200	6.33e-1	1.07e-0	1.45e-0	1.56e-0	1.55e-0		1.20e-0	5.11e-1
300	9.46e-1	1.49e-0	1.98e-0	2.17e-0	2.16e-0		1.75e-0	
500	1.43e-0				3.19e-0			
900	2.08e-0	3.02e-0	3.94e-0	4.57e-0	4.71e-0		4.28e-0	
1000	2.22e-0	3.14e-0	4.20e-0	4.84e-0	5.02e-0	4.97e-0	4.63e-0	2.37e-0
2000	3.10e-0				7.32e-0			
5000	4.07e-0				1.08e-1			
10000	4.96e-0				1.41e+1			

Sputtered energy of Ga by Ga

program: newtrim (Laszlo)
 ne=12, na= 8

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	3.05e-5				9.85e-3			
50	2.13e-3				6.15e-2			
100	8.31e-3	3.53e-2	7.45e-2	1.01e-1	1.09e-1		9.82e-2	4.68e-2
150	1.30e-2	4.43e-2	8.92e-2	1.21e-1	1.32e-1		1.21e-1	
200	1.59e-2	4.85e-2	9.64e-2	1.31e-1	1.45e-1		1.36e-1	6.10e-2
300	1.94e-2	5.23e-2	1.02e-1	1.40e-1	1.58e-1		1.59e-1	
500	2.21e-2				1.67e-1			
900	2.33e-2	5.43e-2	9.95e-2	1.44e-1	1.66e-1		1.96e-1	
1000	2.36e-2	5.30e-2	9.81e-2	1.41e-1	1.67e-1	1.86e-1	1.98e-1	1.24e-1
2000	2.23e-2				1.57e-1			
5000	1.73e-2				1.34e-1			
10000	1.49e-2				1.20e-1			

Ga → Ga

Particle reflection coefficient of backscattered Ga from Ga
 z1=31, m1 = 69.72, z2=31, m2 = 69.72, sbe=2.97 eV, rho=5.91 g/cm**3
 ef=2.47 eV, esb=2.97 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot = 1 (KrC)
 program: newtrim (Laszlo)
 ne=12, na= 8

Eq(eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	2.43e-5				1.14e-1			
50	3.46e-3				4.10e-1			
100	1.13e-2	7.66e-2	2.08e-1	3.68e-1	4.73e-1		7.08e-1	9.19e-1
150	1.63e-2	8.10e-2	2.06e-1	3.54e-1	4.53e-1		6.96e-1	
200	1.92e-2	8.08e-2	1.96e-1	3.38e-1	4.32e-1		6.80e-1	9.28e-1
300	2.34e-2	7.91e-2	1.82e-1	3.11e-1	3.97e-1		6.39e-1	
500	2.43e-2				3.54e-1			
900	2.15e-2	6.48e-2	1.37e-1	2.39e-1	3.02e-1		5.09e-1	
1000	2.66e-2	6.42e-2	1.35e-1	2.33e-1	2.93e-1	3.81e-1	4.93e-1	8.37e-1
2000	2.05e-2				2.49e-1			
5000	1.71e-2				2.11e-1			
10000	1.16e-2				1.87e-1			

Energy reflection coefficient of Ga backscattered from Ga
 ne=12, na= 8

Eo(eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	3.37e-6				3.22e-2			
50	2.16e-4				1.41e-1			
100	6.01e-4	1.02e-2	4.67e-2	1.14e-1	1.72e-1		3.49e-1	6.00e-1
150	7.95e-4	9.89e-3	4.37e-2	1.07e-1	1.64e-1		3.52e-1	
200	8.77e-4	9.50e-3	4.03e-2	9.96e-2	1.53e-1		3.43e-1	6.55e-1
300	1.05e-3	8.61e-3	3.53e-2	8.79e-2	1.35e-1		3.16e-1	
500	9.41e-4				1.12e-1			
900	7.65e-4	5.72e-3	2.18e-2	5.54e-2	8.73e-2		2.24e-1	
1000	9.73e-4	6.00e-3	2.10e-2	5.36e-2	8.31e-2	1.34e-1	2.15e-1	5.84e-1
2000	6.36e-4				6.39e-2			
5000	6.81e-4				5.05e-2			
10000	2.77e-4				4.46e-2			

Average depth (mean range) in Å of Ga implanted in Ga
 ne=12, na= 8

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	2.39e+0				7.67e-1			
50	4.24e+0				2.16e+0			
100	6.26e+0	5.52e+0	4.78e+0	4.21e-10	3.89e+0		3.15e+0	2.09e+0
150	7.80e+0	6.95e+0	6.08e+0	5.44e-10	5.09e+0		4.23e+0	
200	9.07e+0	8.12e+0	7.13e+0	6.42e+0	6.01e+0		5.10e+0	3.74e+0
300	1.12e+1	1.00e+1	8.84e+0	7.99e+0	7.55e+0		6.51e+0	
500	1.46e+1				9.81e+0			
900	1.99e+1	1.78e+1	1.57e+1	1.41e+1	1.32e+1		1.17e+1	
1000	2.09e+1	1.88e+1	1.64e+1	1.49e+1	1.38e+1	1.31e+1	1.22e+1	1.05e+1
2000	3.02e+1				2.02e+1			
5000	5.18e+1				3.34e+1			
10000	7.99e+1				5.02e+1			

Ga → Ga

Ga on Ga, Maxwellian velocity distribution, sheath potential 0 kT
 z1= 31, m1= 69.72, z2= 31, m2= 69.72, she=2.97 eV, rho= 5.91 g/cm**3
 ef=2.92 (2.47) eV, esb=2.97 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx, newtrim(Laszlo)
 ne= 12

kT(eV)	Y	Y _e	E _{sp}	R _{AΓ}	R _Z	E _b	range
2	2.99e-4	1.90e-4	2.54e+0	6.95e-4	7.41e-4	4.27e+0	1.53e-1
3	1.47e-3	8.26e-4	3.38e+0	3.79e-3	3.38e-3	5.35e+0	3.29e-1
5	8.53e-3	3.81e-3	4.46e+0	1.91e-2	1.47e-2	7.67e+0	6.74e-1
10	4.91e-2	1.55e-2	6.29e+0	7.73e-2	4.91e-2	1.27e+1	1.26e+0
20	1.77e-1	3.76e-2	8.48e+0	1.66e-1	8.96e-2	2.16e+1	2.24e+0
50	5.77e-1	7.00e-2	1.22e+1	2.54e-1	1.16e-1	4.58e+1	4.42e+0
100	1.10e-0	8.75e-2	1.59e+1	2.75e-1	1.16e-1	8.40e+1	6.83e+0
200	1.90e-0	9.78e-2	2.05e+1	2.65e-1	1.01e-1	1.52e+2	1.00e+1
500	3.47e-0	9.96e-2	2.88e+1	2.31e-1	8.28e-2	3.61e+2	1.63e+1
1000	4.98e-0	9.47e-2	3.82e+1	2.05e-1	7.15e-2	6.99e+2	2.36e+1
2000	6.67e-0	8.60e-2	5.10e+1	1.88e-1	6.12e-2	1.29e+3	3.50e+1
5000	9.45e-0	7.25e-2	7.56e+1	1.58e-1	5.07e-2	3.16e+3	5.89e+1

Ga on Ga, Maxwellian velocity distribution, sheath potential 3 kT
 ne=12

kT(eV)	Y	Y _e	E _{sp}	B _{iV}	R _e	E _b	range
2	1.02e-3	2.54e-4	2.49e+0	8.79e-4	3.38e-4	3.85e+0	1.07e+0
3	5.42e-3	1.15e-3	3.20e+0	4.59e-3	1.55e-3	5.06e+0	1.52e+0
5	2.92e-2	4.85e-3	4.15e+0	1.65e-2	4.73e-3	7.17e+0	2.32e+0
10	1.55e-1	1.73e-2	5.58e+0	4.20e-2	9.64e-3	1.15e+1	3.71e+0
20	4.47e-1	3.28e-2	7.33e+0	5.95e-2	1.07e-2	1.81e+1	5.66e+0
50	1.16e-0	4.56e-2	9.83e+0	6.31e-2	8.67e-3	3.43e1	9.32e+0
100	1.93e-0	4.85e-2	1.26e+1	5.89e-2	7.14e-3	6.05e+1	1.33e+1
200	2.90e-0	4.77e-2	1.64e+1	5.09e-2	5.54e-3	1.09e+2	1.90e+1
500	4.27e-0	4.08e-2	2.39e+1	4.20e-2	4.18e-3	2.49e+2	3.18e+1
1000	5.30e-0	3.63e-2	3.39e+1	3.73e-2	4.22e-3	5.62e+2	4.59e+1
2000	6.07e-0	2.94e-2	4.78e+1	2.49e-2	1.99e-3	7.88e+2	7.28e+1
5000	7.78e-0	2.10e-2	6.77e+1	2.88e-2	2.78e-3	2.42e+3	1.36e+2

Ga on Ga, Maxwellian velocity distribution, sheath potential 9 kT
 ne=11

kT(eV)	Y	Y _e	E _{sp}	R _{at}	B _e	E _b	range
1.4	1.25e-3	1.54e-4	1.90e+0	4.93e-4	1.01e-4	3.15e+0	1.75e+0
2	6.21e-3	7.25e-4	2.57e+0	2.50e-3	4.47e-4	3.92e+0	2.36e+0
5	1.17e-1	8.51e-3	4.00e+0	1.78e-2	2.36e-3	7.27e+0	4.25e+0
10	3.90e-1	1.91e-2	5.38e+0	3.15e-2	3.26e-3	1.14e+1	6.33e+0
20	8.66e-1	2.82e-2	7.15e+0	3.73e-2	3.13e-3	1.85e1	9.15e+0
50	1.79e-0	3.34e-2	1.03e+1	3.83e-2	2.58e-3	3.71e+1	1.48e+1
100	2.62e-0	3.17e-2	1.33e1	3.36e-2	2.01e-3	6.57e+1	2.13e+1
200	3.58e-0	2.97e-2	1.83e+1	2.90e-2	1.52e-3	1.15e+2	3.06e+1
500	4.80e-0	2.36e-2	2.71e+1	2.40e-2	1.50e-3	3.43e+2	5.31e+1
1000	5.53e-0	1.89e-2	3.75e+1	2.05e-2	1.23e-3	6.62e+2	7.81e+1
2000	6.41e-0	1.48e-2	5.07e+1	1.75e-2	1.37e-3	1.72e+3	1.27e+2

Hg → Ga

Sputtering yield of Ga by Hg

z1 = 80, m1 = 200.59, z2=31, m2= 69.72, sbe=2.97 eV, rho=5.91 g/cm**3
 ef=2.10, esb=2.60, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipotr= 1 (KrG)
 program: newtrim (Laszlo), TPP 9/82
 only low fluence! ne= 4, na= 1

E ₀ (eV)	0°
100	7.97e-2
200	3.20e-1
300	5.62e-1
400	7.90e-1

Sputtered energy of Ga by Hg

z1 = 80, m1=:200.59, z2=31, m2= 69.72, sbe=2.97 eV, rho=5.91 g/cm**3
 ef=2.10, esb=2.60, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrG)
 program: newtrim (Laszlo)
 only low fluence! ne= 4, na= 1

Bo (eV)	0°
100	2.17e-3
200	6.60e-3
300	9.58e-3
400	1.17e-2

Average depth (mean range) in Å of Hg implanted in Ga

only low fluence! ne= 4, na= 1

Ro (eV)	0°
100	1.02e+1
200	1.42e+1
300	1.70e+1
400	1.94e+1

Mg → Ge

Particle reflection coefficient of Mg backscattered from Ge
 $z1 = 12, m1 = 24.00, z2 = 32, m2 = 72.59, \rho = 5.32 \text{ g/cm}^3$
 $ef = 1.00 \text{ eV}, esb = 1.00 \text{ eV}, ca = 1.00, kk0 = 2, kdeel = 3, ipot = 1 \text{ (KrC)}$
 program: trrange3
 only low fluence!
 $ne = 2, na = 1$

$E_0 \text{ (eV)}$	0°
100000	$3.55e-2$
200000	$1.94e-2$

Energy reflection coefficient of Mg backscattered from Ge
 only low fluence!
 $ne = 2, na = 1$

$E_0 \text{ (eV)}$	0°
100000	$6.72e-3$
200000	$3.44e-3$

Average depth (mean range) in Å of Mg implanted in Ge
 only low fluence!
 $ne = 2, na = 1$

$B_0 \text{ (eV)}$	0°
100000	$1.21e+3$
200000	$2.30e+3$

Al Ge

Particle reflection coefficient of Al backscattered from Ge
 $z1 = 13, m1 = 27.00, z2 = 32, m2 = 72.59, \rho = 5.32 \text{ g/cm}^3$
 $ef = 1.00 \text{ eV}, esb = 1.00 \text{ eV}, ca = 1.00, kk0 = 2, kdeel = 3, ipot = 1 \text{ (KrC)}$
 program: trrange3
 only low fluence!
 $ne = 2, na = 1$

$E_0 \text{ (eV)}$	0°
100000	$3.24e-2$
200000	$1.85e-2$

Energy reflection coefficient of Al backscattered from Ge
 only low fluence!
 $ne = 2, na = 1$

$B_0 \text{ (eV)}$	0°
100000	$5.60e-3$
200000	$3.02e-3$

Average depth (mean range) in Å of Al implanted in Ge
 only low fluence!
 $ne = 2, na = 1$

$E_0 \text{ (eV)}$	0°
100000	$1.12e+3$
200000	$2.14e+3$

Si Ge

Particle reflection coefficient of Si backscattered from Ge
 $z1 = 14$, $m1 = 29.00$ $z2 = 32$, $m2 = 72.59$, $\rho = 5.32 \text{ g/cm}^3$
 $ef = 1.00 \text{ eV}$, $esb = 1.00 \text{ eV}$, $ca = 1.00$, $kk0 = 2$, $kdee1 = 3$, $ipot = 1 \text{ (KrC)}$
 program: *trrange3*
only low fluence!
 $ne = 2$, $na = 1$

$B_0 \text{ (eV)}$	0°
100000	$3.02e-2$
200000	$1.74e-2$

Energy reflection coefficient of Si backscattered from Ge
only low fluence!
 $ne = 2$, $na = 1$

$E_0 \text{ (eV)}$	0°
100000	$5.02e-3$
200000	$2.70e-3$

Average depth (mean range) in Å of Si implanted in Ge
only low fluence!
 $ne = 2$, $na = 1$

$E_0 \text{ (eV)}$	0°
100000	$1.04e+3$
200000	$1.99e+3$

P Ge

Particle reflection coefficient of P backscattered from Ge
 $z1 = 15$, $m1 = 31.00$, $z2 = 32$, $m2 = 72.59$, $\rho = 5.32 \text{ g/cm}^3$
 $ef = 1.00 \text{ eV}$, $esb = 1.00 \text{ eV}$, $ca = 1.00$, $kk0 = 2$, $kdee1 = 3$, $ipot = 1 \text{ (KrC)}$
 program: *trrange3*
only low fluence!
 $ne = 2$, $na = 1$

$E_0 \text{ (eV)}$	0°
100000	$2.81e-2$
200000	$1.67e-2$

Energy reflection coefficient of P backscattered from Ge
only low fluence!
 $ne = 2$, $na = 1$

$B_0 \text{ (eV)}$	0°
100000	$4.32e-3$
200000	$2.46e-3$

Average depth (mean range) in Å of P implanted in Ge
only low fluence!
 $ne = 2$, $na = 1$

$B_0 \text{ (eV)}$	0°
100000	$9.73e+2$
200000	$1.86e+3$

Ar → Ge

Sputtering yield of Ge by Ar

21= 18, m1 = 39.95, z2=29, m2= 63.54, sbe=3.88 eV, rho= 5.32 g/cm**3

ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot=1 (KrC)

program: TPP 9/82

ne=12, na= 1

B ₀ (eV)	0°
50	4.42e-2
100	2.06e-1
200	4.88e-1
500	1.01e-0
1000	1.43e-0
2000	1.83e-0
5000	2.29e-0
10000	2.49e-0
20000	2.54e-0
50000	2.32e-0
100000	1.97e-0
200000	1.59e-0

Sputtered energy of Ge by Ar

ne=12, na= 1

B ₀ (eV)	0°
50	3.10e-3
100	1.04e-2
200	1.71e-2
500	2.17e-2
1000	2.08e-2
2000	1.81e-2
5000	1.37e-2
10000	1.04e-2
20000	7.61e-3
50000	4.16e-3
100000	2.36e-3
200000	1.23e-3

Ar → Ge

Particle reflection coefficient of Ar backscattered from Ge
 $z1=18, m1=39.95, z2=29, m2=63.54, sbe=3.88$ eV. $\rho=5.32$ g/cm**3
 $ef=0.50$ eV. $esb=0.00$ eV, $ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1$ (KrC)
 program:
 $ne=12, na=1$

E_0 (eV)	0°
50	2.44e-1
100	1.93e-1
200	1.58e-1
500	1.23e-1
1000	1.02e-1
2000	8.56e-2
5000	7.11e-2
10000	5.83e-2
20000	4.29e-2
50000	2.92e-2
100000	1.91e-2
200000	1.17e-2

Energy reflection coefficient of Ar backscattered from Ge
 $ne=12, na=1$

E_0 (eV)	\bar{O}^s
50	2.72e-2
100	2.22e-2
200	1.80e-2
500	1.38e-2
1000	1.10e-2
2000	9.52e-3
5000	7.99e-3
10000	6.38e-3
20000	4.86e-3
50000	3.42e-3
100000	2.09e-3
200000	1.29e-3

Average depth (mean range) in Å of Ar implanted in Ge
 $ne=12, na=1$

E_0 (eV)	0°
50	8.14e+0
100	1.05e+1
200	1.37e+1
500	2.06e+1
1000	2.93e+1
2000	4.32e+1
5000	7.56e+1
10000	1.21e+2
20000	2.03e+2
50000	4.29e+2
100000	8.00e+2
200000	1.53e+3

Bi → Ge

Average depth (mean range) in Å of Bi implanted in Ge
 $z1=83, m1=209.00, z2=32, m2=72.59, \rho=5.32$ g/cm**3
 $ef=1.00$ eV, $esb=1.00$ eV, $ca=1.00, kk0=2, kdee1=3, ipot=1$ (KrC)
 program: ttrange3
 only low fluence!
 $ne=2, na=1$

E_0 (eV)	0°
200000	5.24e+2
400000	8.74e+2

Xe → Zr

Sputtering yield of Zr by Xe

z1=54, l1l1=131.30, z2=40, m2=91.22, sbe=6.33 eV, rho=6.49 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 program : IPP 9/82
 ne=8, na=1

E ₀ (eV)	0°
50	9.70e-5
50	1.47e-4
50	1.27e-4
50	1.27e-4
100	1.13e-2
200	1.01e-1
500	4.33e-1
1000	8.46e-1

Sputtered energy of Zr by Xe

ne=8, na=1

E ₀ (eV)	0°
50	4.10e-6
50	6.54e-6
50	5.75e-6
50	5.71e-6
100	4.32e-4
200	3.11e-3
500	9.16e-3
1000	1.29e-2

Particle reflection coefficient of Xe backscattered from Zr

z1=54, m1=131.30, z2=40, m2=91.22, sbe=6.33 eV, rho=6.49 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 program :
 ne=8, na=1

E ₀ (eV)	0°
50	7.60e-3
50	7.58e-3
50	6.70e-3
50	5.91e-3
100	5.25e-3
200	5.14e-3
500	4.49e-3
1000	4.27e-3

Energy reflection coefficient of Xe backscattered from Zr

ne=8, na=1

E ₀ (eV)	0°
50	1.33e-4
50	1.32e-4
50	1.28e-4
50	1.30e-4
100	9.67e-5
200	7.31e-5
500	6.90e-5
1000	6.18e-5

Average depth (mean range) in Å of Xe implanted in Zr

ne=7, na=1

E ₀ (eV)	0°
50	5.43e+0
50	8.65e+0
50	8.66e+0
50	8.68e+0
100	1.06e+1
200	1.34e+1
1000	2.50e+1

D → Nb

Sputtering yield of Nb by D

z1 = 1, m1 = 2.01, z2=41, m2= 92.91, sbe=7.59 eV, rho = 8.60 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx, TPP 9/82
 ne = 7, na = 1

Bp(eV)	0°
140	2.77e-4
200	1.69e-3
300	4.53e-3
500	8.70e-3
1000	1.34e-2
2000	1.44e-2
5000	1.23e-2

Sputtered energy of Zr by Xe

program: testvmcx
 ne = 7, na = 1

Eq(eV)	0°
140	2.65e-6
200	2.60e-5
300	7.56e-5
500	1.40e-4
1000	1.69e-4
2000	1.26e-4
5000	5.82e-5

Particle reflection coefficient of D backscattered from Nb

z1 = 1, m1 = 2.01, z2=41, m2= 92.91, sbe=7.59 eV, rho = 8.60 g/cm**3
 ef=0.95 eV, esb = 1.00 eV, ca=1.00, kk0 = kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne = 7, na = 1

E ₀ (eV)	0°
140	5.54e-1
200	5.34e-1
300	5.09e-1
500	4.75e-1
1000	4.20e-1
2000	3.56e-1
5000	2.54e-1

Energy reflection coefficient of D backscattered from Nb

ne = 7, na = 1

E ₀ (eV)	0°
140	3.36e-1
200	3.18e-1
300	2.96e-1
500	2.68e-1
1000	2.25e-1
2000	1.78e-1
5000	1.11e-1

Average depth (mean range) in Å of D implanted in Nb

ne = 7, na = 1

E ₀ (eV)	0°
140	5.55e4-1
200	6.87e-1
300	8.82e+1
500	1.23e+2
1000	1.95e+2
2000	3.23e+2
5000	6.55e+2

H -4- Mo

Sputtering yield of Mo by H

zl= 1, ml= 1.01, z2=42, m2= 95.94, sbe=6.83 eV, rho = 10.21 g/cm**3
 ef=0.95, 0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 3, 4, kdee2=3, ipot=ipotr=1 (KrC)
 program: TESTVMCX, TPP 9/82
 ne= 2, na=14

E ₀ (eV)	0°	15°	25°	30°	45°	50°	60°	70°	75°	80°	85°	87°
2000	5.99e-3	5.89e-3		7.06e-3	1.05e-2		1.75e-2	2.84e-2	3.87e-2	5.30e-2	5.16e-2	1.90e-2
50000	1.36e-3		1.94e-3			4.95e-3			1.91e-2	3.01e-2	6.63e-2	9.43e-2

E ₀ (eV)	88°	89°
50000	1.09e-1	6.30e-2

Sputtered energy of Mo by H

program: TESTVMCX
 ne= 2, na=12

E _s (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°	88°	89°
2000	3.25e-5	3.23e-5	3.74e-5	6.02e-5	9.92e-5	1.67e-4	2.46e-4	3.54e-4	4.16e-4	1.77e-4		
50000								2.99e-5	6.27e-5	8.93e-5	1.08e-4	7.12e-5

Particle reflection coefficient of H backscattered from Mo

zl= 1, ml= 1.01, z2= 42, m2= 95.94, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef=0.95, 0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 3, 4, kdee2 = 3, ipot=ipotr= 1 (KrC)
 program: TESTVMCX
 ne= 2, na=12

E _s (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°	88°	89°
2000	3.37e-1	3.49e-1	3.84e-1	4.45e-1	5.37e-1	6.19e-1	6.69e-1	7.35e-1	8.63e-1	9.66e-1		
50000								4.15e-1	5.65e-1	6.59e-1	7.29e-1	8.91e-1

Energy reflection coefficient of H backscattered from Mo

ne= 2, na=12

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°	88°	89°
2000	1.59e-1	1.66e-1	1.92e-1	2.38e-1	3.21e-1	4.06e-1	4.68e-1	5.58e-1	7.53e-1	9.21e-1		
50000								1.54e-1	2.88e-1	4.02e-1	5.06e-1	7.84e-1

Average depth (mean range) in Å of H implanted in Mo

ne= 2, na=12

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°	88°	89°
2000	2.51e+2	2.49e+2	2.42e+2	2.34e+2	2.24e+2	2.19e+2	2.17e+2	2.14e+2	2.14e+2	2.14e+2		
50000								8.18e+2	7.73e+2	7.66e+2	7.62e+2	7.73e+2

D -> Mo

Sputtering yield of Mo by D

z1 = 1, m1 = 2.01, z2=42, m2= 95.94, sbe=6.83 eV, rho = 10.21 g/cm**3
 ef=0.98 eV, esb=1.00 eV, ca=1.00, kko=kkOr=2, kdee1=3, 4, kdee2=3, ipot=ipot=1 (KrC)
 program: testvmcx, trspvlcs, newtrim (Laszlo), TPP 9/82
 ne=12, na=10

Eo(eV)	0°	25°	50°	65°	75°	80°	85°	87°	88°	89°
120	1.50e-4			1.34e-4						
130	3.35e-4			3.00e-4						
140	5.81e-4			5.63e-4						
150	8.72e-4			8.62e-4						
170	1.52e-3			1.62e-3						
200	2.86e-3			3.26e-3						
500	1.14e-2			2.42e-2						
1000	1.67e-2			4.59e-2						
2000	1.69e-2			6.51e-2						
5000	1.46e-2			6.30e-2						
50000	3.50e-3	4.70e-3	1.01e-2		4.38e-2	6.84e-2	1.34e-1	1.82e-1	1.98e-1	1.16e-1
100000	2.50e-3	2.62e-3	4.80e-3		2.60e-2	4.59e-2	9.15e-2	1.41e-1	1.58e-1	1.60e-1

Sputtered energy of Mo by D

program: testvmcx, trspvlcs, newtrim (Laszlo)
 ne=12, na= 7

E ₀ (eV)	0°	65°	80°	85°	87°	88°	89°
120	1.14e-6	1.21e-6					
130	3.16e-6	2.93e-6					
140	6.01e-6	6.39e-6					
150	1.00e-5	1.06e-5					
170	2.05e-5	2.38e-5					
200	4.35e-5	5.18e-5					
500	1.75e-4	3.80e-4					
1000	2.02e-4	5.58e-4					
2000	1.37e-4	5.87e-4					
5000	6.46e-5	3.15e-4					
50000			7.17e-5	1.61e-4	2.43e-4	2.53e-4	1.74e-4
100000			3.26e-5	7.83e-5	1.19e-4	1.24e-4	1.28e-4

D → Mo

Particle reflection coefficient of D backscattered from Mo
 z1 = 1, m1 = 2.01, z2=42, m2= 95.94, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.98 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 3, 4, kdee2=3, ipot=ipot= 1 (KrC)
 program: testvmcx, trspvlcs, newtrim (Laszlo)
 ne=13, na= 7

E ₀ (eV)	0°	65°	80°	85°	87°	88°	89°
20	6.71e-1						
120	5.68e-1	7.76e-1					
130	5.65e-1	7.70e-1					
140	5.59e-1	7.65e-1					
150	5.56e-1	7.61e-1					
170	5.48e-1	7.52e-1					
200	5.41e-1	7.43e-1					
500	4.84e-1	6.83e-1					
1000	4.26e-1	6.39e-1					
2000	3.63e-1	5.89e-1					
5000	2.60e-1	5.19e-1					
50000			4.46e-1	5.96e-1	6.81e-1	7.44e-1	8.95e-1
100000			3.67e-1	5.34e-1	6.35e-1	6.92e-1	8.21e-1

Energy reflection coefficient of D backscattered from Mo
 ne=13, na= 7

E ₀ (eV)	0°	65°	80°	85°	87°	88°	89°
20	4.45e-1						
120	3.50e-1	6.05e-1					
130	3.46e-1	5.97e-1					
140	3.42e-1	5.90e-1					
150	3.38e-1	5.84e-1					
170	3.32e-1	5.73e-1					
200	3.24e-1	5.60e-1					
500	2.75e-1	4.90e-1					
1000	2.29e-1	4.38e-1					
2000	1.83e-1	3.85e-1					
5000	1.14e-1	3.10e-1					
50000			1.86e-1	3.26e-1	4.38e-1	5.38e-1	7.99e-1
100000			1.16e-1	2.46e-1	3.58e-1	4.49e-1	6.52e-1

Average depth (mean range) in of D implanted in Mo
 ne=13, na= 7

Bo (eV)	0°	65°	80°	85°	87°	88°	89°
20	1.59e+1						
120	4.40e+1	4.19e+1					
130	4.62e+1	4.39e+1					
140	4.82e+1	4.58e+1					
150	5.03e+1	4.76e+1					
170	5.41e+1	5.14e+1					
200	5.99e+1	5.66e+1					
500	1.06e+2	9.88e+1					
1000	1.70e+2	1.55e+2					
2000	2.80e+2	2.50e+2					
5000	5.67e+2	4.81e+2					
50000			1.10e+3	1.05e+3	1.04e+3	1.05e+3	1.06e+3
100000			1.55e+3	1.43e+3	1.42e+3	1.41e+3	1.41e+3

D → Mo

D on Mo, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1, m1 = 2.01, z2=42, m2= 95.94, sbe=6.89 eV, rho = 10.20 g/cm**3
 ef=0.90 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program: newtrim (Laszlo)
 ne= 8

kT(eV)	Y	Y _E	E _{sp}	R _N	Re	B _{fc}	range
40	3.27e-4	1.52e-5	3.71e+0	7.26e-1	5.09e-1	5.60e+1	3.45e+1
50	7.49e-4	3.12e-5	4.16e+0	7.14e-1	4.93e-1	6.92e+1	3.91e+1
100	4.57e-3	1.42e-4	6.23e+0	6.71e-1	4.46e-1	1.33e+2	5.86e+1
200	1.21e-2	2.83e-4	9.40e+0	6.31e-1	4.00e-1	2.54e+2	9.03e+1
500	2.77e-2	3.80e-4	1.37e+1	5.66e-1	3.36e-1	5.95e+2	1.66e+2
1000	3.57e-2	2.77e-4	1.56e+1	5.18e-1	2.87e-1	1.12e+3	2.73e+2
2000	3.81e-2	2.09e-4	2.19e+1	4.53e-1	2.27e-1	2.00e+3	4.49e+2
5000	3.73e-2	1.05e-4	2.82e+1	3.61e-1	1.55e-1	4.29e+3	9.09e+2

D on Mo, Maxwellian velocity distribution, sheath potential 3 kT
 ne= 9

kT(eV)	Y	Y _E	B _{sp}	R _N	Re	E _b	range
20	1.86e-4	4.06e-6	2.19e+0	6.09e-1	3.93e-1	6.45e+1	3.90e+1
30	9.74e-4	2.07e-5	3.19e+0	5.87e-1	3.70e-1	9.46e+1	4.95e+1
50	4.51e-3	8.39e-5	4.65e+0	5.57e-1	3.40e-1	1.53e+2	6.72e+1
100	1.23e-2	1.97e-4	8.00e+0	5.14e-1	3.02e-1	2.94e+2	1.04e+2
200	1.77e-2	2.15e-4	1.22e+1	4.59e-1	2.57e-1	5.61e+2	1.66e+2
500	2.15e-2	1.49e-4	1.72e+1	3.79e-1	1.92e-1	1.26e+3	3.21e+2
1000	1.99e-2	8.92e-5	2.24e+1	3.06e-1	1.40e-1	2.29e+3	5.44e+2
2000	1.54e-2	3.93e-5	2.55e+1	2.16e-1	8.58e-2	3.97e+3	9.46e+2
4000	1.05e-2	1.43e-5	2.73e+1	1.35e-1	4.52e-2	6.69e+3	1.66e+3

T -> Mo

Sputtering yield of Mo by T

z1 = 1, m1 = 3.02, z2=42, m2 = 95.94, sbe = 6.89 eV, rho = 10.20 g/cm**3
 ef=0.90 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: newtrim, TPP 9/82
 ne = 7, na = 2

E ₀ (eV)	0°	65°
100	9.32e-4	7.36e-4
170	6.67e-3	8.00e-3
300	1.59e-2	2.93e-2
500	2.20e-2	5.84e-2
1000	2.73e-2	9.33e-2
2000	2.90e-2	1.01e-1
5000	2.58e-2	9.56e-2

Sputtered energy of Mo by T

program: newtrim
 ne = 7, na = 2

E ₀ (eV)	0°	65°
100	1.45e-5	1.28e-5
170	1.57e-4	2.00e-4
300	3.37e-4	7.16e-4
500	4.43e-4	1.18e-3
1000	4.31e-4	1.44e-3
2000	2.78e-4	1.09e-3
5000	1.32e-4	5.25e-4

Particle reflection coefficient of T backscattered from Mo

z1 = 1, m1 = 3.02, z2 = 42, m2 = 95.94, sbe = 6.89 eV, rho = 10.20 g/cm**3
 ef=0.90 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot=1 (KrC)
 program: newtrim
 ne = 7, na = 2

E ₀ (eV)	0°	65°
100	5.58e-1	7.77e-1
170	5.33e-1	7.40e-1
300	4.98e-1	7.08e-1
500	4.68e-1	6.83e-1
1000	4.20e-1	6.37e-1
2000	3.61e-1	5.94e-1
5000	2.68e-1	5.21e-1

Energy reflection coefficient of T backscattered from Mo

ne = 7, na = 2

E ₀ (eV)	0°	65°
100	3.39e-1	6.07e-1
170	3.16e-1	5.58e-1
300	2.88e-1	5.20e-1
500	2.63e-1	4.89e-1
1000	2.27e-1	4.34e-1
2000	1.83e-1	3.99e-1
5000	1.21e-1	3.20e-1

Average depth (mean range) in of T implanted in Mo

ne = 7, na = 2

E ₀ (eV)	0°	65°
100	3.78e+1	3.58e+1
170	5.21e+1	4.89e+1
300	7.49e+1	6.96e+1
500	1.05e+2	9.68e+1
1000	1.70e+2	1.55e+2
2000	2.88e+2	2.56e+2
5000	5.95e+2	5.08e-f-2

T -> Mo

T on Mo. Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1. m1= 2.01. z2=42. m2= 95.94. sbe=6.89 eV. rho=10.20 g/cm**3
 ef=0.90 eV. esb = 1.00 eV. cas=1.00, kk0 = kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program: newtrim (Laszlo)
 ne=10

kT(eV)	Y	Y _#	R _{sp}	H _N	R _f	B _b	range
30	5.42e-4	3.62e-5	4.02e-]0	7.28e-1	5.12e-1	4.22e+1	2.76e+1
40	1.49e-3	8.85e-5	4.77e+0	7.11e-1	4.92e-1	5.53e+1	3.26e+1
70	6.27e-3	2.88e-4	6.46e-f-0	6.81e-1	4.56e-1	9.42e+1	4.57e+1
100	1.10e-2	4.18e-4	7.60e+0	6.58e-1	4.33e-1	1.32e+2	5.66e+1
170	2.23e-2	6.64e-4	1.01e+1	6.29e-1	4.01e-1	2.15e+2	7.87e+1
300	3.81e-2	8.09e-4	1.28e-(-1	5.92e-1	3.64e-1	3.70e+2	1.15e+2
500	4.99e-2	8.12e-4	1.64e+1	5.62e-1	3.38e-1	6.03e+2	1.67e-(-2
1000	5.75e-2	6.24e-4	2.17e-f-1	5.06e-1	2.83e-1	1.12e+3	2.82e-f-2
2000	6.42e-2	4.20e-4	2.60e-]-1	4.51e-1	2.31e-1	2.03e+3	4.73e+2
5000	5.52e-2	2.01e-4	3.63e+1	3.69e-1	1.68e-1	4.54e+3	9.86e+2

T on Mo. Maxwellian velocity distribution, sheath potential 3 kT
 ne= 10

kT(eV)	Y	Y _e	E _{sp}	R _N	R _e	R _b	range
20	7.85e-4	2.65e-5	3.37e+0	5.90e-1	3.73e-1	6.32e+1	3.71e+1
40	7.49e-3	2.18e-4	5.81e+0	5.55e-1	3.39e-1	1.22e-]-2	5.64e+1
70	1.79e-2	4.42e-4	8.61e-t-0	5.21e-1	3.09e-1	2.08e+2	8.06e+1
100	2.48e-2	5.30e-4	1.07e-f-1	5.00e-1	2.94e-1	2.95e+2	1.02e+2
170	3.13e-2	5.00e-4	1.35e+1	4.65e-1	2.62e-1	4.78e+2	1.48e+2
300	3.40e-2	4.07e-4	1.80e+1	4.22e-1	2.30e-1	8.18e+2	2.24e+2
500	3.44e-2	2.92e-4	2.12e-J-1	3.78e-1	1.96e-1	1.30e+3	3.31e-]-2
1000	3.23e-2	1.66e-4	2.57e+1	3.11e-1	1.47e-1	2.37e+3	5.75e+2
2000	2.51e-2	8.08e-5	3.21e-]-1	2.27e-1	9.50e-2	4.18e-J-3	1.02e-]-3
5000	1.36e-2	2.01e-5	3.71e+1	1.25e-1	4.19e-1	8.39e+3	2.22e+3

He → Mo

Sputtering yield of Mo by He

z1 = 2, m1 = 4.00, z2 = 42, m2 = 95.94, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 5, kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx, TPP 9/82
 ne = 2, na = 9

E ₀ (eV)	0°	25°	50°	75°	80°	85°	87°	88°	89°
50000	2.64e-2	3.50e-2	6.95e-2	2.45e-1	3.75e-1	6.17e-1	6.56e-1	5.91e-1	9.49e-2
100000	1.67e-2	2.27e-2	3.97e-2	1.64e-1	2.40e-1	4.47e-1	6.04e-1	6.10e-1	3.65e-1

Sputtered energy of Mo by He

program: testvmcx
 ne = 2, na = 5

E ₀ (eV)	80°	85°	87°	88°	89°
50000	5.93e-4	1.12e-3	1.31e-3	1.27e-3	2.04e-4
100000	2.70e-4	5.08e-4	6.78e-4	7.90e-4	5.06e-4

Particle reflection coefficient of He backscattered from Mo

z1 = 2, m1 = 4.00, z2 = 42, m2 = 95.94, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = 5, kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx
 ne = 2, na = 5

E ₀ (eV)	80°	85°	87°	88°	89°
50000	4.85e-1	6.14e-1	6.98e-1	7.93e-1	9.73e-1
100000	4.15e-1	5.77e-1	6.61e-1	7.42e-1	8.88e-1

Energy reflection coefficient of He backscattered from Mo

ne = 2, na = 5

E ₀ (eV)	80°	85°	87°	88°	89°
50000	2.41e-1	3.77e-1	4.94e-1	6.30e-1	9.47e-1
100000	1.70e-1	3.15e-1	4.23e-1	5.29e-1	7.88e-1

Average depth (mean range) in of He implanted in Mo

ne = 2, na = 5

E ₀ (eV)	80°	85°	87°	88°	89°
50000	6.57e+2	6.23e+2	6.43e+2	6.50e+2	6.73e+2
100000	9.82e+2	9.31e+2	9.08e+2	9.18e+2	9.29e+2

He -> Mo

Sputtering yield of Mo (7 isotopes) by He
 z1 = 2, m1 = 4.00, z2=42, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdec1 = kdec2 = 3, ipot=ipotr=1 (KrC)
 m2= 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2=0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00
 program: trvmc95
 ne=12, na= 1, n(m2) = 7

Eo(eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
70	1.466e-4	7.796e-5	1.226e-4	1.176e-4	6.176e-5	1.432e-4	4.763e-5	850000000
70	1.470e-4	7.734e-5	1.224e-4	1.180e-4	6.169e-5	1.422e-4	4.737e-5	850000000
70	1.465e-4	7.712e-5	1.228e-4	1.176e-4	6.205e-5	1.419e-4	4.791e-5	600000000
100	9.730e-4	5.651e-4	9.390e-4	9.465e-4	5.251e-4	1.274e-3	4.730e-4	600000000
100	9.730e-4	5.660e-4	9.387e-4	9.466e-4	5.239e-4	1.274e-3	4.736e-4	190000000
100	9.699e-4	5.665e-4	9.394e-4	9.493e-4	5.219e-4	1.276e-3	4.721e-4	160000000
200	4.490e-3	2.711e-3	4.586e-3	4.722e-3	2.664e-3	6.620e-3	2.560e-3	350000000
500	1.018e-2	6.231e-3	1.064e-2	1.106e-2	6.279e-3	1.571e-2	6.168e-3	250000000
1000	1.347e-2	8.282e-3	1.415e-2	1.472e-2	8.379e-3	2.101e-2	8.275e-3	150000000
2000	1.535e-2	9.469e-3	1.619e-2	1.687e-2	9.610e-3	2.413e-2	9.514e-3	90000000
5000	1.519e-2	9.366e-3	1.604e-2	1.670e-2	9.542e-3	2.393e-2	9.451e-3	50000000
5000	1.518e-2	9.369e-3	1.603e-2	1.676e-2	9.546e-3	2.403e-2	9.493e-3	15000064

Sputtered energy of Mo (7 isotopes) by He
 ne=12, na= 1, n(m2)= 7

Eo(eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
70	2.713e-6	1.348e-6	2.050e-6	1.897e-6	9.614e-7	2.156e-6	6.657e-7	850000000
70	2.714e-6	1.337e-6	2.046e-6	1.910e-6	9.611e-7	2.144e-6	6.634e-7	850000000
70	2.709e-6	1.333e-6	2.049e-6	1.902e-6	9.649e-7	2.133e-6	6.744e-7	600000000
100	2.767e-5	1.555e-5	2.538e-5	2.518e-5	1.375e-5	3.283e-5	1.181e-5	600000000
100	2.766e-5	1.559e-5	2.550e-5	2.515e-5	1.373e-5	3.285e-5	1.178e-5	190000000
100	2.746e-5	1.553e-5	2.541e-5	2.527e-5	1.369e-5	3.289e-5	1.177e-5	160000000
200	1.431e-4	8.493e-5	1.422e-4	1.449e-4	8.128e-5	2.000e-4	7.604e-5	350000000
500	2.500e-4	1.511e-4	2.560e-4	2.641e-4	1.491e-4	3.707e-4	1.436e-4	250000000
1000	2.389e-4	1.447e-4	2.459e-4	2.548e-4	1.439e-4	3.591e-4	1.399e-4	150000000
2000	1.825e-4	1.112e-4	1.887e-4	1.955e-4	1.107e-4	2.769e-4	1.083e-4	90000000
5000	9.999e-5	6.063e-5	1.035e-4	1.072e-4	6.139e-5	1.520e-4	5.911e-5	50000000
5000	9.963e-5	6.116e-5	1.035e-4	1.075e-4	6.100e-5	1.523e-4	5.950e-5	15000064

He -4- Mo

Particle reflection coefficient of He backscattered from Mo (7 isotopes)
 z1= 2, m1 = 4.00, z2=42, sbe=6.83 eV, rho = 10.21 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0 = kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 m2 = 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2=0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00
 program: trvmc95
 ne=12, na= 1

E ₀ (eV)	0°	nh
70	5.9232e-1	850000000
70	5.9231e-1	850000000
70	5.9231e-1	600000000
100	5.7147e-1	600000000
100	5.7148e-1	190000000
100	5.7146e-1	160000000
200	5.3703e-1	350000000
500	4.9565e-1	250000000
1000	4.6152e-1	150000000
2000	4.2144e-1	90000000
5000	3.5541e-1	50000000
5000	3.5512e-1	15000064

Energy reflection coefficient of He backscattered from Mo (7 isotopes)
 ne=12, na= 1

E ₀ (eV)	0°	nh
70	3.6532e-1	850000000
70	3.6532e-1	850000000
70	3.6533e-1	600000000
100	3.4733e-1	600000000
100	3.4735e-1	190000000
100	3.4733e-1	160000000
200	3.1877e-1	350000000
500	2.8680e-1	250000000
1000	2.6180e-1	150000000
2000	2.3298e-1	90000000
5000	1.8597e-1	50000000
5000	1.8583e-1	15000064

Average depth (mean range) in Å of He implanted in Mo (7 isotopes)
 ne=12, na= 1

E ₀ (eV)	0°	nh
70	2.0181e+1	850000000
70	2.0180e+1	850000000
70	2.0179e+1	600000000
100	2.4804e+1	600000000
100	2.4804e+1	190000000
100	2.4805e+1	160000000
200	3.7600e+1	350000000
500	6.7532e+1	250000000
1000	1.0880e+2	150000000
2000	1.8160e+2	90000000
5000	3.7809e+2	50000000
5000	3.7819e+2	15000064

C -4- Mo

C on Mo, Maxwellian velocity distribution, sheath potential 9 kT
 z1= 6, m1= 12.01, z2=42, m2= 95.94, sbe=6.83 eV, rho= 10.21 g/cm**3
 ef=0.98 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: trvmc
 only low fluence!
 ne= 4

kT(eV)	Y	Y _β	E _{βp}	R _{TV}	R _β	E _β	range
5	1.19e-2	8.05e-4	3.71e+0	5.53e-1	2.65e-1	2.64e+1	7.44e+0
10	7.12e-2	4.66e-3	7.21e+0	4.85e-1	2.22e-1	5.03e+1	1.07e+1
20	1.80e-1	9.44e-3	1.15e-j-1	4.29e-1	1.88e-1	9.65e+1	1.55e+1
40	3.22e-1	1.18e-2	1.61e+1	3.90e-1	1.64e-1	1.85e+2	2.31e+1

O Mo

Sputtering yield of Mo by O)
 z1= 8, m1= 16.00, z2=42, m2= 95.94, sbe=6.83 eV, rho= 10.20 g/cm**3
 ef=0.95 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: TPP 9/82
 only low fluence!
 ne= 9, na= 1

E ₀ (eV)	0°
20	2.80e-4
30	3.60e-3
40	1.22e-2
50	2.15e-2
70	5.48e-2
100	1.07e-1
200	2.28e-1
500	4.51e-1
1000	6.42e-1

Ne → Mo

Sputtering yield of Mo (7 isotopes) by Ne

z1=10, m1= 20.18, z2=42, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kkO=kkOr=2, kdee1 = kdee2 = 3, ipot=ipotr = 1 (KrC)
 m2= 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2=0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00
 program: trvmc95
 ne= 2, na= 1, n(m2)= 7

E ₀ (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
100	1.499e-2	9.102e-3	1.546e-2	1.597e-2	9.033e-2	2.252e-2	8.754e-3	350000000
100	1.494e-2	9.083e-3	1.541e-2	1.592e-2	9.004e-3	2.245e-2	8.730e-3	350000000

Sputtered energy of Mo (7 isotopes) by Ne

ne= 2, na= 1, n(m2)= 7

E _q (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
100	1.162e-3	6.982e-4	1.178e-3	1.210e-3	6.809e-4	1.688e-3	6.487e-4	350000000
100	1.157e-3	6.951e-4	1.173e-3	1.205e-3	6.770e-4	1.680e-3	6.455e-4	350000000

Particle reflection coefficient of Ne backscattered from Mo (7 isotopes)

z1=10, m1= 20.18, z2=42, sbe=6.83 eV, rho=10.21 g/cm**3
 cf=0.20 eV, esb=0.00 eV, ca=1.00, kkO=kkOr=2, kdee1 = kdee2 = 3, ipot=ipotr= 1 (KrC)
 m2= 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2=0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00
 program: trvmc95
 ne= 2, na= 1

E ₀ (eV)	0°.....	nh
100	4.3782e-1	350000000
100	4.3782e-1	350000000

Energy reflection coefficient of Ne backscattered from Mo (7 isotopes)

ne= 2, na= 1

E ₀ (eV)	0°	nh
100	1.5043e-1	350000000
100	1.5043e-1	350000000

Average depth (mean range) in Å of Ne implanted in Mo (7 isotopes)

ne= 2, na= 1

E _q (eV)	0°.....	nh
100	7.6080e+0	350000000
100	7.6258e+0	350000000

Ar → Mo

Sputtering yield of Mo (2 isotopes) by Ar

z1 = 18, m1 = 39.95, z2=42, m2= 92.00, 100.00, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot= 1 (KrC)
 alpha=0.00

program: testvmcx, trvmc
 ne= 8, na= 1, n(m2) = 2

E ₀ (eV)	m2 = 92.00	100.00	92	100	nh
5000	1.096e-0	1.065e-0	0.5000	0.5000	2000000
5000	1.096e-0	1.066e-0	0.5000	0.5000	2000000
5000	1.094e-0	1.065e-0	0.5000	0.5000	1500000
5000	1.078e-0	1.079e-0	0.4930	0.5070	2000000
5000	1.079e-0	1.082e-0	0.4920	0.5080	2000000
5000	1.072e-0	1.086e-0	0.4900	0.5100	2000000
10000	1.243e-0	1.211e-0	0.5000	0.5000	1600000
10000	1.225e-0	1.225e-0	0.4935	0.5065	1700000

Sputtered energy of Mo (2 isotopes) by Ar

ne= 8, na= 1, n(m2)= 2

E ₀ (eV)	m2 = 92.00	100.00	92	100	nh
5000	9.773e-3	9.226e-3	0.5000	0.5000	2000000
5000	9.786e-3	9.239e-3	0.5000	0.5000	2000000
5000	9.753e-3	9.253e-3	0.5000	0.5000	1500000
5000	9.638e-3	9.362e-3	0.4930	0.5070	2000000
5000	9.643e-3	9.395e-3	0.4920	0.5080	2000000
5000	9.576e-3	9.431e-3	0.4900	0.5100	2000000
10000	7.501e-3	7.061e-3	0.5000	0.5000	1600000
10000	7.366e-3	7.134e-3	0.4935	0.5065	1700000

Particle reflection coefficient of Ar backscattered from Mo (2 isotopes)

z1 = 18, m1= 39.95, z2=42, m2= 92.00, 100.00, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 alpha=0.00

program: testvmcx, trvmc
 ne= 8, na= 1

E ₀ (eV)	0°	92	100	nh
5000	1.2234e-1	0.5000	0.5000	2000000
5000	1.2257e-1	0.5000	0.5000	2000000
5000	1.2208e-1	0.5000	0.5000	1500000
5000	1.2281e-1	0.4930	0.5070	2000000
5000	1.2308e-1	0.4920	0.5080	2000000
5000	1.2240e-1	0.4900	0.5100	2000000
10000	1.0202e-1	0.5000	0.5000	1600000
10000	1.0170e-1	0.4935	0.5065	1700000

Energy reflection coefficient of Ar backscattered from Mo (2 isotopes)

ne= 8, na= 1

E ₀ (eV)	0°	92	100	nh
5000	1.9446e-2	0.5000	0.5000	2000000
5000	1.9386e-2	0.5000	0.5000	2000000
5000	1.9323e-2	0.5000	0.5000	1500000
5000	1.9436e-2	0.4930	0.5070	2000000
5000	1.9469e-2	0.4920	0.5080	2000000
5000	1.9393e-2	0.4900	0.5100	2000000
10000	1.6201e-2	0.5000	0.5000	1600000
10000	1.6227e-2	0.4935	0.5065	1700000

Average depth (mean range) in of Ar implanted in Mo (2 isotopes)

ne= 8, na= 1

E ₀ (eV)	0°	92	100	nh
5000	4.7541e-1	0.5000	0.5000	2000000
5000	4.7528e+1	0.5000	0.5000	2000000
5000	4.7615e+1	0.5000	0.5000	1500000
5000	4.7580e+1	0.4930	0.5070	2000000
5000	4.7609e+1	0.4920	0.5080	2000000
5000	4.7609e+1	0.4900	0.5100	2000000
10000	7.5684e+1	0.5000	0.5000	1600000
10000	7.5765e+1	0.4935	0.5065	1700000

Ar → Mo

Sputtering yield of Mo (7 isotopes) by Ar
 z1 = 18, m1 = 39.95, z2 = 42, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 m2 = 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2 = 0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha = 0.00, rd = 50.00
 program: trvmc95
 ne = 20, na = 4, n(m2) = 7

E _a (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh	comment
50	1.113e-3	6.586e-4	1.105e-3	1.130e-3	6.305e-4	1.551e-3	5.871e-4	500000000	
70	4.954e-3	2.987e-3	5.056e-3	5.205e-3	2.934e-3	7.276e-3	2.803e-3	300000000	
70	4.961e-3	2.988e-3	5.055e-3	5.211e-3	2.936e-3	7.278e-3	2.802e-3	500000000	
100	1.363e-2	8.311e-3	1.415e-2	1.465e-2	8.297e-3	2.068e-2	8.064e-3	200000000	
100	1.363e-2	8.308e-3	1.413e-2	1.463e-2	8.296e-3	2.068e-2	8.065e-3	350000000	
200	4.522e-2	2.780e-2	4.748e-2	4.938e-2	2.808e-2	7.047e-2	2.770e-2	100000000	
200	4.522e-2	2.781e-2	4.751e-2	4.942e-2	2.811e-2	7.042e-2	2.771e-2	210000000	
500	1.127e-1	6.958e-2	1.191e-1	1.241e-1	7.074e-2	1.776e-1	7.013e-2	80000000	
1000	1.772e-1	1.096e-1	1.877e-1	1.958e-1	1.117e-1	2.806e-1	1.110e-1	50000000	
2000	2.479e-1	1.534e-1	2.630e-1	2.744e-1	1.568e-1	3.942e-1	1.560e-1	25000064	
5000	3.358e-1	2.083e-1	3.570e-1	3.725e-1	2.129e-1	5.358e-1	2.122e-1	10000000	
5000	3.362e-1	2.083e-1	3.572e-1	3.729e-1	2.131e-1	5.360e-1	2.126e-1	15000064	
10000	3.836e-1	2.377e-1	4.070e-1	4.259e-1	2.431e-1	6.119e-1	2.427e-1	8000000	
20000	3.985e-1	2.470e-1	4.241e-1	4.427e-1	2.528e-1	6.368e-1	2.525e-1	9000064	
20000	4.005e-1	2.483e-1	4.262e-1	4.454e-1	2.544e-1	6.401e-1	2.536e-1	9000064	rd=60.00 Å
100	1.571e-2	9.564e-3	1.625e-2	1.684e-2	9.542e-3	2.378e-2	9.264e-3	350000000	alpha= 15°
100	2.173e-2	1.321e-2	2.246e-2	2.322e-2	1.315e-2	3.276e-2	1.275e-2	350000000	alpha=30°
100	3.005e-2	1.832e-2	3.114e-2	3.224e-2	1.826e-2	4.556e-2	1.775e-2	400000000	alpha=60°
100	1.477e-2	9.007e-3	1.535e-2	1.588e-2	9.011e-3	2.248e-2	8.774e-3	240000000	zbl
5000	-3.743e-1	2.321e-1	3.980e-1	4.155e-1	2.378e-1	5.979e-1	2.370e-1	10000000	zbl

Sputtered energy of Mo (7 isotopes) by Ar
 ne=20, na= 4, n(m2) = 7

E _o (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh	comment
50	9.598e-5	5.629e-5	9.446e-5	9.605e-5	5.344e-5	1.310e-4	4.917e-5	500000000	
70	4.123e-4	2.469e-4	4.163e-4	4.272e-4	2.400e-4	5.940e-4	2.273e-4	300000000	
70	4.125e-4	2.470e-4	4.165e-4	4.279e-4	2.403e-4	5.936e-4	2.273e-4	500000000	
100	1.027e-3	6.234e-4	1.058e-3	1.091e-3	6.166e-4	1.531e-3	5.940e-4	200000000	
100	1.028e-3	6.226e-4	1.056e-3	1.091e-3	6.161e-4	1.531e-3	5.938e-4	350000000	
200	2.500e-3	1.529e-3	2.606e-3	2.702e-3	1.533e-3	3.834e-3	1.500e-3	100000000	
200	2.500e-3	1.529e-3	2.605e-3	2.704e-3	1.533e-3	3.835e-3	1.500e-3	210000000	
500	3.737e-3	2.294e-3	3.912e-3	4.068e-3	2.314e-3	5.794e-3	2.278e-3	80000000	
1000	3.956e-3	2.434e-3	4.152e-3	4.320e-3	2.456e-3	6.157e-3	2.423e-3	50000000	
2000	3.710e-3	2.283e-3	3.896e-3	4.049e-3	2.310e-3	5.781e-3	2.275e-3	25000064	
5000	2.985e-3	1.835e-3	3.131e-3	3.260e-3	1.853e-3	4.649e-3	1.831e-3	10000000	
5000	2.986e-3	1.834e-3	3.135e-3	3.265e-3	1.857e-3	4.644e-3	1.830e-3	15000064	
10000	2.322e-3	1.421e-3	2.427e-3	2.530e-3	1.435e-3	3.604e-3	1.417e-3	8000000	
20000	1.651e-3	1.013e-3	1.734e-3	1.800e-3	1.019e-3	2.562e-3	9.997e-4	9000064	
20000	1.660e-3	1.018e-3	1.739e-3	1.808e-3	1.031e-3	2.569e-3	1.009e-3	9000064	rd=60.00 Å
100	1.294e-3	7.833e-4	1.327e-3	1.373e-3	7.754e-4	1.927e-3	7.467e-4	350000000	alpha= 15°
100	2.166e-3	1.310e-3	2.223e-3	2.292e-3	1.295e-3	3.219e-3	1.248e-3	350000000	alpha=30°
100	4.992e-3	3.028e-3	5.132e-3	5.298e-3	2.993e-3	7.447e-3	2.887e-3	400000000	alpha=60°
100	1.148e-3	6.959e-4	1.183e-3	1.219e-3	6.905e-4	1.718e-3	6.666e-4	240000000	zbl
5000	3.501e-3	1.876e-3	3.189e-3	3.319e-3	1.891e-3	4.746e-3	1.868e-3	10000000	zbl

Ar Mo

Particle reflection coefficient of Ar backscattered from Mo (7 isotopes)
 z1= 18, m1= 39.95, z2=42, sbe=6.83 eV. rho = 10.21 g/cm**3
 ef=0.20 eV. esb=0.00 eV. ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 m2= 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2= 0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00. rd=50.00
 program: trvme95
 ne=20. na= 4, n(m2)= 7

Eo(eV)	0°	nh	comment
50	4.082e-1	500000000	
70	3.711e-1	300000000	
70	3.711e-1	500000000	
100	3.337e-1	200000000	
100	3.338e-1	350000000	
200	2.725e-1	100000000	
200	2.727e-1	210000000	
500	2.140e-1	80000000	
1000	1.819e-1	50000000	
2000	1.565e-1	25000064	
5000	1.284e-1	10000000	
5000	1.283e-1	15000064	
10000	1.088e-1	8000000	
20000	8.981e-2	9000064	
20000	8.988e-2	9000064	rd = 60.00 Å
100	3.584e-1	350000000	alpha=15°
100	4.326e-1	350000000	alpha=30°
100	7.666e-1	400000000	alpha=60°
100	3.834e-1	240000000	zbl
5000	1.232e-1	10000000	zbl

Energy reflection coefficient of Ar backscattered from Mo (7 isotopes)
 ne=20, na= 4, n(m2)= 7

Bo(eV)	0°	nh	comment
50	7.077e-2	500000000	
70	6.549e-2	300000000	
70	6.550e-2	500000000	
100	5.937e-2	200000000	
100	5.938e-2	350000000	
200	4.806e-2	100000000	
200	4.810e-2	210000000	
500	3.660e-2	80000000	
1000	3.055e-2	50000000	
2000	2.612e-2	25000064	
5000	2.163e-2	10000000	
5000	2.163e-2	15000064	
10000	1.871e-2	8000000	
20000	1.581e-2	9000064	
20000	1.585e-2	9000064	rd = 60.00 Å
100	7.092e-2	350000000	alpha=15°
100	1.112e-1	350000000	alpha=30°
100	4.006e-1	400000000	alpha=60°
100	7.006e-2	240000000	zbl
5000	2.169e-2	10000000	zbl

Average depth (mean range) in Å of Ar implanted in Mo (7 isotopes)
 ne=20, na= 4, n(m2)= 7

E _o (eV)	0°	nh	comment
50	3.963e+0	500000000	
70	4.675e+0	300000000	
70	4.675e+0	500000000	
100	5.569e+0	200000000	
100	5.569e+0	350000000	
200	7.874e+0	100000000	
200	7.873e+0	210000000	
500	1.268e+1	80000000	
1000	1.853e+1	50000000	
2000	2.766e+1	25000064	
5000	4.901e+1	10000000	
5000	4.899e+1	15000064	
10000	7.877e+1	8000000	
20000	1.323e+2	9000064	
20000	1.324e+2	9000064	rd=60.00 Å
100	5.501e+0	350000000	alpha=15°
100	5.322e+0	350000000	alpha=30°
100	4.654e+0	400000000	alpha=60°
100	4.243e+0	240000000	zbl
5000	4.397e+1	10000000	zbl

Kr —yMo

Sputtering yield of Mo by Kr

z1=36, m1= 83.80, z2=42, m2= 95.94, sbe=6.89 eV, rho=10.20 g/cm**3
 ef=0.30 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvme, trvmc
 ne= 6, na= 2

Eo(eV)	0°	45°
50	9.15e-4	
53		3.40e-2
100	3.20e-2	
500	6.36e-1	
1000	1.19e-0	
5000	2.69e-0	

Sputtered energy of Mo by Kr

ne= 6, na= 2

Bo (eV)	0°	45°
50	5.54e-5	
53		4.86e-3
100	1.67e-3	
500	1.63e-2	
1000	2.08e-2	
5000	1.95e-2	

Particle reflection coefficient of Kr backscattered from Mo

z1=36, m1= 83.80, z2=42, m2= 95.94, sbe=6.89 eV, rho=10.20 g/cm**3
 ef=0.30 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvme, trvmc
 ne= 6, na= 2

Eo (eV)	0°	45°
50	1.44e-1	
53		4.52e-1
100	1.23e-1	
500	8.89e-2	
1000	6.92e-2	
5000	4.19e-2	

Energy reflection coefficient of Kr backscattered from Mo

ne= 6, na= 2

Eo (eV)	0°	45°
50	6.90e-3	
53		1.05e-1
100	5.89e-3	
500	3.97e-3	
1000	3.26e-3	
5000	2.37e-3	

Average depth (mean range) in Å of Kr implanted in Mo

ne= 6, na= 2

Eo (eV)	0°	45°
50	3.33e+0	
53		2.65e+0
100	4.85e+0	
500	1.08e+1	
1000	1.52e+1	
5000	3.61e+1	

Mo -> Mo

Sputtering yield of Mo by Mo

z1 = 42, m1 = 95.94, z2=42, m2 = 95.94, sbe=6.89, 6.83 eV, rho = 10.21 g/cm**3
 ef=6.39, 6.78 eV, esb=6.89, 6.83 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl (KrC)
 program: newtrim (Laszlo), testvmcx, TPP 9/82
 ne=28, na=14

Bq (eV)	0°	10°	20°	30°	40°	45°	50°	55°	57.5°	60°	62.5°	65°
15												2.04e-4
17												3.88e-4
18												5.49e-4
20												6.49e-4
25	6.90e-6											4.04e-3
30	2.61e-5											1.15e-2
35	7.30e-5											
40	7.56e-5											
42	1.27e-4											
45	2.45e-4											
48	4.44e-4											
50	6.36e-4											
65	3.87e-3											
80	1.04e-2											
100	2.59e-2											
200	1.51e-1											
250	2.46e-1											
300	3.15e-1	3.61e-1	4.84e-1	6.50e-1	8.68e-1		1.04e-0	1.07e-0	1.07e-0	1.07e-0	1.04e-0	9.92e-1
350	3.90e-1	4.51e-1	5.71e-1	7.83e-1	9.94e-1	1.10e-0	1.19e-0	1.23e-0	1.23e-0	1.23e-0	1.19e-0	1.16e-0
500	6.14e-1											1.53e-0
1000	1.12e-0	1.20e-0	1.44e-0	1.77e-0	2.17e-0	2.41e-0	2.60e-0	2.73e-0	2.81e-0	2.82e-0	2.80e-0	2.71e-0
2000	1.76e-0	1.87e-0	2.21e-0	2.53e-0	3.28e-0		3.88e-0	4.22e-0	4.26e-0	4.42e-0	4.36e-0	4.38e-0
5000	2.88e-0											
10000	3.42e-0											
20000	3.96e-0											
45000	4.87e-0											
50000	4.88e-0											
100000	4.11e-0											

Eq (eV)	70°	80°
300	8.53e-1	3.99e-1
350	9.84e-1	4.55e-1
1000	1.18e-0	
2000	4.11e-0	2.21e-0

Sputtered energy of Mo by Mo

program: newtrim (Laszlo), testvmcx
 ne=27, na=14

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	55°	57.5°	60°	62.5°	65°
15												3.40e-5
17												6.70e-5
18												9.49e-5
20												1.26e-4
25	3.37e-7											8.11e-4
30	1.32e-6											2.45e-3
35	3.78e-6											
40	4.75e-6											
42	7.68e-6											
45	1.55e-5											
48	2.76e-5											
50	3.89e-5											
65	2.25e-4											
80	5.51e-4											
100	1.27e-3											
200	5.76e-3											
250	8.21e-3											
300	9.82e-3	1.23e-2	2.15e-2	3.66e-2	6.36e-2		9.80e-2	1.12e-1	1.20e-1	1.25e-1	1.26e-1	1.29e-1
350	1.10e-2	1.45e-2	2.30e-2	4.03e-2	6.77e-2	8.51e-2	1.02e-1	1.19e-1	1.26e-1	1.33e-1	1.37e-1	1.38e-1
500	1.47e-2											1.51e-1
1000	1.89e-2	2.17e-2	3.18e-2	4.94e-2	7.78e-2	9.88e-2	1.17e-1	1.36e-1	1.52e-1	1.56e-1	1.67e-1	1.75e-1
2000	1.99e-2	2.41e-2	3.17e-2	4.56e-2	7.59e-2		1.13e-1	1.39e-1	1.49e-1	1.57e-1	1.67e-1	1.79e-1
5000	2.04e-2											
10000	1.60e-2											
20000	1.39e-2											
50000	1.07e-2											
100000	5.69e-3											

E _s (eV)	70°	80°
300	1.20e-1	6.03e-2
350	1.29e-1	6.45e-1
1000		9.86e-2
2000	1.94e-1	1.32e-1

Mo → Mo

Particle reflection coefficient of Mo backscattered from Mo
 z1=42, m1= 95.94, z2= 42, m2= 95.94, sbe=6.89, 6.83 eV, rho=10.21 g/cm**3
 cf=6.39, 6.78 eV, esb=6.89, 6.83 eV, ca=1.00, kk0=kk0r=2, kdee=kdee2=3, ipot=ipotr = 1 (KrC)
 program: newtrim (Laszlo), testvmcx
 ne = 28, na=14

Eq(eV)	0°	10°	20°	30°	40°	45°	50°	55°	57.5°	60°	62.5°	65°
15												6.12e-5
17												3.62e-4
18												7.06e-4
20												1.88e-3
25												1.14e-2
30												3.33e-2
35	3.04e-7											
40	8.33e-6											
42	1.15e-5											
45	2.28e-5											
48	4.46e-5											
50	6.97e-5											
50	2.87e-4											
65	3.12e-4											1.67e-1
80	9.97e-4											3.62e-1
100	2.12e-3											4.46e-1
200	1.07e-2											5.41e-1
265	1.04e-2											
300	1.24e-2	1.98e-2	3.37e-2	7.45e-2	1.40e-1		2.47e-1	3.33e-1	3.77e-1	4.29e-1	4.67e-1	5.38e-1
350	1.36e-2	1.96e-2	3.70e-2	7.22e-2	1.40e-1	1.86e-1	2.51e-1	3.24e-1	3.67e-1	4.16e-1	4.70e-1	5.29e-1
500	2.02e-2											5.13e-1
1000	2.40e-2	2.60e-2	4.06e-2	6.85e-2	1.13e-1	1.51e-1	2.05e-1	2.68e-1	2.89e-1	3.41e-1	3.91e-1	4.34e-1
2000	2.85e-2	3.05e-2	3.63e-2	6.35e-2	1.07e-1		1.93e-1	2.15e-1	2.51e-1	2.95e-1	3.25e-1	3.79e-1
5000	2.04e-2											3.12e-1
10000	2.20e-2											2.78e-1
20000	1.67e-2											2.38e-1
50000	8.80e-3											2.26e-1
100000												2.20e-1

E ₀ (eV)	70°	80°
300	6.63e-1	9.07e-1
350	6.59e-1	9.07e-1
1000		8.72e-1
2000	4.88e-1	8.20e-1

Energy reflection coefficient of Mo backscattered from Mo
 ne=29, na=14

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	55°	57.5°	60°	62.5°	65°
15												1.35e-5
17												8.03e-5
18												1.57e-4
20												4.31e-4
25												2.78e-3
30												8.83e-3
35	3.00e-9											
40	1.85e-8											
40	5.66e-7											
42	6.67e-7											
45	1.51e-6											
48	2.97e-6											
50	5.05e-6											
50	2.36e-5											5.40e-2
65	2.15e-5											
80	6.66e-5											1.29e-1
100	1.21e-4											1.68e-1
200	6.24e-4											2.25e-1
265	5.67e-4											
300	6.36e-4	1.22e-3	2.87e-3	9.32e-3	2.42e-2		6.30e-2	1.01e-1	1.22e-1	1.52e-1	1.89e-1	2.26e-1
350	6.85e-4	1.16e-3	3.05e-3	8.25e-3	2.49e-2	3.79e-2	6.15e-2	9.63e-2	1.20e-1	1.46e-1	1.81e-1	2.21e-1
500	9.14e-4											2.13e-1
500	1.11e-3											
1000	9.35e-4	1.64e-3	2.81e-3	7.20e-3	1.61e-2	2.65e-2	4.45e-2	6.70e-2	8.12e-2	1.04e-1	1.33e-1	1.67e-1
2000	1.07e-3	1.14e-3	2.05e-3	5.24e-3	1.41e-2		3.77e-2	4.81e-2	6.45e-2	7.94e-2	1.02e-1	1.33e-1
5000	8.24e-4											9.42e-2
10000	8.85e-4											8.24e-2
20000	5.31e-4											6.47e-2
50000	4.91e-4											6.17e-2
100000												6.09e-2

Eq (eV)	70°	80°
300	3.31e-1	6.05e-1
350	3.27e-1	6.16e-1
1000		6.15e-1
2000	2.06e-1	5.64e-1

Mo → Mo

Average depth (mean range) in A of Mo implanted in Mo
 z1=42, m1 = 95.94, z2=42, m2 = 95.94, sbe=6.89, 6.83 eV, rho = 10.21 g/cm**3
 ef=6.39, 6.78 eV, esb=6.89, 6.83 eV, ca=1.00, kk0 = kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: newtrim (Laszlo), testvmcx
 ne=28, na=14

E ₀ (eV)	0°	10°	20°	30°	40°	45 ^b	50°	55°	57.5°	60 ^u	62.5°	65°
15												3.09e-1
17												3.33e-1
18												3.45e-1
20												3.60e-1
25	1.67e+0											4.22e-1
30	1.92e+0											5.05e-1
35	2.13e+0											
40	1.92e+0											
42	2.00e+0											
45	2.11e+0											
48	2.22e+0											
50	2.33e+0											
50	2.88e+0											8.00e-1
65	3.16e+0											
80	3.67e+0											1.38e+0
100	4.19e+0											1.82e+0
200	6.14e+0											3.40e+0
265	6.92e-f-0											
300	7.60e+0	7.50e+0	7.22e+0	6.81e+0	6.26e+0		5.58e4-0	5.32e+0	5.10e+0	4.89e+0	4.77e4-0	4.48e4-0
350	8.32e+0	8.20e+0	7.99e+0	7.37e4-0	6.84e+0	6.45e+0	6.15e4-0	5.75e+0	5.69e4-0	5.36e+0	5.17e4-0	5.01e+0
500	9.97e+0											6.08e4-0
1000	1.45e+1	1.39e+1	1.36e+1	1.27e+1	1.17e+1	1.14e+1	1.06e+1	1.03e+1	9.71e+0	9.60e+0	9.34e+0	8.95e+0
2000	2.07e+1	1.99e+1	1.96e4-1	1.85e+1	1.67e+1		1.53e4-1	1.41e+1	1.41e4-1	1.35e+1	1.30e+1	1.25e+1
5000	3.41e+1											2.05e-H
10000	4.99e+1											3.00e+1
20000	7.53e+1											4.58e+1
50000	1.40e+2											8.29e+1
100000	2.40e4-2											1.35e+2

E _q (eV)	70 ⁷⁵	80 ⁷⁵
300	4.09e+0	2.86e+0
350	4.62e+0	3.26e+0
1000		6.88e+0
2000	1.16e+1	9.99e+0

Mo → Mo

Mo on Mo, Maxwellian velocity distribution, sheath potential 0 kT
 z1=42, m1= 95.94, z2=42, m2= 95.94, sbe=6.89, 6.83 eV, rho = 10.20 g/cm**3
 cf=6.39, 6.78 eV, esb=6.89, 6.83 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot=1 (KrC)
 program: newtrim (Laszlo), testvmcx
 ne=12

kT(eV)	Y	Y _s	E _{sp}	# _N	R _N	R _E	R _e	range
5	4.52e-4	2.70e-4	5.96e-10	9.49e-4	9.60e-4	1.01e+1	3.11e-1	
7	1.68e-3	9.30e-4	7.78e+0	3.94e-3	3.48e-3	1.24e+1	4.75e-1	
10	5.73e-3	2.77e-3	9.69e-10	1.31e-2	1.06e-2	1.63e+1	6.82e-1	
20	3.89e-2	1.29e-2	1.33e+1	6.02e-2	3.94e-2	2.63e+1	1.26e-f-0	
50	2.01e-1	4.17e-2	2.08e-f-1	1.64e-1	8.67e-2	5.27e+1	2.57e-f-0	
100	4.90e-1	6.56e-2	2.67e+1	2.27e-1	1.04e-1	9.16e+1	4.24e+0	
200	9.48e-1	7.58e-2	3.14e+1	2.62e-1	1.11e-1	1.66e+2	6.60e+0	
500	1.87e-0	9.43e-2	5.13e-11	2.63e-1	8.87e-2	3.44e-12	1.16e+1	
1000	3.00e-0	9.74e-2	6.47e4-1	2.16e-1	8.32e-2	7.67e+2	1.55e+1	
2000	4.23e-0	1.18e-1	1.13e+2	2.29e-1	7.18e-2	1.26e+3	2.40e+1	
5000	6.15e-0	8.80e-2	1.35e+2	2.06e-1	8.81e-2	4.05e+3	3.76e+1	
10000	8.54e-0	7.72e-2	1.76e+2	1.55e-1	4.41e-2	5.54e+3	5.63e-11	

Mo on Mo, Maxwellian velocity distribution, sheath potential 3 kT
 ne= 13

kT(eV)	Y	Y _{e2}	E _{sp}	R _N	R _E	B _{fe}	range
4	5.91e-4	1.47e-4	4.96e-10	4.64e-4	1.87e-4	8.06e+0	1.11e+0
5	1.60e-3	3.75e-4	5.86e+0	1.34e-3	4.95e-4	9.27e+0	1.35e+0
7	5.67e-3	1.21e-3	7.49e+0	4.46e-3	1.49e-3	1.17e+1	1.76e-f-0
10	1.97e-2	3.50e-3	8.88e+0	1.16e-2	3.48e-3	1.50e+1	2.27e4-0
20	1.14e-1	1.37e-2	1.21e4-1	3.34e-2	7.91e-3	2.36e+1	3.61e+0
50	4.69e-1	3.17e-2	1.69e+1	5.56e-2	9.56e-3	4.30e+1	6.23e+0
100	9.48e-1	4.10e-2	2.16e-11	5.94e-2	8.20e-3	6.90e+1	9.05e4-0
200	1.57e-0	4.61e-2	2.95e+1	5.54e-2	5.29e-3	9.58e4-1	1.31e+1
500	2.60e-0	3.68e-2	3.52e4-1	4.50e-2	3.80e-3	2.11e+2	2.04e+1
1000	3.69e-0	3.63e-2	4.93e+1	4.73e-2	4.84e-3	5.13e-12	3.08e-f-1
2000	4.40e-0	3.44e-2	7.81e+1	4.29e-2	3.83e-3	8.96e+2	4.72e-H
5000	5.65e-0	2.47e-2	1.08e+2	2.26e-2	1.28e-3	1.41e+3	7.97e+1
10000	6.23e-0	1.85e-2	1.47e+2	2.33e-2	2.98e-3	6.34e+3	1.26e+2

Mo on Mo, Maxwellian velocity distribution, sheath potential 9 kT
 ne= 15

kT(eV)	Y	Y _e	E _{sp}	R _v	R _{ig}	E&	range
2.4	3.27e-4	4.18e-5	3.38e+0	9.20e-5	1.95e-5	5.59e4-0	1.57e+0
3	9.41e-4	1.16e-4	4.07e+0	3.37e-4	7.17e-5	7.03e4-0	1.87e+0
4	3.47e-3	4.12e-4	5.22e-f-0	1.43e-3	2.61e-4	8.03e+0	2.30e+0
5	8.61e-3	9.54e-4	6.10e+0	3.02e-3	5.21e-4	9.50e-10	2.68e+0
7	3.01e-2	2.86e-3	7.32e+0	7.37e-3	1.11e-3	1.16e-f-1	3.32e-10
10	8.06e-2	6.23e-3	8.51e+0	1.44e-2	1.90e-3	1.45e+1	4.13e+0
20	2.93e-1	1.52e-2	1.14e+1	2.56e-2	2.77e-3	2.38e+1	6.16e-f-0
30	5.00e-1	2.06e-2	1.36e4-1	3.19e-2	2.96e-3	3.06e4-1	7.66e-10
50	8.46e-1	2.60e-2	1.69e+1	3.50e-2	2.77e-3	4.35e-11	9.97e+0
100	1.47e-0	2.98e-2	2.23e+1	3.70e-2	2.44e-3	7.27e+1	1.43e+1
200	2.21e-0	3.00e-2	2.99e+1	3.32e-2	2.25e-3	1.49e+2	2.05e+1
500	3.28e-0	2.66e-2	4.45e+1	2.85e-2	1.72e-3	3.32e+2	3.38e-11
1000	4.11e-0	2.31e-2	6.17e-11	2.50e-2	1.49e-3	6.56e+2	5.06e+1
2000	4.80e-0	1.80e-2	8.23e+1	1.63e-2	4.95e-4	6.66e4-2	7.61e+1
5000	5.41e-0	1.37e-2	1.38e4-2	9.06e-3	8.90e-4	5.36e+3	1.48e+2

Xe → Mo

Sputtering yield of Mo (2 isotopes) by Xe

z1=54, m1=131.30, z2=42, m2= 92.00, 100.00, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kkO=kkOr=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 alpha=0.00

program: trvmc
 ne= 4, na= 1, n(m2)= 2

E ₀ (eV)	m2 = 92.00	100.00	c2(92)	c2(100)
5000	1.457e-0	1.419e-0	0.5000	0.5000
5000	1.437e-0	1.438e-0	0.4935	0.5065
10000	1.917e-0	1.871e-0	0.5000	0.5000
10000	1.894e-0	1.896e-0	0.4940	0.5060

Sputtered energy of Mo (2 isotopes) by Xe

ne= 4, na= 1, n(m2)= 2

E ₀ (eV)	m2 = 92.00	100.00	c2(92)	c2(100)
5000	9.875e-3	9.406e-3	0.5000	0.5000
5000	9.759e-3	9.563e-3	0.4935	0.5065
10000	8.936e-3	8.500e-3	0.5000	0.5000
10000	8.847e-3	8.628e-3	0.4940	0.5060

Particle reflection coefficient of Xe backscattered from Mo (2 isotopes)

z1=54, m1=131.30, z2=42, m2= 92.00, 100.00, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kkO=kkOr=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 alpha=0.00

program: trvmc
 ne= 4, na= 1

E ₀ (eV)	0°	c2(92)	c2(100)
5000	6.6469e-3	0.5000	0.5000
5000	6.5269e-3	0.4935	0.5065
10000	5.4627e-3	0.5000	0.5000
10000	5.4736e-3	0.4940	0.5060

Energy reflection coefficient of Xe backscattered from Mo (2 isotopes)

ne= 4, na= 1

E ₀ (eV)	0°	c2(92)	c2(100)
5000	1.0724e-4	0.5000	0.5000
5000	1.1108e-4	0.4935	0.5065
10000	9.6071e-5	0.5000	0.5000
10000	9.7227e-5	0.4940	0.5060

Average depth (mean range) in Å of Xe implanted in Mo (2 isotopes)

ne= 4, na= 1

E ₀ (eV)	0°	c2(92)	c2(100)
5000	3.3742e+1	0.5000	0.5000
5000	3.3737e+1	0.4935	0.5065
10000	4.8992e+1	0.5000	0.5000
10000	4.8991e+1	0.4940	0.5060

Xe → Mo

Sputtering yield of Mo (7 isotopes) by Xe

z1=54, m1=131.30, z2=42, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 m2= 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2=0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00
 program: trvmc95
 ne= 2, na= 1, n(m2) = 7

E ₀ (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
100	1.838e-3	1.120e-3	1.901e-3	1.969e-3	1.114e-3	2.777e-3	1.082e-3	1500000000
100	1.837e-3	1.118e-3	1.894e-3	1.968e-3	1.113e-3	2.781e-3	1.083e-3	400000000

Sputtered energy of Mo (7 isotopes) by Xe

ne= 2, na= 1, n(m2)= 7

E ₀ (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
100	7.508e-5	4.579e-5	7.770e-5	8.056e-5	4.556e-5	1.137e-5	4.432e-5	1500000000
100	7.511e-5	4.570e-5	7.748e-5	8.057e-5	4.562e-5	1.138e-5	4.443e-5	400000000

Particle reflection coefficient of Xe backscattered from Mo (7 isotopes)

z1=54, m1=131.30, z2=42, sbe=6.83 eV, rho=10.21 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 m2= 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2=0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha=0.00
 program: trvmc95
 ne= 2, na= 1

E ₀ (eV)	0°	nh
100	9.5655e-3	1500000000
100	9.5666e-3	400000000

Energy reflection coefficient of Xe backscattered from Mo (7 isotopes)

ne= 2, na= 1

E ₀ (eV)	0°	nh
100	1.6728e-4	1500000000
100	1.6738e-4	400000000

Average depth (mean range) in Å of Xe implanted in Mo (7 isotopes)

ne= 2, na= 1

E _q (eV)	0°	nh
100	4.8206e+0	1500000000
100	4.8206e+0	400000000

Hg → Mo

Sputtering yield of Mo by Hg

z1=80, m1=200.59, z2=42, m2= 95.94, sbe=6.83 eV, rho=10.20 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 program: IPP 9/82
 only low fluence!
 ne=12, na= 1

Ep(eV)	0°
50	3.70e-5
100	5.30e-3
200	7.52e-2
500	4.13e-1
1000	9.39e-1
2000	1.62e-0
5000	2.73e-0
10000	3.74e-0
20000	4.72e-0
50000	5.89e-0
100000	6.74e-0
200000	7.09e-0

Rn → Mo

Sputtering yield of Mo (7 isotopes) by Rn
 z1 = 86, m1 = 222.00, z2 = 42, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 m2 = 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2 = 0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha = 0.00
 program: trvmc95
 ne = 4, na = 1, n(m2) = 7

E ₀ (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
100	6.991e-4	4.259e-4	7.237e-4	7.484e-4	4.244e-4	1.057e-4	4.118e-4	150000000
100	7.002e-4	4.270e-4	7.238e-4	7.496e-4	4.242e-4	1.056e-4	4.107e-4	900000000
100	6.983e-4	4.256e-4	7.244e-4	7.509e-4	4.239e-4	1.054e-4	4.137e-4	350000000
5000	4.320e-1	2.679e-1	4.588e-1	4.795e-1	2.742e-1	6.890e-1	2.733e-1	10000000

Sputtered energy of Mo (7 isotopes) by Rn
 ne = 4, na = 1, n(m2) = 7

E ₀ (eV)	m2=91.91	93.91	94.91	95.90	96.91	97.91	99.91	nh
100	2.515e-5	1.533e-5	2.610e-5	2.698e-5	1.533e-5	3.817e-5	1.488e-5	150000000
100	2.518e-5	1.540e-5	2.608e-5	2.704e-5	1.528e-5	3.814e-5	1.483e-5	900000000
100	2.510e-5	1.529e-5	2.603e-5	2.706e-5	1.532e-5	3.802e-5	1.494e-5	350000000
5000	2.692e-3	1.662e-3	2.843e-3	2.960e-3	1.684e-3	4.231e-3	1.672e-3	10000000

Particle reflection coefficient of Rn backscattered from Mo (7 isotopes)
 z1 = 86, m1 = 222.00, z2 = 42, sbe = 6.83 eV, rho = 10.21 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 m2 = 91.91, 93.91, 94.91, 95.90, 96.91, 97.91, 99.91
 c2 = 0.1483, 0.0925, 0.1592, 0.1668, 0.0956, 0.2413, 0.0963
 alpha = 0.00
 program: trvmc95
 ne = 4, na = 1

E ₀ (eV)	0°	nh
100	2.9659e-5	150000000
100	2.9227e-5	900000000
100	2.9600e-5	350000000
5000	2.1510e-4	10000000

Energy reflection coefficient of Rn backscattered from Mo (7 isotopes)
 ne = 4, na = 1

E ₀ (eV)	0°	nh
100	2.0536e-7	150000000
100	2.0395e-7	900000000
100	2.0724e-7	350000000
5000	9.4885e-7	10000000

Average depth (mean range) in Å of Rn implanted in Mo (7 isotopes)
 ne = 4, na = 1

E ₀ (eV)	0°	nh
100	6.5227e+0	150000000
100	6.5227e+0	900000000
100	6.5225e+0	350000000
5000	3.8657e+1	10000000

He -> Pd

Sputtering yield of Pd by He

z1= 2, m1= 4.00, z2=46, m2=106.40, sbe=3.91 eV, rho=11.96 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvmcx
 ne= 3, na= 1

E _s (eV)	30°
500	1.42e-1
1000	1.81e-1
1500	2.00e-1

Sputtered energy of Pd by He

ne= 3, na= 1

E _o (eV)	30°
500	2.44e-3
1000	2.11e-3
1500	1.73e-3

Particle reflection coefficient He backscattered from Pd

z1= 2, m1= 4.00, z2=46, m2=106.40, sbe=3.91 eV, rho=11.96 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvmcx
 ne= 3, na= 1

E _o (eV)	30°
500	5.22e-1
1000	4.83e-1
1500	4.52e-1

Energy reflection coefficient He backscattered from Pd

ne= 3, na= 1

B _o (eV)	30°
500	2.99e-1
1000	2.68e-1
1500	2.46e-1

Average depth (mean range) in Å of He implanted in Pd

ne= 3, na= 1

E _q (eV)	30°
500	5.63e+1
1000	8.68e+1
1500	1.13e+2

Xe -4- Pel

Sputtering yield of Pd by Xe
 z1=54, m1 = 131.30, z2=46, m2= 106.40, sbe=3.91 eV, rho = 11.96 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program : trspvmcx
 ne= 3, na= 1

E ₀ (eV)	30°
500	1.95e-0
1000	3.24e-0
1500	4.08e-0

Sputtered energy of Pd by Xe
 ne= 3, na= 1

E ₀ (eV)	30°
500	6.04e-2
1000	6.43e-2
1500	6.22e-2

Particle reflection coefficient Xe backscattered from Pd
 z1=54, m1 = 131.30, z2=46, m2 = 106.40, sbe=3.91 eV, rho = 11.96 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program : trspvmcx
 ne= 3, na= 1

E ₀ (eV)	30°
500	7.42e-2
1000	6.84e-2
1500	5.34e-2

Energy reflection coefficient Xe backscattered from Pd
 ne= 3, na= 1

E ₀ (eV)	30°
500	5.33e-3
1000	4.32e-3
1500	3.43e-3

Average depth (mean range) in Å of Xe implanted in Pd
 ne= 3, na= 1

E ₀ (eV)	30°
500	8.74e+0
1000	1.20e+1
1500	1.48e+1

D → Ag

Sputtering yield of Ag by D

z1 = 1, m1 = 2.01, z2 = 47, m2 = 107.87, rho = 10.47 g/cm**3
 ef = 0.95 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx
 ne = 6, na = 3, n(sbe) = 5

sbe	2.66 eV	2.76 eV	2.87 eV	2.91 eV	2.95 eV	2.76 eV	2.95 eV	2.76 eV	2.87 eV	2.95 eV
E ₀ (eV)	0°	0°	0°	0°	0°	50°	50°	70°	70° ⁵	70°
50	2.51e-4	1.45e-4	1.02e-4	5.11e-5	3.81e-5					
55	6.54e-4	4.46e-4	2.99e-4	2.43e-4	2.06e-4					
60	1.25e-3	9.58e-4	6.69e-4	5.92e-4	5.24e-4	9.07e-4	4.78e-4	3.75e-4	2.59e-4	1.99e-4
70	2.91e-3	2.33e-3	1.89e-3	1.67e-3	1.54e-3					
80	4.92e-3	4.13e-3	3.45e-3	3.23e-3	2.99e-3					
100	9.39e-3	8.28e-3	7.25e-3	6.79e-3	6.59e-3					

Sputtered energy of Ag by D

ne = 6, na = 3, n(sbe) = 5

sbe	2.66 eV	2.76 eV	2.87 eV	2.91 eV	2.95 eV	2.76 eV	2.95 eV	2.76 eV	2.87 eV	2.95 eV
E ₀ (eV)	0°	0°	0°	0°	0°	50°	50°	70°	70°	70°
50	1.60e-6	7.87e-7	4.59e-7	2.10e-7	1.45e-7					
55	5.46e-6	3.35e-6	2.02e-6	1.59e-6	1.25e-6					
60	1.26e-5	8.69e-6	5.66e-6	4.87e-6	4.20e-6	8.73e-6	4.04e-6	3.54e-6	2.24e-6	1.57e-6
70	3.42e-5	2.66e-5	2.07e-5	1.80e-5	1.72e-5					
80	6.47e-5	5.29e-5	4.26e-5	3.95e-5	3.67e-5					
100	1.35e-4	1.17e-4	1.03e-4	9.44e-5	9.09e-5					

Particle reflection coefficient of D backscattered from Ag

z1 = 1, m1 = 2.01, z2 = 47, m2 = 107.87, rho = 10.47 g/cm**3
 ef = 0.95 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx
 ne = 6, na = 3, n(sbe) = 5

sbe	2.66 eV	2.76 eV	2.87 eV	2.91 eV	2.95 eV	2.76 eV	2.95 eV	2.76 eV	2.87 eV	2.95 eV
E ₀ (eV)	0°	0°	0°	0°	0°	50°	50°	70°	70° ⁵	70°
50	6.26e-1	6.26e-1	6.37e-1	6.26e-1	6.26e-1					
55	6.22e-1	6.21e-1	6.21e-1	6.21e-1	6.21e-1					
60	6.17e-1	6.17e-1	6.17e-1	6.17e-1	6.17e-1	7.29e-1	7.29e-1	8.68e-1	8.68e-1	8.68e-1
70	6.09e-1	6.09e-1	6.10e-1	6.09e-1	6.09e-1					
80	6.02e-1	6.02e-1	6.02e-1	6.03e-1	6.02e-1					
100	5.91e-1	5.91e-1	5.91e-1	5.90e-1	5.91e-1					

Energy reflection coefficient of D backscattered from Ag

ne = 6, na = 3, n(sbe) = 5

sbe	2.66 eV	2.76 eV	2.87 eV	2.91 eV	2.95 eV	2.76 eV	2.95 eV	2.76 eV	2.87 eV	2.95 eV
E ₀ (eV)	0°	0°	0°	0°	0°	50°	50°	70°	70°	70°
50	4.08e-1	4.08e-1	4.14e-1	4.08e-1	4.08e-1					
55	4.03e-1	4.03e-1	4.03e-1	4.03e-1	4.03e-1					
60	3.99e-1	3.98e-1	3.99e-1	3.99e-1	3.99e-1	5.35e-1	5.35e-1	7.41e-1	7.41e-1	7.41e-1
70	3.90e-1	3.90e-1	3.91e-1	3.90e-1	3.90e-1					
80	3.83e-1	3.83e-1	3.83e-1	3.84e-1	3.83e-1					
100	3.72e-1	3.72e-1	3.72e-1	3.71e-1	3.72e-1					

Average depth (mean range) in Å of D implanted in Ag

ne = 6, na = 3, n(sbe) = 5

sbe	2.66 eV	2.76 eV	2.87 eV	2.91 eV	2.95 eV	2.76 eV	2.95 eV	2.76 eV	2.87 eV	2.95 eV
E ₀ (eV)	0°	0°	0°	0°	0°	50°	50°	70°	70°	70°
50	3.00e+1	3.00e+1	2.23e+1	3.00e+1	3.00e+1					
55	3.16e+1	3.16e+1	3.16e+1	3.16e+1	3.16e+1					
60	3.32e+1	3.31e+1	3.31e+1	3.31e+1	3.31e+1	3.23e+1	3.23e+1	3.18e+1	3.17e+1	3.17e+1
70	3.62e+1	3.61e+1	3.61e+1	3.61e+1	3.61e+1					
80	3.89e+1	3.89e+1	3.89e+1	3.89e+1	3.89e+1					
100	4.41e+1	4.41e+1	4.41e+1	4.41e+1	4.41e+1					

He → Ag

Sputtering yield of Ag by He

z1 = 2, m1 = 4.00, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kkOr = 1, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program:
 ne = 8, na = 2

E ₀ (eV)	0°	75°
50	8.62e-3	
100	4.43e-2	
300	1.20e-1	
500	1.51e-1	
1000	1.82e-1	
2000	1.70e-1	4.64e-1
4000	2.00e-1	
10000	1.52e-1	

Sputtered energy of Ag by He
 ne = 6, na = 1

Bo (eV)	0°
50	2.05e-4
100	1.17e-3
300	2.27e-3
500	2.21e-3
1000	1.71e-3
4000	7.58e-4

Particle reflection coefficient of He backscattered from Ag

z1 = 2, m1 = 4.00, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kkO = kkOr = 1, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program:
 ne = 6, na = 1

Ep (eV)	0°
50	6.10e-1
100	5.68e-1
300	5.07e-1
500	4.79e-1
1000	4.33e-1
4000	3.32e-1

Energy reflection coefficient of He backscattered from Ag
 ne = 6, na = 1

E ₀ (eV)	0°
50	3.75e-1
100	3.36e-1
300	2.82e-1
500	2.62e-1
1000	2.28e-1
4000	1.57e-1

Average depth (mean range) in Å of He implanted in Ag
 ne = 6, na = 1

Bo (eV)	0°
50	1.80e+1
100	2.61e+1
300	4.88e+1
500	6.58e+1
1000	1.03e+2
4000	2.72e+2

Na → Ag

Sputtering yield of Ag by Na

z1 = 11, m1 = 22.99, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = eV, esb = eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: TPP 9/82
 only low fluence!
 ne = 1, na = 7

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°
30000	2.34e-0	2.74e-0	3.33e-0	4.11e-0	5.22e-0	7.08e-0	9.42e-0

Sputtered energy of Ag by Na

program:
 only low fluence!
 ne = 1, na = 7

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°
30000	4.15e-3	4.92e-3	6.85e-3	9.60e-3	1.41e-2	2.14e-2	3.24e-2

Particle reflection coefficient of Na backscattered from Ag

z1 = 11, m1 = 22.99, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = eV, esb = eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program:
 only low fluence!
 ne = 1, na = 7

B ₀ (eV)	0°	15°	30°	40°	50°	60°	70°
30000	1.21e-1	1.35e-1	1.64e-1	2.05e-1	2.57e-1	3.40e-1	4.41e-1

Energy reflection coefficient of Na backscattered from Ag

ne = 1, na = 7

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°
30000	3.25e-2	3.69e-2	4.91e-2	6.97e-2	9.70e-2	1.49e-1	2.26e-1

Average depth (mean range) in Å of Na implanted in Ag

ne = 1, na = 7

B ₀ (eV)	0°	15°	30°	40°	50°	60°	70°
30000	2.80e+2	2.72e+2	2.56e+2	2.40e+2	2.28e+2	2.10e+2	1.93e+2

Ar → Ag

Sputtering yield of Ag by Ar

z1 = 18, m1 = 39.95, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kkO = kkOr = 1, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trspvmcx, trspvlcs
 ne = 7, na = 1

E ₀ (eV)	0°
50	1.27e-1
100	4.37e-1
300	1.28e-0
500	1.83e-0
1000	2.64e-0
2500	4.03e-0
4000	4.22e-0

Sputtered energy of Ag by Ar

ne = 7, na = 1

E ₀ (eV)	0°
50	9.64e-3
100	2.39e-2
300	3.68e-2
500	3.82e-2
1000	3.49e-2
2500	3.19e-2
4000	2.38e-2

Particle reflection coefficient of Ar backscattered from Ag

z1 = 18, m1 = 39.95, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kkO = kkOr = 1, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trspvmcx, trspvlcs
 ne = 7, na = 1

Bo (eV)	0°
50	4.19e-1
100	3.48e-1
300	2.61e-1
500	2.35e-1
1000	2.00e-1
2500	1.83e-1
4000	1.44e-1

Energy reflection coefficient of Ar backscattered from Ag

ne = 7, na = 1

E ₀ (eV)	0°
50	8.62e-2
100	7.08e-2
300	5.07e-2
500	4.41e-2
1000	3.68e-2
2500	3.53e-2
4000	2.48e-2

Average depth (mean range) in Å of Ar implanted in Ag

ne = 7, na = 1

Bo (eV)	0°
50	4.46e+0
100	6.23e+0
300	1.07e+1
500	1.38e+1
1000	2.00e+1
2500	3.42e+1
4000	4.41e+1

K → Ag

Sputtering yield of Ag by K

z1 = 19, m1 = 39.10, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = eV, esb = eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: TPP 9/82
 only low fluence!
 ne = 1, na = 8

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	4.76e-0	4.99e-0	6.52e-0	8.05e-0	1.03e+1	1.34e+1	1.68e+1	1.79e+1

Sputtered energy of Ag by K

program:
 only low fluence!
 ne = 1, na = 8

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	8.42e-3	9.33e-3	1.55e-2	2.27e-2	3.44e-2	5.00e-2	7.27e-2	9.49e-2

Particle reflection coefficient of K backscattered from Ag

z1 = 19, m1 = 39.10, z2 = 47, m2 = 107.87, sbe = 2.97 eV, rho = 10.47 g/cm**3
 ef = eV, esb = eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program:
 only low fluence!
 ne = 1, na = 8

Ro (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	8.21e-2	8.83e-2	1.20e-1	1.52e-1	2.12e-1	2.90e-1	3.95e-1	5.66e-1

Energy reflection coefficient of K backscattered from Ag

ne = 1, na = 7

B ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	1.43e-2	1.63e-2	2.74e-2	3.83e-2	6.59e-2	1.06e-1	1.80e-1	3.41e-1

Average depth (mean range) in Å of K implanted in Ag

ne = 1, na = 8

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	1.72e+2	1.69e+2	1.58e+2	1.49e+2	1.35e+2	1.25e+2	1.13e+2	1.05e+2

Xe → Ag

Sputtering yield of Ag by Xe

z1=54, l1l1=131.30, z2=47, m2=107.87, sbe=2.97 eV, rho=10.47 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=1, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: trspvmcx, trspvlcs
 ne= 6, na= 1

Eq(eV)	0°
50	2.75e-2
100	2.06e-1
300	1.05e-0
500	1.71e-0
1000	2.85e-0
4000	5.79e-0

Sputtered energy of Ag by Xe

ne= 6, na= 1

Bo(eV)	0°
50	1.15e-3
100	6.95e-3
300	2.11e-2
500	2.63e-2
1000	2.91e-2
4000	2.59e-2

Particle reflection coefficient of Xe backscattered from Ag

z1=54, m1 = 131.30, z2=47, m2=107.87, sbe=2.97 eV, rho=10.47 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kkO=kkOr=1, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: trspvmcx, trspvlcs
 ne= 6, na= 1

E ₀ (eV)	0°
50	4.29e-2
100	2.83e-2
300	1.97e-2
500	1.95e-2
1000	1.60e-2
4000	1.30e-2

Energy reflection coefficient of Xe backscattered from Ag

ne= 6, na= 1

E ₀ (eV)	0°
50	5.51e-4
100	5.07e-4
300	3.45e-4
500	3.88e-4
1000	2.89e-4
4000	2.37e-4

Average depth (mean range) in Å of Xe implanted in Ag

ne= 6, na= 1

E ₀ (eV)	0°
50	3.63e+0
100	5.26e+0
300	8.99e+0
500	1.14e+1
1000	1.57e+1
4000	3.08e+1

H -> In

Sputtering yield of Tn by TT

z1= 1, m1 = 1.01, z2=49, m2 = 114.82, sbe=2.49 eV, rho=7.31 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program: TESTVMCX, TPP 9/82 '
 ne= 1, na=10

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°
2000	1.65e-2	1.79e-2	2.24e-2	2.94e-2	5.41e-2	7.68e-2	1.04e-1	1.33e-1	1.42e-1	9.06e-2

Sputtered energy of Tn by H

program: testvmcx
 ne= 1, na=10

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°
2000	5.16e-5	5.90e-5	6.64e-5	9.36e-5	1.82e-4	2.67e-4	3.59e-4	5.18e-4	6.52e-4	4.71e-4

Particle reflection coefficient of H backscattered from Tn

z1= 1, m1= 1.01, z2=49, m2 = 114.82, sbe=2.49 eV, rho=7.31 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program: testvmcx
 ne= 1, na=10

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°
2000	3.60e-1	3.71e-1	4.07e-1	4.69e-1	5.55e-1	6.28e-1	6.74e-1	7.35e-1	8.28e-1	9.16e-1

Energy reflection coefficient of H backscattered from Tn

ne= 1, na=10

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°
2000	1.74e-1	1.83e-1	2.08e-1	2.56e-1	3.33e-1	4.15e-1	4.74e-1	5.58e-1	6.99e-1	8.42e-1

Average depth (mean range) in Å of H implanted in In

ne= 1, na=10

E ₀ (eV)	0°	15°	30°	45°	60°	70°	75°	80°	85°	87°
2000	4.02e+2	3.97e+2	3.89e+2	3.75e+2	3.67e+2	3.56e+2	3.47e+2	3.49e+2	3.47e+2	3.49e+2

D → In

Sputtering yield of Tn by D

z1= 1, m1= 2.01, z2=49, m2 = 114.82, sbe=2.52 eV, rho=7.31 g/cm**3
 ef=0.90 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: newtrim (Laszlo), TPP 9/82
 ne= 7, na= 2

E ₀ (eV)	0°	65°
100	6.98e-3	7.79e-3
200	2.10e-2	3.60e-2
500	3.71e-2	9.42e-2
1000	4.29e-2	1.27e-1
2000	4.20e-2	1.38e-1
5000	3.67e-2	1.36e-1
10000	2.81e-2	1.10e-1

Sputtered energy of Tn by D

program: newtrim (Laszlo)
 ne= 7, na= 2

E ₀ (eV)	0°	65°
100	9.77e-5	1.17e-4
200	2.89e-4	5.01e-4
500	3.89e-4	9.72e-4
1000	2.93e-4	9.44e-4
2000	1.93e-4	7.11e-4
5000	8.29e-5	3.64e-4
10000	3.45e-5	1.92e-4

Particle reflection coefficient of D backscattered from Tn

z1= 1, m1= 2.01, z2=49, m2 = 114.82, sbe=2.52 eV, rho=7.31 g/cm**3
 ef=0.90 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 program: newtrim (Laszlo)
 ne= 7, na= 2

E ₀ (eV)	0°	65°
100	5.90e-1	7.68e-1
200	5.57e-1	7.40e-1
500	5.01e-1	6.96e-1
1000	4.53e-1	6.55e-1
2000	3.89e-1	6.09e-1
5000	2.89e-1	5.31e-1
10000	2.05e-1	4.67e-1

Energy reflection coefficient of D backscattered from Tn

ne= 7, na= 2

E ₀ (eV)	0°	65°
100	3.69e-1	5.91e-1
200	3.38e-1	5.52e-1
500	2.89e-1	4.98e-1
1000	2.49e-1	4.53e-1
2000	2.01e-1	4.04e-1
5000	1.33e-1	3.24e-1
10000	8.25e-2	2.61e-1

Average depth (mean range) in Å of D implanted in Tn

ne= 7, na= 2

E ₀ (eV)	0°	65°
100	6.90e+1	6.56e+1
200	1.02e+2	9.65e+1
500	1.76e+2	1.65e+2
1000	2.78e+2	2.57e+2
2000	4.51e+2	4.06e+2
5000	8.92e+2	7.64e+2
10000	1.55e+3	1.27e+3

D → In

D on Tn, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1, m1 = 2.01, z2 = 49, m2 = 114.82, she = 2.52 eV, rho = 7.31 g/cm**3
 ef = 0.90 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx, newtrim (Laszlo)
 ne = 8

kT(eV)	Y	Y ₂₁	E _{sp}	R _{AΓ}	R ₂₁	E _s	range
20	9.93e-4	3.60e-5	1.45e-f-0	7.41e-1	5.34e-1	2.88e+1	4.05e+1
50	9.15e-3	2.37e-4	2.59e+0	7.04e-1	4.85e-1	6.90e+1	6.68e+1
100	2.44e-2	4.52e-4	3.70e+0	6.77e-1	4.48e-1	1.32e+2	1.00e+2
200	4.62e-2	6.19e-4	5.37e+0	6.37e-1	4.04e-1	2.55e+2	1.51e+2
500	7.50e-2	5.35e-4	7.11e-f-0	5.82e-1	3.48e-1	5.96e+2	2.69e+2
1000	8.71e-2	4.04e-4	9.21e+0	5.31e-1	3.00e-1	1.12e+3	4.34e+2
2000	9.03e-2	2.69e-4	1.19e+1	4.74e-1	2.44e-1	2.06e+3	7.22e+2
5000	8.23e-2	1.25e-4	1.52e+1	3.83e-1	1.70e-1	4.45e+3	1.43e+3

D on In, Maxwellian velocity distribution, sheath potential 3 kT
 ne = 9

kT(eV)	Y	Y _e	E _{sp}	B _{iv}	R _e	E _b	range
10	6.86e-4	1.25e-5	9.14e-1	6.48e-1	4.32e-1	3.34e+1	4.65e+1
20	7.38e-3	1.25e-4	1.70e+0	6.18e-1	4.00e-1	6.46e+1	6.78e+1
50	2.63e-2	3.59e-4	3.42e-f-0	5.76e-1	3.57e-1	1.55e+2	1.14e-t-2
100	3.91e-2	4.02e-4	5.15e-j-0	5.35e-1	3.20e-1	2.99e+2	1.75e+2
200	5.15e-2	3.65e-4	7.06e-j-0	4.88e-1	2.79e-1	5.69e+2	2.75e+2
500	5.31e-2	2.01e-4	9.44e-l-0	4.04e-1	2.11e-1	1.31e+3	5.17e+2
1000	4.91e-2	1.13e-4	1.15e+1	3.28e-1	1.55e-1	2.36e+3	8.63e+2
2000	3.48e-2	5.12e-5	1.48e+1	2.45e-1	1.03e-1	4.20e+3	1.47e+3
5000	2.40e-2	1.44e-5	1.50e-f-1	1.33e-1	4.39e-2	8.24e+3	3.09e+3

T -> In

Sputtering yield of In by T

z1= 1, m1= 3.01, z2=49, m2= 114.82, sbe=2.52 eV, rho=7.31 g/cm**3
 ef=0.90 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2= 3, ipot=ipotr=1 (KrC)
 program: newtrim (Laszlo), TPP 9/82
 ne= 8, na= 2

E ₀ (eV)	0°	65°
50	3.48e-3	
100	1.74e-2	2.38e-2
200	3.91e-2	7.84e-2
500	6.03e-2	1.63e-1
1000	6.99e-2	2.06e-1
2000	7.12e-2	2.27e-1
5000	6.33e-2	2.12e-1
10000	4.95e-2	

Sputtered energy of In by T

program: newtrim (Laszlo)
 ne= 8, na= 2

Eq(eV)	0°	65°
50	6.17e-5	
100	3.70e-4	5.30e-4
200	7.14e-4	1.51e-3
500	7.48e-4	2.05e-3
1000	5.94e-4	1.83e-3
2000	3.80e-4	1.33e-3
5000	1.76e-4	6.87e-4
10000	7.57e-5	

Particle reflection coefficient of T backscattered from In

z1= 1, m1= 3.01, z2=49, m2= 114.82, sbe=2.52 eV, rho=7.31 g/cm**3
 ef=0.90 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: newtrim (Laszlo)
 ne= 8, na= 2

Eq(eV)	0°	65°
50	6.02e-1	
100	5.72e-1	7.61e-1
200	5.45e-1	7.29e-1
500	4.97e-1	6.88e-1
1000	4.49e-1	6.52e-1
2000	3.92e-1	6.08e-1
5000	2.99e-1	5.39e-1
10000	2.18e-1	

Energy reflection coefficient of T backscattered from In

ne= 8, na= 2

E ₀ (eV)	0°	65°
50	3.80e-1	
100	3.52e-1	5.80e-1
200	3.26e-1	5.40e-1
500	2.86e-1	4.94e-1
1000	2.49e-1	4.55e-1
2000	2.06e-1	4.09e-1
5000	1.41e-1	3.40e-1
10000	9.21e-2	

Average depth (mean range) in Å of T implanted in In

ne= 8, na= 2

E ₀ (eV)	0°	65°
50	4.51e4-1	
100	6.62e+1	6.30e4-1
200	9.93e+1	9.39e+1
500	1.76e4-2	1.64e+2
1000	2.81e+2	2.59e+2
2000	4.60e+2	4.23e+2
5000	9.38e+2	8.18e+2
10000	1.67e+3	

T -> In

T on In, Maxwellian velocity distribution, sheath potential 0 kT
 z1 = 1, m1 = 3.01, z2 = 49, m2 = 114.82, sbe = 2.52 eV, rho = 7.31 g/cm**3
 ef = 0.90 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: newtrim (Laszlo)
 ne = 8

kT(eV)	Y	γ_E	Esp	R_{Ar}	R_b	Eb	range
20	3.70e-3	1.73e-4	1.87e+0	7.27e-1	5.18e-1	2.85e+1	3.84e+1
50	2.18e-2	7.17e-4	3.30e+0	6.92e-1	4.73e-1	6.85e+1	6.42e+1
100	4.98e-2	1.09e-3	4.39e+0	6.65e-1	4.38e-1	1.32e+2	9.73e+1
200	8.17e-2	1.26e-3	6.19e+0	6.32e-1	4.04e-1	2.57e+2	1.48e+2
500	1.24e-1	1.05e-3	8.49e+0	5.81e-1	3.56e-1	6.13e+2	2.71e+2
1000	1.42e-1	7.89e-4	1.11e+1	5.33e-1	3.05e-1	1.14e+3	4.52e+2
2000	1.48e-1	5.22e-4	1.40e+1	4.78e-1	2.59e-1	2.14e+3	7.55e+2
5000	1.21e-1	2.20e-4	1.81e+1	3.95e-1	1.79e-1	4.53e+3	1.57e+3

T on In, Maxwellian velocity distribution, sheath potential 3 kT
 ne = 8

kT(eV)	Y	γ_E	Esp	R_{Ar}	R_b	Eb	range
20	1.97e-2	4.62e-4	2.35e+0	6.03e-1	3.86e-1	6.40e+1	6.52e+1
50	5.10e-2	8.68e-4	4.26e+0	5.67e-1	3.49e-1	1.54e+2	1.11e+2
100	7.03e-2	8.96e-4	6.37e+0	5.30e-1	3.16e-1	2.98e+2	1.73e+2
200	8.40e-2	6.75e-4	8.04e+0	4.84e-1	2.81e-1	5.81e+2	2.74e+2
500	8.35e-2	3.70e-4	1.11e+1	4.10e-1	2.19e-1	1.33e+3	5.33e+2
1000	7.61e-2	2.06e-4	1.35e+1	3.42e-1	1.68e-1	2.15e+3	9.13e+2
2000	5.98e-2	1.07e-4	1.78e+1	2.58e-1	1.14e-1	4.40e+3	1.59e+3
5000	3.51e-2	3.09e-5	2.20e+1	1.46e-1	5.13e-2	8.79e+3	3.41e+3

T on In, Maxwellian velocity distribution, sheath potential 9 kT
 ne = 6

kT(eV)	Y	γ_E	Esp	R_{Ar}	R_b	Eb	range
10	2.13e-2	4.69e-4	2.42e+0	5.84e-1	3.64e-1	6.84e+1	6.93e+1
20	4.30e-2	7.90e-4	4.04e+0	5.50e-1	3.34e-1	1.33e+2	1.04e+2
50	6.74e-2	7.99e-4	6.51e+0	5.05e-1	2.93e-1	3.19e+2	1.85e+2
100	7.55e-2	5.85e-4	8.51e+0	4.55e-1	2.59e-1	6.26e+2	2.97e+2
200	7.60e-2	3.75e-4	1.09e+1	3.95e-1	2.10e-1	1.17e+3	4.89e+2
500	7.10e-2	1.92e-4	1.48e+1	3.19e-1	1.53e-1	2.63e+3	9.99e+2

In → In

Sputtering yield of Tn by Tn

zl=49, ml = 114.82, z2=49, m2 = 114.82, sbe=2.52 eV, rho=7.31 g/cm**3
 ef=2.02 eV, esb=2.52 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: newtrim (Laszlo), TPP 9/82
 ne= 9, na= 8

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	1.31e-3				7.76e-2			
50	6.65e-2				4.49e-1			
100	2.97e-1	6.00e-1	8.66e-1	9.76e-1	9.64e-1		7.96e-1	4.29e-1
200	7.49e-1	1.22e-0	1.63e-0	1.79e-0	1.79e-0	1.70e-0	1.50e-0	7.54e-1
500	1.76e-0				3.57e-0			
1000	2.76e-0	3.78e-0	4.85e-0	5.48e-0	5.63e-0	5.61e-0	5.29e-0	3.04e-0
2000	4.00e-0				8.44e-0			
5000	5.89e-0				1.34e+1			
10000	7.18e-0				1.78e+1			

Sputtering yield of Tn by Tn

program: newtrim (Laszlo)
 ne= 9, na= 8

B ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	7.21e-5				1.55e-2			
50	2.87e-3				7.44e-2			
100	9.76e-3	3.68e-2	7.77e-2	1.09e-1	1.20e-1		1.19e-1	6.89e-2
200	1.79e-2	5.07e-2	9.82e-2	1.36e-1	1.52e-1	1.61e-1	1.57e-1	8.70e-2
500	2.58e-2				1.73e-1			
1000	2.76e-2	5.99e-2	1.07e-1	1.51e-1	1.75e-1	1.96e-1	2.08e-1	1.49e-1
2000	2.75e-2				1.69e-1			
5000	2.43e-2				1.57e-1			
10000	2.06e-2				1.41e-1			

Particle reflection coefficient of Tn backscattered from In

zl=49, ml = 114.82, z2=49, m2 = 114.82, sbe = 2.52 eV, rho=7.31 g/cm**3
 ef=2.02 eV, esb=2.52 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr= 1 (KrC)
 program: newtrim (Laszlo)
 ne= 9, na= 8

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	5.76e-5				1.24e-1			
50	3.90e-3				3.69e-1			
100	1.32e-2	7.25e-2	1.86e-1	3.25e-1	4.21e-1		6.47e-1	8.79e-1
200	2.11e-2	8.03e-2	1.86e-1	3.09e-1	3.94e-1	4.96e-1	6.18e-1	8.88e-1
500	3.02e-2				3.39e-1			
1000	2.98e-2	7.39e-2	1.43e-1	2.39e-1	2.92e-1	3.83e-1	4.84e-1	7.99e-1
2000	2.75e-2				2.65e-1			
5000	2.57e-2				2.31e-1			
10000	1.87e-2				2.01e-1			

Energy reflection coefficient of In backscattered from In

ne= 9, na= 8

E ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	4.85e-6				3.55e-2			
50	2.12e-4				1.22e-1			
100	6.56e-4	8.85e-3	3.81e-2	9.35e-2	1.43e-1		3.02e-1	5.48e-1
200	9.20e-4	8.54e-3	3.53e-2	8.40e-2	1.28e-1	1.96e-1	2.91e-1	5.92e-1
500	1.11e-3				9.98e-2			
1000	1.13e-3	6.08e-3	2.05e-2	5.26e-2	8.01e-2	1.27e-1	1.99e-1	5.23e-1
2000	9.73e-4				6.74e-2			
5000	6.69e-4				5.16e-2			
10000	5.60e-4				4.94e-2			

Average depth (mean range) in Å of Tn implanted in In

ne= 9, na= 8

B ₀ (eV)	0°	30°	45°	55°	60°	65°	70°	80°
20	3.58e+0				1.44e- 0			
50	5.83e+0				3.27e- 0			
100	8.19e- 0	7.28e+0	6.37e+0	5.69e+0	5.31e+0		4.46e+0	3.24e+0
200	1.14e4-1	1.02e+1	9.04e+0	8.22e+0	7.72e4-0	7.22e+0	6.68e- 0	5.21e- 0
500	1.73e+1				1.19e+1			
1000	2.39e-f-1	2.16e+1	1.89e-H	1.70e+1	1.63e+1	1.51e+1	1.45e+1	1.24e+1
2000	3.29e+1				2.27e+1			
5000	5.19e+1				3.51e+1			
10000	7.67e+1				5.11e+1			

In -> In

In on In, Maxwellian velocity distribution, sheath potential 0 kT
 z1=49, m1 = 114.82, z2=49, m2= 114.82, sbe=2.52 eV, rho= 7.31 g/cm**3
 ef=2.02 eV, esb=2.52 eV, ca=1.00, kk0=kk0r=2. kdee1 = kdee2 = 3, ipot=ipot=1 (KrC)
 program: testvmcx, newtrim (Laszlo)
 ne= 12

kT(eV)	Y	Ye	Esp	H _N	Re	E _b	range
2	5.91e-4	3.45e-4	2.34e+0	9.82e-4	9.47e-4	3.86e+0	5.14e-1
3	2.68e-3	1.38e-3	3.08e+0	5.09e-3	4.26e-3	5.01e+0	7.73e-1
5	1.34e-2	5.75e-3	4.28e+0	2.13e-2	1.56e-2	7.30e+0	1.28e+0
10	6.98e-2	2.05e-2	5.87e+0	7.75e-2	4.67e-2	1.21e+1	2.06e-f-0
20	2.26e-1	4.44e-2	7.87e+0	1.58e-1	8.11e-2	2.05e+1	3.31e+0
50	6.75e-1	7.61e-2	1.13e+1	2.35e-1	1.02e-1	4.35e+1	5.87e-)-0
100	1.28e-0	9.52e-2	1.49e+1	2.52e-1	1.01e-1	7.98e+1	8.59e+0
200	2.22e-0	1.04e-1	1.89e+1	2.52e-1	9.11e-2	1.45e+2	1.22e+1
500	4.04e-0	1.10e-1	2.75e+1	2.29e-1	8.04e-2	3.55e-)-2	1.86e-f-1
1000	6.07e-0	1.06e-1	3.50e+1	2.19e-1	6.88e-2	6.35e+2	2.59e+1
2000	8.48e-0	1.02e-1	4.68e+1	1.89e-1	5.89e-2	1.21e+3	3.44e+1
5000	1.25e+1	9.19e-2	7.39e-J-1	1.59e-1	4.31e-2	2.73e+3	5.86e+1

In on In, Maxwellian velocity distribution, sheath potential 3 kT
 ne=12

kT(eV)	Y	Ye	Esp	R:v	Re	E _b	range
1.4	4.41e-4	1.02e-4	1.62e-)-0	2.15e-4	8.75e-5	2.85e-)-0	1.39e+0
2	2.02e-3	4.47e-4	2.21e+0	1.16e-3	4.23e-4	3.64e+0	1.84e+0
3	9.22e-3	1.85e-3	3.01e+0	5.11e-3	1.58e-3	4.64e+0	2.45e-)-0
5	4.25e-2	6.48e-3	3.81e+0	1.64e-2	4.27e-3	6.50e+0	3.48e+0
10	1.91e-1	1.93e-2	5.05e+0	3.96e-2	8.25e-3	1.04e+1	5.19e+0
20	5.23e-1	3.43e-2	6.56e+0	5.71e-2	9.38e-3	1.64e+1	7.44e+0
50	1.33e-0	4.87e-2	9.20e-)-0	6.66e-2	8.18e-3	3.08e+1	1.15e+1
100	2.24e-0	5.37e-2	1.19e+1	6.63e-2	7.16e-3	5.39e-)-1	1.58e+1
200	3.42e-0	5.32e-2	1.55e+1	6.41e-2	5.97e-3	9.30e+1	2.18e+1
500	5.58e-0	5.04e-2	2.26e+1	5.12e-2	4.54e-3	2.22e+2	3.41e+1
1000	7.62e-0	4.55e-2	3.02e+1	4.89e-2	4.96e-3	5.14e-)-2	4.80e+1
2000	9.22e-0	3.76e-2	4.05e+1	4.07e-2	3.23e-3	7.88e+2	6.81e-)-1

In on In, Maxwellian velocity distribution, sheath potential 9 kT
 ne= 12

kT(eV)	Y	YE	Esp	Rtv	Re	E _b	range
1.1	8.29e-4	9.79e-5	1.43e+0	2.01e-4	4.00e-5	2.41e+0-0	2.34e+0
1.4	2.44e-3	2.94e-4	1.85e+0	7.26e-4	1.39e-4	2.94e+0	2.75e+0
2	1.12e-2	1.20e-3	2.36e-)-0	2.63e-3	4.15e-4	3.48e+0	3.53e+0
5	1.49e-1	9.77e-3	3.61e+0	1.77e-2	2.06e-3	6.40e+0	5.82e-)-0
10	4.60e-1	2.07e-2	4.94e+0	3.21e-2	2.90e-3	9.96e+0	8.24e+0
20	9.99e-1	3.00e-2	6.59e-)-0	4.05e-2	3.13e-3	1.70e-)-1	1.13e-)-1
50	2.11e-0	3.64e-2	9.48e+0	4.53e-2	2.88e-3	3.49e-f-1	1.74e+1
100	3.28e-0	3.88e-2	1.30e+1	4.09e-2	2.32e-3	6.25e+1	2.39e+1
200	4.73e-0	3.73e-2	1.74e+1	4.09e-2	2.44e-3	1.32e+2	3.32e+1
500	6.92e-0	3.28e-2	2.60e+1	3.69e-2	1.55e-3	2.31e+2	5.20e-)-1
1000	8.48e-0	2.50e-2	3.23e+1	2.39e-2	1.54e-3	7.08e+2	7.80e+1
2000	1.01e+1	2.07e-2	4.47e+1	4.38e-2	2.24e-3	1.12e-J-3	1.17e+2

Cs -4 Cs

Sputtering yield of Cs by Cs

z1=55, m1 = 132.91, z2=55, m2=132.91, sbe = 0.82 eV, rho = 1.899 g/cm**3
 ef=0.77 eV, esb=0.82 eV, iwc=2, inel=3, ipot=1 (KrC)
 program: tridyn (idrel=1)
 ne = 9, na= 6

E ₀ (eV)	0°	10°	20°	30°	40°	50°
100	7.68e-1					
500	3.05e-0					
1000	4.74e-0					
2000	6.94e-0					
4000	2.14e+1	2.19e+1	2.30e+1	2.48e+1	2.67e+1	2.81e+1
8000	2.82e+1					
20000	1.62e+1					
40000	1.91e+1					
80000	1.99e+1					

Sputtered energy of Cs by Cs

ne = 9, na= 6

B ₀ (eV)	0°	10°	20°	30°	40°	50°
100	1.69e-2					
500	2.93e-2					
1000	3.10e-2					
2000	3.07e-2					
4000	4.69e-2	5.00e-2	6.13e-2	8.21e-2	1.14e-1	1.56e-1
8000	3.70e-2					
20000	1.88e-2					
40000	1.68e-2					
80000	1.13e-2					

Particle reflection coefficient of Cs backscattered from Cs

z1=55, m1 = 132.91, z2=55, m2 = 132.91, sbe=0.82 eV, rho = 1.899 g/cm**3
 ef=0.77 eV, esb=0.82 eV, iwc=2, inel=3, ipot=1 (KrC)
 program: tridyn (idrel=1)
 ne = 9, na= 6

B ₀ (eV)	0°	10°	20°	30°	40°	50°
100	2.17e-2					
500	3.24e-2					
1000	3.25e-2					
2000	3.10e-2					
4000	2.99e-2	3.39e-2	4.52e-2	7.21e-2	1.14e-1	1.85e-1
8000	2.56e-2					
20000	1.83e-2					
40000	1.60e-2					
80000	1.40e-2					

Energy reflection coefficient of Cs backscattered from Cs

ne = 9, na= 6

B ₀ (eV)	0°	10°	20°	30°	40°	50°
100	9.25e-4					
500	1.15e-3					
1000	1.13e-3					
2000	1.05e-3					
4000	9.28e-4	1.18e-3	2.44e-3	5.58e-3	1.36e-2	3.25e-2
8000	7.95e-4					
20000	6.67e-4					
40000	6.06e-4					
80000	4.60e-4					

Average depth (mean range) in Å of Cs implanted in Cs

ne = 9, na= 6

B ₀ (eV)	0°	10°	20°	30°	40°	50°
100	4.51e+1					
500	8.30e+1					
1000	1.10e+2					
2000	1.47e+2					
4000	1.88e+2	1.86e+2	1.79e+2	1.69e+2	1.56e+2	1.42e+2
8000	2.72e+2					
20000	4.83e+2					
40000	7.15e+2					
80000	1.13e+3					

Cs -> Cs

Sputtering yield of Cs by Cs
z1=55, m1 = 132.91, z2=55, m2=132.91, sbe = 0.82 eV, rho = 1.899 g/cm**3
ef=0.77 eV, esb=0.82 eV, iwc=2, inel=3, ipot = 3 (ZBL)
program: tridyn (idrel=1)
ne= 5, na= 1

E ₀ (eV)	0°
4000	8.25e+0
5000	8.76e+0
20000	1.37e+1
40000	1.52e+1
80000	1.61e+1

Sputtered energy of Cs by Cs
ne= 5, na= 1

E ₀ (eV)	0°
4000	2.46e-2
5000	2.30e-2
20000	1.79e-2
40000	1.37e-2
80000	1.00e-3

Kr → Sm

Sputtering yield of Sm by Kr

z1 = 36, m1 = 83.80, z2 = 62, m2 = 150.35, sbe=2.16 eV, rho = 7.54 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program : IPP 9/82
 ne=16, na= 1

R0 (eV)	0°	comment
50	1.62e-1	
100	4.82e-1	
200	1.01e-0	
200	9.97e-1	
200	1.01e-0	
200	1.35e-0	kdee1 = kdee2=2 (OR)
200	7.73e-1	kdee1 = kdee2 = 1 (LS)
500	1.98e-0	
1000	2.80e-0	
2000	4.15e-0	
5000	5.47e-0	
10000	7.08e-0	
20000	7.99e-0	
50000	8.65e-0	
100000	8.55e-0	
200000	7.92e-0	

Sputtered energy of Sm by Kr

program :
 ne=16, na= 1

R0 (eV)	0°	comment
50	9.24e-3	
100	1.98e-2	
200	2.85e-2	
200	2.81e-2	
200	2.85e-2	
200	3.85e-2	kdee1=kdee2=2 (OR)
200	2.19e-2	kdee1 = kdee2 = 1 (LS)
500	3.13e-2	
1000	3.42e-2	
2000	3.18e-2	
5000	2.67e-2	
10000	2.23e-2	
20000	1.70e-2	
50000	1.16e-2	
100000	7.82e-3	
200000	4.97e-3	

Kr → Sm

Particle reflection coefficient of Kr backscattered from Sm
 z1=36, m1 = 83.80, z2=62, m2=150.35, sbe=2.16 eV, rho=7.54 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot = 1 (KrC)
 program : TPP 9/82
 ne=16, na= 1

E ₀ (eV)	0°	comment
50	2.38e-1	
100	2.01e-1	
200	1.81e-1	
200	1.74e-1	
200	1.74e-1	
200	1.97e-1	kdee1 = kdee2 = 2 (OR)
200	1.62e-1	kdee1 = kdee2 = 1 (LS)
500	1.46e-1	
1000	1.28e-1	
2000	1.19e-1	
5000	9.66e-2	
10000	8.41e-2	
20000	7.55e-2	
50000	5.72e-2	
100000	4.02e-2	
200000	3.09e-2	

Energy reflection coefficient of Kr backscattered from
 ne=16, na= 1

E ₀ (eV)	0°	comment
50	2.53e-2	
100	2.13e-2	
200	1.92e-2	
200	1.80e-2	
200	1.76e-2	
200	2.14e-2	kdee1 = kdee2 = 2 (OR)
200	1.64e-2	kdee1 = kdee2 = 1 (LS)
500	1.46e-2	
1000	1.29e-2	
2000	1.16e-2	
5000	9.70e-3	
10000	8.62e-3	
20000	7.86e-3	
50000	6.06e-3	
100000	4.64e-3	
200000	3.30e-3	

Average depth (mean range) in Å of Kr implanted in
 ne=15, na= 1

E ₀ (eV)	0°	comment
50	1.07e+1	
100	1.33e+1	
200	1.68e+1	
200	1.70e+1	
200	1.68e+1	
200	1.76e+1	kdee1 = kdee2 = 2 (OR)
200	1.63e+1	kdee1 = kdee2 = 1 (LS)
500	2.39e+1	
1000	2.83e+1	
2000	4.36e+1	
5000	6.55e+1	
10000	1.00e+2	
20000	1.53e+2	
50000	2.81e+2	
100000	4.70e+2	

H → Ta

Sputtering yield of Ta by H

z1= 1, m1= 1.01, z2=73, m2=180.95, sbe=8.10 eV, rho=16.60 g/cm**3
 ef=0.98 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1= 4, kdee2=3, ipot=ipotrl (KrC)
 program: testvmcx, TPP 9/82
 ne= 1, na= 8

E ₀ (eV)	0°	30°	50°	70°	80°	85°	87°	88°
25000	1.95e-3	3.63e-3	7.48e-3	1.93e-2	3.68e-2	6.69e-2	8.30e-2	7.81e-1

Sputtered energy of Ta by H

program: testvmcx
 ne= 1, na= 4

E ₀ (eV)	80°	85°	87°	88°
25000	4.55e-5	9.12e-5	1.30e-4	1.23e-4

Particle reflection coefficient of Pt backscattered from Ta

z1= 1, m1= 1.01, z2=73, m2= 180.95, sbe=8.10 eV, rho=16.60 g/cm**3
 ef=0.98 eV, esb= 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=4, kdee2=3, ipqt=ipotrl (KrC)
 program: testvmcx
 ne= 1, na= 4

E ₀ (eV)	80°	85°	87°	88°
25000	5.70e-1	6.86e-1	7.87e-1	8v21e-1

Energy reflection coefficient of H backscattered from Ta

ne= 1, na= 4

E ₀ (eV)	80°	85°	87°	88°
25000	3.35e-1	4.80e-1	5.86e-1	6.86e-1

Average depth (mean range) in Å of H implanted in Ta

ne= 1, na= 4

E ₀ (eV)	80°	85°	87°	88°
25000	8.61e+2	8.53e+2	8.50e+2	8.45e+2

H → W

Sputtering yield of W by H

z1 = 1, m1 = 1.01, z2 = 74, m2 = 183.65, esb = 8.68 eV, rho = 19.29 g/cm**3
 ef = 0.95 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2; kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: testvmcx, trvmc
 ne = 11, na = 12

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	70°	75°	80°	85°	87°
500	1.18e-5	1.43e-5	1.23e-5	1.65e-5	1.88e-5		2.03e-5		1.17e-5	6.44e-6	8.94e-7	
550	4.25e-5	4.28e-5	5.43e-5	5.53e-5	6.10e-5		5.80e-5		4.15e-5	2.39e-5	3.99e-6	
600	8.88e-5	9.04e-5	9.68e-5	1.21e-4	1.34e-4		1.31e-4		9.76e-5	5.70e-5	1.20e-5	
700	2.42e-4	2.55e-4	2.85e-4	3.04e-4	3.43e-4		3.39e-4		2.82e-4	1.87e-4	3.85e-5	
800	4.18e-4	4.62e-4	5.22e-4	5.70e-4	6.28e-4		6.86e-4		5.85e-4	3.86e-4	1.02e-4	
900	6.72e-4	6.70e-4	7.36e-4	8.36e-4	9.57e-4		1.02e-3		9.32e-4	6.94e-4	2.12e-4	
1000	8.64e-4	9.04e-4	9.91e-4	1.09e-3	1.24e-3		1.49e-3		1.44e-3	1.14e-3	3.91e-4	
2000	2.42e-3	2.41e-3	2.82e-3	3.70e-3		4.90e-3		7.16e-3	9.77e-3	1.23e-2	1.18e-2	4.48e-3
5000	3.32e-3											
10000	3.15e-3											
20000	2.50e-3											

Sputtered energy of W by H

ne = 11, na = 12

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	70°	75°	80°	85°	87°
500	1.85e-8	2.14e-8	2.08e-8	2.63e-8	2.96e-8		3.46e-8		1.92e-8	9.19e-9	1.35e-9	
550	8.45e-8	9.95e-8	1.20e-7	1.26e-7	1.37e-7		1.38e-7		9.42e-8	5.16e-8	8.59e-9	
600	2.37e-7	2.42e-7	2.47e-7	3.26e-7	3.64e-7		3.70e-7		2.77e-7	1.53e-7	3.07e-8	
700	7.82e-7	8.33e-7	9.38e-7	1.03e-6	1.17e-6		1.21e-6		1.00e-6	6.37e-7	1.25e-7	
800	1.53e-6	1.67e-6	1.94e-6	2.28e-6	2.37e-6		2.67e-6		2.35e-6	1.51e-6	4.02e-7	
900	2.66e-6	2.67e-6	2.95e-6	3.46e-6	3.96e-6		4.32e-6		3.90e-6	2.95e-6	9.06e-7	
1000	3.55e-6	3.68e-6	4.08e-6	4.67e-6	5.37e-6		6.44e-6		6.22e-6	5.10e-6	1.66e-6	
2000	1.01e-5	9.89e-6	1.17e-5	1.49e-5		2.12e-5		3.03e-5	4.31e-5	5.60e-5	6.16e-5	2.55e-5
5000	9.74e-6											
10000	5.94e-6											
20000	2.97e-6											

H -> W

Particle reflection coefficient of TJ backscattered from W
 z1= 1, m1= 1.01, z2=74, m2=183.65, esb=8.68 eV, rho=19.29 g/cm**3
 cf=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3; ipot=ipottr = 1 (KrC)
 program: testvmcx, trvmc
 ne=17, na=12

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	70°	75°	80°	85°	87°
10	7.58e-1	7.67e-1	7.93e-1	8.40e-1	8.80e-1		9.22e-1		9.59e-1	9.72e-1	9.80e-1	
20	7.17e-1	7.29e-1	7.52e-1	8.05e-1	8.51e-1		9.04e-1		9.57e-1	9.77e-1	9.88e-1	
50	6.68e-1	6.77e-1	7.05e-1	7.51e-1	7.97e-1		8.59e-1		9.37e-1	9.73e-1	9.93e-1	
100	6.32e-1	6.41e-1	6.67e-1	7.15e-1	7.56e-1		8.17e-1		9.06e-1	9.58e-1	9.93e-1	
200	5.94e-1	6.05e-1	6.29e-1	6.75e-1	7.19e-1		7.75e-1		8.61e-1	9.29e-1	9.90e-1	
300	5.71e-1	5.80e-1	6.09e-1	6.55e-1	6.97e-1		7.54e-1		8.35e-1	9.04e-1	9.85e-1	
500	5.39e-1	5.49e-1	5.77e-1	6.25e-1	6.68e-1		7.24e-1		8.03e-1	8.69e-1	9.72e-1	
550	5.32e-1	5.42e-1	5.71e-1	6.19e-1	6.62e-1		7.18e-1		7.97e-1	8.63e-1	9.69e-1	
600	5.27e-1	5.36e-1	5.64e-1	6.14e-1	6.57e-1		7.13e-1		7.92e-1	8.57e-1	9.65e-1	
700	5.15e-1	5.25e-1	5.55e-1	6.04e-1	6.48e-1		7.04e-1		7.82e-1	8.46e-1	9.58e-1	
800	5.05e-1	5.15e-1	5.45e-1	5.95e-1	6.40e-1		6.96e-1		7.74e-1	8.37e-1	9.51e-1	
900	4.95e-1	5.06e-1	5.36e-1	5.86e-1	6.32e-1		6.89e-1		7.66e-1	8.28e-1	9.45e-1	
1000	4.87e-1	4.97e-1	5.27e-1	5.78e-1	6.25e-1		6.83e-1		7.60e-1	8.21e-1	9.38e-1	
2000	4.25e-1	4.36e-1	4.68e-1	5.24e-1		6.04e-1		6.72e-1	7.18e-1	7.74e-1	8.86e-1	9.70e-1
5000	3.23e-1											
10000	2.40e-1											
20000	1.55e-1											

Energy reflection coefficient of H backscattered from W
 ne=17, na=12

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	70°	75°	80°	85°	87°
10	5.64E-1	5.77E-1	6.15E-1	6.83E-1	7.45E-1		8.13E-1		8.80E-1	9.05E-1	9.21E-1	
20	5.13E-1	5.27E-1	5.62E-1	6.34E-1	7.04E-1		7.90E-1		8.84E-1	9.23E-1	9.47E-1	
50	4.51E-1	4.63E-1	4.97E-1	5.59E-1	6.25E-1		7.21E-1		8.53E-1	9.20E-1	9.62E-1	
100	4.10E-1	4.19E-1	4.50E-1	5.09E-1	5.67E-1		6.56E-1		8.01E-1	8.95E-1	9.65E-1	
200	3.70E-1	3.81E-1	4.08E-1	4.62E-1	5.16E-1		5.96E-1		7.30E-1	8.45E-1	9.60E-1	
300	3.47E-1	3.55E-1	3.84E-1	4.37E-1	4.89E-1		5.64E-1		6.90E-1	8.05E-1	9.51E-1	
500	3.16E-1	3.25E-1	3.53E-1	4.04E-1	4.54E-1		5.25E-1		6.42E-1	7.50E-1	9.29E-1	
550	3.10E-1	3.19E-1	3.47E-1	3.98E-1	4.48E-1		5.19E-1		6.33E-1	7.39E-1	9.23E-1	
600	3.05E-1	3.14E-1	3.41E-1	3.92E-1	4.42E-1		5.12E-1		6.25E-1	7.30E-1	9.17E-1	
700	2.95E-1	3.04E-1	3.32E-1	3.82E-1	4.32E-1		5.01E-1		6.12E-1	7.13E-1	9.05E-1	
800	2.86E-1	2.95E-1	3.23E-1	3.73E-1	4.23E-1		4.92E-1		6.01E-1	6.99E-1	8.93E-1	
900	2.78E-1	2.87E-1	3.14E-1	3.64E-1	4.14E-1		4.83E-1		5.91E-1	6.87E-1	8.82E-1	
1000	2.71E-1	2.80E-1	3.07E-1	3.57E-1	4.07E-1		4.76E-1		5.82E-1	6.76E-1	8.71E-1	
2000	2.21e-1	2.30e-1	2.56e-1	3.06e-1		3.87e-1		4.68e-1	5.27e-1	6.09e-1	7.88e-1	9.30e-1
5000	1.50e-1											
10000	9.88e-2											
20000	5.54e-2											

Average depth (mean range) in Å of H implanted in W
 ne=17, na=12

E ₀ (eV)	0°	15°	30°	45°	55°	60°	65°	70°	75°	80°	85°	87°
10	1.30E+1	1.29E+1	1.29E+1	1.28E+1	1.27E+1		1.27E+1		1.25E+1	1.25E+1	1.25E+1	
20	1.82E+1	1.82E+1	1.82E+1	1.80E+1	1.79E+1		1.77E+1		1.76E+1	1.77E+1	1.76E+1	
50	2.86E+1	2.86E+1	2.85E+1	2.83E+1	2.80E+1		2.80E+1		2.77E+1	2.76E+1	2.75E+1	
100	4.09E+1	4.06E+1	4.04E+1	4.01E+1	3.97E+1		3.93E+1		3.90E+1	3.90E+1	3.90E+1	
200	5.85E+1	5.81E+1	5.76E+1	5.70E+1	5.62E+1		5.61E+1		5.57E+1	5.52E+1	5.51E+1	
300	7.27E+1	7.27E+1	7.16E+1	7.08E+1	7.01E+1		6.94E+1		6.85E+1	6.86E+1	6.85E+1	
500	9.63E+1	9.59E+1	9.49E+1	9.33E+1	9.23E+1		9.12E+1		9.00E+1	9.00E+1	9.00E+1	
550	1.02E+2	1.01E+2	1.00E+2	9.84E+1	9.73E+1		9.61E+1		9.51E+1	9.49E+1	9.49E+1	
600	1.07E+2	1.06E+2	1.05E+2	1.03E+2	1.02E+2		1.01E+2		9.98E+1	9.94E+1	9.93E+1	
700	1.17E+2	1.16E+2	1.15E+2	1.13E+2	1.11E+2		1.10E+2		1.09E+2	1.08E+2	1.08E+2	
800	1.26E+2	1.26E+2	1.24E+2	1.22E+2	1.20E+2		1.18E+2		1.17E+2	1.17E+2	1.17E+2	
900	1.36E+2	1.35E+2	1.33E+2	1.30E+2	1.29E+2		1.27E+2		1.25E+2	1.25E+2	1.25E+2	
1000	1.44E+2	1.44E+2	1.42E+2	1.39E+2	1.37E+2		1.35E+2		1.33E+2	1.33E+2	1.32E+2	
2000	2.22e+2	2.21e+2	2.17e+2	2.11e+2		2.05e+2		2.01e+2	2.00e+2	1.99e+2	1.98e+2	1.98e+2
5000	4.12e+2											
10000	6.81e+2											
20000	1.16e+3											

H-> W

H on W. Maxwellian velocity distribution, sheath potential 3 kT
 z1 = 1. m1 = 1.01. z2=74. m2 = 183.85. sbe=8.68 eV. rho = 19.30 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00. kkO=kkOr=2. kdee1 = kdee2=3. ipot=ipotrl=1 (KrC)
 program: testvmcx
 ne=7

kT(eV)	Y	γ_E	E_{sp}	Bat	R_E	Rb	range
50	1.00e-6		9.63e-1	6.04e-1		1.59e+2	6.17e+1
70	1.15e-5		1.78e+0	5.84e-1		2.19e+2	7.46e+1
100	7.50e-5		2.77e+0	5.63e-1		3.05e+2	9.16e+1
150	4.96e-4		3.77e+0	5.35e-1		4.44e+2	1.16e+2
200	1.07e-3		4.95e+0	5.15e-1		5.78e+2	1.38e+2
300	1.90e-3		6.99e+0	4.81e-1		8.35e+2	1.78e+2
500	2.99e-3		1.01e+1	4.34e-1		1.32e+3	2.48e+2

D -> W

Sputtering yield of W by D

z1 = 1, m1= 2.01, z2=74, m2 = 183.85, esb = 8.68 eV. rho = 19.30 g/cm**3

ef=0.98 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: trspvmcx

ne=22, na=9

EO(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
250	2.34e-5	2.33e-5	2.50e-5	3.08e-5	3.00e-5	2.64e-5	1.43e-5	5.19e-6	2.86e-6
260	5.05e-5								
270	7.63e-5	8.21e-5	8.33e-5	1.00e-4	9.70e-5	9.17e-5	5.54e-5	2.16e-5	3.40e-6
290	1.62e-4					1.82e-4			
300	2.08e-4	2.21e-4	2.37e-4	2.82e-4	2.73e-4	2.32e-4	1.53e-4	7.83e-5	9.13e-6
300	2.33e-4					2.36e-4			
310	2.87e-4					3.11e-4			
320	3.55e-4					4.14e-4			
350	5.98e-4	6.04e-4	6.83e-4	7.34e-4	7.85e-4	7.52e-4	4.75e-4	2.60e-4	4.13e-5
350						7.49e-4			
400	1.11e-3	1.16e-3	1.18e-3	1.33e-3	1.53e-3	1.39e-3	9.83e-4	5.91e-4	9.55e-5
400	1.09e-3					1.39e-3			
500	2.20e-3	2.32e-3	2.49e-3	2.74e-3	2.93e-3	3.08e-3	2.50e-3	1.72e-3	3.56e-4
500	2.37e-3					2.94e-3			
600	3.39e-3	3.31e-3	3.42e-3	4.11e-3	4.55e-3	4.76e-3	4.73e-3	3.78e-3	1.12e-3
700	4.22e-3	4.14e-3	4.84e-3	5.23e-3	6.38e-3	7.10e-3	7.42e-3	6.92e-3	2.52e-3
700						6.80e-3			
1000	6.55e-3	7.11e-3	7.78e-3	9.22e-3	1.07e-2	1.26e-2	1.82e-2	2.04e-2	1.15e-2
1000	6.22e-3					1.33e-2			
2000	9.54e-3					2.66e-2			
5000	1.05e-2					3.85e-2			
10000						3.60e-2			

Sputtered energy of W by D

ne=22, na=9

B ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
250	6.43e-8	6.37e-8	6.80e-8	8.51e-8	8.95e-8	8.06e-8	3.89e-8	1.41e-8	4.10e-9
260	1.61e-7								
270	2.80e-7	3.12e-7	3.24e-7	4.06e-7	3.95e-7	3.79e-7	2.21e-7	7.90e-8	1.06e-8
290	7.66e-7					9.10e-7			
300	1.04e-6	1.11e-6	1.20e-6	1.47e-6	1.44e-6	1.27e-6	8.06e-7	3.90e-7	4.63e-8
300	1.17e-6					1.26e-6			
310	1.55e-6					1.75e-6			
320	1.99e-6					2.51e-6			
350	3.89e-6	3.98e-6	4.56e-6	5.02e-6	5.41e-6	5.12e-6	3.23e-6	1.75e-6	2.64e-7
350						5.13e-6			
400	8.04e-6	8.70e-6	8.56e-6	1.02e-5	1.21e-5	1.10e-5	7.77e-6	4.66e-6	7.04e-7
400	7.99e-6					1.12e-5			
500	1.87e-5	1.96e-5	2.18e-5	2.41e-5	2.66e-5	2.76e-5	2.25e-5	1.55e-5	3.04e-6
500	2.00e-5					2.66e-5			
600	3.03e-5	2.88e-5	3.12e-5	3.75e-5	4.14e-5	4.39e-5	4.36e-5	3.54e-5	1.03e-5
700	3.77e-5	3.78e-5	4.23e-5	4.93e-5	5.80e-5	6.48e-5	7.03e-5	6.41e-5	2.45e-5
700						6.28e-5			
1000	5.60e-5	6.18e-5	6.73e-5	8.18e-5	9.43e-5	1.14e-4	1.63e-4	1.86e-4	1.25e-4
1000	5.40e-5					1.18e-4			
2000	6.78e-5					1.85e-4			
5000	4.48e-5					1.71e-4			
10000						1.12e-4			

D > W

Particle reflection coefficient of D backscattered from W

z1= 1, m1 = 2.01, z2= 74, m2 = 183.85, esb= 8.68 eV, rho = 19.30 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2 = 3, ipot=ipotr = 1 (KrC)
 program: trspvmcx
 ne = 28, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	7.61E-1	7.70E-1	7.98E-1	8.42E-1	8.82E-1	9.23E-1	9.60E-1	9.73E-1	9.80E-1
20	7.24E-1	7.33E-1	7.60E-1	8.10E-1	8.53E-1	9.06E-1	9.58E-1	9.78E-1	9.88E-1
50	6.79E-1	6.87E-1	7.14E-1	7.58E-1	8.05E-1	8.64E-1	9.39E-1	9.74E-1	9.93E-1
100	6.49E-1	6.54E-1	6.81E-1	7.27E-1	7.63E-1	8.23E-1	9.09E-1	9.60E-1	9.93E-1
200	6.12E-1	6.24E-1	6.43E-1	6.90E-1	7.31E-1	7.86E-1	8.69E-1	9.32E-1	9.90E-1
200	6.14e-1								
250	6.02E-1	6.11E-1	6.37E-1	6.80E-1	7.21E-1	7.74E-1	8.55E-1	9.20E-1	9.88E-1
260	6.01e-1								
270	5.98E-1	6.07E-1	6.33E-1	6.77E-1	7.17E-1	7.70E-1	8.50E-1	9.15E-1	9.87E-1
290	5.95E-1								
300	5.92E-1	6.01E-1	6.28E-1	6.72E-1	7.12E-1	7.64E-1	8.44E-1	9.09E-1	9.86E-1
300	5.93e-1								
310	5.91e-1								
320	5.89e-1								
350	5.84E-1	5.93E-1	6.20E-1	6.64E-1	7.04E-1	7.57E-1	8.34E-1	9.00E-1	9.83E-1
350									
400	5.77E-1	5.85E-1	6.12E-1	6.57E-1	6.97E-1	7.50E-1	8.27E-1	8.91E-1	9.80E-1
400	5.78e-1								
500	5.64E-1	5.73E-1	6.00E-1	6.45E-1	6.86E-1	7.38E-1	8.14E-1	8.77E-1	9.74E-1
500	5.58e-1								
600	5.53E-1	5.61E-1	5.88E-1	6.36E-1	6.78E-1	7.29E-1	8.03E-1	8.65E-1	9.67E-1
700	5.43E-1	5.50E-1	5.79E-1	6.25E-1	6.68E-1	7.22E-1	7.94E-1	8.55E-1	9.61E-1
700									
700									
1000	5.17E-1	5.28E-1	5.57E-1	6.05E-1	6.46E-1	7.03E-1	7.74E-1	8.33E-1	9.42E-1
1000	5.12e-1								
2000	4.57E-1								
5000	3.64E-1								
10000	2.71E-1								

Energy reflection coefficient of D backscattered from W
 ne = 28, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	5.71E-1	5.85E-1	6.24E-1	6.90E-1	7.52E-1	8.20E-1	8.85E-1	9.11E-1	9.25E-1
20	5.25E-1	5.36E-1	5.74E-1	6.44E-1	7.12E-1	7.98E-1	8.90E-1	9.28E-1	9.51E-1
50	4.69E-1	4.79E-1	5.12E-1	5.73E-1	6.40E-1	7.33E-1	8.61E-1	9.26E-1	9.67E-1
100	4.33E-1	4.42E-1	4.71E-1	5.30E-1	5.83E-1	6.72E-1	8.12E-1	9.04E-1	9.70E-1
200	3.94E-1	4.06E-1	4.31E-1	4.85E-1	5.39E-1	6.16E-1	7.47E-1	8.56E-1	9.66E-1
200	3.95e-1								
250	3.84E-1	3.93E-1	4.21E-1	4.73E-1	5.25E-1	6.00E-1	7.26E-1	8.37E-1	9.62E-1
260	3.82e-1								
270	3.79E-1	3.89E-1	4.17E-1	4.69E-1	5.20E-1	5.94E-1	7.19E-1	8.29E-1	9.60E-1
290	3.76e-1								
300	3.74E-1	3.83E-1	4.12E-1	4.63E-1	5.14E-1	5.87E-1	7.09E-1	8.19E-1	9.57E-1
300	3.74e-1								
310	3.72E-1								
320	3.71E-1								
350	3.66E-1	3.75E-1	4.03E-1	4.54E-1	5.04E-1	5.76E-1	6.95E-1	8.04E-1	9.52E-1
350									
400	3.59E-1	3.67E-1	3.96E-1	4.47E-1	4.96E-1	5.67E-1	6.84E-1	7.90E-1	9.47E-1
400	3.59e-1								
500	3.46E-1	3.56E-1	3.83E-1	4.33E-1	4.84E-1	5.52E-1	6.65E-1	7.67E-1	9.37E-1
500	3.45e-1								
600	3.36E-1	3.44E-1	3.73E-1	4.23E-1	4.73E-1	5.41E-1	6.49E-1	7.49E-1	9.25E-1
700	3.27E-1	3.35E-1	3.64E-1	4.13E-1	4.62E-1	5.32E-1	6.37E-1	7.34E-1	9.14E-1
700									
700									
1000	3.04E-1	3.14E-1	3.42E-1	3.92E-1	4.38E-1	5.08E-1	6.09E-1	7.00E-1	8.83E-1
1000	3.03e-1								
2000	2.55E-1								
5000	1.83E-1								
10000	1.21E-1								

D -> W

Average depth (mean range) in Å of D implanted in W
 $n_e=28$, $n_a=9$

Bo (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	1.33E4-1	1.33E+1	1.33E+1	1.32E4-1	1.32E+1	1.31E4-1	1.30E+1	1.30E+1	1.29E4-1
20	1.90E+1	1.89E+1	1.89E+1	1.87E+1	1.86E+1	1.86E+1	1.84E+1	1.84E+1	1.82E+1
50	3.04E4-1	3.01E+1	3.00E+1	2.96E+1	2.94E+1	2.95E4-1	2.94E+1	2.89E+1	2.91E+1
100	4.37E+1	4.32E+1	4.31E4-1	4.23E+1	4.21E+1	4.20E+1	4.18E+1	4.15E+1	4.19E4-1
200	6.30E+1	6.28E4-1	6.25E+1	6.15E+1	6.12E+1	6.03E+1	6.04E+1	5.94E+1	5.98E+1
200	6.28e4-1								
250	7.11E+1	7.09E4-1	7.03E+1	6.95E+1	6.89E+1	6.83E4-1	6.78E+1	6.77E+1	6.76E+1
260	7.27e4-1								
270	7.42e+1	7.40e+1	7.35e+1	7.25e+1	7.19e+1	7.13e+1	7.07e+1	7.05e+1	7.03e+1
290	7.73e+1								
300	7.88E+1	7.85E+1	7.78E+1	7.69E+1	7.62E4-1	7.55E+1	7.49E+1	7.48E+1	7.45E+1
300	7.87e+1					7.55e+1			
310	8.01e+1					7.68e+1			
320	8.16e+1					7.82e+1			
350	8.58E+1	8.56E4-1	8.49E+1	8.38E+1	8.31E+1	8.23E+1	8.17E+1	8.14E+1	8.12E+1
350						8.23e+1			
400	9.28E+1	9.25E4-1	9.16E+1	9.03E4-1	8.94E+1	8.88E+1	8.79E+1	8.76E4-1	8.75E+1
400	9.27e+1					8.85e+1			
500	1.06E+2	1.05E4-2	1.04E+2	1.03E4-2	1.02E+2	1.01E+2	9.98E+1	9.96E4-1	9.94E+1
500	1.02e+2					1.00e+2			
600	1.18E+2	1.17E+2	1.16E+2	1.14E+2	1.13E+2	1.12E-J-2	1.11E+2	1.11E+2	1.10E+2
700	1.29E+2	1.29E+2	1.27E4-2	1.25E+2	1.24E+2	1.22E+2	1.21E+2	1.21E4-2	1.21E+2
700						1.22e+2			
1000	1.61E+2	1.60E+2	1.58E+2	1.56E4-2	1.53E+2	1.52E+2	1.50E+2	1.50E+2	1.49E4-2
1000	1.57e+2					1.51e+2			
2000	2.48e+2					2.33e+2			
5000	4.75e+2					4.28e+2			
10000	8.02e+2					6.84eJ-2			

D on W, Maxwellian velocity distribution, sheath potential 0 kT
 $z1=1$, $m1=2.01$, $z2=74$, $m2=183.85$, $sbe=8.68$ eV, $\rho=19.30$ g/cm**3
 $ef=0.98$ eV, $esb=1.00$ eV, $ca=1.00$, $kk0=kk0r=2$, $kdee1=kdee2=3$, $ipotr=1(KrC)$
 program: testvmcx
 $n_e=8$

kT(eV)	Y	Y _E	E _{sp}	γ _{7V}	H _E	E _b	range
70	8.28e-5	2.18e-6	3.68e+0	7.44e-1	5.32e-1	1.00e+2	5.09e+1
100	3.54e-4	7.92e-6	4.48e+0	7.26e-1	5.10e-1	1.40e+2	6.16e4-1
140	9.57e-4	1.92e-5	5.61e4-0	7.09e-1	4.89e-1	1.93e+2	7.42e+1
200	2.13e-3	3.78e-5	7.09e4-0	6.91e-1	4.67e-1	2.70e+2	9.06e+1
300	4.42e-3	6.50e-5	8.83e4-0	6.69e-1	4.40e-1	3.96e+2	1.15e4-2
500	8.58e-3	9.84e-5	1.15e+1	6.39e-1	4.07e-1	6.36e+2	1.57e+2
1000	1.56e-2	1.22e-4	1.57e4-1	5.91e-1	3.55e-1	1.20e+3	2.46e+2
2000	2.15e-2	1.11e-4	2.07e+1	5.36e-1	2.98e-1	2.22e+3	3.95e+2

D on W, Maxwellian velocity distribution, sheath potential 3 kT
 $n_e=13$

kT(eV)	Y	Y _E	E _{sp}	R _N	R _E	E _b	range
36	2.67e-5	3.02e-7	2.04e+0	6.46e-1	4.31e-1	1.21e+2	5.84e+1
40	5.35e-5		2.54e+0	6.33e-1		1.36e+2	5.87e+1
45	1.06e-4		2.53e+0	6.28e-1		1.49e+2	6.28e+1
50	2.41e-4		2.82e+0	6.21e-1		1.65e-f-2	6.68e+1
60	4.78e-4		3.52e+0	6.13e-1		1.97e4-2	7.41e+1
75	1.06e-3		4.04e+0	6.02e-1		2.43e+2	8.47e+1
100	2.57e-3		5.12e+0	5.86e-1		3.19e4-2	1.00e+2
140	4.54e-3		6.84e+0	5.66e-1		4.37e+2	1.24e+2
200	6.67e-3		9.08e+0	5.44e-1		6.11e+2	1.54e+2
300	9.26e-3		1.19e+1	5.13e-1		8.88e+2	2.01e+2
500	1.15e-2		1.58e+1	4.71e-1		1.42e+3	2.83e+2
1000	1.21e-2		2.20e-H	4.03e-1		2.61e+3	4.62e+2
2000	1.23e-2	3.47e-5	2.82e+1	3.24e-1	1.52e-1	4.68e+3	7.74e+2

T -> W

Sputtering yield of W by T

z1= 1, m1= 3.02, z2=74, m2=183.85, esb= 8.68 eV, rho = 19.29 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvmcx
 ne=17, na=9

Bo (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
160	9.83E-6	7.83E-6	8.08E-6	1.26E-5	1.26E-5	9.53E-6	2.89E-6		
170	3.77E-5	4.08E-5	4.54E-5	5.05E-5	4.47E-5	3.87E-5	1.62E-5	6.08E-6	
170	3.65E-5								
180	9.81E-5	1.00E-4	1.05E-4	1.16E-4	1.14E-4	8.79E-5	4.71E-5	1.98E-5	1.93E-6
200	3.03E-4	3.07E-4	3.23E-4	3.59E-4	3.55E-4	2.99E-4	1.64E-4	7.18E-5	9.69E-6
250	1.23E-3	1.29E-3	1.28E-3	1.46E-3	1.45E-3	1.34E-3	7.91E-4	4.24E-4	5.49E-5
300	2.41E-3	2.48E-3	2.71E-3	2.85E-3	2.91E-3	2.91E-3	1.91E-3	1.07E-3	1.52E-4
300	2.35E-3					2.87E-3			
400	4.89E-3	4.91E-3	5.17E-3	5.90E-3	6.64E-3	6.73E-3	5.97E-3	3.98E-3	9.08E-4
500	7.22E-3	7.54E-3	8.13E-3	9.01E-3	1.02E-2	1.13E-2	1.17E-2	9.68E-3	2.94E-3
500	7.45E-3					1.12E-2			
700	1.11E-2	1.08E-2	1.25E-2	1.46E-2	1.69E-2	2.04E-2	2.67E-2	2.70E-2	1.25E-2
700						2.04E-2			
1000	1.49E-2	1.50E-2	1.67E-2	1.98E-2	2.41E-2	3.19E-2	4.67E-2	5.34E-2	3.08E-2
1000	1.45E-2					3.17E-2			
2000	1.85E-2					5.28E-2			
5000	2.00E-2					6.52E-2			

Sputtered energy of W by T

ne=17, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
160	2.14e-8	1.91e-8	2.14e-8	3.48e-8	3.57e-8	2.86e-8	7.69e-9		
170	1.47e-7	1.68e-7	1.80e-7	2.25e-7	2.02e-7	1.67e-7	6.90e-8	2.49e-8	
170	1.39e-7								
180	4.98e-7	5.24e-7	5.47e-7	6.38e-7	6.45e-7	5.04e-7	2.51e-7	1.02e-7	8.41e-9
200	2.18e-6	2.24e-6	2.39e-6	2.72e-6	2.72e-6	2.30e-6	1.21e-6	5.03e-7	6.64e-8
250	1.26E-5	1.34E-5	1.32E-5	1.59E-5	1.61E-5	1.46E-5	8.50E-6	4.57E-6	5.78E-7
300	2.90E-5	2.98E-5	3.31E-5	3.55E-5	3.70E-5	3.73E-5	2.45E-5	1.36E-5	1.86E-6
300	2.87e-5					3.68e-5			
400	6.61E-5	6.67E-5	6.87E-5	8.21E-5	9.16E-5	9.50E-5	8.34E-5	5.42E-5	1.25E-5
500	9.71E-4	1.03E-4	1.12E-4	1.27E-4	1.44E-4	1.62E-4	1.65E-4	1.39E-4	4.47E-5
500	9.63e-5					1.60e-4			
700	1.47E-4	1.51E-4	1.67E-4	1.97E-4	2.27E-4	2.68E-4	3.53E-4	3.91E-4	2.04E-4
700						2.70e-4			
1000	1.72E-4	1.76E-4	1.96E-4	2.32E-4	2.85E-4	3.80E-4	5.85E-4	7.24E-4	4.93E-4
1000	1.77e-4					3.75e-4			
2000	1.58e-4					4.74e-4			
5000	1.03e-4					3.46e-4			

T → W

Particle reflection coefficient of T backscattered from W
 z1 = 1, m1 = 3.02, z2=74, m2=183.85, esb=8.68 eV, rho = 19.29 g/cm**3
 ef=0.98 eV, esb = 1.00 eV, ca=1.00, kk0r=2, kdeel = kdec2=3, ipot=ipotrr=1 (KrC)
 program: trspvmcx
 ne=22, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	7.51E-1	7.60E-1	7.89E-1	8.37E-1	8.78E-1	9.19E-1	9.58E-1	9.71E-1	9.79E-1
20	7.15E-1	7.25E-1	7.53E-1	8.03E-1	8.48E-1	9.02E-1	9.57E-1	9.77E-1	9.88E-1
50	6.69E-1	6.79E-1	7.07E-1	7.53E-1	7.98E-1	8.60E-1	9.37E-1	9.73E-1	9.93E-1
100	6.40E-1	6.50E-1	6.75E-1	7.18E-1	7.63E-1	8.20E-1	9.06E-1	9.59E-1	9.93E-1
140	6.25E-1	6.34E-1	6.59E-1	7.04E-1	7.46E-1	8.02E-1	8.88E-1	9.47E-1	9.92E-1
160	6.19E-1	6.28E-1	6.54E-1	6.98E-1	7.39E-1	7.95E-1	8.80E-1	9.42E-1	9.92E-1
170	6.16E-1	6.25E-1	6.51E-1	6.95E-1	7.36E-1	7.91E-1	8.77E-1	9.39E-1	9.91E-1
170	6.16E-1								
180	6.14E-1	6.22E-1	6.48E-1	6.92E-1	7.33E-1	7.89E-1	8.73E-1	9.36E-1	9.91E-1
200	6.09E-1	6.18E-1	6.44E-1	6.88E-1	7.28E-1	7.83E-1	8.67E-1	9.31E-1	9.90E-1
250	5.99E-1	6.07E-1	6.34E-1	6.78E-1	7.18E-1	7.72E-1	8.53E-1	9.19E-1	9.88E-1
300	5.90E-1	5.99E-1	6.26E-1	6.69E-1	7.09E-1	7.63E-1	8.42E-1	9.08E-1	9.85E-1
300	5.90E-1					7.63E-1			
400	5.75E-1	5.84E-1	6.11E-1	6.56E-1	6.97E-1	7.49E-1	8.26E-1	8.90E-1	9.80E-1
500	5.63E-1	5.72E-1	5.99E-1	6.45E-1	6.85E-1	7.39E-1	8.13E-1	8.76E-1	9.74E-1
500	5.63E-1					7.38E-1			
700	5.43E-1	5.53E-1	5.82E-1	6.30E-1	6.68E-1	7.22E-1	7.96E-1	8.55E-1	9.60E-1
700						7.23E-1			
1000	5.20E-1	5.30E-1	5.59E-1	6.07E-1	6.50E-1	7.03E-1	7.76E-1	8.34E-1	9.42E-1
1000	5.18E-1					7.05E-1			
2000	4.69E-1					6.66E-1			
5000	3.86E-1					6.06E-1			

Energy reflection coefficient of T backscattered from W
 ne=22, na=9

Eq (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	5.57E-1	5.70E-1	6.11E-1	6.80E-1	7.43E-1	8.12E-1	8.81E-1	9.06E-1	9.22E-1
20	5.12E-1	5.25E-1	5.64E-1	6.35E-1	7.04E-1	7.92E-1	8.87E-1	9.26E-1	9.50E-1
50	4.58E-1	4.70E-1	5.05E-1	5.68E-1	6.32E-1	7.27E-1	8.58E-1	9.25E-1	9.67E-1
100	4.25E-1	4.35E-1	4.67E-1	5.21E-1	5.82E-1	6.67E-1	8.09E-1	9.03E-1	9.71E-1
140	4.09E-1	4.18E-1	4.48E-1	5.03E-1	5.59E-1	6.41E-1	7.81E-1	8.84E-1	9.70E-1
160	4.03E-1	4.12E-1	4.42E-1	4.96E-1	5.50E-1	6.31E-1	7.68E-1	8.74E-1	9.69E-1
170	4.00E-1	4.09E-1	4.39E-1	4.92E-1	5.47E-1	6.27E-1	7.63E-1	8.70E-1	9.69E-1
170	4.00E-1								
180	3.97E-1	4.07E-1	4.36E-1	4.89E-1	5.43E-1	6.22E-1	7.57E-1	8.66E-1	9.68E-1
200	3.92E-1	4.02E-1	4.31E-1	4.84E-1	5.37E-1	6.15E-1	7.47E-1	8.57E-1	9.67E-1
250	3.82E-1	3.91E-1	4.21E-1	4.72E-1	5.24E-1	5.99E-1	7.27E-1	8.37E-1	9.63E-1
300	3.74E-1	3.83E-1	4.12E-1	4.63E-1	5.14E-1	5.88E-1	7.10E-1	8.20E-1	9.59E-1
300	3.74E-1					5.87E-1			
400	3.59E-1	3.69E-1	3.98E-1	4.48E-1	4.99E-1	5.69E-1	6.86E-1	7.92E-1	9.49E-1
500	3.49E-1	3.58E-1	3.86E-1	4.37E-1	4.85E-1	5.56E-1	6.67E-1	7.70E-1	9.38E-1
500	3.49E-1					5.56E-1			
700	3.31E-1	3.41E-1	3.69E-1	4.21E-1	4.67E-1	5.36E-1	6.42E-1	7.36E-1	9.16E-1
700						5.36E-1			
1000	3.11E-1	3.21E-1	3.48E-1	3.98E-1	4.48E-1	5.15E-1	6.16E-1	7.07E-1	8.87E-1
1000	3.10E-1					5.15E-1			
2000	2.67E-1					4.72E-1			
5000	2.02E-1					4.04E-1			

Average depth (mean range) in Å of T implanted in W
 ne=22, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	1.29E+1	1.28E4-1	1.28E4-1	1.28E+1	1.26E+1	1.26E+1	1.25E+1	1.24E+1	1.24E+1
20	1.83E+1	1.83E+1	1.82E+1	1.82E+1	1.79E+1	1.79E+1	1.78E-J-1	1.78E+1	1.77E-J-1
50	2.95E+1	2.95E+1	2.93E+1	2.91E+1	2.89E4-1	2.86E+1	2.86E+1	2.84E+1	2.82E4-1
100	4.27E4-1	4.28E+1	4.23E-H	4.20E+1	4.15E-J-1	4.12E+1	4.09E-H	4.08E+1	4.07E4-1
140	5.13E+1	5.12E+1	5.08E+1	5.03E+1	5.00E4-1	4.96E-J-1	4.92E-J-1	4.87E+1	4.93E+1
160	5.53E+1	5.51E+1	5.47E+1	5.41E-J-1	5.36E+1	5.33E+1	5.29E+1	5.28E4-1	5.29E+1
170	5.71E+1	5.70E+1	5.66E+1	5.59E+1	5.55E+1	5.50E+1	5.46E+1	5.45E4-1	5.37E4-1
170	5.71E-J-1								
180	5.90E+1	5.88E+1	5.84E+1	5.77E+1	5.73E+1	5.67E+1	5.64E+1	5.62E+1	5.60E+1
200	6.26E+1	6.24E4-1	6.19E+1	6.13E4-1	6.07E+1	6.02E+1	5.98E+1	5.97E+1	5.95E+1
250	7.10E+1	7.09E+1	7.03E+1	6.95E-J-1	6.88E+1	6.82E+1	6.76E4-1	6.75E+1	6.72E+1
300	7.89E+1	7.86E+1	7.79E4-1	7.69E4-1	7.62E+1	7.55E+1	7.50E4-1	7.48E+1	7.44E+1
300	7.89E+1					7.55E+1			
400	9.33E+1	9.31E+1	9.21E+1	9.10E+1	8.99E+1	8.92E+1	8.84E+1	8.84E+1	8.81E+1
500	1.07E+2	1.06E+2	1.05E+2	1.04E+2	1.03E+2	1.02E+2	1.01E4-2	1.01E+2	9.96E+1
500	1.07E+2					1.02E+2			
700	1.31E4-2	1.30E-J-2	1.29E4-2	1.28E+2	1.26E+2	1.24E+2	1.23E+2	1.23E-J-2	1.24E+2
700						1.25E+2			
1000	1.64E+2	1.64E+2	1.62E+2	1.60E+2	1.57E+2	1.55E4-2	1.53E+2	1.53E+2	1.54E+2
1000	1.64E+2					1.55E+2			
2000	2.59E+2					2.44E+2			
5000	5.05E+2					4.55E-J-2			

T → W

T on W, Maxwellian velocity distribution, sheath potential 0 kT
 z1= 1. m1= 3.02. z2=74. m2= 183.85. sbe=8.68 eV. rho = 19.30 g/cm**3
 ef=0.98 eV. esb= 1.00 eV. ca=1.00. kk0=kk0r=2, kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program: testvmcx
 ne= 10

kT(eV)	Y	$\gamma_{\bar{e}}$	E_{SP}	R_N	$R_{\bar{e}}$	$E_{\bar{e}}$	range
40	5.90e-5	2.31e-6	3.13e+0	7.65e-1	5.63e-1	5.89e+1	3.73e+1
50	1.64e-4	6.30e-6	3.84e+0	7.55e-1	5.50e-1	7.28e+1	4.20e+1
60	3.22e-4	1.17e-5	4.37e+0	7.47e-1	5.39e-1	8.65e+1	4.63e+1
80	8.55e-4	2.73e-5	5.11e+0	7.34e-1	5.23e-1	1.14e+2	5.41e+1
100	1.63e-3	4.96e-5	6.09e+0	7.22e-1	5.09e-1	1.41e+2	6.14e+1
200	6.54e-3	1.49e-4	9.10e+0	6.89e-1	4.70e-1	2.73e+2	9.13e+1
300	1.16e-2	2.19e-4	1.13e+1	6.68e-1	4.45e-1	4.00e+2	1.17e+2
500	1.93e-2	2.75e-4	1.43e+1	6.41e-1	4.15e-1	6.47e+2	1.61e+2
1000	3.06e-2	2.97e-4	1.94e+1	5.96e-1	3.66e-1	1.23e+3	2.57e+2
2000	3.99e-2	2.48e-4	2.49e+1	5.47e-1	3.14e-1	2.29e+3	4.19e+2

T on W, Maxwellian velocity distribution, sheath potential 3 kT
 ne= 13

kT(eV)	Y	$\gamma_{\bar{b}}$	E_{SP}	R_A	$R_{\bar{b}}$	$E_{\bar{b}}$	range
24	3.64e-5	6.56e-7	2.17e+0	6.59e-1	4.48e-1	8.15e+1	4.64e+1
30	1.77e-4		2.56e+0	6.41e-1		1.02e+2	4.94eR1
36	4.11e-4		2.89e+0	6.33e-1		1.21e+2	5.48e+1
50	1.70e-3		4.24e+0	6.18e-1		1.66e+2	6.67e+1
60	2.57e-3	4.14e-5	4.83e+0	6.16e-1	4.02e-1	1.96e+2	7.75e-f-1
70	4.22e-3		5.55e+0	6.03e-1		2.29e+2	8.16e+1
100	7.43e-3		7.38e+0	5.85e-1		3.22e+2	1.02e+2
200	1.48e-2		1.21e+1	5.46e-1		6.21e+2	1.59e-f-2
300	1.91e-2	1.94e-4	1.52e+1	5.24e-1	3.15e-1	9.02e+2	2.11e+2
400	2.03e-2		1.78e+1	4.98e-1		1.18e+3	2.53e+2
600	2.26e-2	1.61e-4	2.14e+1	4.66e-1	2.65e-1	1.71e+3	3.41e+2
1000	2.33e-2	1.21e-4	2.60e+1	4.17e-1	2.25e-1	2.70e+3	4.94e+2
2000	2.04e-2	6.91e-5	3.39e+1	3.41e-1	1.67e-1	4.91e+3	8.37e+2

He -4 W

Sputtering yield of W by He

z1= 2, m1 = 4.00, z2=74, m2 = 183.85, esb=8.68 eV, rho=19.29 g/cm**3
 ef=0.20 eV, esb = 0.00 eV, ca=1.00, kk0=r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: trvmc
 ne=20, na=9

Eq (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
125	8.26E-6	9.32E-6	1.12E-5	1.11E-5	9.05E-6	4.44E-6	2.00E-6		
130	3.21E-5	3.56E-5	3.51E-5	3.27E-5	2.86E-5	1.57E-5	3.40E-6		
140	1.32E-4	1.36E-4	1.43E-4	1.45E-4	1.16E-4	7.19E-5	1.94E-5	3.74E-6	
150	3.10E-4	3.22E-4	3.19E-4	3.16E-4	2.87E-4	1.95E-4	6.19E-5	1.25E-5	
170	9.50E-4	9.41E-4	1.01E-3	1.01E-3	8.69E-4	6.13E-4	2.32E-4	6.15E-5	
200	2.33E-3	2.44E-3	2.50E-3	2.63E-3	2.27E-3	1.86E-3	7.62E-4	2.31E-4	2.15E-6
250	5.42E-3	5.27E-3	5.76E-3	5.92E-3	6.10E-3	4.86E-3	2.49E-3	9.07E-4	1.58E-5
300	8.61E-3	8.63E-3	9.41E-3	1.02E-2	9.96E-3	9.35E-3	5.74E-3	2.52E-3	7.76E-5
350	1.21E-2	1.17E-2	1.28E-2	1.42E-2	1.49E-2	1.45E-2	1.02E-2	5.80E-3	2.41E-4
400	1.47E-2	1.49E-2	1.63E-2	1.87E-2	1.97E-2	2.09E-2	1.79E-2	9.86E-3	5.58E-4
500	2.03E-2	2.10E-2	2.27E-2	2.63E-2	2.90E-2	3.34E-2	3.32E-2	2.32E-2	2.01E-3
600	2.42E-2	2.57E-2	2.80E-2	3.30E-2	3.79E-2	4.67E-2	5.19E-2	4.08E-2	4.95E-3
700	2.88E-2	3.04E-2	3.31E-2	3.88E-2	4.58E-2	5.82E-2	6.78E-2	5.84E-2	9.14E-3
1000	3.78E-2	3.97E-2	4.32E-2	5.49E-2	6.78E-2	8.93E-2	1.15E-1	1.06E-1	2.63E-2
1400	4.57E-2	4.70E-2	5.31E-2	7.02E-2	8.85E-2	1.18E-1	1.59E-1	1.57E-1	5.54E-2
2000	5.15E-2	5.43E-2	6.31E-2	8.25E-2	1.07E-1	1.47E-1	2.01E-1	2.11E-1	1.01E-1
5000	5.91E-2	6.36E-2	7.64E-2	1.03E-1	1.39E-1	1.89E-1	2.84E-1	3.31E-1	2.67E-1
10000	5.63E-2	6.28E-2	7.47E-2	1.04E-1	1.36E-1	1.96E-1	3.07E-1	3.81E-1	3.93E-1
20000	4.78E-2	5.24E-2	6.44E-2	9.04E-2	1.22E-1	1.77E-1	2.90E-1	3.92E-1	4.79E-1
50000	3.23E-2	3.48E-2	4.49E-2	6.46E-2	8.69E-2	1.27E-1	2.26E-1	3.25E-1	4.94E-1

Sputtered energy of W by He

ne=20, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
125	2.08e-8	2.68e-8	3.18e-8	3.61e-8	3.06e-8	1.40e-8	6.54e-9		
130	1.27e-7	1.51e-7	1.51e-7	1.44e-7	1.30e-7	6.83e-8	1.25e-8		
140	8.49e-7	8.78e-7	9.35e-7	9.63e-7	7.76e-7	4.76e-7	1.17e-7	2.09e-8	
150	2.53e-6	2.69e-6	2.71e-6	2.69e-6	2.49e-6	1.69e-6	4.74e-7	9.04e-8	
170	1.03E-5	1.02E-5	1.10E-5	1.14E-5	9.98E-6	6.82E-6	2.45E-6	6.30E-7	
200	3.17E-5	3.35E-5	3.46E-5	3.71E-5	3.17E-5	2.65E-5	1.05E-5	3.05E-6	3.11E-8
250	8.64E-5	8.36E-5	9.33E-5	1.01E-4	9.90E-4	8.17E-5	4.18E-5	1.47E-5	2.45E-7
300	1.46E-4	1.48E-4	1.62E-4	1.81E-4	1.79E-4	1.68E-4	1.02E-4	4.41E-5	1.34E-6
350	2.10E-4	2.03E-4	2.28E-4	2.49E-4	2.68E-4	2.66E-4	1.89E-4	1.07E-4	4.68E-6
400	2.53E-4	2.60E-4	2.83E-4	3.31E-4	3.59E-4	3.80E-4	3.31E-4	1.86E-4	1.18E-5
500	3.46E-4	3.57E-4	3.96E-4	4.49E-4	5.08E-4	5.92E-4	6.19E-4	4.61E-4	4.58E-5
600	3.96E-4	4.24E-4	4.75E-4	5.52E-4	6.34E-4	7.82E-4	9.41E-4	8.11E-4	1.15E-4
700	4.56E-4	4.81E-4	5.28E-4	6.20E-4	7.35E-4	9.48E-4	1.20E-3	1.15E-3	2.15E-4
1000	5.38E-4	5.61E-4	6.15E-4	7.64E-4	9.64E-4	1.29E-3	1.86E-3	1.91E-3	5.80E-4
1400	5.63E-4	5.80E-4	6.50E-4	8.57E-4	1.09E-3	1.52E-3	2.27E-3	2.50E-3	1.10E-3
2000	5.35E-4	5.54E-4	6.44E-4	8.32E-4	1.11E-3	1.60E-3	2.42E-3	2.82E-3	1.70E-3
5000	3.57E-4	3.77E-4	4.47E-4	6.34E-4	8.76E-4	1.25E-3	2.00E-3	2.57E-3	2.55E-3
10000	2.09E-4	2.32E-4	2.88E-4	4.06E-4	5.61E-4	8.55E-4	1.45E-3	1.90E-3	2.34E-3
20000	1.04E-4	1.19E-4	1.56E-4	2.26E-4	3.15E-4	4.89E-4	8.64E-4	1.23E-3	1.73E-3
50000	3.28E-5	3.71E-5	5.19E-5	8.46E-5	1.25E-4	1.86E-4	3.60E-4	5.48E-4	9.08E-4

He -> W

Particle reflection coefficient of He backscattered from W
 z1 = 2, m1 = 4.00, z2 = 74, m2 = 183.85, esb = 8.68 eV, rho = 19.29 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdcel = kdcec = 3, ipot = ipotr = 1 (KrC)
 program: trvmc
 ne = 24, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	8.09E-1	8.21E-1	8.48E-1	8.93E-1	9.30E-1	9.70E-1	9.96E-1	1.00E+0	1.00E+0
20	7.49E-1	7.59E-1	7.93E-1	8.47E-1	8.95E-1	9.48E-1	9.91E-1	9.99E-1	1.00E+0
50	6.80E-1	6.88E-1	7.19E-1	7.75E-1	8.31E-1	8.99E-1	9.74E-1	9.96E-1	1.00E+0
100	6.37E-1	6.47E-1	6.76E-1	7.28E-1	7.79E-1	8.50E-1	9.46E-1	9.88E-1	1.00E+0
125	6.24E-1	6.34E-1	6.63E-1	7.14E-1	7.64E-1	8.34E-1	9.34E-1	9.84E-1	1.00E+0
130	6.22E-1	6.31E-1	6.61E-1	7.12E-1	7.62E-1	8.31E-1	9.32E-1	9.83E-1	1.00E+0
140	6.18E-1	6.27E-1	6.57E-1	7.07E-1	7.57E-1	8.26E-1	9.28E-1	9.80E-1	1.00E+0
150	6.14E-1	6.24E-1	6.52E-1	7.04E-1	7.53E-1	8.21E-1	9.23E-1	9.78E-1	1.00E+0
170	6.07E-1	6.18E-1	6.46E-1	6.96E-1	7.45E-1	8.12E-1	9.15E-1	9.74E-1	1.00E+0
200	5.98E-1	6.07E-1	6.36E-1	6.86E-1	7.35E-1	8.01E-1	9.04E-1	9.68E-1	1.00E+0
250	5.88E-1	5.97E-1	6.26E-1	6.76E-1	7.22E-1	7.87E-1	8.89E-1	9.58E-1	9.99E-1
300	5.78E-1	5.87E-1	6.17E-1	6.65E-1	7.13E-1	7.75E-1	8.74E-1	9.49E-1	9.99E-1
350	5.71E-1	5.82E-1	6.10E-1	6.58E-1	7.03E-1	7.65E-1	8.64E-1	9.39E-1	9.98E-1
400	5.64E-1	5.73E-1	6.01E-1	6.51E-1	6.97E-1	7.57E-1	8.52E-1	9.31E-1	9.97E-1
500	5.51E-1	5.63E-1	5.90E-1	6.38E-1	6.85E-1	7.45E-1	8.37E-1	9.15E-1	9.95E-1
600	5.43E-1	5.54E-1	5.83E-1	6.33E-1	6.75E-1	7.35E-1	8.23E-1	9.02E-1	9.93E-1
700	5.35E-1	5.43E-1	5.75E-1	6.25E-1	6.67E-1	7.25E-1	8.14E-1	8.90E-1	9.90E-1
1000	5.14E-1	5.23E-1	5.55E-1	6.02E-1	6.49E-1	7.07E-1	7.91E-1	8.62E-1	9.80E-1
1400	4.92E-1	5.02E-1	5.33E-1	5.86E-1	6.30E-1	6.89E-1	7.69E-1	8.38E-1	9.64E-1
2000	4.68E-1	4.80E-1	5.09E-1	5.61E-1	6.11E-1	6.71E-1	7.52E-1	8.14E-1	9.41E-1
5000	3.94E-1	4.06E-1	4.42E-1	4.98E-1	5.50E-1	6.18E-1	7.00E-1	7.57E-1	8.66E-1
10000	3.26E-1	3.41E-1	3.76E-1	4.37E-1	4.94E-1	5.67E-1	6.55E-1	7.17E-1	8.16E-1
20000	2.49E-1	2.63E-1	3.02E-1	3.67E-1	4.31E-1	5.08E-1	6.10E-1	6.75E-1	7.69E-1
50000	1.43E-1	1.54E-1	1.92E-1	2.59E-1	3.28E-1	4.20E-1	5.39E-1	6.12E-1	7.18E-1

Energy reflection coefficient of He backscattered from W
 ne = 24, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	5.95E-1	6.14E-1	6.58E-1	7.35E-1	8.03E-1	8.86E-1	9.62E-1	9.84E-1	9.95E-1
20	5.28E-1	5.43E-1	5.90E-1	6.74E-1	7.53E-1	8.51E-1	9.50E-1	9.81E-1	9.94E-1
50	4.52E-1	4.63E-1	5.03E-1	5.81E-1	6.63E-1	7.76E-1	9.17E-1	9.72E-1	9.93E-1
100	4.07E-1	4.19E-1	4.54E-1	5.21E-1	5.94E-1	7.02E-1	8.68E-1	9.53E-1	9.92E-1
125	3.94E-1	4.05E-1	4.39E-1	5.04E-1	5.73E-1	6.78E-1	8.47E-1	9.44E-1	9.91E-1
130	3.92E-1	4.03E-1	4.37E-1	5.01E-1	5.69E-1	6.74E-1	8.44E-1	9.42E-1	9.91E-1
140	3.88E-1	3.99E-1	4.32E-1	4.95E-1	5.63E-1	6.66E-1	8.36E-1	9.38E-1	9.90E-1
150	3.85E-1	3.95E-1	4.28E-1	4.91E-1	5.57E-1	6.59E-1	8.29E-1	9.34E-1	9.90E-1
170	3.78E-1	3.89E-1	4.21E-1	4.82E-1	5.47E-1	6.46E-1	8.16E-1	9.26E-1	9.90E-1
200	3.70E-1	3.80E-1	4.12E-1	4.72E-1	5.34E-1	6.31E-1	7.98E-1	9.15E-1	9.89E-1
250	3.60E-1	3.69E-1	4.00E-1	4.58E-1	5.18E-1	6.10E-1	7.73E-1	8.97E-1	9.87E-1
300	3.51E-1	3.60E-1	3.91E-1	4.47E-1	5.06E-1	5.93E-1	7.51E-1	8.80E-1	9.85E-1
350	3.43E-1	3.54E-1	3.83E-1	4.39E-1	4.95E-1	5.81E-1	7.35E-1	8.65E-1	9.83E-1
400	3.37E-1	3.46E-1	3.76E-1	4.30E-1	4.88E-1	5.70E-1	7.18E-1	8.51E-1	9.81E-1
500	3.27E-1	3.37E-1	3.65E-1	4.18E-1	4.74E-1	5.54E-1	6.94E-1	8.25E-1	9.76E-1
600	3.18E-1	3.29E-1	3.57E-1	4.12E-1	4.62E-1	5.41E-1	6.74E-1	8.03E-1	9.71E-1
700	3.12E-1	3.20E-1	3.50E-1	4.04E-1	4.53E-1	5.30E-1	6.60E-1	7.85E-1	9.65E-1
1000	2.95E-1	3.03E-1	3.33E-1	3.83E-1	4.34E-1	5.07E-1	6.27E-1	7.42E-1	9.45E-1
1400	2.77E-1	2.86E-1	3.14E-1	3.66E-1	4.15E-1	4.86E-1	5.99E-1	7.05E-1	9.17E-1
2000	2.58E-1	2.68E-1	2.94E-1	3.44E-1	3.96E-1	4.66E-1	5.74E-1	6.69E-1	8.79E-1
5000	2.02E-1	2.11E-1	2.39E-1	2.88E-1	3.37E-1	4.08E-1	5.11E-1	5.91E-1	7.63E-1
10000	1.55E-1	1.64E-1	1.88E-1	2.37E-1	2.86E-1	3.57E-1	4.59E-1	5.41E-1	6.85E-1
20000	1.07E-1	1.14E-1	1.38E-1	1.81E-1	2.29E-1	2.98E-1	4.04E-1	4.85E-1	6.19E-1
50000	5.14E-2	5.62E-2	7.27E-2	1.07E-1	1.48E-1	2.13E-1	3.19E-1	4.02E-1	5.38E-1

Average depth (mean range) in Å of He implanted in W
 ne=24, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	9.20E+0	9.20E+0	9.10E4-0	9.10E+0	9.00E4-0	9.00E+0	8.70E-J-0	8.80E+0	8.70E+0
20	1.24E+1	1.24E+1	1.23E+1	1.23E+1	1.22E+1	1.21E4-1	1.19E+1	1.17E+1	1.22E+1
50	1.90E+1	1.92E+1	1.90E+1	1.88E+1	1.86E+1	1.85E+1	1.83E-J-1	1.81E+1	1.62E+1
100	2.69E4-1	2.69E4-1	2.67E+1	2.65E4-1	2.61E+1	2.61E+1	2.60E+1	2.53E+1	2.55E+1
125	3.02E+1	3.02E+1	2.99E+1	2.96E-H	2.93E4-1	2.91E+1	2.88E+1	2.85E+1	2.72E+1
130	3.09E4-1	3.08E+1	3.05E+1	3.02E+1	2.99E+1	2.96E4-1	2.94E-H	2.93E+1	3.06E+1
140	3.21E-J-1	3.20E+1	3.17E+1	3.13E+1	3.11E+1	3.08E+1	3.05E+1	3.03E+1	3.25E+1
150	3.32E+1	3.31E+1	3.29E+1	3.24E+1	3.22E+1	3.19E+1	3.16E+1	3.14E+1	3.05E+1
170	3.55E+1	3.54E+1	3.51E+1	3.46E4-1	3.43E+1	3.40E+1	3.37E+1	3.34E4-1	3.65E-J-1
200	3.85E4-1	3.84E+1	3.81E+1	3.75E4-1	3.72E4-1	3.69E+1	3.66E+1	3.64E+1	3.59E+1
250	4.35E+1	4.34E+1	4.29E+1	4.24E+1	4.18E+1	4.15E+1	4.12E+1	4.10E+1	4.04E+1
300	4.81E+1	4.77E-J-1	4.74E4-1	4.66E4-1	4.62E-J-1	4.58E+1	4.53E+1	4.51E+1	4.45E+1
350	5.22E+1	5.20E+1	5.14E+1	5.09E-H	5.00E+1	4.96E+1	4.94E+1	4.89E+1	4.79E+1
400	5.62E+1	5.58E+1	5.54E+1	5.46E+1	5.39E-J-1	5.32E+1	5.28E4-1	5.28E4-1	5.24E+1
500	6.36E+1	6.34E+1	6.26E+1	6.20E+1	6.10E+1	6.05E+1	5.95E+1	5.93E-H	5.89E+1
600	7.06E+1	7.03E+1	6.94E+1	6.84E4-1	6.74E+1	6.71E+1	6.59E-H	6.57E+1	6.57E+1
700	7.71E4-1	7.69E+1	7.59E-J-1	7.47E-H	7.39E+1	7.29E+1	7.22E+1	7.19E+1	7.17E+1
1000	9.53E+1	9.47E-J-1	9.34E+1	9.17E+1	9.07E+1	8.93E+1	8.81E+1	8.76E-J-1	8.84E+1
1400	1.16E+2	1.16E+2	1.15E+2	1.12E+2	1.11E+2	1.09E+2	1.07E+2	1.08E+2	1.07E+2
2000	1.46E-J-2	1.46E+2	1.43E+2	1.40E+2	1.37E+2	1.35E+2	1.34E+2	1.33E+2	1.33E+2
5000	2.69E+2	2.67E-J-2	2.63E+2	2.55E+2	2.49E+2	2.44E+2	2.39E+2	2.37E+2	2.37E+2
10000	4.44E+2	4.40E+2	4.29E+2	4.12E+2	4.02E+2	3.89E+2	3.81E+2	3.79E+2	3.75E+2
20000	7.54E+2	7.45E+2	7.20E+2	6.87E+2	6.59E+2	6.33E-J-2	6.15E4-2	6.06E+2	6.01E+2
50000	1.58E+3	1.55E+3	1.47E+3	1.37E+3	1.28E+3	1.21E+3	1.15E+3	1.12E+3	1.11E+3

C → W

Sputtering yield of W by C

z1 = 6, m1 = 12.01, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.30 g/cm**3
 ef = 3.95 eV, esb = 4.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdec2 = 3, ipot = ipotr = 1 (KrC)
 program : testvmcx
 only low fluence!
 ne = 11, na = 1

E ₀ (eV)	0°	comment
55	4.77e-5	ef=0.95, esb = 1.00 eV
60	2.68e-4	ef=0.95, esb = 1.00 eV
70	2.25e-3	
100	1.23e-2	
200	6.24e-2	
500	1.66e-1	
1000	2.67e-1	
2000	3.68E-1	
5000	4.54e-1	
10000	5.02e-1	
40000	4.06e-1	ef=1.00, esb = 1.00 eV

Sputtered energy of W by C

only low fluence!
 ne = 11, na = 1

E ₀ (eV)	0°	comment
55	5.49e-7	ef=0.95, esb = 1.00 eV
60	4.59e-6	ef=0.95, esb = 1.00 eV
70	6.75e-5	
100	5.02e-4	
200	2.69e-3	
500	5.36e-3	
1000	6.08e-3	
2000	5.76E-3	
5000	4.16e-3	
10000	2.78e-3	
40000	8.53e-4	ef=1.00, esb=1.00 eV

C -> W

Particle reflection coefficient of C backscattered from W
 $z1 = 6$, $m1 = 12.01$, $z2 = 74$, $m2 = 183.85$, $sbe = 8.68$ eV, $\rho = 19.30$ g/cm**3
 $ef = 3.95$ eV, $esb = 4.00$ eV, $ca = 1.00$, $kk0 = kk0r = 2$, $kdee1 = kdee2 = 3$, $ipot = ipotr = 1$ (KrC)
 program : testvmcx
 only low fluence!
 $ne = 11$, $na = 1$

E_0 (eV)	0°	comment
55	6.23e-1	ef=0.95, esb = 1.00 eV
60	6.16e-1	ef=0.95, esb = 1.00 eV
70	5.81e-1	
100	5.61e-1	
200	5.25e-1	
500	4.77e-1	
1000	4.52e-1	
2000	4.22E-1	
5000	3.65e-1	
10000	3.27e-1	
40000	2.16e-1	ef=1.00, esb = 1.00 eV

Energy reflection coefficient of C backscattered from W
 only low fluence!
 $ne = 11$, $na = 1$

E_0 (eV)	0°	comment
55	3.55e-1	ef=0.95, esb = 1.00 eV
60	3.50e-1	ef=0.95, esb = 1.00 eV
70	3.28e-1	
100	3.10e-1	
200	2.79e-1	
500	2.40e-1	
1000	2.23e-1	
2000	2.02E-1	
5000	1.68e-1	
10000	1.45e-1	
40000	8.68e-2	ef=1.00, esb = 1.00 eV

Average depth (mean range) in Å of C implanted in W
 only low fluence!
 $ne = 11$, $na = 1$

E_0 (eV)	0°	comment
55	9.11e+0	ef=0.95, esb = 1.00 eV
60	9.50e+0	ef=0.95, esb = 1.00 eV
70	1.01e+1	
100	1.21e+1	
200	1.72e+1	
500	2.82e+1	
1000	4.14e+1	
2000	6.12E+1	
5000	1.10e+2	
10000	1.73e+2	
40000	5.00e+2	ef=1.00, esb = 1.00 eV

C on W, Maxwellian velocity distribution, sheath potential 9 kT
 $z1 = 6$, $m1 = 12.01$, $z2 = 74$, $m2 = 183.85$, $sbe = 8.68$ eV, $\rho = 19.29$ g/cm**3
 $ef = 0.98$ eV, $esb = 1.00$ eV, $ca = 1.00$, $kk0 = kk0r = 2$, $kdee1 = kdee2 = 3$, $ipot = ipotr = 1$ (KrC)
 program: trvmc
 only low fluence!
 $ne = 4$

kT(eV)	Y	Y _m	E _s p	Rat	R _m	E _b	range
5	2.45e-4	8.40e-6	1.88e+0	6.50e-1	3.83e-1	3.24e+1	9.23e+0
10	1.59e-2	7.08e-4	4.90e+0	5.92e-1	3.33e-1	6.19e+1	1.29e-H
20	7.19e-2	3.10e-3	9.49e+0	5.45e-1	2.94e-1	1.19e+2	1.82e+1
40	1.61e-1	5.52e-3	1.51e+1	5.07e-1	2.62e-1	2.28e+2	2.61e+1

N -> W

Sputtering yield of W by N

z1 = 7. m1 = 14.01. z2 = 74. m2 = 183.85. sbe = 8.68 eV. rho = 19.29 g/cm**3
 ef = 0.98 eV. esb = 1.00 eV. ca = 1.00. kk0 = kk0r = 2. kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrG)
 program: trvnc
 ne = 22, na = 9

Eo(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
47	9.30e-6	7.00e-6							
48	1.82E-5	1.60E-5	1.20E-5	5.70E-6	2.30E-6				
50	5.70E-5	5.25E-5	3.93E-5	2.11E-5	1.07E-5	2.85E-6			
52	1.35E-4	1.28E-4	9.18E-5	5.06E-5	2.86E-5	9.30E-6			
55	3.60E-4	3.30E-4	2.56E-4	1.52E-4	8.47E-5	2.75E-5	3.08E-6		
60	9.73E-4	9.57E-4	7.55E-4	4.74E-4	2.76E-4	1.08E-4	1.52E-5	2.20E-6	
70	3.26E-3	3.26E-3	2.84E-3	2.02E-3	1.31E-3	5.87E-4	1.08E-4	1.98E-5	1.50E-6
80	7.00E-3	6.70E-3	6.06E-3	4.61E-3	3.18E-3	1.61E-3	3.52E-4	7.13E-5	6.20E-6
90	1.17E-2	1.14E-2	1.06E-2	8.58E-3	6.13E-3	3.36E-3	8.56E-4	2.12E-4	1.76E-5
100	1.72E-2	1.70E-2	1.60E-2	1.30E-2	1.03E-2	6.07E-3	1.78E-3	4.90E-4	4.29E-5
120	2.77E-2	2.79E-2	2.82E-2	2.53E-2	2.17E-2	1.43E-2	5.43E-3	1.70E-3	1.23E-4
140	3.99E-2	4.07E-2	4.14E-2	4.06E-2	3.50E-2	2.65E-2	1.14E-2	3.67E-3	2.47E-4
200	7.57E-2	8.00E-2	8.32E-2	8.70E-2	9.07E-2	7.77E-2	4.11E-2	1.50E-2	8.58E-4
300	1.32E-1	1.35E-1	1.48E-1	1.71E-1	1.85E-1	1.80E-1	1.15E-1	4.56E-2	2.65E-3
500	2.13E-1	2.21E-1	2.52E-1	3.10E-1	3.51E-1	3.68E-1	2.66E-1	1.26E-1	8.67E-3
1000	3.39E-1	3.58E-1	4.22E-1	5.35E-1	6.24E-1	6.89E-1	5.80E-1	3.49E-1	4.00E-2
2000	4.69e-1								
3000	5.40e-1								
5000	6.05e-1								
10000	6.54e-1								
20000	6.18e-1								
50000	5.30e-1								

Sputtered energy of W by N

ne = 22, na = 9

Eo(eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
47	9.95e-8	7.47e-8							
48	2.19e-7	2.10e-7	1.92e-7	8.93e-8	4.20e-8				
50	8.42e-7	8.26e-7	6.77e-7	3.68e-7	1.82e-7	4.76e-8			
52	2.44E-6	2.31E-6	1.73E-6	1.00E-6	5.63e-7	1.87E-7			
55	7.80E-6	7.08E-6	5.73E-6	3.39E-6	1.85E-6	5.84E-7	6.31E-8		
60	2.61E-5	2.56E-5	2.10E-5	1.33E-5	7.59E-6	2.81E-6	3.75E-7	5.17E-8	
70	1.16E-4	1.16E-4	1.03E-4	7.42E-5	4.59E-5	1.97E-5	3.52E-6	6.60E-7	5.65E-8
80	2.85E-4	2.74E-4	2.52E-4	1.93E-4	1.32E-4	6.64E-5	1.39E-5	2.82E-6	3.05E-7
90	5.22E-4	5.06E-4	4.88E-4	3.93E-4	2.86E-4	1.56E-4	3.69E-5	9.32E-6	8.21E-7
100	7.88E-4	7.97E-4	7.61E-4	6.10E-4	5.13E-4	3.05E-4	8.38E-5	2.38E-5	2.27E-6
120	1.35E-3	1.35E-3	1.40E-3	1.30E-3	1.13E-3	7.54E-4	2.93E-4	9.69E-5	7.37E-6
140	1.92E-3	1.98E-3	2.10E-3	2.11E-3	1.89E-3	1.47E-3	6.53E-4	2.27E-4	1.59E-5
200	3.56E-3	3.78E-3	4.01E-3	4.41E-3	4.74E-3	4.30E-3	2.61E-3	1.04E-3	6.16E-5
300	5.49E-3	5.78E-3	6.39E-3	7.63E-3	8.72E-3	9.35E-3	7.08E-3	3.12E-3	1.94E-4
500	7.36E-3	7.71E-3	8.78E-3	1.15E-2	1.38E-2	1.63E-2	1.42E-2	7.70E-3	5.65E-4
1000	8.26E-3	8.76E-3	1.04E-2	1.40E-2	1.77E-2	2.21E-2	2.24E-2	1.55E-2	2.06E-3
2000	7.47e-3								
3000	6.94e-3								
5000	5.74e-3								
10000	3.92e-3								
20000	2.42e-3								
50000	1.06e-3								

N → W

Particle reflection coefficient of N backscattered from W
 z1= 7. ml= 14.01. z2= 74. m2= 183.85. sbe= 8.68 eV. rho=19.29 g/cm**3
 ef=0.98 eV. esb=1.00 eV. ca=1.00. kk0=kk0r=2. kdeel = kdec2 = 3. ipot=ipot = 1 (KrC)
 program: trvmc
 ne=25. na=9

Eq (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	7.68E-1	7.83E-1	8.14E-1	8.62E-1	9.01E-1	9.43E-1	9.74E-1	9.84E-1	9.88E-1
20	7.17E-1	7.34E-1	7.73E-1	8.36E-1	8.85E-1	9.39E-1	9.80E-1	9.91E-1	9.96E-1
40	6.52E-1	6.68E-1	7.13E-1	7.87E-1	8.50E-1	9.19E-1	9.78 E-1	9.93E-1	9.99E-1
47	6.37e-1	6.53e-1							
48	6.35E-1	6.51E-1	6.95E-1	7.72E-1	8.38E-1	9.12E-1	9.76E-1	9.93E-1	9.99E-1
50	6.31E-1	6.47E-1	6.92E-1	7.68E-1	8.35E-1	9.10E-1	9.76E-1	9.93E-1	9.99E-1
52	6.28E-1	6.43E-1	6.88E-1	7.65E-1	8.32E-1	9.08E-1	9.75E-1	9.93E-1	9.99E-1
55	6.22E-1	6.38E-1	6.83E-1	7.60E-1	8.28E-1	9.05E-1	9.74E-1	9.93E-1	9.99E-1
60	6.14E-1	6.30E-1	6.75E-1	7.52E-1	8.21E-1	9.01E-1	9.73E-1	9.93E-1	9.99E-1
70	6.00E-1	6.15E-1	6.61E-1	7.39E-1	8.09E-1	8.92E-1	9.70E-1	9.92E-1	9.99E-1
80	5.90E-1	6.04E-1	6.49E-1	7.27E-1	7.98E-1	8.84E-1	9.67E-1	9.92E-1	9.99E-1
90	5.83E-1	5.96E-1	6.39E-1	7.15E-1	7.88E-1	8.76E-1	9.64E-1	9.91E-1	9.99E-1
100	5.68E-1	5.88E-1	6.31E-1	7.08E-1	7.78E-1	8.70E-1	9.61E-1	9.91E-1	9.99E-1
120	5.58E-1	5.72E-1	6.16E-1	6.89E-1	7.63E-1	8.58E-1	9.56E-1	9.89E-1	9.99E-1
140	5.45E-1	5.61E-1	6.04E-1	6.78E-1	7.48E-1	8.45E-1	9.50E-1	9.88E-1	9.99E-1
200	5.25E-1	5.35E-1	5.77E-1	6.48E-1	7.19E-1	8.15E-1	9.32E-1	9.82E-1	9.99E-1
300	4.99E-1	5.11E-1	5.52E-1	6.19E-1	6.85 E-1	7.77E-1	9.09E-1	9.73E-1	9.99E-1
500	4.72E-1	4.82E-1	5.18E-1	5.84E-1	6.48E-1	7.36E-1	8.70E-1	9.54E-1	9.98E-1
1000	4.38E-1	4.51E-1	4.84E-1	5.44E-1	6.09E-1	6.82E-1	8.10E-1	9.10E-1	9.94E-1
2000	4.11e-1								
3000	3.79e-1								
5000	3.55e-1								
10000	3.18e-1								
20000	2.67e-1								
50000	2.03e-1								

Energy reflection coefficient of N backscattered from W
 ne=25. na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	4.40E-1	4.60E-1	5.04E-1	5.78E-1	6.48E-1	7.32E-1	8.13E-1	8.43E-1	8.62E-1
20	4.14E-1	4.35E-1	4.86E-1	5.75E-1	6.55E-1	7.55E-1	8.58E-1	8.97E-1	9.21E-1
40	3.66E-1	3.85E-1	4.38E-1	5.35E-1	6.27E-1	7.43E-1	8.71E-1	9.22E-1	9.52E-1
47	3.55e-1	3.72e-1							
48	3.53E-1	3.71E-1	4.23E-1	5.20E-1	6.15E-1	7.35E-1	8.71E-1	9.26E-1	9.58 E-1
50	3.50E-1	3.68E-1	4.19E-1	5.17E-1	6.12E-1	7.33E-1	8.70 E-1	9.26E-1	9.59E-1
52	3.47E-1	3.65E-1	4.16E-1	5.13E-1	6.09E-1	7.31 E-1	8.70E-1	9.26E-1	9.60E-1
55	3.43E-1	3.60E-1	4.12E-1	5.09E-1	6.04E-1	7.28E-1	8.69E-1	9.28E-1	9.61E-1
60	3.37E-1	3.54E-1	4.04E-1	5.01E-1	5.97E-1	7.23E-1	8.68E-1	9.28E-1	9.63E-1
70	3.26E-1	3.42E-1	3.92E-1	4.87E-1	5.84E-1	7.12E-1	8.65E-1	9.29E-1	9.66E-1
80	3.18E-1	3.33E-1	3.81E-1	4.75E-1	5.72E-1	7.03E-1	8.61E-1	9.29E-1	9.68E-1
90	3.11E-1	3.25E-1	3.72E-1	4.63E-1	5.61E-1	6.93E-1	8.57E-1	9.29E-1	9.70E-1
100	3.03E-1	3.18E-1	3.65E-1	4.55E-1	5.49E-1	6.85E-1	8.53E-1	9.28E-1	9.72E-1
120	2.92E-1	3.07E-1	3.51E-1	4.37E-1	5.32E-1	6.69E-1	8.44E-1	9.26E-1	9.74E-1
140	2.84E-1	2.97E-1	3.41E-1	4.23E-1	5.16E-1	6.54E-1	8.36E-1	9.24E-1	9.75E-1
200	2.68E-1	2.78E-1	3.17E-1	3.95E-1	4.81E-1	6.15E-1	8.10E-1	9.15E-1	9.77E-1
300	2.49E-1	2.59E-1	2.96E-1	3.65E-1	4.43E-1	5.69E-1	7.74E-1	8.98E-1	9.77E-1
500	2.29E-1	2.38E-1	2.69E-1	3.33E-1	4.02E-1	5.17E-1	7.18E-1	8.66E-1	9.75E-1
1000	2.07E-1	2.16E-1	2.45E-1	3.00E-1	3.62E-1	4.53E-1	6.34E-1	7.95E-1	9.64E-1
2000	1.89e-1								
3000	1.72e-1								
5000	1.56e-1								
10000	1.36e-1								
20000	1.10e-1								
50000	7.70e-2								

N - >> W

Average depth (mean range) in Å of N implanted in W
 z1 = 7. ml = 14.01, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.29 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvmc
 ne = 25, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	3.80E+0	3.80E+0	3.80E4-0	3.70E4-0	3.70E+0	3.60E+0	3.50E4-0	3.50E+0	3.40E4-0
20	5.30E4-0	5.30E+0	5.20E+0	5.20E+0	5.10E+0	5.00E+0	4.90E+0	4.80E4-0	4.70E+0
40	7.20E+0	7.20E+0	7.20E4-0	7.10E+0	7.00E4-0	6.80E4-0	6.60E4-0	6.50E4-0	6.50E+0
47	7.81e+0	7.78e+0							
48	7.90E+0	7.90E+0	7.80E+0	7.70E+0	7.60E+0	7.40E4-0	7.20E+0	7.10E+0	7.00E+0
50	8.00E4-0	8.00E4-0	7.90E+0	7.80E+0	7.70E+0	7.60E4-0	7.40E4-0	7.20E4-0	6.90E4-0
52	8.20E+0	8.20E+0	8.10E+0	8.00E4-0	7.90E+0	7.70E+0	7.40E+0	7.50E+0	7.30E4-0
55	8.40E4-0	8.40E4-0	8.30E4-0	8.20E+0	8.10E+0	7.90E+0	7.70E+0	7.60E4-0	7.30E+0
60	8.70E4-0	8.70E4-0	8.60E4-0	8.50E+0	8.40E+0	8.20E+0	8.00E+0	7.90E+0	7.50E+0
70	9.40E4-0	9.40E+0	9.30E4-0	9.10E+0	9.00E4-0	8.90E4-0	8.60E+0	8.40E+0	8.30E+0
80	1.00E+1	1.00E+1	9.90E+0	9.70E+0	9.60E4-0	9.40E4-0	9.20E+0	9.00E+0	8.80E4-0
90	1.06E+1	1.06E+1	1.04E+1	1.02E+1	1.01E+1	1.00E+1	9.70E+0	9.40E+0	9.40E+0
100	1.12E4-1	1.11E4-1	1.10E+1	1.08E+1	1.06E+1	1.04E+1	1.02E+1	1.00E+1	9.70E4-0
120	1.22E+1	1.22E4-1	1.20E+1	1.18E+1	1.16E+1	1.14E4-1	1.11E+1	1.09E+1	1.08E+1
140	1.32E+1	1.31E+1	1.30E+1	1.27E+1	1.24E+1	1.23E+1	1.19E+1	1.18E+1	1.15E4-1
200	1.57E+1	1.57E+1	1.55E+1	1.51E+1	1.48E+1	1.45E+1	1.41E+1	1.40E+1	1.37E+1
300	1.92E+1	1.91E+1	1.90E+1	1.84E+1	1.82E+1	1.77E+1	1.74E+1	1.71E+1	1.63E+1
500	2.50E+1	2.50E+1	2.47E4-1	2.41E+1	2.34E+1	2.32E+1	2.26E+1	2.24E+1	2.16E4-1
1000	3.67E+1	3.65E+1	3.57E+1	3.45E4-1	3.38E+1	3.31E4-1	3.23E+1	3.23E+1	3.18E4-1
2000	5.41e+1								
3000	6.88e+1								
5000	9.41e+1								
10000	1.53e+2								
20000	2.53e4-2								
50000	5.15e4-2								

O -> W

Sputtering yield of W by O

z1 = 8, m1 = 16.00, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.30 g/cm**3
 ef = 0.95 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: TPP 9/82
 only low fluence!
 ne = 9, na = 1

E ₀ (eV)	0°
50	3.63e-4
100	2.17e-2
200	9.00e-2
300	1.52e-1
500	2.45e-1
1000	3.71e-1
2000	5.33e-1
5000	6.89e-1
6000	7.64e-1

Ne W

Sputtering yield of W by Ne

z1 = 10, m1 = 20.18, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.29 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvme
 ne = 14, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
40	9.80E-6	7.70E-6	4.40E-6	1.80E-6	2.00E-6				
45	1.64E-4	1.37E-4	1.01E-4	4.66E-5	2.21E-5	4.88E-6			
50	7.38E-4	6.43E-4	4.83E-4	2.82E-4	1.44E-4	4.22E-5	2.52E-6		
60	3.61E-3	3.30E-3	2.74E-3	1.78E-3	1.09E-3	4.35E-4	5.33E-5	5.00E-6	
70	8.44E-3	8.11E-3	7.47E-3	5.27E-3	3.45E-3	1.69E-3	2.95E-4	4.46E-5	
80	1.58E-2	1.48E-2	1.41E-2	1.05E-2	7.52E-3	4.17E-3	9.51E-4	1.79E-4	
100	3.15E-2	3.13E-2	3.07E-2	2.59E-2	2.11E-2	1.40E-2	4.70E-3	8.37E-4	5.15E-6
140	6.97E-2	6.94E-2	7.15E-2	7.05E-2	6.58E-2	5.08E-2	2.06E-2	4.65E-3	3.58E-5
200	1.23E-1	1.29E-1	1.39E-1	1.50E-1	1.53E-1	1.33E-1	6.38E-2	1.72E-2	1.93E-4
300	2.02E-1	2.14E-1	2.38E-1	2.77E-1	2.91E-1	2.75E-1	1.46E-1	5.07E-2	8.85E-4
400	2.67E-1	2.82E-1	3.22E-1	3.88E-1	4.30E-1	4.11E-1	2.39E-1	9.32E-2	2.23E-3
500	3.24E-1	3.45E-1	4.00E-1	4.88E-1	5.41E-1	5.35E-1	3.37E-1	1.39E-1	4.54E-3
700	4.25E-1	4.44E-1	5.14E-1	6.38E-1	7.16E-1	7.37E-1	5.06E-1	2.38E-1	1.23E-2
1000	5.33E-1	5.62E-1	6.66E-1	8.18E-1	9.43E-1	9.76E-1	7.53E-1	3.99E-1	2.98E-2

Sputtered energy of W by Ne

ne = 22, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
40	1.81e-7	1.58e-7	9.73e-8	4.89e-8	1.06e-7				
45	4.44e-6	3.82e-6	3.06e-6	1.41e-6	6.32e-7	1.37e-7			
50	2.59E-5	2.26E-5	1.79E-5	1.07E-5	5.34E-6	1.54E-6	1.21E-7		
60	1.63E-4	1.53E-4	1.29E-4	8.42E-5	5.03E-5	2.14E-5	2.91E-6	3.16E-7	
70	4.42E-4	4.29E-4	4.09E-4	2.92E-4	1.97E-4	9.88E-5	1.85E-5	3.05E-6	
80	8.87E-4	8.80E-4	8.36E-4	6.35E-4	4.66E-4	2.66E-4	6.30E-5	1.30E-5	
100	1.91E-3	1.92E-3	1.95E-3	1.70E-3	1.48E-3	9.78E-4	3.65E-4	7.09E-5	3.81E-7
140	4.12E-3	4.20E-3	4.44E-3	4.68E-3	4.58E-3	3.83E-3	1.77E-3	4.35E-4	2.90E-6
200	6.81E-3	7.39E-3	8.15E-3	9.36E-3	1.02E-2	9.88E-3	5.63E-3	1.64E-3	1.62E-5
300	9.82E-3	1.04E-2	1.18E-2	1.51E-2	1.72E-2	1.84E-2	1.21E-2	4.53E-3	7.32E-5
400	1.15E-2	1.20E-2	1.41E-2	1.87E-2	2.22E-2	2.49E-2	1.74E-2	7.62E-3	1.79E-4
500	1.26E-2	1.35E-2	1.57E-2	2.08E-2	2.57E-2	2.96E-2	2.29E-2	1.06E-2	3.18E-4
700	1.38E-2	1.43E-2	1.72E-2	2.33E-2	2.85E-2	3.42E-2	2.92E-2	1.58E-2	7.77E-4
1000	1.42E-2	1.52E-2	1.79E-2	2.43E-2	3.15E-2	3.70E-2	3.56E-2	2.18E-2	1.61E-3

Ne -> W

Particle reflection coefficient of Ne backscattered from W
 z1 = 10, m1 = 20.18, z2=74, m2 = 183.85, sbe=8.68 eV, rho = 19.29 g/cm**3
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr = 1 (KrC)
 program: trvmc
 ne=17, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	8.10E-1	8.24E-1	8.53E-1	8.97E-1	9.36E-1	9.74E-1	9.96E-1	1.00E-f-0	1.00E+0
20	7.44E-1	7.61E-1	7.98E-1	8.59E-1	9.09E-1	9.62E-1	9.95E-1	9.99E-1	1.00E+0
30	6.97E-1	7.14E-1	7.58E-1	8.28E-1	8.86E-1	9.50E-1	9.93E-1	9.99E-1	1.00E+0
40	6.62E-1	6.80E-1	7.26E-1	8.03E-1	8.67E-1	9.38E-1	9.90E-1	9.99E-1	1.00E+0
45	6.48E-1	6.66E-1	7.13E-1	7.92E-1	8.59E-1	9.32E-1	9.89E-1	9.99E-1	1.00E+0
50	6.36E-1	6.54E-1	7.01E-1	7.82E-1	8.50E-1	9.27E-1	9.88E-1	9.99E-1	1.00E+0
60	6.16E-1	6.32E-1	6.80E-1	7.63E-1	8.36E-1	9.17E-1	9.85E-1	9.98E-1	1.00E+0
70	5.99E-1	6.15E-1	6.62E-1	7.48E-1	8.23E-1	9.08E-1	9.82E-1	9.98E-1	1.00E+0
80	5.85E-1	6.02E-1	6.46E-1	7.34E-1	8.10E-1	8.99E-1	9.79E-1	9.98E-1	1.00E+0
100	5.61E-1	5.79E-1	6.25E-1	7.13E-1	7.88E-1	8.83E-1	9.74E-1	9.97E-1	1.00E-f-0
140	5.31E-1	5.44E-1	5.93E-1	6.76E-1	7.54E-1	8.58E-1	9.63E-1	9.94E-1	1.00E-f-0
200	5.02E-1	5.19E-1	5.65E-1	6.42E-1	7.17E-1	8.23E-1	9.46E-1	9.90E-1	1.00E-f-0
300	4.71E-1	4.87E-1	5.27E-1	6.07E-1	6.82E-1	7.86E-1	9.25E-1	9.82E-1	1.00E-f-0
400	4.54E-1	4.66E-1	5.15E-1	5.86E-1	6.58E-1	7.57E-1	9.05E-1	9.73E-1	1.00E-f-0
500	4.39E-1	4.56E-1	4.96E-1	5.60E-1	6.36E-1	7.38E-1	8.80E-1	9.66E-1	1.00E-f-0
700	4.22E-1	4.35E-1	4.72E-1	5.40E-1	6.05E-1	7.05E-1	8.54E-1	9.48E-1	9.99E-1
1000	4.04E-1	4.15E-1	4.52E-1	5.16E-1	5.83E-1	6.75E-1	8.16E-1	9.23E-1	9.98E-1

Energy reflection coefficient of Ne backscattered from W
 ne=17, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	4.10E-1	4.32E-1	4.80E-1	5.68E-1	6.59E-1	7.76E-1	8.97E-1	9.44E-1	9.77E-1
20	3.77E-1	3.98E-1	4.52E-1	5.48E-1	6.41E-1	7.64E-1	8.97E-1	9.49E-1	9.83E-1
30	3.48E-1	3.69E-1	4.26E-1	5.26E-1	6.23E-1	7.51E-1	8.93E-1	9.50E-1	9.85E-1
40	3.27E-1	3.47E-1	4.03E-1	5.07E-1	6.06E-1	7.37E-1	8.88E-1	9.49E-1	9.86E-1
45	3.19E-1	3.38E-1	3.94E-1	4.97E-1	5.98E-1	7.31E-1	8.86E-1	9.49E-1	9.86E-1
50	3.11E-1	3.30E-1	3.85E-1	4.89E-1	5.90E-1	7.25E-1	8.83E-1	9.48E-1	9.86E-1
60	2.98E-1	3.16E-1	3.69E-1	4.73E-1	5.77E-1	7.13E-1	8.78E-1	9.47E-1	9.87E-1
70	2.87E-1	3.04E-1	3.55E-1	4.59E-1	5.63E-1	7.02E-1	8.73E-1	9.45E-1	9.87E-1
80	2.79E-1	2.95E-1	3.43E-1	4.46E-1	5.51E-1	6.92E-1	8.67E-1	9.43E-1	9.87E-1
100	2.63E-1	2.79E-1	3.27E-1	4.26E-1	5.28E-1	6.74E-1	8.57E-1	9.40E-1	9.87E-1
140	2.45E-1	2.57E-1	3.02E-1	3.94E-1	4.93E-1	6.41E-1	8.39E-1	9.33E-1	9.86E-1
200	2.27E-1	2.39E-1	2.81E-1	3.62E-1	4.54E-1	6.02E-1	8.13E-1	9.22E-1	9.85E-1
300	2.08E-1	2.21E-1	2.56E-1	3.33E-1	4.19E-1	5.55E-1	7.80E-1	9.05E-1	9.84E-1
400	1.97E-1	2.08E-1	2.45E-1	3.12E-1	3.92E-1	5.25E-1	7.48E-1	8.87E-1	9.82E-1
500	1.89E-1	1.99E-1	2.32E-1	2.96E-1	3.75E-1	4.98E-1	7.018E-1	8.74E-1	9.80E-1
700	1.79E-1	1.88E-1	2.18E-1	2.78E-1	3.45E-1	4.65E-1	6.80E-1	8.44E-1	9.77E-1
1000	1.67E-1	1.76E-1	2.06E-1	2.63E-1	3.26E-1	4.30E-1	6.28E-1	8.05E-1	9.71E-1

Average depth (mean range) in Å of Ne implanted in W
 ne=17, na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	3.70E+0	3.60E+0	3.60E-J-0	3.60E+0	3.50E+0	3.40E+0	3.30E+0	3.20E-f-0	2.90E+0
20	4.70E+0	4.70E+0	4.60E+0	4.60E+0	4.50E-J-0	4.40E+0	4.20E+0	4.10E+0	4.00E+0
30	5.50E+0	5.40E+0	5.40E+0	5.30E+0	5.20E+0	5.10E+0	4.90E+0	4.80E+0	4.50E-f-0
40	6.10E+0	6.10E+0	6.10E+0	6.00E+0	5.90E+0	5.70E+0	5.50E+0	5.30E+0	5.10E+0
45	6.40E+0	6.40E+0	6.40E+0	6.30E+0	6.20E+0	6.00E-J-0	5.80E+0	5.40E+0	5.00E+0
50	6.70E+0	6.70E+0	6.60E+0	6.50E+0	6.40E+0	6.30E-J-0	6.00B+0	6.00E+0	5.70E+0
60	7.30E+0	7.20E+0	7.20E+0	7.00E+0	6.90E+0	6.80E+0	6.50E-1-0	6.30E+0	6.20E+0
70	7.80E+0	7.70E+0	7.60E+0	7.50E+0	7.40E+0	7.20E+0	6.90E+0	6.70E+0	5.60E+0
80	8.20E+0	8.20E+0	8.10E+0	8.00E-f-0	7.80E+0	7.60E+0	7.30E-J-0	7.10E+0	6.70E+0
100	9.10E+0	9.00E+0	8.90E+0	8.80E+0	8.60E+0	8.40E-f-0	8.10E+0	7.90E-J-0	7.70E+0
140	1.06E+1	1.05E+1	1.04E+1	1.02E+1	1.00E-f-1	9.80E+0	9.30E+0	9.10E+0	8.30E+0
200	1.26E+1	1.25E+1	1.23E+1	1.19E+1	1.16E-J-1	1.15E+1	1.12E+1	1.08E+1	1.08E-1
300	1.53E+1	1.51E+1	1.49E-J-1	1.44E+1	1.40E+1	1.38E+1	1.36E+1	1.34E+1	1.22E+1
400	1.76E+1	1.74E-J-1	1.71E+1	1.68E+1	1.62E+1	1.59E+1	1.54E-f-1	1.52E+1	1.44E+1
500	1.97E-J-1	1.96E+1	1.92E+1	1.87E-J-1	1.82E+1	1.77E-J-1	1.72E+1	1.70E+1	1.63E+1
700	2.35E+1	2.34E+1	2.30E-J-1	2.22E+1	2.16E+1	2.10E+1	2.07E+1	1.99E+1	1.90E+1
1000	2.85E+1	2.82E+1	2.74E+1	2.65E+1	2.58E-1-1	2.53E+1	2.47E+1	2.43E-J-1	2.30E+1

Ar → W

Sputtering yield of W by Ar

z1 = 18, m1 = 39.95, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.29 g/cm**3

ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrG)

program: trvmc

ne = 18, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
28	9.03e-7								
29	2.97e-6								
30	1.03e-5	1.54e-5	1.89e-5	1.39e-5	6.10e-6	2.00e-6			
35	1.17e-4	1.16e-4	1.13e-4	7.32e-5	3.97e-5	2.08e-5	4.80e-6		
40	4.63e-4	4.26e-4	3.63e-4	2.59e-4	1.70e-4	9.82e-5	3.55e-5	8.10e-6	
45	1.26e-3	1.21e-3	1.01e-3	7.35e-4	5.69e-4	3.79e-4	1.47e-4	3.07e-5	
50	2.85e-3	2.74e-3	2.41e-3	1.83e-3	1.48e-3	1.04e-3	4.24e-4	8.66e-5	1.20e-6
55	5.23e-3	5.12e-3	4.44e-3	3.73e-3	3.16e-3	2.39e-3	9.13e-4	1.85e-4	
60	8.40e-3	8.23e-3	7.65e-3	6.36e-3	5.86e-3	4.35e-3	1.72e-3	3.40e-4	2.40e-6
70	1.75e-2	1.75e-2	1.63e-2	1.51e-2	1.41e-2	1.12e-2	4.05e-3	7.82e-4	9.60e-6
80	2.86e-2	2.90e-2	2.93e-2	2.82e-2	2.57e-2	2.10e-2	7.61e-3	1.51e-3	1.39e-5
100	5.60e-2	5.54e-2	5.93e-2	6.20e-2	5.85e-2	4.78e-2	1.82e-2	4.00e-3	4.54e-5
140	1.16e-1	1.19e-1	1.33e-1	1.50e-1	1.49e-1	1.22e-1	5.03e-2	1.22e-2	1.68e-4
200	2.01e-1	2.13e-1	2.50e-1	2.91e-1	2.98e-1	2.50e-1	1.11e-1	3.11e-2	5.67e-4
300	3.36e-1	3.59e-1	4.23e-1	5.08e-1	5.23e-1	4.56e-1	2.27e-1	7.70e-2	2.00e-3
500	5.62e-1	5.91e-1	7.03e-1	8.40e-1	8.99e-1	8.17e-1	4.63e-1	1.82e-1	8.08e-3
700	7.25e-1	7.78e-1	9.26e-1	1.11e-0	1.19e-0	1.13e-0	6.81e-1	3.04e-1	1.84e-2
1000	9.26e-1	9.93e-1	1.19e-0	1.42e-0	1.54e-0	1.52e-0	1.02e-0	4.98e-1	3.94e-2

Sputtered energy of W by Ar

ne = 18j, na = 9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
28	3.16e-8								
29	1.11e-7								
30	4.34e-7	7.73e-7	1.19e-6	9.26e-7	4.44e-7	1.57e-7			
35	5.98E-6	6.60E-6	7.76E-6	5.60E-6	3.37E-6	2.05E-6	6.27E-7		
40	2.65E-5	2.68E-5	2.58E-5	2.16E-5	1.54E-5	1.01E-5	4.13E-6	9.58E-7	
45	7.98E-5	8.21E-5	7.56E-5	6.21E-5	5.39E-5	3.91E-5	1.65E-5	3.66E-6	
50	1.94E-4	1.97E-4	1.85E-4	1.59E-4	1.46E-4	1.08E-4	4.92E-5	1.06E-5	9.36E-8
55	3.72E-4	3.80E-4	3.63E-4	3.51E-4	3.24E-4	2.64E-4	1.13E-4	2.33E-5	
60	6.12E-4	6.36E-4	6.49E-4	6.19E-4	6.17E-4	4.90E-4	2.24E-4	4.52E-5	2.79E-7
70	1.33E-3	1.40E-3	1.46E-3	1.51E-3	1.50E-3	1.34E-3	5.60E-4	1.11E-4	1.18E-6
80	2.27E-3	2.39E-3	2.64E-3	2.86E-3	2.84E-3	2.64E-3	1.10E-3	2.21E-4	1.56E-6
100	4.45E-3	4.54E-3	5.29E-3	6.30E-3	6.56E-3	6.12E-3	2.75E-3	6.06E-4	5.49E-6
140	8.70E-3	9.24E-3	1.11E-2	1.43E-2	1.61E-2	1.53E-2	7.50E-3	1.88E-3	1.98E-5
200	1.35E-2	1.47E-2	1.83E-2	2.47E-2	2.91E-2	2.91E-2	1.57E-2	4.53E-3	5.90E-5
300	1.88E-2	2.07E-2	2.59E-2	3.65E-2	4.37E-2	4.60E-2	2.79E-2	9.91E-3	1.75E-4
500	2.40E-2	2.59E-2	3.28E-2	4.68E-2	5.82E-2	6.30E-2	4.44E-2	1.92E-2	6.11E-4
700	2.55E-2	2.83E-2	3.66E-2	5.18E-2	6.44E-2	7.35E-2	5.52E-2	2.73E-2	1.21E-3
1000	2.64E-2	2.96E-2	3.80E-2	5.50E-2	6.84E-2	7.99E-2	6.70E-2	3.74E-2	2.32E-3

Ar - 4 W

Particle reflection coefficient of Ar backscattered from W
 z1 = 18. m1 = 39.95. z2=74. m2 = 183.85. sbe=8.68 eV. rho = 19.29 g/cm**3
 ef=0.20 eV. esb = 0.00 eV. ca=1.00. kk0 = kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program: trvnc
 ne=18. na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	7.40E-1	7.60E-1	7.96E-1	8.56E-1	9.09E-1	9.62E-1	9.94E-1	9.99E-1	1.00E4-0
20	6.86E-1	7.07E-1	7.54E-1	8.27E-1	8.89E-1	9.53E-1	9.93E-1	9.99E-1	1.00E-f-O
30	6.41E-1	6.63E-1	7.15E-1	7.99E-1	8.68E-1	9.42E-1	9.92E-1	9.99E-1	1.00E4-0
35	6.22E-1	6.44E-1	6.99E-1	7.86E-1	8.59E-1	9.37E-1	9.91E-1	9.99E-1	1.00E+0
40	6.05E-1	6.27E-1	6.83E-1	7.74E-1	8.50E-1	9.31E-1	9.90E-1	9.99E-1	1.00E+0
45	5.90E-1	6.12E-1	6.70E-1	7.64E-1	8.41E-1	9.26E-1	9.89E-1	9.99E-1	1.00E+0
50	5.77E-1	5.99E-1	6.58E-1	7.53E-1	8.33E-1	9.21E-1	9.87E-1	9.99E-1	1.00E+0
55	5.65E-1	5.87E-1	6.45E-1	7.44E-1	8.26E-1	9.16E-1	9.86E-1	9.99E-1	1.00E+0
60	5.56E-1	5.78E-1	6.35E-1	7.34E-1	8.18E-1	9.12E-1	9.85E-1	9.98E-1	1.00E+0
70	5.35E-1	5.56E-1	6.17E-1	7.19E-1	8.05E-1	9.03E-1	9.82E-1	9.98E-1	1.00E4-0
80	5.21E-1	5.42E-1	6.02E-1	7.04E-1	7.92E-1	8.94E-1	9.80E-1	9.98E-1	1.00E+0
100	4.97E-1	5.16E-1	5.73E-1	6.76E-1	7.70E-1	8.78E-1	9.74E-1	9.97E-1	1.00E-f-O
140	4.60E-1	4.80E-1	5.35E-1	6.40E-1	7.35 E-1	8.52E-1	9.65E-1	9.95E-1	1.00E-f-O
200	4.31E-1	4.44E-1	4.97E-1	5.99E-1	6.95E-1	8.19E-1	9.51E-1	9.92E-1	1.00E+0
300	3.93E-1	4.13E-1	4.63E-1	5.57E-1	6.49E-1	7.76E-1	9.27E-1	9.85E-1	1.00E-f-O
500	3.60E-1	3.71E-1	4.17E-1	5.08E-1	5.97E-1	7.24E-1	8.90E-1	9.71E-1	1.00E-f-O
700	3.38E-1	3.52E-1	3.98E-1	4.77E-1	5.63E-1	6.79E-1	8.63E-1	9.56E-1	9.99E-1
1000	3.17E-1	3.29E-1	3.81E-1	4.58E-1	5.36E-1	6.45E-1	8.23E-1	9.36E-1	9.99E-1

Energy reflection coefficient of Ar backscattered from W
 ne=18. na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	2.34E-1	2.57E-1	3.08E-1	4.07E-1	5.15E-1	6.62E-1	8.27E-1	9.00E-1	9.56E-1
20	2.27E-1	2.50E-1	3.05E-1	4.06E-1	5.11E-1	6.59E-1	8.34 E-1	9.11E-1	9.68E-1
30	2.15E-1	2.36E-1	2.92E-1	3.97E-1	5.02E-1	6.50E-1	8.32E-1	9.14E-1	9.72E-1
35	2.09E-1	2.30E-1	2.86E-1	3.92E-1	4.97E-1	6.46E-1	8.30 E-1	9.14E-1	9.74E-1
40	2.04E-1	2.24E-1	2.80E-1	3.86E-1	4.93E-1	6.41E-1	8.29E-1	9.15E-1	9.75E-1
45	1.99E-1	2.18E-1	2.74E-1	3.80E-1	4.88E-1	6.37E-1	8.27E-1	9.15E-1	9.75E-1
50	1.94E-1	2.13E-1	2.68E-1	3.75E-1	4.83E-1	6.32E-1	8.25E-1	9.14E-1	9.76E-1
55	1.90E-1	2.08E-1	2.62E-1	3.70E-1	4.78 E-1	6.28E-1	8.23E-1	9.14E-1	9.76E-1
60	1.86E-1	2.05E-1	2.58E-1	3.64E-1	4.74E-1	6.25E-1	8.21E-1	9.13E-1	9.77E-1
70	1.79E-1	1.96E-1	2.49E-1	3.54E-1	4.63E-1	6.17E-1	8.16E-1	9.12E-1	9.77E-1
80	1.74E-1	1.90E-1	2.41E-1	3.45E-1	4.54E-1	6.07E-1	8.12E-1	9.11E-1	9.78E-1
100	1.64E-1	1.79E-1	2.28E-1	3.27E-1	4.39E-1	5.94E-1	8.03E-1	9.08E-1	9.78E-1
140	1.49E-1	1.64E-1	2.07E-1	3.03E-1	4.11E-1	5.68E-1	7.87E-1	9.02E-1	9.78E-1
200	1.38E-1	1.48E-1	1.88E-1	2.76E-1	3.76E-1	5.35E-1	7.67E-1	8.92E-1	9.78E-1
300	1.23E-1	1.35E-1	1.70E-1	2.46E-1	3.39E-1	4.93E-1	7.35 E-1	8.76E-1	9.76E-1
500	1.09E-1	1.18E-1	1.47E-1	2.15E-1	2.98E-1	4.41E-1	6.85E-1	8.50E-1	9.73E-1
700	1.01E-1	1.10E-1	1.38E-1	1.97E-1	2.73E-1	4.00E-1	6.50E-1	8.25E-1	9.70E-1
1000	9.39E-2	1.00E-1	1.29E-1	1.82E-1	2.52E-1	3.67E-1	6.01E-1	7.92E-1	9.64E-1

Average depth (mean range) in Å of Ar implanted in W
 ne=18. na=9

E ₀ (eV)	0°	15°	30°	45°	55°	65°	75°	80°	85°
10	2.40E+0	2.40E4-0	2.30E4-0	2.30E+0	2.20E4-0	2.10E4-0	1.90E+0	1.70E+0	1.40E4-0
20	3.30E+0	3.20E+0	3.20E+0	3.10E+0	3.00E4-0	2.90E+0	2.60E+0	2.50E4-0	1.90E+0
30	3.90E+0	3.80E4-0	3.80E+0	3.70E+0	3.60E-J-0	3.40E+0	3.20E+0	3.10E4-0	2.70E+0
35	4.10E4-0	4.10E-J-0	4.00E+0	3.90E4-0	3.80E4-0	3.70E+0	3.40E+0	3.20E-J-0	2.90E+0
40	4.30E+0	4.30E+0	4.30E+0	4.20E+0	4.00E+0	3.90E-J-0	3.60E4-0	3.40E4-0	S.10E-f-O
45	4.60E+0	4.50E4-0	4.50E-J-0	4.40E4-0	4.20E+0	4.10E+0	3.80E-J-0	3.60E4-0	3.20E+0
50	4.80E-f-0	4.70E-f-0	4.70E4-0	4.50E+0	4.40E+0	4.20E-J-0	4.00E+0	3.70E4-0	3.10E4-0
55	4.90E+0	4.90E+0	4.80E+0	4.70E+0	4.60E+0	4.40E+0	4.10E+0	3.90E4-0	3.60E+0
60	5.10E4-0	5.10E4-0	5.00E+0	4.90E+0	4.80E4-0	4.60E-J-0	4.20E4-0	4.00E-J-0	3.20E+0
70	5.50E+0	5.40E+0	5.40E+0	5.20E4-0	5.10E-J-0	4.90E+0	4.60E4-0	4.30E+0	3.40E+0
80	5.80E+0	5.80E+0	5.70E4-0	5.50E4-0	5.40E+0	5.20E-J-0	4.80E+0	4.50E4-0	4.10E+0
100	6.40E+0	6.30E+0	6.30E+0	6.10E+0	5.90E4-0	5.70E4-0	5.30E-J-0	4.90E+0	4.40E+0
140	7.40E-J-0	7.40E+0	7.20E-J-0	7.00E4-0	6.80E-J-0	6.50E+0	6.20E4-0	5.80E+0	6.10E4-0
200	8.70E+0	8.60E+0	8.40E-J-0	8.20E-J-0	7.90E+0	7.60E4-0	7.20E+0	6.80E+0	6.00E+0
300	1.05E-J-1	1.05E-J-1	1.02E+1	9.80E+0	9.50E+0	9.10E+0	8.60E4-0	8.20E+0	9.20E4-0
500	1.34E+1	1.33E-J-1	1.29E4-1	1.24E+1	1.19E-J-1	1.15E+1	1.09E4-1	1.06E4-1	9.70E+0
700	1.59E+1	1.57E-J-1	1.52E+1	1.46E+1	1.42E+1	1.35E4-1	1.29E-J-1	1.24E-H	1.14E-J-1
1000	1.89E4+1	1.88E+1	1.81E+1	1.74E+1	1.66E-J-1	1.59E-J-1	1.53E+1	1.48E+1	1.38E+1

Ar -> W

Sputtering yield of W by Ar

z1 = 18, m1 = 39.95, z2 = 74, m2 = 183.85, sbe (eV), rho = 19.29 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvmc01
 ne = 2, na = 1, n(sbe) = 5

E ₀ (eV)	25	30
sbe (eV)		
4.34	1.01e-3	4.21e-3
5.00	2.91e-4	1.82e-3
6.00	4.24e-5	4.37e-4
7.00	3.56e-6	9.12e-5
8.00		1.36e-5

Sputtered energy of W by Ar

ne = 2, na = 1, n(sbe) = 5

E ₀ (eV)	25	30
sbe (eV)		
4.34	6.81e-5	3.19e-4
5.00	1.76e-5	1.28e-4
6.00	2.13e-6	2.62e-5
7.00	1.51e-7	4.76e-6
8.00		6.21e-7

Particle reflection coefficient of Ar backscattered from W

z1 = 18, m1 = 39.95, z2 = 74, m2 = 183.85, sbe (eV), rho = 19.29 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trvmc01
 ne = 2, na = 1, n(sbe) = 5

E ₀ (eV)	25	30
sbe (eV)		
4.34	6.55e-1	6.32e-1
5.00	6.55e-1	6.33e-1
6.00	6.55e-1	6.34e-1
7.00	6.55e-1	6.34e-1
8.00		6.33e-1

Energy reflection coefficient of Ar backscattered from W

ne = 2, na = 1, n(sbe) = 5

E ₀ (eV)	25	30
sbe (eV)		
4.34	2.18e-1	2.12e-1
5.00	2.18e-1	2.12e-1
6.00	2.18e-1	2.12e-1
7.00	2.18e-1	2.12e-1
8.00		2.12e-1

Average depth (mean range) in Å of Ar implanted in W

ne = 2, na = 1, n(sbe) = 5

Eq (eV)	25	30
sbe (eV)		
4.34	3.50e+0	3.78e+0
5.00	3.50e+0	3.78e+0
6.00	3.50e+0	3.78e+0
7.00	3.50e+0	3.78e-f-0
8.00		3.78e+0

Sputtering yield of W by Ar

z1 = 18, m1 = 39.95, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.29 g/cm**3
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 e0 = 25 eV, alpha = 0 deg., Maxwellian target temperature tt (K) program: trvmc01
 ne = 1, na = 1, n(tt) = 4

E ₀ (eV)	25
tt (K)	
9000	1.50e-5
15000	1.00e-4
25000	3.80e-4
50000	1.09e-3

W -> AV

Sputtering yield of W by W
 z1=s74. m1 = 183.85. z2=74. m2 = 183.85, sbe=8.68 eV. rho = 19.30 g/cm**3
 ef=8.60 eV. esb = 8.68 eV. ca=1.00, kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program: trvmc. trspvmcx. testvmcx
 ne=58. na=16

E ₀ (eV)	0°	10°	15°	20°	30°	40°	45°	50°	55°	60°	65°	70°
9									4.60e-7		1.25e-6	
10									3.11E-6		6.44E-6	
12									1.73E-5		2.99E-5	
15					2.98E-6		5.69E-6		3.44E-5		7.10E-5	
17											1.04E-4	
20			2.50E-6		3.29E-5		1.69E-4		2.61E-4		1.49e-4	
20											3.22E-4	
25	6.28E-7		1.46E-5		1.36E-4		4.18E-4		6.28E-4		2.80e-4	
25											8.73E-4	
23											5.41e-4	
25											8.70e-4	
27	1.40e-6		1.38e-5		9.02e-5		2.96e-4		5.53e-4		1.14e-3	
28											1.79e-3	
30	5.80E-6		4.91E-5		3.11E-4		8.89E-4		1.55E-3		2.63E-3	
30	5.50e-6	1.82e-5		8.59e-5	2.69e-4	5.87e-4	8.89E-4	1.10e-3		2.09e-3	2.79e-3	3.43e-3
35	2.13E-5		1.14E-4		6.18E-4		1.93E-3		3.71E-3		6.34E-3	
35	2.30e-6											
36	1.10e-5										7.93e-3	
37	2.83e-5											
38	5.81e-5											
40	5.60E-5		2.39E-4		1.15E-3		4.02E-3		7.70E-3		1.25E-2	
40	1.43e-4										1.29e-2	
42	2.89e-4											
45	5.69e-4											
50	1.92E-4		7.04E-4		3.64E-3		1.23E-2		2.16E-2		3.08E-2	
50	1.77e-4	3.60e-4		1.20e-3	3.51e-3	8.85e-3		1.78e-2		2.79e-2	3.22e-2	3.54e-2
55	3.13e-4											
60	5.89E-4		1.85E-3		8.48E-3		2.64E-2		4.29E-2		5.59E-2	
60	5.42e-4										5.91e-2	
65	9.32e-4											
70	1.51E-3		4.16E-3		1.70E-2		4.71E-2		7.08E-2		8.55E-2	
70	1.41e-3										8.60e-2	
80	3.15E-3		7.97E-3		2.83E-2		7.25E-2		1.02E-1		1.18E-1	
80	2.99e-3										1.22e-1	
100	9.54E-3		2.04E-2		6.03E-2		1.31E-1		1.71E-1		1.86E-1	
100	9.26e-3	1.42e-2		3.01e-2	5.99e-2	1.06e-1		1.60e-1		1.88e-1	1.90e-1	1.80e-1
120	2.04E-2		3.92E-2		1.00E-1		1.96E-1		2.45E-1		2.54E-1	
140	3.58E-2		6.20E-2		1.43E-1		2.64E-1		3.20E-1		3.27E-1	
140	3.55e-2										3.19e-1	
150	4.26e-2											
200	9.68E-2		1.44E-1		2.80E-1		4.56E-1		5.29E-1		5.20E-1	
200	9.16e-2										5.28e-1	
250	1.53e-1											
300	2.28E-1		2.99E-1		5.01E-1		7.38E-1		8.42E-1		7.94E-1	
300	2.17e-1								8.59e-1			
350	2.92e-1	3.26e-1		4.34e-1	5.98e-1	7.93e-1		9.52e-1	9.84e-1	9.79e-1	9.23e-1	8.15e-1
400	3.59e-1			5.22e-1		8.98e-1		1.07e-0	1.12e-0	1.12e-0	1.06e-0	9.19e-1
450									1.27e-0			
500	4.97E-1		6.04E-1		8.85E-1		1.22E+0		1.36E+0		1.28E+0	
500	4.79e-1								1.37e-0		1.29e-0	
800	8.47e-1	8.97e-1		1.06e-0	1.35e-0	1.66e-0		1.90e-0	1.97e-0	1.97e-0	1.95e-0	1.72e-0
1000	1.07E-0		1.21E+0		1.62E+0		2.14E+0		2.38E+0		2.29E+0	
1000	1.04e-0	1.11e-0		1.31e-0	1.60e-0	1.96e-0		2.29e-0		2.35e-0	2.30e-0	2.02e-0
2000	1.81e-0				2.59e-0					3.89e-0	3.87e-0	
2500	2.10e-0	2.20e-0		2.50e-0	2.98e-0	3.56e-0		4.16e-0	4.41e-0	4.50e-0	4.49e-0	4.09e-0
5000	3.14e-0										6.91e-0	
10000	4.36e-0										1.01e+1	
20000	5.66e-0										1.45e+1	
45000	6.92e-0											
50000	7.16e-0										2.12e-f-1	
100000	7.87e-0										2.53e4-1	

Bo (eV)	75°	80°	85°	87°
9	1.88e-6	2.15e-6	2.31e-6	
10	1.03E-5	1.12E-5	1.14E-5	
12	3.71E-5	4.22E-5	3.98E-5	
15	1.13E-4	1.12e-4	1.11E-4	
20	3.47E-4	3.59E-4	3.52E-4	
25	1.19E-3	1.31E-3	1.39E-3	
27	1.81e-3	2.08e-3	2.27e-3	
30	3.78E-3	4.06E-3	4.21E-3	
30	3.94e-3	4.42e-3	4.39e-3	
35	8.31E-3	9.01E-3	9.26E-3	
40	1.54E-2	1.54E-2	1.65E-2	
50	3.40E-2	3.34E-2	3.23E-2	
50	3.68e-2	3.69e-2	3.32e-2	3.35e-2
60	5.46E-2	5.36E-2	5.04E-2	
70	8.16E-2	7.49E-2	6.95E-2	
80	1.09E-1	9.68E-2	8.85E-2	
100	1.61E-1	1.38E-1	1.19E-1	
100		1.42e-1	1.23e-1	
120	2.09E-1	1.74E-1	1.45E-1	
140	2.53E-1	2.02E-1	1.64E-1	
200	3.73E-1	2.77E-1	2.00E-1	
300	5.52E-1	3.85E-1	2.39E-1	
350		4.44e-1	2.62e-1	
400		4.97e-1		
500	8.81E-1	5.72E-1	2.99E-1	
800	1.35e-0	8.47e-1	3.89e-1	
1000	1.62E+0	1.03E+0	4.30E-1	
1000		1.04e-0	4.41e-1	
2000	2.94e-0			
2500	3.48e-0	2.36e-0	7.89e-1	

W-> W

Sputtered energy of W by W

21=74, m1 = 183.85, z2=74, m2=183.85, sbe=8.68 eV, rho = 19.30 g/cm**3
 ef=8.60 eV, esb = 8.68 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: trvmc, trspvmcx, testvmcx
 ne=58, na=16

E ₀ (eV)	0°	10°	15°	20°	30°	40°	45°	50°	55°	60°	65°	70°
9									4.52e-8		1.45e-7	
10									3.08e-7		7.89e-7	
12							5.68e-7		2.06E-6		4.07E-6	
15					2.31E-7		3.73E-6		9.18E-6		1.58E-5	
17											2.28e-5	
20			1.51E-7		2.76E-6		2.03E-5		3.78E-5		5.42E-5	
20											4.70e-5	
23											9.94e-5	
25	5.03E-8		1.04E-6		1.23E-5		5.22E-5		9.56E-5		1.56E-4	
25											1.59e-4	
27	6.37e-8		9.24e-7		8.40e-6		3.70e-5		8.66e-5		2.13e-4	
28											3.33e-4	
30	2.91E-7		3.44E-6		2.91E-5		1.17E-4		2.47E-4		4.96E-4	
30	1.29e-6	6.64e-6		6.73e-6	2.55e-5	6.90e-5		1.59e-4		3.66e-4	5.35e-4	6.95e-4
35	1.06E-6		7.74E-6		5.97E-5		2.65E-4		6.17E-4		1.25E-3	
35	2.30e-6											
36	1.10e-5										1.59e-3	
37	2.83e-5											
38	5.81e-5											
40	2.79E-6		1.65E-5		1.16E-4		5.73E-4		1.33E-3		2.57E-3	
40	1.43e-4										2.66e-3	
42	2.89e-4											
45	5.69e-4											
50	9.96E-6		5.05E-5		3.84E-4		1.83E-3		3.91E-3		6.58E-3	
50	9.66e-6	2.36e-5		1.18e-4	3.72e-4	1.17e-3		2.95e-3		5.45e-3	6.89e-3	8.06e-3
55	1.93e-5											
60	3.15E-5		1.36E-4		9.31E-4		3.97E-3		7.83E-3		1.22E-2	
60	2.90e-5										1.27e-2	
65	5.52e-5											
70	8.20E-5		3.08E-4		1.85E-3		7.18E-3		1.31E-2		1.85E-2	
70	7.83e-5										1.87e-2	
80	1.70E-4		5.84E-4		3.01E-3		1.09E-2		1.85E-2		2.55E-2	
80	1.64e-4										2.61e-2	
100	5.02E-4		1.42E-3		6.15E-3		1.90E-2		3.02E-2		3.94E-2	
100	4.78e-4	8.61e-4		2.40e-3	6.03e-3	1.36e-2		2.56e-2		3.62e-2	3.93e-2	4.04e-2
120	1.00E-3		2.58E-3		9.69E-3		2.72E-2		4.18E-2		5.20E-2	
140	1.67E-3		3.82E-3		1.32E-2		3.52E-2		5.24E-2		6.39E-2	
140	1.65e-3										6.21e-2	
150	1.91e-3											
200	4.03E-3		7.73E-3		2.25E-2		5.31E-2		7.62E-2		9.05E-2	
200	3.73e-3										8.98e-2	
250	6.12e-3											
300	8.09E-3		1.34E-2		3.33E-2		7.16E-2		1.02E-1		1.18E-1	
300	7.39e-3								1.03e-1			
350	9.48e-3	1.18e-2		2.00e-2	3.58e-2	6.08e-2		9.28e-2	1.09e-1	1.21e-1	1.21e-1	1.22e-1
400	1.10e-2			2.27e-2		6.60e-2		9.83e-2	1.14e-1	1.28e-1	1.35e-1	1.30e-1
450									1.22e-1			
500	1.41E-2		2.10E-2		4.47E-2		8.99E-2		1.25E-1		1.46E-1	
500	1.32e-2								1.23e-1		1.45e-1	
800	1.88e-2	2.17e-2		3.16e-2	5.05e-2	8.02e-2		1.16e-1	1.40e-1	1.55e-1	1.65e-1	1.65e-1
1000	2.15E-2		2.92E-2		5.46E-2		1.04E-1		1.44E-1		1.77E-1	
1000	2.04e-2	2.39e-2		3.42e-2	5.26e-2	8.29e-2		1.21e-1		1.60e-1	1.75e-1	1.73e-1
2000	2.47e-2				5.69e-2					1.68e-1	1.87e-1	
2500	2.52e-2	2.83e-2		3.82e-2	5.64e-2	8.44e-2		1.23e-1	1.46e-1	1.70e-1	1.91e-1	1.98e-1
5000	2.56e-2										1.91e-1	
10000	2.41e-2										1.88e-1	
20000	2.05e-2										1.73e-1	
45000	1.68e-2											
50000	1.66e-2										1.47e-1	
100000	1.25e-2										1.27e-1	

E _g (eV)	75°	80°	85°	87°
9	2.46e-7	2.83e-7	3.09e-7	
10	1.39e-6	1.56e-6	1.62e-6	
12	5.72E-6	6.87E-6	6.58E-6	
15	1.93E-5	1.97E-5	2.01E-5	
20	6.49E-5	7.05E-5	7.25E-5	
25	2.36E-4	2.68E-4	2.90E-4	
27	3.75e-4	4.49e-4	4.96e-4	
30	7.96E-4	8.86E-4	9.38E-4	
30	8.27e-4	9.94e-4	1.00e-3	
35	1.87E-3	2.06E-3	2.16E-3	
40	3.55E-3	3.71E-3	4.05E-3	
50	8.21E-3	8.37E-3	8.26E-3	
50	8.76e-3	9.30e-3	8.65e-3	8.61e-3
60	1.39E-2	1.37E-2	1.30E-2	
70	2.00E-2	1.90E-2	1.80E-2	
80	2.66E-2	2.44E-2	2.27E-2	
100	3.86E-2	3.41E-2	2.98E-2	
100		3.43e-2	3.05e-2	
120	4.81E-2	4.15E-2	3.49E-2	
140	5.61E-2	4.69E-2	3.78E-2	
200	7.48E-2	5.73E-2	4.06E-2	
300	9.48E-2	6.75E-2	3.98E-2	
350		7.21e-2	3.97e-2	
400		7.67e-2		
500	1.19E-1	7.94E-2	3.76E-2	
800	1.35e-1	9.02e-2	3.40e-2	
1000	1.53E-1	1.00E-1	3.40E-2	
1000		9.81e-2	3.49e-2	
2000	1.81e-1			
2500	1.90e-1	1.39e-1	4.19e-2	

W -> W

Particle reflection coefficient of W backscattered from W
 21=74, m1 = 183.85, z2=74, m2 = 183.85, sbe=8.68 eV. rho = 19.30 g/cm**3
 ef=8.60 eV, esb= 8.68 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trvmc, trspvmc, testvmc
 ne=51, na=16

Bq(eV)	0°	10°	15°	20°	30°	40°	45°	50°	55°	60°	65°	70°
15											1.00E-7	
17											2.63E-6	
20							3.60E-7		3.95E-6		4.73E-5	
20											4.87E-5	
23											3.48E-4	
25					2.40E-7		2.18E-5		1.78E-4		9.39E-4	
25											8.85E-4	
27			3.00E-9		1.15E-6		6.87E-5		4.91E-4		2.17E-3	
28											2.95E-3	
30					5.70E-6		2.44E-4		1.43E-3		5.14E-3	
30	1.40E-7	2.00E-7			5.10E-6	8.42E-5					5.28E-3	8.45E-3
35			3.33E-7		4.46E-5		1.13E-3	5.84E-4	5.03E-3	2.76E-3	1.47E-2	
36											1.80E-2	
40			3.80E-6		2.04E-4		3.12E-3		1.15E-2		3.03E-2	
40											3.06E-2	
50	2.10E-6		5.70E-5		1.19E-3		1.14E-2		3.31E-2		7.30E-2	
50	3.43E-6	1.60E-5		1.68E-4	1.18E-3	5.80E-3		2.02E-2		4.98E-2	7.24E-2	9.82E-2
55	1.93E-5										1.23E-1	
60	2.12E-5		2.54E-4		3.50E-3		2.40E-2		6.28E-2		1.24E-1	
60	2.00E-5										1.76E-1	
65	5.10E-5										1.72E-1	
70	8.15E-5		6.55E-4		6.57E-3		3.86E-2		9.30E-2		2.27E-1	
70	7.10E-5										2.26E-1	
80	1.90E-4		1.26E-3		1.07E-2		5.45E-2		1.23E-1		3.11E-1	
80	2.27E-4										3.17E-1	4.01E-1
100	6.89E-4		2.90E-3		1.91E-2		8.32E-2		1.74E-1		3.78E-1	
100	6.51E-4	1.54E-3		5.52E-3	1.93E-2	5.33E-2		1.24E-1		2.35E-1	4.25E-1	
120	1.39E-3		4.88E-3		2.73E-2		1.08E-1		2.16E-1		4.24E-1	
140	2.25E-3		7.20E-3		3.49E-2		1.25E-1		2.47E-1		4.95E-1	
140	2.22E-3										4.95E-1	
150	2.75E-3										4.95E-1	
200	5.40E-3		1.32E-2		5.12E-2		1.60E-1		2.98E-1		5.17E-1	
200	5.50E-3										5.05E-1	
250	7.88E-3										5.07E-1	
300	1.09E-2		2.12E-2		6.47E-2		1.77E-1		3.18E-1		4.72E-1	
300	8.20E-3								3.15E-1		4.58E-1	
350	1.29E-2	1.74E-2		3.45E-2	6.89E-2	1.39E-1		2.38E-1	3.28E-1	4.12E-1	5.27E-1	6.42E-1
400	1.44E-2			3.84E-2		1.36E-1		2.40E-1	3.11E-1	4.09E-1	5.18E-1	6.35E-1
450									3.11E-1		5.05E-1	
500	1.76E-2		2.97E-2		7.41E-2		1.83E-1		3.20E-1		5.07E-1	
500	1.76E-2			4.48E-2	7.84E-2	1.33E-1		2.32E-1	3.15E-1	3.85E-1	4.72E-1	6.10E-1
800	2.30E-2	2.83E-2			7.74E-2		1.70E-1		3.01E-1		4.58E-1	
1000	2.46E-2		3.71E-2		7.59E-2	1.30E-1		2.14E-1	2.85E-1		4.49E-1	5.87E-1
1000	2.35E-2	2.97E-2		4.41E-2	7.63E-2				3.70E-1		4.18E-1	
2000	2.79E-2			4.46E-2	7.05E-2	1.17E-1		1.85E-1	3.23E-1	3.17E-1	3.93E-1	5.07E-1
2500	2.74E-2	3.16E-2							3.17E-1		3.65E-1	
5000	2.61E-2										2.89E-1	
10000	2.10E-2										2.50E-1	
20000	2.14E-2										2.54E-1	
45000	1.94E-2										2.37E-1	
50000	1.67E-2											
100000	1.40E-2											

Bq(eV)	75°	80°	85°	87°
15	1.48E-6	2.83E-6	4.08E-6	
20	2.18E-4	3.54E-4	4.61E-4	
25	2.83E-3	4.00E-3	4.90E-3	
27	5.86E-3	7.94E-3	9.56E-3	
30	1.23E-2	1.61E-2	1.90E-2	
30	1.23E-2	1.64E-2	1.91E-2	
35	3.07E-2	3.82E-2	4.48E-2	
40	5.67E-2	6.90E-2	8.06E-2	
50	1.25E-1	1.51E-1	1.69E-1	
50	1.25E-1	1.50E-1	1.69E-1	1.76E-1
60	2.05E-1	2.45E-1	2.75E-1	
70	2.86E-1	3.40E-1	3.81E-1	
80	3.62E-1	4.30E-1	4.79E-1	
100	4.91E-1	5.76E-1	6.33E-1	
100		5.79E-1	6.32E-1	
120	5.83E-1	6.71E-1	7.34E-1	
140	6.43E-1	7.36E-1	7.99E-1	
200	7.25E-1	8.26E-1	8.94E-1	
300	7.60E-1	8.68E-1	9.39E-1	
350		8.72E-1	9.49E-1	
400		8.78E-1		
500	7.63E-1	8.85E-1	9.64E-1	
800	7.57E-1	8.83E-1	9.74E-1	
1000	7.27E-1	8.74E-1	9.76E-1	
1000		8.76E-1	9.76E-1	
2000	6.67E-1			
2500	6.34E-1	8.20E-1	9.69E-1	

W → W

Energy reflection coefficient of W backscattered from W
 z1=74, m1 = 183.85, z2=74, m2 = 183.85, sbe=8.68 eV, rho = 19.30 g/cm**3
 ef=8.60 eV, esb = 8.68 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipot=1 (KrC)
 program: trvmc, trspvmcx, testvmcx
 ne = 51, na=16

E ₀ (eV)	0°	10°	15°	20°	30°	40°	45°	50°	55°	60°	65°	70°
15											3.19E-8	
17											6.80E-7	
20							6.18E-8		7.52E-7		9.56E-6	
20											9.79E-6	
23											7.13E-5	
25					3.04E-8		3.50E-6		3.08E-5		1.95E-4	
25											1.81E-4	
27					1.64E-7		1.13E-5		8.89E-5		4.70E-4	
28											6.47E-4	
30					6.93E-7		3.95E-5		2.71E-4		1.17E-3	
30	3.86E-7	3.18E-7			1.41E-6	1.35E-5	1.92E-4	1.01E-4	1.03E-3	5.65E-4	1.20E-3	2.06E-3
35			2.52E-8		5.63E-6						3.62E-3	
36											4.48E-3	
40	1.00E-9		3.36E-7		2.58E-5		5.69E-4		2.48E-3		7.93E-3	
40											8.07E-3	
50	1.20E-7		5.19E-6		1.59E-4		2.19E-3		7.89E-3		2.10E-2	
50	1.28E-6	1.90E-6		1.81E-5	1.59E-4	9.96E-4		4.36E-3		1.29E-2	2.10E-2	3.06E-2
55	1.93E-5											
60	1.29E-6		2.33E-5		4.80E-4		4.81E-3		1.58E-2		3.78E-2	
60	1.69E-6										3.81E-2	
65	3.43E-6											
70	5.25E-6		6.30E-5		9.27E-4		8.00E-3		2.43E-2		5.65E-2	
70	4.26E-6										5.46E-2	
80	1.18E-5		1.21E-4		1.51E-3		1.16E-2		3.29E-2		7.55E-2	
80	1.41E-5										7.50E-2	
100	4.36E-5		2.64E-4		2.72E-3		1.79E-2		4.83E-2		1.08E-1	
100	4.09E-5	1.22E-4		5.95E-4	2.79E-3	1.00E-2		3.04E-2		7.39E-2	1.10E-1	1.53E-1
120	8.31E-5		4.37E-4		3.84E-3		2.34E-2		6.09E-2		1.35E-1	
140	1.31E-4		6.23E-4		4.86E-3		2.70E-2		7.07E-2		1.56E-1	
140	1.29E-4										1.56E-1	
150	1.54E-4											
200	2.85E-4		1.07E-3		6.82E-3		3.41E-2		8.69E-2		1.91E-1	
200	2.93E-4										1.90E-1	
250	3.62E-4											
300	5.36E-4		1.54E-3		8.07E-3		3.70E-2		9.25E-2		2.07E-1	
300	4.26E-4								9.05E-2			
350	6.04E-4	1.06E-3		3.02E-3	8.34E-3	2.32E-2		5.74E-2	9.54E-2	1.40E-1	2.11E-1	3.00E-1
400	6.91E-4			3.16E-3		2.27E-2		5.85E-2	8.79E-2	1.41E-1	2.06E-1	3.02E-1
450									8.87E-2			
500	8.09E-4		1.94E-3		8.24E-3		3.61E-2		8.80E-2		2.03E-1	
500	7.90E-4								9.02E-2		2.00E-1	
800	9.68E-4	1.48E-3		3.27E-3	8.35E-3	2.01E-2		5.34E-2	8.11E-2	1.24E-1	1.83E-1	2.79E-1
1000	1.03E-3		2.17E-3		7.77E-3		3.02E-2		7.32E-2		1.74E-1	
1000	9.97E-4	1.45E-3		2.98E-3	7.66E-3	1.87E-2		4.48E-2		1.17E-1	1.70E-1	2.71E-1
2000	1.06E-3				6.80E-3					9.39E-2	1.46E-1	
2500	1.04E-3	1.37E-3		2.84E-3	6.13E-3	1.48E-2		3.36E-2	5.46E-2	9.10E-2	1.34E-1	2.19E-1
5000	1.09E-3										1.16E-1	
10000	5.90E-4										8.34E-2	
20000	7.20E-4										6.96E-2	
45000	6.69E-4											
50000	6.20E-4										6.66E-2	
100000	4.91E-4										6.58E-2	

E ₀ (eV)	75°	80°	85°	87°
15	3.44E-7	6.26E-7	9.31E-7	
20	4.85E-5	8.22E-5	1.09E-4	
25	6.85E-4	1.01E-3	1.28E-3	
27	1.48E-3	2.11E-3	2.63E-3	
30	3.25E-3	4.51E-3	5.50E-3	
30	3.26E-3	4.60E-3	5.56E-3	
35	8.85E-3	1.16E-2	1.42E-2	
40	1.75E-2	2.24E-2	2.74E-2	
50	4.24E-2	5.45E-2	6.36E-2	
50	4.25E-2	5.38E-2	6.32E-2	6.64E-2
60	7.40E-2	9.45E-2	1.10E-1	
70	1.09E-1	1.37E-1	1.61E-1	
80	1.43E-1	1.82E-1	2.11E-1	
100	2.05E-1	2.60E-1	3.02E-1	
100		2.62E-1	3.01E-1	
120	2.56E-1	3.21E-1	3.75E-1	
140	2.96E-1	3.71E-1	4.32E-1	
200	3.63E-1	4.64E-1	5.46E-1	
300	4.07E-1	5.32E-1	6.41E-1	
350		5.49E-1	6.69E-1	
400		5.58E-1		
500	4.26E-1	5.80E-1	7.23E-1	
800	4.23E-1	5.95E-1	7.75E-1	
1000	4.04E-1	5.91E-1	7.90E-1	
1000		5.92E-1	7.91E-1	
2000	3.56E-1			
2500	3.39E-1	5.39E-1	8.19E-1	

W -> W

Average depth (mean range) in Å of W implanted in W
 z1=74. m1 = 183.85. z2=74. m2 = 183.85. sbe = 8.68 eV. rho=19.30 g/cm**3
 ef=8.60 eV. esb=8.68 eV. ca=1.00. kko=kkOr=2. kdee=kdee2=3. ipot=ipotrl (KrC)
 program: trvmc. trspvmc. testvmc
 ne=52. na=16

E ₀ (eV)	0°	10°	15°	20°	30°	40°	45°	50°	55°	60°	65°	70°
9									4.00e-1		4.00e-1	
10	7.00E-1		7.00E-1		6.00E-1		5.00E-1		5.00E-1		4.00E-1	
12	9.00E-1		8.00E-1		7.00E-1		6.00E-1		6.00E-1		5.00E-1	
15	1.10E+0		1.00E+0		9.00E-1		8.00E-1		7.00E-1		6.00E-1	
17											4.08e-1	
20	1.30E+0		1.30E+0		1.10E+0		9.00E-1		8.00E-1		6.00E-1	
20											4.45e-1	
23											4.77e-1	
25	1.60E+0		1.50E+0		1.30E+0		1.10E+0		9.00E-1		7.00E-1	
25											4.98e-1	
27	1.70E+0		1.60E+0		1.40E+0		1.10E+0		9.00E-1		7.00E-1	
28											5.29e-1	
30	1.80E+0		1.70E+0		1.50E+0		1.20E+0		9.00E-1		7.00E-1	
30	1.74e+0	1.70e+0		1.60e+0	1.43e+0	1.20e+0		9.36e-1		6.71e-1	5.51e-1	4.42e-1
35	2.00E+0		1.90E+0		1.70E+0		1.30E+0		1.00E+0		8.00E-1	
36											6.13e-1	
40	2.20E+0		2.10E+0		1.80E+0		1.40E+0		1.10E+0		8.00E-1	
40											6.57e-1	
50	2.50E+0		2.40E+0		2.10E+0		1.60E+0		1.30E+0		9.00E-1	
50	2.50e+0	2.45e+0		2.29e+0	2.04e+0	1.70e+0		1.32e+0		9.37e-1	7.71e-1	6.02e-1
60	2.80E+0		2.70E+0		2.30E+0		1.80E+0		1.40E+0		1.00E+0	
60	2.82e+0										8.94e-1	
65	2.95e+0											
70	3.10E+0		3.00E+0		2.60E+0		2.00E+0		1.60E+0		1.20E+0	
70	3.09e+0										1.03e+0	
80	3.40E+0		3.20E+0		2.80E+0		2.20E+0		1.70E+0		1.30E+0	
80	3.34e+0										1.17e+0	
100	3.80E+0		3.60E+0		3.20E+0		2.60E+0		2.10E+0		1.60E+0	
100	3.80e+0	3.71e+0		3.50e+0	3.14e+0	2.72e+0		2.26e+0		1.70e+0	1.46e+0	1.20e-f-0
120	4.20E+0		4.00E+0		3.60E+0		2.90E+0		2.40E+0		1.90E+0	
140	4.60E+0		4.40E+0		3.90E+0		3.20E+0		2.70E+0		2.20E+0	
140	4.56e+0										2.11e+0	
150	4.72e+0											
200	5.50E+0		5.30E+0		4.80E+0		4.10E+0		3.50E+0		3.00E+0	
200	5.49e+0										2.94e+0	
250	6.10e+0											
300	6.70E+0		6.50E+0		6.00E+0		5.20E+0		4.60E+0		3.90E+0	
300	6.66e+0								4.57e+0			
350	7.19e+0	7.12e+0		6.85e+0	6.44e+0	5.95e+0		5.25e+0	5.05e+0	4.65e+0	4.40e+0	3.89e+0
400	7.71e+0			7.30e+0		6.31e+0		5.82e+0	5.49e+0	5.02e+0	4.69e+0	4.22e+0
450									5.75e+0			
500	8.60E+0		8.40E+0		7.70E+0		6.80E+0		6.10E+0		5.40E+0	
500	8.68e+0								6.04e+0		5.33e+0	
800	1.07e+1	1.06e+1		1.02e+1	9.75e+0	8.97e+0		8.16e-f-0	7.85e+0	7.14e+0	6.86e+0	6.25e+0
1000	1.19E+1		1.16E+1		1.08E+1		9.50E+0		8.60E+0		7.60E+0	
1000	1.20e+1	1.19e+1		1.15e+1	1.08e+1	9.89e+0		9.14e+0		8.17e+0	7.84e+1	7.27e+0
2000	1.65e+1				1.49e+1					1.13e+1	1.07e+1	
2500	1.83e+1	1.81e+1		1.75e+1	1.65e+1	1.53e+1		1.39e+1	1.30e+1	1.24e+1	1.16e+1	1.09e+1
5000	2.56e+1										1.64e+1	
10000	3.62e+1										2.25e+1	
20000	5.24e+1										3.17e+1	
45000	8.28e+1											
50000	8.88e+1										5.25e+1	
100000	1.35e+2										8.14e+1	

E ₀ (eV)	75°	80°	85°	87°
9	4.00e-1	4.00e-1	4.00e-1	
10	4.00E-1	4.00E-1	4.00E-1	
12	5.00E-1	4.00E-1	4.00E-1	
15	5.00E-1	5.00E-1	4.00E-1	
20	5.00E-1	5.00E-1	5.00E-1	
25	5.00E-1	5.00E-1	5.00E-1	
27	5.00e-1	5.00e-1	5.00e-1	
30	6.00E-1	5.00E-1	5.00E-1	
30	3.52e-1	2.88e-1	2.45e-1	
35	6.00E-1	5.00E-1	5.00E-1	
40	6.00E-1	5.00E-1	5.00E-1	
50	7.00E-1	6.00E-1	5.00E-1	
50	4.73e-1	3.80e-1	3.19e-1	3.06e-1
60	7.00E-1	6.00E-1	6.00E-1	
70	8.00E-1	7.00E-1	6.00E-1	
80	9.00E-1	7.00E-1	7.00E-1	
100	1.10E+0	9.00E-1	8.00E-1	
100		7.68e-1	6.21e-1	
120	1.30E+0	1.10E+0	9.00E-1	
140	1.60E+0	1.30E+0	1.10E+0	
200	2.20E+0	1.80E+0	1.50E+0	
300	3.10E+0	2.60E+0	2.10E+0	
350		2.82e+0	2.19e+0	
400		3.08e+0		
500	4.40E+0	3.80E+0	3.00E+0	
800	5.84e+0	4.79e+0	4.12e+0	
1000	6.50E+0	5.80E+0	4.60E+0	
1000		5.63e+0	4.28e+0	
2000	9.27e+0			
2500	1.03e+1	9.21e+0	7.87e+0	

W → W

Sputtering yield of W by W

z1 = 74, m1 = 183.85, z2 = 74, m2 = 183.85, sbe = 8.68 eV, rho = 19.29 g/cm**3
 ef = 8.63 eV, esb = 8.68 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 3('bl')
 program: ecklc (CRAY-T3E)
 ne = 19, na = 2

E ₀ (eV)	0°	45°
18		3.25e-7
19		9.11e-7
20		2.45e-6
25		6.66e-5
27	8.03e-7	1.52e-4
30	3.69e-6	4.20e-4
35	1.80e-5	1.43e-3
40	5.18e-5	3.39e-3
50	2.30e-4	1.13e-2
60	7.08e-4	2.41e-2
70	1.80e-3	4.17e-2
80	3.87e-3	6.37e-2
100	1.22e-2	1.16e-1
120	2.70e-2	1.76e-1
140	4.77e-2	2.38e-1
200	1.36e-1	4.32e-1
300	3.19e-1	7.34e-1
500	6.90e-1	1.26e-0
1000	1.45e-0	2.32e-0

Sputtered energy of W by W

ne = 19, na = 2

E ₀ (eV)	0°	45°
18		5.34e-8
19		1.41e-7
20		3.62e-7
25		9.18e-6
27	3.32e-8	2.13e-5
30	1.60e-7	6.03e-5
35	7.99e-7	2.10e-4
40	2.44e-6	5.04e-4
50	1.17e-5	1.71e-3
60	3.85e-5	3.65e-3
70	1.02e-4	6.27e-3
80	2.23e-4	9.46e-3
100	7.04e-4	1.68e-2
120	1.51e-3	2.46e-2
140	2.59e-3	3.24e-2
200	6.52e-3	5.30e-2
300	1.28e-2	7.73e-2
500	2.14e-2	1.03e-1
1000	3.02e-2	1.22e-1

W -> W

Particle reflection coefficient of W backscattered from W
 z1=74, m1 = 183.85, z2= 74, m2= 183.85, sbe=8.68 eV, rho = 19.29 g/cm**3
 ef=8.63 eV, esb= 8.68 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=3(zbl)
 program: ecklc (CRAY-T3E)
 ne=19, na=2

E ₀ (eV)	0°	45°
18		2.20e-8
19		1.14e-7
20		4.00e-7
25		4.01e-5
27		1.06e-4
30		3.10e-4
35		1.12e-3
40		2.90e-3
50	2.00e-8	1.07e-2
60	9.40e-7	2.54e-2
70	1.05e-5	4.52e-2
80	5.45e-5	6.71e-2
100	3.64e-4	1.11e-1
120	1.02e-3	1.50e-1
140	1.93e-3	1.80e-1
200	5.55e-3	2.33e-1
300	1.15e-2	2.60e-1
500	1.97e-2	2.58e-1
1000	2.81e-2	2.24e-1

Energy reflection coefficient of W backscattered from W
 ne=19, na=2

E ₀ (eV)	0°	45°
18		2.77e-9
19		1.11e-8
20		4.10e-8
25		6.03e-6
27		1.68e-5
30		5.22e-5
35		1.98e-4
40		5.31e-4
50		2.02e-3
60	5.28e-8	4.97e-3
70	6.21e-7	9.18e-3
80	3.28e-6	1.40e-2
100	2.41e-5	2.42e-2
120	7.11e-5	3.34e-2
140	1.32e-4	4.08e-2
200	3.52e-4	5.38e-2
300	6.59e-4	5.93e-2
500	9.69e-4	5.61e-2
1000	1.19e-3	4.41e-2

Average depth (mean range) in Å of W implanted in W
 ne=19, na=2

E ₀ (eV)	0°	45°
18		1.81e-1
19		1.89e-1
20		1.97e-1
25		2.48e-1
27	3.82e-1	2.71e-1
30	4.54e-1	3.06e-1
35	5.76e-1	3.65e-1
40	6.84e-1	4.19e-1
50	8.59e-1	5.13e-1
60	1.01e+0	6.00e-1
70	1.15e+0	6.88e-1
80	1.30e+0	7.79e-1
100	1.58e+0	9.69e-1
120	1.83e+0	1.16e+0
140	2.06e+0	1.35e+0
200	2.68e+0	1.89e+0
300	3.54e+0	2.66e+0
500	4.92e+0	3.85e+0
1000	7.44e+0	5.92e+0

W W

W on W, Maxwellian velocity distribution, sheath potential 0 kT
 z1=74, m1 = 183.85, z2=74, m2 = 183.85, sbe=8.68 eV. rho = 19.30 g/cm**3
 ef=8.60 eV, esb = 8.68 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 program: trspvmcx
 ne=12

kT(eV)	Y	Y _β	E _{sp}	R _N	Γ _e	E _b	range
7	6.57e-4	3.84e-4	8.19e+0	1.08e-3	1.03e-3	1.33eR1	4.72e-1
12	4.54e-3	2.24e-3	1.18e+1	8.28e-3	6.76e-3	1.96e+1	7.91e-1
20	2.10e-2	8.11e-3	1.55e+1	3.09e-2	2.14e-2	2.77e+1	1.18e+0
30	5.38e-2	1.67e-2	1.84e+1	6.41e-2	3.99e-2	3.74e+1	1.59e+0
50	1.39e-1	3.33e-2	2.39e+1	1.21e-1	6.61e-2	5.48e+1	2.29e+0
70	2.34e-1	4.58e-2	2.74e+1	1.57e-1	8.12e-2	7.23e+1	2.91e+0
100	3.75e-1	5.83e-2	3.16e+1	1.99e-1	9.47e-2	9.67e+1	3.73e+0
200	7.62e-1	7.77e-2	4.06e+1	2.40e-1	9.82e-2	1.63e+2	5.68e+0
500	1.72e-0	9.91e-2	5.87e+1	2.54e-1	9.19e-2	3.70e+2	9.34e+0
1000	2.83e-0	1.07e-1	7.63e+1	2.38e-1	8.21e-2	6.96e+2	1.30e+1
2000	4.29e-0	1.09e-1	1.03e+2	2.23e-1	7.55e-2	1.38e+3	1.78e+1
5000	7.05e-0	9.85e-2	1.43e+2	1.90e-1	5.91e-2	3.20e+3	2.78e+1

W on W, Maxwellian velocity distribution, sheath potential 3 kT
 ne=21

kT(eV)	Y	Y _β	E _{sp}	R _{Ar}	R _b	E _b	range
5	5.07e-4	1.22e-4	6.02e+0	2.87e-4	1.17e-4	1.02e+1	1.27e+0
6	1.17e-3	2.74e-4	6.99e+0	7.27e-4	2.74e-4	1.13e+1	1.46e+0
7	2.12e-3	4.90e-4	8.07e+0	1.28e-3	4.55e-4	1.24e+1	1.65e+0
10	8.31e-3	1.62e-3	9.76e+0	4.80e-3	1.58e-3	1.65e+1	2.11e+0
14	2.42e-2	4.07e-3	1.18e+1	1.16e-2	3.31e-3	2.00e+1	2.63e+0
20	6.13e-2	8.71e-3	1.42e+1	2.09e-2	5.09e-3	2.44e+1	3.29e+0
24	9.52e-2	1.20e-2	1.51e+1	2.65e-2	6.13e-3	2.77e+1	3.64e+0
30	1.48e-1	1.60e-2	1.62e+1	3.42e-2	7.15e-3	3.13e+1	4.16e+0
36	2.03e-1	1.96e-2	1.74e+1	3.90e-2	7.93e-3	3.67e+1	4.62e+0
40	2.42e-1	2.24e-2	1.85e+1	4.30e-2	8.37e-3	3.89e+1	4.88e+0
45	2.86e-1	2.44e-2	1.92e+1	4.69e-2	8.99e-3	4.32e+1	5.22e+0
50	3.37e-1	2.68e-2	2.00e+1	4.96e-2	9.27e-3	4.68e+1	5.50e+0
60	4.26e-1	3.04e-2	2.14e+1	5.12e-2	8.67e-3	5.08e+1	6.10e+0
70	5.22e-1	3.37e-2	2.27e+1	5.58e-2	9.22e-3	5.80e+1	6.55e+0
75	5.69e-1	3.54e-2	2.33e+1	5.57e-2	8.66e-3	5.83e+1	6.86e+0
100	7.57e-1	3.82e-2	2.52e+1	6.08e-2	9.02e-3	7.42e+1	7.88e+0
200	1.46e-0	4.79e-2	3.30e+1	6.34e-2	8.11e-3	1.28e+2	1.09e+1
400	2.37e-0	5.13e-2	4.33e+1	6.17e-2	6.46e-3	2.09e+2	1.51e+1
1000	3.89e-0	4.95e-2	6.36e+1	5.50e-2	4.24e-3	3.86e+2	2.36e+1
2000	5.42e-0	4.45e-2	8.24e+1	4.66e-2	4.31e-3	9.27e+2	3.36e+1
5000	7.82e-0	3.78e-2	1.21e+2	4.00e-2	3.25e-3	2.04e+3	5.33e+1

W on W, Maxwellian velocity distribution, sheath potential 9 kT
 ne=20

kT(eV)	Y	Y _e	E _{sp}	R _N	R _β	E _f	range
3	2.72e-4	3.39e-5	4.12e+0	5.60e-5	1.28e-5	7.53e+0	1.75e+0
4	1.04e-3	1.28e-4	5.41e+0	2.76e-4	5.43e-5	8.65e+0	2.14e+0
5	2.80e-3	3.33e-4	6.55e+0	9.53e-4	1.67e-4	9.61e+0	2.49e+0
7	1.16e-2	1.22e-3	8.05e+0	3.04e-3	4.75e-4	1.20e+1	3.06e+0
10	3.95e-2	3.50e-3	9.74e+0	7.27e-3	1.03e-3	1.55e+1	3.76e+0
20	1.93e-1	1.19e-2	1.36e+1	1.88e-2	2.18e-3	2.56e+1	5.51e+0
24	2.64e-1	1.43e-2	1.43e+1	2.43e-2	2.46e-3	2.67e+1	6.03e+0
30	3.68e-1	1.76e-2	1.58e+1	2.83e-2	2.67e-3	3.11e+1	6.72e+0
36	4.73e-1	2.06e-2	1.73e+1	3.07e-2	2.71e-3	3.50e+1	7.35e+0
40	5.32e-1	2.18e-2	1.80e+1	3.16e-2	2.83e-3	3.94e+1	7.76e+0
45	6.16e-1	2.37e-2	1.90e+1	3.31e-2	2.81e-3	4.20e+1	8.22e+0
50	6.80e-1	2.47e-2	1.99e+1	3.61e-2	2.77e-3	4.23e+1	8.65e+0
60	8.47e-1	2.74e-2	2.14e+1	3.80e-2	3.00e-3	5.20e+1	9.41e+0
70	9.69e-1	2.89e-2	2.29e+1	3.96e-2	2.89e-3	5.61e+1	1.02e+1
75	1.03e-0	2.92e-2	2.33e+1	3.93e-2	2.89e-3	6.05e+1	1.05e+1
100	1.33e-0	3.25e-2	2.69e+1	4.14e-2	3.17e-3	8.43e+1	1.21e+1
200	2.22e-0	3.52e-2	3.49e+1	3.78e-2	2.35e-3	1.37e+2	1.67e+1
500	3.74e-0	3.55e-2	5.23e+1	4.00e-2	2.36e-3	3.25e+2	2.56e+1
1000	5.22e-0	3.31e-2	6.99e+1	3.28e-2	1.65e-3	5.53e+2	3.63e+1
2000	6.29e-0	2.70e-2	9.42e+1	2.75e-2	1.29e-3	1.03e+3	5.25e+1

He -> Pt

Sputtering yield of Pt by He
 z1= 2. m1 = 4.00. z2= 78. m2= 195.09. sbe=5.86 eV. rho=21.44 g/cm**3
 ef=0.50 eV. esb= 0.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipotr=1 (KrC)
 program : trvme95. trspvmcx
 ne= 4. na= 2

E ₀ (eV)	0°	30°
500		4.49e-2
1000		7.35e-2
1500	7.59e-2	9.25e-2
3000	8.77e-2	

Sputtered energy of Pt by He
 ne= 4, na= 2

MeV)	0°	30°
500		7.00e-4
1000		8.54e-4
1500	7.16e-4	8.82e-4
3000	5.50e-4	

Particle reflection coefficient of He backscattered from Pt
 z1= 2. m1 = 4.00. z2= 78. m2= 195.09. sbe=5.86 eV. rho=21.44 g/cm**3
 ef=0.50 eV. esb= 0.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2 = 3. ipot=ipotr= 1 (KrC)
 program : trvme95. trspvmcx
 ne= 4. na= 2

Ro (eV)	0°	30°
500		5.99e-1
1000		5.60e-1
1500	4.95e-1	5.36e-1
3000	4.46e-1	

Energy reflection coefficient of He backscattered from Pt
 ne= 4, na= 2

E ₀ (eV)	0°	30°
500		3.75e-1
1000		3.38e-1
1500	2.80e-1	3.14e-1
3000	2.41e-1	

Average depth (mean range) in Å of He implanted in Pt
 ne= 4, na= 2

Eq (eV)	0°	30°
500		6.02e+1
1000		9.01e+1
1500	1.15e+2	1.14e+2
3000	1.80e+2	

Ne -> Pt

Sputtering yield of Pt by Ne

z1 = 10, m1 = 20.18, z2 = 78, m2 = 195.09, sbe = 5.86 eV, rho = 21.44 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trvme95
 ne = 6, na = 1

E ₀ (eV)	0°
40	1.63e-3
200	2.61e-1
600	6.75e-1
3000	1.40e-0
5000	1.70e-0
9000	1.76e-0

Sputtered energy of Pt by Ne

ne = 6, na = 2

E _q (eV)	0°
40	6.75e-5
200	1.30e-2
600	1.90e-2
3000	1.47e-2
5000	1.28e-2
9000	9.52e-3

Particle reflection coefficient of Ne backscattered from Pt

z1 = 10, m1 = 20.18, z2 = 78, m2 = 195.09, sbe = 5.86 eV, rho = 21.44 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program : trvme95
 ne = 6, na = 1

B ₀ (eV)	0°
40	6.64e-1
200	5.07e-1
600	4.36e-1
3000	3.82e-1
5000	3.53e-1
9000	3.38e-1

Energy reflection coefficient of Ne backscattered from Pt

ne = 6, na = 1

E ₀ (eV)	0°
40	3.40e-1
200	2.34e-1
600	1.90e-1
3000	1.70e-1
5000	1.42e-1
9000	1.48e-1

Average depth (mean range) in Å of Ne implanted in Pt

ne = 6, na = 1

B ₀ (eV)	0°
40	5.71e+0
200	1.19e4-1
600	2.07e+1
3000	5.37e+1
5000	6.84e+1
9000	1.10e+2

Xe -> Pt

Sputtering yield of Pt by Xe
 $z1=54$, $m1 = 131.30$, $z2=78$, $m2 = 195.09$, $sbe=5.86$ eV, $\rho=21.44$ g/cm**3
 $ef=0.50$ eV, $esb=0.00$ eV, $ca=1.00$, $kk0=kk0r=2$, $kdee1 = kdee2 = 3$, $ipotr=ipotr=1$ (KrC)
 program : trvmc95, trspvmcx
 $ne = 8$, $na = 2$

Eo(eV)	0°	30°
40	8.42e-4	
200	3.35e-1	
500		1.47e-0
600	1.33e-0	
1000		2.49e-0
1500		3.24e-0
3000	4.08e-0	
5000	5.25e-0	

Sputtered energy of Pt by Xe
 $ne = 8$, $na = 2$

Eo(eV)	0°	30°
40	5.16e-5	
200	1.53e-2	
500		6.13e-2
600	3.33e-2	
1000		6.86e-2
1500		6.87e-2
3000	3.83e-2	
5000	3.62e-2	

Particle reflection coefficient of Xe backscattered from Pt
 $z1=54$, $m1 = 131.30$, $z2=78$, $m2 = 195.09$, $sbe=5.86$ eV, $\rho=21.44$ g/cm**3
 $ef=0.50$ eV, $esb=0.00$ eV, $ca=1.00$, $kk0=kk0r=2$, $kdee1 = kdee2=3$, $ipotr=ipotr=1$ (KrC)
 program : trvmc95, trspvmcx
 $ne = 8$, $na = 2$

E _o (eV)	0°	30°
40	2.27e-1	
200	1.91e-1	
500		2.31e-1
600	1.54e-1	
1000		2.10e-1
1500		1.90e-1
3000	1.03e-1	
5000	9.15e-2	

Energy reflection coefficient of Xe backscattered from Pt
 $ne = 8$, $na = 2$

B _o (eV)	0°	30°
40	1.48e-2	
200	1.39e-2	
500		3.14e-2
600	1.12e-2	
1000		2.61e-2
1500		2.37e-2
3000	7.38e-3	
5000	6.56e-3	

Average depth (mean range) in Å of Xe implanted in Pt
 $ne = 8$, $na = 2$

E _o (eV)	0°	30°
40	2.43e+0	
200	5.60e+0	
500		8.00e+0
600	9.22e+0	
1000		1.08e+1
1500		1.29e+1
3000	1.97e+1	
5000	2.52e+1	

$\mu \rightarrow \text{Au}$

Particle reflection coefficient of p . backscattered from Au
 $z1 = 1$. mix 0.11. $z2 = 79$. $m2 = 196.97$. $sbe = 3.80$ eV. $\rho = 19.31$ g/cm³
 $ef = 0.50$ eV. $esb = 0.00$ eV. $ca = 1.00$. $kk0 = kk0r = 2$. $kdee2 = 3$. $ipot = ipotr = 1$ (KrC)
 10 - 1000 eV : $kdee1 = 3$. 1000 - 20000 eV : $kdee1 = 4$
 program: trvmc
 $ne = 8$, $na = 1$

E_0 (eV)	0°
10	6.72e-1
100	4.83e-1
500	3.79e-1
1000	3.15e-1
1000	2.46e-1
5000	1.24e-1
10000	8.52e-2
20000	4.85e-2

Energy reflection coefficient of β . backscattered from Au
 $ne = 8$, $na = 1$

E_0 (eV)	0°
10	4.27e-1
100	2.43e-1
500	1.69e-1
1000	1.29e-1
1000	9.43e-2
5000	4.13e-2
10000	2.69e-2
20000	1.66e-2

Average depth (mean range) in Å of μ . implanted in Au
 $ne = 8$, $na = 1$

B_0 (eV)	0°
10	8.74e+0
100	2.60e+1
500	6.00e+1
1000	8.80e+1
1000	7.02e+1
5000	2.01e+2
10000	3.40e+2
20000	6.06e+2

D -> Au

Sputtering yield of Au by D

z1 = 1, m1 = 2.01, z2=79, m2 = 196.97, sbe=3.80, 3.93 eV, rho = 19.31 g/cm**3
 ef=0.98 (0.90) eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee=kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx, newtrim (Laszlo), TPP 9/82
 ne=27, na= 8

Bo (eV)	0°	30°	45°	60°	65°	75°	80°	85°
120	8.40e-5				5.88e-5			
130	2.44e-4				1.89e-4	9.63e-5		
135	3.49e-4	2.68e-4	2.58e-4		2.86e-4			
140	4.92e-4		5.34e-4		4.11e-4	2.10e-4	8.94e-5	
150	7.96e-4	8.35e-4	8.74e-4	7.45e-4	6.86e-4	3.63e-4	1.71e-4	
155	9.27e-4							
160	1.14e-3				1.04e-3	5.78e-4	2.56e-4	
165	1.33e-3							
170		1.73e-3	1.63e-3	1.60e-3		8.27e-4	3.78e-4	
180	2.01e-3					1.09e-3	5.76e-4	
190						1.48e-3	7.85e-4	
200	3.05e-3	3.27e-3	3.41e-3	3.34e-3	3.08e-3	1.89e-3	9.39e-4	
210							1.24e-3	
250	5.45e-3	6.16e-3	6.59e-3	6.96e-3		4.84e-3		
300	7.84e-3	8.68e-3	9.59e-3	1.10e-2	1.00e-2	8.81e-3	6.25e-3	1.47e-3
350				1.46e-2				
400	1.21e-2		1.60e-2			2.02e-2		
500	1.60e-2	1.67e-2	1.96e-2	2.49e-2		3.33e-2	3.25e-2	1.27e-2
700				3.76e-2				
750	2.15e-2	2.35e-2	2.79e-2			6.33e-2		
1000	2.51e-2	2.74e-2	3.43e-2	5.21e-2		8.49e-2	9.55e-2	5.98e-2
2000	2.91e-2				8.45e-2			
3000		3.73e-2	4.91e-2	7.34e-2		1.43e-1		
5000	2.98e-2							
10000	2.58e-2	3.14e-2	4.59e-2	6.81e-2		1.42e-1		
30000						1.03e-1		
kjoooo						5.73e-2		

Sputtered energy of Au by D

program: testvmcx, newtrim (Laszlo), TPP 9/82
 ne=27, na= 8

B _s (eV)	0°	30°	45°	60°	65°	75°	80°	85°
120	2.46e-7				1.81e-7			
130	9.75e-7				8.04e-7	3.85e-7		
135	1.52e-6				1.34e-6			
140	2.39e-6		2.67e-6		2.10e-6	9.99e-7	4.17e-7	
150	4.32e-6	4.70e-6	5.17e-6	4.37e-6	3.96e-6	2.05e-6	9.17e-7	
155	5.25e-6							
160	6.81e-6				6.59e-6	3.60e-6	1.54e-6	
165	8.21e-6							
170		1.15e-5	1.10e-5	1.09e-5		5.46e-6	2.50e-6	
180	1.41e-5					7.68e-6	3.95e-6	
190						1.10e-5	5.80e-6	
200	2.27e-5	2.44e-5	2.62e-5	2.57e-5	2.46e-5	1.46e-5	7.18e-6	
210							1.01e-5	
250	4.54e-5	5.13e-5	5.62e-5	5.98e-5		4.16e-5		
300	6.60e-5	7.44e-5	8.31e-5	9.62e-5	9.35e-5	7.91e-5	5.48e-5	1.32e-5
350				1.30e-4				
400	1.02e-4		1.42e-4			1.79e-4		
500	1.28e-4	1.41e-4	1.65e-4	2.06e-4		2.72e-4	2.97e-4	1.34e-4
700				2.82e-4				
750	1.53e-4	1.69e-4	2.05e-4			4.83e-4		
1000	1.64e-4	1.81e-4	2.22e-4	3.33e-4		5.99e-4	7.14e-4	5.42e-4
2000	1.29e-4				3.95e-4			
3000		1.28e-4	1.77e-4	2.56e-4		5.57e-4		
5000	7.43e-5							
10000	3.75e-5	4.55e-5	7.27e-5	1.21e-4		2.66e-4		
30000						8.20e-5		
100000						2.40e-5		

D → Au

Particle reflection coefficient of D backscattered from Au
 z1 = 1. m1 = 2.01. z2 = 79. m2 = 196.97. sbe = 3.80 ; 3.93 eV. rho = 19.31 g/cm**3
 ef = 0.98 (0.90) eV. esb = 1.00 eV. ca = 1.00. kk0 = kk0r = 2. kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrC)
 program: testvmcx. newtrim (Laszlo)
 ne = 28, na = 8

E ₀ (eV)	0°	30°	45°	60°	65°	75°	80°	85°
100	6.50e-1				8.22e-1			
120	6.43e-1				8.13e-1			
130	6.39e-1	6.72e-1	7.15e-1		8.09e-1	8.90e-1		
135	6.38e-1				8.07e-1			
140	6.36e-1		7.11e-1		8.05e-1	8.86e-1	9.43e-1	
150	6.33e-1	6.66e-1	7.09e-1	7.73e-1	8.01e-1	8.82e-1	9.40e-1	
155	6.32e-1							
160	6.30e-1				7.98e-1	8.78e-1	9.38e-1	
165	6.29e-1							
170		6.61e-1	7.03e-1	7.66e-1		8.75e-1	9.35e-1	
180	6.25e-1					8.71e-1	9.32e-1	
190						8.68e-1	9.30e-1	
200	6.19e-1	6.51e-1	6.95e-1	7.59e-1	7.86e-1	8.66e-1	9.27e-1	
210							9.25e-1	
250	6.08e-1	6.42e-1	6.85e-1	7.48e-1		8.53e-1		
300	5.99e-1	6.36e-1	6.78e-1	7.40e-1	7.68e-1	8.42e-1	9.05e-1	9.82e-1
350					7.33e-1			
400	5.84e-1		6.59e-1			8.27e-1		
500	5.70e-1	6.10e-1	6.51e-1	7.18e-1		8.12e-1	8.73e-1	9.69e-1
700				6.98e-1				
750	5.49e-1	5.80e-1	6.27e-1			7.96e-1		
1000	5.24e-1	5.65e-1	6.11e-1	6.78e-1		7.84e-1	8.35e-1	9.36e-1
2000	4.69e-1				6.66e-1			
3000		4.73e-1	5.28e-1	6.06e-1		7.14e-1		
5000	3.75e-1							
10000	2.96e-1	3.43e-1	4.11e-1	5.04e-1		6.35e-1		
30000						5.21e-1		
100000						3.96e-1		

Energy reflection coefficient of D backscattered from Au
 ne = 28, na = 8

E ₀ (eV)	0°	30°	45°	60°	65°	75°	80°	85°
100	6.50e-1				8.22e-1			
120	6.43e-1				8.13e-1			
130	6.39e-1	6.72e-1	7.15e-1		8.09e-1	8.90e-1		
135	6.38e-1				8.07e-1			
140	6.36e-1		7.11e-1		8.05e-1	8.86e-1	9.43e-1	
150	6.33e-1	6.66e-1	7.09e-1	7.73e-1	8.01e-1	8.82e-1	9.40e-1	
155	6.32e-1							
160	6.30e-1				7.98e-1	8.78e-1	9.38e-1	
165	6.29e-1							
170		6.61e-1	7.03e-1	7.66e-1		8.75e-1	9.35e-1	
180	6.25e-1					8.71e-1	9.32e-1	
190						8.68e-1	9.30e-1	
200	6.19e-1	6.51e-1	6.95e-1	7.59e-1	7.86e-1	8.66e-1	9.27e-1	
210							9.25e-1	
250	6.08e-1	6.42e-1	6.85e-1	7.48e-1		8.53e-1		
300	5.99e-1	6.36e-1	6.78e-1	7.40e-1	7.68e-1	8.42e-1	9.05e-1	9.82e-1
350					7.33e-1			
400	5.84e-1		6.59e-1			8.27e-1		
500	5.70e-1	6.10e-1	6.51e-1	7.18e-1		8.12e-1	8.73e-1	9.69e-1
700				6.98e-1				
750	5.49e-1	5.80e-1	6.27e-1			7.96e-1		
1000	5.24e-1	5.65e-1	6.11e-1	6.78e-1		7.84e-1	8.35e-1	9.36e-1
2000	4.69e-1				6.66e-1			
3000		4.73e-1	5.28e-1	6.06e-1		7.14e-1		
5000	3.75e-1							
10000	2.96e-1	3.43e-1	4.11e-1	5.04e-1		6.35e-1		
30000						5.21e-1		
100000						3.96e-1		

D -> Au

Average depth (mean range) in A of D implanted in Au
 z1 = 1, m1 = 2.01, z2=79, m2 = 196.97, sbe=3.80, 3.93 eV, rho = 19.31 g/cm**3
 ef=0.98 (0.90) eV, esb = 1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipotr=1 (KrC)
 program: testvmcx, newtrim (Laszlo)
 ne=28, na= 8

E ₀ (eV)	0°	30°	45°	60°	65°	75°	80°	85°
100	4.72e-1				4.54e+1			
120	5.17e+1				5.00e+1			
130	5.39e+1	5.34e+1	5.29e+1		5.21e+1	5.18e+1		
135	5.50e-1				5.31e+1			
140	5.60e+1		5.49e+1		5.42e+1	5.39e+1	5.37e+1	
150	5.81e-1	5.76e+1	5.70e-1	5.64e+1	5.62e+1	5.58e-1	5.56e+1	
155	5.91e+1							
160	6.01e+1				5.81e+1	5.77e+1	5.76e+1	
165	6.11e+1							
170		6.14e+1	6.08e+1	6.02e+1		5.96e+1	5.94e+1	
180	6.41e+1					6.15e+1	6.12e+1	
190						6.31e+1	6.31e+1	
200	6.77e+1	6.71e+1	6.64e+1	6.57e+1	6.51e+1	6.50e+1	6.48e+1	
210							6.65e+1	
250	7.67e+1	7.59e+1	7.48e-1	7.41e+1		7.29e-1		
300	8.48e+1	8.36e+1	8.26e-1	8.17e+1	8.08e+1	8.05e+1	8.05e+1	8.07e+1
350				8.89e+1				
400	9.94e+1		9.61e+1			9.46e+1		
500	1.13e+2	1.12e+2	1.10e+2	1.08e-2		1.07e+2	1.06e-2	1.07e+2
700				1.32e+2				
750	1.44e+2	1.42e-2	1.40e+2			1.36e+2		
1000	1.70e+2	1.68e+2	1.66e+2	1.63e+2		1.61e+2	1.60e+2	1.60e+2
2000	2.66e+2				2.49e+2			
3000		3.42e+2	3.34e+2	3.26e-2		3.18e+2		
5000	4.98e+2							
10000	8.41e+2	8.06e+2	7.70e+2	7.34e+2		7.10e+2		
30000						1.17e+3		
100000						2.44e+3		

He -> Au

Sputtering yield of Au by He

z1= 2, m1= 4.00, z2=79, m2=196.97, sbe=3.80 eV, rho=19.30 g/cm**3
 ef=3.80 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 program: trspvmcx, cascpol, case, IPP 9/82
 ne= 7, na= 2

E ₀ (eV)	0°	75°	comment
100	5.46e-3		
300	4.98e-2		
500	7.42e-2		
1000	1.06e-1		
2000	1.70e-1	4.64e-1	ca= 1.09
4000	1.31e-1		
10000	1.52e-1		

Sputtered energy of Au by He

program: trspvmcx, cascpol, case
 ne= 7, na= 2

E ₀ (eV)	0°	75°	comment
100	7.28e-5		
300	7.63e-4		
500	9.42e-4		
1000	9.91e-4		
2000	1.01e-3	3.60e-3	ca= 1.09
4000	5.26e-4		
10000	3.02e-4		

Particle reflection coefficient of He backscattered from Au

z1= 2, m1= 4.00, z2=79, m2=196.97, sbe=3.80 eV, rho=19.30 g/cm**3
 ef=3.80 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotrl (KrC)
 program: trspvmcx, cascpol, case
 ne= 8, na= 2

E ₀ (eV)	0°	75°	comment
50	6.79e-1		
100	6.41e-1		
300	5.79e-1		
500	5.60e-1		
1000	5.25e-1		
2000	4.93e-1	7.76e-1	ca=1.09
4000	4.35e-1		
10000	3.51e-1		

Energy reflection coefficient of He backscattered from Au

ne= 8, na= 2

E ₀ (eV)	0°	75°	comment
50	4.56e-1		
100	4.14e-1		
300	3.56e-1		
500	3.33e-1		
1000	3.02e-1		
2000	2.94e-1	6.25e-1	ca=1.09
4000	2.31e-1		
10000	1.80e-1		

Average depth (mean range) in Å of He implanted in Au

ne= 8, na= 2

E ₀ (eV)	0°	75°	comment
50	2.07e-H		
100	2.93e+1		
300	5.15e+1		
500	6.87e+1		
1000	1.02e+2		
2000	1.26e+2	1.18e-j-2	ca=1.09
4000	2.44e-f-2		
10000	4.19e-j-2		

He → Au

Sputtering yield of Au by He

z1 = 2, m1 = 4.00, z2=79, m2 = 196.97; sbe=3.80 eV, rho = 19.31 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2, ipot=ipot (KrC)
 alpha=0.00 program: trspvmcx
 ne= 4, na= 1, n(ipot) = 3

E ₀ (eV)	KrC	Mol	ZBL	comment
4000	1.15e-1			kdee1=kdee2 = 1 (LS)
4000	1.58e-1			kdee1=kdee2=2 (OB)
4000		1.61e-1	1.59e-1	kdee1=kdee2=3
4000	1.09e-1			kdee1=kdee2=3, ca=0.8

Sputtered energy of Au by He

ne= 4, na= 1, n(ipot)= 3

E ₀ (eV)	KrC	Mol	ZBL	comment
4000	4.34e-4			kdee1 = kdee2=1 (LS)
4000	5.87e-4			kdee1=kdee2=2 (OR)
4000		6.17e-4	5.50e-4	kdee1=kdee2 = 3
4000	4.73e-4			kdee1=kdee2=3, ca=0.8

Particle reflection coefficient of He backscattered from Au

z1 = 2, m1 = 4.00, z2=79, m2 = 196.97; sbe=3.80 eV, rho = 19.31 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2, ipot=ipot (KrC)
 alpha=0.00 program: trspvmcx
 ne= 8, na= 1, n(ipot) = 3

Eq (eV)	KrC	Mol	ZBL	comment
50	6.45e-1			kdee1=kdee2 = 1 (LS)
50	7.15e-1			kdee1 = kdee2=2 (OR)
50		7.38e-1	7.06e-1	kdee1=kdee2=3
50	6.27e-1			kdee1=kdee2=3, ca=0.8
4000	4.19e-1			kdee1=kdee2 = 1 (LS)
4000	4.28e-1			kdee1 = kdee2=2 (OR)
4000		4.28e-1	4.39e-1	kdee1 = kdee2=3
4000	4.00e-1			kdee1=kdee2=3, ca=0.8

Energy reflection coefficient of He backscattered from Au

ne= 8, na= 1, n(ipot)= 3

E ₀ (eV)	KrC	Mol	ZBL	comment
50	4.20e-1			kdee1=kdee2 = 1 (LS)
50	4.96e-1			kdee1=kdee2=2 (OR)
50		5.32e-1	4.96e-1	kdee1=kdee2=3
50	3.92e-1			kdee1 = kdee2 = 3, ca=0.8
4000	2.21e-1			kdee1=kdee2 = 1 (LS)
4000	2.25e-1			kdee1=kdee2=2 (OR)
4000		2.36e-1	2.43e-1	kdee1=kdee2=3
4000	2.00e-1			kdee1=kdee2=3, ca=0.8

Average depth (mean range) in Å of He implanted in Au

ne= 8, na= 1, n(ipot)= 3

E ₀ (eV)	KrC	Mol	ZBL	comment
50	1.84e+1			kdee1 = kdee2= 1 (LS)
50	2.41e+1			kdee1=kdee2 = 2 (OR)
50		1.59e+1	1.53e+1	kdee1=kdee2=3
50	2.79e+1			kdee1=kdee2=3, ca=0.8
4000	2.40e+2			kdee1=kdee2= 1 (LS)
4000	2.54e+2			kdee1=kdee2 = 2 (OR)
4000		2.23e+2	2.18e+2	kdee1=kdee2=3
4000	2.90e+2			kdee1 = kdee2=3, ca=0.8

Ne → Au

Sputtering yield of Au by Ne

z1=10, m1= 20.18, z2=79, m2=196.97, sbe=3.80 eV, rho=19.30 g/cm**3
 ef=3.80 eV, esb=0.00 eV, ca=1.09, kk0=kk0r=1, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 program: cascpol, case
 ne= 2, na= 2

E ₀ (eV)	0°	75°
2000	2.73e-0	2.46e-0
10000		6.53e-0

Sputtered energy of Au by Ne
 ne= 2, na= 2

Bo(eV)	0°	75°
2000	2.72e-2	4.90e-2
10000		3.93e-2

Particle reflection coefficient of Ne backscattered from Au

z1=10, m1= 20.18, z2=79, m2=196.97, sbe=3.80 eV, rho=19.30 g/cm**3
 ef=3.80 eV, esb=0.00 eV, ca=1.09, kkO=kkOr=1, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: cascpol, case
 ne= 2, na= 2

E ₀ (eV)	0°	75°
2000	4.02e-1	8.08e-1
10000		6.67e-1

Energy reflection coefficient of Ne backscattered from Au
 ne= 2, na= 2

B ₀ (eV)	0°	75°
2000	1.83e-1	6.33e-1
10000		4.71e-1

Na → Au

Sputtering yield of Au by Na

zl=11, m1 = 22.99, z2=79, m2=196.97, sbe=3.80 eV, rho = 19.30 g/cm**3
 ef= eV, esb= eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 only low fluence!
 TPP9/82
 ne= 1, na= 8

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	2.20e-0	2.45e-0	3.03e-0	3.45e-0	4.42e-0	5.62e-0	7.42e-0	8.27e-0

Sputtered energy of Au by Na

ne= 1, na= 8

Bo (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	4.12e-3	4.73e-3	6.50e-3	8.03e-3	1.13e-2	1.60e-2	2.38e-2	3.11e-2

Particle reflection coefficient of Na backscattered from Au

zl = 11, m1 = 22.99, z2=79, m2=196.97, sbe=3.80 eV, rho = 19.30 g/cm**3
 ef= eV, esb= eV, ca=1.00, kk0 = kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 only low fluence!
 ne= 1, na= 8

Bq (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	2.29e-1	2.33e-1	2.74e-1	3.06e-1	3.61e-1	4.32e-1	5.32e-1	6.71e-1

Energy reflection coefficient of Na backscattered from Au

ne= 1, na= 8

E _r (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	8.13e-2	8.78e-2	1.08e-1	1.27e-1	1.65e-1	2.21e-1	3.08e-1	4.65e-1

Average depth (mean range) in Å of Na implanted in Au

ne= 1, na= 8

B _a (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	2.39e+2	2.36e+2	2.26e+2	2.17e+2	2.07e+2	1.99e+2	1.89e+2	1.84e+2

Ar → Au

Sputtering yield of Au by Ar

z1= 18, m1= 39.95, z2=79, m2=196.97, sbe=3.80 eV, rho= 19.31 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2=3, ipot=ipotr = 1 (KrC)
 program: trspvmcx, trspvlcs, TPP 9/82
 ne= 9, na= 1

E _a (eV)	0°
50	7.43e-2
100	2.86e-1
300	9.30e-1
500	1.38e-0
1000	2.10e-0
2000	3.03e-0
3000	3.72e-0
4000	3.68e-0
100000	4.03e-0

Sputtered energy of Au by Ar

program: trspvmcx, trspvlcs
 ne= 8, na= 1

E ₀ (eV)	0°
50	5.84e-3
100	1.86e-2
300	3.31e-2
500	3.62e-2
1000	3.57e-2
2000	3.45e-2
3000	3.41e-2
4000	2.60e-2

Particle reflection coefficient of Ar backscattered from Au

z1= 18, m1= 39.95, z2=79, m2 = 196.97, sbe=3.80 eV, rho = 19.31 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdee2 = 3, ipot=ipotr=1 (KrC)
 program: trspvmcx, trspvlcs
 ne= 8, na= 1

E ₀ (eV)*	CP
50	5.67e-1
100	4.89e-1
300	3.99e-1
500	3.66e-1
1000	3.35e-1
2000	3.01e-1
3000	2.84e-1
4000	2.74e-1

Energy reflection coefficient of Ar backscattered from Au

ne= 8, na= 1

Ro (eV)	0°
50	2.04e-1
100	1.71e-1
300	1.31e-1
500	1.16e-1
1000	1.03e-1
2000	9.50e-2
3000	8.88e-2
4000	8.12e-2

Average depth (mean range) in Å of Ar implanted in Au

ne= 8, na= 1

E ₀ (eV)	0°
50	5.16e+0
100	6.96e+0
300	1.15e+1
500	1.46e+1
1000	2.06e+1
2000	3.07e+1
3000	3.78e+1
4000	4.38e+1

K -> Au

Sputtering yield of Au by K

z1 = 19, m1 = 42.00, z2=79, m2=196.97, sbe=3.80 eV, rho = 19.30 g/cm**3
 ef= eV, esb=2.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 IPP9/82
 only low fluence!
 ne= 1, na= 8

Eq(eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	4.72e-0	5.11e-0	5.99e-0	7.31e-0	8.90e-0	1.11e +1	1.33e4-1	1.30e+1

Sputtered energy of Au by K

ne= 1, na= 8

B ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	1.03e-2	1.15e-2	1.52e-2	2.06e-2	2.82e-2	3.88e-2	5.51e-2	6.62e-2

Particle reflection coefficient of K backscattered from Au

z1 = 19, m1 = 42.00, z2=79, m2=196.97, sbe=3.80 eV, rho = 19.30 g/cm**3
 ef= eV, esb = 2.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)
 only low fluence!
 ne= 1, na= 8

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	1.79e-1	1.94e-1	2.18e-1	2.60e-1	3.21e-1	3.86e-1	4.87e-1	6.41e-1

Energy reflection coefficient of K backscattered from Au

ne= 1, na= 8

Eq(eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	4.94e-2	5.55e-2	6.83e-2	9.13e-2	1.27e-1	1.75e-1	2.56e-1	4.24e-1

Average depth (mean range) in Å of K implanted in Au

ne= 1, na= 8

E ₀ (eV)	0°	15°	30°	40°	50°	60°	70°	80°
30000	1.50e+2	1.48e+2	1.43e+2	1.36e+2	1.29e+2	1.20e+2	1.16e+2	1.08e+2

Xe → Au

Sputtering yield of Au by Xe

z1=54, m1 = 131.00, z2=79, m2 = 196.97, sbe=3.80 eV, rho = 19.30 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0 = kk0r=2, kdee1 = kdee2=3, ipot=ipotr = 1 (KrC)
 program: trspvmcx, cascpol, trspstest, TPP 9/82
 ne = 9, na = 2

E ₀ (eV)	0°	75°	comment
50	2.70e-2		
100	2.16e-1		
300	1.07e-0		
500	1.71e-0		
1000	2.87e-0		
2000	4.49e-0		
2000	6.54e-0	4.29e-0	ca=1.09
3000	5.54e-0		
4000	5.95e-0		

Sputtered energy of Au by Xe

program: trspvmcx, cascpol, trspstest
 ne = 9, na = 2

E ₀ (eV)	0°	75°	comment
50	1.73e-3		
100	1.07e-2		
300	3.11e-2		
500	3.77e-2		
1000	4.14e-2		
2000	4.42e-2		
2000	6.89e-2	1.67e-1	ca=1.09
3000	4.34e-2		
4000	3.75e-2		

Particle reflection coefficient of Xe backscattered from Au

z1 = 54, m1 = 131.00, z2=79, m2 = 196.97, sbe = 3.80 eV, rho = 19.30 g/cm**3
 ef=0.50 eV, esb = 0.00 eV, ca=1.00, kk0 = kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program: trspvmcx, cascpol, trspstest
 ne = 9, na = 2

E ₀ (eV)	0°	75°	comment
50	2.36e-1		
100	2.23e-1		
300	1.79e-1		
500	1.64e-1		
1000	1.38e-1		
2000	1.27e-1		
2000	1.49e-1	7.99e-1	ca=1.09
3000	1.07e-1		
4000	9.52e-2		

Energy reflection coefficient of Xe backscattered from Au

ne = 9, na = 2

E ₀ (eV)	0°	75°	comment
50	1.73e-2		
100	1.66e-2		
300	1.33e-2		
500	1.21e-2		
1000	1.02e-2		
2000	9.71e-3		
2000	1.18e-2	4.72e-1	ca = 1.09
3000	8.04e-3		
4000	6.69e-3		

Average depth (mean range) in Å of Xe implanted in Au

ne = 9, na = 2

E ₀ (eV)	0°	75°	comment
50	3.34e+0		
100	4.75e+0		
300	7.76e+0		
500	9.73e+0		
1000	1.32e+1		
2000	1.83e+1		
2000	1.12e+1	7.29e+0	ca=1.09
3000	2.18e+1		
4000	2.56e+1		

Au → Au

Sputtering yield of Au by Au

z1 = 79, IX11 = 196.97, z2 = 79, m2 = 196.97, sbe = 3.93 eV, rho = 19.30 g/cm**3
 ef = 3.43 eV, esb = 3.93 eV, ca = 1.00, kk0 = kk0r = 2, kdec1 = kdec2 = 3, ipot = ipotr = 1 (KrC)
 program: newtrim (Laszlo)
 ne = 24, na = 2

E ₀ (eV)	0°	65°
10		5.28e-5
12		5.31e-4
13		1.10e-3
14		1.98e-3
15		3.11e-3
20		1.61e-2
30	5.97e-4	6.51e-2
33	1.20e-3	
37	2.65e-3	
40	4.49e-3	1.28e-1
50	1.34e-2	
60	3.03e-2	
80	8.38e-2	
100	1.50e-1	
120	2.11e-1	
140	2.80e-1	
150	3.11e-1	
170	3.91e-1	
200	5.09e-1	
250	6.74e-1	
300	8.36e-1	
400	1.22e-0	
500	1.40e-0	
600	1.60e-0	2.74e-0

Sputtered energy of Au by Au

ne = 24, na = 2

E ₀ (eV)	0°	65°
10		1.09e-5
12		1.03e-4
13		2.07e-4
14		3.74e-4
15		6.07e-4
20		3.33e-3
30	3.46e-5	1.37e-2
33	7.01e-5	
37	1.51e-4	
40	2.52e-4	2.65e-2
50	7.12e-4	
60	1.50e-3	
80	3.59e-3	
100	6.15e-3	
120	7.93e-3	
140	1.02e-2	
150	1.06e-2	
170	1.30e-2	
200	1.52e-2	
250	1.86e-2	
300	2.13e-2	
400	2.63e-2	
500	2.78e-2	
600	2.87e-2	1.89e-1

Au → Au

Particle reflection coefficient of Au backscattered from Au
 z1=79. m1 = 196.97. z2=79. m2 = 196.97. sbe = 3.93 eV. rho = 19.30 g/cm**3
 ef=3.43 eV. esb = 3.93 eV. ca=1.00. kk0 = kk0r=2. kdee1 = kdee2 = 3. ipots=ipotr = 1 (KrC)
 program: newtrim (Laszlo)
 ne=24. na= 2

R _n (eV)	0°	65°
10		2.21e-4
12		1.47e-3
13		2.94e-3
14		5.23e-3
15		8.92e-3
20		4.19e-2
30	1.44e-5	1.55e-1
33	2.86e-5	
37	1.09e-4	
40	1.89e-4	2.74e-1
50	7.22e-4	
60	1.68e-3	
80	4.09e-3	
100	7.34e-3	
120	9.22e-3	
140	1.05e-2	
150	1.33e-2	
170	1.57e-2	
200	1.90e-2	
250	2.18e-2	
300	2.59e-2	
400	2.45e-2	
500	2.48e-2	
600	2.86e-2	4.96e-1

Energy reflection coefficient of Au backscattered from Au
 ne=24. na= 2

E ₀ (eV)	0°	65°
10		5.30e-5
12		3.57e-4
13		7.09e-4
14		1.29e-3
15		2.22e-3
20		1.13e-2
30	7.91e-7	4.73e-2
33	1.92e-6	
37	6.14e-6	
40	1.09e-5	9.06e-2
50	4.28e-5	
60	1.04e-4	
80	2.55e-4	
100	4.48e-4	
120	4.47e-4	
140	5.23e-4	
150	6.71e-4	
170	8.79e-4	
200	9.23e-4	
250	9.22e-4	
300	9.99e-4	
400	8.09e-4	
500	9.82e-4	
600	1.44e-3	1.95e-1

Average depth (mean range) in Å of Au implanted in Au
 ne=24. na= 2

E ₀ (eV)	0°	65°
10		1.97e-1
12		2.23e-1
13		2.41e-1
14		2.63e-1
15		2.78e-1
20		3.62e-1
30	1.80e+0	5.63e-1
33	1.93e+0	
37	2.25e+0	
40	2.55e+0	7.84e-1
50	2.93e+0	
60	3.27e+0	
80	3.85e+0	
100	4.31e+0	
120	4.74e+0	
140	5.13e+0	
150	5.31e+0	
170	5.65e+0	
200	6.10e+0	
250	6.82e+0	
300	7.53e+0	
400	8.65e+0	
500	9.42e+0	
600	1.00e+1	6.81e+0

Au → Au

Backward sputtering, forward sputtering, transmission; backscattering
 z1=79, m1=196.97, z2=79, m2=196.97, sbe=3.80 eV, rho=19.31 g/cm**3
 ef=3.75 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 e0=2.3e-f-8 eV, dx=1000 Å
 program: trvmc95
 na= 3

alpha(degree)	Y	Y _F	YT	Y _{Tb}	T _N	T _F	R _N	Re
0	1.52e+0	1.26e-5	1.61e+0	9.28e-5	1.00e-0	9.90e-1		
45	1.89e-J-0	6.69e-5	2.00e+0	1.41e-4	1.00e-0	9.86e-1	9.99e-6	3.86e-6
70	3.93e4-0	2.12e-4	4.09e+0	2.77e-4	1.00e-0	9.71e+0	2.60e-4	1.59e-4

Kr → Hg

Sputtering yield of Hg by Kr
 z1=36, m1= 83.80, z2=80, m2=200.59, sbe=6.36 eV, rho=13.60 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl=1 (KrC)
 program : TPP 9/82
 ne=13, na=12

B ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
50	8.75e-3											
100	9.07e-2											
200	2.85e-1											
500	7.62e-1											
762	1.06e-0	1.10e-0	1.23e-0	1.43e-0	1.66e-0	1.77e-0	1.88e-0	1.99e-0	1.77e-0	1.42e-0	8.30e-1	1.45e-1
1000	1.27e-0											
2000	1.92e-0											
5000	2.88e-0											
10000	3.65e-0											
20000	4.33e-0											
50000	4.95e-0											
100000	4.92e-0											
200000	4.69e-0											

Sputtered energy of Hg by Kr
 program :
 ne=13, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
50	6.92e-4											
100	6.52e-3											
200	1.56e-2											
500	2.59e-2											
762	2.87e-2	3.02e-2	3.72e-2	4.89e-2	6.68e-2	7.86e-2	9.10e-2	1.15e-1	1.28e-1	1.15e-1	7.53e-2	1.11e-2
1000	2.93e-2											
2000	2.97e-2											
5000	2.68e-2											
10000	2.31e-2											
20000	1.88e-2											
50000	1.31e-2											
100000	8.76e-3											
200000	5.83e-3											

Kr -> Hg

Particle reflection coefficient of Kr backscattered from Hg
 z1=36. m1 = 83.80. z2=80. m2 = 200.59. sbe=6.36 eV. rho = 13.60 g/cm**3
 ef=0.50 eV. esb=0.00 eV. ca=1.00. kkO=kkOr=2, kdee1 = kdee2=3. ipot=:ipot = 1 (KrC)
 program :
 ne=13. na=12

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
50	3.49e-1											
100	3.09e-1											
200	2.65e-1											
500	2.22e-1											
762	2.02e-1	2.14e-1	2.29e-1	2.60e-1	3.13e-1	3.48e-1	3.85e-1	4.91e-1	6.50e-1	7.60e-1	8.90e-1	9.94e-1
1000	1.99e-1											
2000	1.74e-1											
5000	1.50e-1											
10000	1.33e-1											
20000	1.19e-1											
50000	9.58e-2											
100000	7.67e-2											
200000	5.52e-2											

Energy reflection coefficient of Kr backscattered from Hg
 ne=13, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
50	5.76e-2											
100	5.17e-2											
200	4.41e-2											
500	3.60e-2											
762	3.15e-2	3.49e-2	4.14e-2	5.38e-2	7.82e-2	9.71e-2	1.19e-1	1.96e-1	3.43e-1	4.74e-1	6.73e-1	9.15e-1
1000	3.14e-2											
2000	2.66e-2											
5000	2.28e-2											
10000	2.03e-2											
20000	1.83e-2											
50000	1.49e-2											
100000	1.17e-2											
200000	8.72e-3											

Average depth (mean range) in Å of Kr implanted in Hg
 ne=13, na=12

E ₀ (eV)	0°	10°	20°	30°	40°	45°	50°	60°	70°	75°	80°	85°
50	8.31e+0											
100	1.02e+1											
200	1.27e+1											
500	1.75e+1											
762	2.09e+1	2.07e+1	2.04e+1	1.97e+1	1.91e+1	1.86e+1	1.82e+1	1.73e+1	1.65e+1	1.60e+1	1.54e+1	1.43e+1
1000	2.35e+1											
2000	3.17e+1											
5000	4.94e+1											
10000	7.18e+1											
20000	1.09e+2											
50000	1.92e+2											
100000	3.18e+2											
200000	5.43e+2											

H → U

Sputtering yield of U by H

z1= 1, m1= 1.01, z2=92, m2=238.03, sbe=5.42 eV, rho=19.07 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : testvmcx, TPP 9/82
 ne= 1, na= 8

Bo(eV)	0°	30°	45°	60°	70°	80°	85°	87°
2000	4.13e-3	5.01e-3	5.78e-3	8.53e-3	1.24e-2	2.20e-2	2.38e-2	1.35e-2

Sputtered energy of U by PT

program : testvmcx
 ne= 1, na= 8

B _s (eV)	0°	30°	45°	60°	70°	80°	85°	87°
2000	1.29e-5	1.62e-5	1.85e-5	2.71e-5	3.99e-5	7.36e-5	9.37e-5	5.75e-5

Particle reflection coefficient of H backscattered from U

z1= 1, m1= 1.01, z2=92, m2=238.03, sbe=5.42 eV, rho=19.07 g/cm**3
 ef=0.95 eV, esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : testvmcx
 ne= 1, na= 8

Bo(eV)	0°	30°	45°	60°	70°	80°	85°	87°
2000	4.55e-1	4.96e-1	5.49e-1	6.26e-1	6.91e-1	7.79e-1	8.72e-1	9.50e-1

Energy reflection coefficient of Pt backscattered from U

ne= 1, na= 8

Bo(eV)	0°	30°	45°	60°	70°	80°	85°	87°
2000	2.44e-1	2.79e-1	3.28e-1	4.08e-1	4.86e-1	6.13e-1	7.63e-1	8.95e-1

Average depth (mean range) in Å of H implanted in U

ne= 1, na= 8

Bq(eV)	0°	30°	45°	60°	70°	80°	85°	87°
2000	2.81e+2	2.75e+2	2.68e+2	2.61e+2	2.56e+2	2.54e+2	2.53e+2	2.53e+2

He → U

Sputtering yield of U by He

z1= 2, m1= 4.00, z2= 92, m2=238.03, sbe=5.42 eV, rho=19.07 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdec2=3, ipot=ipotr=1 (KrC)
 program : TPP 9/82
 ne=12, na= 1

Bp(eV)	0°
200	5.40e-3
300	1.63e-2
500	2.27e-2
1000	4.45e-2
3000	6.40e-2
5000	6.54e-2
10000	5.94e-2
30000	4.57e-2
50000	3.12e-2
75000	2.59e-2
100000	2.09e-2
200000	1.26e-2

Ne → U

Sputtering yield of U by Ne

z1= 10, m1= 20.18, z2= 92, m2=238.03, sbe=5.42 eV, rho= 19.07 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdec2=3, ipot=ipotr=1 (KrC)
 program : TPP 9/82
 ne=13, na= 1

B ₀ (eV)	0°
50	7.30e-3
100	7.56e-2
300	2.96e-1
500	4.26e-1
1000	6.46e-1
2000	8.72e-1
3000	9.97e-1
5000	1.17e-0
10000	1.28e-0
30000	1.34e-0
100000	9.68e-1
300000	5.84e-1
500000	5.12e-1

Ar → U

Sputtering yield of U by Ar

z1= 10, m1= 20.18, z2= 92, m2=238.03, sbe=5.42 eV, rho= 19.07 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdeel = kdec2=3, ipot=ipotr=1 (KrC)
 program : IPP 9/82
 ne=11, na= 1

Bo(eV)	0°
50	2.22e-2
100	1.37e-1
300	5.07e-1
1000	1.19e-0
3000	2.00e-0
10000	2.77e-0
30000	3.08e-0
34300	3.05e-0
100000	2.77e-0
300000	2.10e-0
500000	1.54e-0

Kr > U

Sputtering yield of U by Kr

z1=36, m1= 83.80, z2=92, m2=238.03, sbe=5.42 eV. rho=19.07 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl (KrC)
 program : IPP 9/82
 ne=12, na=15

E ₀ (eV)	0°	15°	20°	30°	45°	50°	55°	60°	65°	70°	75°	80°
50	1.93e-2											
100	1.48e-1											
300	6.78e-1											
1000	1.70e-0											
3000	3.09e-0											
10000	4.67e-0											
17900	5.76e-0	5.88e-0	6.26e-0	6.97e-0	9.15e-0	1.01e-1	1.04e+1	1.11eH-1	1.21e+1	1.23e4-1	1.20e+1	1.05e-1-1
17930	5.47e-0											
30000	6.12e-0											
100000	6.37e-0											
300000	5.80e-0											
500000	4.93e-0											

E ₀ (eV)	82.5°	85°	87.5° ^U
17900	8.78e+0	5.96e+0	1.26e-0

Sputtered energy of U by Kr

program :
 ne= 1, na=15

H ₀ (eV)	0°	15°	20°	30°	45°	50°	55°	60°	65°	70°	75°	80°
17900	2.25e-2	2.48e-2	2.83e-2	3.61e-2	5.73e-2	6.64e-2	8.00e-2	8.98e-2	1.03e-1	1.13e-1	1.25e-1	1.27e-1

Bo (eV)	82.5°	85°	87.5° ^U
17900	1.11e-1	7.55e-2	1.41e-2

Particle reflection coefficient of Kr backscattered from U

z1=36, m1= 83.80, z2=92, m2=238.03, sbe=5.42 eV. rho=19.07 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotrl (KrC)
 program :
 ne= 1, na=15

E ₀ (eV)	0°	15°	20°	30°	45°	50°	55°	60°	65°	70°	75°	80°
17900	1.60e-1	1.71e-1	1.63e-1	1.93e-1	2.51e-1	2.94e-1	3.18e-1	3.87e-1	4.28e-1	4.97e-1	5.61e-1	6.57e-1

Bo (eV)	82.5°	85°	87.5°
17900	7.32e-1	8.47e-1	9.86e-1

Energy reflection coefficient of Kr backscattered from IT

ne= 1, na=15

Bq (eV)	0°	15°	20°	30°	45°	50°	55°	60°	65°	70°	75°	80°
17900	3.09e-2	3.13e-2	3.25e-2	4.23e-2	7.14e-2	8.80e-2	1.07e-1	1.42e-1	1.79e-1	2.27e-1	2.96e-1	4.07e-1

E ₀ (eV)	82.5°	85°	87.5°
17900	6.99e-1	8.05e-1	9.34e-1

Average depth (mean range) in Å of Kr implanted in U

ne= 1, na=15

E ₀ (eV)	0°	15°	20°	30°	45°	50°	55°	60°	65°	70°	75°	80°
17900	8.13e+1	8.29e+1	8.09e+1	7.81e+1	7.14e+1	6.90e+1	6.72e+1	6.58e-f-1	6.19e+1	6.03e+1	5.91e+1	5.87e+1

E ₀ (eV)	82.5°	85°	87.5°
17900	5.70e+1	5.51e+1	4.83e+1

Xc - U

Sputtering yield of U by Xe

z1 = 54. m1 = 131.30. z2 = 92. m2 = 238.03. sbe = 5.42 eV. rho = 19.07 g/cm**3
 ef = 0.50 eV. esb = 0.00 eV. ca = 1.00. kk0 = kk0r = 2. kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrC)
 program : TPP 9/82
 ne = 12. na = 1

E ₀ (eV)	0°
50	6.30e-3
70	3.26e-2
100	1.01e-1
200	3.72e-1
300	6.33e-1
1000	1.80e-0
3000	3.41e-0
10000	5.35e-0
30000	7.58e-0
100000	8.62e-0
300000	8.98e-0
500000	8.13e-0

Rn -> U

Sputtering yield of U by Rn

z1 = 86. m1 = 222.00. z2 = 92. m2 = 238.03. sbe = 5.42 eV. rho = 19.07 g/cm**3
 ef = 0.50 eV. esb = 0.00 eV. ca = 1.00. kk0 = kk0r = 2. kdee1 = kdee2 = 3. ipot = ipotr = 1 (KrC)
 program : IPP 9/82
 ne = 12. na = 1

R ₀ (eV)	0°
50	9.00e-4
70	9.70e-3
100	4.05e-2
150	1.37e-1
200	2.47e-1
300	4.69e-1
1000	1.62e-0
3000	3.30e-0
10000	5.85e-0
30000	8.55e-0
100000	1.12e+1
300000	1.25e+1

u->u

Sputtering yield of U by U

z1=92, m1 = 238.03, z2=92, m2=238.03, sbe=5.42 eV, rho = 19.07 g/cm**3
 ef=5.37 eV, esb=5.42 eV, ca=1.00, kk0=kkOr=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program : TPP 9/82
 ne=11, na= 1

E ₀ (eV)	0°
70	1.32e-2
100	4.84e-2
150	1.38e-1
200	2.58e-1
300	4.60e-1
500	8.84e-1
1000	1.64e-0
3000	3.35e-0
10000	6.06e-0
30000	8.50e-0
100000	1.14e+1

Sputtered energy of U by U

program : trspvmc
 ne= 7, na= 1

E _q (eV)	ca=1.00	ca=1.15
	0°	0°
70	7.78e-4	1.02e-3
100	2.28e-3	3.59e-3
200	9.19e-3	1.26e-2
500	1.95e-2	2.68e-2
1000	2.56e-2	3.40e-2
3000	2.84e-2	3.59e-2
10000	2.63e-2	2.90e-2

Particle reflection coefficient of U backscattered from U

z1=92, m1 = 238.03, z2=92, m2=238.03, sbe=5.42 eV, rho = 19.07 g/cm**3
 ef=5.37 eV, esb=5.42 eV, ca=1.00, kkO=kkOr=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program : trspvmc
 ne= 7, na= 1

E ₀ (eV)	ca=1.00	ca= 1.15
	0°	0°
70	6.60e-4	1.42e-3
100	2.90e-3	5.40e-3
200	1.26e-2	1.54e-2
500	2.15e-2	2.62e-2
1000	2.66e-2	3.17e-2
3000	2.74e-2	3.30e-2
10000	2.23e-2	2.29e-2

Energy reflection coefficient of U backscattered from U

ne= 7, na= 1

E ₀ (eV)	ca=1.00	ca=1.15
	0°	0°
70	3.46e-5	1.18e-4
100	1.38e-4	3.09e-4
200	5.83e-4	8.48e-4
500	8.93e-4	1.19e-3
1000	1.15e-3	1.30e-3
3000	1.09e-3	1.25e-3
10000	7.81e-4	9.25e-4

Average depth (mean range) in Å of U implanted in U

ne= 7, na= 1

Bo(eV)	ca=1.00	ca=1.15
	0°	0°
70	3.83e+0	2.35e-)-0
100	4.61e+0	2.95e-f-0
200	6.46e+0	4.38e+0
500	9.93e+0	7.18e-)-0
1000	1.38e+1	1.02e+1
3000	2.30e4-1	1.73e+1
10000	4.11e+1	3.28e+1

Compound targets

O -4- BeO

Sputtering yield of BeO by O

z1 = 8, m1 = 16.00

z2 = 4 (0.50), 8 (0.50), m2 = 9.01, 16.00, sbe=6.33 eV, rho = 3.01 g/cm**3

ef=6.30 eV, esb = 6.33 eV, ca=1.00, kk0 = kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: trspvmcx, TPP 9/82

only low fluence !

ne=10, na=17

Be

Eo(eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5°	65°	67.5°	70°
100	1.23e-2											
140	2.66e-2											
200	5.03e-2	6.00e-2	1.01e-1	1.62e-1	2.52e-1	3.58e-1	3.95e-1	4.22e-1		3.96e-1		3.37e-1
300	8.18e-2	9.59e-2	1.39e-1	2.19e-1	3.35e-1	4.75e-1	5.34e-1	5.82e-1	5.87e-1	5.78e-1		5.02e-1
500	1.31e-1	1.44e-1	1.99e-1	2.87e-1	4.23e-1	6.24e-1		7.94e-1		8.36e-1		7.95e-1
1000	1.92e-1	2.11e-1	2.66e-1	3.71e-1	5.38e-1	7.78e-1		1.07e-0		1.18e-0	1.24e-0	1.26e-0
2000	2.40e-1											
3000	2.54e-1	2.84e-1	3.36e-1	4.33e-1	6.12e-1	8.96e-1		1.29e-0		1.56e-0		1.81e-0
5000	2.64e-1											
10000	2.35e-1											

Be

Bo (eV)	72.5°	75°	77.5°	80°	85°
200		2.40e-1		1.27e-1	6.18e-2
300		3.66e-1		1.82e-1	6.02e-2
500		5.90e-1		2.99e-1	6.81e-2
1000	1.20e-0	1.11e-0	9.21e-1	6.52e-1	1.05e-1
3000		1.98e-0		1.76e-0	4.68e-1

O

Bq (eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5°	65°	67.5°	70°
100	5.77e-3											
140	1.46e-2											
200	2.89e-2	3.45e-2	6.70e-2	1.20e-1	2.05e-1	3.11e-1	3.55e-1	3.75e-1		3.61e-1		3.05e-1
300	5.05e-2	6.61e-2	1.01e-1	1.70e-1	2.80e-1	4.23e-1	5.03e-1	5.22e-1	5.35e-1	5.30e-1		4.64e-1
500	8.35e-2	9.99e-2	1.41e-1	2.35e-1	3.63e-1	5.48e-1		7.31e-1		7.77e-1		7.56e-1
1000	1.35e-1	1.51e-1	1.96e-1	2.93e-1	4.52e-1	6.88e-1		9.70e-1		1.09e-0	1.14e-0	1.19e-0
2000	1.81e-1											
3000	1.96e-1	2.01e-1	2.57e-1	3.54e-1	5.09e-1	7.55e-1		1.16e-0		1.43e-0		1.70e-0
5000	2.08e-1											
10000	1.88e-1											

O

Eo (eV)	72.5°	75°	77.5°	80°	85°
200		2.11e-1		1.15e-1	4.86e-2
300		3.29e-1		1.62e-1	5.45e-2
500		5.70e-1		2.72e-1	5.75e-2
1000	1.16e-0	1.06e-0	8.84e-1	6.28e-1	9.22e-2
3000		1.88e-0		1.70e-0	4.46e-1

O → BeO

Sputtered energy of BeO by O

z1 = 8, ml = 16,00

z2 = 4 (0.50); 8 (0.50); m2 = 9.01, 16.00, sbe = 6.33 eV, rho = 3.01 g/cm**3

ef=6.30 eV, esb = 6.33 eV, ca=1.00; kk0=kk0r=2; kdee1 = kdee2 = 3, ipot=ipot=1 (KrC)

program: trspvmcx

only low fluence !

ne=10, na=17

Be

B ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5°	65°	67.5°	70°
100	2.42e-4											
140	5.17e-4											
200	8.67e-4	1.20e-3	3.08e-3	7.32e-3	1.63e-2	3.20e-2	4.22e-2	4.91e-2	6.01e-2	5.39e-2		5.15e-2
300	1.25e-3	1.84e-3	3.76e-3	8.19e-3	1.84e-2	3.50e-2	4.64e-2	5.46e-2		6.44e-2		6.32e-2
500	1.73e-3	2.27e-3	3.96e-3	8.84e-3	1.80e-2	3.27e-2		5.61e-2		6.71e-2		7.34e-2
1000	1.94e-3	2.44e-3	4.13e-3	8.12e-3	1.53e-2	2.88e-2		5.00e-2		6.23e-2	6.87e-2	7.45e-2
2000	1.83e-3											
3000	1.62e-3	1.75e-3	3.14e-3	5.54e-3	1.02e-2	1.94e-2		3.56e-2		4.68e-2		6.10e-2
5000	1.38e-3											
10000	9.05e-4											

Be

B ₀ (eV)	72.5°	75°	77.5°	80°	85°
200		4.03e-2		2.12e-2	9.60e-3
300		4.79e-2		2.59e-2	7.87e-3
500		5.81e-2		3.29e-2	7.49e-3
1000	7.29e-2	7.19e-2	6.25e-2	4.62e-2	7.34e-3
3000		6.57e-2		6.28e-2	1.96e-2

O

E ₀ (eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5 ^U	65°	67.5 ^U	70°
100	2.42e-4											
140	5.17e-4											
200	8.67e-4	1.20e-3	3.08e-3	7.32e-3	1.63e-2	3.20e-2	4.22e-2	4.91e-2	6.01e-2	5.39e-2		5.15e-2
300	1.25e-3	1.84e-3	3.76e-3	8.19e-3	1.84e-2	3.50e-2	4.64e-2	5.46e-2		6.44e-2		6.32e-2
500	1.73e-3	2.27e-3	3.96e-3	8.84e-3	1.80e-2	3.27e-2		5.61e-2		6.71e-2		7.34e-2
1000	1.94e-3	2.44e-3	4.13e-3	8.12e-3	1.53e-2	2.88e-2		5.00e-2		6.23e-2	6.87e-2	7.45e-2
2000	1.83e-3											
3000	1.62e-3	1.75e-3	3.14e-3	5.54e-3	1.02e-2	1.94e-2		3.56e-2		4.68e-2		6.10e-2
5000	1.38e-3											
10000	9.05e-4											

O

E ₀ (eV)	72.5°	75°	77.5°	80°	85°
200		3.97e-2		2.28e-2	9.63e-3
300		5.07e-2		2.63e-2	8.03e-3
500		6.52e-2		3.54e-2	7.93e-3
1000	7.97e-2	7.67e-2	6.97e-2	5.43e-2	8.87e-3
3000		7.15e-2		7.21e-2	2.43e-2

O -> BeO

Particle reflection coefficient of O backscattered from

z1= 8, m1= 16.00

z2= 4 (0.50), 8 (0.50), m2= 9.01, 16.00, sbe = 6.33 eV, rho = 3.01 g/cm**3

ef=6.30 eV, esb=6.33 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: trspvmcx, TPP 9/82

only low fluence !

ne=10, na=17

Ro (eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5°	65°	67.5°	70°
100	4.70e-4											
140	1.04e-3											
200	1.33e-3	2.78e-3	7.98e-3	2.40e-2	5.98e-2	1.50e-1	2.28e-1	3.33e-1		4.64e-1		6.26e-1
300	2.17e-3	3.60e-3	8.90e-3	2.43e-2	5.76e-2	1.29e-1	1.92e-1	2.85e-1	3.52e-1	4.18e-1		5.79e-1
500	3.35e-3	4.10e-3	8.80e-3	2.04e-2	4.68e-2	1.03e-1		2.29e-1		3.42e-1		4.82e-1
1000	3.05e-3	2.80e-3	5.70e-3	1.54e-2	3.45e-2	7.77e-2		1.75e-1		2.46e-1	3.02e-1	3.66e-1
2000	1.60e-3											
3000	1.30e-3	2.40e-3	4.60e-3	9.20e-3	2.19e-2	5.05e-2		1.13e-1		1.76e-1		2.59e-1
5000	1.50e-3											
10000	6.00e-4											

Bo (eV)	72.5°	75°	77.5°	80°	85°
200		7.84e-1		9.08e-1	9.70e-1
300		7.60e-1		9.12e-1	9.82e-1
500		6.89e-1		8.87e-1	9.86e-1
1000	4.52e-1	5.48e-1	6.68e-1	7.95e-1	9.84e-1
3000		3.72e-1		5.77e-1	9.22e-1

Energy reflection coefficient of O backscattered from

only low fluence !

ne=10, na=17

Eg (eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5°	65°	67.5°	70°
100	3.04e-5											
140	6.79e-5											
200	6.65e-5	2.05e-4	7.18e-4	2.97e-3	1.06e-2	3.74e-2	6.76e-2	1.19e-1		1.98e-1		3.21e-1
300	1.06e-4	1.98e-4	7.34e-4	2.58e-3	9.50e-3	2.96e-2	5.37e-2	9.73e-2	1.32e-1	1.76e-1		2.95e-1
500	1.10e-4	2.20e-4	6.41e-4	1.98e-3	6.80e-3	2.15e-2		7.12e-2		1.30e-1		2.33e-1
1000	1.00e-4	1.43e-4	3.83e-4	1.66e-3	4.77e-3	1.43e-2		4.72e-2		8.73e-2	1.18e-1	1.55e-1
2000	1.35e-4											
3000	4.39e-5	8.83e-5	2.54e-4	6.55e-4	2.48e-3	8.56e-3		2.81e-2		5.27e-2		9.43e-2
5000	7.74e-5											
10000	2.07e-5											

Ro (eV)	72.5°	75°	77.5°	80°	85°
200		4.67e-1		6.27e-1	7.33e-1
300		4.68e-1		6.66e-1	8.05e-1
500		4.21e-1		6.62e-1	8.57e-1
1000	2.20e-1	3.04e-1	4.32e-1	5.82e-1	8.88e-1
3000		1.75e-1		3.64e-1	8.13e-1

Average depth (mean range) in Å of O implanted in

only low fluence !

ne=10, na=17

R0 (eV)	0°	10°	20°	30°	40°	50°	55°	60°	62.5°	65°	67.5°	70°
100	4.28e+0											
140	5.51e+0											
200	7.18e+0	7.08e+0	6.70e+0	6.14e+0	5.44e+0	4.69e+0	4.29e+0	3.88e+0		3.48e+0		3.12e+0
300	9.66e+0	9.50e+0	9.08e+0	8.29e+0	7.35e+0	6.42e+0	5.87e+0	5.37e+0	5.15e+0	4.87e+0		4.47e+0
500	1.40e+1	1.38e+1	1.32e+1	1.22e+1	1.08e+1	9.39e+0		8.02e+0		7.29e+0		6.66e+0
1000	2.38e+1	2.33e+1	2.23e+1	2.06e+1	1.85e+1	1.60e+1		1.35e+1		1.26e+1	1.19e+1	1.13e+1
2000	4.14e+1											
3000	5.89e+1	5.79e+1	5.51e+1	5.13e+1	4.61e+1	3.94e+1		3.30e+1		2.98e+1		2.70e+1
5000	9.25e+1											
10000	1.79e+2											

Ro (eV)	72.5°	75°	77.5°	80°	85°
200		2.67e+0		2.09e+0	1.60e+0
300		3.91e+0		3.15e+0	2.61e+0
500		6.15e+0		5.21e+0	4.03e+0
1000	1.07e+1	1.03e+1	9.70e+0	9.08e+0	7.28e+0
3000		2.44e+1		2.27e+1	1.88e+1

H -> B₄C

Sputtering yield of B4C by H
 zl= 1. ml= 1.01. z2= 5 (0.8). 6 (0.2). m2= 10.81. 12.01. alpha=0.00
 testvmx: sbe=5.73. 7.42 eV. rho=2.51 g/cm**3. ef=1.00 eV
 trspvmc: sbe=5.90. 7.40 eV. rho=2.28 g/cm**3. ef=0.90 eV
 esb= 1.00 eV. ca=1.00. kk0=kk0r=2. kdee1 = kdee2=3. ipot=ipot=1 (KrC)
 program: testvmx. IPP 9/82. trspvmc
 only low fluence !
 ne=12. na= 1

E ₀ (eV)	B	C	B + C	comment
40	3.61e-4	5.35e-5	4.15e-4	
50	1.23e-3	2.19e-4	1.45e-3	
70	2.99e-3	6.41e-4	3.63e-3	
100	5.17e-3	1.32e-3	6.49e-3	
100	5.49e-3	1.09e-3	6.58e-3	trspvmc
200	7.61e-3	1.72e-3	9.33e-3	
300	7.70e-3	1.93e-3	9.63e-3	trspvmc
333	7.93e-3	2.03e-3	9.96e-3	trspvmc
500	7.57e-3	1.83e-3	9.39e-3	
1000	6.40e-3	1.40e-3	7.80e-3	
1000	5.67e-3	1.47e-3	7.14e-3	trspvmc
2000	4.40e-3	1.06e-3	5.46e-3	trspvmc

Sputtered energy of B4C by H
 program: testvmx. trspvmc
 only low fluence !
 ne=12. na= 1

Bo (eV)	B	C	B + C	comment
40	1.17e-5	1.37e-6	1.31e-5	
50	5.10e-5	7.62e-6	5.86e-5	
70	1.43e-4	2.80e-5	1.71e-4	
100	2.45e-4	5.89e-5	3.04e-4	
100	2.68e-4	4.60e-5	3.14e-4	trspvmc
200	3.10e-4	5.81e-5	3.68e-4	
300	2.56e-4	6.13e-5	3.17e-4	trspvmc
333	2.45e-4	6.24e-5	3.17e-4	trspvmc
500	1.85e-4	4.22e-5	2.27e-4	
1000	1.01e-4	2.05e-5	1.22e-4	
1000	8.82e-5	2.05e-5	1.09e-4	trspvmc
2000	4.33e-5	1.05e-5	5.38e-5	trspvmc

H -> B₄C

Particle reflection coefficient of H backscattered from B₄C
 z1 = 1, m1 = 1.01, z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, alpha=0.00
 testvmcx: sbe=5.73, 7.42 eV, rho=2.51 g/cm**3, ef=1.00 eV
 trspvmc: sbe=5.90, 7.40 eV, rho=2.28 g/cm**3, ef=0.90 eV
 esb=1.00 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 program: testvmcx, trspvmc
 only low fluence !
 ne=12, na= 1

E ₀ (eV)	0°	comment
40	3.43e-1	
50	3.22e-1	
70	2.93e-1	
100	2.65e-1	
100	2.63e-1	trspvmc
200	2.09e-1	
300	1.76e-1	trspvmc
333	1.70e-1	trspvmc
500	1.38e-1	
1000	8.57e-2	
1000	8.43e-2	trspvmc
2000	4.35e-2	trspvmc

Energy reflection coefficient of H backscattered from B₄C
 only low fluence !
 ne=12, na= 1

E ₀ (eV)	0°	comment
40	1.57e-1	
50	1.44e-1	
70	1.28e-1	
100	1.12e-1	
100	1.11e-1	trspvmc
200	8.26e-2	
300	6.56e-2	trspvmc
333	6.25e-2	trspvmc
500	4.82e-2	
1000	2.68e-2	
1000	2.62e-2	trspvmc
2000	1.19e-2	trspvmc

Average depth (mean range) in Å of H implanted in B₄C
 only low fluence !
 ne=12, na= 1

E ₀ (eV)	0°	comment
40	1.18e+1	
50	1.40e+1	
70	1.82e+1	
100	2.43e+1	
100	2.67e+1	trspvmc
200	4.31e+1	
300	6.73e+1	trspvmc
333	7.34e+1	trspvmc
500	9.53e+1	
1000	1.76e+2	
1000	1.94e+2	trspvmc
2000	3.58e+2	trspvmc

D -> B₄C

Sputtering yield of B₄C by D

z1 = 1, m1 = 2.01, z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe = 5.73, 7.42 eV, rho = 2.51 g/cm**3

ef = 1.00 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: testvmcx, IPP 9/82

only low fluence!

ne = 11, na = 2

E ₀ (eV)	B		C		B + C	
	0°	85°	0°	85°	0°	85°
25	1.47e-4		1.90e-5		1.66e-4	
30	7.54e-4		1.02e-4		8.56e-4	
40	2.75e-3		5.28e-4		3.27e-3	
50	4.75e-3		9.73e-4		5.72e-3	
70	8.26e-3		2.07e-3		1.03e-2	
100	1.15e-2		2.71e-3		1.42e-2	
200	1.51e-2		3.50e-3		1.86e-2	
500	1.49e-2		3.67e-3		1.86e-2	
1000	1.34e-2		2.98e-3		1.63e-2	
8000	4.10e-3		1.20e-3		5.30e-3	
100000		3.06e-2		7.54e-3		3.81e-2

Sputtered energy of B₄C by D

program: testvmcx

only low fluence!

ne = 11, na = 2

E ₀ (eV)	B		C		B + C	
	0°	85°	0°	85°	0°	85°
25	6.95e-6		6.72e-7		7.62e-6	
30	4.22e-5		5.13e-6		4.73e-5	
40	1.77e-4		3.04e-5		2.07e-4	
50	3.21e-4		5.82e-5		3.79e-4	
70	5.72e-4		1.39e-4		7.11e-4	
100	7.32e-4		1.50e-4		8.82e-4	
200	7.42e-4		1.55e-4		8.97e-4	
500	4.45e-4		1.04e-4		5.49e-4	
1000	2.46e-4		5.20e-5		2.98e-4	
8000	1.91e-5		2.96e-6		2.21e-5	
100000		5.26e-5		1.04e-5		6.30e-5

D -> B₄C

Particle reflection coefficient of D backscattered from B₄C
 z1 = 1, m1 = 2.01; z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe=5.73, 7.42 eV, rho=2.51 g/cm**3
 ef=1.00 eV, esb = 1.00 eV, ca=1.00, kk0 = kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmx
 only low fluence!
 ne=11, na= 2

E ₀ (eV)	0°	85°
25	2.95e-1	
30	2.78e-1	
40	2.54e-1	
50	2.35e-1	
70	2.12e-1	
100	1.92e-1	
200	1.52e-1	
500	1.03e-1	
1000	6.68e-2	
8000	6.40e-3	
100000		2.91e-1

Energy reflection coefficient of D backscattered from B₄C
 only low fluence!
 ne=11, na= 2

B ₀ (eV)	0°	85°
25	1.09e-1	
30	1.02e-1	
40	9.17e-2	
50	8.39e-2	
70	7.42e-2	
100	6.59e-2	
200	5.03e-2	
500	3.20e-2	
1000	1.90e-2	
8000	1.28e-3	
100000		4.05e-2

Average depth (mean range) in Å of D implanted in B₄C
 only low fluence!
 ne=11, na= 2

E ₀ (eV)	0°	85°
25	7.04e+0	
30	8.10e4-0	
40	1.02e+1	
50	1.22e+1	
70	1.61e+1	
100	2.17e+1	
200	4.02e+1	
500	9.45e+1	
1000	1.85e+2	
8000	1.29e+3	
100000		9.82e+2

D B₄C

Sputtering yield of B₄C by T)

z1 = 1, m1 = 2.01, z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe = 5.98, 5.98 eV, rho = 2.52 g/cm**3

ef = 0.90 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: trspvmc

only low fluence!

ne = 3, na = 6

B

E ₀ (eV)	0°	30°	45°	60°	75°	85°
100	1.14e-2	1.74e-2	3.19e-2	5.79e-2	6.04e-2	2.50e-3
300	1.46e-2					
500	1.60e-2	2.83e-2	5.35e-2	1.05e-1	2.02e-1	4.03e-2

C

E ₀ (eV)	0°	30°	45°	60°	75°	85°
100	2.59e-3	3.84e-3	7.24e-3	1.27e-2	1.43e-2	6.15e-4
300	3.60e-3					
500	3.66e-3	7.95e-3	1.27e-2	2.55e-2	5.39e-2	1.07e-2

B + C

E ₀ (eV)	0°	30°	45°	60°	75°	85°
100	1.40e-2	2.12e-2	3.91e-2	7.06e-2	7.47e-2	3.12e-3
300	1.82e-2					
500	1.97e-2	3.63e-2	6.62e-2	1.31e-1	2.56e-1	5.10e-2

Sputtered energy of B₄C by D

only low fluence!

ne = 3, na = 6

B

E _a (eV)	0°	30°	45°	60°	75°	85°
100	7.56e-4	1.20e-3	2.37e-3	5.00e-3	7.00e-3	3.89e-4
300	5.66e-4					
500	4.57e-4	8.15e-4	1.81e-3	4.42e-3	9.76e-3	3.06e-3

C

B ₀ (eV)	0°	30°	45°	60°	75°	85°
100	1.63e-4	2.49e-4	4.95e-4	1.04e-3	1.59e-3	8.50e-5
300	1.37e-4					
500	1.04e-4	2.41e-4	4.43e-4	1.15e-3	2.80e-3	7.48e-4

B + C

E ₀ (eV)	0°	30°	45°	60°	75°	85°
100	9.19e-4	1.45e-3	2.87e-3	6.04e-3	8.59e-3	3.12e-3
300	7.03e-4					
500	5.61e-4	1.06e-3	2.25e-3	5.57e-3	1.26e-2	3.81e-3

Particle reflection coefficient of D backscattered from B₄C

z1 = 1, m1 = 2.01, z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe = 5.98, 5.98 eV, rho = 2.52 g/cm**3

ef = 0.90 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: trspvmc

only low fluence!

ne = 3, na = 6

E ₀ (eV)	0°	30°	45°	60°	75°	85°
100	1.92e-1	2.49e-1	3.40e-1	4.96e-1	8.18e-1	9.97e-1
300	1.28e-1					
500	1.04e-1	1.51e-1	2.14e-1	3.36e-1	5.55e-1	9.66e-1

Energy reflection coefficient of D backscattered from B₄C

only low fluence!

ne = 3, na = 6

E ₀ (eV)	0°	30°	45°	60°	75°	85°
100	6.56e-2	9.85e-2	1.56e-1	2.85e-1	6.66e-1	9.58e-1
300	4.14e-2					
500	3.22e-2	5.27e-2	8.58e-2	1.61e-1	3.65e-1	9.17e-1

Average depth (mean range) in Å of D implanted in B₄C

only low fluence!

ne = 3, na = 6

B ₀ (eV)	0°	30°	45°	60°	75°	85°
100	2.16e+1	2.03e+1	1.88e+1	1.74e+1	1.61e+1	1.46e+1
300	6.43e+1					
500	9.38e+1	8.73e+1	7.90e+1	6.95e+1	6.26e+1	5.89e+1

He -4- B₄C

Sputtering yield of B₄C by He

z1= 2, m1= 4.00, z2= 5 (0.8), 6 (0.2), m2= 10.81, 12.01, sbe=5.73, 7.42 eV, rho = 2.51 g/cm**3

ef=0.50 eV, esb=0.00 eV, ca=1.00, kkO=kkOr=2, kdecl = kdee2=3, ipot=ipotrl (KrC)

program: testvmcx, TPP 9/82, trspvmc

only low fluence!

ne=10., na= 5

B

E ₀ (eV)	0°	30°	60°	75°	85°	comment
30	8.92e-4					
40	3.61e-3					
50	8.27e-3					
70	1.65e-2					
100	2.51e-2					
200	4.14e-2					
500	5.70e-2					
800	5.89e-2	1.09e-1	3.77e-1	6.38e-1	3.79e-2	sbe = 5.98, 5.98 eV
1000	5.76e-2					
2000	4.72e-2					

C

E ₀ (eV)	0°	30°	60°	75°	85°	comment
30	1.45e-4					
40	7.64e-4					
50	1.77e-3					
70	3.57e-3					
100	6.09e-3					
200	9.53e-3					
500	1.26e-2					
800	1.55e-2	2.63e-2	9.33e-2	1.60e-1	8.13e-3	sbe=5.98, 5.98 eV
1000	1.30e-2					
2000	1.216e-2					

B + C

E ₀ (eV)	0°	30°	60°	75°	85°	comment
30	1.04e-3					
40	4.37e-3					
50	1.00e-2					
70	2.01e-2					
100	3.12e-2					
200	5.09e-2					
500	6.96e-2					
800	7.44e-2	1.35e-1	4.70e-1	7.98e-1	4.60e-2	sbe=5.98, 5.98 eV
1000	7.06e-2					
2000	5.93e-2					

He -> B₄C

Sputtered energy of B₄C by He
 program: testvmcx. trspvnc
 only low fluence!
 ne=10., na= 5

B

E _q (eV)	0°	30°	60°	75°	85°	comment
30	6.29e-5					
40	2.73e-4					
50	6.24e-4					
70	1.20e-3					
100	1.66e-3					
200	2.03e-3					
500	1.63e-3					
800	1.35e-3	3.10e-3	1.58e-2	3.24e-2	2.63e-3	sbe=5.98, 5.98 eV
1000	1.18e-3					
2000	6.03e-4					

C

E ₀ (eV)	0°	30°	60°	75°	85°	comment
30	1.09e-5					
40	5.64e-5					
50	1.20e-4					
70	2.36e-4					
100	4.00e-4					
200	4.78e-4					
500	3.69e-4					
800	3.98e-4	7.38e-4	3.85e-3	7.82e-3	5.22e-4	sbe=5.98, 5.98 eV
1000	2.51e-4					
2000	1.59e-4					

B + C

E ₀ (eV)	0°	30°	60°	75°	85°	comment
30	7.38e-5					
40	3.29e-4					
50	7.44e-4					
70	1.44e-3					
100	2.06e-3					
200	2.51e-3					
500	2.00e-3					
800	1.75e-3	3.84e-3	1.97e-2	4.02e-2	3.15e-3	sbe = 5.98, 5.98 eV
1000	1.43e-3					
2000	7.62e-4					

He -> B₄C

Particle reflection coefficient of He backscattered from B₄C
 z1= 2, m1= 4.00, z2= 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe=5.73, 7.42 eV, rho=2.51 g/cm**3
 ef=0.50 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: testvmcx, trspvmc
only low fluence!
 ne=10, na= 5

E ₀ (eV)	0°	30°	60°	75°	85°
30	2.47e-1				
40	2.12e-1				
50	1.88e-1				
70	1.59e-1				
100	1.33e-1				
200	9.90e-2				
500	6.88e-2				
800	5.18e-2	8.40e-2	2.71e-1	5.16e-1	9.84e-1
1000	4.85e-2				
2000	2.88e-2				

Energy reflection coefficient of He backscattered from B₄C
only low fluence!
 ne=10, na= 5

B

E _D (eV)	0°	30°	60°	75°	85°
30	5.45e-2				
40	4.64e-2				
50	4.11e-2				
70	3.42e-2				
100	2.86e-2				
200	2.07e-2				
500	1.40e-2				
800	1.07e-2	2.11e-2	1.13e-1	3.19e-1	9.45e-1
1000	9.93e-3				
2000	5.33e-3				

Average depth (mean range) in Å of He implanted in B₄C
only low fluence!
 ne=10, na= 5

B

E ₀ (eV)	0°	30°	60°	75°	85°
30	4.41e+0				
40	5.48e+0				
50	6.48e+0				
70	8.43e+0				
100	1.12e+1				
200	1.99e+1				
500	4.52e+1				
800	7.04e+1	6.27e+1	4.76e+1	4.02e+1	2.64e+1
1000	8.73e+1				
2000	1.74e+2				

C → B₄C

Sputtering yield of B₄C by C

z1= 6, m1 = 12.01, z2= 5 (0.8), 6 (0.2), m2= 10.81, 12.01. sbe = 5.98, 5.98 eV. rho=2.52 g/cm**3
 ef=2.00 eV. esb = 2.50 eV. ca=1.00, kk0= kk0r= 2, kdee1 = kdee2= 3, ipot=ipot = 1 (KrC)

program: trspmc
 only low fluence !
 ne= 4, na= 4

B

E ₀ (eV)	0°	60°	70°	80°	comment
150			3.83e-1		sbe = 5.90, 7.40 eV, esb = 2.60 eV
300			8.30e-1		sbe=5.90, 7.40 eV, esb = 2.60 eV
1000	2.10e-1	1.34e-0	1.77e-0	1.07e-0	
3000			2.24e-0		

C

E ₀ (eV)	0°	60°	70°	80°	comment
150			8.92e-2		sbe=5.90, 7.40 eV, esb = 2.60 eV
300			2.11e-1		sbe=5.90, 7.40 eV, esb = 2.60 eV
1000	4.34e-2	3.36e-1	4.47e-1	2.64e-1	
3000			5.36e-	1	

B + C

E ₀ (eV)	0°	60°	70°	80°	comment
150			4.72e-1		sbe=5.90, 7.40 eV, esb = 2.60 eV
300			1.04e-0		sbe=5.90, 7.40 eV, esb=2.60 eV
1000	2.53e-2	1.68e-0	2.22e-0	1.33e-0	
2000			2.78e-0		

Sputtered energy of B₄C by C

only low fluence !
 ne= 4, na= 4

B

Ro (eV)	0°	60°	70°	80°	comment
150			7.00e-2		sbe = 5.90, 7.40 eV, esb = 2.60 eV
300			9.73e-2		sbe=5.90, 7.40 eV, esb = 2.60 eV
1000	3.43e-3	6.47e-2	9.79e-2	7.45e-2	
3000			7.13e-	2	

C

Ro (eV)	0°	60°	70°	80°	comment
150			1.51e-2		sbe=5.90, 7.40 eV, esb=2.60 eV
300			2.50e-2		sbe=5.90, 7.40 eV, esb = 2.60 eV
1000	7.06e-4	1.70e-2	2.55e-2	1.95e-2	
3000			1.94e-2		

B + C

Ro (eV)	0°	60°	70°	80°	comment
150			8.51e-2		sbe=5.90, 7.40 eV, esb = 2.60 eV
300			1.08e-1		sbe=5.90, 7.40 eV, esb=2.60 eV
1000	4.14e-3	8.17e-2	1.23e-1	9.40e-2	
2000			9.07e-2		

c -> b₄c

Particle reflection coefficient of C backscattered from B₄C
 z1 = 6, m1= 12.01, z2= 5 (0.8), 6 (0.2), m2= 10.81, 12.01, sbe=5.98, 5.98 eV, rho=2.52 g/cm**3
 ef=2.00 eV, esb = 2.50 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3. ipot=ipot=1 (KrC)
 program: trspvnc
 only low fluence !
 ne = 4, na= 4

Eo(eV)	0°	60°	70°	80°	comment
150			6.87e-1		esb=2.60 eV
300			5.37e-1		esb = 2.60 eV
1000	4.90e-3	1.68e-1	3.36e-1	7.58e-1	
3000			2.38e-1		

Energy reflection coefficient of C backscattered from B₄C
 only low fluence !
 ne = 4, na= 4

Bo(eV)	0°	60°	70°	80°	comment
150			3.82e-1		esb=2.60 eV
300			2.75e-1		esb=2.60 eV
1000	1.98e-4	4.76e-2	1.42e-1	5.57e-1	
3000			8.65e-2		

Average depth (mean range) in A of C implanted in B₄C
 only low fluence !
 ne = 4, na= 4

Eo(eV)	0°	60°	70°	80°	comment
150			3.83e+0		esb=2.60 eV
300			6.93e4-0		esb=2.60 eV
1000	3.11e4-1	1.79e4-1	1.49e+1	1.24e+1	
3000			4.10e+1		

O → B₄C

Sputtering yield of B₄C by O

z1 = 8, m1 = 16.00, z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe = 5.90, 7.40 eV
 rho = 0.85, 1.62, 2.28, 2.52 g/cm**3, sbe(average) = 1.17, 1.28, 2.21, 5.98, 6.05 eV, alpha=0.00
 ef=2.10 eV, esb = 2.60 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipot = 1 (KrC)

program: trspvmc

only low fluence !

ne = 5, na = 1, n(rho) = 4

B

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
Ro (eV) 0°	0°	0°	0°	0°	0°	0°	
100							1.03e-2
150	4.12e-1	1.41e-1	5.90e-1	8.32e-1	3.03e-1	2.88e-2	
300	6.19e-1	2.51e-1	8.48e-1	1.29e-0	8.98e-2	5.32e-1	1.02e-1
1000	8.63e-1	4.48e-1	1.17e-0	1.68e-0	2.34e-1	8.48e-1	2.52e-1
3000	9.86e-1	5.52e-1	1.18e-0	1.79e-0	3.13e-1	9.60e-1	3.18e-1

C

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
Ro (eV) 0°	0°	0°	0°	0°	0°	0°	
100							2.31e-3
150	1.04e-1	3.37e-2	1.38e-1	1.94e-1	7.06e-2	6.12e-3	
300	1.39e-1	5.81e-2	2.26e-1	3.17e-1	2.14e-2	1.20e-1	2.46e-2
1000	1.98e-1	1.10e-1	2.93e-1	4.60e-1	5.02e-2	2.09e-1	5.61e-2
3000	2.76e-1	1.23e-1	3.02e-1	4.39e-1	6.55e-2	2.30e-1	7.04e-2

B + C

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
Ro (eV) 0°	0°	0°	0°	0°	0°	0°	
100							1.26e-2
150	5.16e-1	1.73e-1	7.28e-1	1.03e-0	3.73e-1	3.48e-2	
300	7.58e-1	3.09e-1	1.07e-0	1.61e-0	1.11e-1	6.51e-1	1.27e-1
1000	1.06e-0	5.58e-1	1.46e-0	2.14e-0	2.84e-1	1.06e-0	3.08e-1
3000	1.26e-0	6.45e-1	1.48e-0	2.23e-0	3.78e-1	1.19e-0	3.88e-1

Sputtered energy of B₄C by O

only low fluence !

ne = 5, na = 1, n(rho) = 4

B

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
Ro (eV) 0°	0°	0°	0°	0°	0°	0°	
100							3.96e-4
150	7.37e-3	3.42e-3	1.01e-2	1.36e-2	5.88e-3	9.71e-4	
300	7.85e-3	4.46e-3	9.38e-3	1.32e-2	8.49e-3	2.50e-3	2.69e-3
1000	5.72e-3	4.74e-3	6.52e-3	8.32e-3	6.63e-3	3.90e-3	4.14e-3
3000	5.13e-3	3.71e-3	4.16e-3	5.36e-3	4.36e-3	2.60e-3	2.70e-3

C

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
Ro (eV) 0°	0°	0°	0°	0°	0°	0°	
100							8.62e-5
150	1.79e-3	8.20e-4	2.07e-3	2.89e-3	1.36e-3	2.04e-4	
300	1.53e-3	9.69e-4	2.48e-3	3.10e-3	1.82e-3	5.17e-4	6.04e-4
1000	1.27e-3	1.25e-3	1.58e-3	1.96e-3	1.66e-3	8.12e-4	8.59e-4
3000	9.54e-4	4.64e-4	8.75e-4	1.51e-3	1.09e-3	6.58e-4	6.01e-4

B + C

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
Bo (eV) 0°	0°	0°	0°	0°	0°	0°	
100							4.78e-4
150	9.16e-3	4.24e-3	1.22e-2	1.65e-2	7.25e-3	1.18e-3	
300	9.38e-3	5.43e-3	1.19e-2	1.63e-2	1.03e-2	3.02e-3	3.29e-3
1000	6.98e-3	5.99e-3	8.09e-3	1.03e-2	8.30e-3	4.17e-3	4.99e-3
3000	6.08e-3	4.17e-3	5.03e-3	6.87e-3	5.45e-3	3.26e-3	3.30e-3

0 -> B₄C

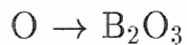
Average depth (mean range) in Å of O implanted in B₄C
 z1 = 8, m1 = 16.00, z2 = 5 (0.8), 6 (0.2), m2 = 10.81, 12.01, sbe = 5.90, 7.40 eV
 rho = 0.85, 1.62, 2.28, 2.52 g/cm**3, sbe (average) = 1.17, 1.28, 2.21, 5.98, 6.05 eV, alpha = 0.00
 ef = 2.10 eV, esb = 2.60 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trspvmc
 only low fluence !
 ne = 5, na = 1, n(rho) = 4

rho(g/cm**3)	0.85	0.85	1.62	2.28	2.28	2.28	2.52
sbe(eV)	1.17	2.21	1.28	1.17	2.21	6.05	5.98
E _o (eV) 0°	0°	0°	0°	0°	0°	0°	
100							4.89e+0
150	2.23e+1	2.19e+1	1.08e4-1	7.51e4-0	7.48e4-0	7.57e+0	
300	3.59e+1	3.45e+1	1.75e+1	1.24e+1	1.22e+1	1.24e+1	1.08e+1
1000	8.45e+1	8.21e+1	4.18e+1	3.09e+1	2.97e4-1	3.07e+1	2.71e+1
3000	2.12e+1	1.95e+2	1.05e+2	7.62e+1	7.36e+1	7.83e+1	6.68e+1

Ne B₄C

Sputtering yield of B₄C by Ne
 z1 = 10, m1 = 20.18, z2 = 5, 6, m2 = 10.81, 12.01, sbe = 6.06 eV, rho = 2.51 g/cm**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: TPP 9/82; total yield only!
 only low fluence !
 ne = 7, na = 1
 B + C

Bo (eV)	0°
100	8.10e-3
300	1.09e-1
500	1.98e-1
1000	3.34e-1
2000	4.46e-1
5000	5.40e-1
10000	5.41e-1



Sputtering yield of B_2O_3 by O

z1 = 8, m1 = 16.00, z2 = 5 (0.4), 8 (0.6), m2 = 10.81, 16.00, sbe=5.90, 2.50 eV
 rho = 1.62 g/cm**3, sbe(average) = 1.28 eV, alpha=0.00
 ef=2.10 eV, esb = 2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 program: trspvmc
 only low fluence !
 ne = 4, na = 1

E ₀ (eV)	B	O	B + O
150	3.26e-1	4.27e-1	7.52e-1
300	4.51e-1	6.21e-1	1.07e-0
1000	6.72e-1	8.54e-1	1.53e-0
3000	6.29e-1	9.17e-1	1.55e-0

Sputtered energy of B_2O_3 by O

only low fluence !
 ne = 4, na = 1

E ₀ (eV)	B	O	B + O
150	5.97e-3	7.21e-3	1.32e-2
300	5.54e-3	7.09e-3	1.26e-2
1000	4.71e-3	4.62e-3	9.33e-3
3000	2.22e-3	2.74e-3	4.95e-3

Average depth (mean range) in Å of O implanted in B_2O_3

only low fluence !
 ne = 4, na = 1

Bo (eV)	gctrc
150	1.22e+1
300	1.94e+1
1000	4.60e+1
3000	1.13e+2

O -> B(OH)₃

Sputtering yield of B(OH)₃ by O

z1 = 8, m1= 16.00, z2= 5 (0.14), 8 (0.43), 1 (0.43), m2 = 10.81, 16.00, 1.01
 sbe = 5.90, 2.50, 2.19 eV, sbe(average) = 1.22 eV, rho=0.85 g/cm**3. alpha=0.00
 ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvnc
 only low fluence !
 ne= 4, na= 1

E ₀ (eV)	B	O	H	B + O + H
150	5.95e-2	1.52e-1	1.89e-1	4.01e-1
300	9.29e-2	2.29e-1	3.62e-1	6.84e-1
1000	1.44e-1	4.07e-1	6.47e-1	1.20e-0
3000	1.32e-1	3.71e-1	7.74e-1	1.28e-0

Sputtered energy of B(OH)₃ by O

only low fluence !
 ne= 4, na= 1

E ₀ (eV)	B	O	H	B + O + H
150	1.40e-3	2.88e-3	3.63e-3	7.91e-3
300	1.46e-3	2.89e-3	4.92e-3	9.27e-3
1000	1.06e-3	2.82e-3	5.67e-3	9.55e-3
3000	1.10e-3	1.20e-3	5.02e-3	7.32e-3

Average depth (mean range) in Å of O implanted in B(OH)₃

only low fluence !
 ne= 4, na= 1

E ₀ (eV)	o ctrc
150	2.26e+1
300	3.61e+1
1000	8.05e+1
3000	1.97e+2

I — SiO₂

Particle reflection coefficient of p backscattered from SiO₂
 z1 = 1, m1 = 0.11, z2=14, 8; m2 = 28.09, 16.00, sbe=4.70 eV, rho = 2.20 g/cm**3
 ef=0.50 eV, esb= 0.00 eV, ca=1.00, kk0=kk0r=2, kdee2 = 3, ipot=ipotr=1 (KrC)
 10 - 1000 eV : kdee1 = 3, 1000 - 20000 eV : kdee1 = 4
 program: trvmc
 only low fluence !
 ne= 8, na= 1

E ₀ (eV)	QCtrc
10	5.64e-1
100	3.02e-1
500	1.48e-1
1000	8.83e-2
1000	7.88e-2
5000	1.28e-2
10000	5.10e-3
20000	1.70e-3

Energy reflection coefficient of p backscattered from SiO₂
 only low fluence !
 ne= 8, na= 1

E ₀ (eV)	Q ^{errc}
10	3.16e-1
100	1.25e-1
500	4.79e-2
1000	2.79e-2
1000	2.32e-2
5000	3.58e-3
10000	1.40e-3
20000	5.71e-4

Average depth (mean range) in Å of p implanted in SiO₂
 only low fluence !
 ne= 8, na= 1

B ₀ (eV)	gctrc
10	8.03e4-0
100	3.11e+1
500	9.03e-1
1000	1.48e+2
1000	1.33e+2
5000	4.50e+2
10000	7.93e+2
20000	1.56e+3

H → Ti Cy

Sputtering yield of Ti Gy by H

z1 = 1, m1 = 1.01, z2 = 22 (0.72, 0.6), 6 (0.28, 0.4), m2 = 47.90, 12.01, sbe = 4.89, 7.40 eV, rho = 4.93 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: trspvmcx

only low fluence !

nt = 2, na = 2

Ti

E ₀ (eV)	0°	30°	comment
500	6.79e-3		x=0.72, y=0.28
2000		6.06e-3	x=0.60, y=0.40

C

E ₀ (eV)	0°	30°	comment
500	7.37e-3		x=0.72, y=0.28
2000		6.63e-3	x=0.60, y=0.40

Ti + C

E ₀ (eV)	0°	30°	comment
500	1.42e-2		x=0.72, y=0.28
2000		1.27e-2	x=0.60, y=0.40

Sputtered energy of Ti_xC_y by H

only low fluence !

ne = 2, na = 2

Ti

E ₀ (eV)	0°	30°	comment
500	9.28e-5		x=0.72, y=0.28
2000		4.10e-5	x=0.60, y=0.40

C

E ₀ (eV)	0°	30°	comment
500	2.23e-4		x=0.72, y=0.28
2000		9.23e-5	x=0.60, y=0.40

Ti + C

E ₀ (eV)	0°	30°	comment
500	3.16e-4		x=0.72, y=0.28
2000		1.33e-4	x=0.60, y=0.40

Particle reflection coefficient of H backscattered from Ti_xGy

z1 = 1, m1 = 1.01, z2 = 22 (0.72, 0.6), 6 (0.28, 0.4), m2 = 47.90, 12.01, sbe = 4.89, 7.40 eV, rho = 4.93 g/cm**3
 ef = 0.98 eV, esb = 1.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: trspvmcx

only low fluence !

ne = 2, na = 2

E ₀ (eV)	0°	30°	comment
500	3.79e-1		x=0.72, y=0.28
2000		2.25e-1	x=0.60, y=0.40

Energy reflection coefficient of H backscattered from Ti_xCy

only low fluence !

ne = 2, na = 2

E ₀ (eV)	0°	30°	comment
500	1.92e-1		x=0.72, y=0.28
2000		9.11e-2	x=0.60, y=0.40

Average depth (mean range) in Å of H implanted in Ti_xCy

only low fluence !

ne = 2, na = 2

E ₀ (eV)	0°	30°	comment
500	9.84e+1		x=0.72, y=0.28
2000		2.62e+2	x=0.60, y=0.40

O -> WO₃

Sputtering yield of WO₃ by O

z1= 8, m1 = 16.00, z2=74 (0.25), 8 (0.75), m2 = 183.85, 16.00. sbe = 6.28, 6.28 eV, rho = 6.47 g/cm**3
 ef=2.50 eV, esb= 2.60 eV, ca=1.00. kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr = 1 (KrC)

program: trspvmc

only low fluence 1

ne=11, na= 4

W

Ro (eV)	0°	30°	60°	85°	comment
50	7.71e-5				sbe = 6.28, 6.28 eV
100	1.68e-3				sbe=6.28, 6.28 eV
200	7.79e-3				sbe = 6.28, 6.28 eV
300	1.30e-2				sbe=6.28, 6.28 eV
500	2.29e-2				sbe = 6.28, 6.28 eV
500	4.46e-2				sbe=8.68, 2.60 eV
1000	4.61e-2	8.06e-2	1.71e-1	2.38e-2	sbe = 6.28, 6.28 eV
1000	6.32e-2	8.75e-2	2.61e-1	3.58e-2	sbe = 8.68, 2.60 eV
2000	6.88e-2				sbe = 6.28, 6.28 eV
6000	8.87e-2	1.33e-1	3.26e-1	3.63e-1	sbe = 6.28, 6.28 eV
6000	1.17e-1	2.04e-1	4.87e-1	4.39e-1	sbe=8.68, 2.60 eV

O

Eo(eV)	0°	30°	60°	85°	comment
50	3.99e-2				sbe=6.28, 6.28 eV
100	1.18e-1				sbe=6.28, 6.28 eV
200	2.33e-1				sbe=6.28, 6.28 eV
300	3.03e-1				sbe=6.28, 6.28 eV
500	4.05e-1				sbe=6.28, 6.28 eV
500	5.79e-1				sbe=8.68, 2.60 eV
1000	5.43e-1	7.50e-1	1.32e-0	1.88e-1	sbe=6.28, 6.28 eV
1000	7.65e-1	9.86e-1	1.78e-0	2.44e-1	sbe = 8.68, 2.60 eV
2000	6.21e-1				sbe = 6.28, 6.28 eV
6000	6.70e-1	8.97e-1	1.74e-0	1.67e-0	sbe = 6.28, 6.28 eV
6000	8.98e-1	1.24e-0	2.27e-0	1.88e-0	sbe = 8.68, 2.60 eV

W + O

Ro (eV)	0°	30°	60°	85°	comment
50	4.00e-2				
100	1.20e-1				
200	2.41e-1				
300	3.16e-1				
500	4.28e-1				
500	6.24e-1				sbe = 8.68, 2.60 eV
1000	5.89e-1	8.31e-1	1.49e-0	2.12e-1	
1000	8.28e-1	1.07e-0	2.04e-0	2.80e-1	sbe=8.68, 2.60 eV
2000	6.90e-1				
6000	7.59e-1	1.03e-0	2.07e-0	2.30e-0	
6000	1.02e-0	1.44e-0	2.76e-0	2.32e-0	sbe = 8.68, 2.60 eV

O - 4WO₃

Sputtered energy of WO₃ by O

only low fluence !

ne=11, na= 4

W

Bo (eV)	0°	30°	60°	85°	comment
50	2.75e-6				sbe=6.28, 6.28 eV
100	8.06e-5				sbe=6.28, 6.28 eV
200	3.59e-4				sbe=6.28, 6.28 eV
300	4.52e-4				sbe=6.28, 6.28 eV
500	5.74e-4				sbe=6.28, 6.28 eV
500	9.92e-4				sbe=8.68, 2.60 eV
1000	8.91e-4	1.46e-3	4.78e-3	1.43e-3	sbe=6.28, 6.28 eV
1000	1.08e-3	1.61e-3	5.34e-3	1.77e-3	sbe=8.68, 2.60 eV
2000	1.00e-3				sbe=6.28, 6.28 eV
6000	6.27e-4	1.14e-3	3.16e-3	7.22e-3	sbe=6.28, 6.28 eV
6000	5.00e-4	1.98e-3	4.03e-3	8.53e-3	sbe=8.68, 2.60 eV

O

B _o (eV)	0°	30°	60°	85°	comment
50	6.29e-3				sbe=6.28, 6.28 eV
100	1.33e-2				sbe=6.28, 6.28 eV
200	1.89e-2				sbe=6.28, 6.28 eV
300	2.05e-2				sbe=6.28, 6.28 eV
500	2.21e-2				sbe=6.28, 6.28 eV
500	2.54e-2				sbe=8.68j 2.60 eV
1000	2.01e-2	3.22e-2	8.04e-2	1.60e-2	sbe=6.28, 6.28 eV
1000	2.20e-2	3.48e-2	8.68e-2	1.52e-2	sbe=8.68, 2.60 eV
2000	1.80e-2				sbe=6.28, 6.28 eV
6000	1.34e-2	1.89e-2	4.72e-2	5.44e-2	sbe=6.28, 6.28 eV
6000	1.26e-2	2.10e-2	4.93e-2	4.41e-2	sbe=8.68, 2.60 eV

W + O

B _o (eV)	0°	30°	60°	85°	comment
50	6.29e-3				
100	1.34e-2				
200	1.93e-2				
300	2.10e-2				
500	2.27e-2				
500	2.64e-2				sbe=8.68, 2.60 eV
1000	2.10e-2	3.37e-2	8.52e-2	1.74e-2	
1000	2.31e-2	3.64e-2	9.21e-2	1.70e-2	sbe=8.68, 2.60 eV
2000	1.90e-2				
6000	1.40e-2	2.00e-2	5.04e-2	6.16e-2	
6000	1.31e-2	2.30e-2	5.33e-2	5.26e-2	sbe=8.68, 2.60 eV

O WO₃

Particle reflection coefficient of O backscattered from WO₃
 z1 = 8, m1 = 16.00, z2 = 74 (0.25), 8 (0.75), m2 = 183.85, 16.00, sbe=6.28, 6.28 eV, rho = 6.47 g/cm**3
 ef=2.50 eV, esb = 2.60 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipotr=1 (KrC)
 program: trspvnc
 only low fluence !
 ne=11, na= 4

E ₀ (eV)	0°	30°	60°	85°	comment
50	1.33e-1				
100	1.30e-1				
200	1.24e-1				
300	1.25e-1				
500	1.18e-1				
500	1.26e-1				sbe = 8.68, 2.60 eV
1000	1.10e-1	1.61e-1	3.24e-1	9.72e-1	
1000	1.06e-1	1.51e-1	3.51e-1	9.69e-1	sbe = 8.68, 2.60 eV
2000	1.11e-1				
6000	1.01e-1	1.29e-1	2.87e-1	7.73e-1	
6000	9.32e-2	1.22e-1	2.85e-1	7.69e-1	sbe = 8.68, 2.60 eV

Energy reflection coefficient of O backscattered from WO₃
 only low fluence !
 ne=11, na= 4

E _q (eV)	0°	30°	60°	85°	comment
50	5.30e-2				
100	4.87e-2				
200	4.34e-2				
300	4.37e-2				
500	3.97e-2				
500	4.49e-2				sbe = 8.68, 2.60 eV
1000	3.77e-2	5.72e-2	1.49e-1	8.97e-1	
1000	3.68e-2	5.49e-2	1.52e-1	8.97e-1	sbe = 8.68, 2.60 eV
2000	4.03e-2				
6000	3.53e-2	4.77e-2	1.27e-1	6.43e-1	
6000	3.11e-2	4.99e-2	1.37e-1	6.49e-1	sbe = 8.68, 2.60 eV

Average depth (mean range) in Å of O implanted in WO₃
 only low fluence !
 ne=11, na= 4

E ₀ (eV)	0°	30°	60°	85°	comment
50	5.30e-10				
100	8.21e+0				
200	1.25e+1				
300	1.63e+1				
500	2.24e+1				
500	2.20e+1				sbe=8.68, 2.60 eV
1000	3.49e+1	3.12e+1	2.38e+1	1.61e+1	
1000	3.39e+1	3.13e+1	2.28e+1	1.59e+1	sbe=8.68, 2.60 eV
2000	5.61e+1				
6000	1.36e+2	1.15e+2	8.40e+1	5.62e+1	
6000	1.26e+2	1.12e+2	8.07e+1	5.43e+1	sbe=8.68, 2.60 eV

Ne -> WO₃

Sputtering yield of WO₃ by Ne

z1 = 10, m1 = 20.18, z2 = 74 (0.25), 8 (0.75), m2 = 183.85, 16.00, sbe = 6.28, 6.28 eV, rho = 6.47 g/cm³, alpha = 0.00
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdeel = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trspvmc
 only low fluence !
 ne = 5, na = 1

E ₀ (eV)	W	O	w 4- O
100	1.98e-3	1.15e-1	1.17e-1
200	8.51e-3	2.35e-1	2.44e-1
500	2.53e-2	4.58e-1	4.83e-1
1000	4.72e-2	5.89e-1	6.36e-1
5000	1.12e-1	8.36e-1	9.48e-1

Sputtered energy of WO₃ by Ne

only low fluence !
 ne = 5, na = 1

E ₀ (eV)	W	O	w + O
100	1.09e-4	1.25e-2	1.26e-2
200	3.88e-4	1.88e-2	1.92e-2
500	8.86e-4	2.50e-2	2.59e-2
1000	1.04e-3	2.18e-2	2.28e-2
5000	1.04e-3	1.78e-2	1.88e-2

Particle reflection coefficient of Ne backscattered from WO₃

z1 = 10, m1 = 20.18, z2 = 74 (0.25), 8 (0.75), m2 = 183.85, 16.00, sbe = 6.28, 6.28 eV, rho = 6.47 g/cm³, alpha = 0.00
 ef = 0.20 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdeel = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: trspvmc
 only low fluence !
 ne = 5, na = 1

E ₀ (eV)	O ⁰
100	1.44e-1
200	1.27e-1
500	1.13e-1
1000	1.06e-1
5000	9.46e-2

Energy reflection coefficient of Ne backscattered from WO₃

only low fluence !
 ne = 5, na = 1

E ₀ (eV)	0°
100	4.54e-2
200	3.91e-2
500	3.34e-2
1000	3.27e-2
5000	3.16e-2

Average depth (mean range) in Å of Ne implanted in WO₃

only low fluence !
 ne = 5, na = 1

E ₀ (eV)	0°
100	7.91e+0
200	1.18e+1
500	2.01e+1
1000	3.15e+1
5000	9.92e+1

Kr -> WO₃

Sputtering yield of WO₃ by Kr
 z1 = 36, m1 = 83.80, z2=74 (0.25), 8 (0.75), m2 = 183.85, 16.00, sbe=3.01, 3.01 eV, rho=6.47 g/cm**3, alpha=0.00
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr = 1 (KrC)
 program: trspvmc
 only low fluence !
 ne= 3, na= 1

Bq(eV)	w	O	w 4- O	comment
6000	4.81e-1	2.82e-0	3.30e-0	
10000	5.82e-1	3.26e-0	3.84e-0	
10000	3.38e-1	1.86e-0	2.20e-0	sbe=6.28, 6.28 eV

Sputtered energy of WO₃ by Kr
 only low fluence !
 ne= 3, na= 1

EO(eV)	w	O	W 4- O	comment
6000	1.96e-3	1.82e-2	2.02e-2	
10000	2.21e-3	1.62e-2	1.84e-2	
10000	2.05e-3	1.58e-2	1.79e-2	sbe=6.28, 6.28 eV

Particle reflection coefficient of Kr backscattered from WO₃
 z1 = 36, m1= 83.80, z2= 74 (0.25), 8 (0.75), m2=183.85, 16.00, sbe=3.01, 3.01 eV, rho=6.47 g/cm**3, alpha=0.00
 ef=0.20 eV, esb=0.00 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvmc
 only low fluence !
 ne= 3, na= 1

Eq(eV)	0°	comment
6000	3.50e-2	
10000	4.94e-2	
10000	4.24e-2	sbe = 6.28, 6.28 eV

Energy reflection coefficient of Kr backscattered from WO₃
 only low fluence !
 ne= 3, na= 1

E ₀ (eV)	0°	comment
6000	3.02e-3	
10000	3.33e-3	
10000	3.35e-3	sbe = 6.28, 6.28 eV

Average depth (mean range) in Å of Kr implanted in WO₃
 only low fluence !
 ne= 3, na= 1

B ₀ (eV)	0°	comment
6000	6.29e4-1	
10000	7.68e4-1	
10000	8.46e4-1	sbe = 6.28, 6.28 eV

O -> WO₄

Sputtering yield of WO₄ by O

z1= 8, mis 16.00, z2=74 (0.20), 8 (0.80), m2=183.85, 16.00, sbe=8.68, 2.60 eV, rho=6.47 g/cm**3, alpha=0.00
 ef=2.50 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: trspvmc

only low fluence !

ne= 3, na= 1

E ₀ (eV)	W	O	w + O
500	3.12e-2	6.69e-1	7.00e-2
1000	5.75e-2	8.71e-1	9.29e-2
6000	8.70e-2	9.22e-1	1.01e-3

Sputtered energy of WO₄ by O

only low fluence !

ne= 3, na= 1

B ₀ (eV)	W	O	w + O
500	5.53e-4	2.45e-2	2.51e-2
1000	7.09e-4	2.30e-2	2.37e-2
6000	5.21e-4	1.16e-2	1.21e-2

Particle reflection coefficient of O backscattered from WO₄

z1= 8, m1= 16.00, z2=74 (0.20), 8 (0.80), m2=183.85, 16.00, sbe=8.68, 2.60 eV, rho=6.47 g/cm**3, alpha=0.00
 ef=2.50 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: trspvmc

only low fluence !

ne= 3, na= 1

B _p (eV)	0°
500	1.05e-1
1000	1.03e-1
6000	7.29e-2

Energy reflection coefficient of O backscattered from WO₄

only low fluence !

ne= 3, na= 1

B ₀ (eV)	0°
500	3.32e-2
1000	3.13e-2
6000	2.37e-2

Average depth (mean range) in Å of O implanted in WO₄

only low fluence !

ne= 3, na= 1

B ₀ (eV)	0°
500	1.89e+1
1000	2.93e+1
6000	1.16e+2

0 -> W_KO_V

Sputtering yield of W_xO_y by O

z1 = 8, m1 = 16.00, z2 = 74 (x), 8 (y), m2 = 183.85, 16.00, sbe = 6.28, 6.28 eV, rho = 6.47 g/cm**3, alpha = 0.00
 ef = 2.50 eV, esb = 2.60 eV, ca = 1.00, kk0 = kk0r = 2, kdel = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: trspvmc

only low fluence !

ne = 5, na = 1, n(x) = 10

W

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
E _o (eV)										
100	2.31e-2	1.76e-2	1.60e-2							
200			5.38e-2	5.25e-2	4.22e-2					
500		1.69e-1			1.15e-1	1.00e-1	8.81e-2			
1000								1.33e-1	8.92e-2	
5000										1.43e-1

O

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
E _o (eV)										
100	2.89e-2	5.43e-2	6.76e-2							
200			1.35e-1	1.63e-1	1.83e-1					
500		2.00e-1			3.06e-1	3.35e-1	3.67e-1			
1000								4.90e-1	5.01e-1	
5000										6.29e-1

W + O

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
Bo (eV)										
100	5.20e-2	7.19e-2	8.36e-2							
200			1.89e-1	2.16e-1	2.25e-1	4.35e-1	4.55e-1			
500		3.69e-1			4.21e-1					
1000								6.23e-1	5.90e-1	
5000										7.72e-1

Sputtered energy of W_xO_y by O

only low fluence !

ne = 5, na = 1, n(x) = 10

W

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
Bo (eV)										
100	1.33e-3	9.79e-4	8.69e-4							
200			2.40e-3	2.38e-3	1.91e-3					
500		5.50e-3			3.38e-3	3.06e-3	2.63e-3			
1000								2.90e-3	1.78e-3	
5000										1.23e-3

O

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
Ro (eV)										
100	4.66e-3	8.69e-3	1.07e-2							
200			1.61e-2	1.93e-2	2.02e-2					
500		1.65e-2			2.40e-2	2.60e-2	2.62e-2			
1000								2.61e-2	2.37e-2	
5000										1.53e-2

W + O

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
E _q (eV)										
100	5.99e-3	9.67e-3	1.16e-2							
200			1.85e-2	2.17e-2	2.21e-2					
500		2.20e-2			2.74e-2	2.91e-2	2.88e-2			
1000								2.90e-2	2.55e-2	
5000										1.65e-2

O -> W_xA_y

Particle reflection coefficient of O backscattered from W_xO_y
 z1 = 8, m1 = 16.00, z2=74 (x), 8 (y), m2 = 183.85, 16.00, sbe = 6.28, 6.28 eV, rho=6.47 g/cm**3, alpha=0.00
 ef=2.50 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)
 program: trspvmc
 only low fluence !
 ne= 5, na= 1, n(x) = 10

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
E ₀ (eV)										
100	4.16e-1	3.66e-1	3.42e-1							
200			3.36e-1	3.08e-1	2.91e-1					
500		3.44e-1			2.77e-1	2.56e-1	2.33e-1			
1000								2.16e-1	1.80e-1	
5000										1.35e-1

Energy reflection coefficient of O backscattered from W_xO_y
 only low fluence !
 ne= 5, na= 1, n(x) = 10

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
E ₀ (eV)										
100	1.93e-1	1.64e-1	1.51e-1							
200			1.45e-1	1.31e-1	1.22e-1					
500		1.46e-1			1.14e-1	1.03e-1	9.13e-2			
1000								8.24e-2	6.49e-2	
5000										5.05e-2

Average depth (mean range) in Å of O implanted in W_xO_y
 only low fluence !
 ne= 5, na= 1, n(x) = 10

x	0.90	0.80	0.75	0.70	0.65	0.60	0.55	0.50	0.40	0.35
B ₀ (eV)										
100	2.78e+1	2.38e+1	2.19e+1							
200			3.15e+1	2.92e+1	2.73e+1					
500		5.38e+1			4.53e+1	4.24e+1	3.91e+1			
1000								5.45e+1	4.81e+1	
5000										1.35e+2

Layered targets

Ar → Li on Cu

Sputtering yield of Li on Cu by Ar

z1 = 18, miss 39.95

layer 1: z2 = 3, m2 = 6.94, sbe = 1.68 eV, rho = 0.53 g/cm**3

layer 2: z2 = 29, m2 = 63.54, sbes = 3.52 eV, rho = 8.95 g/cm**3

ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipots = ipotr = 1 (KrC)

program: testvmcx

e0 = 6000 eV, alpha = 0.00, dx(l) = thickness (in A) of layer l

only low fluence !

ne = 11, n(m2) = 2

dx (Å)	Li	Cu
0		3.77e-0
1	2.16e-1	4.74e-0
2	3.49e-1	4.31e-0
4	1.13e-0	2.99e-0
6	1.49e-0	1.44e-0
8	1.58e-0	8.50e-1
10	1.52e-0	4.76e-1
12	1.60e-0	3.77e-1
14	1.57e-0	2.55e-1
20	1.53e-0	1.20e-1
30	1.54e-0	4.73e-2

Sputtered energy of Li on Cu by Ar

only low fluence !

ne = 11, n(m2) = 2

dx (A)	Li	Cu
0		1.62e-2
1	1.95e-3	9.82e-3
2	3.09e-3	8.73e-3
4	4.12e-3	6.05e-3
6	5.43e-3	4.02e-3
8	6.42e-3	3.42e-3
10	6.97e-3	2.42e-3
12	7.79e-3	2.05e-3
14	8.19e-3	1.68e-3
20	8.85e-3	1.05e-3
30	8.91e-3	4.34e-4

Ar → Li on Cu

Particle reflection coefficient of Ar backscattered from Li on Cu
 $z1 = 18$, $m1 = 39.95$
 layer 1: $z2 = 3$, $m2 = 6.94$, $sbe = 1.68$ eV, $\rho = 0.53$ g/cm**3
 layer 2: $z2 = 29$, $m2 = 63.54$, $sbe = 3.52$ eV, $\rho = 8.95$ g/cm**3
 $ef = 0.50$ eV, $esb = 0.00$ eV, $ca = 1.00$, $kk0 = kk0r = 2$, $kdee1 = kdee2 = 3$, $ipotr = ipotr = 1$ (KrC)
 program: testvmcx
 $e0 = 6000$ eV, $\alpha = 0.00$, $dx(1) =$ thickness (in Å) of layer 1
only low fluence !
 $ne = 11$, $n(m2) = 2$

dx (Å)	0°
0	5.80e-2
1	3.72e-2
2	3.35e-2
4	3.83e-2
6	2.80e-2
8	2.68e-2
10	2.83e-2
12	2.92e-2
14	2.97e-2
20	2.42e-2
30	2.09e-2

Energy reflection coefficient of Ar backscattered from Li on Cu
only low fluence !
 $ne = 11$, $n(m2) = 2$

dx (Å)	0°
0	5.08e-3
1	2.79e-3
2	2.52e-3
4	2.68e-3
6	1.85e-3
8	2.16e-3
10	1.80e-3
12	1.51e-3
14	1.92e-3
20	9.27e-4
30	7.49e-4

Average depth (mean range) in Å of Ar implanted in Li on Cu
only low fluence !
 $ne = 11$, $n(m2) = 2$

dx (Å)	0°
0	4.50e+1
1	4.65effl
2	4.62effl
4	4.86effl
6	5.06effl
8	5.14effl
10	5.50e+1
12	5.57effl
14	5.75effl
20	6.33e+1
30	7.24e+1

Ar → Li on Cu

Sputtering yield of Li on Cu by Ar

z1 = 18, m1 = 39.95

layer 1: z2 = 3, m2 = 6.94, sbe = 1.67 eV, ef = 1.65 eV, rho = 4.60e-2 atoms/A**3

layer 2: z2 = 29, m2 = 63.54, sbe = 3.52 eV, ef = 3.50 eV, rho = 8.48e-2 atoms/A**3
 ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: tridyn (version 3.3), idrel = 1 (static)

e0 = 6000 eV, alpha = 0.00. dx(1) = thickness (in Å) of layer 1

only low fluence !
 ne = 15, n(m2) = 2

dx (Å)	Li	Cu
0		4.01e-0
1.5	1.03e-0	2.89e-0
2	1.36e-0	2.64e-0
3	1.83e-0	2.29e-0
4	2.13e-0	1.98e-0
5	2.46e-0	1.82e-0
5	2.12e-0	1.64e-0
6	2.51e-0	1.51e-0
7.5	2.54e-0	1.19e-0
10	2.43e-0	8.30e-1
12.5	2.27e-0	5.68e-1
15	2.15e-0	4.31e-1
20	2.09e-0	2.54e-1
25	2.09e-0	1.71e-1
30	1.93e-0	1.14e-1

Sputtered energy of Li on Cu by Ar

only low fluence !

ne = 15, n(m2) = 2

dx (Å)	Li	Cu
0		1.77e-2
1.5	2.15e-3	1.27e-2
2	2.95e-3	1.07e-2
3	3.80e-3	1.13e-2
4	5.78e-3	9.55e-3
5	6.57e-3	8.85e-3
5	5.61e-3	8.66e-3
6	6.79e-3	8.28e-3
7.5	7.92e-3	6.75e-3
10	9.21e-3	5.27e-3
12.5	1.10e-2	4.18e-3
15	1.00e-2	2.72e-3
20	1.08e-2	2.38e-3
25	1.20e-2	1.82e-3
30	1.35e-2	9.79e-4

Ar → Li on Cu

Particle reflection coefficient of Ar backscattered from Li on Cu

z1 = 18, m1 = 39.95

layer 1: z2 = 3, m2 = 6.94, sbe = 1.67 eV, ef = 1.65 eV, rho = 4.60e-2 atoms/A**3

layer 2: z2 = 29, m2 = 63.54, sbe = 3.52 eV, ef = 3.50 eV, rho = 8.48e-2 atoms/A**3

ef = 0.50 eV, esb = 0.00 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

program: tridyn (version 3.3), idrel = 1 (static)

e0 = 6000 eV, alpha = 0.00, dx(1) = thickness (in Å) of layer 1

only low fluence !

ne = 15, n(m2) = 2

dx (Å)	0°
0	5.60e-3
1.5	4.00e-3
2	3.52e-3
3	3.34e-3
4	4.28e-3
5	3.99e-3
5	3.82e-3
6	3.74e-3
7.5	4.50e-3
10	3.35e-3
12.5	1.89e-3
15	2.15e-3
20	2.09e-3
25	1.93e-3
30	1.03e-3

Energy reflection coefficient of Ar backscattered from Li on Cu

only low fluence !

ne = 15, n(m2) = 2

dx (Å)	0°
0	5.30e-2
1.5	5.20e-2
2	4.20e-2
3	5.20e-2
4	5.50e-2
5	5.70e-2
5	4.90e-2
6	5.70e-2
7.5	4.90e-2
10	4.70e-2
12.5	4.20e-2
15	4.10e-2
20	3.90e-2
25	5.10e-2
30	2.40e-2

Average depth (mean range) in Å of Ar implanted in Li on Cu

only low fluence !

ne = 15, n(m2) = 2

dx (Å)	0°
0	4.40e+1
1.5	4.71e+1
2	4.69e+1
3	4.69e+1
4	4.98e+1
5	4.79e+1
5	4.93e+1
6	4.95e+1
7.5	5.31e+1
10	5.41e+1
12.5	5.62e+1
15	5.94e+1
20	6.23e+1
25	6.66e+1
30	7.09e+1

D → Li on LiCu

Sputtering yield of Li on LiCu by D
 z1 = 1, m1 = 2.01, ef = 0.20 eV, dns0 = 1.00e-1 atoms/A**3
 layer 1: z2 = 3, m2 = 6.94, sbe = 1.67 eV, ef = 1.65 eV, rho = 4.60e-2 atoms/A**3
 layer 2: z2 = 3 (0.24), 29 (0.76), m2 = 6.94, 63.54, sbe = 1.67, 3.52 eV,
 ef = 1.65, 3.50 eV, rho = 4.60e-2, 8.48e-2 atoms/A**3
 ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: tridyn (version 3.3), idrel = 1 (static)
 alpha = 0.00, dx(1) = thickness (in A) of layer 1
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 15, n(m2) = 2

E ₀	30 eV		100 eV		300 eV		1000 eV	
	Li	Cu	Li	Gu	Li	Cu	Li	Cu
0	4.62e-2	6.00e-5	5.66e-2	8.43e-3	4.63e-2	2.55e-2	3.18e-2	2.73e-2
1	6.29e-2	2.00e-5						
1.5			8.16e-2	4.00e-3	6.94e-2	1.93e-2	4.35e-2	2.18e-2
2	8.19e-2				8.16e-2	1.45e-2	4.75e-2	1.88e-2
3	8.94e-2		1.10e-1	1.77e-3	8.41e-2	1.11e-2	5.66e-2	1.45e-2
4	9.70e-2							
5			1.30e-1	1.67e-4	1.05e-1	5.00e-3	7.00e-2	1.16e-2
6	9.16e-2							
7.5					1.22e-1	3.27e-3	8.45e-2	5.75e-3
8	8.39e-2							
10	7.36e-2		1.43e-1		1.33e-1	6.00e-4	8.35e-2	3.88e-3
15	4.85e-2		1.41e-1		1.44e-1		8.78e-2	1.50e-3
20	3.48e-2		1.25e-1		1.50e-1		8.68e-2	7.50e-4
25	2.79e-2		1.17e-1		1.46e-1		8.56e-2	2.50e-4
30	2.36e-2		1.02e-1		1.41e-1		1.01e-1	

Sputtered energy of Li on LiCu by D
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 15, n(m2) = 2

E ₀	30 eV		100 eV		300 eV		1000 eV	
	Li	Cu	Li	Cu	Li	Cu	Li	Cu
0	5.05e-3	2.01e-6	3.94e-3	2.00e-4	1.97e-3	4.68e-4	6.61e-4	3.38e-4
1	7.51e-3	5.16e-7						
1.5			6.10e-3	8.67e-5	2.95e-3	3.36e-4	8.30e-4	2.04e-4
2	9.61e-3				3.23e-3	2.54e-4	1.08e-3	1.91e-4
3	1.01e-2		7.94e-3	2.79e-5	3.40e-3	1.70e-4	1.06e-3	1.50e-4
4	1.04e-2							
5			8.82e-3	2.21e-5	4.21e-3	7.97e-5	1.24e-3	1.06e-4
6	8.91e-3							
7.5					5.08e-3	3.30e-5	1.54e-3	4.28e-5
8	7.72e-3							
10	6.48e-3		9.01e-3		5.33e-3	3.93e-6	1.40e-3	3.07e-5
15	3.82e-3		8.21e-3		5.67e-3		1.85e-3	8.35e-6
20	2.33e-3		6.88e-3		5.64e-3		1.54e-3	3.57e-6
25	1.84e-3		6.51e-3		5.69e-3		1.90e-3	1.90e-6
30	1.56e-3		5.23e-3		5.41e-3		2.20e-3	

D → Li on LiCu

Particle reflection coefficient of D backscattered from Li on LiCu
 $z1= 1, m1= 2.01, ef=0.20$ eV, $dns0=1.00e-1$ atoms/A**3
 layer 1: $z2= 3, m2= 6.94, sbe=1.67$ eV, $ef=1.65$ eV, $\rho=4.60e-2$ atoms/A**3
 layer 2: $z2= 3$ (0.24), 29 (0.76), $m2= 6.94, 63.54, sbe=1.67, 3.52$ eV,
 $ef=1.65, 3.50$ eV, $\rho=4.60e-2, 8.48e-2$ atoms/A**3
 $ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipot= 1$ (KrC)
 program: tridyn (version 3.3), idrel=1 (static)
 $\alpha=0.00, dx(l)=thickness$ (in A) of layer l
only low fluence !
 $ne= 4, na= 1, n(dx(l)) = 15, n(m2)= 2$

Eq	30 eV	100 eV	300 eV	1000 eV
dx (Å)	0°	0°	0°	0°
0	5.19e-1	4.53e-1	4.10e-1	3.24e-1
1	4.92e-1			
1.5		4.43e-1	3.93e-1	3.35e-1
2	4.79e-1		4.03e-1	3.27e-1
3	4.65e-1	4.38e-1	4.00e-1	3.30e-1
4	4.56e-1			
5		4.32e-1	3.99e-1	3.25e-1
6	4.25e-1			
7.5			3.91e-1	3.35e-1
8	3.96e-1			
10	3.62e-1	4.11e-1	3.90e-1	3.28e-1
15	2.77e-1	3.83e-1	3.76e-1	3.24e-1
20	2.19e-1	3.48e-1	3.82e-1	3.22e-1
25	1.80e-1	3.18e-1	3.64e-1	3.20e-1
30	1.60e-1	2.84e-1	3.53e-1	3.13e-1

Energy reflection coefficient of D backscattered from Li on LiCu
only low fluence !
 $ne= 4, na= 1, n(dx(l)) = 15, n(m2)= 2$

E ₀	30 eV	100 eV	300 eV	1000 eV
dx (Å)	0°	0°	0°	0°
0	3.04e-1	2.57e-1	2.24e-1	1.61e-1
1	2.67e-1			
1.5		2.41e-1	2.13e-1	1.66e-1
2	2.45e-1		2.11e-1	1.64e-1
3	2.26e-1	2.31e-1	2.11e-1	1.62e-1
4	2.11e-1			
5		2.22e-1	2.09e-1	1.62e-1
6	1.77e-1			
7.5			2.01e-1	1.64e-1
8	1.52e-1			
10	1.27e-1	1.92e-1	1.96e-1	1.60e-1
15	8.15e-2	1.63e-1	1.83e-1	1.56e-1
20	5.75e-2	1.36e-1	1.80e-1	1.52e-1
25	4.56e-2	1.15e-1	1.65e-1	1.53e-1
30	4.09e-2	9.65e-2	1.56e-1	1.45e-1

Average depth (mean range) in Å of D implanted in Li on LiCu
only low fluence !
 $ne= 4, na= 1, n(dx(l)) = 15, n(m2)= 2$

E ₀	30 eV	100 eV	300 eV	1000 eV
dx (Å)	0°	0°	0°	0°
0	1.61e-f-1	3.64e4-1	8.04e+1	2.00e+2
1	1.64e+1			
1.5		3.71e+1	7.95e+1	2.00e+2
2	1.68e4-1		8.01e+1	2.01e+2
3	1.72e+1	3.78e+1	8.09e+1	1.98e4-2
4	1.74e+1			
5		3.94e+1	8.28e-f-1	2.04e+2
6	1.79e4-1			
7.5			8.43e+1	2.05e+2
8	1.83e4-1			
10	1.84e+1	4.12e+1	8.59e+1	2.04e+2
15	1.94e+1	4.24e+1	8.89e+1	2.10e+2
20	2.07e+1	4.40e+1	9.18e+1	2.10e+2
25	2.24e-H	4.57e+1	9.32e4-1	2.13e+2
30	2.41e+1	4.72e+1	9.57e+1	2.20e+2

D → Li on LiCu

Sputtering yield of Li on LiCu by D
 z1= 1. m1= 2.01. ef=0.20 eV. dns0=1.00e-1 atoms/A**3
 layer 1: z2= 3, m2= 6.94, sbe=1.67 eV. ef=1.65 eV, rho=4.60e-2 atoms/A**3
 layer 2: z2=3 (0.06), 29 (0.94). m2= 6.94, 63.54, sbe=1.67. 3.52 eV,
 ef=1.65, 3.50 eV, rho=4.60e-2, 8.48e-2 atoms/A**3
 ca=1.00. kkO=kkOr=2, kdee1=kdee2=3, ipot=ipot=1 (KrC)
 program: tridyn (version 3.3). idrel=1 (static)
 alpha=0.00. dx(l)=thickness (in A) of layer l
 only low fluence !
 ne= 4, na= 1. n(dx(l)) = 16, n(m2)= 2

Bo	30 eV		100 eV		300 eV		1000 eV	
	Li	Cu	Li	Cu	Li	Cu	Li	Cu
0	1.33e-2		1.32e-2	1.31e-2	1.23e-2	3.88e-2	6.50e-3	5.05e-2
1	4.55e-2							
1.5			5.66e-2	7.57e-3	4.65e-2	3.09e-2	2.83e-2	3.57e-2
2	7.49e-2		7.23e-2	5.20e-3	5.57e-2	2.35e-2	4.03e-2	3.04e-2
2.5					6.45e-2	2.26e-2		
3	9.17e-2		9.15e-2	2.47e-3	7.54e-2	1.90e-2	5.11e-2	2.59e-2
4	1.01e-1							
5			1.19e-1	5.00e-4	9.89e-2	1.05e-2	5.99e-2	1.67e-2
6	1.05e-1							
7.5					1.12e-1	4.30e-3	7.49e-2	9.10e-3
8	9.49e-2							
10	8.54e-2		1.52e-1		1.31e-1	1.50e-3	8.13e-2	6.10e-3
15	5.64e-2		1.57e-1		1.40e-1	1.00e-4	9.14e-2	2.30e-3
20	3.86e-2		1.43e-1		1.46e-1		9.05e-2	8.00e-4
25	2.83e-2		1.27e-1		1.48e-1		9.42e-2	1.11e-4
30	2.64e-2		1.14e-1		1.64e-1		1.05e-1	

Sputtered energy of Li on LiCu by D
 only low fluence !
 ne= 4, na= 1, n(dx(l)) = 16, n(m2)= 2

Bq	30 eV		100 eV		300 eV		1000 eV	
	Li	Cu	Li	Cu	Li	Cu	Li	Cu
0	1.47e-3		9.94e-4	3.05e-4	5.47e-4	6.90e-4	1.68e-4	4.32e-4
1	6.14e-3							
1.5			4.90e-3	1.56e-4	1.89e-3	5.21e-4	3.62e-4	3.21e-4
2	9.43e-3		5.85e-3	8.65e-5	2.23e-3	3.55e-4	5.16e-4	2.61e-4
2.5					2.27e-3	3.49e-4		
3	1.08e-2		6.98e-3	3.54e-5	2.68e-3	2.79e-4	8.07e-4	2.27e-4
4	1.14e-2							
5			9.05e-3	4.68e-6	3.67e-3	1.49e-4	8.61e-4	1.43e-4
6	1.09e-2							
7.5					4.32e-3	5.25e-5	1.13e-3	8.24e-5
8	9.19e-3							
10	7.67e-3		9.96e-3		5.41e-3	8.10e-6	1.20e-3	6.49e-5
15	4.47e-3		9.80e-3		5.18e-3	6.66e-7	1.68e-3	1.57e-5
20	2.83e-3		8.80e-3		5.73e-3		2.00e-3	4.76e-5
25	1.87e-3		7.00e-3		5.88e-3		2.04e-3	1.43e-7
30	1.77e-3		6.12e-3		6.26e-3		2.25e-3	

D → Li on LiCu

Particle reflection coefficient of D backscattered from Li on LiCu
 z1 = 1. m1 = 2.01, ef=0.20 eV. dns0 = 1.00e-1 atoms/A**3
 layer 1: z2 = 3. m2 = 6.94, sbe=1.67 eV. ef=1.65 eV. rho = 4.60e-2 atoms/A**3
 layer 2: z2 = 3 (0.06). 29 (0.94). m2=6.94, 63.54, sbe = 1.67, 3.52 eV.
 ef=1.65, 3.50 eV, rho = 4.60e-2, 8.48e-2 atoms/A**3
 ca=1.00, kk0=kk0r=2, kdee1=kdee2 = 3, ipot=ipotr= 1 (KrC)
 program: tridyn (version 3.3). idrel=1 (static)
 alpha=0.00, dx(1) = thickness (in Å) of layer 1
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 16, n(m2) = 2

E _e	30 eV	100 eV	300 eV	1000 eV
dx (Å)	0°	0°	0°	0°
0	6.01e-1	5.16e-1	4.49e-1	3.61e-1
1	5.58e-1			
1.5		4.96e-1	4.41e-1	3.64e-1
2	5.49e-1	4.94e-1	4.46e-1	3.59e-1
2.5			4.43e-1	
3	5.34e-1	4.99e-1	4.44e-1	3.57e-1
4	5.26e-1			
5		4.83e-1	4.35e-1	3.53e-1
6	4.93e-1			
7.5			4.32e-1	3.63e-1
8	4.57e-1			
10	4.11e-1	4.60e-1	4.34e-1	3.56e-1
15	3.12e-1	4.31e-1	4.27e-1	3.49e-1
20	2.34e-1	3.99e-1	4.16e-1	3.50e-1
25	1.89e-1	3.57e-1	4.02e-1	3.54e-1
30	1.64e-1	3.24e-1	3.96e-1	3.56e-1

Energy reflection coefficient of D backscattered from Li on LiCu
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 16, n(m2) = 2

E _e	30 eV	100 eV	300 eV	1000 eV
dx (Å)	0°	0°	0°	0°
0	3.74e-1	3.06e-1	2.50e-1	1.87e-1
1	3.20e-1			
1.5		2.81e-1	2.42e-1	1.84e-1
2	2.98e-1	2.76e-1	2.45e-1	1.85e-1
2.5			2.42e-1	
3	2.74e-1	2.75e-1	2.41e-1	1.79e-1
4	2.55e-1			
5		2.57e-1	2.35e-1	1.78e-1
6	2.14e-1			
7.5			2.27e-1	1.82e-1
8	1.81e-1			
10	1.49e-1	2.22e-1	2.25e-1	1.76e-1
15	9.45e-2	1.92e-1	2.13e-1	1.73e-1
20	6.21e-2	1.61e-1	2.02e-1	1.72e-1
25	4.85e-2	1.32e-1	1.87e-1	1.69e-1
30	4.17e-2	1.11e-1	1.77e-1	1.69e-1

Average depth (mean range) in Å of D implanted in Li on LiCu
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 16, n(m2) = 2

E _e	30 eV	100 eV	300 eV	1000 eV
dx (Å)	0°	0°	0°	0°
0	1.43e+1	3.09e+1	6.46e+1	1.54e+2
1	1.46e-f-1			
1.5		3.18e4-1	6.55e+1	1.57e+2
2	1.52e+1	3.22e+1	6.62e+1	1.58e-f-2
2.5			6.63e- -1	
3	1.55e+1	3.29e- -1	6.63e+1	1.59e-)-2
4	1.59e+1			
5		3.38e+1	6.83e+1	1.61e-)-2
6	1.63e-f-1			
7.5			6.98e+1	1.60e-J-2
8	1.65e- -1			
10	1.67e+1	3.61e+1	7.06e+1	1.64e+2
15	1.77e+1	3.80e+1	7.42e+1	1.66e+2
20	1.92e- -1	3.96e+1	7.79e+1	1.72e+2
25	2.10e+1	4.14e+1	8.05e+1	1.76e+2
30	2.30e+1	4.26e+1	8.31e+1	1.79e+2

Ar → Li on LiCu

Sputtering yield of Li on LiCu by Ar
 z1 = 18, m1 = 39.95
 layer 1: z2 = 3, m2 = 6.94, sbe = 1.67 eV, ef = 1.65 eV, rho = 4.60e-2 atoms/A**3
 layer 2: z2 = 3 (0.24), 29 (0.76), m2 = 6.94, 63.54, sbe = 1.67, 3.52 eV,
 ef = 1.65, 3.50 eV, rho = 4.60e-2, 8.48e-2 atoms/A**3
 ef = 0.20, sbe = 0.00, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: tridyn (version 3.3), idrel = 1 (static)
 e0 = 6000 eV, alpha = 0.00, dx(l) = thickness (in A) of layer l
 only low fluence !
 ne = 11, n(m2) = 2

dx (Å)	Li	Cu
0	1.48e-0	2.16e-0
1.5	1.83e-0	1.74e-0
2	2.04e-0	1.51e-0
3	2.38e-0	1.36e-0
5	2.36e-0	9.55e-1
10	2.67e-0	4.71e-1
12.5	2.40e-0	3.71e-1
15	2.39e-0	2.88e-1
20	2.45e-0	2.06e-1
25	2.13e-0	1.27e-1
30	2.19e-0	7.20e-2

Sputtered energy of Li on LiCu by Ar
 only low fluence !
 ne = 15, n(m2) = 2

dx (A)	Li	Cu
0	9.27e-3	1.06e-2
1.5	1.03e-2	7.99e-3
2	9.59e-3	7.31e-3
3	1.07e-2	6.99e-3
5	1.15e-2	5.53e-3
10	1.37e-2	3.31e-3
12.5	1.46e-2	2.46e-3
15	1.45e-2	2.34e-3
20	1.50e-2	2.29e-3
25	1.68e-2	8.19e-4
30	1.81e-2	4.60e-4

Ar → Li on LiCu

Particle reflection coefficient of Ar backscattered from Li on LiCu
 z1 = 18, m1 = 39.95
 layer 1: z2 = 3, m2 = 6.94, sbe = 1.67 eV, ef = 1.65 eV, rho = 4.60e-2 atoms/A**3
 layer 2: z2 = 3 (0.24), 29 (0.76), m2 = 6.94, 63.54, sbe = 1.67, 3.52 eV,
 ef = 1.65, 3.50 eV, rho = 4.60e-2, 8.48e-2 atoms/A**3
 ef = 0.20, sbe = 0.00, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)
 program: tridyn (version 3.3), idrel = 1 (static)
 e0 = 6000 eV, alpha = 0.00, dx(l) = thickness (in Å) of layer l
 only low fluence !
 ne = 11, n(m2) = 2

dx (Å)	0°
0	4.60e-2
1.5	5.20e-2
2	4.10e-2
3	4.50e-2
5	4.00e-2
10	4.80e-2
12.5	4.00e-2
15	3.10e-2
20	3.20e-2
25	3.30e-2
30	2.50e-2

Energy reflection coefficient of Ar backscattered from Li on LiCu
 only low fluence !
 ne = 11, n(m2) = 2

dx (Å)	0°
0	3.42e-3
1.5	4.55e-3
2	2.93e-3
3	4.25e-3
5	2.71e-3
10	2.15e-3
12.5	2.18e-3
15	1.67e-3
20	1.36e-3
25	1.06e-3
30	9.20e-4

Average depth (mean range) in Å of Ar implanted in Li on LiCu
 only low fluence !
 ne = 11, n(m2) = 2

dx (Å)	0°
0	6.56e+1
1.5	6.69e+1
2	6.79e+1
3	6.81e+1
5	6.97e+1
10	7.47e+1
12.5	7.68e+1
15	7.91e+1
20	8.27e+1
25	8.50e+1
30	8.83e+1

O → B2O3 on B

Sputtering yield of R₂O₃ on B by O

z1 = 8, m1 = 16.00

1.layer: z2 = 5 (0.40), 8 (0.60), m2 = 10.81, 16.00, sbe = 5.90, 2.50 eV, rho = 1.62 g/cm**3

2.layer: z2 = 5, m2 = 10.81, sbe = 5.90 eV, rho = 2.35 g/cm**3

ef = 2.10 eV, esb = 2.60 eV, ca = 1.00, kk0 = kk0r = 2, kdeel = kdee2 = 3, ipot = ipotr = 1 (KrC)

alpha = 0.00, dx(l) = thickness of 1.layer

program: trspvmc

only low fluence !

ne = 4, na = 1, n(dx(l)) = 2

B (1.layer)

dx (Å)	5	10
E _o (eV)		
100	2.39e-1	2.53e-1
300	4.68e-1	4.72e-1
1000	5.87e-1	6.07e-1
3000		6.03e-1

O (1.layer)

dx (Å)	5	10
B _o (eV)		
100	2.86e-1	2.83e-1
300	5.56e-1	6.16e-1
1000	8.37e-1	8.07e-1
3000		7.99e-1

B (2.layer)

dx (Å)	5	10
B _o (eV)		
100	5.10e-3	
300	4.43e-2	5.13e-4
1000	1.01e-1	1.43e-2
3000		3.28e-2

Sputtered energy of B2O3 on B by O

only low fluence !

ne = 4, na = 1, n(dx(l)) = 2

B (1.layer)

dx (Å)	5	10
B _o (eV)		
100	5.90e-3	5.99e-3
300	5.06e-3	6.44e-3
1000	3.05e-3	4.19e-3
3000		2.05e-3

O (1.layer)

dx (Å)	5	10
B _o (eV)		
100	5.89e-3	6.06e-3
300	5.75e-3	6.64e-3
1000	4.42e-3	4.81e-3
3000		2.32e-3

B (2.layer)

dx (Å)	5	10
B _o (eV)		
100	1.69e-4	
300	7.62e-4	6.83e-6
1000	1.21e-3	4.22e-4
3000		4.79e-4

O → B₂O₃ on B

Particle reflection coefficient of O backscattered from B₂C₃ on B
 z1 = 8, m1 = 16.00
 1.layer: z2 = 5 (0.40), 8 (0.60), m2 = 10.81, 16.00, sbe=5.90, 2.50 eV, rho = 1.62 g/cm**3
 2.layer: z2 = 5, m2 = 10.81, sbe = 5.90 eV, rho = 2.35 g/cm**3
 ef=2.10 eV, esb = 2.60 eV, ca=1.00, kkO=kkOr=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 alpha=0.00, dx(1) =thickness of 1.layer
 program: trspvmc
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 2

dx (Å)	5	10
Bo (eV)		
100	4.37e-3	5.46e-3
300	6.58e-3	6.15e-3
1000	4.68e-3	3.96e-3
3000		1.75e-3

Energy reflection coefficient of O backscattered from B₂O₃ on B
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 2

dx (Å)	5	10
Ro (eV)		
100	1.84e-4	1.94e-4
300	3.12e-4	2.83e-4
1000	2.89e-4	7.97e-5
3000		4.88e-5

Average depth (mean range) in Å of O implanted in B₂O₃ on B
 only low fluence !
 ne = 4, na = 1, n(dx(1)) = 2

dx (Å)	5	10
Eq (eV)		
100	7.60e+0	8.94e+0
300	1.42e+1	1.59e+1
1000	3.22e-1	3.38e+1
3000		8.05e+1

0 -4 B₂O₃ on B₄C

Sputtering yield of R2O3 on B4C by O
 z1 = 8, m1= 16.00
 1.layer: z2= 5 (0.40), 8 (0.60), m2= 10.81, 16.00,
 sbe=5.90, 2.50 eV, sbe(mean) = 1.28 eV, rho = 1.62 g/cm**3
 2.layer: z2= 5 (0.80), 6 (0.20), m2= 10.81, 12.01
 sbe=5.90, 7.40 eV, sbe(mean) = 6.05 eV, rho= 2.28 g/cm**3
 ef=2.10 eV, esb = 2.60 eV. ca=1.00. kk0=kk0r=2. kdee1=kdee2=3, ipot=ipot=1 (KrC)
 alpha=0.00, dx(B2O3) = 2,...10 Å, dx(b4c) = 10000 Å
 program: trspvmc
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 4

B (1.layer)

dx (Å)	2	4	5	10
E _o (eV)				
150				3.25e-1
300				4.51e-1
1000				6.17e-1
3000	1.54e-1	5.26e-1	6.46e-1	5.74e-1

O (1.layer)

dx (Å)	2	4	5	10
E _o (eV)				
150				4.13e-1
300				5.83e-1
1000				8.45e-1
3000	1.81e-1	6.73e-1	8.45e-1	8.23e-1

B (2.layer)

dx (Å)	2	4	5	10
E _o (eV)				
300				7.12e-4
1000				1.05e-2
3000	1.22e-0	2.69e-1	1.71e-1	1.69e-2

C (2.layer)

dx (Å)	2	4	5	10
E _o (eV)				
300				3.56e-4
1000				2.09e-3
3000	2.85e-1	5.75e-2	2.81e-2	2.11e-3

Sputtered energy of B2O3 on B4G by O
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 4

B (1.layer)

dx (Å)	2	4	5	10
R _o (ev)				
150				5.82e-3
300				6.01e-3
1000				3.91e-3
3000	6.13e-4	1.37e-3	1.43e-3	2.45e-3

O (1.layer)

dx (Å)	2	4	5	10
E _o (eV)				
150				6.90e-3
300				6.66e-3
1000				5.05e-3
3000	8.13e-4	1.55e-3	2.02e-3	2.73e-3

B (2.layer)

dx (Å)	2	4	5	10
E _o (eV)				
300				2.85e-5
1000				3.08e-4
3000	2.86e-3	1.68e-3	1.79e-3	6.18e-4

C (2.layer)

dx (Å)	2	4	5	10
E _o (eV)				
300				2.28e-5
1000				4.86e-5
3000	6.19e-4	2.60e-4	2.75e-4	2.78e-5

O → B₂O₃ on B₄C

Particle reflection coefficient of O backscattered from B₂O₃ on B₄C
 z1 = 8, m1 = 16.00
 1.layer: z2 = 5 (0.40), 8 (0.60), m2 = 10.81, 16.00,
 sbe=5.90, 2.50 eV, sbe(mean) = 1.28 eV, rho = 1.62 g/cm**3
 2.layer: z2 = 5 (0.80), 6 (0.20), m2 = 10.81, 12.01
 sbe=5.90, 7.40 eV, sbe(mean) = 6.05 eV, rho = 2.28 g/cm**3
 ef=2.10 eV, esb = 2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2 = 3, ipot=ipotr=1 (KrC)
 alpha=0.00, dx(B₂O₃)=2,...10 Å, dx(b₄c) = 10000 Å
 program: trspvmc
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 2

dx (Å)	2	10
E _o (eV)		
150		4.65e-3
300		5.70e-3
1000		5.58e-3
3000	9.74e-4	4.22e-3

Energy reflection coefficient of O backscattered from B₂O₃ on B₄C
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 2

dx (Å)	2	10
E _o (eV)		
150		1.81e-4
300		1.77e-4
1000		3.88e-4
3000	5.03e-5	3.22e-4

Average depth (mean energy) in Å of O implanted in B₂O₃ on B₄C
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 4

dx (Å)	2	4	5	10
E _o (eV)				
150				1.08e4-1
300				1.59e+1
1000				3.32e+1
3000	7.38e+1	7.55e4-1	7.70e4-1	7.91e4-1

O -> B(OH)₃ on B

Sputtering yield of B(OH)₃ on B by O

z1= 8, m1= 16.00
 1.layer: z2= 5 (0.14), 8 (0.43), 1 (0.43), m2= 10.81, 16.00, 1.01,
 sbe=5.90, 2.50, 2.19 eV, rho=0.85 g/cm**3
 2.layer: z2= 5, m2= 10.81, sbe=5.90 eV, rho= 2.35 g/cm**3
 ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 alpha=0.00, dx(bo3h3) = 10 Å
 program: trspvmc
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 2

B (1.layer)

E _o (eV)	0°
100	3.61e-2
300	7.30e-2
1000	1.30e-1
3000	1.20e-1

O (1.layer)

E _o (eV)	0°
100	9.94e-2
300	2.17e-1
1000	3.15e-1
3000	3.63e-1

H (1.layer)

E _o (eV)	0°
100	1.12e-1
300	3.39e-1
1000	4.38e-1
3000	4.14e-1

B (2.layer)

E _o (eV)	0°
300	6.23e-3
1000	3.44e-2
3000	6.03e-2

Sputtered energy of B(OH)₃ on B by O

z1= 8, m1= 16.00
 1.layer: z2= 5 (0.14), 8 (0.43), 1 (0.43), m2= 10.81, 16.00, 1.01,
 sbe=5.90, 2.50, 2.19 eV, rho=0.85 g/cm**3
 2.layer: z2= 5, m2= 10.81, sbe=5.90 eV, rho= 2.35 g/cm**3
 ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl (KrC)
 alpha=0.00, dx(bo3h3) = 10 Å
 program: trspvmc
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 2

B (1.layer)

E _o (eV)	0°
100	9.75e-4
300	1.03e-3
1000	9.49e-4
3000	3.63e-4

O (1.layer)

E _o (eV)	0°
100	2.41e-3
300	2.86e-3
1000	1.97e-3
3000	1.45e-3

H (1.layer)

E _o (eV)	0°
100	2.32e-3
300	4.98e-3
1000	3.88e-3
3000	1.57e-3

B (2.layer)

E _o (eV)	0°
300	1.35e-4
1000	5.24e-4
3000	5.83e-4

O -> B(OH)₃ on B

Particle reflection coefficient of O backscattered from B(OH)₃ on B
 z1 = 8, m1 = 16.00
 1.layer: z2= 5 (0.14), 8 (0.43), 1 (0.43), m2= 10.81, 16.00, 1.01,
 sbe = 5.90, 2.50, 2.19 eV, rho = 0.85 g/cm**3
 2.layer: z2 = 5, m2= 10.81, sbe=5.90 eV, rho= 2.35 g/cm**3
 ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipot=1 (KrC)
 alpha=0.00, dx(bo3h 3)= 10 Å
 program: trspvmc
 only low fluence !
 ne= 4, na= 1, n(dx(1)) = 2

Bo (eV)	0°
100	2.98e-3
300	4.89e-3
1000	1.64e-3
3000	2.44e-3

Energy reflection coefficient of O backscattered from B(OH)₃ on B
 only low fluence !
 ne= 4, na= 1, n(dx(1))= 2

E _o (eV)	0°
100	2.05e-4
300	1.90e-4
1000	9.73e-5
3000	2.47e-5

Average depth (mean range) in Å of O implanted in B(OH)₃ on B
 only low fluence !
 ne= 4, na= 1, n(dx(1))= 2

E _o (eV)	0°
100	1.24e+1
300	1.93e+1
1000	3.72e+1
3000	8.41e+1

O -> B(OH)₃ on B₄C

Sputtering yield of B(OH)₃ on B₄C by O

z1 = 8, m1 = 16.00

1.layer: z2= 5 (0.14), 8 (0.43), 1 (0.43), m2= 10.81, 16.00, 1.01,

sbe = 5.90, 2.50, 2.19 eV, sbe(mean) = 1.22 eV, rho = 0.85 g/cm**3

2.layer: z2= 5 (0.80), 6 (0.20), m2= 10.81, 12.01

sbe=5.90, 7.40 eV, sbe(mean) = 6.05 eV, rho= 2.28 g/cm**3

ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1=kdee2=3, ipot=ipotr=1 (KrC)

alpha=0.00, dx(B(OH)3)=2,...20 Å, dx(b4c) = 10000 Å

program: trspvme

only low fluence !

ne= 4, na= 1, n(dx(l))= 7

B (1.layer)

dx (Å)	2	3	4	5	7	10	20
E _o (eV)							
150	1.77e-2	3.96e-2	5.60e-2	5.22e-2	6.69e-2	5.97e-2	
300	2.43e-2	5.45e-2	8.59e-2	9.47e-2	8.11e-2	9.56e-2	9.65e-2
1000	3.02e-2	7.44e-2	1.12e-1	1.20e-1	1.34e-1	1.23e-1	1.46e-1
3000		6.87e-2	1.06e-1	1.34e-1			

O (1.layer)

dx (Å)	2	3	4	5	7	10	20
E _o (eV)							
150	4.20e-2	1.04e-1	1.51e-1	1.55e-1	1.74e-1	1.51e-1	
300	5.91e-2	1.41e-1	2.43e-1	2.43e-1	2.24e-1	2.53e-1	2.38e-1
1000	9.46e-2	1.99e-1	3.28e-1	3.96e-1	3.79e-1	3.20e-1	3.66e-1
3000		2.04e-1	2.97e-1	3.98e-1			

H (1.layer)

dx (Å)	2	3	4	5	7	10	20
E _o (eV)							
150	7.50e-2	1.07e-1	1.34e-1	1.48e-1	1.98e-1	1.85e-1	
300	9.25e-2	1.42e-1	1.88e-1	2.03e-1	2.77e-1	3.35e-1	3.53e-1
1000	1.30e-1	1.75e-1	2.45e-1	2.88e-1	3.74e-1	4.04e-1	5.92e-1
3000		2.02e-1	2.54e-1	2.89e-1			

B (2.layer)

dx (Å)	2	3	4	5	7	10	20
E _o (eV)							
150	4.25e-1	2.62e-1	1.12e-1	3.15e-2	6.55e-3	2.60e-4	
300	6.67e-1	4.45e-1	1.87e-1	7.50e-2	2.21e-2	3.25e-3	
1000	1.00e-0	6.82e-1	3.39e-1	1.75e-1	8.22e-2	2.71e-2	2.95e-3
3000		6.97e-1	3.15e-1	1.86e-1			

C (2.layer)

dx (Å)	2	3	4	5	7	10	20
E _o (eV)							
150	1.10e-1	5.99e-2	2.73e-2	9.58e-3			
300	1.69e-1	1.07e-1	4.28e-2	1.38e-2	5.64e-3		
1000	2.39e-1	1.92e-1	7.56e-2	2.93e-2	1.61e-2	2.85e-3	1.48e-3
3000		1.72e-1	8.03e-2	4.25e-2			

O -> B(OH)₃ on B₄C

Sputtered energy of B(OH)₃ on B₄C by O

zl = 8, ml = 16.00

1.layer: z2 = 5 (0.14), 8 (0.43), 1 (0.43), m2 = 10.81, 16.00, 1.01.

sbe = 5.90, 2.50; 2.19 eV, sbe(mean) = 1.22 eV, rho = 0.85 g/cm**3

2.layer: z2 = 5 (0.80), 6 (0.20), m2 = 10.81, 12.01

sbe = 5.90, 7.40 eV, sbe(mean) = 6.05 eV, rho = 2.28 g/cm**3

ef = 2.10 eV, esb = 2.60 eV, ca = 1.00, kk0 = kk0r = 2, kdee1 = kdee2 = 3, ipot = ipotr = 1 (KrC)

alpha = 0.00, dx(B(OH)₃) = 2, ..., 20 Å, dx(b4c) = 10000 Å

program: trspvmc

only low fluence. 1

ne = 4, na = 1, n(dx(l)) = 7

B (1.layer)

dx (Å)	2	3	4	5	7	10	20
E ₀ (eV)							
150	3.88e-4	7.36e-4	9.02e-4	7.81e-4	1.26e-3	1.22e-3	
300	3.49e-4	6.59e-4	1.02e-3	1.10e-3	9.92e-4	1.28e-3	1.46e-3
1000	2.33e-4	4.75e-4	4.33e-4	6.64e-4	6.69e-4	8.80e-4	9.68e-4
3000		1.60e-4	1.90e-4	2.24e-4			

O (1.layer)

dx (Å)	2	3	4	5	7	10	20
E ₀ (eV)							
150	9.14e-4	1.98e-3	2.57e-3	2.72e-3	3.10e-3	2.74e-3	
300	9.37e-4	1.73e-3	2.52e-3	2.30e-3	2.54e-3	3.34e-3	3.10e-3
1000	7.48e-4	1.19e-3	1.42e-3	1.75e-3	2.18e-3	1.95e-3	2.80e-3
3000		4.04e-4	8.04e-4	7.25e-4			

H (1.layer)

dx (Å)	2	3	4	5	7	10	20
E ₀ (eV)							
150	1.60e-3	2.20e-3	2.62e-3	2.84e-3	3.72e-3	3.28e-3	
300	1.64e-3	2.15e-3	2.82e-3	3.10e-3	3.85e-3	5.33e-3	4.91e-3
1000	1.30e-3	1.62e-3	1.89e-3	2.29e-3	2.44e-3	3.52e-3	5.15e-3
3000		1.16e-3	1.02e-3	9.40e-4			

B (2.layer)

dx (Å)	2	3	4	5	7	10	20
E ₀ (eV)							
150	5.27e-3	3.07e-3	1.22e-3	4.12e-4	1.42e-4	4.65e-6	
300	4.90e-3	3.28e-3	1.52e-3	7.48e-4	3.54e-4	4.00e-5	
1000	3.79e-3	2.31e-3	1.67e-3	1.26e-3	1.17e-3	2.87e-4	9.37e-5
3000		1.35e-3	8.06e-4	1.43e-3			

C (2.layer)

dx (Å)	2	3	4	5	7	10	20
E ₀ (eV)							
100	1.25e-3	6.85e-4	3.05e-4	1.23e-4			
300	1.17e-3	6.81e-4	2.51e-4	1.18e-4	6.86e-5		
1000	7.81e-4	6.70e-4	3.01e-4	3.08e-4	2.14e-4	8.77e-5	6.54e-5
3000		2.51e-4	1.74e-4	1.56e-4			

O -> B(OH)₃ on B₄C

Particle reflection coefficient of O backscattered from B(OH)₃ on B₄C
 z1 = 8, m1= 16.00
 1.layer: z2= 5 (0.14), 8 (0.43), 1 (0.43), m2= 10.81, 16.00, 1.01,
 sbe = 5.90, 2.50, 2.19 eV, sbe(mean) = 1.22 eV, rho = 0.85 g/cm**3
 2.layer: z2= 5 (0.80), 6 (0.20), m2= 10.81, 12.01
 sbe=5.90, 7.40 eV, sbe(mean) =6.05 eV, rho= 2.28 g/cm**3
 ef=2.10 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotrl=1 (KrC)
 alpha=0.00, dx(B(OH)3)=2.....20 A, dx(b4c) = 10000 A
 program: trspvmc
 only low fluence !
 ne= 3, na= 1, n(dx(l))= 7

dx (A)	2	3	4	5	7	10	20
B _o (eV)							
150	7.97e-4	1.40e-3	1.62e-3	1.85e-3	2.07e-3	3.11e-3	
300	1.30e-3	1.63e-3	1.70e-3	3.73e-3	3.08e-3	5.10e-3	3.95e-3
1000					1.61e-3	2.14e-3	1.48e-3

Energy reflection coefficient of O backscattered from B(OH)₃ on B₄C
 only low fluence !
 ne= 3, na= 1, n(dx(l))= 7

dx (A)	2	3	4	5	7	10	20
B _o (eV)							
150	4.63e-5	5.57e-5	8.40e-5	5.51e-5	8.93e-5	1.43e-4	
300	5.85e-5	8.70e-5	4.52e-5	1.66e-4	1.93e-4	2.40e-4	1.91e-4
1000					3.41e-5	3.28e-5	4.23e-5

Average depth (mean range) in Å of O implanted in B(OH)₃ on B₄C
 only low fluence !
 ne= 4, na= 1, n(dx(l))= 7

dx (A)	2	3	4	5	7	10	20
E _x (eV)							
150	9.48e+0	9.91e+0	1.06e+1	1.15e+1	1.28e+1	1.45e+1	
300	1.44e+1	1.48e+1	1.55e+1	1.64e+1	1.76e+1	1.94e+1	2.53e+1
1000	3.36e+1	3.28e+1	3.27e+1	3.45e+1	3.59e+1	3.77e+1	4.36e+1
3000		7.56e+1	7.72e+1	7.86e+1			

O -> O on WO₃

Sputtering yield of O on WO₃ by O

z1 = 8, m1 = 16.00

layer 1: z2= 8, m2= 16.00, sbe=2.60 eV, rho=1.14 g/cm**3

layer 2: z2= 74 (0.25), 8 (0.75), m2=183.85, 16.00, dx=10000 A, sbe = 6.28, 6.28 eV, rho=6.47 g/cm**3

ef=2.50 eV, esb=2.60 eV, ca=1.00, kk0=kk0r=2, kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

program: trspvme

only low fluence !

ne= 3, na= 1, n(dx1)= 2

O (1.layer)

dx (Å)	1	5
B _o (eV)		
1000	8.71e-2	6.85e-1

W (2.layer)

dx (Å)	1	5
E _o (eV)		
1000	8.29e-2	4.30e-2

O (2.layer)

dx (Å)	1	5
B _o (eV)		
1000	8.72e-1	2.98e-1

Sputtered energy of O on WO₃ by O

only low fluence !

ne= 3, na= 1, n(dx1)= 2

O (1.layer)

dx (Å)	1	5
B _o (eV)		
1000	2.72e-3	9.07e-3

W (2.layer)

dx (Å)	1	5
B _o (eV)		
1000	7.57e-4	4.28e-4

O (2.layer)

dx (X)	1	5
E _o (eV)		
1000	2.06e-2	1.00e-2

Particle reflection coefficient of O backscattered from O on WO₃

only low fluence !

ne= 3, na= 1, n(dx1)= 2

dx (Å)	1	5
B _o (eV)		
1000	7.87e-2	7.51e-2

Energy reflection coefficient of O backscattered from O on WO₃

only low fluence !

ne= 3, na= 1, n(dx1)= 2

dx (Å)	1	5
B _o (eV)		
1000	2.27e-2	1.74e-2

Average depth (mean range) in Å of O implanted in O on WO₃

only low fluence !

ne= 3, na= 1, n(dx1)= 2

dx (Å)	1	5
B _o (eV)		
1000	3.44e+1	3.47e+1

O -> WO₃ on W

Sputtering yield of WO₃ on W by O

z1 = 8, m1 = 16.00

1.layer: z2=74 (0.25), 8 (0.75), m2=183.85, 16.00, sbe = 6.28, 6.28 eV, rho = 6.47 g/cm**3

2.layer: z1= 74, m2=183.85, sbe = 8.68 eV, rho = 19.30 g/cm**3

ef=2.50 eV, esb=2.60 eV, ca=1.00, kkO=kkOr=2. kdee1 = kdee2=3, ipot=ipotr=1 (KrC)

alpha=0.00, dx(1) =thickness of 1.layer

program: trspvmc

only low fluence. !

ne= 9, na= 1, n(dx) = 3

W (1.layer)

dx (Å)	10	15	25
E _o (eV)			
50			7.71e-5
100		1.74e-3	1.66e-3
200	8.86e-3		
300	1.88e-2		
500	4.09e-2	2.93e-2	2.00e-2
1000	8.79e-2	6.40e-2	6.01e-2
2000	1.36e-1		
5000	1.38e-1	1.46e-2	
6000	1.80e-1		

O (1.layer)

dx (Å)	10	15	25
E _o (eV)			
50			3.99e-2
100		1.19e-1	1.19e-1
200	2.67e-1		
300	3.85e-1		
500	5.57e-1	4.87e-1	4.02e-1
1000	7.14e-1	6.78e-1	6.25e-1
2000	7.94e-1		
5000	7.04e-1	9.04e-1	
6000	7.09e-1		

W (2.layer)

dx (Å)	10
E _o (eV)	
200	6.19e-6
300	3.09e-4
500	1.63e-3
1000	8.24e-3
2000	2.54e-2
5000	5.53e-2
6000	6.77e-2

Sputtered energy of WO₃ on W by O

only low fluence. !

ne= 9, na= 1, n(dx)= 3

W (1.layer)

dx (Å)	10	15	25
E _o (eV)			
50			2.75e-6
100		7.97e-5	9.25e-5
200	3.52e-4		
300	6.02e-4		
500	1.11e-3	8.38e-4	5.71e-4
1000	1.76e-3	1.03e-3	1.22e-3
2000	1.99e-3		
5000	1.28e-3	1.50e-3	
6000	1.56e-3		

O (1.layer)

dx (Å)	10	15	25
E _o (eV)			
50			6.29e-3
100		1.37e-2	1.36e-2
200	2.14e-2		
300	2.69e-2		
500	3.25e-2	2.57e-2	2.24e-2
1000	3.54e-2	2.71e-2	2.37e-2
2000	2.71e-2		
5000	1.59e-2	1.92e-2	
6000	1.25e-2		

W (2.layer)

dx (Å)	10
E _o (eV)	
200	7.37e-8
300	4.94e-6
500	2.70e-5
1000	7.52e-5
2000	3.90e-4
5000	8.52e-4
6000	8.79e-4

O > WO₃ on W

Particle reflection coefficient of O backscattered from WO₃ on W
 z1 = 8, m1 = 16.00
 1.layer: z2=74 (0.25), 8 (0.75). m2=183.85, 16.00, sbe=6.28, 6.28 eV. rho=6.47 g/cm**3
 2.layer: z1= 74. m2=183.85. sbe=8.68 eV. rho=19.30 g/cm**3
 ef=2.50 eV. esb=2.60 eV, ca=1.00. kk0=kk0r=2. kdee1=kdee2=3. ipot=ipot=1 (KrC)
 alpha=0.00. dx(l)=thickness of l.layer
 program: trspvme
 only low fluence !
 ne= 9, na= 1, n(dx)= 3

dx (A)	10	15	25
E ₀ (eV)			
50			1.33e-1
100			1.31e-1
200	1.47e-1	1.31e-1	
300	1.71e-1		
500	2.15e-1	1.47e-1	1.19e-1
1000	2.67e-1	1.95e-1	1.27e-1
2000	3.14e-1		
5000	3.12e-1	3.03e-1	
6000	3.01e-1		

Energy reflection coefficient of O backscattered from WO₃ on W
 only low fluence !
 ne= 9, na= 1, n(dx)= 3

dx (A)	10	15	25
E ₀ (eV)			
50			5.30e-2
100		4.84e-2	4.90e-2
200	4.71e-2		
300	5.07e-2		
500	5.95e-2	4.16e-2	4.01e-2
1000	8.66e-2	5.62e-2	3.80e-2
2000	1.08e-1		
5000	1.14e-1	1.09e-1	
6000	1.13e-1		

Average depth (mean range) in Å of O implanted in WO₃ on W
 only low fluence !
 ne= 9, na= 1, n(dx)= 3

dx (A)	10	15	25
E ₀ (eV)			
50			5.30e-10
100		8.10e4-0	8.17e+0
200	1.11e+1		
300	1.41e+1		
500	1.92e+1	1.86e4-1	2.01e4-1
1000	2.86e+1	2.82e-1-1	2.96e-f-1
2000	4.75e+1		
5000	8.05e+1	7.63e+1	
6000	9.80e+1		